AMI.

1980 MOS Products Catalog

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MOS Products Catalog

American Microsystems, Inc., the first commercial producer of MOS/LSI beginning in 1966, is a major designer, manufacturer and marketer of circuits for the consumer, EDP and communications markets.

AMI is the leading designer of custom LSI, makes and markets its proprietary S2000 family of 4-bit microcomputers, is a major alternate source for the S6800 8-bit microprocessor family and the only alternate source for the S9900 16-bit family of microprocessors. The Company provides the market with selected 1K and 4K low power CMOS Static RAMs, 16K and 32K ROMs.

The most experienced designer of systems-oriented MOS/LSI communication circuits, AMI provides components for station equipment, PABX and Central Office Switching systems, data communications and advanced signal processing applications.

AMI is pioneering in same-chip integration of digital and analog circuitry, and is a recognized leader in switched capacitor filter technology.

Processing capability includes N-Channel, advanced silicon gate CMOS and the largest production capability available in P-Channel.

Headquartered in Santa Clara, California, AMI has design centers in Santa Clara, Pocatello, Idaho and Swindon, England. Wafer fabricating plants are in Santa Clara and Pocatello, and assembly facilities are in Seoul, Korea and the Philippines.

Field sales offices are located throughout the United States, in Europe and in the Far East. Their listing, plus those of domestic and international representatives and distributors appear on pages B.27 through B.31 of this publication.

AMI.

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S2559A	—	—	—	MK-5086(D)	—	—
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S2559C	—	—	—	MK-5086(D), MK-5087(F)	—	—
S2559D	—	—	—	—	—	—
S2560A	AY-5-9151(F), AY-5-9152(F)	—	MT-4320(F)	MK-5098(F), MK-5099(F)	—	MM-5393(F), MM-53190(F)
S2561	—	—	—	—	—	—
S2561A	—	—	ML-8204(F)	—	—	—
S2561C	—	—	—	—	—	—
S2562	TZ-2001(F)	—	—	MK-5170(F)	—	—
S2859	—	—	—	—	—	—
S2860	—	—	—	MK-5089(F)	—	—
S2861A	—	—	—	MK-5087(F)	—	—
S2861B	—	—	—	—	—	—
S3501/S3502	—	2910/2912(F)	—	MK-5151(FC)	MC-14406/14414(F)	—
S3503/S3504	—	2911/2912(F)	—	MK-5156(FC)	MC-14407/14414(F)	—
S3525A/B	—	—	MT-8865(F)	—	—	—

Memory Products

Vendor	CMOS RAMs					NMOS ROMs		
	256×4	1K×1	1K×4	4K×1		2K×8	4K×8	8K×8
AMI	S5101	S6508	S6514*	S6504*		S6831B	S68332	S68364*
AMD	—	—	—	—		9216	9232	—
EA	—	—	—	—		8316	2332	—
FSC	—	—	—	—		3516	—	—
FUJITSU	—	—	8414	8404		—	—	—
GI	—	—	—	—		9316	9332	9364
HARRIS	6561	6508	6514	6504		—	—	—
HITACHI	435101	—	4334	4315		—	—	—
INTEL	5101	—	—	—		2316	2332	2364
INTERSIL	6551	6508	6514	6504		—	—	—
MARUMAN	—	—	—	—		2316	2332	2364
MITSUBISHI	—	—	—	—		58731	58733	—
MOSTEK	—	—	—	—		34000	—	37000
MOTOROLA	145101	146508	—	146504		68316	68332	68364
NATIONAL	74C920	74C929	—	6504		2316	52132	52164
NEC	5101	6508	444	—		2316	2332	2364
OKI	573	574	—	—		3870	—	—
RCA	5101	1821	1825	5104		—	—	—
ROCKWELL	—	—	—	—		2316	—	—
SIEMENS	—	—	—	—		8316	8332	—
SIGNETICS	—	—	—	—		2600	2632	2664
SGS	—	—	—	—		2316	—	—
SSS	5101	5102	—	—		—	—	—
SYNERTEK	5101	5102	—	—		2316	2332	2364
TI	—	—	—	—		8316	4732	4764
TOSHIBA	5101	5508	5514	5504		331	333	—

*To Be Announced

AMI®

S6800 Family

AMI	Fairchild	General Instruments	Hitachi	Motorola	National	Texas Instruments
S1602	—	AY-3-1014	—	—	MM5303N	TMS6011
S2350	—	—	—	—	—	—
S6800	F6800	—	HD46800	MC6800	—	—
S6801	—	—	—	MC6801	—	—
S6802	F6802	—	HD46802	MC6802	—	—
S6805	—	—	HD46805	MC6805	—	—
S6808	F6808	—	HD46808	MC6808	—	—
S6809	—	—	—	MC6809	—	—
S6810	F6810	—	HD46810	MC6810	—	—
S6821	F6821	—	HD46821	MC6821	—	—
S6840	F6840	—	HD46840	MC6840	—	—
S6846	F6846	—	HD46846	MC6846	—	—
S6850	F6850	—	HD46850	MC6850	—	—
S6852	F6852	—	HD46852	MC6852	—	—
S6854	F6854	—	HD46854	MC6854	—	—
S68488	F68488	—	HD468488	MC68488	—	—
S6894	—	—	—	—	—	—
S68045	—	—	—	—	—	—
S68047	—	—	—	—	—	—

S9900 Family

AMI	Texas Instruments
S9900	TMS9900
S9901	TMS9901
S9902	TMS9902
S9903	TMS9903
S9940	TMS9940
S9980	TMS9980
S9981	TMS9981

AMI's Six Step Program for Success in Custom LSI.

No other company can match AMI's track record in developing state-of-the-art custom MOS products. With more than 1,400 custom devices designed and manufactured since 1967, AMI has more experience than any other integrated circuit company in building a wide variety of custom microcircuits.

AMI not only has the experience but the design engineering organization and the advanced production and testing facilities to produce the highest quality MOS/LSI circuits. Because AMI also offers standard memory, microprocessor, telecommunication and consumer products and the widest variety of custom LSI processes in the industry, we're able to be objective in helping customers determine their most cost effective approach.

AMI can participate at any level of the custom LSI process.

We participate at any level in the design of the custom IC, from the classic "we'll-design-and-produce-it-for-you" approach where we have complete responsibility, to the "Customer Tooling" cooperative approach for customers who do their own design but want us to do the manufacturing. We will even enter into long-term, fully-funded joint development agreements, designing ICs for families of end products, joining together your systems designers with our circuit designers.

We've developed a six step program in which you, the customer, can work with us to successfully develop the custom IC for your product by:

1. Considering All the Factors.
2. Looking At the Custom Options.
3. Selecting the Right MOS/LSI Process.
4. Designing The Best Circuit.
5. Fabricating the Optimum Device.
6. Testing For Reliable Performance.

The results are a unique product designed to your complete satisfaction.

Step One: Considering all the Factors.

There are many ways to build your product, so, why do we believe the custom MOS/LSI approach is right for you? For the answer let's look at the alternatives:

Electromechanical. These assemblies suffer compared to MOS circuits: in reliability because moving parts wear; in convenience because of the greater space needed; and because of their limits in handling highly complex functions.

Hardwired Logic. This is more expensive due to the high labor and material cost involved. Much space is needed and power is much higher than for MOS/LSI circuits.

Standard Circuits. Standard ICs perform the same jobs as custom ICs but require more devices, higher assembly costs, more power and space with lower reliability.

Microprocessors. Using standard microprocessors requires several microcircuits, and much of the device's capability may not be needed. A custom circuit, however, can combine all your needed functions on one IC, conserving space and cost.

The custom MOS/LSI decision

The advantages of custom MOS/LSI circuits become more apparent when considered in relation to IC complexity, component count, power consumption and confidentiality (it's your circuit exclusively).

Complexity. An application suitable for custom LSI is usually one needing moderately complex circuits or functions; i.e., more than 100 to 500 gates. Fewer than this might not justify the engineering, design, and manufacturing effort required for the custom IC.

Custom LSI may be the only way technically to achieve a desired result, no matter what the development cost.

Component Count. An important consideration affecting cost is the number of components in a system that are eliminated by the substitution of a single custom LSI circuit. A reduction in component count significantly lowers the number of electrical interconnections and increases product reliability.

This factor often reduces troubleshooting problems at the board, subsystem and system levels, minimizes field

repairs and usually reduces warranty costs. The reduction in component count also decreases assembly and initial checkout costs.

Power Consumption. The amount of power required to operate an end product is increasingly an important consideration. MOS/LSI circuits require much less power than the electro-mechanical and hardwired logic alternatives. A custom MOS/LSI solution usually requires less power than the multi-chip alternatives offered by standard circuits and microprocessors. For battery operated designs, we offer custom, high performance/ultra-low power complementary MOS (CMOS) capability.

Confidentiality. Of prime concern in any highly competitive market situation is confidentiality of design. AMI treats each circuit assignment as a highly proprietary project insuring complete security to, and through, the product's manufacturing life.

Step Two: Looking at the Custom Options.

There are two basic ways AMI teams up with its customers, although we are very flexible:

☐ AMI designs and makes the circuit to meet customer requirements; or,

☐ the customer designs the IC with AMI assistance and AMI produces it.

The total AMI approach

AMI's custom capability encompasses the entire development sequence of a product. The services we provide start with five conceptual planning steps:

☐ System Definition;

☐ System Design and Partitioning;

☐ Preliminary Logic Design/Simulation;

☐ Final Logic Design; and

☐ LSI Circuit Design.

First, system definition requires the customer to have full knowledge of the system requirements for the custom IC. Working with AMI's application engineers, the two companies form a team to develop a final system which not only meets the needs, but optimizes performance and economics.

Second, system partitioning follows the joint development of system definition. This involves the cataloging of functions into MOS subfunctions, and then into chip

functions. At this step the optimum MOS process for the application is chosen. Usually, functional flow charts and timing diagrams are generated at this time as a preliminary step in logic design.

Once partitioning is complete, preliminary logic design and simulation can be done. The chip functions are translated into MOS logic diagrams. Traditional breadboarding techniques are quite often used to verify these logic designs. AMI uses proprietary computerized simulation programs for verification. These programs check the design as well as help reduce time and cost factors for design verification.

Final logic design is next. First, system errors discovered through breadboarding or simulation are corrected. Earlier partitioning may be refined if the final logic design indicates the need. During the final logic design step all system design objectives are analyzed again. MOS logic diagrams are finalized, the chip sizes are estimated, and testing procedures are generated.

And then—the chip design. The topological chip layout is a precise science. The exact dimensions and placement for each transistor and other components must be determined. Here again AMI uses computerized circuit analysis programs to validate chip designs and verify that the design meets the performance objectives. The computerized analysis not only substantiates logic, it is an integral part of the on-going quality assurance program at AMI.

The cooperative approach

In this approach, the customer designs the circuit and has complete control over the logic and electrical requirements, the design budget and schedule, and the design changes prior to tooling.

Design workshops, consultation and information documentation packages are provided by us depending on the needs of the customer. We divide our customer interfacing into four phases: **Phase 1** is a feasibility study; **Phase 2** is a preliminary wafer fabrication or sample run; **Phase 3**, pre-production yield evaluation; and **Phase 4**, production.

Phase 1 begins before MOS logic is drawn. AMI customer tooling engineers provide suggestions on MOS design, discuss process and design rule parameters, provide a standard device, help plan ahead for testing, and provide information on packaging and tooling interface.

Our experience has shown that the customer tooling interface works best when the customer is aware from the

start of how we will make the device. If it's already been designed, Phase 1 begins when AMI provides a process and design rule questionnaire. This gives us information about packaging requirements, testing needs and tooling interface level. Our customer tooling experts review the data to see if AMI can meet all the requirements. At the end we supply at no charge a program plan, a firm quotation for the next two phases, and a budget quote for production.

During **Phase 2** we'll process one wafer lot and then map, optically inspect, package and ship sample quantities of untested ICs, and, if the customer requires them, several untested wafers. Furthermore, AMI guarantees these samples will be within the agreed parameters and will meet our standards of quality and workmanship. The customer can supply working plates for Phase 2, or AMI will accept pattern generator tapes or 10x reticles.

After the customer approves the Phase 2 sample devices, AMI moves to **Phase 3**: pre-production yield evaluation. Here we guarantee the required manufacturing documentation, run acceptances on the test program, and build the wafer probe cards and the program board for AMI testers. We then make several reproducibility runs of wafers and sort them for yield information.

From these runs AMI engineers will assemble and final test a number of good devices. The unit cost for them will be based on the costs of assembly, type of package and final test. These units provide the customer with a low volume production run for additional evaluation and start-up production commitments.

Pre-production deliveries actually start during Phase 3. Initial production deliveries during **Phase 4** usually begin 9 to 11 weeks after approval of the pre-production units.

. . . But there are other options

We're not biased particularly in favor of custom LSI, especially if it becomes clear it's not the best way to solve a customer problem. AMI is also a major microprocessor supplier in the 4-, 8-, and 16-bit categories: our own family of S2000 single chip microcomputers, the Motorola-designed 6800, and Texas Instrument's 9900 product line, respectively.

By having available both custom LSI and standard microprocessors, we can offer customers alternatives that can also combine the two. For example, to test the market for a new product, we can design a microprocessor-based system which provides a relatively quick, though not necessarily cost effective way to get a product to market. As part of the approach, we customize the microprocessor program or "software," and then, if

the product is successful, design and make a custom LSI circuit dedicated to that particular application.

But if a microprocessor—ours or anyone else's—is the best solution, custom LSI is still useful, for microprocessors can't operate alone. They need interface devices. To achieve a system with a minimum chip count, custom devices can be designed to allow the customer to efficiently interface standard microprocessors with the customer's system.

Step Three: Choosing the right MOS/LSI process.

One of the most important decisions to be made in the custom LSI approach is determining the right MOS/LSI process.

Where many of our competitors offer one, and possibly two MOS processes with which to build devices, AMI offers seven custom MOS process options, more than any other company supplying custom circuits. They are:

P-channel high voltage metal gate

This is the most mature process in the industry and because of its relative simplicity, has the lowest cost per wafer. It provides high noise immunity, making it ideal for applications involving mechanical equipment which can generate RF noise and where low power dissipation is not a prime requirement.

P-channel ion implanted metal gate

This is very similar to its high voltage P-channel process, with two additional processing steps. An ion implantation of the gate areas reduces the device thresholds to levels consistent with the low voltage P-channel process while at the same time retaining the high field thresholds of the high voltage process.

A second ion implant in selected gate regions reduces those thresholds to the point of forcing depletion mode transistor operation. The use of depletion mode devices as load transistors greatly increases device speed per unit area, can lower power, improve noise margins, makes bipolar interfacing easier, permits the use of unregulated power supplies, and allows generation of full amplitude signals on chip with only one power supply. This latter feature can be especially useful in converting certain logic implementations to much simpler forms which thereby reduce chip area significantly. This process has been used in several different standard memory products as well as many custom chip applications where speed, noise immunity and wide power supply tolerances are specified.

P-channel silicon gate (SiGate)

This process has two main features: (1) somewhat smaller transistor structures due to a self-aligning fabrication technique that eliminates certain masking tolerance problems, and (2) a partial third layer of interconnect which can sometimes significantly reduce cell area and interconnections between cells. The self-aligning gate structure lowers the effective gate capacitance. The circuit response is faster than regular P-channel low voltage devices, but slower than ion implanted circuits with depletion mode load devices. This process has been mostly used in memory applications and in customer tooled circuits. AMI no longer designs products in this process.

N-channel silicon gate

This process uses ion implantation in the field areas to achieve high field threshold without having to resort to thick field oxides. Then the gate regions are implanted to establish the required control of device thresholds. This process is designed for single supply circuits that do not have stringent performance requirements but must have significant packing densities. This packing density results from the following: (1) for a given device N-channel can charge or discharge a mode faster than P-channel, (2) the self-aligning feature of the process, and, (3) the extra layer of interconnect inherent in silicon gate which can be used to reduce chip interconnect area.

N-channel ion implanted SiGate with depletion loads

This is a high performance process; it offers all the advantages of the N-channel, ion implanted SiGate process plus the increased speed associated with depletion loads. The drawback to this process lies in the increased complexity of the additional processing steps.

Complementary MOS (CMOS)

The CMOS technology has many advantages. Its biggest asset is that CMOS draws very little power. The majority of the power is consumed when switching occurs. Under static conditions or during power down CMOS dissipates virtually no DC power. CMOS is also very fast, and it has very high noise immunity, comparable to ion implanted circuits using depletion mode transistors. Like ion implanted depletion mode circuits, CMOS can work over a very wide single supply power range. The area used per logic function has been larger than with

other processes, but this is decreasing with advanced CMOS techniques. CMOS chips are currently used in low power, often battery operated applications such as electronic watches, clocks, and memories where the ability to work at very low power is an absolute requirement, and in automotive electronics, where low standby current and high noise immunity are important. CMOS is also making important inroads into microprocessors and communications circuitry.

Present CMOS technologies include both standard metal gate and silicon gate, as well as a high density, isoplanar silicon gate process.

Five-Micron CMOS

AMI's major second generation 5-micron CMOS process uses an n+ only ubiquitous P-well approach to improve performance, simplify layout and reduce circuit size. This process permits implanting in the field oxide region, thus eliminating guard rings. AMI's process also reduces P-well doping levels below alternative 5-micron processes and consequently lowers junction capacitances and increases switching speeds.

We use this 5-micron process to design and produce switched capacitor circuits for analog and digital functions. Among the kinds of circuits that can benefit enormously from mixed digital-analog approaches are low-noise, high-gain op amps, high-speed offset-cancelled comparators and high-current line buffers. CMOS linear subsystems have appeared on AMI-designed circuits to perform A to D and D to A conversion, switched capacitor filtering and quasi-adaptive phase lock and auto-zero loops. System level integrated circuits have been designed and fabricated for complex filter functions, DTMF, MF and SF receivers, low and medium speed modems, codecs, voice compression, industrial control and voice synthesis.

Step Four: Designing the best circuit.

A key to AMI's success in the custom LSI business is its Computer-Aided Design (CAD) capability. Our CAD capabilities, the most advanced in the semiconductor industry, are based on a wealth of experience in custom MOS/LSI circuit design work. CAD software and hardware aids are employed throughout the custom IC development cycle, from the early logic design stage to creation of production tooling.

Logic Simulation

Early in the design phase logic simulation is used to verify that the logic is sound. The circuit is extensively simulated to verify logical correctness as well as timing and signal propagation characteristics. Logic simulation is used throughout the design cycle from hierarchical block-level logic design to test program generation.

SIMAD is an MOS oriented four-state logic simulator which supports assignable rise and fall switching delay. It includes such features as:

☐ block-oriented input notation, including macros, Boolean expressions, and array notation;

☐ basic logic gates, several types of MOS transmission gates, RAMs, ROMs, shift-registers, and user specified combinational logic gates;

☐ four-state (ϕ, 1, u, z) simulation;

☐ multi-phase user specified clocking schemes;

☐ assignable rise and fall delay;

☐ race detection and inertial delay simulation;

☐ versatile input, output, and simulation control options;

☐ checkpoint-restart capability;

☐ accurate initialization algorithm;

☐ extensive compression and formating of simulation results for automatic test equipment.

Circuit simulation

At the circuit design phase, a circuit simulator containing semiconductor device models is used to identify undesirable circuit behavior. Exact circuit behavior is simulated and the results are used to insure the circuit will operate within allowable tolerances.

The ASPEC circuit simulator can perform non-linear DC, non-linear DC transfer function, non-linear transient and small signal (linear) AC circuit analysis. Built-in component models include independent voltage and current sources; linear elements such as resistance, inductance, capacitance, transconductance, voltage controlled switches and coupled-inductors. Non-linear transistor models for junction field effect transistors (JFETs), MOSFETs, and bipolar junction transistors (BJT) are also available.

The MOSFET model simulates linear and saturation region DC operation; body effect as a function of substrate bias; channel length modulation in saturation; mobility reduction at elevated gate voltages; channel pinchoff; short channel effects; weak inversion; as well as full non-linear voltage-dependent modeling of the MOS capacitors which determine device transient behavior.

Symbolic mask design using SIDS

AMI has developed an advanced symbolic mask design system for MOS ICs. This Symbolic Interactive Design System (SIDS) reduces the total mask design cycle time as much as 50 percent, with half the manpower effort and half the cost of the hand drawn approach. SIDS eliminates hand drafting by using symbols to represent complex multi-level circuit elements.

SIDS circuit masks are designed symbolically on an interactive color CRT terminal. The mask design process is supported by such checking aids as:

☐ Design Rule Checking (DRC) which checks for all symbol-to-symbol layout violations;

☐ TRACE, which traces a circuit node and visually highlights the node on the color CRT terminal so the user can observe circuit continuity errors.

☐ CONTINUITY, which generates a net list from a logic description file, compares it to a net list traced from the symbolic layout, and prints out any continuity differences.

The final SIDS step is the conversion from symbols to polygons (STP) and the generation of the pattern generation (PATGEN) tape.

Hardware design aids

☐ On-site Burroughs 7765 large scale computer with multiprocessing capability.

☐ Prime minicomputers in Santa Clara, Pocatello and Swindon, England.

☐ A Calma GDSII interactive graphics system for digitizing and editing of composite drawings; includes 3 digitizing surfaces and 4 CRT edit stations.

☐ High speed, high resolution Electromask pattern generator.

☐ Versatec 42 inch high speed electrostatic plotter.

☐ Calcomp 748 Flatbed Plotter.

Software design aids

- ☐ ASPEC Circuit Simulator
- ☐ Semiconductor device models tailored to AMI processes
- ☐ Tides Logic Simulator for:
  - — Logic Validation
  - — Pattern Validation
  - — Test Word Generation
- ☐ SIDS for mask design
- ☐ Geometrical Design Rule Checking (DRC) for hand drawn circuits
- ☐ Trace and continuity checking for hand drawn circuits
- ☐ Device test program development aids

Step Five: Fabricating the optimum device.

A partnership

AMI's long history of success in the custom MOS/LSI business is the result of a close, working partnership between AMI and each of our customers.

These customers have taken advantage of orders of magnitude increases in circuit complexity over the years, thereby reducing even further the component count in their systems.

The flexibility of AMI's development program allows the customer to select the interface point best suited to his particular needs. The most common interface points are noted as (*) in the review of the sequence of steps involved in developing a custom MOS/LSI circuit below:

1. System Definition Design (*)
2. Preliminary logic design and simulation(*)
3. Final logic design and system design review
4. Chip circuit design
5. Topological design
6. Artwork generation (*)
7. Mask fabrication (*)
8. Wafer fabrication and map test
9. Wafer sort test (*)
10. Final test and characterization
11. Product assurance tests

Step Six: Testing for reliable performance

Currently more than 50% of the custom LSI circuits designed by AMI work the first time. The key to this impressive record is a comprehensive program of quality assurance, rigorous testing and constant double checking of each step.

It starts at the initial stages of logic design, with the custom LSI chip designed to incorporate facilities for ease of testing and ends with prototype debugging.

Common test data base

To facilitate the processing of vast quantities of test data, a base of parametric and functional information with run, wafer or die resolution has been created by AMI engineers.

With this data analysis system, each user creates a personal data base secured by user code and information inputted from magnetic tape, cards or remote terminals. Using an interactive command language for manipulation of data, subsets of test information can be retrieved and listed through the use of key attributes—test group, process, product number, test date, test time at start, operator ID, save data, run or lot number. The retrieved data base subset can be analyzed statistically as: histograms, scatter plots, wafer maps, trend charts, tabulations of percentiles, means, standard deviations and correlation coefficients.

Extensive test facilities

AMI maintains fourteen Fairchild Sentry II and 600 automated test systems, plus a wide range of other testers for debugging of protypes, solving design and testing problems and production testing.

Quality assurance

An on-going activity that pervades the entire design and manufacturing process is AMI's quality assurance program. This includes a special group of inspectors organizationally separate from the production group, whose main responsibility is to examine and test the custom LSI circuits and all the raw materials that go into them. Some of the quality control checkpoints include:

- ☐ final logic design where system objectives are reviewed;

☐ chip circuit design, where it is verified that performance meets objectives;

☐ working plates check;

☐ mask fabrication check;

☐ wafer fabrication check;

☐ wafer sort;

☐ scribe and break with 100% optical inspection;

☐ die attach checks;

☐ lead bonding followed by 100% preseal optical inspection;

☐ seal checks;

☐ final tests; and,

☐ final electrical/environmental tests.

At each one of these pre-production steps meticulous checks of both design and workmanship are made. And only after the checks at each of these steps are completed is a device considered fully manufacturable. It is then turned over to production with its yield history. In production a similar series of quality control checks is made.

Custom MOS/LSI from AMI

The information in this section has been presented to show not only how and why custom can be used, but also to explain the types of custom services available at AMI, and the level of commitment at AMI to total custom circuit development and to customer tooling processing. If your application can benefit from high quality custom MOS/LSI circuits, AMI is the place to go for design, engineering, manufacturing, and testing capability. To get in contact with AMI Custom, just complete the inquiry card at the back of this catalog.

AMI
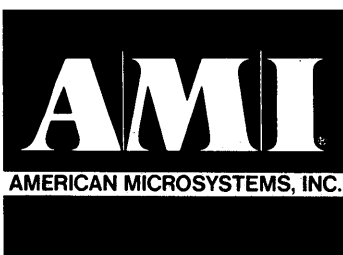
Communication Products

STATION PRODUCTS

Part No.	Description	Process	Power Supplies	Packages
S2559A/B	Digital Tone Generator	CMOS	3.5V to 13V	16 Pin
S2559C/D	Digital Tone Generator	CMOS	2.75V to 10V	16 Pin
S2859	Digital Tone Generator	CMOS	3.0V to 10.0V	16 Pin
S2860	Digital Tone Generator	CMOS	3.5V	16 Pin
S2861A/B	Digital Tone Generator	CMOS	2.5V to 10.0V	16 Pin
S2560A/B	Pulse Dialer	CMOS	1.5V to 3.5V	18 Pin
S2561, S2561C	Tone Ringer	CMOS	4.0V to 12.0V	18 Pin
S2561A	Tone Ringer	CMOS	4.0V to 12.0V	8 Pin
S2562	Repertory Dialer	CMOS	3.5V to 7.5V	40 Pin

PCM PRODUCTS

Part No.	Description	Process	Power Supplies	Packages
S3501/S3501A	μ-Law Encoder with Filter	CMOS	±5V	18 Pin
S3502/S3502A	μ-Law Decoder with Filter	CMOS	±5V	16 Pin
S3503	A-Law Encoder with Filter	CMOS	±5V	18 Pin
S3504	A-Law Decoder with Filter	CMOS	±5V	16 Pin

OTHER PRODUCTS

S2811	Signal Processing Peripheral	VMOS	5V	28 Pin
S2814	Fast Fourier Transformer	VMOS	5V	28 Pin
S3525A/B	DTMF Bandsplit Filter	CMOS	10.0V to 13.5V	18 Pin

AMI
AMERICAN MICROSYSTEMS, INC.

S2559A/B/C/D

DIGITAL
TONE GENERATOR

COMMUNI-
CATIONS

Features

- [ ] **Wide Operating Supply Voltage Range: 3.5 to 13.0 Volts (A, B) 2.75 to 10 Volts (C, D)**
- [ ] **Low Power CMOS Circuitry Allows Device Power to be Derived Directly from the Telephone Lines or from Small Batteries, e.g., 9V**
- [ ] **Uses TV Crystal Standard (3.58 MHz) to Derive all Frequencies thus Providing Very High Accuracy and Stability**
- [ ] **Mute Drivers On Chip**
- [ ] **Interfaces Directly to a Standard Telephone Push-Button or Calculator Type X-Y Keyboard**
- [ ] **The Total Harmonic Distortion is Below Industry Specification**
- [ ] **On Chip Generation of a Reference Voltage to Assure Amplitude Stability of the Dual Tones Over the Operating Voltage and Temperature Range**
- [ ] **Dual Tone as Well as Single Tone Capability**
- [ ] **Four Options Available:**
     A:3.5 to 13.0V Mode Select
     B:3.5 to 13.0V Chip Disable
     C: 2.75 to 10V Mode Select
     D: 2.75 to 10V Chip Disable

General Description

The S2559 Digital Tone Generator is specifically designed to implement a dual tone telephone dialing system. The device can interface directly to a standard pushbutton telephone keyboard or calculator type X-Y keyboard and operates directly from the telephone lines. All necessary dual-tone frequencies are derived from the widely used TV crystal standard providing very high accuracy and stability. The required sinusoidal waveform for the individual tones is digitally synthesized on the chip. The waveform so generated has very low total harmonic distortion. A voltage reference is generated on the chip which is stable over the operating voltage and temperature range and regulates the signal levels of the dual tones to meet the recommended telephone industry specifications. These features permit the S2559 to be incorporated with a slight modification of the standard 500 type telephone basic circuitry to form a pushbutton dual-tone telephone. Other applications of the device include radio and mobile telephones, remote control, Point-of-Sale, and Credit Card Verification Terminals and process control.

Block Diagram

Pin Configuration
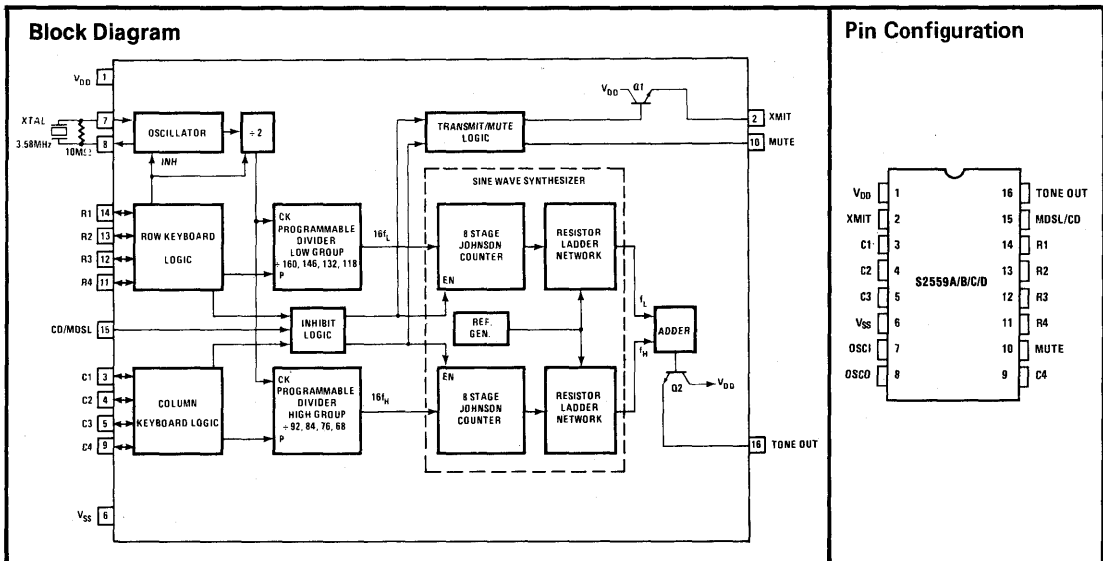
Absolute Maximum Ratings

DC Supply Voltage ($V_{DD} - V_{SS}$) S2559 A, B .... +13.5V

DC Supply Voltage ($V_{DD} - V_{SS}$) S2559 C, D .... +10.5V

Operating Temperature .... $-25°C$ to $+70°C$

Storage Temperature .... $-55°C$ to $+125°C$

Power Dissipation at 25°C 500mW

Input Voltage .... $-0.6 \leqslant V_{IN} \leqslant V_{DD} + 0.6$

S2559A & B Electrical Characteristics:

(Specifications apply over the operating temperature range of $-25°C$ to $70°C$ unless otherwise noted. Absolute values of measured parameters are specified.)

Symbol	Parameter/Conditions		$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	Supply Voltage						
V_{DD}	Tone Out Mode (Valid Key Depressed)			3.5		13.0	V
	Non Tone Out Mode (No Key Depressed)			3.0		13.0	V
	Supply Current						
I_{DD}	Standby (No Key Selected, Tone, XMIT		3.5		0.4	40	μA
	and MUTE Outputs Unloaded)		13.0		1.5	130	μA
	Operating (One Key Selected, Tone, XMIT		3.5		0.95	2.9	mA
	and MUTE Outputs Unloaded)		13.0		11	33	mA
	Tone Output						
V_{OR}	Single Tone Mode Output Voltage	Row Tone, $R_L = 390\Omega$	5.0	417	596	789	mVrms
		Row Tone, $R_L = 240\Omega$	12.0	378	551	725	mVrms
dB_{CR}	Ratio of Column to Row Tone		3.5 – 13.0	1.75	2.54	3.75	dB
%DIS	Distortion*		3.5 – 13.0			10	%
	XMIT, MUTE Outputs						
V_{OH}	XMIT, Output Voltage, High (No Key Depressed)(Pin 2)	(I_{OH}=15mA)	3.5	2.0	2.3		V
		(I_{OH}=50mA)	13.0	12.0	12.3		V
I_{OF}	XMIT, Output Source Leakage Current, V_{OF}=0V		13.0			100	μA
V_{OL}	MUTE (Pin 10) Output Voltage, Low, (No Key Depressed), No Load		3.5		0	0.4	V
			13.0		0	0.5	V
V_{OH}	MUTE, Output Voltage, High, (One Key Depressed) No Load		3.5	3.0	3.5		V
			13.0	13.0	13.5		V
I_{OL}	MUTE, Output Sink Current	V_{OL}=0.5V	3.5	0.66	1.7		mA
			13.0	3.0	8.0		mA
I_{OH}	MUTE, Output Source Current	V_{OH}=2.5V	3.5	0.18	0.46		mA
		V_{OH}=9.5V	13.0	0.78	1.9		mA
	Oscillator Input/Output						
I_{OL}	Output Sink Current One Key Selected	V_{OL}=0.5V	3.5	0.26	0.65		mA
		V_{OL}=0.5V	13.0	1.2	3.1		mA
I_{OH}	Output Source Current One Key Selected	V_{OH}=2.5V	3.5	0.14	0.34		mA
		V_{OH}=9.5V	13.0	0.55	1.4		mA

Distortion measured in accordance with the specifications described in Ref. 1 as the "ratio of the total power of all extraneous frequencies in the voiceband above 500Hz accompanying the signal to the total power of the frequency pair".

S2559A & B Electrical Characteristics: (Continued)

Symbol	Parameter/Conditions		$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	Input Current						
I_{IL}	Leakage Sink Current, One Key Selected	$V_{IL} = 13.0V$	13.0			1.0	μA
I_{IH}	Leakage Source Current One Key Selected	$V_{IH} = 0.0V$	13.0			1.0	μA
I_{IL}	Sink Current	$V_{IL} = 0.5V$	3.5	24	93		μA
	No Key Selected	$V_{IL} = 0.5V$	13.0	27	130		μA
t_{START}	Oscillator Startup Time		3.5		3	6	mS
			13.0		0.8	1.6	mS
$C_{I/O}$	Input/Output Capacitance				12	16	pF
					10	14	pF
	Input Currents						
I_{IL}	Row & Column Inputs	Sink Current, $V_{IL} = 3.5V$ (Pull-down)	3.5	7	17		μA
		Sink Current $V_{IL} = 13.0V$ (Pull-down)	13.0	150	400		μA
I_{IH}		Source Current, $V_{IH} = 3.0V$ (Pull-up)	3.5	90	230		μA
		Source Current, $V_{IH} = 12.5V$ (Pull-up)	13.0	370	960		μA
I_{IH}	Mode Select Input (S2559C)	Source Current, $V_{IH} = 0.0V$ (Pull-up)	3.5	1.5	3.6		μA
		Source Current, $V_{IH} = 0.0V$ (Pull-up)	13.0	23	74		μA
I_{IL}	Chip Disable Input (S2559D)	Source Current, $V_{IL} = 3.5V$ (Pull-down)	3.5	4	10		μA
		Sink Current, $V_{IL} = 13.0V$ (Pull-down)	13.0	90	240		μA

S2559C & D Electrical Characteristics:

(Specifications apply over the operating temperature range of $-25°C$ to $70°C$ unless otherwise noted. Absolute values of measured parameters are specified.)

Symbol	Parameter/Conditions		$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	Supply Voltage						
V_{DD}	Tone Out Mode (Valid Key Depressed)			2.75		10.0	V
	Non Tone Out Mode (No Key Depressed)			2.5		10.0	V
	Supply Current						
I_{DD}	Standby (No Key Selected, Tone, XMIT and MUTE Outputs Unloaded)		3.0		0.3	30	μA
			10.0		1.0	100	μA
	Operating (One Key Selected, Tone, XMIT and MUTE Outputs Unloaded)		3.0		1.0	2.0	mA
			10.0		8	16.0	mA
	Tone Output						
V_{OR}	Single Tone Mode Output Voltage		3.5	250	362	474	mVrms
		Row Tone, $R_L = 390\Omega$	5.0	367	546	739	mVrms
		Row Tone, $R_L = 240\Omega$	10.0	328	501	675	mVrms

S2559C & D Electrical Characteristics: (Continued)

Symbol	Parameter/Conditions		$(V_{DD}-V_{SS})$ Volts	Min.	Typ.	Max.	Units
dB_{CR}	Ratio of Column to Row Tone		3.0 − 10.0	1.75	2.54	3.75	dB
%DIS	Distortion*		3.0 − 10.0			10	%
	XMIT, MUTE Outputs						
V_{OH}	XMIT, Output Voltage, High (No Key Depressed)(Pin 2)	$(I_{OH}=15mA)$	3.0	1.5	1.8		V
		$(I_{OH}=50mA)$	10.0	8.5	8.8		V
I_{OF}	XMIT, Output Source Leakage Current, $V_{OF}=0V$		10.0			100	μA
V_{OL}	MUTE (Pin 10) Output Voltage, Low, (No Key Depressed), No Load		2.75		0	0.5	V
			10.0		0	0.5	V
V_{OH}	MUTE, Output Voltage, High, (One Key Depressed) No Load		2.75	2.5	2.75		V
			10.0	9.5	10.0		V
I_{OL}	MUTE, Output Sink Current	$V_{OL}=0.5V$	3.0	0.53	1.3		mA
			10.0	2.0	5.3		mA
I_{OH}	MUTE, Output Source Current	$V_{OH}=2.5V$	3.0	0.17	0.41		mA
		$V_{OH}=9.5V$	10.0	0.57	1.5		mA
	Oscillator Input/Output						
I_{OL}	Output Sink Current One Key Selected	$V_{OL}=0.5V$	3.0	0.21	0.52		mA
		$V_{OL}=0.5V$	10.0	0.80	2.1		mA
I_{OH}	Output Source Current One Key Selected	$V_{OH}=2.5V$	3.0	0.13	0.31		mA
		$V_{OH}=9.5V$	10.0	0.42	1.1		mA
	Input Current						
I_{IL}	Leakage Sink Current, One Key Selected	$V_{IL}=10.0V$	10.0			1.0	μA
I_{IH}	Leakage Source Current One Key Selected	$V_{IH}=0.0V$	10.0			1.0	μA
I_{IL}	Sink Current	$V_{IL}=0.5V$	3.0	24	93		μA
	No Key Selected	$V_{IL}=0.5V$	10.0	27	130		μA
t_{START}	Oscillator Startup Time		3.5		2	5	mS
			10.0		0.25	4	mS
$C_{I/O}$	Input/Output Capacitance		3.0		12	16	pF
			10.0		10	14	pF
	Input Currents						
I_{IL}	Row & Column Inputs	Sink Current, $V_{IL}=3.0V$ (Pull-down)	3.0	6.5	16		μA
		Sink Current $V_{IL}=10.0V$ (Pull-down)	10.0	9.2	24		μA
I_{IH}		Source Current, $V_{IH}=2.5V$ (Pull-up)	3.0	85	210		μA
		Source Current, $V_{IH}=9.5V$ (Pull-up)	10.0	280	740		μA
I_{IH}	Mode Select Input (S2559C)	Source Current, $V_{IH}=0.0V$ (Pull-up)	3.0	1.4	3.3		μA
		Source Current, $V_{IH}=3.0V$ (Pull-up)	10.0	18	46		μA
I_{IL}	Chip Disable Input (S2559D)	Source Current, $V_{IL}=3.0V$ (Pull-down)	3.0	3.9	9.5		μA
		Sink Current, $V_{IL}=10.0V$ (Pull-down)	10.0	55	143		μA

*Distortion measured in accordance with the specifications described in Ref. 1 as the "ratio of the total power of all extraneous frequencies in the voiceband above 500Hz accompanying the signal to the total power of the frequency pair".

Table 1. Comparisons of Specified vs Actual Tone Frequencies Generated by S2559

ACTIVE INPUT	OUTPUT FREQUENCY Hz		% ERROR SEE NOTE
	SPECIFIED	ACTUAL	
R1	697	699.1	+0.30
R2	770	766.2	−0.49
R3	852	847.4	−0.54
R4	941	948.0	+0.74
C1	1,209	1,215.9	+0.57
C2	1,336	1,331.7	−0.32
C3	1,477	1,471.9	−0.35
C4	1,633	1,645.0	+0.73

NOTE: % Error does not include oscillator drift.

Table 2. XMIT and MUTE Output Functional Relationship

OUTPUT	'DIGIT' KEY RELEASED	'DIGIT' KEY DEPRESSED	COMMENT
XMIT	V_{DD}	High Impedance	Can source at least 50mA at 10V with 1.5V max. drop
MUTE	V_{SS}	V_{DD}	Can source or sink current

Circuit Description

The S2559 is designed so that it can be interfaced easily to the dual tone signaling telephone system and that it will more than adequately meet the recommended telephone industry specifications regarding the dual tone signaling scheme.

Design Objectives

The specifications that are important to the design of the Digital Tone Generator are summarized below: the dual tone signal consists of linear addition of two voice frequency signals. One of the two signals is selected from a group of frequencies called the "Low Group" and the other is selected from a group of frequencies called the "High Group". The low group consists of four frequencies 697, 770, 852 and 941 Hz. The high group consists of four frequencies 1209, 1336, 1477 and 1633 Hz. A keyboard arranged in a row, column format (4 rows x 3 or 4 columns) is used for number entry. When a push button corresponding to a digit (0 thru 9) is pushed, one appropriate row (R1 thru R4) and one appropriate column (C1 thru C4) is selected. The active row input selects one of the low group frequencies and the active column input selects one of the high group frequencies. In standard dual tone telephone systems, the highest high group frequency of 1633Hz (Col. 4) is not used. The frequency tolerance must be ±1.0%. However, the S2559 provides a better than .75% accuracy. The total harmonic and intermodulation distortion of the dual tone must be less than 10% as seen at the telephone terminals. (Ref. 1.) The high group to low group signal amplitude ratio should be 2.0 ±2dB and the absolute amplitude of the low group and high group tones must be within the allowed range. (Ref. 1.) These requirements apply when the telephone is used over a short loop or long loop and over the operating temperature range. The design of the S2559 takes into account these considerations.

Oscillator

The device contains an oscillator circuit with the necessary parasitic capacitances on chip so that it is only necessary to connect a 10MΩ feedback resistor and the standard 3.58MHz TV crystal across the OSCI and OSCO terminals to implement the oscillator function. The oscillator functions whenever a row input is activated. The reference frequency is divided by 2 and then drives two sets of programmable dividers, the high group and the low group.

Keyboard Interface

The S2559 employs a calculator type scanning circuitry to determine key closures. When no key is depressed, active pull-down resistors are "on" on the row inputs and active pull-up resistors are "on" on the column inputs. When a key is pushed a high level is seen on one of the row inputs, the oscillator starts and the keyboard scan logic turns on. The active pull-up or pull-down resistors are selectively switched on and off as the keyboard scan logic determines the row and the column inputs that are selected. The advantage of the scanning technique is that a keyboard arrangement of SPST switches are shown in Figure 2 without the need for a common line, can be used. Conventional telephone push button keyboards as shown in Figure 1 or X-Y keyboards with common can also be used. The common line of these keyboards can be left unconnected or wired "high".

Logic Interface

The S2559 can also interface with CMOS logic outputs directly. The S2559 requires active "High" logic levels. Since the active pull-up resistors present in the S2559 are fairly low value (500Ω typ), diodes can be used as shown in Figure 3 to eliminate excessive sink current flowing into the logic outputs in their "Low" state.

Tone Generation

When a valid key closure is detected, the keyboard logic programs the high and low group dividers with appropriate divider ratios so that the output of these dividers cycle at 16 times the desired high group and low group frequencies. The outputs of the programmable dividers drive two 8-stage Johnson counters. The symmetry of the clock input to the two divide by 16 Johnson counters allows 32 equal time segments to be generated within each output cycle. The 32 segments are used to digitally synthesize a stair-step waveform to approximate the sinewave function (see Figure 3). This is done by connecting a weighted resistor ladder network between the outputs of the Johnson counter, V_{DD} and V_{REF}. V_{REF} closely tracks V_{DD} over the operating voltage and temperature range and therefore the peak-to-peak amplitude V_P ($V_{DD} - V_{REF}$) of the stairstep function is fairly constant. V_{REF} is so chosen that V_P falls within the allowed range of the high group and low group tones.

Figure 1. Standard Telephone Push Button Keyboard
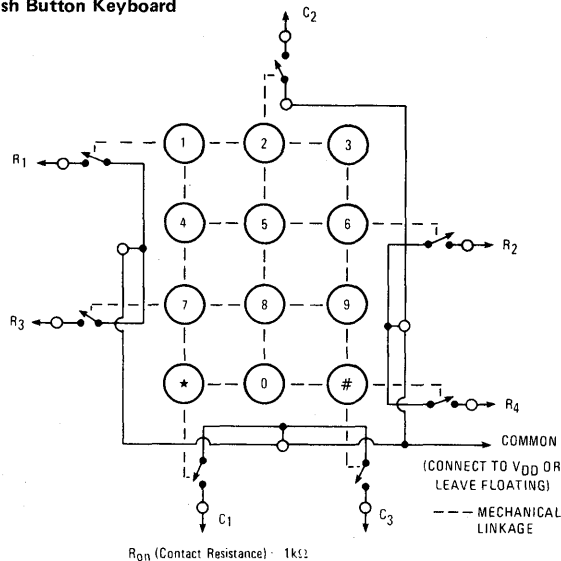
Figure 2. SPST Matrix Keyboard Arranged in the 2 of 8 Row, Column Format

Figure 3. Logic Interface for Keyboard Inputs of the S2559

G1 THRU G8 ANY TYPE CMOS GATE
D1 THRU D8 DIODES TYPE IN914 (OPTIONAL)
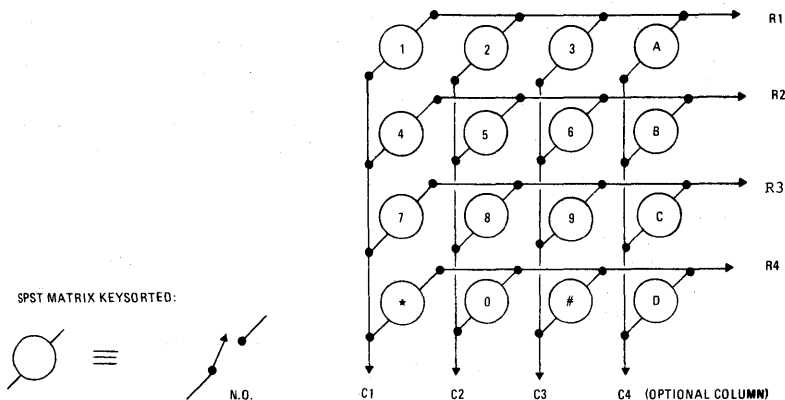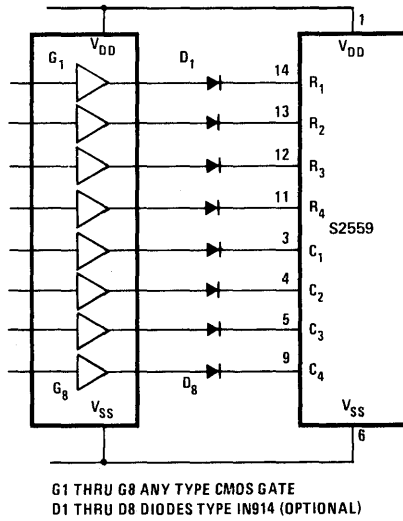
Figure 4. Stairstep Waveform of the Digitally Synthesized Sinewave
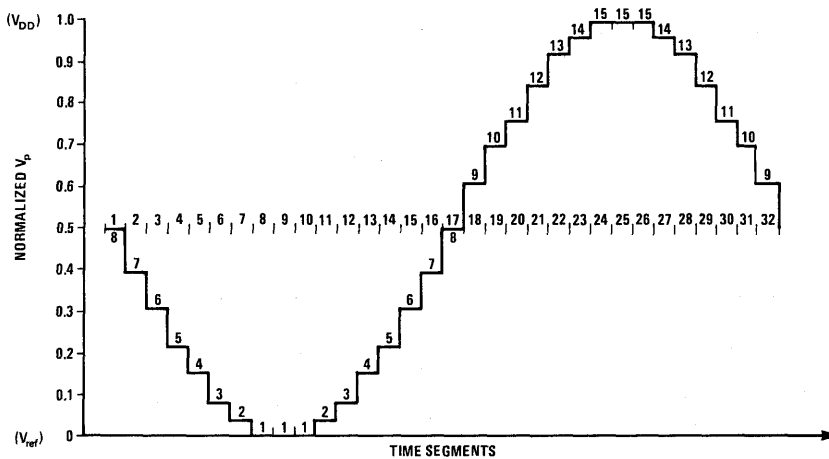
The individual tones generated by the sinewave synthesizer are then linearly added and drive a bipolar NPN transistor connected as emitter follower to allow proper impedance transformation, at the same time preserving signal level.

Dual Tone Mode

When one row and one column is selected dual tone output consisting of an appropriate low group and high group tone is generated. If two digit keys, that are not either in the same row or in the same column, are depressed, the dual tone mode is disabled and no output is provided.

Single Tone Mode

Single tones either in the low group or the high group can be generated as follows. A low group tone can be generated by activating the appropriate row input or by depressing two digit keys in the appropriate row. A high group tone can be generated by depressing two digit keys in the appropriate column, i.e., selecting the appropriate column input and two row inputs in that column.

Mode Select

S2559A and S2559C have a Mode Select (MDSL) input (Pin 15). When MDSL is left floating (unconnected) or connected to V_{DD}, both the dual tone and single tone modes are available. If MDSL is connected to V_{SS}, the single tone mode is disabled and no output tone is produced if an attempt for single tone is made. The S2559B and S2559D do not have the Mode Select option.

Chip Disable

The S2559B and S2559D have a Chip Disable input at Pin 15 instead of the Mode Select input. The chip disable for the S2559B and S2559D is active "high." When the chip disable is active, the tone output goes to V_{SS}, the row, column inputs go into a high impedance state, the oscillator is inhibited and the MUTE and XMIT outputs go into active states. The effect is the device essentially disconnects from the keyboard. This allows one keyboard to be shared among several devices.

Crystal Specification

A standard television color burst crystal is specified to have much tighter tolerance than necessary for tone generation application. By relaxing the tolerance specification the cost of the crystal can be reduced. The recommended crystal specification is as follows:

Frequency: 3.579545MHz ±0.02%
$R_S \leqslant 100\Omega$, L_M = 96MHY
C_M = 0.02pF C_h = 5pF

MUTE, XMIT Outputs

The S2559 A, B, C, D have a CMOS buffer for the MUTE output and a bipolar NPN transistor for the XMIT output. With no keys depressed, the MUTE output is "low" and the XMIT output is in the active state so that substantial current can be sourced to a load. When a key is depressed, the MUTE output goes high, while the XMIT output goes into a high impedance state. When Chip Disable is "high" the MUTE output is forced "low" and the XMIT output is in active state regardless of the state of the keyboard inputs.

Amplitude/Distortion Measurements

Amplitude and distortion are two important parameters in all applications of the Digital Tone Generator. Amplitude depends upon the operating supply voltage as well as the load resistance connected on the Tone Output pin. The on-chip reference circuit is fully operational when the supply voltage equals or exceeds 5 volts and as a consequence the tone amplitude is regulated in the supply voltage range above 5 volts. The load resistor value also controls the amplitude. If R_L is low the reflected impedance into the base of the output transistor is low and the tone output amplitude is lower. For R_L greater than 5KΩ the reflected impedance is sufficiently large and highest amplitude is produced. Individual tone amplitudes can be measured by applying the dual tone signal to a wave analyzer (H-P type 3581A) and amplitudes at the selected frequencies can be noted. This measurement also permits verification of the preemphasis between the individual frequency tones.

Distortion is defined as "the ratio of the *total* power of all extraneous frequencies in the *voiceband* above 500Hz accompanying the signal to the power of the frequency *pair*." This ratio must be less than 10% or when expressed in dB must be lower than −20dB. (Ref. 1.) Voiceband is conventionally the frequency band of 300Hz to 3400Hz. Mathematically distortion can be expressed as:

$$\text{Dist.} = \frac{\sqrt{(V_1)^2+(V_2)^2+ . . +(V_n)^2}}{\sqrt{(V_L)^2+(V_H)^2}}$$

where $(V_1) \ldots (V_n)$ are extraneous frequency (i.e., intermodulation and harmonic) components in the 500Hz to 3400Hz band and V_L and V_H are the individual frequency components of the DTMF signal. The expression can be expressed in dB as:

$$DIST_{dB} = 20 \log \frac{\sqrt{(V_1)^2 + (V_2)^2 + \ldots (V_n)^2}}{\sqrt{(V_L)^2 + (V_H)^2}}$$

$$= 10 \left\{ \log \left[(V_1)^2 + \ldots (V_n)^2 \right] - \log \left[(V_L)^2 + (V_H)^2 \right] \right\} \ldots (1)$$

An accurate way of measuring distortion is to plot a spectrum of the signal by using a spectrum analyzer (H-P type 3580A) and an X-Y plotter (H-P type 7046A). Individual extraneous and signal frequency components are then noted and distortion is calculated by using the expression (1) above. Figure 6 shows a spectrum plot of a typical signal obtained from a S2559D device operating from a fixed supply of 4Vdc and $R_L = 10k\Omega$ in the test circuit of Figure 5. Mathematical analysis of the spectrum shows

distortion to be −30dB (3.2%). For quick estimate of distortion, a rule of thumb as outlined below can be used.

"As a first approximation distortion in dB equals the difference between the amplitude (dB) of the extraneous component that has the highest amplitude and the amplitude (dB) of the low frequency signal." This rule of thumb would give an estimate of −28dB as distortion for the spectrum plot of Figure 6 which is close to the computed result of −30dB.

In a telephone application amplitude and distortion are affected by several factors that are interdependent. For detailed discussion of the telephone application and other applications of the 2559 Tone Generator, refer to the applications note "Applications of Digital Tone Generator."

Ref. 1: *Bell System Communications Technical Reference, PUB 47001,* "Electrical Characteristics of Bell System Network Facilities at the Interface with Voiceband Ancillary and Data Equipment," August 1976.

Figure 5. Test Circuit for Distortion Measurement

Figure 6. A Typical Spectrum Plot

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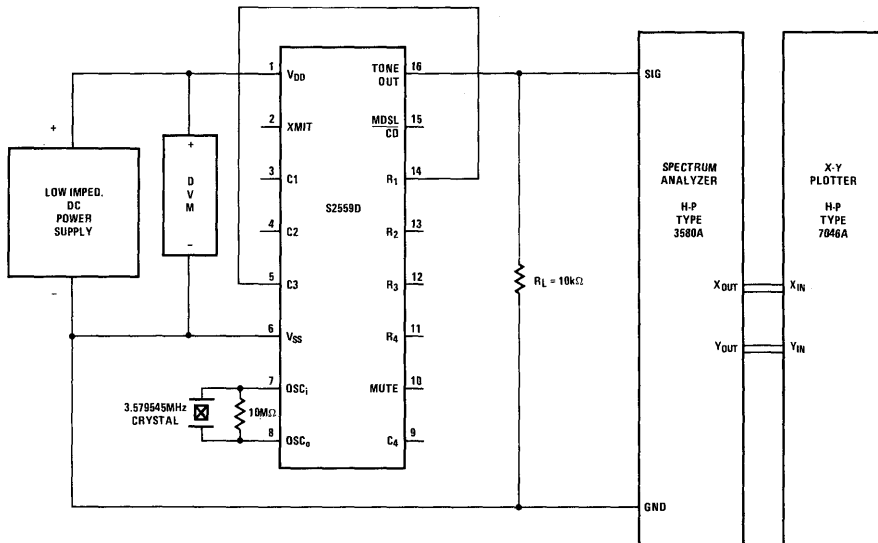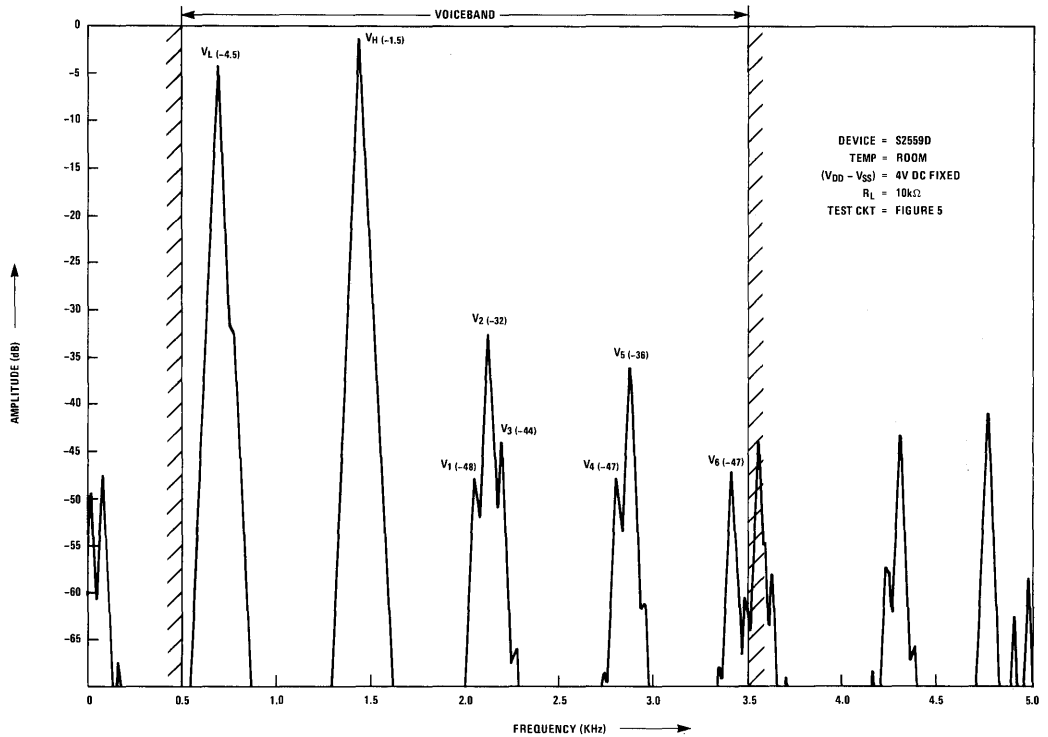
DIGITAL TONE GENERATOR

Features

- ☐ Wide Operating Supply Voltage Range: 3.0 to 10 Volts
- ☐ Low Power CMOS Circuitry Allows Device Power to be Derived Directly from the Telephone Lines or from Small Batteries, e.g., 9V
- ☐ Uses TV Crystal Standard (3.58 MHz) to Derive all Frequencies thus Providing Very High Accuracy and Stability
- ☐ Timing Sequence for XMIT, REC MUTE Outputs
- ☐ Interfaces Directly to a Standard Telephone Push-Button or Calculator Type X-Y Keyboard with Common Terminal
- ☐ The Total Harmonic Distortion is Below Industry Specification
- ☐ On Chip Generation of a Reference Voltage to Assure Amplitude Stability of the Dual Tones Over the Operating Voltage and Temperature Range
- ☐ Dual Tone as Well as Single Tone Capability
- ☐ Darlington Configuration Tone Output

General Description

The S2859 Digital Tone Generator is specifically designed to implement a dual tone telephone dialing system. The device can interface directly to a standard pushbutton telephone keyboard or X-Y keyboard with common terminal connected to V_{SS} and operates directly from the telephone lines. All necessary dual-tone frequencies are derived from the widely used TV crystal standard providing very high accuracy and stability. The required sinusoidal waveform for the individual tones is digitally synthesized on the chip. The waveform so generated has very low total harmonic distortion. A voltage reference is generated on the chip which is stable over the operating voltage and temperature range and regulates the signal levels of the dual tones to meet the recommended telephone industry specifications. These features permit the S2859 to be incorporated with a slight modification of the standard 500 type telephone basic circuitry to form a pushbutton dual-tone telephone. Other applications of the device include radio and mobile telephones, remote control, point-of-sale, and credit card verification terminals and process control.

Block Diagram

Pin Configuration

Absolute Maximum Ratings:

DC Supply Voltage ($V_{DD} - V_{SS}$) .... +10.5V
Operating Temperature .... −25°C to +70°C
Storage Temperature .... −55°C to +125°C
Power Dissipation at 25°C 500mW
Input Voltage .... $-0.6 \leqslant V_{IN} \leqslant V_{DD} + 0.6$
Input/Output Current (except tone output) 15mA
Tone Output Current 50mA

Electrical Characteristics:

(Specifications apply over the operating temperature range of −25°C to 70°C unless otherwise noted. Absolute values of measured parameters are specified.)

Symbol	Parameter/Conditions			$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	Supply Voltage							
V_{DD}	Tone Out Mode (Valid Key Depressed)				3.0	—	10.0	V
	Non Tone Out Mode (Mute Outputs Toggle With Key Depressed)				2.2	—	10.0	V
V_Z	Internal Zener Diode Voltage, $I_Z = 5mA$			—	—	12.0	—	V
	Supply Current							
I_{DD}	Standby (No Key Selected, Tone and Mute Outputs Unloaded)			3.0	—	0.001	0.3	mA
				10.0	—	0.003	1.0	mA
	Operating (One Key Selected, Tone and Mute Outputs Unloaded)			3.0	—	1.3	2.0	mA
				10.0	—	11	18	mA
	Tone Output							
V_{OR}	Single Tone	Row	$R_L = 100\Omega$	5.0	366	462	581	mVrms
	Mode Output Voltage	Tone	$R_L = 100\Omega$	10.0	370	482	661	mVrms
dB_{CR}	Ratio of Column to Row Tone			3.0−10.0	1.0	2.0	3.0	dB
%DIS	Distortion*			3.0−10.0	—	—	10	%
	REC, XMIT MUTE Outputs							
I_{OH}	Output Source Current		$V_{OH} = 1.2V$	2.2	0.43	1.1	—	mA
			$V_{OH} = 2.5V$	3.0	1.3	3.1	—	mA
			$V_{OH} = 9.5V$	10.0	4.3	11	—	mA

Distortion measured in accordance with the specifications described in Ref. 1 as the "ratio of the total power of all extraneous frequencies in the voiceband above 500Hz accompanying the signal to the total power of the frequency pair".

Electrical Characteristics: (Continued)

Symbol	Parameter/Conditions		$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	OSCILLATOR Input/Output						
I_{OL}	One Key Selected	$V_{OL} = 0.5V$	3.0	0.21	0.52	–	mA
	Output Sink Current	$V_{OL} = 0.5V$	10.0	0.80	2.1	–	mA
I_{OH}	Output Source Current	$V_{OH} = 2.5V$	3.0	0.13	0.31	–	mA
	One Key Selected	$V_{OH} = 9.5V$	10.0	0.42	1.1	–	mA
I_{IL}	Input Current Leakage Sink Current One Key Selected	$V_{IL} = 10.0V$	10.0	–	–	1.0	μA
I_{IH}	Leakage Source Current One Key Selected	$V_{IH} = 0.0V$	10.0	–	–	1.0	μA
I_{IL}	Sink Current	$V_{IL} = 0.5V$	3.0	24	58	–	μA
	No Key Selected	$V_{IL} = 0.5V$	10.0	27	66	–	μA
t_{START}	Oscillator Time		3.0	–	2	5	ms
			10.0	–	0.25	0.75	ms
$C_{I/O}$	Input/Output Capacitance		3.0	–	12	16	pF
			10.0	–	10	14	pF
	Row, Column and Chip Enable Inputs						
V_{IL}	Input Voltage, Low		3.0	–	–	0.75	V
			10.0	–	–	3.0	V
V_{IH}	Input Voltage, High		3.0	2.4		–	V
			10.0	7.0		–	V
I_{IH}	Input Current	$V_{IH} = 0.0V$	3.0	20	60	100	μA
	(Pull up)	$V_{IH} = 0.0V$	10.0	66	200	336	μA

Circuit Description

The S2859 is designed so that it can be interfaced easily to the dual tone signaling telephone system and that it will more than adequately meet the recommended telephone industry specifications regarding the dual tone signaling scheme.

Design Objectives

The specifications that are important to the design of the Digital Tone Generator are summarized below: the dual tone signal consists of linear addition of two voice frequency signals. One of the two signals is selected from a group of frequencies called the "Low Group" and the other is selected from a group of frequencies called the "High Group". The low group consists of four frequencies 697, 770, 852 and 941 Hz. The high group consists of four frequencies 1209, 1336, 1477 and 1633 Hz. A keyboard arranged in a row, column format (4 rows x

3 or 4 columns) is used for number entry. When a push button corresponding to a digit (0 thru 9) is pushed, one appropriate row (R1 thru R4) and one appropriate column (C1 thru C4) is selected. The active row input selects one of the low group frequencies and the active column input selects one of the high group frequencies. In standard dual tone telephone systems, the highest high group frequency of 1633Hz (Col. 4) is not used. The frequency tolerance must be ±1.0%. However, the S2859 provides a better than .75% accuracy. The total harmonic and intermodulation distortion of the dual tone must be less than 10% as seen at the telephone terminals. (Ref. 1.) The high group to low group signal amplitude ratio should be 2.0 ± 2dB and the absolute amplitude of the low group and high group tones must be within the allowed range. (Ref. 1.) These requirements apply when the telephone is used over a short loop or long loop and over the operating temperature range. The design of the S2859 takes into account these considerations.

Oscillator

The device contains an oscillator circuit with the necessary parasitic capacitances on chip so that it is only necessary to connect a $10M\Omega$ feedback resistor and the standard 3.58MHz TV crystal across the OSCI and OSCO terminals to implement the oscillator function. The oscillator functions whenever a row input is activated. The reference frequency is divided by 2 and then drives two sets of programmable dividers, the high group and the low group.

Keyboard Interface

The S2859 can interface with either the standard telephone pushbutton keyboard (see Figure 1) or an X-Y keyboard with common. The common of the keyboard must be connected to V_{SS}.

Figure 1. Standard Telephone Push Button Keyboard

Logic Interface

The S2859 can also interface with CMOS logic ouputs directly. (See Figure 2.) The S2859 requires active "Low" logic levels. Low levels on a row and a column input corresponds to a key closure. The pull-up resistors present on the row and column inputs are in the range of $33k\Omega - 150k\Omega$.

Tone Generation

When a valid key closure is detected, the keyboard logic programs the high and low group dividers with appropriate divider ratios so that the output of these dividers cycle at 16 times the desired high group and low group frequencies. The outputs of the programmable dividers drive two 8-stage Johnson counters. The symmetry of

the clock input to the two divide by 16 Johnson counters allows 32 equal time segments to be generated within each output cycle. The 32 segments are used to digitally synthesize a stair-step waveform to approximate the sinewave function (see Figure 3). This is done by connecting a weighted resistor ladder network between the outputs of the Johnson counter, V_{DD} and V_{REF}. V_{REF} closely tracks V_{DD} over the operating voltage and temperature range and therefore the peak-to-peak amplitude VP ($V_{DD} - V_{REF}$) of the stair-step function is fairly constant. V_{REF} is so chosen that VP falls within the allowed range of the high group and low group tones.

Table 1. Comparisons of Specified Vs. Actual Tone Frequencies Generated by S2859

ACTIVE INPUT	OUTPUT FREQUENCY Hz		%ERROR SEE NOTE
	SPECIFIED	ACTUAL	
R1	697	699.1	+0.30
R2	770	766.2	-0.49
R3	852	847.4	-0.54
R4	941	948.0	+0.74
C1	1209	1215.9	+0.57
C2	1336	1331.7	-0.32
C3	1477	1471.9	-0.35
C4	1633	1645.0	+0.73

NOTE: %ERROR DOES NOT INCLUDE OSCILLATOR DRIFT

Figure 2. Logic Interface for Keyboard Inputs of the S2859

G1 THRU G8 ANY TYPE CMOS GATE

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Figure 3. Stairstep Waveform of the Digitally Synthesized Sinewave

The individual tones generated by the sinewave synthesizer are then linearly added and drive a Darlington NPN transistor connected as an emitter follower to allow proper impedance transformation at the same time preserving signal level.

Dual Tone Mode

When one row and one column is selected dual tone output consisting of an appropriate low group and high group tone is generated. If two digit keys, that are not either in the same row or in the same column, are depressed, the dual tone mode is disabled and no output is provided.

Single Tone Mode

Single tones either in the low group or the high group can be generated as follows. A low group tone can be generated by depressing two digit keys in the appropriate row. A high group tone can be generated by depressing two digit keys in the appropriate column, i.e., selecting the appropriate column input and two row inputs in that column.

Chip Enable

The S2859 has a chip enable input at pin 15. The chip enable for the S2859 is active "High". When the chip enable is "Low", the tone output goes to V_{SS}, the oscillator is inhibited and the MUTE outputs go into an open state.

Crystal Specification

A standard television color burst crystal is specified to have much tighter tolerance than necessary for tone generation application. By relaxing the tolerance specification the cost of the crystal can be reduced. The recommended crystal specification is as follows:

Frequency: $3,579545MHz \pm 0.02\%$

R_S 100Ω, $L_M = 96MHY$

$C_M = 0.02pF$ $C_H = 5pF$ $C_L = 12pF$

MUTE Outputs

The S2859 has P-Channel buffers for the REC MUTE and XMIT MUTE outputs. With no keys depressed,

the MUTE outputs are open. When a key is depressed, the MUTE outputs go high. When chip enable is "Low" the MUTE outputs are forced in the "open" state regardless of the state of the keyboard.

Timing Sequence

Figure 4 illustrates the sequence in which the MUTE outputs operate when a key is depressed and released. When a valid key is depressed the REC MUTE output goes high first. The XMIT MUTE output goes high after a delay of about 1.6ms. This allows the receiver to be muted prior to the muting of the transmitter and generation of the dual tone. This prevents an undesirable click to be heard in the earpiece due to the momentary interruption of the direct current flowing through the network during the transition time when the transmitter is disconnected and dual tone applied. On release of the key the XMIT MUTE output goes open first, simultaneously the dual tone output is removed. The receiver at this time is still muted so that the click due to the momentary interruption of the direct current during the release of the key is not heard at the earpiece. The REC MUTE output goes open after a delay of about 1.7ms which reconnects the receiver to the network. The leading and trailing edge delays are guaranteed for supply voltages exceeding 3.0 volts. Below 3.0 volts the REC, XMIT MUTE outputs and tone output coincide with each other.

Amplitude/Distortion Measurements

Amplitude and distortion are two important parameters in all applications of the digital tone generator. Amplitude depends upon the operating supply voltage as well as the load resistance connected on the tone output pin. The on-chip reference circuit is fully operational when the supply voltage equals or exceeds 4 volts and as a consequence the tone amplitude is regulated in the supply voltage range above 4 volts. The load resistor value also controls the amplitude. If R_L is low the reflected impedance into the base of the output transistor is low and the tone output amplitude is lower. For R_L greater than $1K\Omega$ the reflected impedance is sufficiently large and highest amplitude is produced. Individual tone amplitudes can be measured by applying the dual tone signal to a wave analyzer (H-P type 3580A) and amplitudes at the selected frequencies can be noted. This measurement also permits verification of the pre-emphasis between the individual frequency tones.

Distortion is defined as "the ratio of the total power of all extraneous frequencies in the voiceband above 500Hz accompanying the signal to the power of the frequency pair". This ratio must be less than 10% or when expressed in dB must be lower than -20dB. (Ref. 1.) Voiceband is conventionally the frequency band of 300Hz to 3400Hz. Mathematically distortion can be expressed as:

$$\text{Dist.} = \frac{\sqrt{(V_1)^2 + (V_2)^2 + \ldots + (V_N)^2}}{\sqrt{(V_L)^2 + (V_H)^2}}$$

where $(V_1) \ldots (V_N)$ are extraneous frequency (i.e., intermodulation and harmonic) components in the 500 Hz to 3400Hz band and V_L and V_H are the individual frequency components of the DTMF signal. The expression can be expressed in dB as:

$$\text{DIST}_{dB} = 20 \log \frac{\sqrt{(V_1)^2 + (V_2)^2 + \ldots + (V_N)^2}}{\sqrt{(V_L)^2 + (V_H)^2}}$$

$$= 10\{\log[(V_1^2 + \ldots (V_N)^2] - \log[(V_L)^2 + (V_H)^2]\} \ldots (1)$$

Table 2. Truth Table

INPUTS				OUTPUTS		
KEYS DEPRESSED	NUMBER OF COLUMNS LOW	NUMBER OF ROWS LOW	CHIP ENABLE	TONE	REC MUTE	XMIT MUTE
X	X	X	0	0	OPEN	OPEN
NONE	0	0	1	0	OPEN	OPEN
ONE	1	1	1	R+C	1	1
TWO OR MORE KEYS IN COLUMN	1	2 OR 3 OR 4	1	C	1	1
TWO OR MORE KEYS IN ROW	2 OR 3 OR 4	1	1	R	1	1
MULTI KEY	OTHER COMBINATIONS	OTHER COMBINATIONS	1	0	OPEN	OPEN
NOTE 1	4	3	1	R+C	A	B

X DON'T CARE   A: 16 (ROW FREQ)   B: 16 (COL FREQ)

NOTE 1: THIS MODE IS USED FOR TEST PURPOSES ONLY. IT IS INITIATED BY CONNECTING ALL COLUMN INPUTS AND THREE OUT OF FOUR ROW INPUTS TO Vss. THE ROW INPUT THAT IS CONNECTED TO VDD ROUTES THE CORRESPONDING 16 TIMES ROW FREQUENCY TO THE REC MUTE OUTPUT AND THE APPROPRIATE 16 TIMES COLUMN FREQUENCY (i.e., R_1 SELECTS C_1 etc.) TO THE XMIT MUTE OUTPUT.

Figure 4. Timing Diagram for $(V_{DD} - V_{SS}) \geqslant 3.0V$
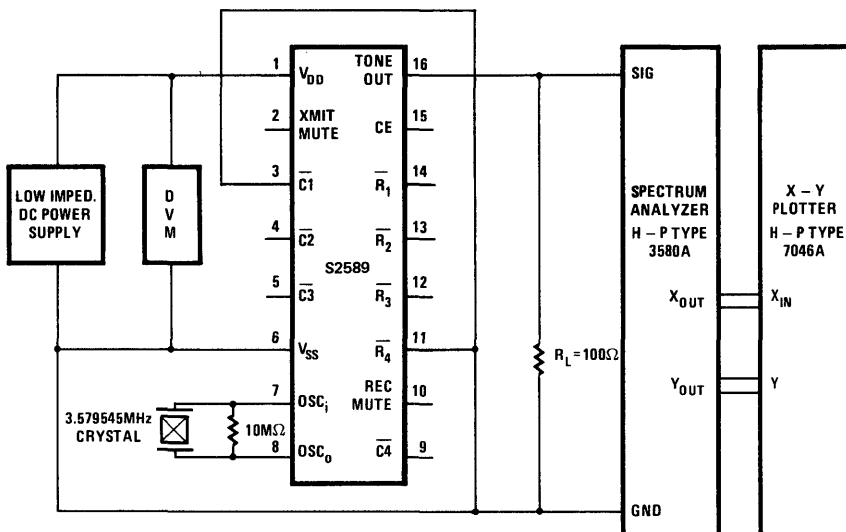
KEY CLOSURE
(VALID ROW,
COL INP)

OSC

REC MUTE

XMIT MUTE

TONE OUTPUT

$t_4 \cong 1.7mS$

$1.3mS \leqslant t_5 \leqslant 1.6mS \quad 0 < t_6 \leqslant 1.7mS$

(EXTERNAL PULL-DOWN RESISTOR ASSUMED ON MUTE OUTPUTS)

Figure 5. Test Circuit for Distortion Measurement

An accurate way of measuring distortion is to plot a spectrum of the signal by using a spectrum analyzer (H-P type 3580A) and an X-Y plotter (H-P type 7046A). Individual extraneous and signal frequency components are then noted and distortion is calculated by using the expression (1) above. Figure 6 shows a spectrum plot of a typical signal obtained from S2859 device operating from a fixed supply of 4VDC and $R_L = 100\Omega$ in the test circuit of Figure 5. Mathematical analysis of the spectrum shows distortion to be -30dB (3.2%). For quick estimate of distortion, a rule of thumb as outlined below can be used.

"As a first approximation distortion in dB equals the difference between the amplitude (dB) of the extraneous component that has the highest amplitude and the amplitude (dB) of the low frequency signal." This rule of thumb would give an estimate of -28dB as distortion for the spectrum plot of Figure 6 which is close to the computed result of -30dB.

In a telephone application amplitude and distortion are affected by several factors that are interdependent. For detailed discussion of the telephone application and other applications of the S2859 Tone Generator, refer to the applications note "Applications of Digital Tone Generator."

Ref. 1: Bell System Communications Technical Reference, PUB 47001, *"Electrical Characteristics of Bell System Network Facilities at the Interface with Voiceband Ancillary and Data Equipment,"* August 1976.

Figure 6. A Typical Spectrum Plot

FREQUENCY (KHz) ⟶
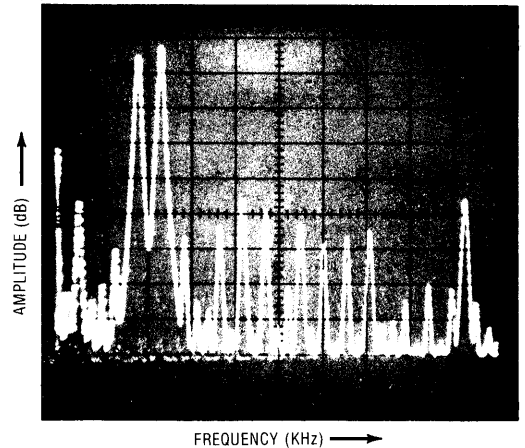
DEVICE: S2859 $R_L = 100\Omega$
TEMP: ROOM   TEST CKT: FIGURE 5
$(V_{DD} - V_{SS})$: 4V DC FIXED   DUAL TONE: R_4, C_1
        HORIZONTAL SCALE = 0.5KHz/DIV
           VERTICAL SCALE   = 10dB/DIV

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DIGITAL TONE GENERATOR

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Features

☐ **Optimized for Constant Operating Supply Voltages, Typically 3.5V**

☐ **Tone Amplitude Stability is Within ±1.3 dB of Nominal Over Operating Temperature Range**

☐ **Low Power CMOS Circuitry Allows Device Power to be Derived Directly from the Telephone Lines or from Small Batteries**

☐ **Uses TV Crystal Standard (3.58 MHz) to Derive all Frequencies thus Providing Very High Accuracy and Stability**

☐ **Specifically Designed for Electronic Telephone Applications**

☐ **Interfaces Directly to a Standard Telephone Push-Button or Calculator Type X-Y Keyboard with Common Terminal**

☐ **The Total Harmonic Distortion is Below Industry Specification**

☐ **Dual Tone as Well as Single Tone Capability**

General Description

The S2860 Digital Tone Generator is specifically designed to implement a dual tone telephone dialing system in applications requiring fixed supply operation and high stability tone output level, making it well suited for electronic telephone applications. The device can interface directly to a standard pushbutton telephone keyboard or X-Y keyboard with common terminal connected to V_{SS} and operates directly from the telephone lines. All necessary dual-tone frequencies are derived from the widely used TV crystal standard providing very high accuracy and stability. The required sinusoidal waveform for the individual tones is digitally synthesized on the chip. The waveform so generated has very low total harmonic distortion. A voltage reference is generated on the chip which is very stable over the operating temperature range and regulates the signal levels of the dual tones to meet the recommended telephone industry specifications.

Block Diagram

Pin Configuration
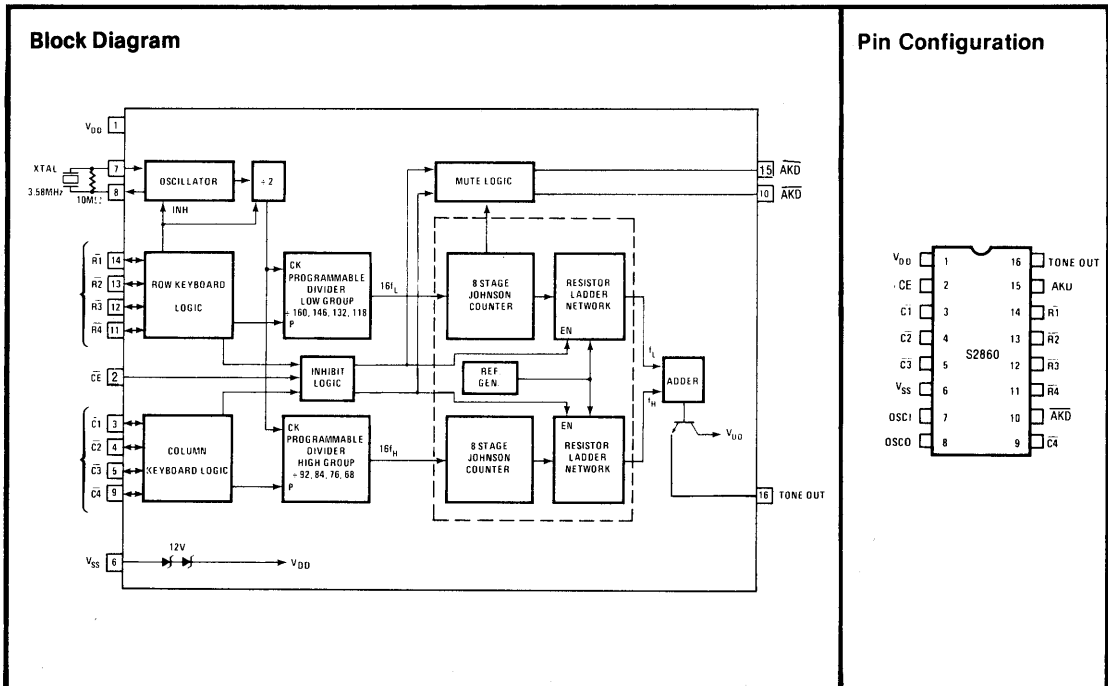
Absolute Maximum Ratings:

DC Supply Voltage ($V_{DD} - V_{SS}$) .... +10.5V
Operating Temperature .... −30 °C to +70 °C
Storage Temperature .... −55 °C to +125 °C
Power Dissipation at 25 °C 500mW
Input Voltage .... $-0.6 \leqslant V_{IN} \leqslant V_{DD} + 0.6$
Input/Output Current (except tone output) 15mA
Tone Output Current 50mA

Electrical Characteristics:

(Specifications apply over the operating temperature range of −30 °C to 70 °C unless otherwise noted. Absolute values of measured parameters are specified.)

Symbol	Parameter/Conditions			$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	Supply Voltage							
V_{DD}	Tone Out Mode (Valid Key Depressed)				3.0	–	10.0	V
	Non Tone Out Mode (AKD Outputs toggle with key depressed)				1.8	–		V
V_Z	Internal Zener Diode Voltage, $I_Z = 5mA$			–	–	12.0	–	V
	Supply Current							
I_{DD}	Standby (No Key Selected, Tone and AKD Outputs Unloaded)			3.5	–	1	20	μA
				10.0	–	5	100	μA
	Operating (One Key Selected, Tone and AKD Outputs Unloaded)			3.5	–	.9	1.25	mA
				10.0	–	3.6	5	mA
	Tone Output							
V_{OR}	Dual Tone	Row	$R_L = 10k\ \Omega$	3.5	305	350	412	mVrms
	Mode Output	Tone	$R_L = 1k\ \Omega$	3.5	272	350	412	mVrms
dB_{CR}	Ratio of Column to Row Tone			3.0 – 10.0	1.0	2.0	3.0	dB
%DIS	Distortion			3.0 – 10.0	–	–	10	%
	AKD Outputs							
I_{OH}	Output Sink Current		$V_{OL} = .7V$	3.5	0.1	1.0	–	mA
	OSCILLATOR Input/Output							
I_{OL}	One Key Selected		$V_{OL} = 0.5V$	3.0	0.21	0.52	–	mA
	Output Sink Current		$V_{OL} = 0.5V$	10.0	0.80	2.1	–	mA
I_{OH}	Output Source Current		$V_{OH} = 2.5V$	3.0	0.13	0.31	–	mA
	One Key Selected		$V_{OH} = 9.5V$	10.0	0.42	1.1	–	mA
I_{IL}	Input Current Leakage Sink Current One Key Selected		$V_{IL} = 10.0V$	10.0	–	–	1.0	μA
I_{IH}	Leakage Source Current One Key Selected		$V_{IH} = 0.0V$	10.0	–	–	1.0	μA
I_{IL}	Sink Current		$V_{IL} = 0.5V$	3.0	24	58	–	μA
	No Key Selected		$V_{IL} = 0.5V$	10.0	27	66	–	μA

Distortion measured in accordance with the specifications described in Ref. 1 as the "ratio of the total power of all extraneous frequencies in the voiceband above 500Hz accompanying the signal to the total power of the frequency pair".

Electrical Characteristics: (Continued)

Symbol	Parameter/Conditions		$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	OSCILLATOR Input/Output (Continued)						
t_{START}	Oscillator Time		3.0	—	2	5	ms
			10.0	—	0.25	0.75	ms
$C_{I/O}$	Input/Output Capacitance		3.0	—	12	16	pF
			10.0	—	10	14	pF
	Row, Column and Chip Enable Inputs						
V_{IL}	Input Voltage, Low		—	$V_{SS}-0.6$		$.2(V_{DD} -V_{SS})$	V
V_{IH}	Input Voltage, High		—	$.8(V_{DD} -V_{SS})$	—	$V_{DD}+0.6$	V
I_{IH}	Input Current	$V_{IH} = 0.0V$	3.0	20	60	100	μA
	(Pull up)	$V_{IH} = 0.0V$	10.0	66	200	336	μA

Oscillator

The S2860 contains an oscillator circuit with the necessary parasitic capacitances on chip so that it is only necessary to connect a $10M\Omega$ feedback resistor and the standard 3.58MHz TV crystal across the OSCI and OSCO terminals to implement the oscillator function. The oscillator functions whenever a row input is activated. The reference frequency is divided by 2 and then drives two sets of programmable dividers, the high group and the low group.

Crystal Specification

A standard television color burst crystal is specified to have much tighter tolerance than necessary for tone generation application. By relaxing the tolerance specification the cost of the crystal can be reduced. The recommended crystal specification is as follows:

Frequency: 3,579545MHz $\pm 0.02\%$
R_S 100Ω, $L_M = 96MH_Y$
$C_M = 0.02pF$ $C_H = 5pF$ $C_L = 12pF$

Keyboard Interface

The S2860 can interface with either the standard telephone pushbutton keyboard (see Figure 1) or an X-Y keyboard with common. The common of the keyboard must be connected to V_{SS}.

Figure 1. Standard Telephone Push Button Keyboard
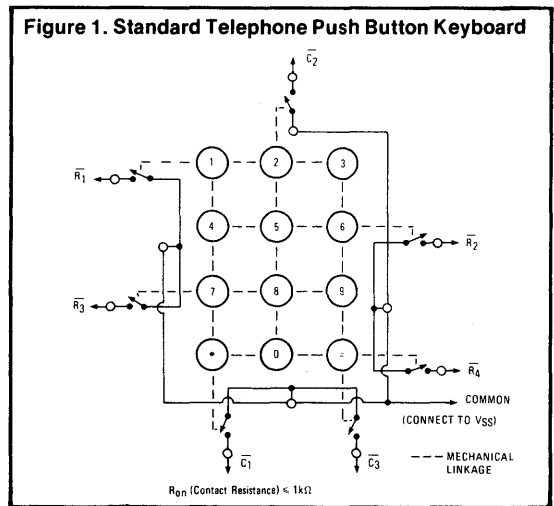
Logic Interface

The S2860 can also interface with CMOS logic outputs directly. (See Figure 2.) The S2860 requires active "Low" logic levels. Low levels on a row and a column input corresponds to a key closure. The pull-up resistors present on the row and column inputs are in the range of $33k\Omega - 150k\Omega$.

Tone Generation

When a valid key closure is detected, the keyboard logic

Tone Generation (Continued)

programs the high and low group dividers with appropriate divider ratios so that the output of these dividers cycle at 16 times the desired high group and low group frequencies. The outputs of the programmable dividers drive two 8-stage Johnson counters. The symmetry of the clock input to the two divide by 16 Johnson counters allows 32 equal time segments to be generated within each output cycle. The 32 segments are used to digitally synthesize a stair-step waveform to approximate the sinewave function (see Figure 3). This is done by connecting a weighted resistor ladder network between the outputs of the Johnson counter, V_{DD} and V_{REF}. V_{REF} closely tracks V_{DD} over the operating voltage and temperature range and therefore the peak-to-peak amplitude VP ($V_{DD} - V_{REF}$) of the stair-step function is fairly constant. V_{REF} is so chosen that VP falls within the allowed range of the high group and low group tones.

The individual tones generated by the sinewave synthesizer are then linearly added and drive an NPN transistor connected as an emitter follower to allow proper impedance transformation at the same time preserving signal level. This allows the device to drive varying resistive loads without significant variation in tone amplitude. For example, a load resistor change from 10kΩ to 1kΩ causes a decrease in tone amplitude of less than 1dB.

Dual Tone Mode

When one row and one column is selected dual tone output consisting of an appropriate low group and high group tone is generated. If two digit keys, that are not either in the same row or in the same column, are depressed, the dual tone mode is disabled and no output is provided.

Single Tone Mode

Single tones either in the low group or the high group can be generated as follows. A low group tone can be generated by depressing two digit keys in the appropriate row. A high group tone can be generated by depressing two digit keys in the appropriate column, i.e., selecting the appropriate column input and two row inputs in that column.

**Table 1. Comparisons of Specified
Vs. Actual Tone Frequencies Generated by S2859**

ACTIVE	OUTPUT FREQUENCY Hz		% ERROR
INPUT	SPECIFIED	ACTUAL	SEE NOTE
R1	697	699.1	+ 0.30
R2	770	766.2	− 0.49
R3	852	847.4	− 0.54
R4	941	948.0	+ 0.74
C1	1209	1215.9	+ 0.57
C2	1336	1331.7	− 0.32
C3	1477	1471.9	− 0.35
C4	1633	1645.0	+ 0.73

NOTE: % ERROR DOES NOT INCLUDE OSCILLATOR DRIFT

**Figure 2. Logic Interface for Keyboard
Inputs of the S2860**

G1 THRU G8 ANY TYPE CMOS GATE

Figure 3. Stairstep Waveform of the Digitally Synthesized Sinewave

Reference Voltage

The structure of the reference voltage employed in the S2860 is shown in Figure 4. It has the following characteristics:

a) V_{REF} is proportional to the supply voltage. Output tone amplitude, which is a function of ($V_{DD} - V_{REF}$), increases with supply voltage (Figure 5).

b) The temperature coefficient of V_{REF} is low due to a single V_{BE} drop. Use of a resistive divider also provvides an accuracy of better than 1%. As a result, tone amplitude variations over temperature and unit to unit are held to less than ±1.3dB over nominal.

c) Resistor values in the divider network are so chosen that V_{REF} is above the V_{BE} drop of the tone output transistor even at the low end of the supply voltage range. The tone output clipping at low supply voltages is thus eliminated, which improves distortion performance.

AKD (Any Key Down or Mute) Outputs

The AKD outputs (pin 15 and pin 10) are identical and consist of open drain N channel devices (see Figure 6.)

When no key is depressed the AKD outputs are open. When a key is depressed the AKD outputs go to V_{SS}. The devices are large enough to sink a minimum of 100µA with voltage drop of 0.2V at a supply voltage of 3.5V.
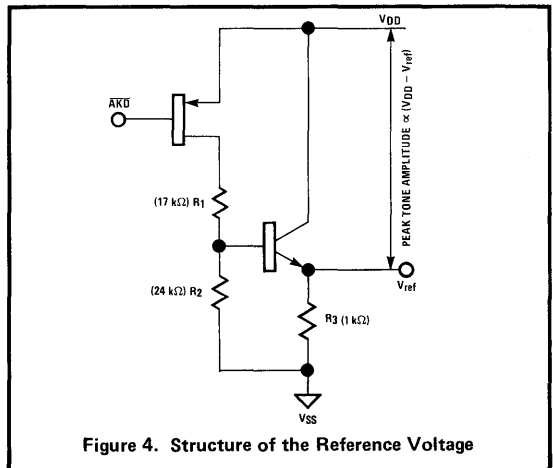
Figure 4. Structure of the Reference Voltage

Figure 5. Typical Tone Output Amplitude Vs Supply Voltage (R_L = 10k)
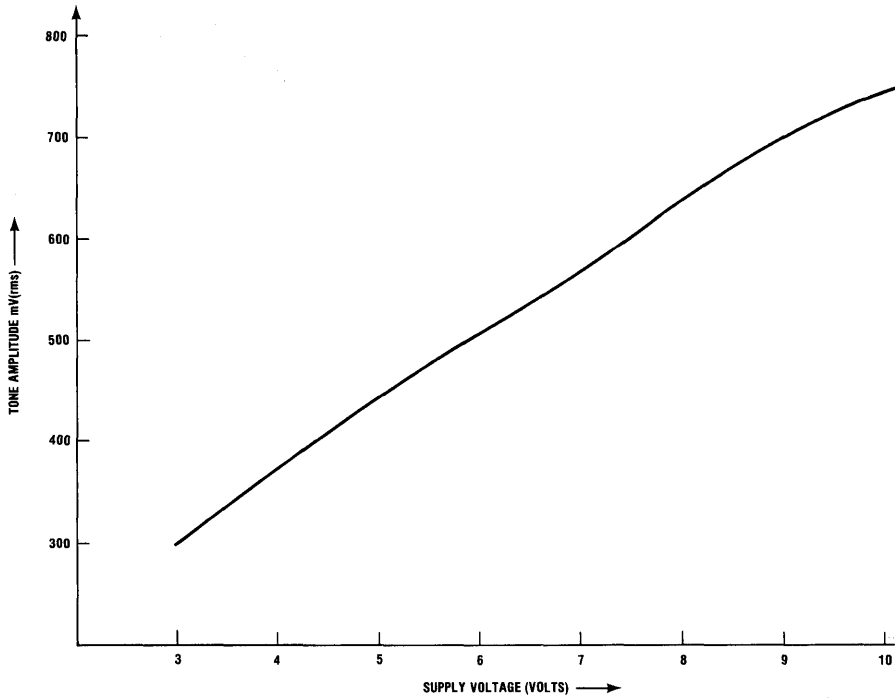
Figure 6. AKD Output Structure

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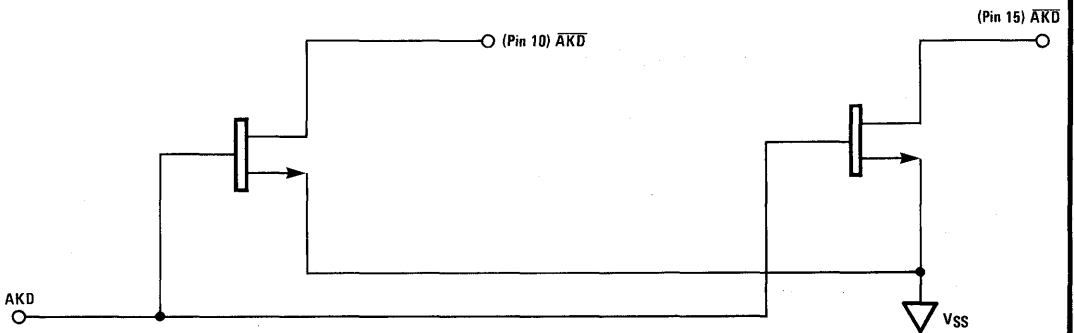
Features

☐ Replaces S2559 Family with Reduced Tone Output Distortion

☐ Wide Operating Supply Voltage Range: 2.5 to 10 Volts

☐ Low Power CMOS Circuitry Allows Device Power to be Derived Directly from the Telephone Lines or from Small Batteries. e.g., 9V

☐ Uses TV Crystal Standard (3.58 MHz) to Derive all Frequencies thus Providing Very High Accuracy and Stability

☐ Oscillator Bias Resistor On Chip

☐ Interfaces Directly to a Standard Telephone Pushbutton or Calculator Type X-Y Keyboard

☐ The Total Harmonic Distortion is Below Industry Specification

☐ On Chip Generation of a Reference Voltage to Assure Amplitude Stability of the Dual Tones Over the Operating Voltage and Temperature Range

☐ Dual Tone as Well as Single Tone Capability

☐ Two Options Available on Pin 15:
    S2861A: Mode Select (Replaces S2559A/C)
    S2861B: Chip Disable (Replaces S2559B/D)

General Description

The S2861A/B devices are improved versions of the S2559 family and are recommended for use in new designs or as replacements for S2559 devices. Functionally the S2861A is identical to S2559A and S2559C. The S2861B is functionally identical to S2559B and S2559D. An exception is the built in oscillator bias resistor across the oscillator input/output pins of S2861 so that the external 10M Ω resistor is no longer necessary.

Certain major differences in electrical performance should be noted. Preemphasis, the ratio of the column tone to the row tone, is changed to 2 dB ± 1 dB in the S2861 and the reference voltage circuit has been improved. These modifications substantially lower distortion in the tone output, especially at low operating voltages, with only a small decrease in available tone output level. Electrical specifications other than tone amplitude and preemphasis are nearly identical to their S2559 counterparts, except for maximum operating voltage, which is higher in the S2559A/B.

Block Diagram

Pin Configuration

S2861A & B Electrical Characteristics:

(Specifications apply over the operating temperature range of $-25\,°C$ to $70\,°C$ unless otherwise noted. Absolute values of measured parameters are specified.)

Symbol	Parameter/Conditions		$(V_{DD} - V_{SS})$ Volts	Min.	Typ.	Max.	Units
	Supply Voltage						
V_{DD}	Tone Out Mode (Valid Key Depressed)			2.75		10.0	V
	Non Tone Out Mode (No Key Depressed)			2.5		10.0	V
	Supply Current						
I_{DD}	Standby (No Key Selected, Tone, XMIT		3.0		0.3	30	μA
	and MUTE Outputs Unloaded)		10.0		1.0	100	μA
	Operating (One Key Selected, Tone, XMIT		3.0		1.0	2.0	mA
	and MUTE Outputs Unloaded)		10.0		8	16.0	mA
	Tone Output						
V_{OR}	Single Tone Mode Output Voltage	Row Tone, $R_L = 390\Omega$	3.5 5.0				mVrms mVrms
		Row Tone, $R_L = 240\Omega$	10.0				mVrms
dB_{CR}	Ratio of Column to Row Tone		3.5 – 13.0	1.0	2.0	3.0	dB
%DIS	Distortion*		3.5 – 13.0			10	%
	XMIT, MUTE Outputs						
V_{OH}	XMIT, Output Voltage, High	$(I_{OH} = 15mA)$	3.0	1.5	1.8		V
	(No Key Depressed)(Pin 2)	$(I_{OH} = 50mA)$	10.0	8.5	8.8		V
I_{OF}	XMIT, Output Source Leakage Current, $V_{OF} = 0V$		10.0			100	μA
V_{OL}	MUTE (Pin 10) Output Voltage, Low,		2.75		0	0.5	V
	(No Key Depressed), No Load		10.0		0	0.5	V
V_{OH}	MUTE, Output Voltage, High,		2.75	2.5	2.75		V
	(One Key Depressed) No Load		10.0	9.5	10.0		V
I_{OL}	MUTE, Output Sink Current	$V_{OL} = 0.5V$	3.0	0.53	1.3		mA
			10.0	2.0	5.3		mA
I_{OH}	MUTE, Output Source Current	$V_{OH} = 2.5V$	3.0	0.17	0.41		mA
		$V_{OH} = 9.5V$	10.0	0.57	1.5		mA
	Oscillator Input/Output						
I_{OL}	Output Sink Current One Key Selected	$V_{OL} = 0.5V$	3.0	0.21	0.52		mA
		$V_{OL} = 0.5V$	10.0	0.80	2.1		mA
I_{OH}	Output Source Current One Key Selected	$V_{OH} = 2.5V$	3.0	0.13	0.31		mA
		$V_{OH} = 9.5V$	10.0	0.42	1.1		mA
	Input Current						
I_{IL}	Leakage Sink Current, One Key Selected	$V_{IL} = 10.0V$	10.0			1.0	μA
I_{IH}	Leakage Source Current One Key Selected	$V_{IH} = 0.0V$	10.0			1.0	μA
I_{IL}	Sink Current	$V_{IL} = 0.5V$	3.0	24	93		μA
	No Key Selected	$V_{IL} = 0.5V$	10.0	27	130		μA
t_{START}	Oscillator Startup Time		3.5		2	5	mS
			10.0		0.25	4	mS

*Distortion measured in accordance with the specifications described in Ref. 1 as the "ratio of the total power of all extraneous frequencies in the voiceband above 500Hz accompanying the signal to the total power of the frequency pair".

S2861A & B Electrical Characteristics: (Continued)

Symbol	Parameter/Conditions		$(V_{DD}-V_{SS})$ Volts	Min.	Typ.	Max.	Units
$C_{I/O}$	Input/Output Capacitance		3.0		12	16	pF
			10.0		10	14	pF
	Input Currents						
I_{IL}	Row & Column Inputs	Sink Current, $V_{IL}=3.0V$ (Pull-down)	3.0	6.5	16		μA
		Sink Current $V_{IL}=10.0V$ (Pull-down)	10.0	9.2	24		μA
I_{IH}		Source Current, $V_{IH}=2.5V$ (Pull-up)	3.0	85	210		μA
		Source Current, $V_{IH}=9.5V$ (Pull-up)	10.0	280	740		μA
I_{IH}	Mode Select Input S2861A	Source Current, $V_{IH}=0.0V$ (Pull-up)	3.0	1.4	3.3		μA
		Source Current, $V_{IH}=3.0V$ (Pull-up)	10.0	18	46		μA
I_{IL}	Chip Disable Input S2861B	Source Current, $V_{IL}=3.0V$ (Pull-down)	3.0	3.9	9.5		μA
		Sink Current, $V_{IL}=10.0V$ (Pull-down)	10.0	55	143		μA

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PULSE DIALER

Features

☐ Low Voltage CMOS Process for Direct Operation From Telephone Lines

☐ Inexpensive R-C Oscillator Design Provides Better than ±5% Accuracy Over Temperature and Unit to Unit Variations

☐ Dialing Rate Can Be Varied By Changing the Dial Rate Oscillator Frequency

☐ Dial Rate Select Input Allows Changing of the Dialing Rate by a 2:1 Factor Without Changing Oscillator Components

☐ Two Selections of Mark/Space Ratios (33-1/3/66-2/3 or 40/60)

☐ Twenty Digit Memory for Input Buffering and for Redial With Access Pause Capability

☐ Mute and Dial Pulse Drivers on Chip

☐ Accepts DPCT Keypad with Common Arranged in a 2 of 7 Format; Also Capable of Interface to SPST Switch Matrix

General Description

The S2560A Pulse Dialer is a CMOS integrated circuit that converts pushbutton inputs to a series of pulses suitable for telephone dialing. It is intended as a replacement for the mechanical telephone dial and can operate directly from the telephone lines with minimum interface. Storage is provided for 20 digits, therefore, the last dialed number is available for redial until a new number is entered. IDP is scaled to the dialing rate such as to produce smaller IDP at higher dialing rates. Additionally, the IDP can be changed by a 2:1 factor at a given dialing rate by means of the IDP select input.

Block Diagram

KEYBOARD INPUTS: R_1, R_4, C_1, C_3

KEYBOARD INTERFACE

20 DIGIT MEMORY

HOOK SWITCH: $\overline{HS}$

DIAL RATE OSC: R_D, C_D, R_E

OSC

R/W POINTER LOGIC

CONTROL LOGIC

$\overline{DP}$

$\overline{MUTE}$

DRS   IPS   M/S

Pin Configuration

	S2560A PULSE DIALER	
R_4 — 1		18 — C_3
R_1 — 2		17 — C_2
R_2 — 3		16 — C_1
R_3 — 4		15 — IPS
$\overline{HS}$ — 5		14 — DRS
R_E — 6		13 — V_{DD}
C_D — 7		12 — M/S
R_D — 8		11 — $\overline{MUTE}$
$\overline{DP}$ — 9		10 — V_{SS}
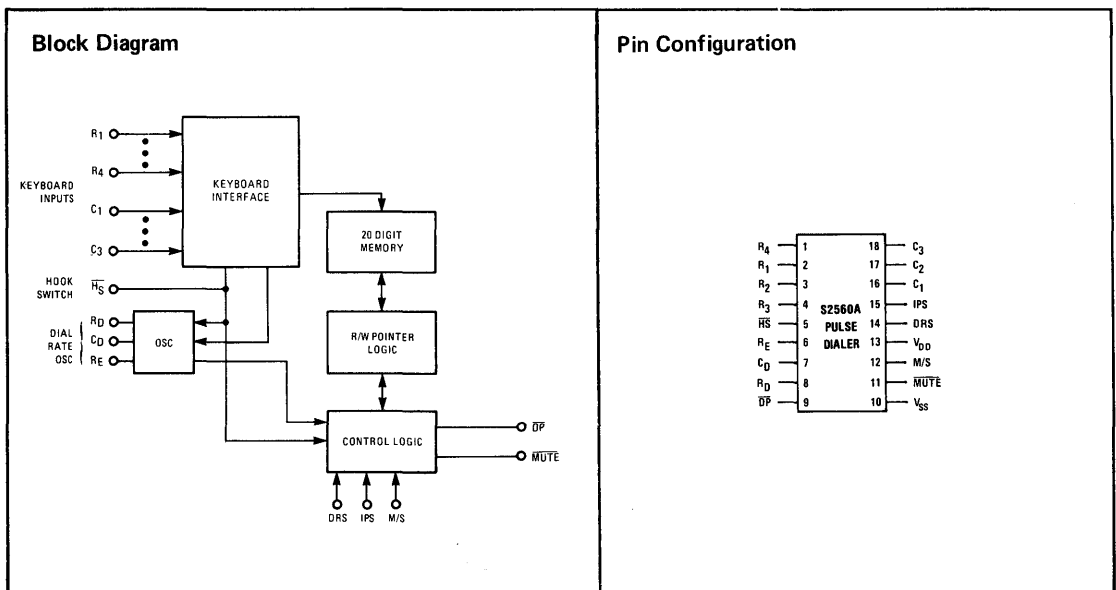
Absolute Maximum Ratings:

Supply Voltage .... +5.5V
Operating Temperature Range .... −25°C to +70°C
Storage Temperature Range .... −40°C to +125°C
Voltage at any Pin .... V_{SS} −0.3V to V_{DD} +0.3V
Lead Temperature (Soldering, 10sec) .... 300°C

Electrical Characteristics:

Specifications apply over the operating temperature and $1.5V \leqslant V_{DD}$ to $V_{SS} \leqslant 3.5V$ unless otherwise specified.

Symbol	Parameter	$V_{DD}-V_{SS}$ (Volts)	Min.	Max.	Units	Conditions
	Output Current Levels					
I_{OLDP}	$\overline{DP}$ Output Low Current (Sink)	3.5	125		µA	$V_{OUT} = 0.4V$
I_{OHDP}	$\overline{DP}$ Output High Current (Source)	1.5 3.5	20 125		µA µA	$V_{OUT} = 1V$ $V_{OUT} = 2.5V$
I_{OLM}	$\overline{MUTE}$ Output Low Current (Sink)	3.5	125		µA	$V_{OUT} = 0.4V$
I_{OHM}	$\overline{MUTE}$ Output High Current (Source)	1.5 3.5	20 125		µA µA	$V_{OUT} = 1V$ $V_{OUT} = 2.5V$
I_{OLT}	Tone Output Low Current (Sink)	1.5	20		µA	$V_{OUT} = 0.4V$
I_{OHT}	Tone Output High Current (Source)	1.5	20		µA	$V_{OUT} = 1V$
I_{DD}	Quiescent Current	1.5		750	nA	"On Hook" $\overline{HS} = V_{DD}$
I_{IL}, I_{IH}	Input Current Average (Keyboard Inputs)	3.5		60	µA	One row end one col. input connected to V_{DD}. Other keyboard inputs open.
I_{IL}, I_{IH}	Input Current Any Other Pin	3.5		100	nA	$V_{IN} = V_{SS}$ or V_{DD}
I_{DD}	Operating Current	1.5 3.5		100 500	µA µA	$\overline{DP}$, $\overline{MUTE}$ open, $\overline{HS} = V_{SS}$ ("Off Hook") Keyboard processing and dial pulsing at 10 pps at conditions as above
fo	Oscillator Frequency	1.5		10	kHz	
Δfo/fo	Frequency Deviation	1.5 to 2.5	−3	+3	%	Fixed R-C oscillator components $50k\Omega \leqslant R_D \leqslant 750k\Omega$; $100pF \leqslant C_D^* \leqslant 1000pF$;
		2.5 to 3.5	−3	+3	%	$750k\Omega \leqslant R_E \leqslant 5M\Omega$ *300pF most desirable value for C_D
	Input Voltage Levels					
V_{IH}	Logical "1"		0.8 $(V_{DD}-V_{SS})$	V_{DD} +0.3	V	
V_{IL}	Logical "0"		V_{SS} −0.3	0.2 $(V_{DD}-V_{SS})$	V	
C_{IN}	Input Capacitance Any Pin			7.5	pF	

The device power supply should always be turned on before the input signal sources, and the input signals should be turned off before the power supply is turned off ($V_{SS} \leqslant V_I \leqslant V_{DD}$ as a maximum limit). This rule will prevent over-dissipation and possible damage of the input-protection diode when the device power supply is grounded. When power is first applied to the device, the device should be in "On Hook" condition ($\overline{HS}=1$). This is necessary because there is no internal power or reset on chip and for proper operation all internal latches must come up in a known state. In applications where the device is hard wired in "Off Hook" ($\overline{HS}=0$) condition, a momentary "On Hook" condition can be presented to the device during power up by use of a capacitor resistor network as shown in Figure 6.

Functional Description

The pin function designations are outlined in Table 1.

Oscillator

The device contains an oscillator circuit that requires three external components: two resistors (R_D and R_E) and one capacitor (C_D). All internal timing is derived from this master time base. To eliminate clock interference in the talk state, the oscillator is only enabled during key closures and during the dialing state. It is disabled at all other times including the "on hook" condition. For a dialing rate of 10 pps the oscillator should be adjusted to 2400 Hz. Typical values of external components for this are R_D and R_E=750kΩ and C_D=270 pF. It is recommended that the tolerance of resistors to be 5% and capacitor to be 1% to insure a ±10% tolerance of the dialing rate in the system.

Keyboard Interface (2560A)

The S2560A employs a scanning technique to determine a key closure. This permits interface to a DPCT keyboard with common connected to V_{DD} (Figure 1), logic interface (Figure 2) and interface to a SPST switch matrix (Figure 7). A high level on the appropriate row and column inputs constitutes a key closure for logic interface. When using a SPST switch matrix, it is necessary to add small capacitors (30 pF) from the column inputs to V_{SS} to insure that the oscillator is shut off after a key is released or after the dialing is complete.

OFF Hook Operation: The device is continuously powered through a 150kΩ resistor during Off hook operation. The DP output is normally high and sources base drive to transistor Q_1 to turn ON transistor Q_2. Transistor Q_2 replaces the mechanical dial contact used in the rotary dial phones. Dial pulsing begins when the user enters a number through the keyboard. The $\overline{DP}$ output goes low shutting the base drive to Q_1 OFF causing Q_2 to open during the pulse break. The $\overline{MUTE}$ output also goes low during dial pulsing allowing muting of the receiver through transistors Q_3 and Q_4. The relationship of dial pulse and mute outputs are shown in Figure 3.

ON Hook Operation: The device is continuously powered through a 10—20MΩ resistor during the ON hook operation. This resistor allows enough current from the tip and ring lines to the device to allow the internal memory to hold and thereby providing storage of the last number dialed.

The dialing rate is derived by dividing down the dial rate oscillator frequency. Table 2 shows the relation-ship of the dialing rate with the oscillator frequency and the dial rate select input. Different dialing rates can be derived by simply changing the external resistor value. The dial rate select input allows changing of the dialing rate by a factor of 2 without the necessity of changing the external component values. Thus, with the oscillator adjusted to 2400Hz, dialing rates of 10 or 20 pps can be achieved. Dialing rates of 7 and 14 pps similarly can be achieved by changing the oscillator frequency to 1680Hz.

The Inter-Digit Pause (IDP) time is also derived from the oscillator frequency and can be changed by a factor of 2 by the IDP select input. With IDP select pin wired to V_{SS}, an IDP of 800ms is obtained for dial rates of 10 and 20 pps. IDP can be reduced to 400ms by wiring the IDP select pin to V_{DD}. At dialing rates of 7 and 14 pps, IDP's of 1143ms and 572ms can be similarly obtained. If the IDP select pin is connected to the dial rate select pin, the IDP is scaled to the dial rate such that at 10 pps an IDP of 800ms is obtained and at 20 pps an IDP of 400ms is obtained.

The user can enter a number up to 20 digits long from a standard 3x4 double contact keypad with common (Figure 1). It is also possible to use a logic interface as shown in Figure 2 for number entry. Antibounce protection circuitry is provided on chip (min. 20ms.) to prevent false entry.

Any key depressions during the on-hook condition are ignored and the oscillator is inhibited. This insures that the current drain in the on-hook condition is very low and used to retain the memory.

Normal Dialing

The user enters the desired numbers through the keyboard after going off hook. Dial pulsing starts as soon as the first digit is entered. The entered digits are stored sequentially in the internal memory. Since the device is designed in a FIFO arrangement, digits can be entered at a rate considerably faster than the output rate. Digits can be entered approximately once every 50ms while the dialing rate may vary from 7 to 20 pps. The number entered is retained in the memory for future redial. Pauses may be entered when required in the dial sequence by pressing the "#" key, which provides access pauses for future redial. Any number of access pauses may be entered as long as the total entries do not exceed twenty.

Auto Dialing

The last number dialed is retained in the memory and therefore can be redialed out by going off hook and pressing the "#" key. Dial pulsing will start when the key is depressed and finish after the entire number is dialed out unless an access pause is detected. In such a case, the dial pulsing will stop and will resume again only after the user pushes the "#" key.

Table 1. S2560A Pin/Function Descriptions

Pin	Number	Function
Keyboard (R_1, R_2, R_3, R_4, C_1, C_2, C_3)	7	These are 4 row and 3 column inputs from the keyboard contacts. These inputs are open when the keyboard is inactive. When a key is pushed, an appropriate row and column input must go to V_{DD} or connect with each other. A logic interface is also possible as shown in Figure 3. Active pull up and pull down networks are present on these inputs when the device begins keyboard scan. The keyboard scan begins when a key is pressed and starts the oscillator. Debouncing is provided to avoid false entry (typ. 20ms).
Inter-Digit Pause Select (IPS)	1	One programmable line is available that allows selection of the pause duration that exists between dialed digits. It is programmed according to the truth table shown in Table 3. Note that preceding the first dialed pulse is an inter-digit time equal to the selected IDP. Two pauses either 400ms or 800ms are available for dialing rates of 10 and 20 pps. IDP's corresponding to other dialing rates can be determined from Tables 2 and 3.
Dial Rate Select (DRS)	1	A programmable line allows selection of two different output rates such as 7 or 14 pps, 10 or 20 pps, etc. See Tables 2 and 3.
Mark/Space (MS)	1	This input allows selection of the mark/space ratio, as per Table 3.
Mute Out ($\overline{MUTE}$)	1	A pulse is available that can provide a drive to turn on an external transistor to mute the receiver during the dial pulsing.

Table 1. (Continued)

Pin	Number	Function
Dial Pulse Out ($\overline{\text{DP}}$)	1	Output drive is provided to turn on a transistor at the dial pulse rate. The normal output will be "low" during "space" and "high" otherwise.
Dial Rate Oscillator	3	These pins are provided to connect external resistors R_D, R_E and capacitor C_D to form an R-C oscillator that generates the time base for the Key Pulser. The output dialing rate and IDP are derived from this time base.
Hook Switch ($\overline{\text{HS}}$)	1	This input detects the state of the hook switch contact; "off hook" corresponds to V_{SS} condition.
Power (V_{DD}, V_{SS})	2	These are the power supply inputs. The device is designed to operate from 1.5V to 3.5V.
	18	

Figure 1. Standard Telephone Pushbutton Keyboard

R_{ON} (CONTACT RESISTANCE) ≤ 1kΩ

COMMON
(CONNECT TO V_{DD})

— — — MECHANICAL
LINKAGE
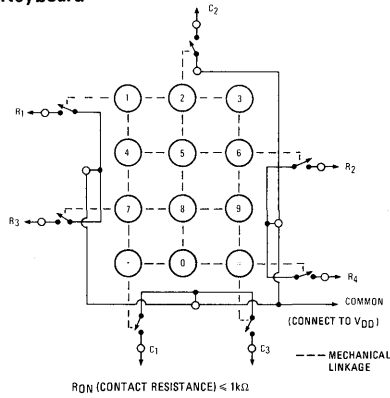
Figure 2. Logic Interface For the S2560

KEYBOARD
INPUTS

S2560
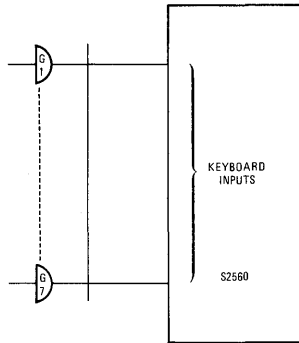
G1 through G7 any CMOS type logic gates

877292

Figure 3. Timing

LOOP CURRENT
DIAL PULSES

$\overline{DP}$

IDP

MARK

SPACE

IDP

$\overline{MUTE}$
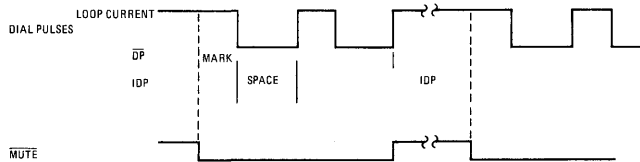
877293

Table 2. Table for Selecting Oscillator Component Values for Desired Dialing Rates and Inter-Digit Pauses

Dial Rate Desired	Osc. Freq. (Hz)	R_D (kΩ)	R_E (kΩ)	C_D (pF)	Dial Rate (pps)		IDP (ms)	
					DRS=V_{SS}	DRS=V_{DD}	IPS=V_{SS}	IPS=V_{DD}
5.5/11	1320				5.5	11	1454	727
6/12	1440				6	12	1334	667
6.5/13	1560				6.5	13	1230	615
7/14	1680	Select components in the			7	14	1142	571
7.5/15	1800	ranges indicated in table			7.5	15	1066	533
8/16	1920	of electrical specifications			8	16	1000	500
8.5/17	2040				8.5	17	942	471
9/18	2160				9	18	888	444
9.5/19	2280				9.5	19	842	421
10/20	2400	750	750	270	10	20	800	400
(f_d/240)/ (f_d/120)	f_d				(f_d/240)	(f_d/120)	$\left(\dfrac{1920}{f_i}\times10^3\right)$	$\left(\dfrac{960}{f_i}\times10^3\right)$

Notes:

1. IDP is dependent on the dialing rate selected. For example, for a dialing rate of 10 pps, an IDP of either 800ms or 400ms can be selected. For a dialing rate of 14 pps, and IDP of either 1142ms or 571ms can be selected.

Table 3.

Function	Pin Designation	Input Logic Level	Selection
Dial Pulse Rate Selection	DRS	V_{SS}	(f/240) pps
		V_{DD}	(f/120) pps
Inter-Digit Pause Selection	IPS	V_{DD}	$\dfrac{960}{f}$ s
		V_{SS}	$\dfrac{1920}{f}$ s
Mark/Space Ratio	M/S	V_{SS}	33-1/3/66-2/3
		V_{DD}	40/60
On Hook/Off Hook	$\overline{HS}$	V_{DD}	On Hook
		V_{SS}	Off Hook

Note: f is the oscillator frequency and is determined as shown in Figure 5.

Figure 4. Pulse Dialer Circuit with Redial

NOTE: PARTS REQUIRE COMMON OF THE KEYBOARD CONNECTED TO V_{DD}
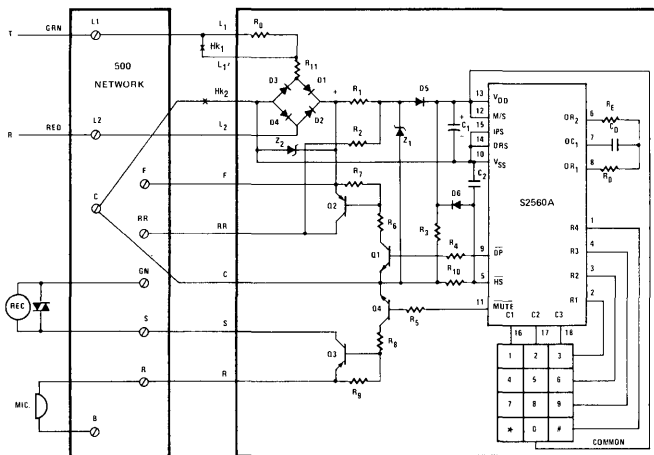
$R_0 = 10 - 20M\Omega$, $R_1 = 150k\Omega$, $R_2 = 2k\Omega$
$R_3 = 470k\Omega$, R_4, $R_5 = 10k\Omega$, $R_{10} = 47k\Omega$
R_6, $R_8 = 2k\Omega$, R_7, $R_9 = 30k\Omega$, $R_{11} = 20\Omega$, 2W
$Z_1 = 3.9V$, $D_1 - D_4 = $ IN4004, D_5, $D_6 = $ IN914, $C_1 = 15\mu F$
$R_E = R_D = 750k\Omega$, $C_D = 270pF$, $C_2 = 0.01\mu$ F
Q_1, $Q_4 = $ 2N5550 TYPE Q_2, $Q_3 = $ 2N5401 TYPE
$Z_2 = $ 1N5379 110V ZENER OR 2X1N4758

Figure 5. Pulse Dialer Circuit with Redial (Single Hook Switch Contact Application for PABX)

NOTE: PARTS REQUIRE COMMON OF THE KEYBOARD CONNECTED TO V_{DD}
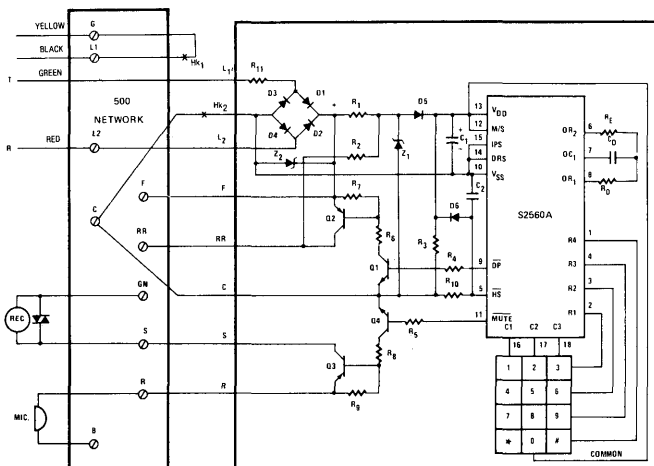
$R_1 = 10-20M\Omega$, $R_2 = 2k\Omega$
$R_3 = 470k\Omega$, R_4, $R_5 = 10k\Omega$
R_6, $R_8 = 2k\Omega$, R_7, $R_9 = 30k\Omega$
$R_{10} = 47k\Omega$, $R_{11} = 20\Omega$, 2W
$Z_1 = 3.9V$, $D_1 - D_4 = $ IN4004
D_5, $D_6 = $ 1N914, $C_1 = 15\mu$ F
R_E, $R_D = 750k\Omega$, $C_D = 270pF$
$C_2 = 0.01\mu F$, Q_1, $Q_4 = $ 2N5550
Q_2, $Q_3 = $ 2N5401
$Z_2 = $ 150V ZENER OR VARISTOR TYPE GE MOV150

Figure 6. Circuit for Applying Momentary "On Hook" Condition During Power Up
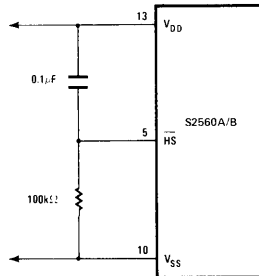
Figure 7. SPST Switch Matrix Interface

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COMMUNI-
CATIONS
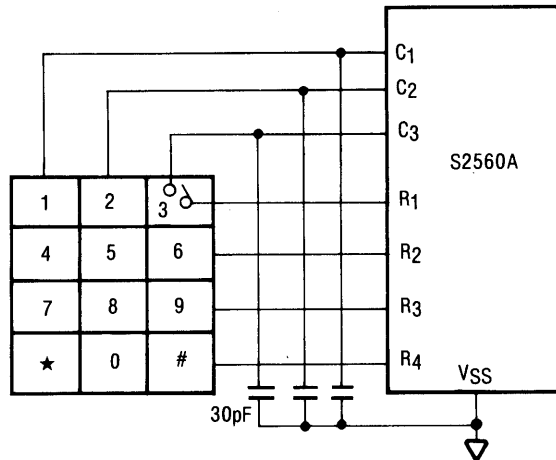
TONE RINGER

Features

- ☐ CMOS Process for Low Power Operation
- ☐ Operates Directly from Telephone Lines with Simple Interface
- ☐ Also Capable of Logic Interface for Non-Telephone Applications
- ☐ Provides a Tone Signal that Shifts Between Two Predetermined Frequencies at Approximately 16Hz to Closely Simulate the Effects of the Telephone Bell
- ☐ Push-Pull Output Stage Allows Direct Drive, Eliminating Capacitive Coupling and Provides Increased Power Output
- ☐ 25mW Output Drive Capability at 10V Operating Voltage

- ☐ Auto Mode Allows Amplitude Sequencing such that the Tone Amplitude Increases in Each of the First Three Rings and Thereafter Continues at the Maximum Level
- ☐ Single Frequency Tone Capability

General Description

The S2561 Tone Ringer is a CMOS integrated circuit that is intended as a replacement for the mechanical telephone bell. It can be powered directly from the telephone lines with minimum interface and can drive a speaker to produce sound effects closely simulating the telephone bell.

Data subject to change at any time without notice. These sheets transmitted for information only.

Block Diagram

*OPTIONAL OUTPUT FOR S2561C

Pin Configuration
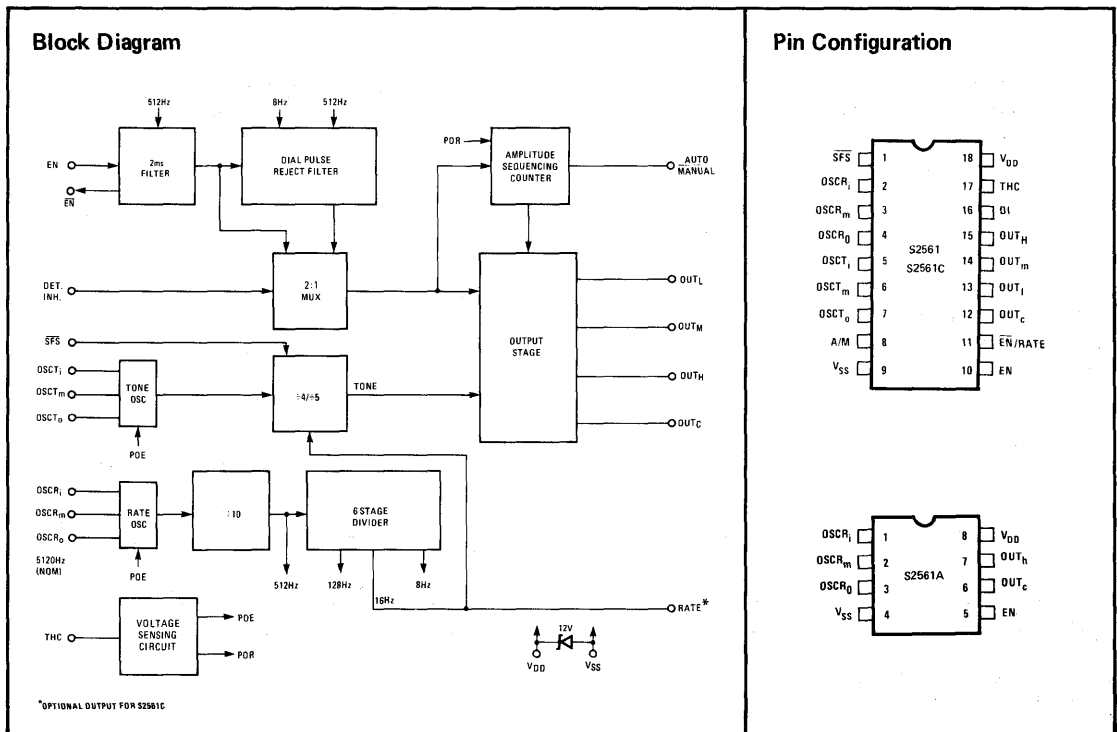
Absolute Maximum Ratings

Supply Voltage .... +12.0V*
Operating Temperature Range .... −25°C to +70°C
Storage Temperature Range .... −40°C to +125°C
Voltage at any Pin .... V_{SS} −0.3V to V_{DD} +0.3V
Lead Temperature (Soldering, 10sec) .... 300°C

This device incorporates a 12V internal zener diode across the VDD to VSS pins. Do NOT connect a low impedance power supply directly across the device unless the supply voltage can be maintained below 12V or current limited to <25mA.

Electrical Characteristics

Specifications apply over the operating temperature and $3.5V \leqslant V_{DD}$ to $V_{SS} < 12.0V$ unless otherwise specified.

Symbol	Parameter	Min.	Max.	Units	Conditions
V_{DS}	Operating Voltage (V_{DD} to V_{SS})	8.0	12.0	V	Ringing, THC pin open
V_{DS}	Operating Voltage	4.0		V	"Auto" mode, non-ringing
I_{DS}	Operating Current		500	µA	Non-ringing, V_{DD}=10V, THC pin open, DI pin open or V_{SS}
I_{OHC}	Output Drive Output Source Current (OUT_H, OUT_C outputs)	5		mA	V_{DD}=10V, V_{OUT}=8.75V
I_{OLC}	Output Sink Current (OUT_H, OUT_C outputs)	5		mA	V_{DD}=10V, V_{OUT}=0.75V
I_{OHM}	Output Source Current (Out_M output)	2		mA	V_{DD}=10V, V_{OUT}=8.75V
I_{OLM}	Output Sink Current (OUT_M output)	2		mA	V_{DD}=10V, V_{OUT}=0.75V
I_{OHL}	Output Source Current (OUT_L output)	1		mA	V_{DD}=10V, V_{OUT}=8.75V
I_{OLL}	Output Sink Current (OUT_L output)	1		mA	V_{DD}=10V, V_{OUT}=0.75V
	CMOS to CMOS				
V_{IH}	Input Logic "1" Level	$0.7 V_{DD}$	V_{DD}+0.3	V	All inputs
V_{IL}	Input Logic "0" Level	V_{SS}−0.3	$0.3 V_{DD}$	V	All inputs
V_{OHR}	Output Logic "1" Level (Rate output)	$0.9 V_{DD}$		V	I_O=10µA (Source)
V_{OLR}	Output Logic "0" Level (Rate output)		0.5	V	I_O=10µA (Sink)
V_{OZ}	Output Leakage Current (OUT_H, OUT_M outputs in high impedance state)		1 1	µA µA	V_{DD}=10V, V_{OUT}=0V V_{DD}=10V, V_{OUT}=10V
C_{IN}	Input Capacitance		7.5	pF	Any pin
$\Delta fo/fo$	Oscillator Frequency Deviation	−5	+5	%	Fixed RC component values $1M\Omega \leqslant R_{ri}$, $R_{ti} \leqslant 5M\Omega$; $100k\Omega \leqslant R_{rm}$, $R_{tm} \leqslant 750k\Omega$; $150pF \leqslant C_{ro}$, $C_{to} \leqslant 3000pF$; $330pF$ recommended value of C_{ro} and C_{to}, supply voltage varied from $9V \pm 2V$ (over temperature and unit-unit variations)
R_{LOAD}	Output Load Impedance Connected Across OUT_H and OUT_C	600		Ω	Tone Frequency Range=300Hz to 3400Hz
I_{IH}, I_L	Leakage Current, $V_{IN}=V_{DD}$ or V_{SS}		100	nA	Any input, except DI pin V_{DD}=10V
V_{TH}	POE Threshold Voltage	6.5	8	V	
V_Z	Internal Zener Voltage	11	13	V	I_Z=5mA

The device power supply should always be turned on before the input signal sources, and the input signals should be turned off before the power supply is turned off ($V_{SS} \leqslant V_I \leqslant V_{DD}$ as a maximum limit). This rule will prevent over-dissipation and possible damage of the input-protection diode when the device power supply is grounded

Functional Description

The S2561 is a CMOS device capable of simulating the effects of the telephone bell. This is achieved by producing a tone that shifts between two predetermined frequencies (512 and 640 Hz) with a frequency ratio of 5:4 at a 16 Hz rate.

Tone Generation: The output tone is derived from a tone oscillator that uses a 3 pin R-C oscillator design consisting of one capacitor and two resistors. The oscillator frequency is divided alternately by 4 or 5 at the shift rate. Thus, with the oscillator adjusted for 5120Hz, a tone signal is produced that alternates between 512Hz and 640Hz at the shift rate. The shift rate is derived from another 3 pin R-C oscillator which is adjusted for a nominal frequency of 5120Hz. It is divided down to 16Hz which is used to produce the shift in the tone frequency. It should be noted that in the special case where both oscillators are adjusted for 5120Hz, it is only necessary to have one external R-C network for one oscillator with the other oscillator driven from it. The oscillators are designed such that for fixed R-C component values an accuracy of ±5% can be obtained over the operating supply voltage, temperature and unit-unit variations. See Table 1 for component and frequency selections. In the single frequency mode, activated by connecting the $\overline{SFS}$ input to V_{SS} only the higher frequency continuous tone is produced by using a fixed divider ratio of 4 and by disabling the shift operation.

Ring Signal Detection: In the following description it is assumed that both the tone and rate oscillators are adjusted for a frequency of 5120 Hz. Ringing signal (nominally 42 to 105 VAC, 20 Hz, 2 sec on/4 sec off duty cycle) applied by the central office between the telephone line pair is capacitively coupled to the tone ringer circuitry as shown in Figure 2. Power for the device is derived from the ringing signal itself by rectification (diodes D1 thru D4) and zener diode clamping (Z_2). The signal is also applied to the EN input after limiting and clamping by a resistor (R_2) and internal diodes to V_{DD} and V_{SS} supplies. Internally the signal is first squared up and then processed thru a 2ms filter followed by a dial pulse reject filter. The 2ms filter is a two stage shift register clocked by a 512 Hz signal derived from the rate oscillator by a divide by 10 circuit. The squared ring signal (typically a square wave) is applied to the D input of the first stage and also to reset inputs of both stages. This provides for rejection of spurious noise spikes. Signals exceeding a duration of 2ms only can pass through the filter. The dial pulse reject filter is clocked at 8 Hz derived from the rate oscillator by a divide by 640 circuit. This circuit is designed

to pass any signal that has at least two transitions in a given 125ms time period. This insures that signals below 8 Hz will be rejected with certainty. Signals over 16 Hz will be passed with certainty and between 8 Hz and 16 Hz there is a region of uncertainty. By adjusting the rate oscillator to a different frequency the break points in frequencies can be varied. For instance for break points of 10 Hz and 20 Hz the rate oscillator can be adjusted to 6400 Hz. Of course this also increases the tone shift rate to 20 Hz. The action of the dial pulse reject filter minimizes the dial pulse interference during dialing although it does not completely eliminate it due to the rather large region of uncertainty associated with this type of discrimination circuitry. The dial pulse filter also has the characteristic that an input signal is not detected unless its duration exceeds 125ms. This insures that the tone ringer will not respond to momentary bursts of ringing less than 125 milliseconds in duration (Ref 1).

In logic interface applications, the 2ms filter and the dial pulse reject filter can be inhibited by wiring the Det. INHIBIT pin to V_{DD}. This allows the tone ringer to be enabled by a logic '1' level applied at the "ENABLE" input without the necessity of a 20Hz ring signal.

Voltage Sensing: The S2561 contains a voltage sensing circuit that enables the output stage and the rate and tone oscillators, only when the supply voltage exceeds a predetermined value. Typical value of this threshold is 7.3 volts. This produces two benefits. First, it insures that the audible intensity of the output tone is fairly constant throughout the ringing period; and secondly, it insures proper circuit operation during the "auto" mode operation by reducing the power consumption to a minimum when the supply voltage drops below 7.3 volts. This extends the supply voltage decay time beyond 4 seconds (off period of the ring signal) with an adequate filter capacitor and insures the proper functioning of the "amplitude sequencing" counter. It is important to note that the operating supply voltage should be well above the threshold value during the ringing period and that the filter capacitor should be large enough so that the ripple on the supply voltage does not fall below the threshold value. A supply voltage of 10 to 12 volts is recommended.

In applications where the tone ringer is continuously powered and below the threshold level, the internal threshold can be bypassed by connecting the THC pin to V_{DD}. The internal threshold can also be reduced

Functional Description (Continued)

by connecting an external zener diode between the THC and V_{DD} pins.

Auto Mode: In the "auto" mode, activated by wiring the "auto/manual" input to V_{SS}, an amplitude sequencing of the output tone can be achieved. Resistors R_L and R_M are inserted in series with the Out_L and Out_M outputs, respectively, and paralleled with the Out_H output (Figure 1). Load is connected across Out_H and Out_C pins. R_L is chosen to be higher than R_M. In this manner the first ring is of the lowest amplitude, second ring is of medium amplitude and the third and consecutive rings thereafter are at maximum amplitude. For the proper functioning of the "amplitude sequencing" counter the device must have at least 4.0 volts across it throughout the ring sequence. The filter capacitor is so chosen that the supply voltage will not drop below 4.0 volts during the off period. At the end of a ring sequence when the off period substantially exceeds the 4 second duration, the counter will be reset. This will insure that the amplitude sequencing will start correctly beginning a new ring sequence. The counter is held in reset during the "manual" mode operation. This produces a maximum ring amplitude at all times.

Output Stage: The output stage is of push-pull type

consisting of buffers L, M, H and C. The load is connected across pins Out_H and Out_C (Figure 2). During ringing, the Out_H and Out_C outputs are out of phase with each other and pulse at the tone rate. During a non-ringing state, all outputs are forced to a known level such as ground which insures that there is no DC component in the load. Thus, direct coupling can be used for driving the load. The major benefit of the push-pull arrangement is increased power output. Four times as much power can be delivered to the load for the same operating voltage. Buffers M and H are three-state. In the "auto" mode buffer M is active only during the second ring and in the "high impedance" state at all other times. Buffer H is active beginning the third ring. In the "manual" mode buffers H, L and C are active at all times while buffer M is in a high impedance state. The output buffers are so designed that they can source or sink 5mA at a V_{DD} of 10 volts without appreciable voltage drop. Care has been taken to make them symmetrical in both source and sink configurations. Diode clamping is provided on all outputs to limit the voltage spikes associated with transformer drive in both directions V_{DD} and V_{SS}.

Normal protection circuits are present on all inputs.

Table 1. S2561/S2561C Pin/Function Descriptions

Pin	Number	Function
Power (V_{DD}*, V_{SS}*)	2	These are the power supply pins. The device is designed to operate over the range of 3.5 to 12.0 volts. A range of 10 to 12 volts is recommended for the telephone application.
Ring Enable (EN*, $\overline{EN}$)	2	These pins are for the 20Hz ring enable input. They can also be used for DC level enabling by wiring the DI pin to V_{DD}. $\overline{EN}$ is available for the S2561 only.
Auto/Manual (A/M)	1	"Auto" mode for amplitude sequencing is implemented by wiring this pin to V_{SS}. "Manual" mode results when connected to V_{DD}. The amplitude sequencing counter is held in reset during the "manual" mode.
Outputs (Out_L, Out_M, Out_H^*, Out_C^*)	4	These are the push-pull outputs. Load is directly connected across Out_H and Out_C outputs. In the "auto" mode, resistors R_L and R_M can be inserted in series with the Out_L and Out_M outputs for amplitude sequencing (see Figure 1).
Oscillators Rate Oscillator ($OSCR_i^*$, $OSCR_m^*$ $OSCR_o^*$)	3	These pins are provided to connect external resistors RR_i, RR_m and capacitor CR_o to form an R-C oscillator with a nominal frequency of 5120Hz. See Table 2 for components selection.

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Table 1 (Continued)

Pin	Number	Function
Tone Oscillator (OSCT$_i$, OSCT$_m$, OSCT$_0$)	3	These pins are provided to connect external resistors RT$_i$, RT$_m$ and capacitor CT$_0$ to form an R-C oscillator from which the tone signal is derived. With the oscillator adjusted to 5120Hz, a tone signal with frequencies of 512Hz and 640Hz results. See Table 2 for components selection.
Threshold Control (THC)	1	The internal threshold voltage is brought out to this pin for modification in non-telephone applications. It should be left open for telephone applications. For power supplies less than 9V connect to V$_{DD}$.
Rate	1	This is an optional output for the S2561C version which replaces the $\overline{EN}$ output. This is a 16Hz output that can be used by external logic as shown in Figure 3-A to produce a 2sec on/4sec off waveform.
Detector Inhibit (DI)	1	When this pin is connected to V$_{DD}$, the dial pulse reject filter is disabled to allow DC level enabling of the tone ringer. This pin should be hardwired to V$_{SS}$ in normal telephone-type applications.
Single Frequency Select ($\overline{SFS}$)	1	When this pin is connected to V$_{SS}$, only a single frequency continuous tone is produced as long as the tone ringer is enabled. In normal applications this pin should be hardwired to V$_{DD}$.
	$\overline{18}$	

Pinouts of 8 pin S2561A package.

Table 2. Selection Chart for Oscillator Components and Output Frequencies

Tone/Rate Oscillator Frequency (Hz)	Oscillator Components			Rate (Hz)	Tone (Hz)
	R$_I$ (kΩ)	R$_M$ (kΩ)	C$_O$ (pF)		
5120	1000	200	330	16	512/640
6400				20	640/800
3200	Select components in the ranges indicated in the table of electrical charateristics			10	320/400
8000				25	800/1000
fo				$\frac{fo}{320}$	$\frac{fo}{10}\Big/\frac{fo}{8}$

Applications

Typical Telephone Application: Figure 2 shows the schematic diagram of a typical telephone application for the S2561 tone ringer circuit. Power is derived from the telephone lines by the network formed by capacitor C_1, resistor R_1, diode bridge d_1 through d_4, and filter capacitor C_2. C_2 is chosen to be large enough so as to insure that the power supply ripple during ringing does not fall below the internal threshold level (typ. 7.3 volts) and to provide large enough decay time during the off period. A typical value of C_2 may be $47\mu F$. C_1 and R_1 are chosen to satisfy the Ringer Equivalence Number (REN) specification (Ref. 1). For REN = 1 the resistor should be a minimum of $8.2k\Omega$. It must be noted that the amount of power that can be delivered to the load depends upon the selection of C_1 and R_1.

The device is enabled by limiting the incoming ring signal through resistors R_2, R_3 and diodes d_5 and d_6. Zener diode Z_1 (typ. 9-27 volts) may be required in certain applications where large voltage transients may occur on the line during dial pulsing. The internal 2ms filter and the dial pulse reject filter will suppress any undesirable components of the signal and will only respond to the normal 20Hz ring signal. Ring signals with frequencies above 16Hz will be detected.

The configuration shown will produce a tone with frequency components of 512Hz and 540 Hz with a shift rate of approximately 16 Hz and deliver at least 25mW to an 8Ω speaker through a $2000\Omega{:}8\Omega$ transformer. If "manual" mode is used, a potentiometer may be inserted in series with the transformer primary to provide volume control. If "automatic" mode is used, resistors R_L and R_M can be chosen to provide desired amplitude sequencing. Typically, signal power will be down $20 \log \left(\dfrac{R_{LOAD}}{R_L + R_{LOAD}} \right)$ dB during the first ring, and down $20 \log \left(\dfrac{R_{LOAD}}{R_M + R_{LOAD}} \right)$ dB during the second ring with maximum power delivered to the load beginning the third and consecutive rings.

In applications where dial pulse rejection is not necessary, such as in DTMF telephone systems, the ENABLE pin may be connected directly to V_{DD}. Det. Inh pin must be connected to V_{DD} to allow DC level enabling of the ringer.

Non-Telephone Applications: The configuration shown in Figure 3-A may be used in non-telephone applications where it is desired to simulate the telephone bell. The internal threshold is bypassed by wiring THC to V_{DD}. The rate output (16Hz) is divided down by a 7 stage divider type 4024 to produce two signals: a 2 second on/2 second off signal and a 4 second on/4 second off signal. The first signal is connected to the EN pin and the second to the DI pin to produce a 2 second on/4 second off telephone-type ring signal. The ring sequence is initiated by removing the reset on the divider. If "auto" mode is used, a reset signal must be applied to the "amplitude sequencing" counter at the end of a ring sequence so that the circuit will respond correctly to a new ring sequence. This is done by temporarily connecting the "auto/manual" input to V_{SS}.

Figure 3-B shows a typical application for alarms, buzzers, etc. Single frequency mode is used by connecting the $\overline{SFS}$ input to V_{SS}. A suitable on/off rate can be determined by using the 7 stage divider circuit. If continuous tone is not desired, the 16Hz output can be used to gate the tone on and off by wiring it into the ENABLE input.

Many other configurations are possible depending upon the user's specific application.

Reference 1. Bell system communications technical reference:

PUB 47001 of August 1976
"Electrical characteristics of Bell System Network Facilities at the interface with Voiceband Ancillary and Data Equipment" — Sections 2.6.1 and 2.6.3.

Figure 1-A. Output Stage Connected for Auto Mode Operation
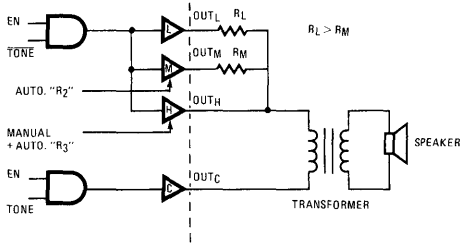
877276

Figure 1-B. Output Stage Connected for Manual Mode Operation.
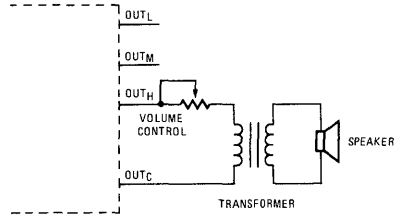
877277

Figure 2. Typical Telephone Application of the S2561 and S2561A
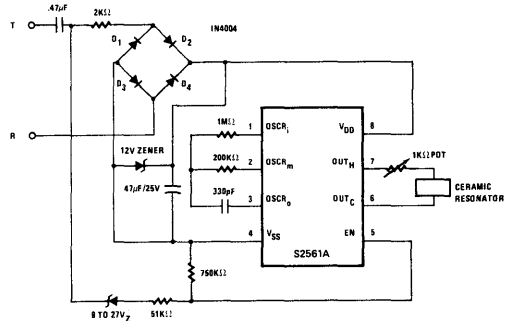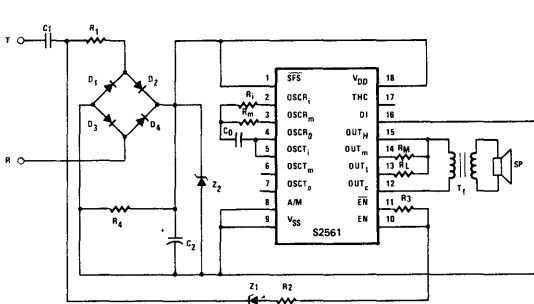
C_1	.47µF/200V	R_1	2KΩ	R_i	1MΩ	R_L	18KΩ	SP	8ΩSPEAKER	
C_2	.47µF/25V	R_2	51KΩ	R_m	200KΩ	R_M	3.3KΩ	T_1	2000Ω/8ΩXFMR	
D_1–D_4	1N4004	R_3	10MΩ	C_0	300pF	R_4	100KΩ	Z_1	9 TO 27V ZENER	
Z_2	1N4742 12V ZENER									

2.45

Figure 3-A. Simulation of the Telephone Bell in Non-Telephone Applications.
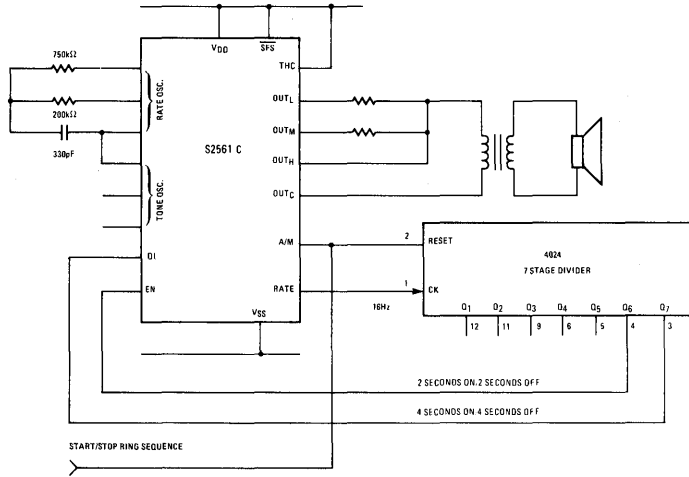
Figure 3-B. Single Frequency Tone Application in Alarms, Buzzers, Etc.

AMI

AMERICAN MICROSYSTEMS, INC.
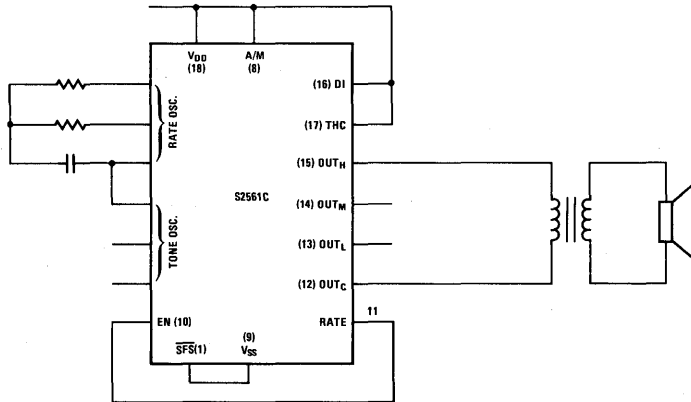
REPERTORY DIALER

COMMUNICATIONS

Features

☐ CMOS Process Achieves Low Power Operation

☐ 8 or 16 Digit Number Capability (Pin Programmable)

☐ Dial Pulse and Mute Output

☐ Tone Outputs Obtained by Interfacing with Standard AMI S2559 Tone Generator

☐ Two Selections of Dial Pulse Rate

☐ Two Selections of Inter-Digit Pause

☐ Memory Storage of 32 8-Digit Numbers or 16 16-Digit Numbers with Standard AMI S5101 RAM

☐ 16-Digit Memory for Input Buffering and for Redial with Access Pause Capability

☐ Accepts the Standard Telephone DPCT Keypad or SPST Switch X-Y Matrix Keyboards; Also Capable of Logic Interface

☐ Ignores Multi Key Entries

☐ Inexpensive, but Accurate R-C Oscillator Design

☐ Provides Better Than ± 3% Accuracy Over Supply Voltage, Temperature and Unit-Unit Variations and Allows Different Dialing Rates, IDP and Tone Drive Timing by Changing the Time Base

☐ Power Fail Detection

☐ BCD Output with Update for Number Display Applications

General Description

The S2562 Repertory Dialer is a CMOS integrated circuit that can perform storing or retrieving, normal dialing, redialing or auto dialing and displaying of one of several telephone numbers. It is intended to be used with the AMI standard S5101—256x4 RAM that functions as telephone number storage. With one S5101 up to 32 8-digit or 16 16-digit numbers can be stored. It can provide either dial pulses or DTMF tones with the addition of the AMI S2559 tone generator for either the dial or tone line applications.

Data subject to change at any time without notice. These sheets transferred for information only.

Block Diagram

Pin Configuration

877283
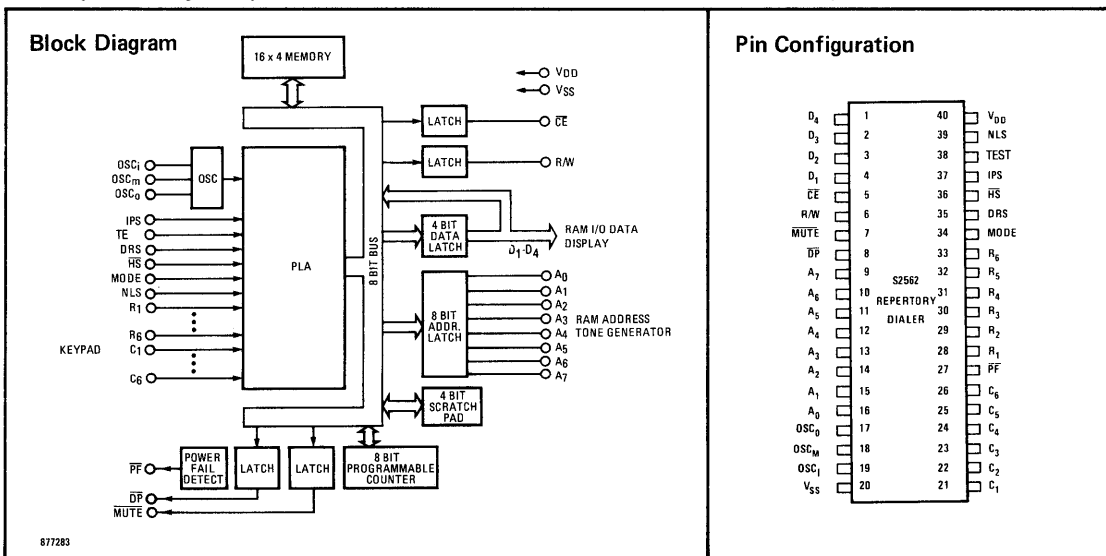
Absolute Maximum Ratings:

Supply Voltage 13.5V
Operating Supply Voltage Range ($V_{DD}-V_{SS}$) .... 3.5V to 7.5V
Operating Temperature Range .... $-25°C$ to $+70°C$
Storage Temperature Range .... $-40°C$ to $+125°C$
Voltage at any Pin .... V_{SS} $-0.3V$ to V_{DD} $+0.3V$
Lead Temperature (Soldering, 10 sec) .... 200°C

Electrical Characteristics:

Specifications apply over the operating temperature range and $4.5V \leqslant V_{DD}$ to $V_{SS} \leqslant 5.5V$ unless otherwise specified. Absolute values of measured parameters are specified.

Symbol	Characteristics	Min.	Max.	Units	Conditions
	Output Drive				
I_{OLDP}	$\overline{DP}$ Output Sink Current	400		μA	$V_{OUT}=0.4V$, $V_{DD}=5V$
I_{OHDP}	$\overline{DP}$ Output Source Current	400		μA	$V_{OUT}=3.6V$, $V_{DD}=5V$
I_{OLM}	$\overline{MUTE}$ Output Sink Current	400		μA	$V_{OUT}=0.4V$, $V_{DD}=5V$
I_{OHM}	$\overline{MUTE}$ Output Source Current	400		μA	$V_{OUT}=3.6V$, $V_{DD}=5V$
I_{OHPF}	$\overline{PF}$ Output Source Current	100		μA	$V_{OUT}=3.6V$, $V_{DD}=5V$
	CMOS to CMOS				
V_{IL}	Logic "0" Input Voltage		1.5	V	All inputs, $V_{DD}=5V$
V_{IH}	Logic "1" Input Voltage	3.5		V	All inputs, $V_{DD}=5V$
V_{OL}	Logic "0" Output Voltage		0.5	V	All outputs except $\overline{DP}$, $\overline{MUTE}$, $\overline{PF}$, $I_O = -10\mu A$, $V_{DD}=5V$
V_{OH}	Logic "1" Output Voltage	4.5		V	All outputs except $\overline{DP}$, $\overline{MUTE}$, $\overline{PF}$, $I_O = -10\mu A$, $V_{DD}=5V$
	Current Levels				
I_{DD}	Quiescent Current		25	μA	Standby, $V_{DD}=5V$
I_{DD}	Operating Current		500	μA	All valid input combinations, $\overline{DP}$, $\overline{MUTE}$, $\overline{PF}$ outputs open $V_{DD}=5V$
I_{IH}	Input Current Any Pin (keyboard inputs)	10	100	μA	$V_{IN}=V_{DD}$, $V_{DD}=5V$
I_{IL}, I_{IH}	Input Current All Other Pins		100	μA	$V_{IN}=V_{SS}$ or V_{DD}, $V_{DD}=5V$
I_{OZ}	Output Current in High Impedance State		1	μA	$V_{DD}=5V$, $V_{OUT}=0V$ data outputs (D1-D4)
			1	μA	$V_{DD}=5V$, $V_{OUT}=5V$
fo	Oscillator Frequency	4	10	kHz	$V_{DD}=5V$ (min. duty cycle 30/70)
Δfo/fo	Frequency Deviation	-3	$+3$	%	$V_{DD}-V_{SS}$ from 4.5V to 5.5V. Fixed R-C oscillator components $50k\Omega \leqslant R_M \leqslant 750k\Omega$; $1M\Omega \leqslant R_I \leqslant 5M\Omega$; $150pF \leqslant C_O$ 3000pF; 330pF most desirable value for C_O, fo < 10kHz over the operating temperature and unit-unit variations
C_{IN}	Input Capacitance, Any Pin		7.5	pF	
V_{TRIP}	Supply Voltage at which $\overline{PF}$ Output Goes Low	2.5	4.5	V	

The device power supply should always be turned on before the input signal sources, and the input signals should be turned off before the power supply is turned off ($V_{SS} \leqslant V_I \leqslant V_{DD}$ as a maximum limit). This rule will prevent over-dissipation and possible damage of the input-protection diode when the device power supply is grounded. Power should be applied to the device in "on hook" condition.

Functional Description

The S2562 is a CMOS controller designed for storing or retrieving, normal dialing, redialing or auto dialing and displaying of one of several telephone numbers. It is intended to be used with the AMI standard S5101 256x4 RAM that functions as a telephone number storage. A single S5101 RAM will store up to 32 8-digit or 16 16-digit telephone numbers. The S2562 can be programmed to work with either 8-digit or 16-digit numbers by means of the Number Length Select (NLS) input.

The S2562 uses an inexpensive, but accurate R-C oscillator as a time base from which the dialing rate and inter-digit pause duration (IDP) are derived. Different dialing rates and IDP durations can be implemented by simply adjusting the oscillator frequency. The dialing rate and IDP can be further changed by a 2:1 factor by means of the dialing rate select (DRS) and inter-digit pause select (IPS) inputs. Thus, for the oscillator frequency of 8kHz, dialing rates of 10 and 20 pps and IDP's of 400 and 800ms can be achieved. The mark/space ratio is fixed independent of the time base at 40/60. Over supply voltage (5V±10%), operating temperature range and unit-unit variations, timing accuracy of ±3% can be achieved. A mute output is also available for muting of the receiver during dial pulsing. See Figure 5 for timing relationship.

The S2562 can be programmed by means of the MODE input for dual tone signaling applications as well. In this mode, it can interface directly with the AMI standard S2559 Tone Generator to produce the required DTMF signals. The tone on/off rate during an auto dial operation in this mode is derived from the time base. For the oscillator frequency of 8kHz, a tone drive rate of 50ms on, 50ms off is obtained. Different rates can be implemented by adjusting the time base as desired. See Tables 2 and 3 for the various combinations. In the tone mode, the mute output is used to gate the tone generator on and off. The 8 address lines that are normally used for addressing the RAM are also used to address the tone generator row, column inputs. Figure 6 shows a typical system application.

The S2562 can perform the following functions:

Normal Dialing

The user enters the desired number digits through the keyboard after going off hook. Dial pulsing starts as soon as the first digit is entered. The entered digits are stored sequentially in the internal memory. Since the device is designed in a FIFO arrangement, digits can be entered at a rate considerably faster than the output rate. Digits can be entered approximately once every 50ms while the dialing rate may vary from 7 to 20 pps. Debouncing is provided on the keyboard entries to avoid false entries. The number entered is retained for future redial. Pauses may be entered when required in the dial sequence by pressing the "#" key, which provides access pauses for future redial. Any number of access pauses may be entered as long as the total entries do not exceed the total number of digits (8 or 16).

An update pulse is generated to update the display digit as a new entry is made.

Redialing

The last number entered is retained in the internal memory and can be redialed by going "off hook" and depressing the "redial" (RDL) key. The RDL key is a unique 2 of 12 matrix location (R5, C3). The number being redialed out is displayed as it is dialed out.

In the tone mode, the redial tone drive rate depends upon the time base as discussed before.

Storing of a Normally Dialed or Redialed Number into the External Memory

After the normal dialing or redialing operation, the telephone number can be stored in the external memory for future repertory dialing use by going on hook and initiating the following key sequence.

1. Push "store" (ST) button.
2. Depress the single digit key corresponding to the desired address location.

Note that the "ST" key is a unique 2 of 12 matrix location (R_5, C_1).

Storing of a Telephone Number into the External Memory

This operation is performed "on hook" and no outdialing occurs. A telephone number can be stored in the desired address location by initiating the following key sequence.

1. Push the "*" key (This instructs the device to accept a new number for storage into the internal memory).
2. Enter the digits (including any access pauses) corresponding to the desired number. Digits will be displayed as they are entered.
3. Push the "ST" key.
4. Push the single digit key corresponding to the desired address location.

The entire sequence can be repeated to store as many numbers as desired. However, any memory locations not addressed with a telephone number "store" operation must be addressed with the following sequence.

1. Push the "*" key.
2. Push the "ST" key.
3. Push the single digit key corresponding to the first unused memory location.
4. Push the "ST" key.

5. Push the single digit key corresponding to the next unused memory location.

Steps 4. and 5. are repeated until all remaining memory locations have been addressed.

It should be noted that accessing all memory locations is required only for initial system set-up. This insures that no memory location will contain invalid data from memory power-up. If a memory location were to have invalid, power-up induced data and that location was addressed by the S2562, the S2562 would enter a "Halt" state and cease its normal program activities. To exit from this condition it is necessary to go "on hook" and perform a "store" operation.

Displaying of a Stored Telephone Number

This is an "on hook" operation Either the last dialed number or the number stored in the external memory can be displayed one digit at a time. The key sequence for displaying the last dialed number is as follows:

Push the "RDL" key.

The number in the external memory can be displayed as follows:

1. Push the "R" key.
2. Push the single digit key corresponding to the desired address location.

Note that the "R" key is a unique 2 of 12 matrix location (R_5, C_2).

The number is displayed one digit at a time at a rate determined by the time base. With a time base of 8kHz the display will be on 500ms, off 500ms. The display is updated by producing an update pulse. The update pulse must be decoded with external logic (one inverter and one 2-input gate) as shown in Figure 6.

The display is blanked by outputting an illegal (non BDC) code such as 1111. The 4511-type BCD to 7 segment decoder driver latch will blank the display when the illegal code is detected. When other driver circuits are employed, external logic must be used to detect the illegal code. Table 4 gives a list of display codes used by S2562.

Repertory Dialing

This is the most common mode of usage and allows the user to dial automatically any number stored in the memory. This mode is initiated by the following key sequence after going off hook.

1. Push the "*" key.
2. Push the single digit key corresponding to the desired address location.

The number is displayed as it is dialed out. In the tone mode, the tone driver rate is dependent on the time base as described earlier.

Pause

Note that the out dialing in the repertory or redial operation continues unless an access pause is detected. The outpulsing will stop and resume only when the user terminates the access pause by pushing the "*" key again.

Power Fail Detection

This output is normally high. When the supply voltage falls below a predetermined value, it goes low. The output can then drive a suitable latching device that will switch the memory to either the tip and ring or an auxiliary battery supply.

Memory Expansion

The memory can be expanded by paralleling additional S5101 RAM's. External logic must be used to enable the desired RAM corresponding to a desired address location. The S2562 can drive up to 2 RAM's without the need of buffering address and data lines.

Keybounce Protection

When a key closure is detected by the S2562, an internal timeout (4ms at fo=8kHz) is started. Any transitions that occur during this timeout will reset the timer to zero so that a key will only be accepted as valid after a noise free timeout period. The key must remain closed for an additional 16ms before released. Thus, the total make time of the key must be at least 20ms. The key must be released for at least 1ms before a new key is activated. Any transitions occurring when the key is released are ignored as long as the make time does not exceed 4ms.

Keyboard Entry Options

Figure 4 shows two options for arrangement of a keyboard for dialing of 32, 8 digit or 16, 16 digit numbers. A single S5101 memory is sufficient for number storage in the basic scheme.

Increasing Number Capacity

To increase the capacity from 16, 16 digit numbers to 32, 16 digit numbers, an additional memory must be used. Since in the 16 digit mode, the S2562 decodes keys in locations 17 through 32 as locations 1 through 16, the additional memory can be simply paralleled with the first memory. Note that keys 17 through 32 are in row 6 and columns 5 and 6. This permits use of a simple decoder to separate the keys into two address fields. A latch then can be set or reset depending upon the location of the key. The outputs of the latch can then directly select the appropriate memory via CE_2 pin of each memory. Capacity can also be increased to 64, 8 digit numbers by paralleling of two 32 key keyboards and two 5101 RAM's selection of appropriate memory can be done as indicated above.

AMI.

Table 1. Pin/Function Descriptions

Pin	Number	Function
Power (V_{DD}, V_{SS})	2	These are the power supply inputs. The device is designed to operate from 3.5V to 7.5V.
Keyboard (R_1-R_6, C_1-C_6)	12	These are 6 row and 6 column inputs from the keyboard contacts. When a key is pushed, an appropriate row and column input must go to V_{DD} or connect to each other. Figures 1 and 2 depict the standard telephone DPCT and X-Y matrix keyboard arrangements that can be used. A logic, interface is also possible as shown in Figure 3. Debouncing is provided to avoid false entry. Key pad entry options are shown in Figure 4.
Number Length Select (NLS)	1	This input permits programming of the device to accept either 8-digit numbers or 16-digit numbers.
Mode Select (MODE)	1	This input allows the use of the device in either dial pulsing applications or tone drive applications.
Dial Rate Select (DRS)	1	This input allows selection of two different dialing rates such as 10 or 20 pps, 7 or 14 pps, etc. See Tables 2 and 3.
Inter-Digit Pause Select (IPS)	1	This allows selection of the pause duration that exists between dialed digits. It is programmed according to the truth table shown in Table 3. Note that preceeding the first dialed digit is an inter- digit time equal to the selected IDP. Two pause durations, either 400ms or 800ms are available at dialing rates of 10 and 20 pps. IDP's corresponding to other dialing rates can be determined from Tables 2 and 3.
Test Input (TEST)	1	This input is used for test purposes. For normal operation it must be tied to V_{DD}.
Mute Output ($\overline{MUTE}$)	1	A pulse is available that can provide drive to turn on an external transistor to mute the receiver during dial pulsing. See Figure 5 for mute and dial pulse output relationship. It is also used as a keyboard disable in the tone drive applications. See Figure 6.
Dial Pulse Output ($\overline{DP}$)	1	Output drive is provided to turn on a transistor at the dial pulse rate. This output will be normally high and go low during "space" or "break."
Display Memory I/O Data (D_1-D_4)	4	These are 4 bidirectional pins for inputting and outputting data to the external memory and display driver.

Table 1. (Continued)

Pin	Number	Function
Memory Enable ($\overline{CE}$)	1	This line controls the external memory operation.
Memory Read/Write (R/W)	1	This line controls the read or the write operation of the external memory. This output along with the $\overline{CE}$ output can be used to produce a pulse to update the external display. See Figure 6.
Tone Generator/Memory Address (A_0-A_7)	8	These are 8 output lines that carry the external memory address and tone generator row/column information.
Hook Switch ($\overline{HS}$)	1	This input conveys the state of the subset. "Off hook" corresponds to V_{SS} condition.
Power Fail Detect ($\overline{PF}$)	1	This output is normally high and goes low when the power supply falls below a certain predetermined value.
Oscillator (OSC_i, OSC_m, OSC_o)	3	These pins are provided to connect external resistors R_I, R_M and capacitor C_O to form an R-C oscillator that generates the time base for the repertory dialer. The output dialing rate, tone drive rate and IDP are derived from this time base.
	40	

Table 2. Table for Selection of Oscillator Component Values for Desired Dialing Rate, I_{DP} or Tone Drive Rate

Dial Rate Desired (PPS)	Osc. Freq. fo (Hz)	Oscillator Components			Dial Rate (PPS)		IDP (ms)		Tone Drive On/Off Time (ms)
		R_M (kΩ)	(R_I) (kΩ)	C_O (pF)	DRS=V_{SS}	DRS=V_{DD}	IPS=V_{SS}	IPS=V_{DD}	
5.5/11	4400	TBD			5.5	11	1454	727	90/90
6/12	4800	220			6	12	1334	667	83.3/83.3
6.5/13	5200	190			6.5	13	1230	615	77/77
7/14	5600				7	14	1142	571	71/71
7.5/15	6000		1000	300	7.5	15	1066	533	66.7/66.7
8/16	6400				8	16	1000	500	62.5/62.5
8.5/17	6800	TBD			8.5	17	942	471	59/59
9/18	7200				9	18	888	444	55.5/55.5
9.5/19	7600				9.5	19	842	421	52.6/52.6
10/20	8000	110			10	20	800	400	50/50
(fo/800/ (fo/400)	fo				fo/800	fo/400	$\frac{6400 \times 10^3}{fo}$	$\frac{3200 \times 10^3}{fo}$	$\frac{400 \times 10^3}{fo}$ / $\frac{400 \times 10^3}{fo}$

Figure 1. Standard Telephone Pushbutton Keyboard

RON (CONTACT RESISTANCE) ≤ 1kΩ
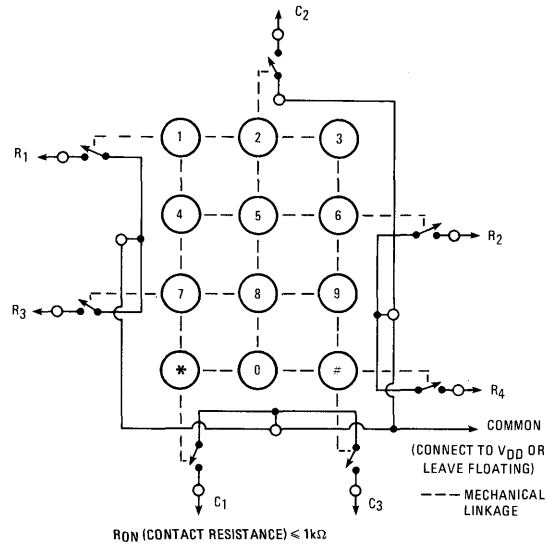
877290

Figure 2. SPST Matrix Keyboard Arranged in the 2 of 12 Row, Column Format
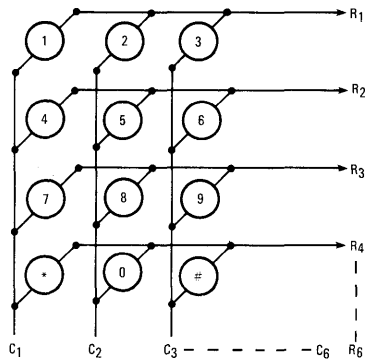
SPST MATRIX KEYBOARD:

877285

2.53
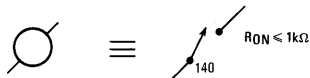
Figure 3. Logic Interface For the S2562
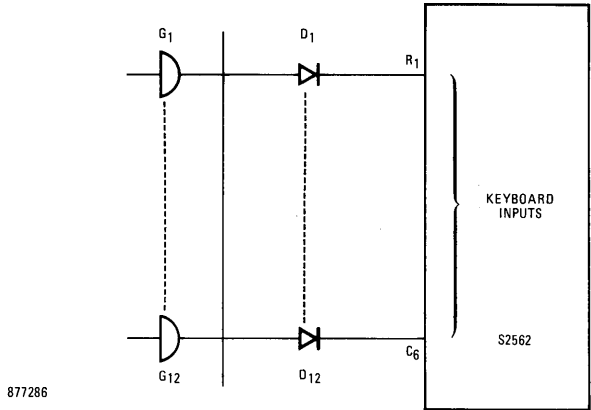
877286

G_1 through G_{12} any CMOS type logic gates.
D_1 through D_{12} DIODES type 1N 914. (Optional)

A valid key closure corresponds to a logic high level on one row and one column

Figure 4. Example of Keypad Entry — Options

OPTION FOR 16,
16 DIGIT NUMBERS
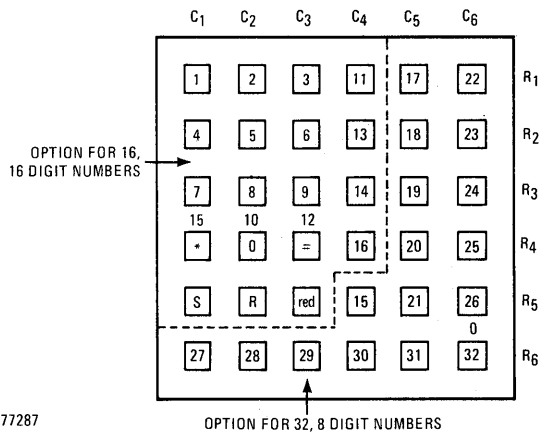
877287

OPTION FOR 32, 8 DIGIT NUMBERS

Table 3

Function	Pin Designation	Input Logic Level	Selection
Dial Rate Selection	DRS	V_{SS} V_{DD}	(fo/800) pps (fo/400) pps
Inter-Digit Pause Selection	IPS	V_{DD} V_{SS}	(3200/fo) S (6400/fo) S
Test Input	TEST	V_{SS} V_{DD}	Test Mode Normal Mode
Hook Switch	$\overline{HS}$	V_{DD} V_{SS}	On Hook Off hook
Mode Selection	MODE	V_{SS} V_{DD}	Dial pulse Tone Drive*
Number Length Selection	NLS	V_{SS} V_{DD}	8 digits 16 digits

*For tone mode also set DRS=V_{SS}, IPS=V_{SS} and Test=V_{DD}.
Note: fo is the oscillator frequency and is determined as shown in Table 2.

Figure 5A. Mute and Dial Pulse Output Timing Relationship

Mute will reset i) when the number of digits dialed out equals either the number of digits entered or the maximum
selected (8 or 16) or ii) when an access pause is detected.
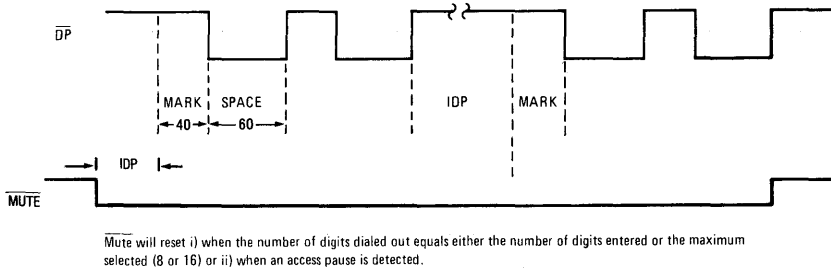
Figure 5B. Mute and Tone Output Timing Relationship

Mute output will reset i) when the number of digits dialed out equals the number of digits entered or equals the maximum selec-
ted (8 or 16) or ii) when an access pause is detected. In the normal dialing mode when digits are entered one at a time the mute
output will reset between digits provided the time between entered digits exceeds $\frac{400}{fo}$. In both the normal dialing or automatic
dialing mode tone will be output for a fixed duration of $\frac{400}{fo}$ (50msec for fo = 8kHz).

Figure 6. Typical Application of the S2562
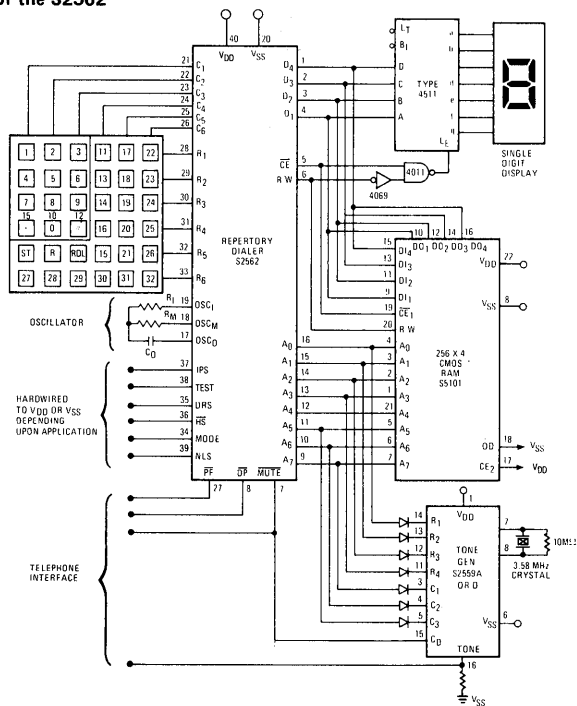
Table 4. Display Codes

D_4	D_3	D_2	D_1	
0	0	0	0	0
0	0	0	1	1
0	0	1	0	2
0	0	1	1	3
0	1	0	0	4
0	1	0	1	5
0	1	1	0	6
0	1	1	1	7
1	0	0	0	8
1	0	0	1	9
1	0	1	0	Not Used
1	0	1	1	Not Used
1	1	0	0	# (Pause)
1	1	0	1	Not Used
1	1	1	0	Beginning of Number
1	1	1	1	Blank

AMI
AMERICAN MICROSYSTEMS, INC.

SINGLE CHANNEL
µ-LAW PCM CODEC/FILTER SET

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Features

☐ CMOS Process for Low Power Dissipation And Wide Supply Voltage Range
☐ Full Independent Encoder with Filter and Decoder with Filter Chip Set
☐ Meets or Exceeds AT&T D3 and CCITT G. 711 and G. 733 Specifications
☐ On-Chip Dual Band Width Phase-Lock Loop Derives All Timing and Provides Automatic Power Down
☐ Low Absolute Group and Relative Delay Distortion
☐ Single Negative Polarity Voltage Reference Input
☐ Encoder with Filter Chip Has Built-In Dual Speed Auto Zero Circuit with Rapid Acquisition During Power Up that Eliminates Long Term Drift Errors and Need for Trimming
☐ Serial Data Rates from 56kb/s to 3.152Mb/s at 8kHz Nominal Sampling Rate
☐ Programmable Gain Input/Output Amplifier Stage

☐ CCIS* Compatible A/B Signaling Option— S3501A/S3502A

General Description

The S3501 and S3502 form a monolithic CMOS Companding Encoder/Decoder chip set designed to implement the per channel voice frequency CODECS used in PCM Channel Bank and PBX systems requiring a µ-255 law transfer characteristic. Each chip contains two sections: (1) a band-limiting filter, and (2) an analog ↔ digital conversion circuit that conforms to the µ-255 law transfer characteristic. Transmission and reception of 8-bit data words containing the analog information is performed at 1.544Mb/s rate with analog sampling occurring at 8kHz rate. A strobe input is provided for synchronizing the transmission and reception of time multiplexed PCM information of several channels over a single transmission line.

*Common Channel Interoffice Signaling

S3501 Block Diagram Encoder with Filter

Pin Configuration

1 CCIS A/B SIGNALING OPTION-S3501A

S3502 Block Diagram Decoder with Filter

CCIS A/B SIGNALING OPTION

Pin Configuration

1 CCIS A/B SIGNALING OPTION-S3502A
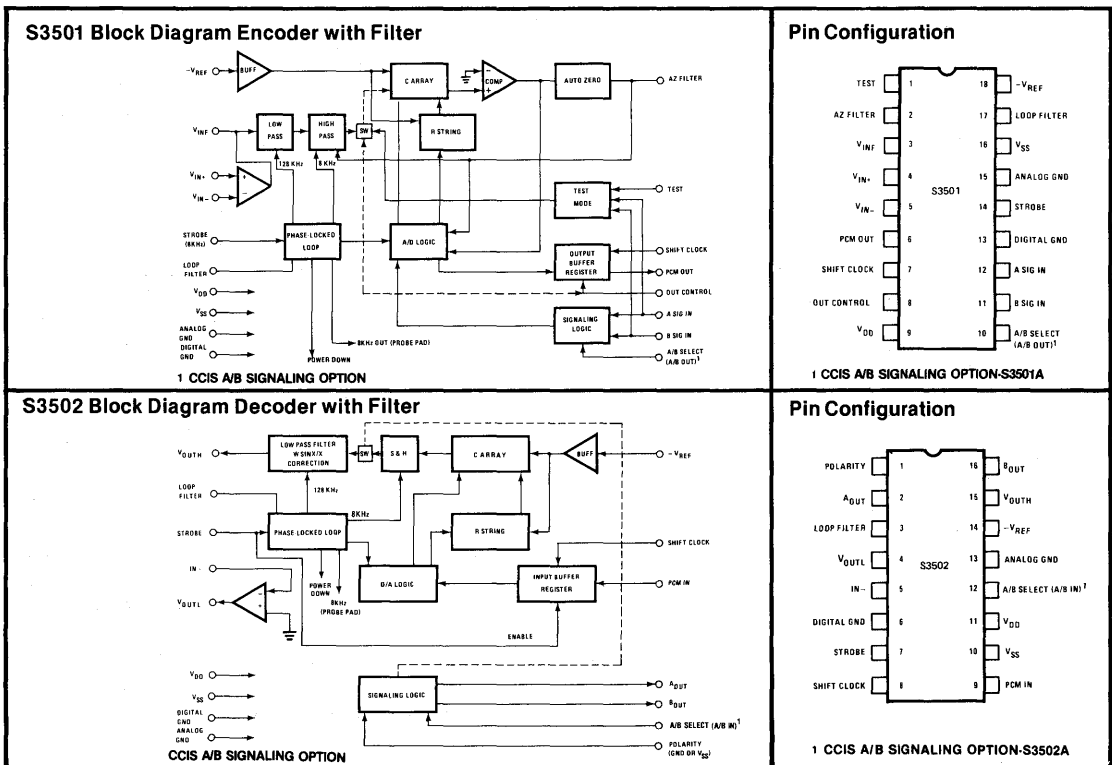
S3501 Encoder with Filter
Functional Description

S3501 Encoder with Filter chip consists of (1) a bandpass filter with D3 filter characteristic, (2) an analog to digital converter that uses a capacitor array, (3) a phaselock loop that generates all internal timing signals from the externally supplied strobe signal and (4) control logic that performs miscellaneous logic functions.

The band-limiting filter is a fifth order low pass elliptic filter followed by a third order Chebyshev high pass filter. The combined response characteristic (Figure 3) exceeds the D3 filter specifications. The loss below 65Hz is at least 25dB which helps minimize the effect of power frequency induced noise.

The analog to digital converter utilizes a capacitor array based on charge redistribution technique (Ref. 1) to perform the analog to digital conversion with a μ-255 law transfer characteristic (see Figure 4).

The timing signals required for the band-pass filter (128kHz and 8kHz) and analog to digital converter (1.024MHz) are generated by a phase-lock loop comprising a VCO, a frequency divider, a loop filter and a lock detector. The loop locks to the externally supplied 8kHz strobe pulses. In the absence of the strobe pulses, the lock detector detects the unlocked condition and forces the device into a power-down mode thereby reducing power dissipation to a minimum. Thus power-down mode is easily implemented by simply gating the strobe pulses "off" when the channel is idle. The lock-up time, when strobe pulses are gated "on", is approximately 20ms. During this time the device outputs an idle code (all 1's) until lock-up is achieved. Note that signaling information is not transmitted during this time.

The control logic implements the loading of the output shift register, gating and shifting of the data word, signaling logic and other miscellaneous functions. A new analog sample is acquired on the rising edge of the strobe pulse. The data word representing the previous analog sample is loaded into the output shift register at this time and shifted out on the positive transitions of the shift clock during the strobe "on" time. (See Figure 1.) The signaling information is latched immediately after the A/B select input makes a transition. The "A" signaling input is selected after a positive transition and the "B"signaling input is selected after a negative transition. Signaling information is transmitted in the eighth bit position (LSB) of the next frame. (See Figures 1 and 2.) In the CCIS compatible A/B signaling option, the A bit is transmitted during the first data bit time. B bit is transmitted during the remaining 7-bit times. (See Figures 1 and 2.)

"All zero" code suppression is provided so that negative input signal values between the decision value numbers 127 and 128 are encoded as "00000010".

S3501 Encoder with Filter
Pin Function Descriptions

Strobe: (Refer to Figure 1 for timing diagram.) This TTL compatible input is typically driven by a pulse stream of 8kHz rate. Its active state is defined as a logic 1 level and should be active for a duration of 8 clock cycles of the shift clock. A logic "1" initiates the following functions: (1) instructs the device to acquire a new analog sample on the rising edge of the signal (logic 0 to logic 1 transition); (2) instructs the device to output the data word representing the previous analog sample onto the PCM-out pin serially at the shift clock rate during its active state; (3) forces the PCM-out buffer into an active state. A logic "0" forces the PCM-out buffer into a high impedance state if the Out Control pin is wired to V_{DD}. This input provides the sync information to the phase-lock loop from which all internal timing is developed. The absence of the strobe conveys power-down status to the device. (See functional description of the phase-lock loop for details.)

Shift Clock: This TTL compatible input is typically a square wave signal at 1.544MHz. The device can operate with clock rates from 56kHz (as in the single channel 7-bit PCM system) to 3.152MHz (as in the T1-C carrier system). Data is shifted out of the PCM-out buffer on the rising edges of the clock after a valid logic 0 to logic 1 transition of the strobe signal.

PCM-Out: This is an open drain buffer capable of driving one low power Schottkey (74ls) TTL load with a suitable external pull-up resistor (2kΩ). This buffer is in active state (as controlled by the value of the data bit) whenever the strobe signal is a logic 1 and is in a high impedance state when the strobe input is a logic 0, if the out control pin is wired to V_{DD} supply. When the out control is wired to V_{SS} the state of the output buffer is controlled by the value of the data bit being shifted out. For 56kHz and 64kHz PCM systems where output data is continuous bit stream, the out control pin should be connected to V_{SS}.

A/B Select: (S3051 only) (Refer to Figure 2 for timing diagram.) This TTL compatible input is provided in order to select the path for the signaling information. It is a transition sensitive input. A positive transition on this input prior to the negative transition of the strobe input selects the "A" signaling input and is transmitted as the eighth bit in the subsequent frame. Similarly, a negative transition causes selection and transmission of information on the "B" signaling input.

A SIG IN, B SIG IN: These two TTL compatible inputs are provided to allow multiplexing of signaling information into the transmitted PCM data word in the eighth bit position in accordance with the timing diagram of Figure 2.

A/B Out: (S3501A only) This is an open drain buffer capable of driving one low power Schottkey (74ls) TTL load with a suitable external pull-up resistor (5kΩ). This is an optional output for implementing CCIS compatible A/B signaling. (See Figure 2b.) During data bit 1 time, A signaling bit is output. During remaining 7-bit times, B signaling bit is output. This output is in a high impedance state when strobe is not present.

Out Control: This is a CMOS compatible input and must be wired to either the V_{DD} or V_{SS} (except in 'test' mode). When connected to the V_{DD} supply, it allows the strobe input to control the active/high impedance state of the PCM-out buffer. When connected to V_{SS}, the PCM-out buffer is always in the active state (corresponding to the data bit being shifted out).

V_{IN-}, V_{IN+}, V_{INF}: These three pins are provided for connecting analog signals in the range of $-V_{REF}$ to $+V_{REF}$ to the device. V_{IN-} and V_{IN+} are the inputs of a high input impedance op amp and V_{INF} is the output of this op amp. These three pins allow the user complete control over the input stage so that the input stage can be connected as a unity gain amplifier, amplifier with gain, amplifier with adjustable gain or as a differential input amplifier. The adjustable gain configuration will facilitate calibration of the transmit channel and testing of the encoder in a stand alone situation. The input stage also allows the user to construct an anti-aliasing filter to provide sufficient suppression at 128kHz.(See Figure 7)

$-V_{REF}$: The input provides the conversion reference for the analog to digital conversion circuit. a value of -3 volts is required. The reference must maintain 100ppM/°C regulation over the operating temperature range. A high input impedance buffer is provided on this input which facilitates bussing of the same reference voltage to several devices as well as local R-C filtering (a series resistance of 400kΩ with 0.1μF connected to analog ground) at the input of the device.

AZ Filter: A capacitor C_{AZ} (nominal 0.1μF) is required from this pin to analog ground for the functioning of the on-chip auto zero circuit. The most significant bit (sign bit) is filtered by the auto zero circuit and fed back to the input of the A/D converter to compensate for filter output offset variations. This technique insures that the long term average of the sign bit will be zero.

Analog Ground, Digital Ground: Two separate pins are provided for connection of analog signals referenced to analog ground and digital signals referenced to digital ground. This minimizes switching noise associated with the digital signals from affecting the analog signals.

V_{DD}, V_{SS}: These are power supply pins. The device is designed to operate from power supply voltages of ±4.75 to ±6.0 volts. (Decoupling capacitors to analog ground should be as close to pins as possible).

Loop Filter: A capacitor C_{LOOP} (nominal 0.1 μF) is required from this pin to digital ground to provide filtering of the phase comparator output. Care should be taken to install the capacitor as close to the pin as possible.

Test: This pin is provided to allow for separate testing of the filter and encoder sections of the circuit. The circuit functions normally when this pin is connected to V_{SS}. When this pin is connected to V_{DD}, test mode results. In this mode when A SIG IN and B SIG IN inputs are connected to V_{SS} the filter output is disconnected from the encoder input. The encoder input is instead connected to the Out Control pin. For other logical combinations of the A SIG IN and B SIG IN inputs the filter output is connected to the Out Control pin.

Ref. 1: "*A Two Chip PCM Voice CODEC with Filters,*"IEEE Journal of Solid State Circuits December 1979.

Figure 1-A. Typical Waveforms in a Time Multiplexed System

SHIFT CLOCK   NOTE 1

STROBE

| | MSB D1 | D2 | D3 | D4 | D5 | D6 | D7 | LSB D8 | |

PCM OUT/IN

ENCODER OUTPUT HIGH Z WHEN OUT CONTROL IS WIRED TO V_{DD}

A/B SELECT

NOTE 1: A/B SELECT GOES HIGH IN 5TH FRAME AND LOW IN 11TH FRAME FOR ENCODER.
FOR DECODER IT GOES HIGH IN 6TH FRAME AND LOW IN 12TH FRAME.

A_{IN} LATCHED

| | A | B | |

A/B OUT (IN)

ENCODER A/B OUT HI Z STATE
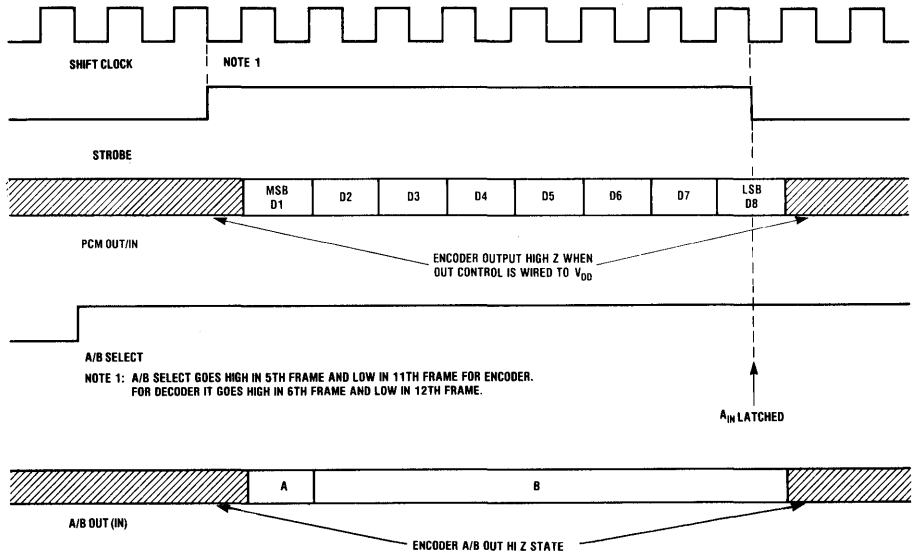
NOTE 2: IDLE CHANNEL NOISE CAN BE REDUCED BY AVOIDING COINCIDENCE BETWEEN THE FALLING EDGE OF THE SHIFT CLOCK AND RISING EDGE OF STROBE SIGNAL.

Figure 1-B. Waveform Detail

t_{rc}

90%

50%

10%

SHIFT CLOCK

t_{fc}

t_{fs}

t_{sc} (ON)

t_{sc} (OFF)

STROBE

t_{rs}

$t_{d(ON)}$

$t_{d(OFF)}$

PCM OUT/IN

t_{fd}

t_{rd}
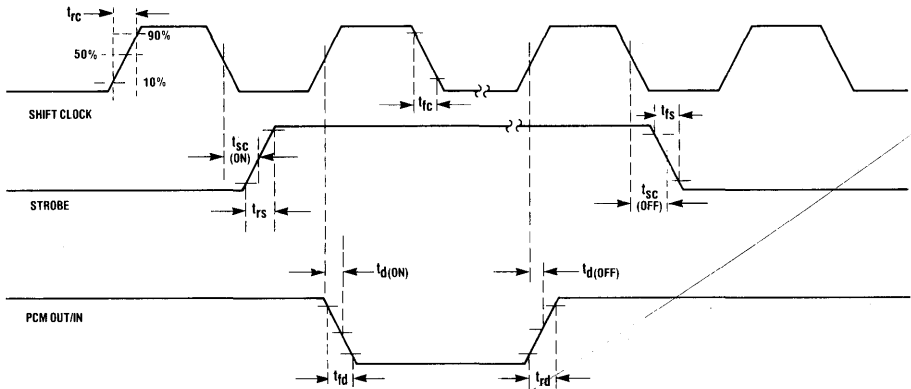
Figure 1-C. 64kHz Continuous Bit Stream Application (Out Control Wired to V_{SS})

SHIFT CLOCK

STROBE

PCM OUT/IN

| LSB D8 | MSB D1 | D2 | D3 | D4 | D5 | D6 | D7 | LSB D8 | MSB D1 | D2 | |

DATA WORD 1   DATA WORD 2

AMI.
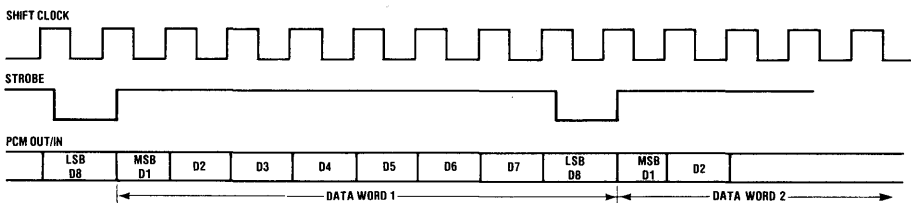
Figure 2-A. Encoder A/B Signalling Waveforms

STROBE

(ENCODER)
A/B SELECT

t_{dss}

t_{dss}

A SIGNALING BIT
LATCHED

A SIGNALING BIT
TRANSMITTED AT D_8 TIME

B SIGNALING
BIT LATCHED

B SIGNALING BIT
TRANSMITTED DURING D_8 TIME

FRAME #

5 6 7 8 9 10 11 12

A/B SELECT

1 24

$A_1 - A_{24}$
TRANSMITTED

CHANNEL STROBES

$B_1 - B_{24}$
TRANSMITTED
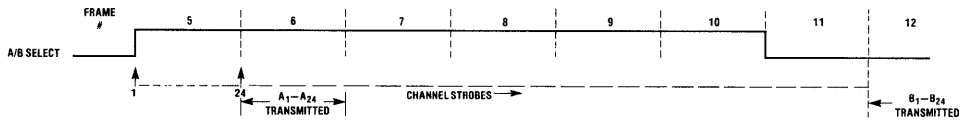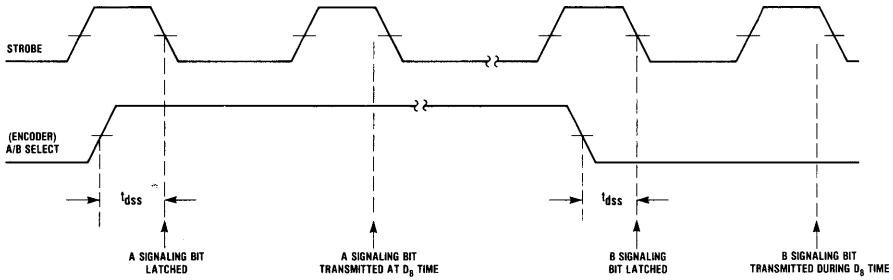
Figure 2-B. CODEC System Timing Diagram

Ch. (n−1)
STROBE

Ch. n STROBE

Ch. (n+1) STROBE

$D_{7(n-1)}$ $D_{8(n-1)}$ $D_{1(n)}$ $D_{2(n)}$ $D_{3(n)}$ $D_{4(n)}$ $D_{5(n)}$ $D_{6(n)}$ $D_{7(n)}$ $D_{8(n)}$ $D_{1(n+1)}$ $D_{2(n+1)}$ $D_{3(n+1)}$ $D_{4(n+1)}$ $D_{5(n+1)}$ $D_{6(n+1)}$ $D_{7(n+1)}$ $D_{8(n+1)}$ $D_{1(n+2)}$ $D_{2(n+2)}$

PCM OUT/IN   (ENCODER/DECODER)

$A_{(n-1)}$ LATCHED

$A_{(n)}$ LATCHED

$A_{(n+1)}$ LATCHED

$B_{(n-1)}$ $A_{(n)}$ $B_{(n)}$ $A_{(n+1)}$ $B_{(n+1)}$ $A_{(n+2)}$ $B_{(n+2)}$

A/B OUT/IN

$B_{(n-1)}$ RECEIVED $A_{(n)}$ RECEIVED

$B_{(n)}$ $A_{(n+1)}$
RECEIVED RECEIVED

$B_{(n+1)}$ $A_{(n+2)}$
RECEIVED RECEIVED

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2.61
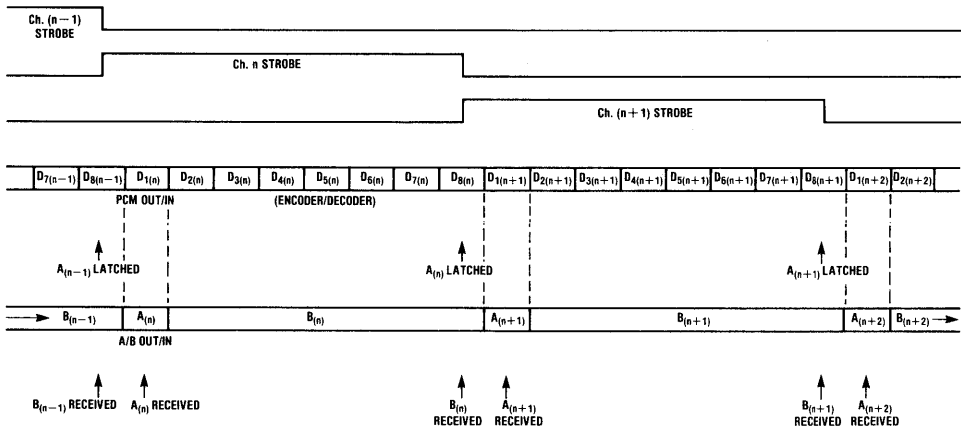
Figure 3. S3501 Encoder Filter Loss Response
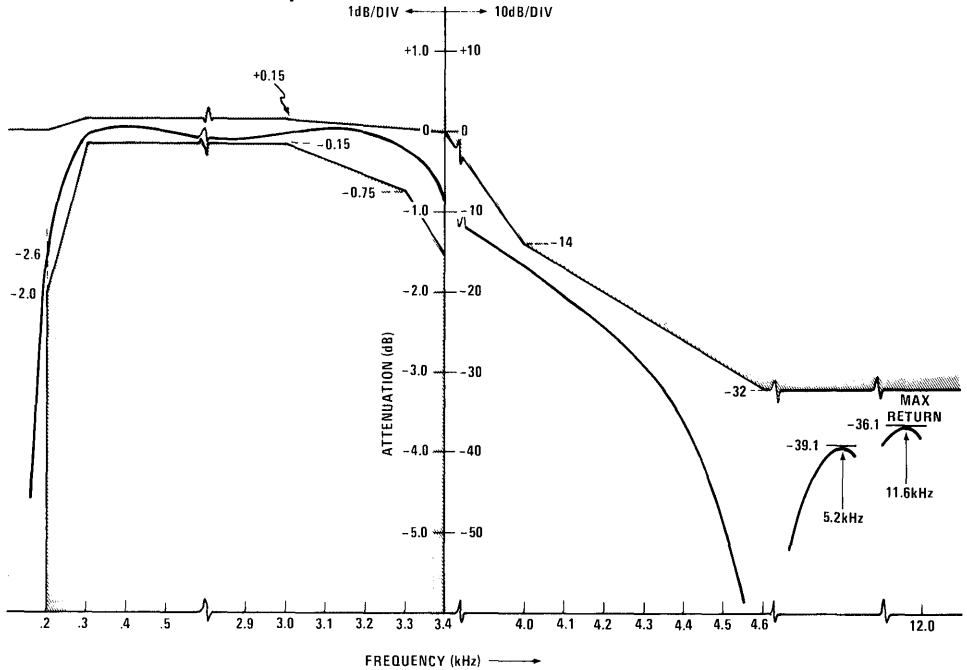
Note: Attenuation at frequencies below 65Hz is at least 25dB

Figure 4. μ-255 Law Transfer Characteristics
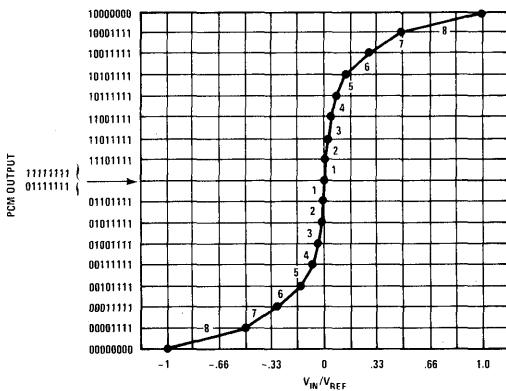
S3501 Transfer Characteristics
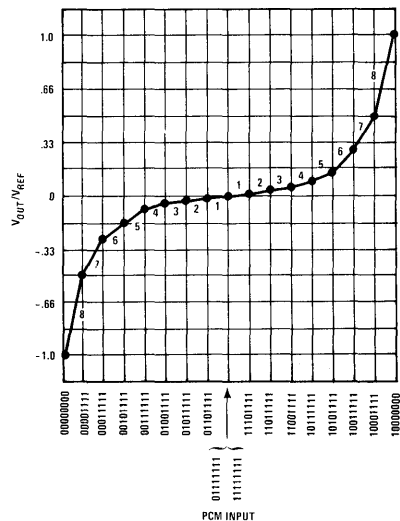
S3502 Transfer Characteristics

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S3501 Absolute Maximum Ratings

DC Supply Voltage V_{DD} .... +6.5V
DC Supply Voltage V_{SS} .... −6.5V
Operating Temperature .... 0°C to +70°C
Storage Temperature .... −55°C to +125°C
Power Dissipation at 25°C 250mW
Digital Input .... −0.3 ⩽ V_{IN} ⩽ V_{DD} + 0.3
Analog Input .... − V_{REF} ⩽ V_{IN} ⩽ + V_{REF}
− V_{REF} .... V_{SS} ⩽ V_{REF} ⩽ 0

S3501 Electrical Operating Characteristics ($T_A = 25$°C)
Power Supply Requirements

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{DD}	Positive Supply	4.75	5.0	6.0	V	
V_{SS}	Negative Suppply	−4.75	−5.0	−6.0	V	
− V_{REF}	Negative Reference	−2.4	−3	−3.25	V	
P_{OPR}	Power Dissipation (Operating)		70	100	mW	$V_{DD}=5.0V$, $V_{SS}=-5.0V$, − $V_{REF}=-3.0V$
P_{STBY}	Power Dissipation (Standby)		15		mW	

S3501 AC Characteristics (Refer to Figures 1 and 2)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
f_{SC}	Shift Clock Frequency	0.056	1.544	3.152	MHz	
D_{SC}	Shift Clock Duty Cycle	40	50	60	%	
t_{rc}	Shift Clock Rise Time			100	ns	
t_{fc}	Shift Clock Fall Time			100	ns	
t_{rs}	Strobe Rise Time			100	ns	
t_{fs}	Strobe Fall Time			100	ns	
t_{sc}(On)	Shift Clock to Strobe (On) Delay	0+		(1/2 CP)−	Shift Clock Period	
t_{sc} (Off)	Shift Clock to Strobe (Off) Delay	0+		(1/2 CP)−	Shift Clock Period	
t_d (On)	Shift Clock to PCM Out (On) Delay		100	125	ns	
t_d (Off)	Shift Clock to PCM Out (Off) Delay		100	125	ns	
t_{rd}	PCM Output Rise Time $C_L=50pF$		100	125	ns	Resistive Pull-Up on PCM Out selected for desired rise time
t_{fd}	PCM Output Fall Time $C_L=50pF$		50	70	ns	
t_{dss}	A/B Select to Strobe Trailing Edge Set Up Time	100			ns	
t_L	Phase-Lock Loop Lock Up Time		20	35	ms	
t_j	P−P Jitter of Strobe Rising Edge			5	μs	

S3501 DC Characteristics ($V_{DD}=+5V$, $V_{SS}=-5V$, $-V_{REF}=-3.0V$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
R_{INA}	Analog Input Resistance	10			$M\Omega$	V_{IN-}, V_{IN+} Inputs
C_{IN}	Input Capacitance			10	pF	All Logic and Analog Input $^\circ$
I_{INL}	Logic Input Low Current (Shift Clock, Strobe)			1	μA	$V_{IL}=0.8V$
I_{INH}	Logic Input High Current			1	μA	$V_{IH}=2.0V$
V_{IL}	Logic Input "Low" Voltage			0.8	V	
V_{IH}	Logic Input "High" Voltage	2.0			V	
I_{REF-}	Negative Reference Current			100	nA	
R_{REF-}	Negative Reference Input Resistance	10			$M\Omega$	
V_{OL}	Logic Output "Low" Voltage (PCM Out)			0.4	V	$I_{OL}=5mA$
V_{OL}	Logic Output "Low" Voltage (A/B Out)			0.8	V	$I_{OL}=1mA$
I_{OH}	PCM Output Off Leakage Current			100	nA	$V_O=0$ to $5V$

S3502 Decoder with Filter
Functional Description

S3502 Decoder with Filter consists of (1) a digital to analog converter that uses a capacitor array; (2) a low pass filter with D3 filter characteristic; (3) a phase-lock loop that generates all internal timing signals from the externally supplied strobe signal and (4) control logic that performs miscellaneous logic functions.

The digital to analog converter uses a capacitor array based on charge redistribution technique (Ref. 1) to perform the D/A conversion with a μ-255 law transfer characteristic (See Figure 4).

The timing signals required for the low pass filter (128kHz) digital to analog converter (1.024MHz) are generated by a phase-lock loop comprised of a VCO, a frequency divider, a loop filter and a lock detector. The loop locks to the externally supplied 8kHz strobe pulses. In the absence of the strobe pulses, the lock detector detects the unlocked condition and forces the device into a power-down mode thereby reducing power dissipation to a minimum. Thus, power-down mode is easily implemented by simply gating the strobe pulses "off" when the channel is idle. During the power-down mode the output amplifier is forced to a high impedance state and the A, B outputs are forced to inactive state. The lock-up time, when strobe pulses are gated "on", is approximate-ly 20ms. During this time the A/B outputs and the analog output stage are held in the idle state.

The control logic implements the loading of the input shift register, signaling logic and other miscellaneous functions. A new data word is shifted into the input register on a positive transition of the strobe signal at the shift clock rate. The received data is decoded by the D/A converter and applied to the sample and hold circuit. The output sample and hold circuit is filtered by a low pass filter. The low pass filter is a sixth order elliptic filter. The combined response of the sample and hold and the low pass filter is shown in Figure 5.

Signaling information is received and latched immediately after the A/B select input makes a positive or negative transition. On the positive transition of the A/B select input information received in the eighth bit of the data word is routed to the A_{OUT} pin and latched until updated again after the next positive transition of the A/B select input. Similarly "B" signaling information is routed and latched at the B_{OUT} pin after each negative transition of the A/B select input. The A and B outputs are designed such that either relay or TTL compatibility can be achieved (see detailed description under Pin/Function descriptions). In the CCIS compatible A/B signaling option "A" bit is latched during the data bit 1 time and "B" bit is latched during the data bit 8 time.

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S3502 Decoder with Filter
Pin/Functions Descriptions

Strobe: (Refer to Figure 1 for timing diagram.) This TTL compatible input is typically driven by a pulse stream of 8kHz rate. Its active state is defined as a logic 1 level and is normaly active for a duration of 8 clock cycles of the shift clock. It initiates the following functions: (1) instructs the device to receive a PCM data word serially on PCM IN pin at the shift clock rate; (2) supplies sync information to the phase-lock loop from which all internal timing is generated; (3) conveys power-down mode to the device by its absence. (See functional description of the phase-lock loop for details.)

Shift Clock: This TTL compatible input is typically a square wave signal at 1.544MHz. The device can operate with clock rates from 56kHz (as in the single channel 7-bit PCM system) to 3.152MHz (as in the T1-C carrier system). Data is shifted in the PCM IN buffer on the falling edges of the clock after the strobe signal makes a logic 0 to logic 1 transition.

PCM IN: This is a TTL compatible input on which time multiplexed PCM data is received serially at the shift clock rate during the active state of the strobe signal.

A/B Select: (S3502 only) (Refer to Figure 6 for timing diagram.) This TTL compatible input is provided in order to select the path for the signaling information. It is a transition sensitive input. A positive transition on this input routes the received signaling bit to the "A" output and a negative transition routes it to the "B" output.

A Out, B Out: These two open drain outputs are provided to output received signaling information. These outputs are designed in such a way that either LS TTL or relay drive compatibility can be achieved. With a suitable pull-up resistor (47KΩ) connected to the LS TTL logic supply, the output voltage will swing between digital ground and the LS TTL logic supply when the polarity pin is connected to digital ground. (See Figure 6.) The output polarity is the same as the received signaling bit polarity. If the polarity pin is connected to the V_{SS} supply, the output voltage will swing between V_{SS} and V_{DD} supplies with a suitable pull-up resistor. This facilitates driving a relay by a PNP emitter grounded transistor in $-48V$ systems. The output polarities are inverted from the received signaling bit polarity to facilitate relay driving.

Polarity: This pin is provided for testing purposes and for controlling the A/B output polarities and TTL/relay

drive compatibilities. For TTL compatibility this pin is connected to digital ground. The A/B output polarities are then the same as the received signaling bit polarities. For relay drive capability this pin is connected to the V_{SS} supply. The A/B output polarities then are inverted from the received signaling bit polarities. Test mode results when this pin is connected to V_{DD}. In this mode the decoder output (S&H output) is connected to the B-Out pin while the filter input is connected to the A-Out pin.

$-V_{REF}$: The input provides the conversion reference for the digital to analog conversion circuit. and the phase-lock loop. A value of -3 volts is required. The reference must maintain 100ppM/°C regulation over the operating temperature range. A high input impedance buffer is provided on this input which facilitates bussing of the same reference voltage to several devices as well as local R-C filtering at the input of the device.

V_{OUTH}: This is the output of the low pass filter which represents the recreated voice signal from the received PCM data words. This is a high impedance output which can be used by itself or connected to the output amplifier stage which has a low output impedance.

V_{OUTL}, IN−: These two pins are the output and input of the uncommitted output amplifier stage. Signal at the V_{OUTH} pin can be connected to this amplifier to realize a low output impedance with the unity gain, increased gain or reduced gain. This allows easier calibration of the receive channel and testing of the decoder in a stand alone situation.

Analog Ground, Digital Ground: Two separate pins are provided for connection of analog signals referenced to analog ground and digital signals referenced to digital ground. This minimizes switching noise associated with the digital signals from affecting the analog signals.

V_{DD}, V_{SS}: These are power supply pins. The device is designed to operate from power supply voltages of ±4.75 to ±6.0 volts.

Loop Filter: A capacitor C_{LOOP} (nominal 0.1μF is required from this pin to digital ground to provide filtering of the phase comparator output.

A/B IN: (S3502A only) This optional TTL compatible input is provided to implement CCIS compatible A/B signaling scheme. Time multiplexed A/B signaling information is applied at this input and recovered by the decoder as shown in Figure 2-b.

S3502 Absolute Maximum Ratings

DC Supply Voltage V_{DD} .... $+6.5\,V$
DC Supply Voltage V_{SS} .... $-6.5\,V$
Operating Temperature .... $0°C$ to $+70°C$
Storage Temperature .... $-55°C$ to $+125°C$
Power Dissipation at $25°C$ .... $250\,mW$
Digital Input .... $-0.3 \leqslant V_{IN} \leqslant V_{DD} +0.3$
Analog Input .... $-V_{REF} \leqslant V_{IN} \leqslant +V_{REF}$
$-V_{REF}$ .... $V_{SS} \leqslant V_{REF} \leqslant 0$

S3502 Electrical Operating Characteristics ($T_A = 25°C$)
Power Supply Requirements

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{DD}	Positive Supply	4.75	5.0	6.0	V	
V_{SS}	Negative Supppply	-4.75	-5.0	-6.0	V	
$-V_{REF}$	Negative Reference	-2.4	-3	-3.25	V	
P_{OPR}	Power Dissipation (Operating)		55	100	mW	$V_{DD}=5.0V$, $V_{SS}=-5.0V$, $-V_{REF}=-3.0V$
P_{STBY}	Power Dissipation (Standby)		15		mW	

S3502 AC Characteristics (Refer to Figures 1 and 6)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
f_{SC}	Shift Clock Frequency	0.056	1.544	3.152	MHz	
D_{SC}	Shift Clock Duty Cycle	40	50	60	%	
t_{rc}	Shift Clock Rise Time			100	ns	
t_{fc}	Shift Clock Fall Time			100	ns	
t_{rs}	Strobe Rise Time			100	ns	
t_{fs}	Strobe Fall Time			100	ns	
t_{sc}(On)	Shift Clock to Strobe (On) Delay	$0+$		(1/2 CP)−	Shift Clock Period	
t_{sc} (Off)	Shift Clock to Strobe (Off) Delay	$0+$		(1/2 CP)−	Shift Clock Period	
t_{rd}	PCM Input Rise Time			100	ns	
t_{fd}	PCM Input Fall Time			100	ns	
t_L	Phase-Lock Loop Lock Up Time		20	35	ms	
t_j	P−P Jitter of Strobe Rising Edge			5	μs	
t_d (On)	Shift Clock to PCM Input (On) Delay			100	ns	
t_d (Off)	Shift Clock to PCM Input (Off) Delay			100	ns	
$t_{A/BS}$	A/B Select Set Up Time to Strobe Trailing Edge	100			ns	
t_{AO}, t_{BO}	Strobe Falling Edge to A/B Out Delay			200	ns	

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Figure 5. S3502 Decoder Filter with Sample & Hold Loss Response
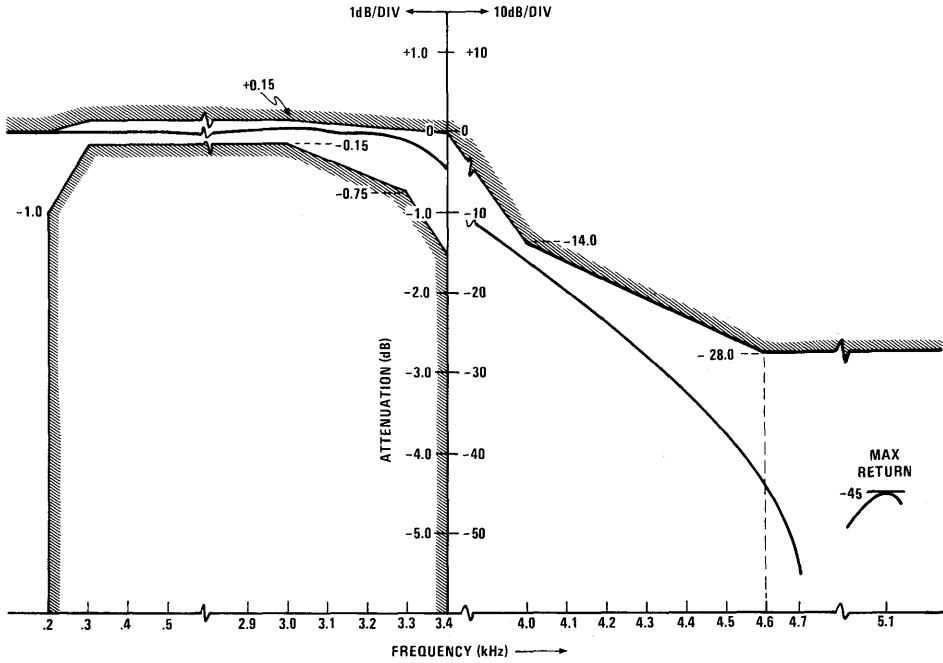
Figure 6. Decoder A/B Output Timing
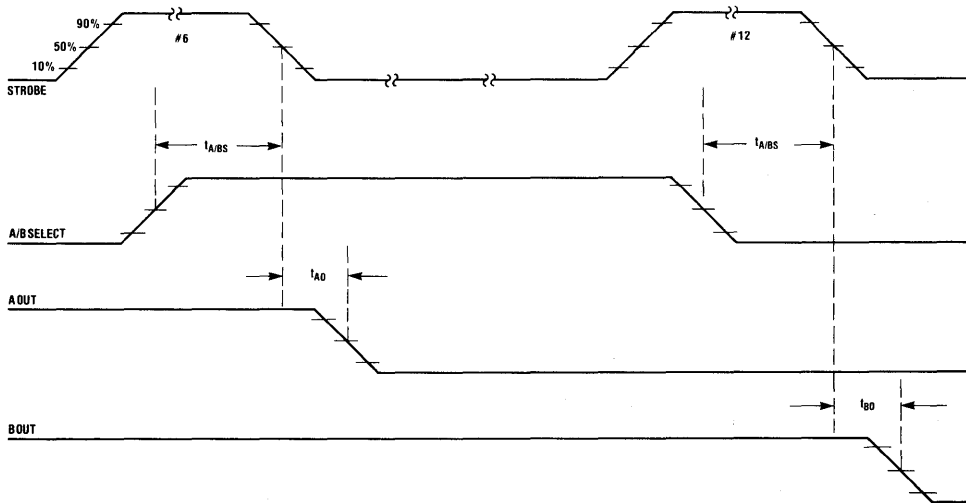
S3502 Decoder with Filter DC Characteristics
($V_{DD} = +5V$, $V_{SS} = -5V$, $-V_{REF} = -3.0V$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$R_L(V_{OUTL})$	Output Load Resistance	600			Ω	
$R_{INA}(IN-)$	Analog Input Resistance	10			MΩ	
$C_{INA}(IN-)$	Analog Input Capacitance			10	pF	
I_{REF-}	Negative Reference Current			100	nA	
R_{REF-}	Negative Reference Input Resistance	10			MΩ	
V_{IL}	Logic Input (Shift Clock, Strobe, PCM In) "Low" Voltage			0.8	V	
V_{IH}	Logic Input "High" Voltage	2.0			V	
I_{INL}	Logic Input "Low" Current			1	μA	$V_{IL} = 0.8V$
I_{INH}	Logic Input "High" Current			1	μA	$V_{IH} = 2.0V$
V_{OL}	A, B Output "Low" Voltage			0.8	V	Polarity=Dig. Gnd, I_{OL}=1mA
V_{OL}	A, B Output "Low" Voltage			$V_{SS}+1.0$	V	Polarity = V_{SS}, I_{OL}=1mA

S3501/S3502 System Characteristics
Typical Group Delay Characteristic

Device	Abs. Gr. Delay μs		Relative Gr. Delay Distortion (Over Band of 1000 Hz to 2600Hz wrt 1000Hz) μs
	f = 1000Hz	f = 2600Hz	
Encoder Low Pass Filter	132	220	88
Encoder High Pass Filter	104	22	−82
Encoder Filter Total	236	242	6
Decoder Low Pass Filter	153	250	97
Encoder + Decoder Filters (Total)	389	492	103
End to End Group Delay (Encoder Analog Input to Decoder Analog Output)	639	742	103

Parameter	Min.	Typ.	Max.	Units	Conditions
Signal-to-Distortion		38 27 22		dB	Analog Input=0 to −30dBm0 Analog Input=−30 to −40dBm0 Analog Input=−40 to −45dBm0
Gain Tracking		±.25 ±.5 ±1.5		dB	Analog Input= +3 to −40dBm0 Analog Input=−40 to −50dBm0 Analog Input=−50 to −55dBm0
Idle Channel Noise a) End to End b) Decoder only		17 7	20 10	dBrnc0	Analog Input=Analog Ground thru 600 Ω PCM In to V_{DD}
Transmission Level Point		+5.2		dBm	With −3V V_{REF} and R_L =600Ω

Figure 7. Suggested Anti-Aliasing Filter for Encoder

PIN 3 (V$_{INF}$)

2000Ω

1300pF

2000Ω   2600Ω

IN

PIN 5 (V$_{IN-}$)

.0065μF

ANALOG GROUND

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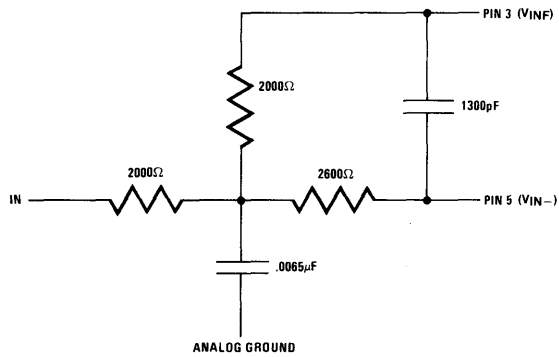
SINGLE CHANNEL
A-LAW PCM CODEC/FILTER SET

Features

☐ CMOS Process, for Low Power Dissipation and Wide Supply Voltage Range

☐ Full Independent Encoder with Filter and Decoder with Filter Chip Set

☐ Meets or Exceeds CCITT G. 711, G.712 and G. 733 Specifications

☐ On-Chip Dual Band Width Phase-Lock Loop Derives All Timing and Provides Automatic Power Down

☐ Low Absolute Group and Relative Delay Distortion

☐ Single Negative Polarity Voltage Reference Input

☐ Encoder with Filter Chip Has Built-In Dual Speed Auto Zero Circuit with Rapid Acquisition During Power Up that Eliminates Long Term Drift Errors and Need for Trimming

☐ Serial Data Rates from 56kb/s to 3.152Mb/s at 8kHz Nominal Sampling Rate

☐ Programmable Gain Input/Output Amplifier Stage

General Description

The S3503 and S3504 form a monolithic CMOS Companding Encoder/Decoder chip set designed to implement the per channel voice frequency CODECS used in PCM systems requiring an A-law transfer characteristic. Each chip contains two sections: (1) a band-limiting filter, and (2) an analog ↔ digital conversion circuit that conforms to the A-law transfer characteristic. Typical transmission and reception of 8-bit data words containing the analog information is performed at 2.048Mb/s rate with analog sampling occurring at 8kHz rate. A strobe input is provided for synchronizing the transmission and reception of time multiplexed PCM information of several channels over a single transmission line. These chips are pin-for-pin replacements for the S3501/S3502 chip set with the exception of the A-law transfer characteristic conforming to CCITT G. 711 and the unused signaling capability which remains available for special applications.

S3503 Block Diagram Encoder With Filter
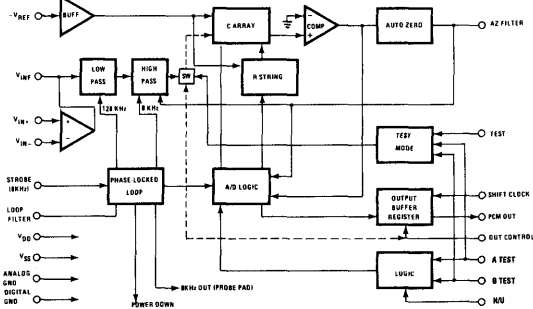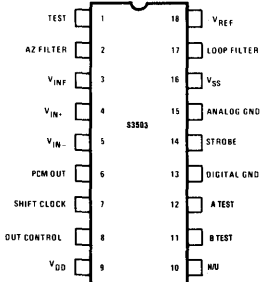
Pin Configuration

PIN 10, 11, 12 TO V_DD FOR NORMAL OPERATION

S3504 Block Diagram Decoder with Filter
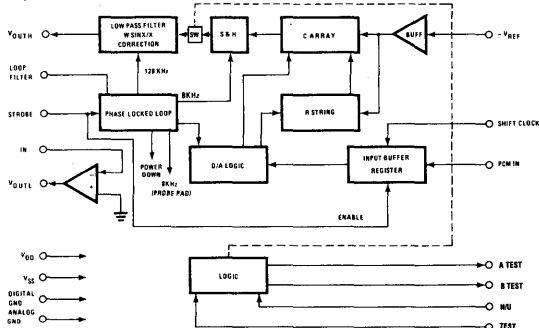
Pin Configuration
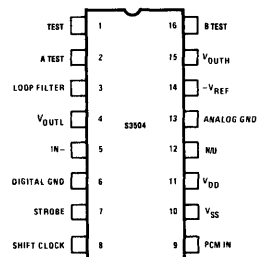
PIN 1 TO DIGITAL GROUND, PIN 2, 16 OPEN FOR NORMAL OPERATION

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SIGNAL PROCESSING PERIPHERAL

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Features

☐ **High Speed VMOS Technology**

☐ **Programmable for Digital Processing of Signals in Voice-Grade Communications Systems and Other Applications with Signal in the Audio Frequency Range**

☐ **Extremely Fast 12-Bit Parallel Multiplier On-Chip (300ns Max. Multiplication Time)**

☐ **Built-in Program ROM (256x17)*, 3-Port Data Memory (256x16) and Add/Subtract Unit (ASU)**

☐ **Pipeline Structure for High Speed Instruction Execution (300ns Max. Cycle Time)**

☐ **Bus-Oriented Parallel I/O for Easy Microprocessor Interface**

☐ **Additional Double Buffered I/O for Ease of Asynchronous Serial Interface**

☐ **On-Chip Crystal Oscillator (20MHz) Circuit**

☐ **Pre-Programmed Standard Parts to Be Announced Shortly**

General Description

The S2811 Signal Processing Peripheral (SPP) is a high speed special purpose arithmetic processor with on-chip ROM, RAM, multiplier, adder/subtractor, accumulator and I/O organized in a pipeline structure to achieve an effective operation of one multiply, add and store of up to 12 bit numbers in 300 nanoseconds.

User Support

A real time in circuit emulator, the RTDS2811 is under development. This is a fully compatible hardware emulator with software assembler/disassembler and editor for rapid program development and debugging.

*Out of the 256 instruction locations of the ROM, 250 are usable by the user program. Six instruction locations are reserved for in-house testing.

Block Diagram

Pin Configuration
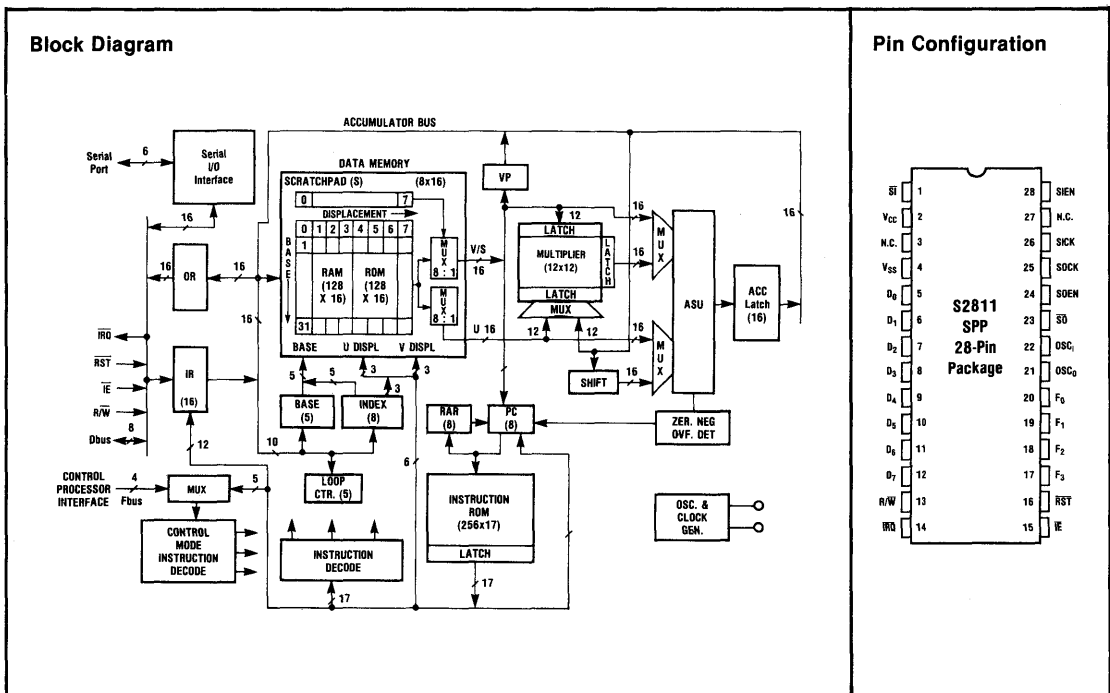
Absolute Maximum Ratings

Supply Voltage 7.0VDC

Operating Temperature Range . . . . 0°C to +70°C

Storage Temperature Range . . . . −55°C to +125°C

Voltage at any Pin . . . . V_{SS} −0.3 to V_{CC} +0.3V

Lead Temperature (soldering, 10 sec.) . . . . 200°C

Electrical Specifications (V_{CC} = 5.0V ±5%; V_{SS} = 0V, T_A = 0°C to +70°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{IH}	Input HIGH Logic "1" Voltage	2.0		V_{CC} +0.3	V	V_{CC} = 5.0V
V_{IL}	Input LOW Logic "0" Voltage	−0.3		0.8	V	V_{CC} = 5.0V
I_{IN}	Input Logic Leakage Current		1.0	2.5	μAdc	V_{IN} = 0V to 5.25V
C_I	Input Capacitance			7.5	pF	
V_{OH}	Output HIGH Voltage	2.4			V	I_{LOAD} = −100μA, V_{CC} = min, C_L = 30pF
V_{OL}	Output LOW Voltage			0.4	V	I_{LOAD} = 1.6mA, V_{CC} = min, C_L = 30pF
f_{CLK}	Clock Frequency	5.0	20		MHz	V_{CC} = 5.0V
P_D	Power Dissipation		0.5	1.0	W	V_{CC} = 5.0V

SPP Pin/Function Descriptions

Microprocessor Interface (16 pins)

D0 through D7   (Input/Output) Bi-directional 8-bit data bus.

F0 through F3   (Input) Control Mode/Operation decode. Four microprocessor address leads are used for this purpose. See "SPP CONTROL MODES AND OPERATIONS." (Table 1)

$\overline{IE}$ (Input) Interface enable. A low level on this pin enables the SPP microprocessor interface. Generated by microprocessor address decode logic.

R/$\overline{W}$ (Input) Read/write select. When HIGH, output data from the SPP is available on the data bus. When LOW, data can be written into SPP.

$\overline{IRQ}$ (Output) Interrupt request. This open-drain output will go LOW when the SPP needs service from the microprocessor.

$\overline{RST}$ (Input) When LOW, clears all internal registers and counters, clears all modes and initiates program execution at location 00.

Serial Interface (6 pins)

SICK, SOCK   Serial Input/Output clocks. Used to shift data into/out of the serial port.

$\overline{SI}$ (Input) Serial input. Serial data input port. Data is entered MSB first and is inverted.

SIEN   (Input) Serial input enable. A HIGH on this input enables the serial input port. The length of the serial input word (16 bits maximum) is determined by the width of this strobe.

$\overline{SO}$ (Output) Serial output. Three-state serial output port. Data is output MSB first and is inverted.

SOEN   (Input) Serial output enable. A HIGH on this input enables the serial output port. The length of the serial output (16 bits maximum) is determined by the width of this strobe.

Miscellaneous

OSC_i, OSC_o An external 20MHz crystal with suitable capacitors to ground can be connected across these pins to form the time base for the SPP. An external clock can also be applied to OSC_i input if the crystal is not used.

V_{CC}, V_{SS} Power supply pins $V_{CC} = +5V$, $V_{SS} = 0$ volt (ground).

Functional Description

The main functional elements of the SPP (see Block Diagram) are:

1. a 256x17 ROM which contains the user program,

2. a 3-port 256x16 data memory (one input and two output ports) which allows simultaneous readout of two words,

3. a 12-bit high-speed parallel multiplier

4. an Add/Subtract unit (ASU),

5. an accumulator register, and,

6. I/O and control circuits.

The SPP is implemented in a combination of clocked and static logic which allows complete overlap of the multiply operation with the read, accumulate, and write operations. The basic instruction cycle is "Read, Modify, Write" where the "Read" brings the operands from the RAM to the multiplier and/or the ASU, the "Modify" operates on those operands and/or the product of the previous operands, and the "Write" stores the result of the "Modify." The cycle time for the instruction is 300 nanoseconds. This results in an arithmetic throughput of about 3.3 multiply and accumulate operations per microsecond. Figure 1 illustrates the SPP Instruction Formats. The OP1 and OP2 instructions are listed in Tables 2 and 3 and Figure 2 illustrates the basic instuction timing.

The SPP is intended to be used as a microprocessor peripheral. The SPP control interface is directly compatible with the 6800 microprocessor bus, but can be adapted to other 8-bit microprocessors with the addition of a few MSI packages.

The high-speed number crunching capability of the SPP gives a standard microprocessor system the necessary computational speed to implement complex digital algorithms in real time.

Operating in a microprocessor system, the SPP can be viewed as a "hardware subroutine" module. The microprocessor can call up a "subroutine" by giving a command to the SPP. A powerful instruction set (including conditional branching and one level of subroutine) permits the SPP to function independently of the microprocessor once the initial command is given. The SPP will interrupt the microprocessor upon completion of its task. The microprocessor is free to perform other operations in the interim.

The SPP contains a high-speed serial port for direct interface to an analog-to-digital (A/D) converter. In many applications, real-time processing of sampled analog data can be performed within the SPP without tying up the main microprocessor. Data transfer to the microprocessor occurs upon completion of the SPP processing. The SPP interface environment is summarized in Figure 3.

Separate input and ouput registers exchange data with the SPP data ports. Serial interface logic converts the parallel 2's complement data to serial 2's complement or sign + magnitude format. Data format and source (serial or parallel port) is software selectable.

Table 1 summarizes direct commands given to the SPP from the control processor. These control modes are specified via four address lines brought to the SPP. The SPP is a memory-mapped peripheral, occupying 16 locations of the microprocessor memory space. Providing the proper SPP address will activate the corresponding control mode.

The control modes and the LIBL command enable real-time modification of the SPP programs. This permits a single SPP program to be used in several different applications. For example, an SPP might be programmed as a "universal" digital filter, with cutoff frequency, filter order, and data source (serial or parallel port) selected at execution time by the control microprocessor.

Figure 1. S2811 Object Code Instruction Formats.

	I_{16}	I_{12} I_{11}	I_8 I_7				I_0
SPP Instruction Format	OP2	OP1	OPERAND				
SPP Addressing Modes	←		17 BITS				→
	5 Bits	4 Bits	3 Bits	3 Bits	1 Bit	1 Bit	
Offset Addressing (UV/US)	OP2	OP1	0_1	0_2	0 = US / 1 = UV	0	
Direct Addressing (D)	OP2	OP1	Address (OH)			1	
Direct Transfer (DT)	OP2	OP1	Transfer Address (HH)				
Literal (L)	OP2	Data Word (HHH)					
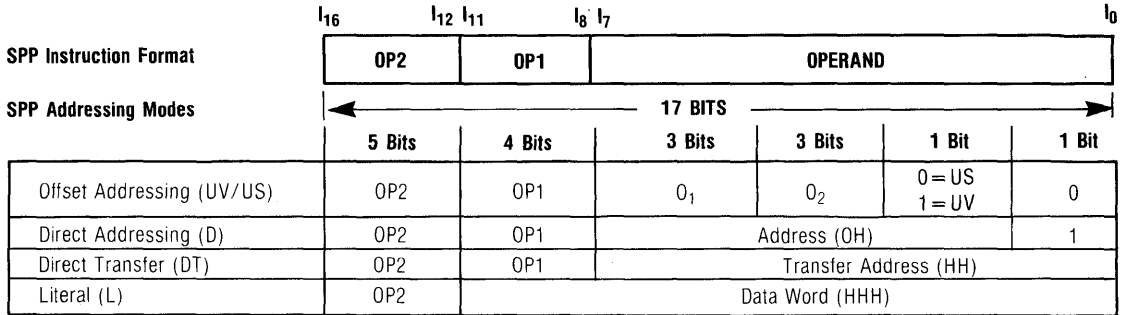
Addressing Mode	Effective Address		Multiplier Operands
	U	V/S	
UV	$(BAS) + 0_1$	$V = (BAS) + 0_2$	$P = U \cdot V$
US	$(BAS) + 0_1$	$S = 0_2$	$P = U \cdot S$
D	—	OH	$P = A \cdot V$

NOTE: 0 indicates an octal digit (3 bits) and H indicates a hexadecimal digit (4 bits)

Table 1. SPP Control Modes and Operations

Input leads F_0-F_3 define several control modes and operations to facilitate the interface between the SPP and a control processor. In general, these inputs are derived from the control processor address leads. The SPP will therefore occupy 16 memory locations, being a memory mapped peripheral.

Control Modes and Operations

F-Bus (F_3-F_0) Hex Value	Mnemonic		Operation/Function
0	CLR	(Clear)	Resets control modes to normal operation.
1	RST	(Reset)	Software master reset. Clears all SPP registers and starts execution at location 00.
2	DUH	(Data U/H)	Specifies MSByte of data word. DUH terminates data word transfer.
3	DLH	(Data L/H)	Specifies LSBs of data word.
4	XEQ	(Execute)	Starts execution at location specified on data lines.
5	SRI	(Ser. Inp.)	Enables serial input port.
6	SRO	(Ser. Out)	Enables serial output port.
7	SMI	(S/M Inp.)	Converts sign-magnitude serial input data to 2's complement form.
8	SMO	(S/M Out)	Converts 2's complement internal data to sign-magnitude serial output.
9	BLK	(Block)	Enables block data transfer.
A	XRM	(Ext. ROM)	Permits control of SPP using external instruction ROM. A special mode used primarily for testing.
B	SOP		Set Overflow Protect.
C	COP		Clear Overflow Protect.
D,E,F			Not Used.

Figure 2. SPP Instruction Timing Diagram

EACH TIME SLOT = 50ns
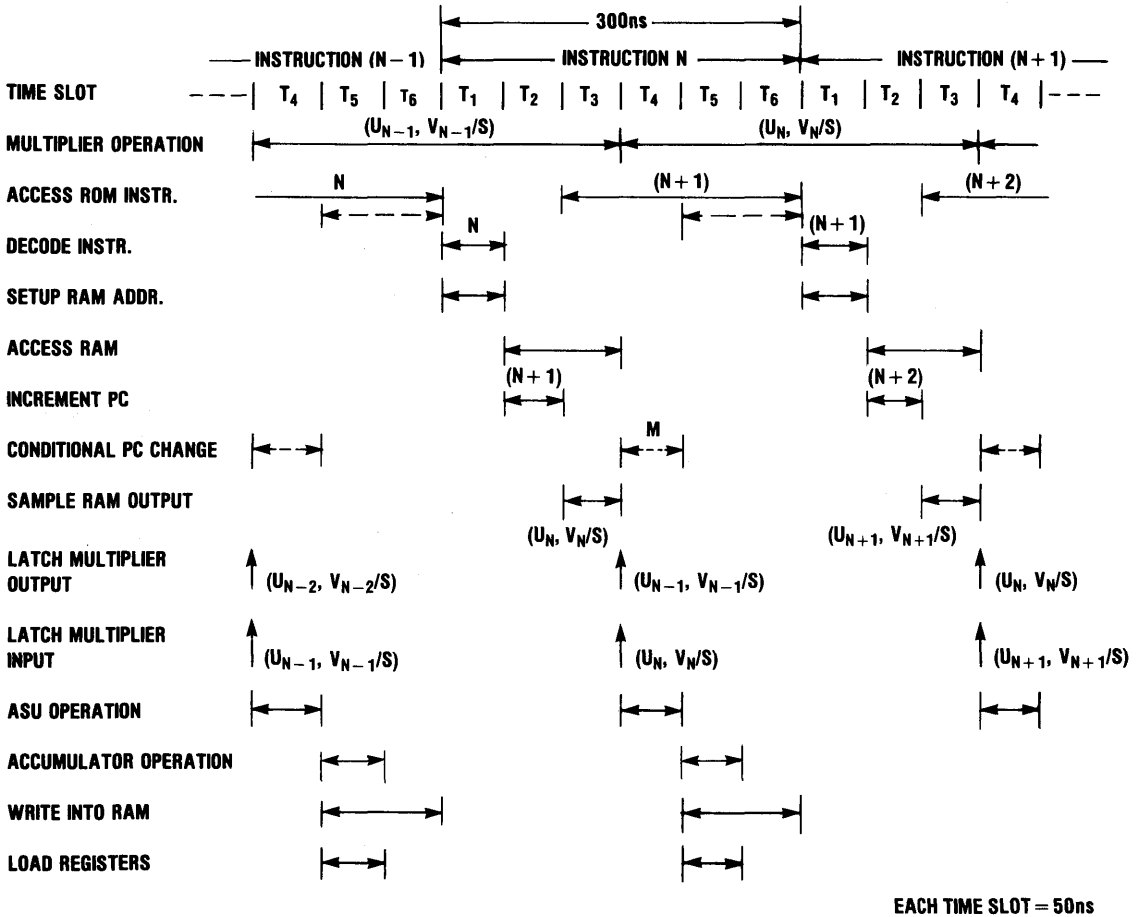
Figure 3. SPP Interface Environment
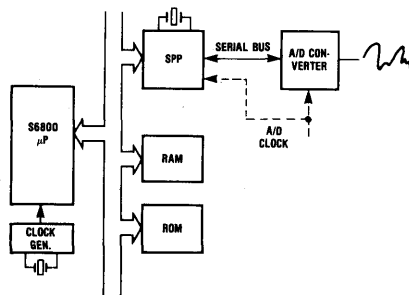
Figure 3-A. SPP to 6800 Interface
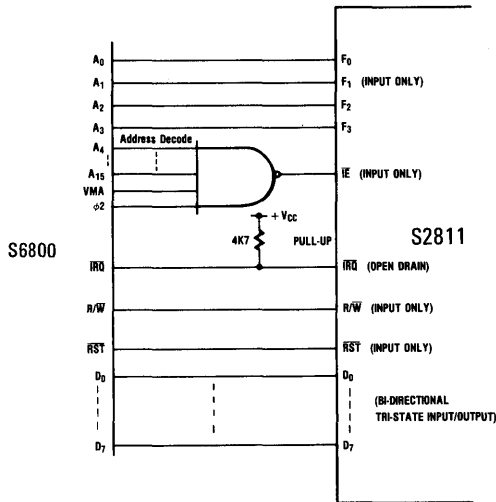
Figure 3-B.
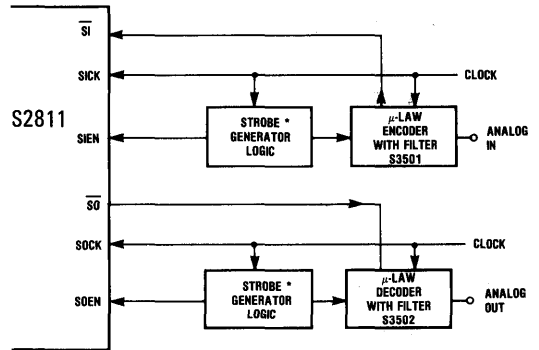
Note 1. μlaw → linear conversion is performed by the SPP software.

*Note 2. The input and output clocks and strobe generators may be realized with two (2) CMOS packages.

Figure 3-C. SPP Serial Port to PCM BUS Interface
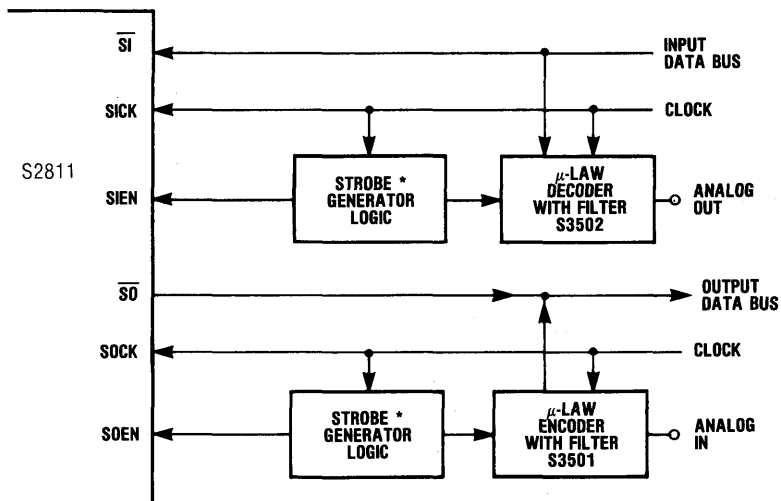
Figure 3-D. SPP Serial Interface Timing

SERIAL INPUT

1. SIEN must be synchronized to the falling edge of SICK such that the rise and fall of SIEN follow falling edge of SICK.
2. Data may contain 1 to 16 bits defined by width of SIEN. SPP will left justify data words < 16 bits.
3. Data are sampled on the trailing edge of SICK.
4. Minimum 16 SICK pulses + 4μsec. are required between SIEN rising edges.
5. If serial input buffer is full, SPP will ignore new input samples.
6. The serial data is inverted and may be either in sign + magnitude or two's complement code.

SERIAL OUTPUT

1 . Rise and fall of SOEN must follow falling edge of SOCK.
2 . Output data will be 1 to 16 bits defined by width of SOEN.
3 . Data are valid from rising edge to rising edge of SOCK so that the receiving system can sample data on trailing edge.
4 . If the serial output buffer is empty, all ones will be output.
5 . SO will be in a high impedance state when not enabled by serial output sequence.
6 . The serial data is inverted and maybe either in sign + magnitude or two's complement code.

Figure 3-E. SPP Parallel Interface Timing
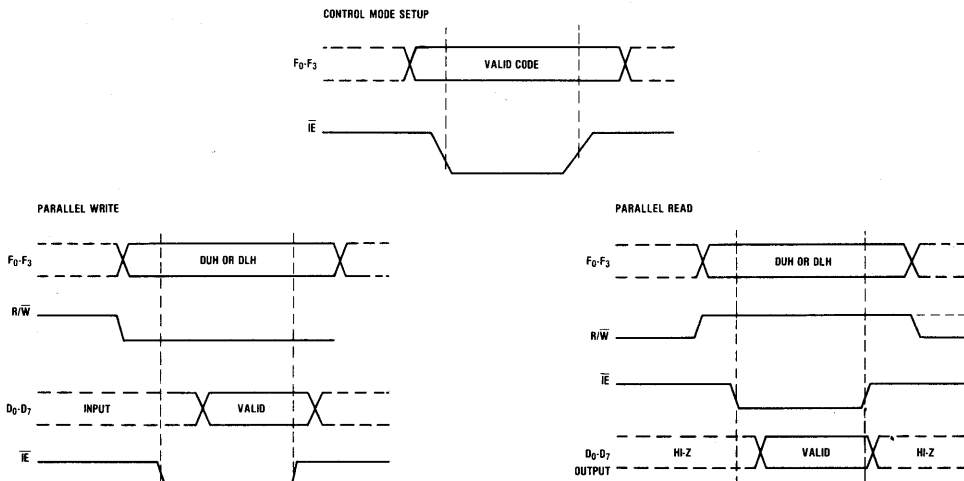
Table 2. OP1 Instructions

TYPE	MNEMONIC	HEX CODE I11-I8	ADDRESS MODES	OPERATIONS	DESCRIPTION
No Operation	NOP	0	- - -	None	**No OP**eration
Accumulator Operations	ABS	C	- - -	ABS (A)→A	**ABS**olute value of accumulator is placed in accumulator.
	NEG	D	- - -	−(A)→A	**NEG**ate accumulator contents (two's complement) and replace in accumulator.
	SHR	E	- - -	(A) / 2→A	**SH**ift **R**ight accumulator contents 1-bit position. Equivalent to dividing contents by two.
	SGV	F	UV/US, D	(A)→A, if sign (A)=sign V/S −(A)→A, if sign (A)≠sign V/S	**SiG**n of RAM output **V** is the sign of accumulator contents. Accumulator contents are negated (two's complement) if different sign from V. Useful in implementing hard limiter function.
Addition Operations	AUZ	2	UV/US	(U)+0→A	Add **U** and **Z**ero. Loads RAM output U into the accumulator.
	AVZ	1	UV/US, D	(V/S)+0→A	Add **V**/S and **Z**ero. Loads RAM output V/S into the accumulator.
	AVA	8	UV/US,D	(V/S)+(A)→A	**A**dd **V**/S and **A**ccumulator contents. Sum is placed back into accumulator.
	AUV	4	UV/US	(U)+(V/S)→A	**A**dd RAM outputs **U** and **V**/S and place sum in accumulator.
Subtraction	SVA	9	UV/US,D	(V/S)−(A)→A	**S**ubtract **V**/S and **A**ccumulator contents. The difference (V − A) is placed in the accumulator.
	SVU	5	UV/ US	(V/S)−(U)→A	**S**ubtract RAM outputs **V** and **U** and place difference (V − U) in the accumulator.
Multiply/ Add Operations	APZ	3	- - - (current inst.) UV/US, D (prec. instr)	(P)+0→A	**A**dd **P**roduct and **Z**ero. Loads multiplier product into the accumulator. The multiplier inputs were set up in the preceding instruction by addressing mode.
	APA	A	- - - (current inst.) UV/US, D (prec. instr)	(P)+(A)→A	**A**dd **P**roduct and **A**ccumulator contents. Result is placed in the accumulator. The multiplier inputs were set up in the preceding instructions by addressing mode.
	APU	6	UV (current instr) UV/US, D (prec. instr)	(P)+(U)→A	**A**dd **P**roduct and RAM output **U**. Sum is placed in accumulator. The multiplier inputs were set up in preceding instruction by addressing mode.
Multiply/ Subtract Operations	SPA	B	- - -(current instr) UV/US, D (prec. instr)	(P)−(A)→A	**S**ubtract **P**roduct and **A**ccumulator contents. Difference (P − A) is placed in accumulator. The multiplier inputs were set up in preceding instruction by addressing mode.
	SPU	7	UV/US (current instr) UV/US, D (prec. instr)	(P)−(U)→A	**S**ubtract **P**roduct and RAM output **U**. Difference (P − U) is placed in accumulator. The multiplier inputs were set up in preceding instruction by addressing mode.

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Table 3. SPP Instruction Set

OP2 Instructions

TYPE	MNEMONIC	HEX CODE I16-I12	ADDRESS MODES	OPERATIONS	DESCRIPTION
No Operation	NOOP	00	- - -	None	**NO OP**eration
Load Instructions	LLTI	1E	Literal	HHH→IR	Load **LiT**eral in **I**nput register. A 12-bit (3 hex digits) literal is transferred to the input register. This instruction cannot be used with an OP1 instruction or with a specified addressing mode. Literal is left justified to occupy bits 4-15 in register.
	LIBL	07	- - -	(IR)→BAS (IR)→LC	Load **I**nput register contents to **B**ase register and **L**oop counter. Bits 11-15 are loaded to the base register, while bits 4-8 are loaded to preset the loop counter. Clears input flag (LOW).
	LACO	02	- - -	(A)→OR	Load **AC**cumulator contents into the **O**utput Register. This is the basic data output instruction. Sets output flag (HIGH).
	LAXV	05	UV/US, D	(A)→IX, V/S (Â)→A	Load **A**ccumulator contents into Inde**X** register and RAM location **V**/S. Accumulator is truncated to 5 most significant bits after the operation.
	LALV	04	UV/US, D	(A)→LC, V/S	Load **A**ccumulator to **L**oop counter and RAM location **V**/S.
	LABV	03	UV/US, D	(A)→BAS, V/S (Â)→A	Load **A**ccumulator to **B**ase and RAM location **V**/S. Truncate accumulator contents to most significant 5 bits after the operation.
Data Transfer Instructions	TACU	0B	UV/US	(A)→U	**T**ransfer **A**ccumulator **C**ontents into RAM location **U**.
	TACV	0C	UV/US, D	(A)→V/S	**T**ransfer **A**ccumulator **C**ontents into RAM location **V**/S.
	TIRV	08	UV/US, D	(IR)→V/S	**T**ransfer **I**nput **R**egister Contents to RAM location **V**/S. This is the basic data input instruction. Clears input flag (LOW).
	TVPV	09	UV/US, D	VP→V/S	**T**ransfer contents of **VP** register (equals previous value of output V) to RAM location **V**/S.
	TAUI	10	UV/US	(A)→U	**T**ransfer **A**ccumulator contents into RAM location **U** using **I**ndex register as base.
Accumulator Operations	CLAC	01	- - -	0→A	**CL**ear the **AC**cumulator. Forces SWAP mode to normal operation and clears overflow flag.
Register Manipulation Instruction	INIX	0D	- - -	(IX) + 1→IX	**IN**crement the Inde**X** register.
	DECB	0E	- - -	(BAS) − 1→BAS	**DEC**rement the **B**ase register.
	INCB	0F	- - -	(BAS) + 1→BAS	**INC**rement the **B**ase register.
	SWAP	06	- - -	BAS↔IX	**SWAP** the roles of Base and Index registers.
Unconditional Branch Instruction	JMUD	15	DT	HH→PC	**JuM**p **U**nconditionally **D**irect to location indicated by 8-bit (two hex digits) literal HH. Cannot be used with an OP1 instruction requiring specific addr. mode.
	JMUI	11	UV/US	[(IX)]→PC	**JuM**p **U**nconditionally **I**ndirect to location indicated by contents of RAM address pointed to by index and displacement indicated by V/S. $[(V/S)_{0-7}]→PC$.

Table 3. SPP Instruction Set (Continued)

OP2 Instructions

TYPE	MNEMONIC	HEX CODE I16-I12	ADDRESS MODES	OPERATIONS	DESCRIPTION
Conditional Branch Instructions	JMCD	16	DT	HH→PC, if LC≠0 (LC) − 1→LC	JuMp Conditionally Direct to location indicated by 8-bit (two hex digits) literal HH, if loop counter is not zero. Loop Counter is decremented after the test.
	JMPZ	19	DT	HH→PC if (A)=0	JuMP to locatioh specified if accumulator contents are Zero as a result of previous instruction.
	JMPN	1A	DT	HH→PC if (A)<0	JuMP to location specified if accumulator contents are Negative as a result of previous instruction.
	JMPO	1B	DT	HH→PC if (A) Overflows	JuMP to location specified if accumulator Overflows as a result of previous instruction.
	JMIF	1C	DT	HH→PC if IF = 0	JuMp if Input Flag is low to location specified (Note 4).
	JMOF	1D	DT	HH→PC if OF = 1	JuMp if Output Flag is high to location specified (Note 4).
Subroutine Instruction	JMSR	14	DT	(PC) + 1→RAR, HH→PC	JuMp to SubRoutine. Execution jumps unconditionally to location indicated by 8-bit (two hex digits) literal HH. Return address is stored in RAR. Cannot be used with an OP1 instruction requiring specified address mode.
	RETN	13	- - -	(RAR)→PC	RETurN from subroutine. Execution continues at instruction following the JMSR instruction.
Complex Instructions	JCDT	18	DT	HH→PC if LC≠0, (LC) − 1→LC (BAS) + 1→BAS, (IX) + 1→IX	Jump Conditionally Direct Dual Tracking. Increment base and Index registers. Loop Counter is decremented after test.
	JCDI	17	DT	HH→PC if LC≠0, (BAS) + 1→BAS (LC) − 1→LC	Jump Conditionally Direct and Increment base register. Loop Counter is decremented after test.
	TVIB	0A	UV/US	(VP)→V/S, (BAS) + 1→BAS	Transfer contents of VP register to RAM location V/S and Increment Base register.
	MODE	1F	- - -	Control mode replaces OP1	OP1 code in this instruction can select any one of the several control MODEs/operations specified in Table 1.
	REPT	12	- - -	PC inhibited if LC≠0 (next instruction) (LC) − 1→LC (each iteration of next instruction.)	REPeat next instruction until LC = 0. Increment PC to access next instruction, then suppresses increment of PC if LC≠0. Loop Counter is decremented with each iteration of the repeated instruction.

NOTES:

1. Whenever the Index register is selected by an instruction OP2 it controls the entire line of code.
2. Loop Counter cannot underflow.
3. S refers to scratchpad.
4. Input flag is low if SPP has not received a new input word.
   Output flag is high if processor has not read previous output word.
5. (A) represents truncation of the accumulator to 5 most significant bits (sign and 4 MSB).
6. Multiplier input latches and the VP register are not updated when either the DT or L addressing modes are used in conjunction with an OP2 instruction.
7. - - - indicates don't care address mode.

SPP Addressing Modes

The SPP provides four methods of data access (see Figure 1). In the direct mode, the full address of the data is specified. Due to limitations in the instruction word size, only one data word at a time may be accessed in this manner, and only even displacement addresses.

In the relative (to base) mode the base register is set up using a LLTI/LIBL sequence, or LABV, and two data words are accessed simultaneously by specifying U and V displacements in the instruction word.

Data may be stored/retrieved from the scratchpad memory by specifying the scratchpad mode and providing scratchpad and U port displacements. The U port data is accessed relative to the base register. The scratchpad data is treated exactly the same as data accessed via the U and V RAM ports, except the 8-word scratchpad block is substituted for the V data block.

The fourth addressing mode is dual-tracking base addressing. This mode greatly increases throughput in matrix operations.

The JMIF and JMOF instructions provide the capability to synchronize the SPP when operating in synchronous sampled data systems. When executed these commands cause the SPP to set the $\overline{IRQ}$ output low, thus requesting service from the microprocessor. The SPP can be put in a wait loop until a new data sample is available at the IR or has been read from the OR, as appropriate. The TIRV and LIBL commands facilitate transfer of input data from the IR to data memory or the base register and loop counter respectively. LACO command provides for data transfer to the OR.

External ROM Mode (Figure 4)— The external ROM mode is primarily intended for testing the SPP; however, it can be used in the program development stage or in certain low speed applications for running the SPP with an off-chip PROM.

In this mode the SPP operates as a state machine. Selecting the XRM command initializes the state machine to the idle state (State 1). A HIGH level on the $\overline{IE}$ input following the entry into the idle state prepares the SPP (State 2) for sequential operation. When $\overline{IE}$ goes LOW the SPP will output PC on the D_0-D_7 lines (State 3). When $\overline{IE}$ goes HIGH, the LOW to HIGH transition can be used by the external logic to latch the PC. The HIGH level of $\overline{IE}$ forces SPP to State 4. A LOW level following this takes it to State 5. States 4 and 5 can be used for accessing the lower 8 significant bits of the instruction from the external PROM. SPP enters the lower order instruction bits from D_0-D_7 lines on the LOW-to-HIGH transition of $\overline{IE}$. The HIGH level of $\overline{IE}$ takes SPP to State 6. The new LOW of $\overline{IE}$ takes it to State 7. States 6 and 7 are used to access the higher order instruction bits from the external PROM on D_0-D_7 lines. At the same time the 17th bit of the instruction word can be entered on the $\overline{IRQ}$ line. These instruction bits are latched by the SPP on the LOW-to-HIGH transition if $\overline{IE}$. The HIGH level of $\overline{IE}$ takes SPP to State 8 which is the execution cycle for the SPP. $\overline{IE}$ must be held HIGH throughout the execution cycle (≈ 300ns). This sequence can be repeated as long as there is no requirement for data transfer to or from the SPP. (See Figure 4.) If the SPP requires service from the microprocessor, the $\overline{IRQ}$ output will be set LOW during State 8 (execution cycle). If the $\overline{IE}$ is taken to a LOW level within 250ns from the beginning of the execution cycle, the SPP will stay in State 1 and allow for data transfer to or from the SPP as normal mode. When $\overline{IE}$ goes back HIGH after completion of data transfer SPP advances to State 2 and the sequence can start again. When transferring two bytes of data the second transfer (DUH) must be initiated ($\overline{IE}$ LOW) within the 250ns limit.

Figure 4. External ROM Cycle Timing Diagram
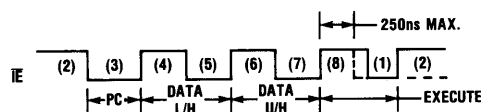
Table 4. OP1, OP2 Code Cross-Compatibility Table

Notes: X indicates the OP1, OP2 combination cannot be used
1. index register provides "base" information
2. CLAC overrides OP2 instruction
3. OP1 bits provide function code—see Table 1
4. address is not used with MODE and is available for setting up multiplier and VP register

Category	OP1→ / OP2↓	NOP	ABS	NEG	SHR	SGV	AUZ	AVZ	AVA	AUV	SVA	SVU	APZ	APA	APU	SPA	SPU	MULTIPLIER SETUP
		(Accumulator Operations)					(Addition Operations)				(Subtraction Operations)		(Multiply/Add Operations)			(Multiply/Sub. Operations)		
No Operation Instruction	NOOP																	
Load Instructions	LLTI	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X
	LIBL																	
	LACO																	
	LAXV																	
	LALV																	
	LABV																	
Data Transfer Instructions	TACU																	
	TACV																	
	TIRV																	
	TVPV																	
	TVIB																	
	TAUI						1	1	1	1	1	1			1		1	1
Accumulator Instructions	CLAC	See note 2 →																
Register Manipulation Instructions	INIX																	
	DECB																	
	INCB																	
	SWAP																	
Unconditional Branch Instructions	JMUD					X	X	X	X	X	X	X			X		X	X
	JMUI					1	1	1	1	1	1	1			1		1	1
Conditional Branch Instructions	JMCD					X	X	X	X	X	X	X			X		X	X
	JMPZ					X	X	X	X	X	X	X			X		X	X
	JMPN					X	X	X	X	X	X	X			X		X	X
	JMPO					X	X	X	X	X	X	X			X		X	X
	JMIF					X	X	X	X	X	X	X			X		X	X
	JMOF					X	X	X	X	X	X	X			X		X	X
Subroutine Instructions	JMSR					X	X	X	X	X	X	X			X		X	X
	RETN																	
Complex Instructions	JCDT					X	X	X	X	X	X	X			X		X	X
	JCDI					X	X	X	X	X	X	X			X		X	X
	MODE	See note 3 →																4
	REPT																	

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Circuit Description

Instruction ROM — The SPP program is stored in a 256x17 bit ROM. The 17-bit wide instruction word (See Figure 1) facilitates multiple operations per instruction. Addresses 250-255 are reserved for chip testing.

Data Memory — The 256x16 bit data memory is organized to provide two operands (U, V) in a single fetch cycle. The 256 data words are structured in a 32-'base' by 8-'displacement' word matrix. Memory is further partitioned such that each base group contains 4 words of RAM (displacements 0 through 3) and 4 words of ROM (displacements 4 through 7). Only the base information is fed to the RAM/ROM core. All eight displacement words associated with that base are accessed in parallel. Two independent displacement multiplexers select the two operands (U, V) from the eight output words. Within an 8-word base, therefore, the memory appears to have three ports.

Scratchpad Memory — An 8-word scratchpad memory (all RAM) is provided so that common data may be accessed with the full efficiency of data contained within an 8-word base. An additional multiplexer on the "V" memory port accesses the scratchpad data instead of data from the main memory core. Since this is independent of the base group, the scratchpad contents may be considered as a "floating" base group. This feature doubles the efficiency of equalizer tap update and similar programs.

VP Register — The VP register provides a one-instruction delay of data accessed from the memory "V" port. The memory read cycle precedes the write cycle (see Figure 2). The VP register consists of two portions. Data from the n-th read cycle first enters the master portion. During the next cycle, data from instruction $n+1$ enters the master portion while the instruction n data shifts to the slave portion. The data in the slave portion may be returned to the memory during the instruction $n+1$ write cycle by use of the commands TVPV or TVIB. thus digital filter z^{-1} delays are implemented with minimal software overhead.

RAR — A return address register allows one level of subroutine nesting. This facilitates repeated use of universal subroutines such as a second order digital filter routine, SIN/COS routine, etc., thus minimizing the program size.

Loop Counter — A loop counter is provided to handle iteration loops up to 32 iterations. Special jump instructions conditional on this loop counter to be zero, provide the iteration test without adding program steps. The loop counter can be loaded from the Input Register as well as the Accumulator.

Index Register — The index register is 5 bits wide and is used to access lookup tables. This register can be incremented by a software command. Lookup table instructions cause the index contents to be used as the data memory base. Table contents may be used either as data or as jump addresses for computed GO-TO operations. Special instructions allow the base and the index register to work together, providing a dual base addressing scheme. The index is also used to step through the data memory during block transfer operations.

ASU — The heart of the SPP is a 16-bit adder/subtractor unit (ASU). The ASU operates with two's complement arithmetic, and is provided with zero, negative and overflow detect circuits. The basic adder cell includes look-ahead carry logic to improve speed. The ASU will deliver a 16-bit sum in 40 nanoseconds. An accumulator latch follows the ASU. A shifter is available to shift the accumulator contents 1 bit to the right, providing a precision divide-by-two.

Multiplier — The SPP incorporates a parallel modified Booth's algorithm multiplier. The multiplier inputs are truncated to 12 bits and the multiplier output is rounded to 16 bits. These truncations produce a product with a resolution of >15 bits. The 16 MSBs of the product are retained. This implies that all numbers in the SPP are represented as fractions less than one in magnitude. The imaginary binary point is to the left of the MSB. This fractional representation and the fixed-point arithmetic requires proper scaling of equations to realize the full accuracy of the SPP. A benefit of fractional representation of numbers is that the multiplier cannot overflow. The propogation delay through the multiplier is 300 nanoseconds. A 300-nanosecond SPP instruction cycle is achieved by pipelining the multiplier. Data entered into the multiplier during instruction n will result in a product available during instruction $n + 1$. (See Figure 2.) The one instruction delay removes the multiplier propogation delay from the overall instruction cycle.

Multiplication is automatically set up by the address mode (see Figure 1). The multiplier is always active. Products are utilized by specifying one of the multiplier OP1 operators (APZ, APA, APU, SPA, SPU). The multiplier latches are updated wherever the instruction operand is a D or UV/S address. They are not updated if the operand is a Literal or DT, and the product of the previous set-up is retained until one of the multiplier OP1 operators is used to read it out.

Programming Examples

In this section two programming examples are provided to illustrate the use of some of the instructions and the power of the instruction set. The first example is that of a second order digital filter section. This can be implemented as a subroutine in the SPP such that the main program can access it repeatedly to implement higher order filter sections. The second example is that of a SINCOS subroutine that computes the values of sin ω and cos ω using an approximation formula. This routine was chosen as it illustrates the use of some of the complex instructions and because it is useful in applications that require carrier generation.

1. A Second Order IIR Digital Filter Section: Figure 5 shows a block diagram, filter equations and the computational process involved in the implementation of this filter. It is clear that storage must be provided for the fixed coefficients a_1, a_2, b_1 and b_2 and previous two intermediate results W_{n-1} and W_{n-2}. Figure 7 illustrates the memory configuration at the beginning of the subroutine. Fixed coefficients are conveniently stored in the ROM portion of the data memory in displacements 4 through 7 while displacements 0 and 1 are used

for storage of past values. It is assumed that the present input sample X_n is loaded in the accumulator by the main program prior to accessing the subroutine. At the end of the subroutine output Yn is left in the accumulator while W_{n-1} and W_{n-2} are replaced by W_n and W_{n-1} so that the next input sample X_{n+1} can be processed. Note that only one base value is used by the filter for the storage and main program must load this value in the base register prior to execution.

Figure 6 illustrates the instruction sequence of the subroutine. Only five instructions are needed to completely process the section. This corresponds to a processing time of 1.5 microseconds. Figure 7 illustrates how the memory map gets modified during the execution. A higher order filter is implemented by cascading of the second order sections. The main program can increment the base register and decrement the loop counter after each iteration until the required number of iterations of this subroutine take place. Since the accumulator holds the output of the filter after each iteration, no storage is required in memory. Figure 8 illustrates the program and memory allotment for implementation of a sixth order filter.

Figure 5. Digital Filter Example

A. Second Order Recursive IIR Digital Filter Section

B. Computation Process

Input Samples $X(n) \cdots, X_{(n-2)}, X_{(n-1)}, \boxed{X_n}, \cdots$

Intermediate Results $W(n) \cdots, \boxed{W_{(n-2)}, W_{(n-1)}, W_n,} \cdots$

Output Samples $Y(n) \cdots, Y_{(n-2)}, Y_{(n-1)}, \widehat{Y_n}, \cdots$

Sampling Instants $\cdots, t_{(n-2)}, t_{(n-1)}, t_n, \cdots$

C. Digital Filter Equations

$$W_n = X_n + a_1 W_{(n-1)} + a_2 W_{(n-2)}$$

$$Y_n = W_n + b_1 W_{(n-1)} + b_2 W_{(n-2)}$$
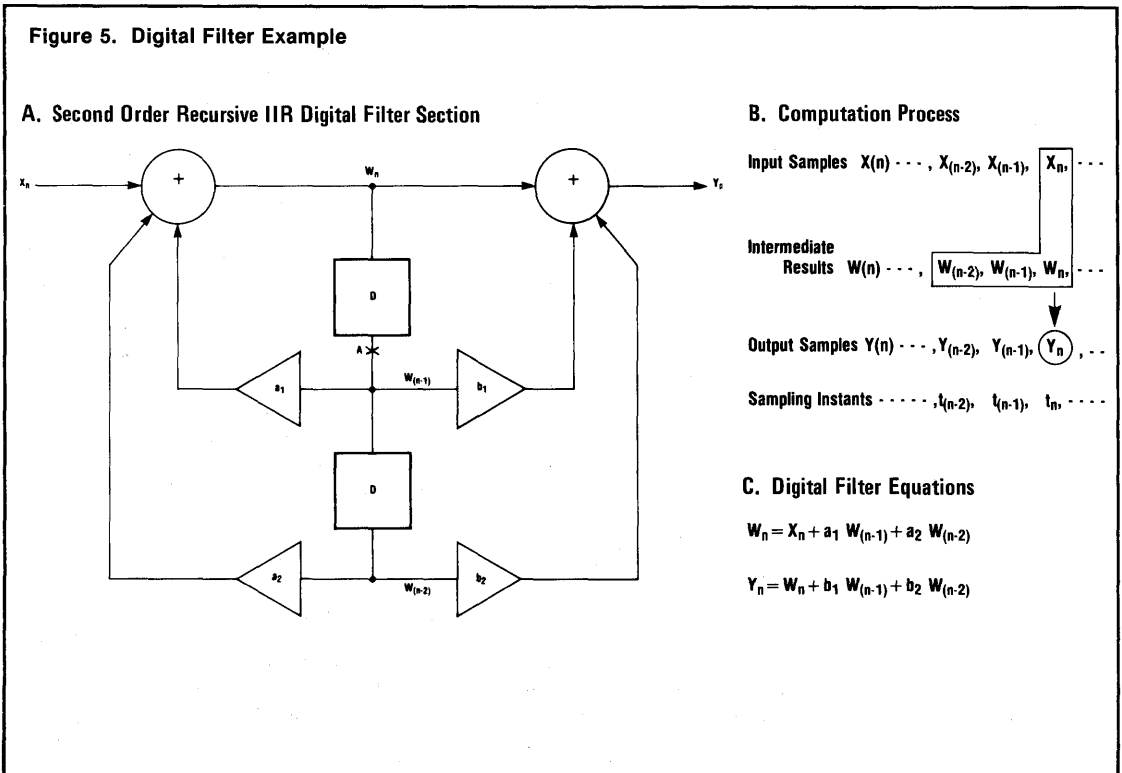
Figure 6. Digital Filter Subroutine

LINE #	LABEL	OP1	OP2	OPERAND	COMMENTS
0	DFIL	NOP	NOOP	UV(4,0)	a_1, $W_{n-1} \rightarrow$ MULT. ACC $= X_n$
1		APA	NOOP	UV(5,1)	a_2, $W_{n-2} \rightarrow$ MULT. $X_n + a_1 W_{n-1} \rightarrow$ ACC
2		APA	TACV	UV(6,0)	b_1, $W_{n-1} \rightarrow$ MULT. $W_n = X_n + a_1 W_{n-1} + a_2 W_{n-2} \rightarrow$ ACC ACC $\rightarrow$ V(0) (replace W_{n-1}) $W_{n-1} \rightarrow$ (VP)
3		APA	TVPV	UV(7,1)	b_2, $W_{n-2} \rightarrow$ MULT. $W_n + b_1 W_{n-1} \rightarrow$ ACC $W_{n-1} \rightarrow$ V(1) (replaces W_{n-2})
4		APA	RETN	—	$Y_n = W_n + b_1 W_{n-1} + b_2 W_{n-2} \rightarrow$ ACC Return to main program

Figure 7. Memory Maps for the Digital Filter

DISPL	BASE = N			
0	W_{n-1}	W_n	W_n	W_n
1	W_{n-2}	W_{n-2}	W_{n-1}	W_{n-1}
2	—	—	—	—
3	—	—	—	—
4	a_1	a_1	a_1	a_1
5	a_2	a_2	a_2	a_2
6	b_1	b_1	b_1	b_1
7	b_2	b_2	b_2	b_2
	Initial	End of line 2	End of line 3	Final
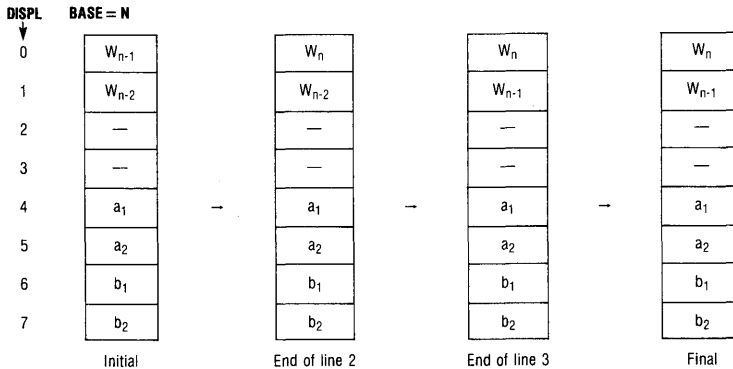
Figure 8-A. Main Program Instructions for a Sixth Order Filter

LABEL	OP1	OP2	OPERAND	COMMENTS
		•		
		•		
		•		
	NOP	LLTI	002	(IR) = 002
	NOP	LIBL	—	$0 \rightarrow$ BAS, $2 \rightarrow$ LC Initialize base register and loop counter
LOOP	—	JMSR	DFIL	Jump to DFIL subroutine
	—	JCDI	LOOP	Increment base, Test if LC = 0
		•		If non zero go to LOOP
		•		Decrement LC after test
		•		Output of the filter is in accumulator at the end of iterations.

Figure 8-B. Memory Map for the Sixth Order Filter

Base → DISPL ↓	0	1	2	—
0	$W_{0(n-1)}$	$W_{1(n-1)}$	$W_{2(n-1)}$	
1	$W_{0(n-2)}$	$W_{1(n-2)}$	$W_{2(n-2)}$	
2	—			
3	—			
4	a_{01}	a_{11}	a_{21}	
5	a_{02}	a_{12}	a_{22}	
6	b_{01}	b_{11}	b_{21}	
7	b_{02}	b_{12}	b_{22}	

Implementation of Second Order Digital Filter with Coefficients >1 in the S2811

In order to be able to implement a digital filter with coefficients in the range of -2 to $+2$ it is necessary to scale the coefficients by a factor of 2 to bring them into the permissible range of -1 and $+1$. However, in order to restore the "loop gain" of the recursive section of the filter it is necessary to correct for this in the signal flow network. The easiest way to do this is to double the signal level at the point A in Figure 5. The modified second order filter subroutine is shown below, together with the basic subroutine. Note that in the modified subroutine all the coefficients must be halved.

Basic Subroutine (|coefficients| <1)

0	NOP	NOOP	UV(4,0)	$a_1, W_{n-1} \to$ MULT. $ACC = X_n$
1	APA	NOOP	UV(5,1)	$a_2, W_{n-2} \to$ MULT. $X_n + a_1 W_{n-1} \to ACC$
2	APA	TACV	UV(6,0)	$b_1, W_{n-1} \to$ MULT. $W_n = X_n + a_1 W_{n-1} + a_2 W_{n-2} \to ACC$ $ACC \to V(0)$ (replace W_{n-1}) $W_{n-1} \to$ (VP)
3		TVPV	UV(7,1)	$b_2, W_{n-2} \to$ MULT. $W_n + b_1 W_{n-1} \to ACC$ $W_{n-1} \to V(1)$ (replaces W_{n-2})
4	APA	RETN		$Y_n = W_n + b_1 W_{n-1} + b_2 W_{n-2} \to ACC$ Return to main program

Modified Subroutine (|coefficients| <2)

0	NOP	NOOP	UV(4,0)	
1	APA	NOOP	UV(5,1)	as above
2	APA	TACV	UV(6,0)	
3	APA	TVPV	UV(7,1)	
4	APA	TACV	US(−,0)	$Y_n = W_n + b_1 W_{n-1} + b_2 W_{n-2} \to$ ACC $\to$ S(0)
5	AUV	TACV	UV(0,0)	$U(0) + V(0) \to ACC \to V(0)$ $= 2W_{n-1}$
6	AVZ	RETN	US(−,0)	$S(0) \to ACC = Y_n$

2. SINCOS: SINCOS is a subroutine that provides the sin ω values for values of ω satisfying the condition $-\pi \le \omega < \pi$. Since all numbers in the SPP are represented as fractions less than 1 it is first necessary to scale by a factor π such that $-1 \le \dfrac{\omega}{\pi} < 1$. The value $\omega' = \dfrac{\omega}{\pi}$ is assumed to be in the accumulator at the beginning of the subroutine. In a practical application the control processor can enter ω' into the SPP before the computation begins. If the control processor does not have scaled values of ω available, an alternative method can be used. In this method the control processor can enter $\dfrac{\omega}{4}$ into the SPP. $\dfrac{\omega}{4}$ can be easily obtained by a 2-bit right shift operation. The SPP can then convert $\dfrac{\omega}{4}$ to $\dfrac{\omega}{\pi}$ by first multiplying $\dfrac{\omega}{4}$ by $\dfrac{2}{\pi}$ and then adding the result to itself. In any event it is assumed that $\omega' = \dfrac{\omega}{\pi}$ is available in the accumulator when the subroutine is accessed. When the control is returned to the main program sin ω is available in s(0) and cos ω is available is s(1) while ω' remains in the accumulator as well as s(2). The subroutine computes the sin ω and cos ω values by use of the following approximation:

For small values of $\Delta\omega$:

$$\sin \Delta\omega \cong \Delta\omega$$

$$\cos \Delta\omega \cong 1$$

$$\sin\omega = \sin (\hat{\omega} + \Delta\omega) = \sin\hat{\omega} \cos\Delta\omega + \cos\hat{\omega} \sin\Delta\omega$$
$$\cong \sin\hat{\omega} + \Delta\omega \cos\hat{\omega}$$

$$\cos\omega = \cos (\hat{\omega} + \Delta\omega) = \cos\hat{\omega} \cos\Delta\omega - \sin\hat{\omega} \sin\Delta\omega$$
$$\cong \cos\hat{\omega} - \Delta\omega \sin\hat{\omega}$$

ω represents the nearest quantized value to ω. In the subroutine the quantized value is obtained by truncating $2|\omega'| = (\dfrac{2}{\pi} |\omega|)$. The truncation results in five

most significant bits including the sign bit. Since absolute value is truncated, sign bit is zero. The four most significant magnitude bits provide sixteen quantized angles $2|\hat{\omega}'| = \omega_q$. ω_q is loaded in the index register. Use of SWAP command allows the index register to access the appropriate block of data memory corresponding to ω_q. Sin $\hat{\omega}$ and cos $\hat{\omega}$ values corresponding to ω_q are stored in displacements 4 and 5 (ROM portion) of the appropriate block addressed by ω_q. Figure 10-A illustrates the organization of the lookup table.

Figure 9 shows a detailed sequence of instructions for the SINCOS routine. The routine is nineteen instructions long and takes 5.7 microseconds to execute. As seen from Figure 9, the first objective of the program is to transform the input angle to the first quadrant. This transformation process is graphically illustrated in Figure 10-B. The input angle ω' is stored in s(0) and a number $[½-|\omega'|]$ is stored in s(1). The signs of these numbers are used to assign the sign to the magnitudes of sin ω and cos ω computed by the approximation formulae. Table 10-C illustrates how the sign of sin ω can be taken from the sign of the angle ω' and sign of cos ω can be taken from the sign of the number $[½-|\omega'|]$. The

signs are assigned by use of the SGV instruction at the end of the subroutine. The quantized angle ω_q is computed by truncation of the number $2|\omega'|$. The truncated value (five most significant bits including sign bit) are loaded in the index register by the LAXV instruction and allows direct access of the sin $\hat{\omega}$ and cos $\hat{\omega}$ values from the appropriate block. $\Delta\omega$ is computed simply as a difference between the input and the quantized angle. The sin ω and cos ω values are stored in s(0) and s(1) respectively while the angle ω' is retained in the accumulator as well as s(2) when the program exits.

The SINCOS subroutine ilustrates the following operations:
— Scaling
— Table Lookup
— Use of SWAP command
— Use of SCRATCHPAD
— All Data Addressing Modes
— Use of SGV command
— Use of TVPV command
— Truncation of the accumulator using LAXV command.

Figure 9. SINCOS Subroutine

SINCOS Routine

LINE #	LABEL	OP1	OP2	OPERAND	COMMENTS
0	SINCOS	NOP	TACV	UA(-,0)	$\omega' = \dfrac{\omega}{\pi} \to$ s(0), ACC
1		ABS	SWAP	- -	$\lvert \omega' \rvert \to$ ACC, SWAP roles of base and index
2		SVA	NOOP	D(½)	½ - $\lvert \omega' \rvert \to$ ACC, D(½) refers to the address of location containing the constant ½
3		NOP	TACV	US(-,1)	½ - $\lvert \omega' \rvert \to$ s(1), ACC
4		AVA	NOOP	US(-,1)	s(1) + ACC $\to$ ACC = (1-2$\lvert \omega' \rvert$)
5		ABS	NOOP	- -	$\lvert (1\text{-}2\lvert \omega' \rvert) \rvert \to$ ACC
6		SVA	NOOP	D(1)	2$\lvert \omega' \rvert \to$ ACC
7		NOP	LAXV	US(-,2)	2$\lvert \omega' \rvert \to$ s(2). $\hat{\omega}' \to$ ACC, IX. $\hat{\omega}'$ = quantized value corresponding to ω
8		SVA	TACV	US(-,2)	2$\lvert \omega' \rvert - \hat{\omega}' = 2\Delta\omega' \to$ ACC, s(2)
9		AVA	NOOP	US(-,2)	s(2) + ACC = $\to$ ACC (4$\Delta\omega'$)
10		NOP	NOOP	D(π/4)	$\dfrac{\pi}{4}$, 4$\Delta\omega' \to$ MULT.
11		APZ	TACV	US(-,2)	$\pi\Delta\omega' \to$ ACC, s(2) ($\pi\Delta\omega' = \Delta\omega$)
12		NOP	NOOP	US(4,2)	sin$\hat{\omega}$, $\Delta\omega \to$ MULT. Index register contents $\hat{\omega}'$ point to sin$\hat{\omega}$ in displacement 4 of the appropriate block.
13		SPU	TACV	US(5,2)	$\Delta\omega$sin$\hat{\omega}$ $-$ cos$\hat{\omega}$ = $-$ cos$\omega \to$ ACC, s(2). $\Delta\omega$, cos$\hat{\omega} \to$ MULT.
14		APU	SWAP	US(4,2)	sin$\hat{\omega}$ + $\Delta\omega$cos$\hat{\omega}$ = sin$\omega \to$ ACC. Transfer control back to base register.
15		SGV	TACV	US(-,0)	Assign the sign of ω' to (sinω) and store result in s(0). sin$\omega \to$ s(0), $\omega' \to$ (VP)
16		AVZ	TVPV	US(-,2)	$-$ cos$\omega \to$ ACC. (VP) = $\omega' \to$ s(2). Refer to the description of the VP register for explanation of TVPV instruction.
17		SGV	TACV	US(-,1)	Assign the sign of [½-$\lvert \omega' \rvert$] to cosω and store result in s(1). cos$\omega \to$ s(1)
18		AVZ	RETN	US(-,2)	$\omega' = \dfrac{\omega}{\pi} \to$ ACC. Return to main program.

Figure 10-A. Organization of the Lookup Table for SINCOS Routine

DISPLACEMENT

DATA MEMORY

RAM → 0, 1, 2, 3

ROM → 4, 5, 6, 7

Row 4: $\sin(0)$ ... $\sin\left(\frac{\pi}{2}\cdot\omega_q\right) = \sin\hat\omega$ ... $\sin\dfrac{15\pi}{32}$

Row 5: $\cos(0)$ ... $\cos\left(\frac{\pi}{2}\cdot\omega_q\right) = \cos\hat\omega$ ... $\cos\dfrac{15\pi}{32}$

BASE, IX $(16\omega_q)$ → 0 | 1 | . . . . | $16\omega_q$ | . . . . | 15 | 16 | 31

ω_q → 0 | $\dfrac{1}{16}$ | . . . . | ω_q | $\dfrac{15}{16}$

$$\omega_q = 2\,|\hat\omega'| = 2\left(\dfrac{|\hat\omega|}{\pi}\right) = \dfrac{2}{\pi}\,|\hat\omega|$$

$$\sin\left(\dfrac{\pi}{2}\,\omega_q\right) = \sin\left(\dfrac{\pi}{2}\cdot\dfrac{2}{\pi}\,|\hat\omega|\right) = \sin\hat\omega$$
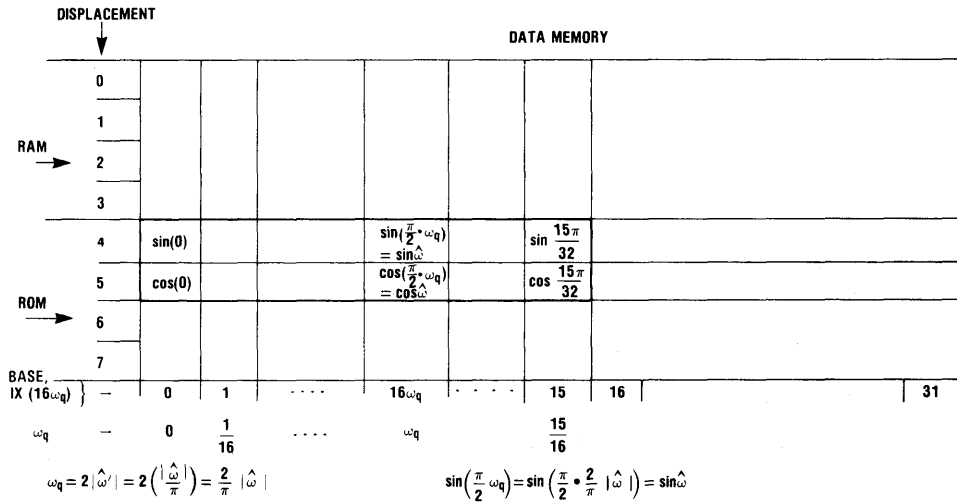
Figure 10-B. Graphical Angle Transformation Process

$$\omega \quad\rightarrow\quad \omega' = \dfrac{\omega}{\pi} \quad\rightarrow\quad 2\,|\omega'|$$
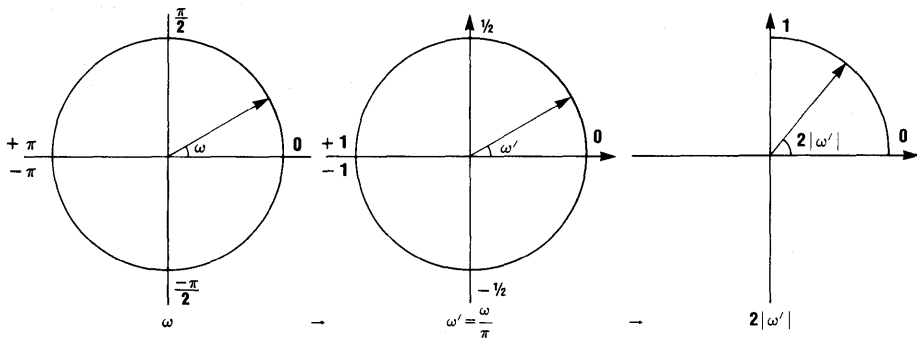
Figure 10-C. Table for Computing Sign of sinω, cosω

QUANDRANTS

	1	2	3	4
Range of ω	$0\rightarrow\pi/2$	$\pi/2\rightarrow\pi$	$-\pi\rightarrow-\pi/2$	$-\pi/2\rightarrow0$
Range of ω'	$0\rightarrow\frac{1}{2}$	$\frac{1}{2}\rightarrow1$	$-1\rightarrow-\frac{1}{2}$	$-\frac{1}{2}\rightarrow0$
Range of $[\frac{1}{2}-|\omega'|]$	$\frac{1}{2}\rightarrow0$	$0\rightarrow-\frac{1}{2}$	$-\frac{1}{2}\rightarrow0$	$0\rightarrow1/2$
Sign of ω'	+	+	−	−
Sign of sinω	+	+	−	−
Sign of $[\frac{1}{2}-|\omega'|]$	+	−	−	+
Sign of cos ω	+	−	−	+

AMI

AMERICAN MICROSYSTEMS, INC.

FAST FOURIER TRANSFORMER

Features

☐ Performs 32 Complex or 64 Real Point Forward or Inverse FFT in 1.5msec Using Decimation in Frequency

☐ Transform Expandable Either by Using Multiple S2814s for Minimum Processing Time or a Single S2814 for Minimum Hardware

☐ Operates with S6800 Microprocessor and 6844 DMA Controller, or S9900 Microprocessor and AM2940 DMA Controller for Higher Speed

☐ Block Data Transfer and I/O Carried Out on Microprocessor Data Bus

☐ Optional Conditional Array Scaling Gives Over 70dB Dynamic Range With 57dB resolution on Transforms Up to 2048 Points.

☐ Optional Windowing Algorithm Permits Use of Arbitrary Weighting

☐ Coefficient Generation On Chip, With Rotation Algorithm for Transform Expansion

☐ Uses AMI's VMOS Technology to Achieve High Speed and Low Power Dissipation

General Description

The AMI S2814 Fast Fourier Transformer calculates FFTs using a decimation in frequency technique for minimum distortion. The S2814 calculates a basic 32-point FFT using internal coefficients. A coefficient rotation algorithm is provided so that larger FFT's may be implemented (in blocks of 32-points). The S2814 includes optional conditional array scaling for maximum range.

The S2814 is intended for use in a microprocessor system (see Figure 1) including a microprocessor, ROM, RAM and a DMA controller. The microprocessor controls the flow of signal processing by selectively calling routines in the S2814. Data points are stored in RAM, and are block transferred into and out of the S2814 using the DMA controller. Windowing weights and setup data are loaded into the S2814 prior to processing. A 6800-compatible source listing of a suitable control program, complete with description, will be available to the S2814 user at no charge. This control program will also be available as a pre-programmed ROM.

Block Diagram

4.0MHz
S6802 MPU
S6846 ROM
RAM*
6844 DMAC
S2814 FFT
20MHz
DATA BUS   ADDRESS BUS
4 BYTES PER TRANSFORM POINT

Pin Configuration

NOT USED	1	28	NOT USED
V_{CC}	2	27	N. C.
N.C.	3	26	NOT USED
V_{SS}	4	25	NOT USED
D_0	5	24	NOT USED
D_1	6	23	NOT USED
D_2	7	22	OSCI
D_3	8	21	OSC_0
D_4	9	20	F_0
D_5	10	19	F_1
D_6	11	18	F_2
D_7	12	17	F_3
$R/\overline{W}$	13	16	$\overline{RST}$
$\overline{IRQ}$	14	15	$\overline{IE}$

DATA BUS (D0–D7), CONTROL BUS (F0–F3)

PACKAGE 28 PIN D.I.L.
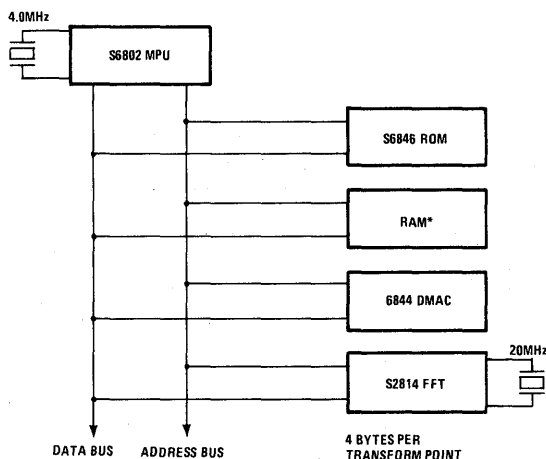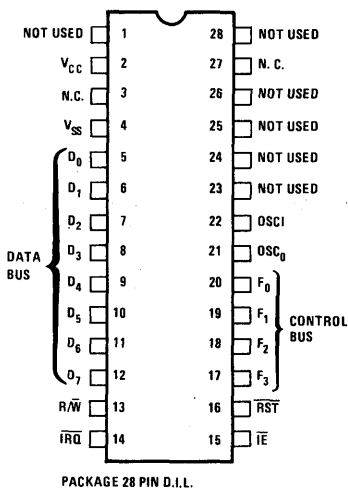
Absolute Maximum Ratings:

Supply Voltage .... +7V D.C.
Operating Temperature Range .... 0°C to +70°C
Storage Temperature Range .... −55°C to +125°C
Voltage on any Pin .... V_{SS} −0.3V to V_{CC} +0.3V
Lead Temperature (Soldering, 10sec) .... 200°C

Abbreviated Electrical Specifications
V_{CC} = 5.0V +5%. V_{SS} = 0V. T_A = 0°C to +70°C

All Inputs and Outputs .... TTL Compatible
Clock Frequency .... 20MHz Guaranteed
Power Dissipation .... 0.5W (Typical) — 1W (Max.)

FFT Performance Data

# Of Points (Complex)	# Of 32 Point Transforms (=N)	Execution Time msec	
		Using Single S2814	Using N S2814s
32	1	1.5	—
64	2	3.35	2.25
128	4	8.2	2.25
256	8	19.4	2.62
512	16	44.8	3.0
1024	32	101.6	3.35
2048	64	225.2	3.5

Note: Executions assume 2Mbyte/sec DMA transfer rate.

AMI
AMERICAN MICROSYSTEMS, INC.

DTMF BANDSPLIT FILTER

Features

☐ CMOS Technology for Wide Operating Single Supply Voltage Range (10.0V to 13.5V). Dual Supplies (±5.0V to ±6.75V) Can Also Be Used.

☐ Uses Standard 3.58MHz Crystal as Time Base.

☐ Ground Reference Internally Derived and Brought Out.

☐ Programmable Gain Input Amplifier Stage

☐ Limiter and Filter Outputs Separately Available

General Description

The S3525 DTMF Bandsplit Filter is a 18-pin monolithic CMOS integrated circuit designed to implement a high quality DTMF tone receiver system in conjunction with a suitable receiver circuit. The device includes a dial tone filter, high group and low group separation filters and limiters for squaring of the filtered signals. An uncommitted input amplifier allows a programmable gain stage. An overall signal gain of 6dB is provided for the low group and high group signals in the circuit. The dial tone filter is designed to provide a rejection of at least 52dB in the frequency band of 300Hz to 500 Hz. The only difference between the S3525A and the S3525B is the frequency of output clock signal at the CKOUT pin. In the S3525B, it is a 894.89kHz square wave while in the S3525A, it is a 3.58MHz buffered oscillator signal. The S3525A can be used with digital DTMF receiver chips that need the TV crystal time base allowing use of only one crystal between the filter and receiver chips.

Block Diagram

Pin Configuration
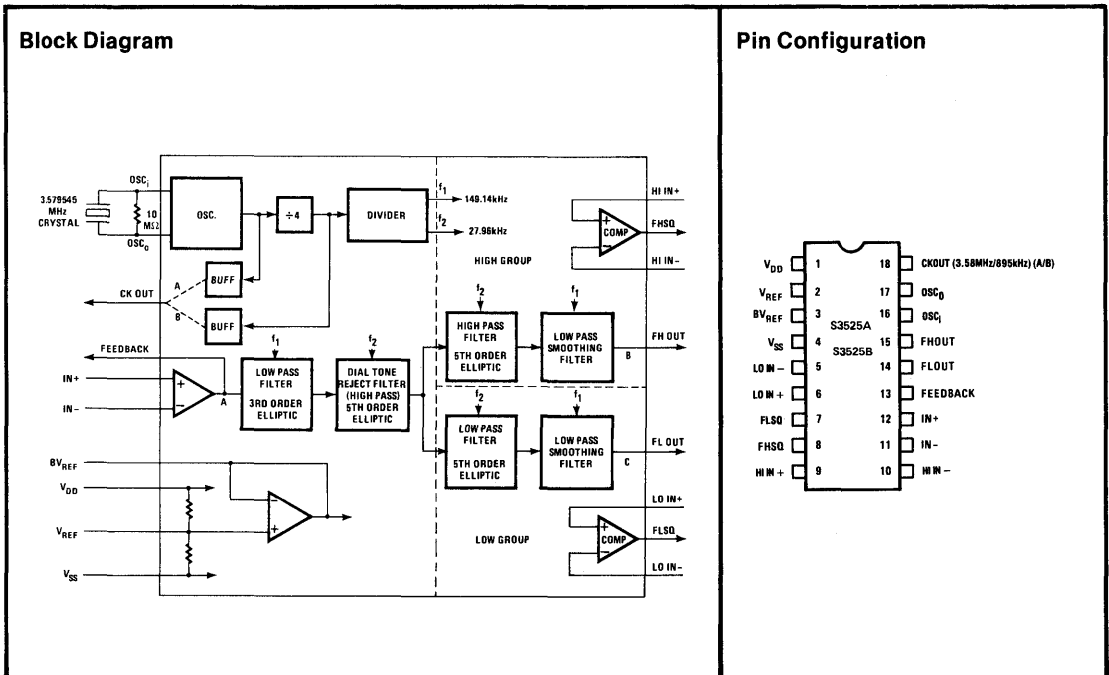
Absolute Maximum Ratings:

DC Supply Voltage (V$_{DD}$ - V$_{SS}$) .... +15.0V
Operating Temperature .... 0°C to +70°C
Storage Temperature .... −55°C to +125°C
Analog Input .... 1/4(V$_{DD}$ - V$_{SS}$) ⩽ V$_{IN}$ ⩽ 3/4(V$_{DD}$ - V$_{SS}$)
Operating Supply Voltage (V$_{DD}$ - V$_{SS}$) .... +10.0V to +13.5V

Electrical Operating Characteristics: $T_A = 25°C$

Symbol	Parameter/Conditions	Min.	Typ.	Max.	Units
V$_{DD}$	Positive Supply (Ref to V$_{SS}$)	10.0	12.0	13.5	V
V$_{OL(CKOUT)}$	Logic Output "Low" Voltage I$_{OL}$ = 160µA	V$_{SS}$		V$_{SS}$ + 0.4	
V$_{OH}$	Logic Output "High" Voltage I$_{OH}$ = 4µA	V$_{DD}$ − 1.0			V
R$_{INA (IN-, IN+)}$	Analog Input Resistance	10			MΩ
C$_{INA (INA-, IN+)}$	Analog Input Capacitance			15	pF
V$_{REF}$	Reference Voltage Out	0.49 (V$_{DD}$ − V$_{SS}$)	0.50 (V$_{DD}$ − V$_{SS}$)	0.51 (V$_{DD}$ − V$_{SS}$)	V
V$_{OR}$ = |BV$_{REF}$-V$_{REF}$|	Offset Reference Voltage			50	mV
P$_D$	Power Dissipation V$_{DD}$ = 12.5V		400		mW
	V$_{DD}$ = 13.5V and 0°C			650	mW

Typical Op Amp Characteristics (On Chip)

G$_{BW}$	Unity Gain Bandwidth	1.2	1.8		MHz
f$_{3dB}$	3dB Point (wrt A$_O$)		70		Hz
A$_O$	DC Open Loop Gain	80	86		dB
ϕ	Phase Margin	60	65		deg
CMRR	Common Mode Rejection	60	70		dB
V$_{OS}$	Offset Voltage		10	25	mV
WN	Wideband Noise Over 3MHz		25	50	µV$_{rms}$
P$_D$	Power Dissipation (V$_{DD}$ − V$_{SS}$) = 10V		5	7.5	mW

System Specifications

Symbol	Parameter/Conditions	Min.	Typ.	Max.	Units
THD	**Total Harmonic Distortion** Total Harmonic Distortion (dB). Dual tone of 770Hz and 1336 Hz sinewave applied at the input of the filter at a level of 3dBm each. Distortion measured at the output of each filter over the band of 300 Hz to 10kHz ($V_{DD}=12V$)	40			dB
ICN	**Idle Channel Noise** Idle Channel Noise measured at the output of each filter with C-message weighting with input of the filter terminated to BV_{REF}			1	mV_{rms}
GD_L	**Group Delay** Low Group Filter Delay over the band of 50Hz to 3kHz		4.5	6.0	ms
GD_H	High Group Filter Delay over the band of 50Hz to 3kHz		4.5	6.0	ms

Pin/Function Descriptions

OSC_i, OSC_o	These pins are for connection of a standard 3.579545MHz crystal and 10mΩ resistor to form the oscillator from which all timing is derived. Necessary parasitic capacitances are built on-chip thus eliminating the need for external capacitors.
CKOUT (S3525A)	Oscillator output is buffered and brought out at this pin. This output can be used to drive the oscillator input of a receiver chip that uses the TV crystal as time base. This allows use of only one crystal between the filter and receiver chips.
CKOUT (S3525B)	This is a divide by 4 output from the oscillator and is provided to supply a clock to receiver chips that use 895kHz as time base.
IN−, IN+, Feedback	These three pins provide access to the input operational amplifier on chip. The feedback pin in conjunction with the IN− and IN+ pins allow a programmable gain stage. (See Note.)
FH OUT, FL OUT	These are outputs from the high group and low group filters. These can be used as inputs to analog receiver circuits.
HI IN−, HI IN+ LO IN−, LO IN+	These are inputs of the high group and low group limiters. These are used for squaring of the respective filter outputs.
FHSQ, FLSQ	These are respectively the high group and low group square wave outputs from the limiters. These are connected to the respective inputs of digital receiver circuits.
V_{DD}, V_{SS}	These are the power supply voltage pins. The device can operate over a range of 10V≤ ($V_{DD}-V_{SS}$) ≤13.5V.
V_{REF}	An internal ground reference is derived from the V_{DD} and V_{SS} supply pins and brought out to this pin. Typically V_{REF} is $1/2(V_{DD}-V_{SS})$ above V_{SS}.
BV_{REF}	Buffered V_{REF} is brought out to this pin

Note: Because the overall signal gain is approximately 6dB, in order to maintain performance, the MAXIMUM signal voltage developed at "feedback" (pin 13) should be $3/8 (V_{DD}-V_{SS})$ ≤ V_{IN} ≤ $5/8 (V_{DD}-V_{SS})$.
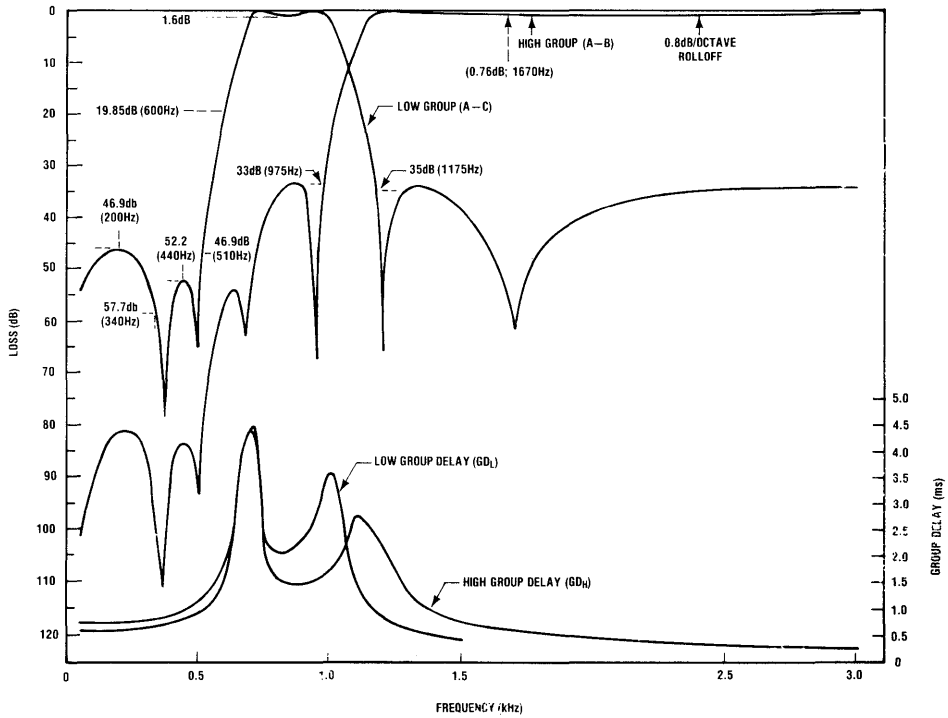
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Figure 1. DTMF Bandsplit Filter Loss/Delay Characteristics

Figure 1. DTMF Bandsplit Filter Loss/Delay Characteristics

REMOTE CONTROL CIRCUITS

Part No.	Description	Process	Power Supplies	I/O Bits	Packages
S2600	Remote Control Transmitter	CMOS	+7V to +10V	11	16 Pin
S2601	Remote Control Receiver	P-I^2	+10V to +18V	5	22 Pin
S2742	Remote Control Decoder	PMOS	+9V		18 Pin
S2743	Remote Control Encoder	PMOS	+9V		16 Pin

TOUCHCONTROL™ INTERFACE CIRCUITS

Part No.	Description	Process	Power Supplies	Input/Output	Packages
S9260/61	Seven-Switch Interface	P-I^2	−13.5V to −18V	CMOS/TTL	22 Pin
S9263/64/65	Sixteen-Switch Interface	PI^2	−13.5V to −18V	CMOS/MOS/TTL	40 Pin
S9262	Fourteen-Switch Interface	PI^2	−13.5V to −18V	MOS/TTL	22 Pin
S9266	Thirty-Two-Switch Interface	P-I^2	−13.5V to −18V	MOS/TTL	40 Pin
TCK-100	Touch Control Evaluation Kit				

CONSUMER CIRCUITS

Part No.	Description	Process	Power Supplies	Digits	Packages
S1856	Digital Clock Circuit — LED/LCD Fluorescent Auto Clock	P-I^2	−6V to −22V	3½	40 Pin
S2709	Fluorescent Automotive Digital Clock	P-I^2	+12V	4	22 Pin

Part No.	Description	Process	Power Supplies	Outputs	Packages
S2809	Universal Display Driver	P-I^2	+8V to +22V	32	40 Pin

ORGAN CIRCUITS

Part No.	Description	Process	Power Supplies	Power Dissipation	Packages
S10110	Analog Shift Register	P-I^2	−24V		8 Pin
S10111	Analog Shift Register	P-I^2	−24V		8 Pin
S10129	Six-Stage Frequency Divider	P-I^2	−14V to −27V	350mW	14 Pin
S10130	Six-Stage Frequency Divider	P-I^2	−14V to −27V	350mW	14 Pin
S10131	Six-Stage Frequency Divider	P-I^2	−14V to −27V	350mW	14 Pin
S10377	Analog Shift Register	P-I^2 MOS	−14V to −27V	350mW	8 Pin
S10430	Divider-Keyer	P-I^2 MOS	−14V to −27V	350mW	40 Pin
S2567	Rhythm Counter	HI V$_T$	−15V to −27V	400mW	14 Pin
S2688	Noise Generator	P-I^2	−14V to −27V	350mW	8 Pin
S8890	Rhythm Generator	P-I^2	−12V	400mW	40 Pin
S9660	Rhythm Generator	P-I^2	−12V	400mW	28 Pin
S50240	Top Octave Synthesizer	P-I^2	−11V to −16V	360mW	16 Pin
S50241	Top Octave Synthesizer	P-I^2	−11V to −16V	360mW	16 Pin
S50242	Top Octave Synthesizer	P-I^2	−11V to −16V	360mW	16 Pin
S50243	Top Octave Synthesizer	P-I^2	−11V to −16V	360mW	16 Pin
S50244	Top Octave Synthesizer	P-I^2	−11V to −16V	360mW	16 Pin
S50245	Top Octave Synthesizer	P-I^2	−11V to −16V	360mW	16 Pin

ENCODER/DECODER
REMOTE-CONTROL 2-CHIP SET

CONSUMER

Features

☐ Small Parts Count — No Crystals Required

☐ Easily Used in LED, Ultrasonic, RF, or Hard-wire Transmission Schemes

☐ Very Low Reception Error

☐ Low Power Drain CMOS Transmitter for Portable and Battery Operation

☐ 31 Commands — 5-bit Output Bus with Data Valid

☐ 3 Analog (LP Filterable PWM) Outputs

☐ Muting (Analog Output Kill/Restore)

☐ Indexing Output — 2½ Hz Pulse Train

☐ Toggle Output (On/Off)

☐ Mask-Programmable Codes

Block Diagram
S2600 Encoder

Pin Configuration
S2600

S2601 Decoder

Pin Configuration
S2601
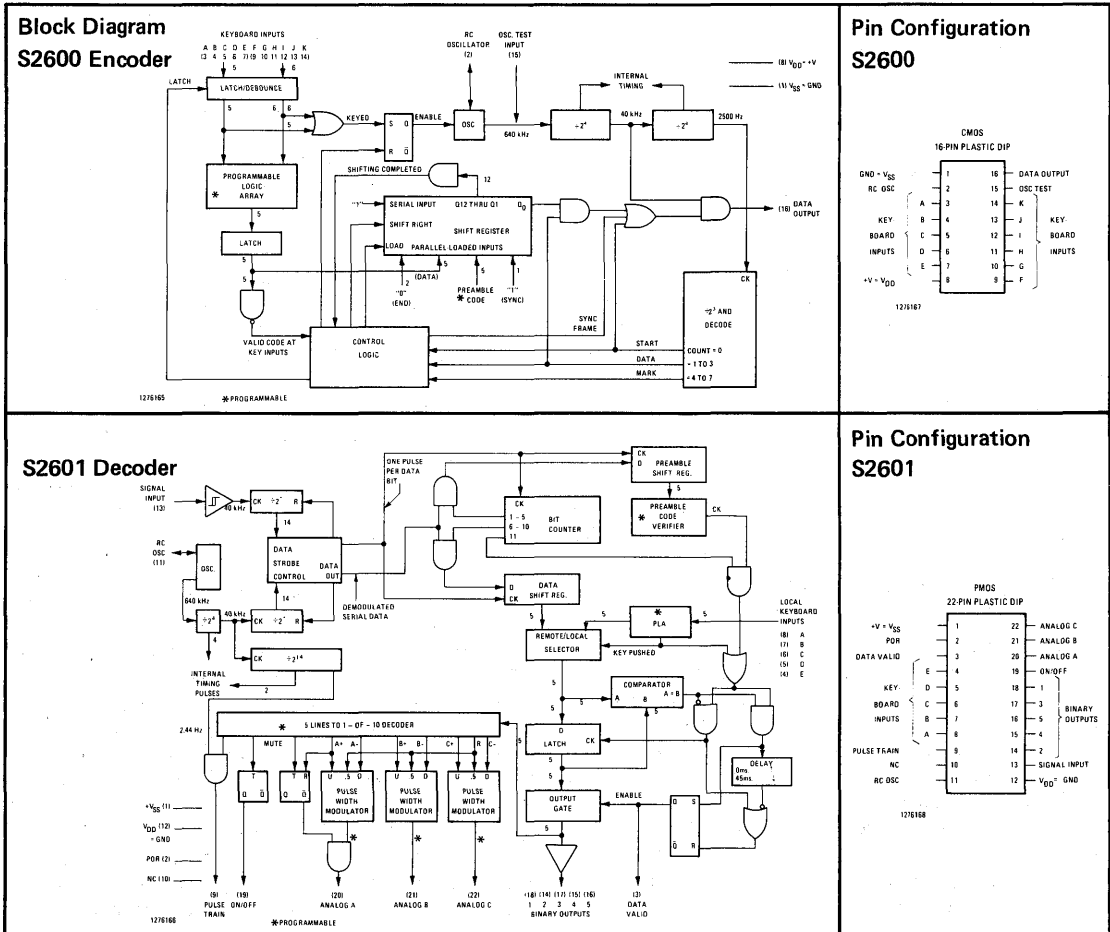
Functional Description

The S2600/S2601 is a set of two LSI circuits which allows a complete system to be implemented for remote control of televisions, toys, security systems, industrial controls, etc. The choice of transmission medium is up to the user and can be ultrasonic, infrared radio frequency, or hardwire such as twisted pair or telephone.

The use of a synchronizing marker technique has eliminated the need for highly accurate frequencies generated by crystals. The S2600 Encoder typically generates a 40kHz carrier which it amplitude-modulates with a base-band message of 12 bits, each bit preceded by a synchronizing marker pulse.

Bits 1 and 12 denote sync and end-of-message, respectively, bits 2 thru 6 constitute a fixed preamble which must be received correctly for the command bits to be received, and bits 7 thru 11 contain the command data. The S2601 Decoder produces an output only after two complete, consecutive, identical, 12-bit transmissions. Marker pulses, preamble bits, and redundant transmissions, have given the S2600/S2601 system a very high immunity to noise, without a large number of discrete components.

S2600 Encoder

The S2600 is a CMOS device with an on-chip oscillator, 11 keyboard inputs, a keyboard encoder, a shift register, and some control logic. The oscillator requires only an external resistor and capacitor, and to conserve power, runs only during transmission. Keyboard inputs are active-low, and have internal pull-up resistors to V_{DD}. When one keyboard input from the group A thru E is activated with one from the group F thru K, the keyboard encoder generates a 5-bit code, as given in the table entitled ((S2600/S2601 CODING," below. This code is loaded into a shift register in parallel with the sync, preamble, and end bits, to form the 12-bit message.

The transmitter output is a 40 kHz square wave of 50% duty factor which has been pulse-code-modulated by (i.e., ANDed with) a signal having a recurring pattern, a bit frame of 3.2 millisecond duration. This bit frame is comprised of three signals: the Start signal which is 0.4 milliseconds of logic "1"; followed by the Data signal which is 1.2 milliseconds of the lowest-order shift register bit; followed by the Mark signal which is 1.6 milliseconds of logic "0" (except in the first bit frame where Mark = 1 to facilitate receiver synchronization).

The shift register is clocked once per bit frame, so that its 12-bit message is transmitted once in 38.4 milliseconds. The minimum number of tranmissions that can occur is two, but if the keyboard inputs are active after the first 3.6 milliseconds of any 12-bit transmission, one more 12-bit transmission will result. Transmissions are always complete, never truncated, regardless of the keyboard inputs.

The Test Input is used for functional testing of the device. A low level input will cause the oscillator frequency to be gated to the Data Output pin. This input has an internal pull-up resistor to V_{DD}.

S2601 Decoder

The S2601 is a PMOS LSI device with an on-chip oscillator, five keyboard inputs, a 40 kHz signal input, and 11 outputs. The oscillator requires only an external R and C. The five keyboard inputs are active-low with internal pull-up resistors to V_{SS}; activation of any two causes one of 10 possible 5-bit codes to be generated and fed to the outputs of the S2601, overriding any 40 kHz signal input.

Two counters, the signal counter and the local counter, are clocked respectively by the signal input and a 40 kHz signal from the local RC oscillator timing chain. A 40 kHz input lasting 3.2 milliseconds (i.e., an initial bit frame) causes the signal counter to overrun and reset both itself and the local counter. At specific intervals thereafter, the local counter generates pulses used to interrogate the contents of the signal counter. Resynchronization of the counters occurs every bit frame so that the interrogation yields valid data bits even if the transmitter oscillator frequency has deviated up to ± 24% with respect to the receiver oscillator frequency.

Decoded data bits from the next five bit frames following the initial synchronizing frame are compared with the fixed preamble code. The next five decoded bits, the command bits, are converted to a parallel format and are compared against the command bits saved from the prior transmission. If they match, and if the preamble bits are correct, the command bits are gated to the receiver outputs. However, a mismatch causes the receiver outputs to be immediately disabled, and the new command bits are saved for comparison against the command bits from the next 12-bit transmission. In the case where 2 identical, proper, 12-bit transmissions are immediately followed either by transmissions with erroneous preamble codes or by

CONSUMER

nothing, the receiver outputs will be activated during the end-frame of the second transmission, and will be disabled 45 milliseconds thereafter. In the rest (disabled) state the five Binary Outputs are at a "1" logic level; when not in the rest state, one or more of the open-sourced output transistors will conduct to V_{DD}. The Data Valid output is low during the rest state, and high whenever data is present at the Binary Outputs.

The S2601 has five other outputs: Pulse Train, On/Off, Analog A, Analog B, and Analog C. The states of these outputs are controlled by the 10 particular Binary Output codes which the receiver Keyboard Inputs can cause to be generated. The Pulse Train output provides a 2.44 Hz square wave (50% duty factor) whenever 11011 appears at the Binary Outputs, but otherwise it remains at a logic "0". This pulse train can be used for indexing, e.g., for stepping a TV channel selector.

The On/Off ("mains") output changes state each time 01111 appears at the Binary Outputs. In TV applications the On/Off output is most often used to kill and restore the main power supply.

Analog Outputs A, B, and C are 10 kHz pulse trains whose duty factors are independently controllable. With a simple low-pass filter each of these outputs can provide 64 distinct DC levels suitable for control of volume, color saturation, brightness, motor speed, etc. Each Analog Output increases its duty factor in response to a particular Binary Output code and decreases its duty factor in response to another code — 6 codes in all. The entire range of 0% to 100% duty factor can be traversed in 26 seconds or at a rate of the oscillator frequency divided by 262,144. All three Analog Outputs are set to 50% duty factor whenever 01011 appears at the Binary Outputs. Analog A is mutable; 01100 sets it to 0% duty factor. If 01100 then disappears and reappears, the original duty factor is restored. This of course implements the TV "sound killer" feature.

The S2601 has an on-chip power-on reset (POR) circuit which sets the Pulse Train and On/Off Outputs to "0," sets the Analog Outputs at 50% duty factor, and insures that Analog A is muted. No external components are required to implement POR, but a POR input has been provided for applications where externally controlled reset is desirable, e.g., where the power supply voltage rise time is extremely slow. The POR input has an internal resistor pull-up to V_{SS}; pulling it low causes a reset.

Message Bit Format
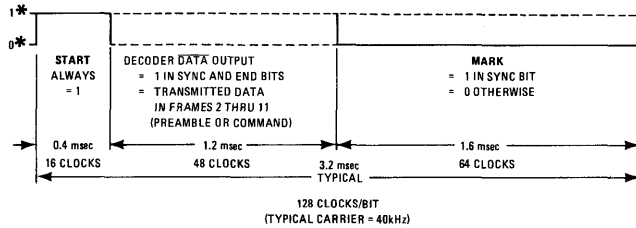
Message Format
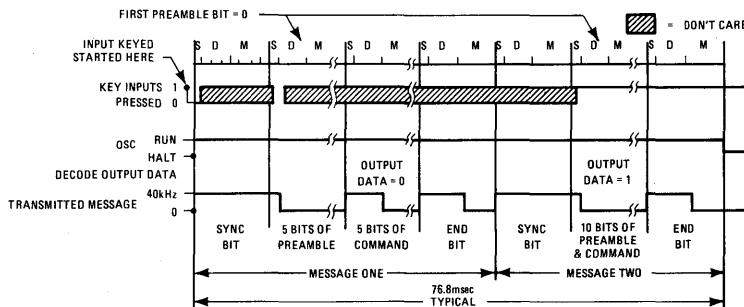
S2600/S2601 Coding

Transmitter Keyboard Input Pins Tied to Vss	Receiver Keyboard Input Pins Tied to Vdd (See Note 1)	Resulting Receiver Binary Outputs 1	2	3	4	5	Receiver Dedicated Functions (Mask programmable except for rest state)
AB	–	0	0	0	0	0	
AF	–	0	0	0	0	1	
AG	–	0	0	0	1	0	
AH	–	0	0	0	1	1	
AI	BC	0	0	1	0	0	Increase Analog C pulse width
AJ	–	0	0	1	0	1	
AK	–	0	0	1	1	0	
BF	AE	0	0	1	1	1	Decrease Analog B pulse width
BG	–	0	1	0	0	0	
BH	–	0	1	0	0	1	
BI	–	0	1	0	1	0	
BJ	DE	0	1	0	1	1	RESET Analog (See Note 2)
BK	CE	0	1	1	0	0	MUTE (See Note 3)
CF	–	0	1	1	0	1	
CG	–	0	1	1	1	0	
CH	CD	0	1	1	1	1	Toggle On/Off Output
CI	–	1	0	0	0	0	
CJ	–	1	0	0	0	1	
CK	–	1	0	0	1	0	
DF	AD	1	0	0	1	1	Increase Analog B pulse width
DG	BD	1	0	1	0	0	Decrease Analog C pulse width
DH	–	1	0	1	0	1	
DI	–	1	0	1	1	0	
DJ	AB	1	0	1	1	1	Increase Analog A pulse width
DK	–	1	1	0	0	0	
EF	–	1	1	0	0	1	
EG	–	1	1	0	1	0	
EH	BE	1	1	0	1	1	Activate Pulse Train Output
EI	–	1	1	1	0	0	
EJ	–	1	1	1	0	1	
EK	AC	1	1	1	1	0	Decrease Analog A pulse width
–	–	1	1	1	1	1	Rest State

NOTES: 1. Receiver keyboard inputs override any remote signal input.
2. Sets Analog A, B, and C waveforms to 50% Duty Factor.
3. First operation sets Analog A to 0% Duty Factor; second operation restores former Analog A Duty Factor.

Electrical Specifications — 2600 Encoder

All voltages measured with respect to V_{SS}.

Absolute Maximum Ratings

Operating ambient temperature T_A .... 0 to +70°C
Storage temperature .... –65°C to +150°C
Positive voltage on any pin .... +14V
Negative voltage on any pin .... –0.3V

Electrical Characteristics

Unless otherwise noted, V_{DD} = 8.5 ± 1.5V and T_A = 0 to +70°C.

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
f0	Oscillator frequency	7	640	2000	kHz	R_{OSC} = 12K, C_{OSC} = 100pF
$\Delta f0/f0$	Frequency deviation	–10		+10	%	Fixed R_{OSC}, C_{OSC}, V_{DD} ± 10%
I_{DD}	Supply current			2	mA	During transmission, Data Output = 1mA
	Standby			10	μA	No transmission (25°C)
V_{IH}	Input "1" threshold	25	50		%V_{DD}	
V_{IL}	Input "0" threshold		50	75	%V_{DD}	
I_{IL}	Input source currrent	50		200	μA	V_I = 0V
I_{OH}	Output source current	1	1.5		mA	$V_0 = V_{DD} – 3V$
I_{OL}	Output sink current	–.2	–.5		mA	V_0 = +0.5V

Note: Circuit operates with V_{DD} from 3.0V to 12.0V.

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Electrical Specifications — S2601 Decoder

All voltages measured with respect to V_{DD}.

Absolute Maximum Ratings

Operating ambient temperature T_A .... $0°C$ to $70°C$
Storage temperature .... $-65°C$ to $+150°C$
V_{SS} power supply voltage .... $+31V$
Positive voltage on any pin .... $V_{SS} +0.3V$
Negative voltage on any pin .... $V_{SS} - 22V$

Electrical Characteristics

Unless otherwise noted, $V_{SS} = 14 \pm 4V$ and $T_A = 0$ to $+70°C$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
f0	Oscillator frequency	7	640	2000	kHz	$R_{OSC}=71K$, $C_{OSC}=25pF$
$\triangle f0/f0$	Frequency deviation	-10		+10	%	Fixed R_{OSC}, C_{OSC}, V_{SS}
I_{SS}	Supply current		34	50	mA	No loads, $V_{DD} = 18V$
			28			$V_{DD} = 10V$
Signal Input:						
V_{IH}	"1" threshold		70	85	$\%V_{SS}$	
V_{IL}	"0" threshold	30	48		$\%V_{SS}$	
$V_{IH}-V_{IL}$	Voltage hysteresis	5		35	$\%V_{SS}$	
Keyboard and POR Inputs:						
V_{IH}	"1" voltage	V_{SS} - .5	V_{SS} - 5.5		V	
V_{IL}	"0" voltage			V_{SS} - 5.5	V	
I_{IL}	Source current	50	150	300	μA	$V_I = V_{SS} - 10V$
	Debounce delay (Keyboard inputs only)	1.45		2.2	msec	
Binary Outputs (open source):						
I_{OL}	Sink current	-1.28			mA	$V_0 = V_{SS} - 5.2V$, $V_{SS}=18V$
		-0.50	-0.60		mA	$V_0 = V_{SS} - 5.2V$, $V_{SS}=10V$
	Duration	34.9			msec	$f0 = Max = 704\,kHz$
Analog Outputs (open drain):						
$\triangle V_{step}$	Step Voltage change		$V_{SS}/64$		V	
I_{OH}	Source current		1.04		mA	$V_0 = V_{SS} - 0.5V$, $V_{SS}=10V$
			1.15		mA	$V_0 = V_{SS} - 0.5V$, $V_{SS}=18V$
		1.0	1.2		mA	$V_0 = V_{SS} - 1V$
f_{step}	Analog step rate		10		kHz	$(f0 \div 64)$
Data Valid, Pulse Train, and On/Off Outputs:						
I_{OH}	Source current	1	1.5		mA	$V_0 = V_{SS} - 2V$
I_{OL}	Sink current	-40	-50		μA	$V_0 = .7V$
t_r	Risetime (.1V_{SS} to .9 V_{SS})			10	μsec	$R_L = \infty$, C_L 50pF
t_f	Falltime (.9V_{SS} to .1 V_{SS})			10	μsec	$R_L = \infty$, C_L 50 pF

Note: Circuit operates with V_{SS} from 7.0V to 30.0V

Circuit Application

+V = 10 TO 18 VDC

12K

9V

C$_1$

100 pF

50pF

C$_2$

R$_1$

33K

C$_p$ 2
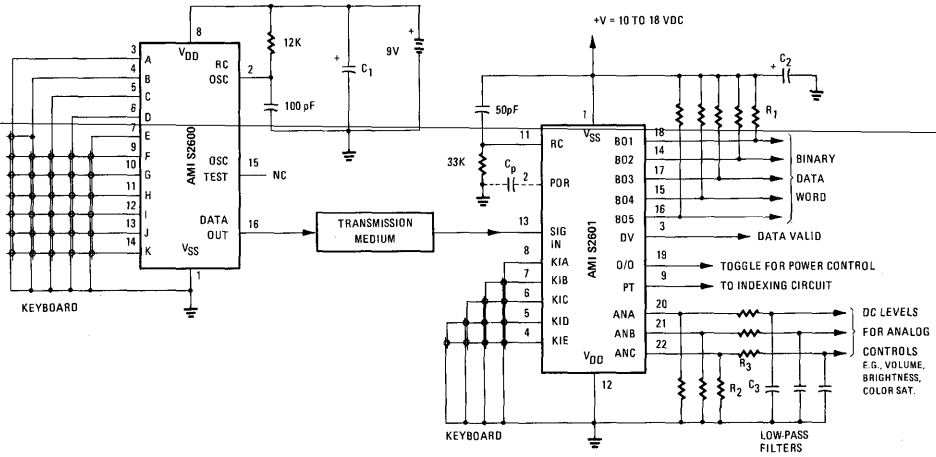
RIPPLE ON FILTER OUTPUT < 10mV p-p USING R$_2$ = 10K, R$_3$ = 100K, C$_3$ = 0.47 μF, V$_{SS}$ = 14VDC
C1, C2, AND Cp OPTIONAL

1276172

KEYBOARD

KEYBOARD

TRANSMISSION MEDIUM

BINARY
DATA
WORD

DATA VALID

TOGGLE FOR POWER CONTROL
TO INDEXING CIRCUIT

DC LEVELS
FOR ANALOG
CONTROLS
E.G., VOLUME,
BRIGHTNESS,
COLOR SAT.

LOW-PASS
FILTERS

ENCODER/DECODER
REMOTE-CONTROL 2-CHIP SET

Features

☐ **RC Oscillator Used — No Crystal Required**

☐ **Phase Locked Loop on Decoder for Reliable Operation**

☐ **512 User Selectable Address Codes**

☐ **Encoder Operates on a Single Rail 9 Volt Supply — Suitable for Inexpensive and Convenient Battery Operation**

☐ **User Can Determine the Type of Transmission Medium to Use**

Applications

☐ **Entry Access Systems**

☐ **Remote Engine Starting for Vehicles and Standby Generators**

☐ **Security Systems**

☐ **Traffic Control**

☐ **Paging Systems**

☐ **Remote Control of Domestic Appliances**

Block Diagram 2743 Encoder
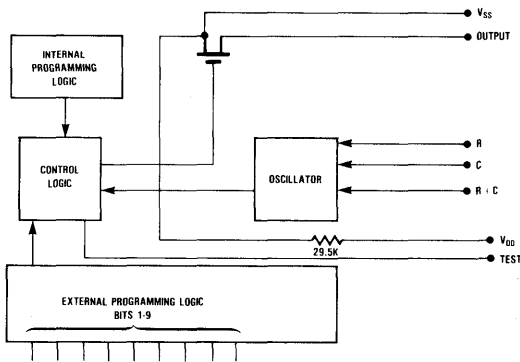
Pin Configuration 2743
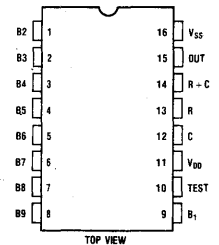
Block Diagram of 2742 Decoder
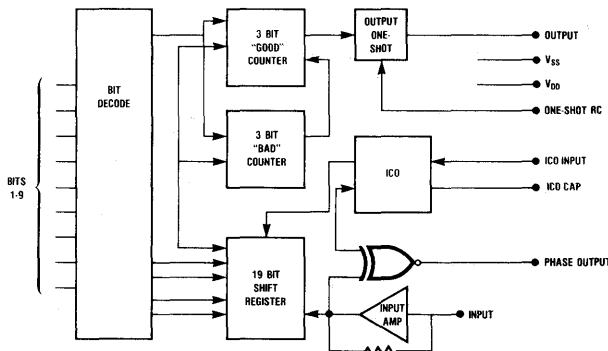
Pin Configuration 2742
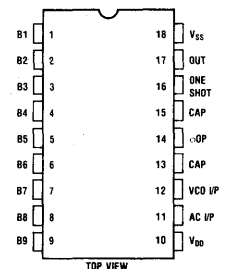
General Description — Encoder/Decoder

This two-chip PMOS set includes a user-programmable serial data encoder for use in a simple low-power transmitter and a serial data decoder for use in a user addressable receiver. The user can select the transmission medium (RF, infrared ultrasonic, or hardwire). The externally selectable message allows up to 512 codes or addresses; this is done with the nine binary inputs on each device. An additional 3 bits of address can be programmed on chip as a fixed preamble.

The serial data encoder encodes by means of a frequency-shift-keyed trinary data pattern composed of 16 data bits. Each data bit will have a length equivalent to 32 cycles of high frequency clock (20kHz typical). Each trinary data pattern will be 512 cycles of 1/2 the oscillator frequency length. The encoder frequency oscillator reference is controlled with an external RC network. The encoder transmitter can be powered by a single 9 volt battery so that a single momentary push button will activate the encoder and transmitter. In the off position there is no current flow.

The serial data decoder in conjunction with a receiver amplifier decodes the transmitted 16-bit coded signal. The on-chip phase-locked-loop locks in on the 20kHz signal even if the transmitted frequency differs from the receiver by up to $\pm 15\%$. The coded signal input is compared with the externally selected code. The serial decoder looks at the transmitted signal a minimum of three times before validating a good message. A 3-bit "good" code counter or a 3-bit "bad" code counter accumulates the number of successive good and bad codes being received.

The decoder has an on-chip one-shot which is user programmed by an external RC combination. Whenever three complete good codes are received in the "good" counter a signal enables the one-shot which controls the signal valid output. If a series of three sequencial bad codes enter the "bad" code counter the "bad" counter resets the "good" code counter and one-shot period and will not allow an active output until the end of the one-shot period. Any "good" code resets the "bad" code counter. If the "good" counter has accumulated three good codes and activated the output one-shot, any occasional "good" code (occurring within the one-shot period) will maintain the output by retriggering the one-shot. The output appears like a single switch, on when "good" codes are received, off when not, with the minimum total period being determined by twice the one-shot

period. The one-shot can be used to prevent the output from switching on and off too rapidly due to system noise. The typical RC components shown in the block diagram give a period of about one second.

Functional Description — Serial Data Encoder

The AMI serial data encoder is comprised of three sections: Oscillator, Programming Logic, and Control Logic. Specifically it will provide logical ones "1", logical zeroes "0", and synchronization pulses "S" and arrange them into a trinary data pattern composed of 16 data bits. Each data bit will be 32 cycles of the high frequency (HF-1/2 Oscillator Frequency) in length. Each trinary data pattern will be 512 cycles of 1/2 the Oscillator Frequency length.

A logical "1" is represented by 32 cycles of the high frequency.

A logical "0" is represented by 16 cycles of the high frequency followed directly by 8 cycles of the low frequency (LF = 1/2 HF).

A synchronization pulse "S" is represented by 16 cycles of the low frequency.

A 16-bit data pattern will be encoded in the device in such a manner as to have three (3) bits programmed internally and nine (9) bits programmed externally.

The Oscillator Frequency equals twice that of the High Frequency, and the High Frequency equals twice that of the Low Frequency.

The Oscillator circuit will require a maximum of three (3) external components (refer to Figure 2).

External programming inputs connected to the device $- V_{DD}$ supply will be considered as a logical "1." The bit programming current will not exceed $50\mu A$. The programming resistance should not exceed $1k\Omega$. Unconnected external bit programming inputs will be considered at a logical "0."

A "1" ($- 5V \le$ "1" $\le V_{DD}$) presented to the "Test" input sets the Internal counter and maintains the output of the device "On." The input impedance of the test input is greater than $5M\Omega$.

For portable operation a 9V transistor battery can be used for the DC voltage supply. Proper circuit polarity must be observed ($- V_{DD}, + V_{SS}$).

S2743 Absolute Maximum Ratings

DC Supply Voltage . . . . – 15V

Input Voltage . . . . V_{SS} + .3V to V_{SS} – 15V

Operating Temperature Range . . . . – 40°C to + 100°C

Storage Temperature Range . . . . – 65°C to + 150°C

Lead Temperature (During Soldering) . . . . 300°C for Max. 10 sec.

S2743 Electrical Characteristics (25°C Air Temperature Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
	Operating Supply Voltage	– 6.65	– 9.5	– 15	V	V_{DD}
	Operating Power Dissipation		27	40	MW	– 8V, – 5mA
	Operating Frequency	2	40	60	kHz	Oscillator
	Programming Bits 1-9, Current			50	μA	Programming Input, R $\le$ 1kΩ
	External Programming Resistance			1	kΩ	Bits 1-9
	(DC Bits 1-9) Program Logical "1"	– 5	– 6.05	V_{DD}	V	
	Input Levels Logical "0"		– 0.4		V	
	Bits 1-9 Current		55		μA	Input R 9V > 1.5M @ 5V
	Test and R + C Input Impedance	5		75	MΩ	Input Resistance 5MΩ
	(DC) Test Input Levels Test ON	– 5		V_{DD}	V	Maintains Output Device ON
	Test OFF (See Note 1)	V_{SS}		– 1	V	Permits Normal Operation
	R, C Resistance Logical "1"		12		kΩ	Resistance to V_{DD}, $\pm$ 20%
	Logical "0" (See Fig.)		3		kΩ	Resistance to V_{SS}, + 20% – 30%
	Output Current (See Note 2)	– 7V	5		mA	Output Voltage = .8V W/V_{DD}

Notes: 1. Effect noted at Pin 15 to V_{SS} 2. Output Voltage Pin 15 to V_{SS} All Voltages measured with respect to V_{SS}

Figure 1. Serial Data Encoder
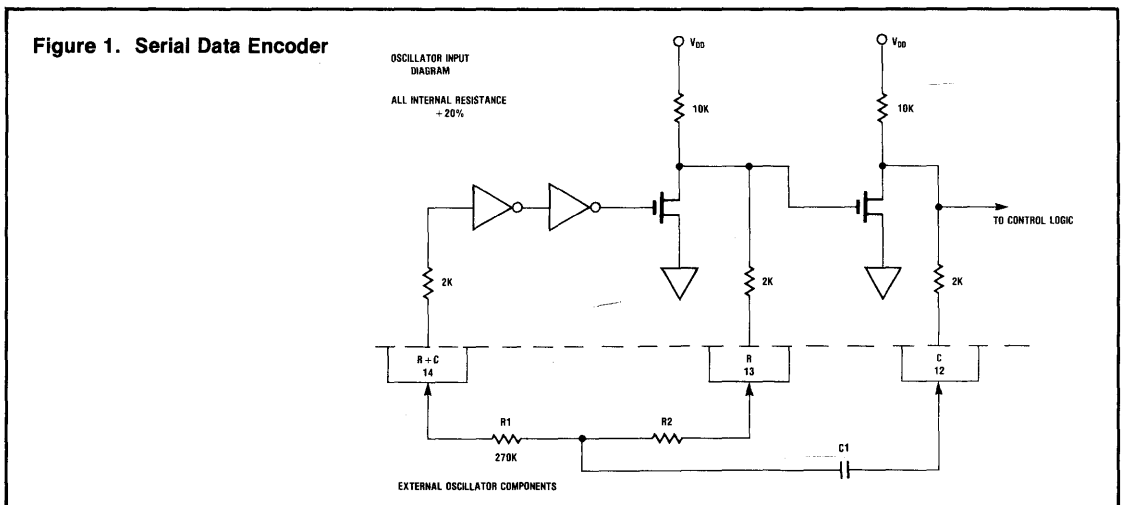
External Oscillator Components

The Astable Multivibrator Circuit employed here required three (3) external components.

R_1 aids in keeping the operating frequency independent of variators in supply voltage. R_2 and C_1 form the RC time constant which controls the oscillator frequency. In this case, R_1 will be specified at 270kΩ regardless of the oscillator operating frequency. Typically it will be found that $R_1 \geq 2T_2$. R_2 should not be greater than 80kΩ or less than 20kΩ; C_1 should not be less than 100pF. A method for determining the approximate value of R_2 and C_1 is:

Start with the approximate formula for oscillator frequency

$$\text{osc. freq} \approx \frac{1}{2RC}$$

It must be noted that the oscillator frequency must be set at twice the desired device high frequency value.

Using a set value of R or C and a known, desired oscillator frequency:

To solve for C; w/osc. freq. = 30kHz; R = 60kΩ

$$C \frac{1}{2Rf} \approx \frac{1}{2(60 \times 10^3)(30 \times 10^3)} \approx 2.77 \times 10^{-10} \quad 277pF$$

In this case, solve for R_2; 2/osc. freq. = 30kHz; C_1 = 500pF

$$R \frac{1}{2cf} \approx \frac{1}{2(500 \times 10^{-12})(30 \times 10^3)} \approx 3.33 \times 10^4 \quad R_2 = 33k\Omega$$

General Description — Serial Data Decoder

The AMI serial data decoder is comprised of four sections: Phase Locked Loop (PLL). 16-Bit Digital Decoder, Good/Bad Code Logic and the Retriggerable Output One-Shot.

The decoder is always on and the phase locked loop is running. A small external capacitor determines the center frequency while an external low pass filter smooths out and generates the ICO control current. The typical center frequency of the PLL is 20kHz allowing the received signal to slightly off frequency and the PLL will still "lock in."

S2742 Absolute Maximum Ratings

The 16-bit trinary data pattern includes:
- 3 "1" bits (fixed) 32 cycles of 20kHz each
- 1 Sync bit 16 cycles at 10kHz
- 3 Mask programmable bits either "1" or "0"
- 9 User-selectable bits externally programmed.

The PLL locks on the "1" bits present in the data pattern. Once locked, the PLL generates a clock which controls the digital decoder section (DDS). The DDS waits for a sync bit and then compares the incoming data pattern bits, one by one, to make sure *all* the bits are correct; fixed ones are ones; mask programmable bits match; and finally verifies that the user-selectable 9-bit pattern is correct.

Bit Position   1   2   3   4   5   6   7   8   9   10 11 12 13 14 15 16
Data Pattern   I   I   I   M   M   M   U   U   U   U   U   U   U   U   I   S

    I   = Fixed "1" (32 cycles at 20kHz)
    M = Mask Programmable Bits
    U = User-Selectable Bits
    S = Sync Bit (16 cycles at 10kHz)

    Time for One Pattern $= 16 \times 32 \times \dfrac{1}{20\text{kHz}} \approx 25\text{mS}$

If the pattern was correct, a good count (GC) is stored in a "Good Pattern Counter" (GPC). If the pattern match did not occur, a bad count (BC) is stored in a "Bad Pattern Counter" (BPC). Then:

1. Any GC resets the BPC.
2. Three (3) BCs in a row will reset the GPC.
3. When the GPC reaches four (4) the one-shot is triggered and an output will occur, i.e., three (3) good codes completed.
4. *Any one* GC after an output, occurring within the one-shot time will retrigger the one-shot and maintain the output on.

The retriggerable one-shot stabilizes the systems operation by introducing hysterisis.

1. It takes more good pattern counts to turn the output on than to maintain it on.
2. After the output goes off, it will stay off for the one-shot period regardless of any good patterns being received.

An external RC is used to control the one-shot period.

DC Supply Voltage	− 20V
Input Voltage	
Operating Temperature Range	− 40°C to + 100°C
Storage Temperature Range	− 20°C to + 70°C
Lead Temperature (During Soldering)	300°C for Max. 10 sec.

S2742 Electrical Characteristics (25°C Air Temperature Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
	Operating Supply Voltage	– 15V		– 20	V	V_{DD}
	Operating Power Dissipation			200	MW	
	Operating Frequency	2	20	75	kHz	Oscillator
	Operating Current Static			– 10	μA	No Signal, No Bit
	(DC Bits 1-9) Program Logical "1"			– 20	V	
	Input Levels Logical "0"			0	V	
	ICO Input Voltage		≈ 4V		V	At Pin 12
	Output Voltage		– 1		V	
	Output Current ($V_{OUT} = -1V$)		10		mA	@1V P-P Output Voltage
	Signal Input, AC Coupled	0.025	0.05	1.0	V/pk-pk	
	Input Impedance, AC Coupled Amplifier		20		kΩ	

Figure 2. Typical Bench Test Setup
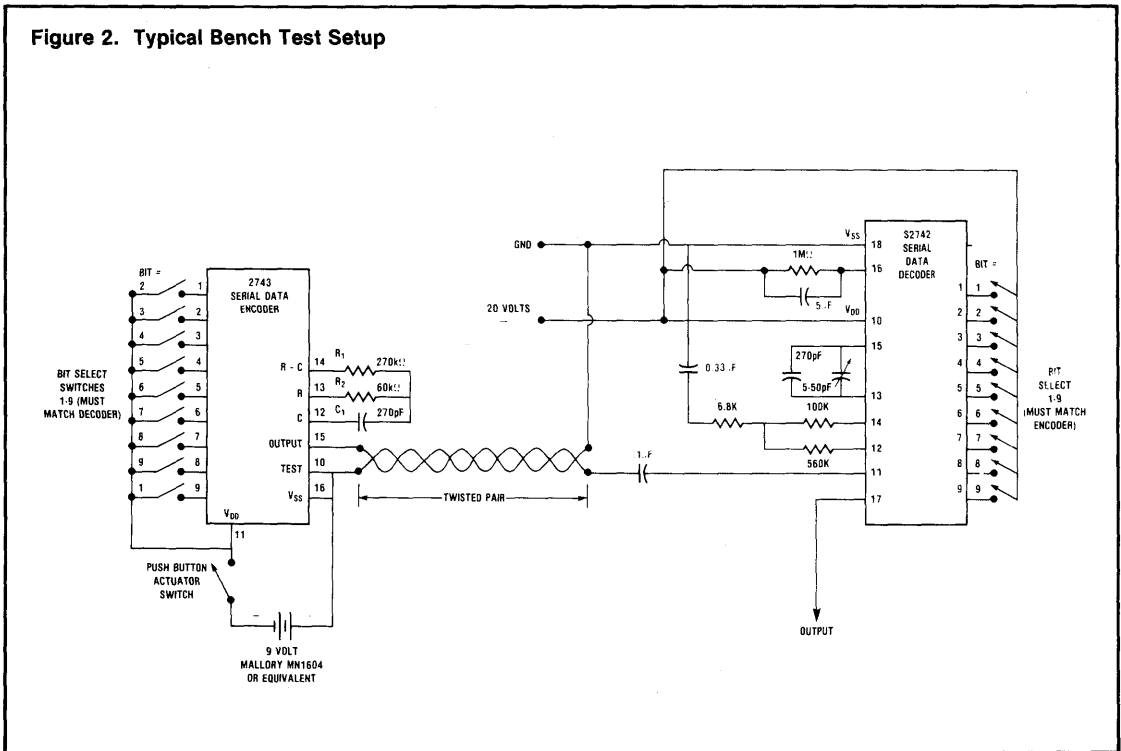
TOUCHCONTROL INTERFACE
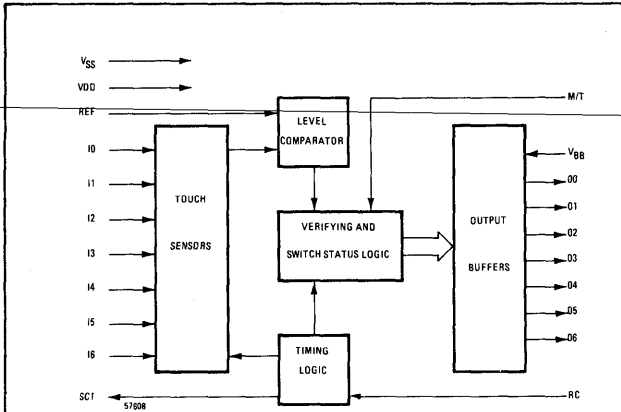
BLOCK DIAGRAM – S9260/S9261 (7 SWITCHES)
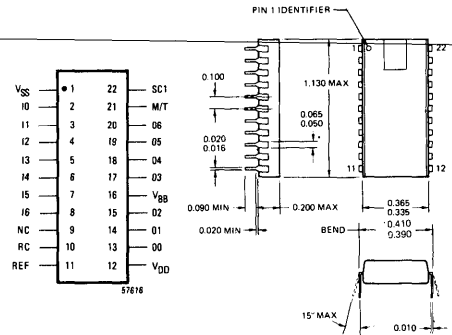
PIN/PACKAGE CONFIGURATION
S9260/S9261
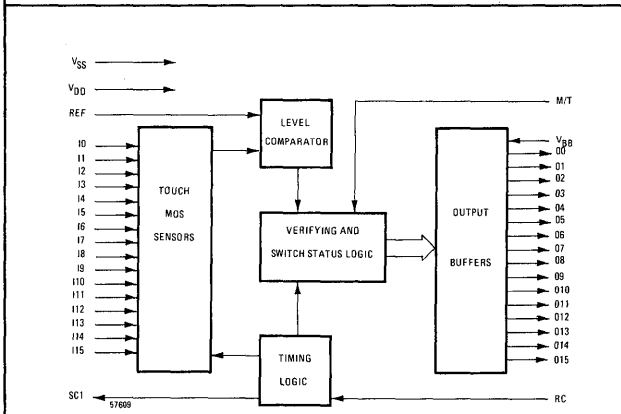
BLOCK DIAGRAM – S9263/S9264/S9265 (16 SWITCHES)
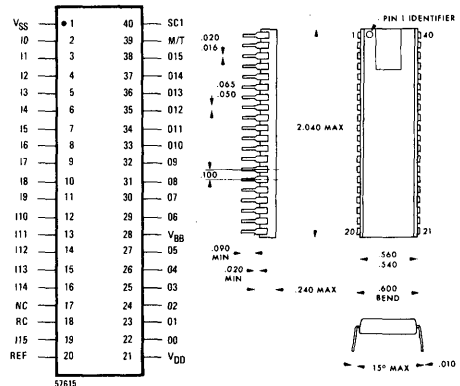
PIN/PACKAGE CONFIGURATION
S9263/S9264/S9265

FEATURES

- Interfaces with up to 16 touch switches
- Eliminates contact noise
- Comparator sensing permits use with wide variety of touch switch configurations

- Momentary or toggle operation electrically selectable
- Outputs are TTL/CMOS/MOS compatible
- Simplifies design of touch-sensitive switches

TOUCH CONTROL

CONSUMER
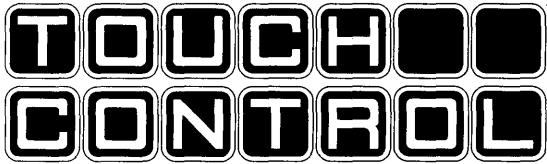
GENERAL DESCRIPTION

The S9260 series of MOS TouchControl interface circuits permits almost any control panel containing mechanical switches to be easily replaced by a flat-surface capacitive control panel providing superior styling, reliability, ease of cleaning, and safety. Connecting directly to a screened or etched pattern on the panel's reverse side, these MOS circuits provide outputs to drive a variety of logic systems from household appliances to industrial controls. All system functions are then selected by merely touching the flat conductive Touch-Control "switch" areas that have been deposited on the panel's front surface in practically any configuration desired.

These circuits provide an individual output for each of up to 16 TouchControl switches. For applications requiring more switches or encoded outputs, refer to AMI's S9262 and S9266, which can interface with up to 32 switches.

FUNCTIONAL DESCRIPTION

Fabricated with P-channel ion implanted MOS/LSI technology, the S9260 family* of TouchControl integrated circuits has been designed to interface with a variety of touch panel switches and provide a high degree of flexibility in the selection of touch panel materials, layout of touch pad configurations, and design of switching functions. These circuits can interface directly with either seven TouchControl switches (22 lead versions) or sixteen TouchControl switches (40 lead versions). For each TouchControl switch input there is a corresponding output that may be used to interface with various logic families such as CMOS or TTL.

Both momentary and "push on – push off" (toggle) switching operations are available on all AMI TouchControl circuits and are electrically selected by the logic levels of one input pin. To ensure reliable switch action, a built-in delay is incorporated in all circuits requiring a minimum touch time for switch response.

TYPICAL APPLICATIONS

- Appliance Control Panels
- Home Entertainment Systems
- Power Tool Controls
- Televisions
- Automotive Controls

- Telephones
- Games
- Fast Food Waterproof Keyboards
- Moisture Proofing
- Industrial Controllers
- Computer Terminals

- Keyboards
- Instrumentation
- 16 to 1 Multiplexers
- Microprocessor Interface
- Vending Machines
- Cash Registers

ABSOLUTE MAXIMUM RATINGS

Voltage on any pin relative to V_{SS}:	+ 0.3V to – 20V	Storage temperature (Ambient) – 65°C to + 150°C
Operating temperature range:	0°C to + 70°C	

*FOR MULTIPLEXED TOUCHCONTROL CIRCUITS SEE AMI S9262 and S9266.

ELECTRICAL CHARACTERISTICS

($0°C < T_A < 70°C$; V_{SS} = 0V; V_{DD} = - 13.5V to - 18.0V unless otherwise specified.)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
V_{IL}	Input logic 0 level — all except "I" inputs.	+ 0.3	0	- 1.5	Volts	Note: M/T input is internally pulled up to V_{SS}
V_{IH}	Input logic 1 level — all except "I" inputs	- 10.0	- 12.0	- 18.0	Volts	
f_{RC}	Internal oscillator frequency measured at RC input.	50		100	kHz	
T_S	Switch delay time	65		135	msec	Frequency measured at RC Input = 50 kHz
T_{RST}	Time to reset all latches using M/T input.		100	135	msec	
V_{OL}	Output low voltage	V_{SS}		- 1.0	Volts	V_{BB} = V_{SS}; 10K resistive load to V_{DD}
V_{OH}	Output high voltage			V_{DD}		
V_{OL}	Output low voltage	V_{SS}		V_{SS} - 0.5	Volts	V_{SS} = +5V; V_{BB} = 0V V_{DD} = 12V; 2800Ω resistive load to V_{SS}
V_{OH}	Output high voltage	V_{BB} + 0.4		V_{BB}		
SC 1	Scan clock output: Output low voltage Output high voltage	V_{SS}		- 1.5 V_{DD}		Max. capacitive loading < 150 pF
I_{DD}	Supply Current		7.0	15.0	ma	Outputs unconnected

OPERATION

Device operation can be understood by referring to Figure 1, depicting a typical application of the S9263. Each of the sixteen pairs of series capacitors labeled S1 — S16 is one touch switch located on a TouchControl panel. (For details on touch panel configuration and operation, see the TouchControl application note included in this APD.) In each capacitor pair, the two common plates represent the conductive area on the control panel surface that is to be touched. The other two plates are formed by two conductive surfaces parallel to the touched surface and located directly under it on the reverse side of the panel. Referring again to Figure 1, the S9263 generates a clock signal on output SC1 that is applied to one plate of each capacitor pair; this signal passes through the two series capacitors and is detected in the MOS circuit. When a panel switch surface is touched, the signal level into the chip dimishes, and the on-chip differential amplifier senses the change and performs the appropriate switching function. For example, if surface S1 is touched, the signal at input 13 decreases, and output 03, normally open, now becomes active and drives the S1 input to the TTL circuitry toward voltage level V_{BB}.

I INPUTS

Inputs from the touch switch pads to the TouchControl circuit are labeled I0 through I15 (S9263, S9264, and S9265) or I0 through I6 (S9260 and S9261). Each I input relates directly to an 0 output of identical numeral.
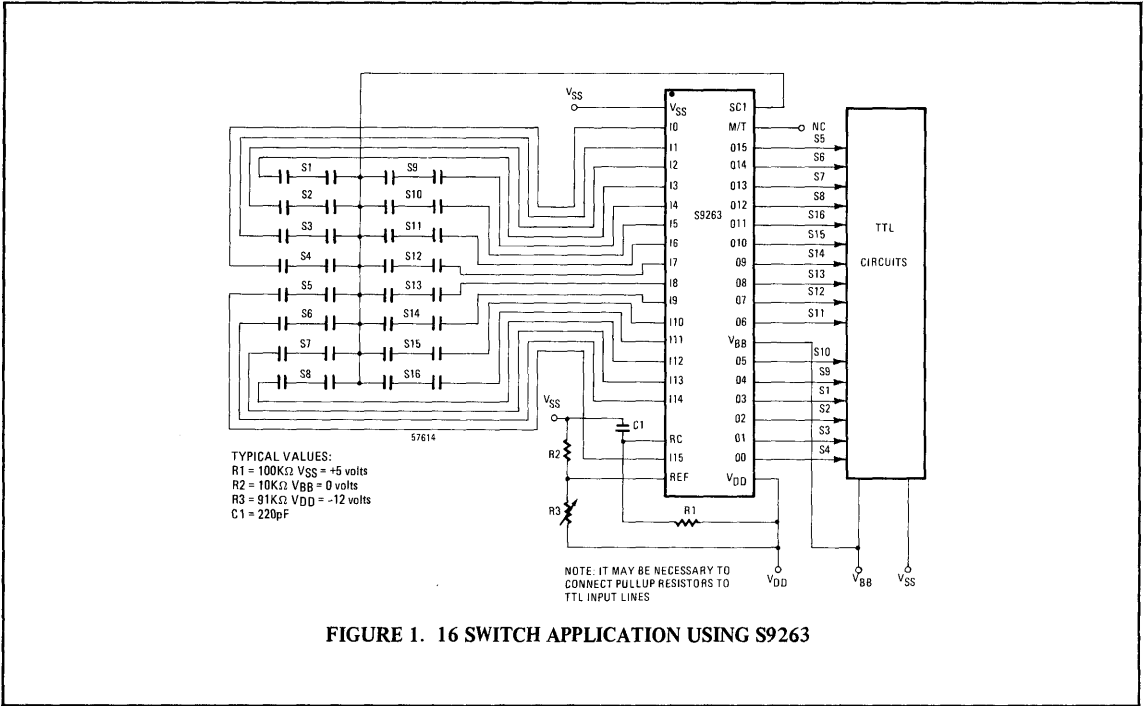
FIGURE 1. 16 SWITCH APPLICATION USING S9263

RC INPUT

A resistor connected to V_{DD} and a capacitor connected to V_{SS} are connected to the RC input pin to establish the on-chip clock frequency that controls the touch switch delay time. Nominal values for these components are suggested in Figure 1, but they may be varied to change clock frequency over a range of 50 kHz to 100 kHz.

REF INPUT

In order to allow flexibility in the choice of Touch-Control panel materials, switch layout, and switch size, AMI Touch Control inputs have been designed to detect a differential change rather than an absolute change in level. To obtain a reference level, two resistors are connected to input REF, one to V_{SS} and the other to V_{DD}.

O OUTPUTS

Each output pin labeled "O" corresponds to an input pin labeled "1." Whenever an input is selected, the output becomes active and will drive an external load toward supply voltage V_{BB}. When outputs are not active, they are high impedance open drain.

V_{BB} SUPPLY

The sources of all output devices are common and connected to pin V_{BB}. This allows TTL compatibility as shown in Figure 1, as well as the ability to drive higher level signals. For instance, if $V_{SS} = 0$ volts, $V_{DD} = -16$ volts, and $V_{BB} = V_{SS}$, then active outputs would drive a load connected to V_{DD} towards V_{SS}. The V_{BB} pin can be used also to switch analog signals; in this configuration the analog signals are applied to the "O" pins and V_{BB} is the output pin.
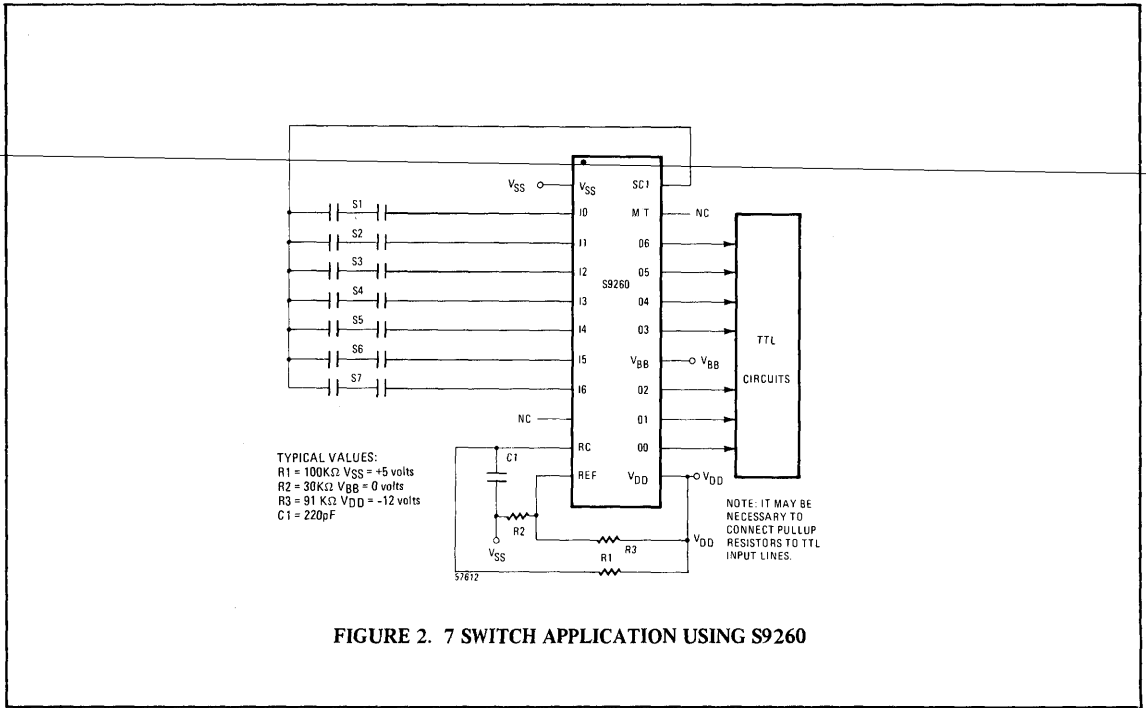
FIGURE 2. 7 SWITCH APPLICATION USING S9260

M/T INPUT

The M/T input pin selects the mode of switch operation, either momentary or toggle. With no connection to the M/T pin momentary operation is selected, and appropriate outputs are active only for the duration of touching a switch. In this mode, no output is active when no switch is touched. A V_{DD} level applied to M/T causes the circuit to operate in the toggle mode. In this condition, the brief touch of any switch will turn on the appropriate output, which will remain latched on until the switch is touched again. Subsequent activations of the switch will toggle the corresponding output on and off alternately. To reset all outputs when the toggle mode is selected, a pulse of V_{SS} level may be applied to the M/T input.

SCI OUTPUT

The SC1 output provides the clock signal for the Touch-Control panel. Its frequency is determined by the RC time con-stant, and it is connected in common with one of each of the two common conductive surfaces on the reverse side of the touch panel.

MOMENTARY AND TOGGLE COMBINATION

The S9261, S9264, and S9265 contain several outputs that are permanently in the momentary mode of operation.

With the M/T input at V_{SS} these parts function identically to the S9260 and S9263. With M/T at a logic 1 level, however, the S9261 has four momentary and three toggle inputs. Table 1 shows the combinations available on all three parts.

CONSUMER

TABLE 1. COMPARISON OF FEATURES

Part Number	Pin Count	Touch Switch Capacity			Number of Outputs
		Total Touch Switch Interface Capability	Touch Inputs Selectable For Either Momentary Or Toggle Operation Through Use of M/T Input	Touch Switch Inputs Fixed In Momentary Operation (Not affected by state of M/T input)	
S9260	22	7	7	0	7
S9261	22	7	3 (I4 thru I6)	4 (I0 thru I3)	7
S9263	40	16	16	0	16
S9264	40	16	8 (I8 thru I15)	8 (I0 thru I7)	16
S9265	40	16	12 (I4 thru I15)	4 (I0 thru I3)	16

TOUCHCONTROL APPLICATION NOTES

PANEL CONSTRUCTION

A TouchControl switch panel consists of a single sheet of a rigid material with conductive surfaces applied on both sides as shown in Figure 3.

A number of materials may be used for touch panels, the selection of the material most suited for a particular application being dependent on such things as durability, appearance, ease of assembly, cost, and dielectric constant of the material.

Regardless of the selected panel material, a touch switch is formed by applying a single conductive surface to its front surface with two other conductive surfaces applied directly in line on the reverse side of the panel. Figure 3 shows three views of a typical touch panel containing two TouchControl switches. On switch one, conductive surface A is applied to the front of

the panel and is the surface to be touched to effect a switch closure. Surfaces B and C are applied directly in line with A on the opposite side of the panel. A should cover completely and may overlap surfaces B and C.

The application of the conductive surfaces depends on selection of the panel materials. If glass is used, for example, it is common to apply a coating of tin oxide, which is then fired on for durability; rear surface conductors may be screened on with a conductive ink. Touch panels may be made more simply from double-sided printed circuit boards in which the conductive TouchControl surfaces are created by standard etching. For breadboarding purposes, a number of conductive tapes and paints are available and may be applied to a variety of touch panel materials.

FIGURE 3. CONSTRUCTION OF A TWO SWITCH TOUCHCONTROL PANEL WITH EQUIVALENT ELECTRICAL CIRCUIT.

ELECTRICAL OPERATION

The three conductive surfaces in a TouchControl switch combine to form two capacitors connected in series, as shown in the schematic diagram of Figure 3. An AC signal generated in the MOS circuit is applied to the rear conductive surface labeled C. This signal is coupled through to surface A by the capacitor formed by C and A. The signal is then coupled to surface B by the capacitor formed by A and B and applied to one of the inputs of the MOS circuit, which detects the signal's presence. When surface A is touched, the amplitude of the signal is significantly decreased because of body capacitance. This is sensed by the MOS circuit, and the appropriate switching function is performed.

TOUCH SWITCH LAYOUT GUIDELINES

AMI TouchControl circuits have been designed to interface with a variety of touch switch configurations. However, there are several guidelines that must be observed to insure a satisfactory TouchControl system.

The size of a TouchControl switch is dependent on the amount of capacitance needed to couple the clock signal to the "I" inputs of the MOS circuits. Because the input capacitance associated with the circuit input is typically five picofarads, it is advisable that each of the two series capacitors formed by the three conductive TouchControl panel surfaces be no less than seven picofarads. Since the capacitance in picofarads can be calculated by $C = 0.22 \in A \div d$, where $\in$ is the dielectric constant, A is area, and d is the material's thickness, it is apparent that minimum switch size is dependent on the thickness and dielectric constant of the panel material. If, for example, the panel is made from 1/8" thick glass with a dielectric constant of 8, then the minimum area of each of the two rear surface conductors is 0.5 sq. inches. Since the touch

surface must cover the entire area of the two rear conductors, it must, then, be at least 1.0 sq. inch. It is desirable to separate the two rear-surface conductors by at least 0.125 inches, so the touch surface would be somewhat larger than 1.0 sq. inch. Higher capacitance, and thus smaller touch switches, can be obtained by using epoxy printed circuit material; though the dielectric constant is lower (around 5.0) the thickness can be decreased substantially.

CIRCUIT TO PANEL CONNECTIONS

There are a number of ways to make the necessary connections between TouchControl circuits and panels. A simple approach is to use a printed circuit board for the touch panel. In this case, the connections to the circuit are made by the etched copper pattern. In laying out a printed circuit, it is important to keep the copper traces running to the individual touch pads separated from each other as much as possible. In most instances a minimum spacing of 0.125" between traces is acceptable, though wider spacing might be necessary in cases where traces will run parallel to each other for distances of over six inches. It is also important to keep the clock output (SC1) at least 0.75 inches away from any input trace. These spacing requirements are guidelines to be followed regardless of the touch panel material.

With glass touch panels, a simple method for breadboarding systems is to fasten individual wires onto the conductive surfaces with a conductive epoxy. For production situations, it is possible to locate the electronic circuitry on a separate printed circuit board. Contact to the glass touch panel can be made through spring contacts mounted in the appropriate locations on the circuit board. An alternate approach is to route the traces on the glass to an edge of the glass, making connection through an edge connector, keeping in mind the spacing requirements between traces.

AMI
AMERICAN MICROSYSTEMS, INC.

MULTIPLEXED TOUCHCONTROL INTERFACE

BLOCK DIAGRAM – S9262 (14 SWITCHES)
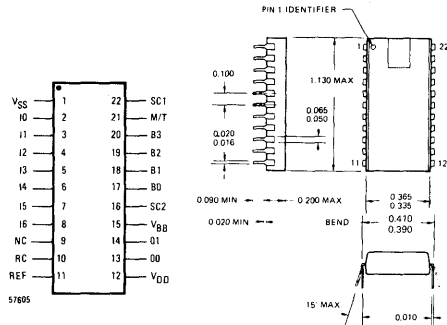
PIN/PACKAGE CONFIGURATION – S9262
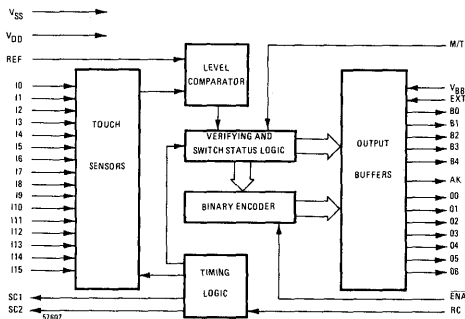
BLOCK DIAGRAM – S9266 (32 SWITCHES)
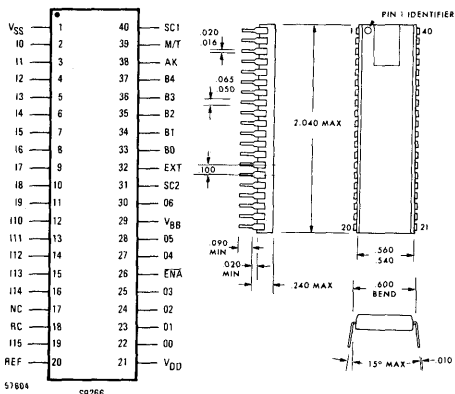
PIN/PACKAGE CONFIGURATION – S9266

FEATURES

- Simplifies design of Touch-sensitive switches
- Interfaces with up to 32 touch switches
- Eliminates contact noise
- Comparator sensing permits use with wide variety of touch switch configurations

- Binary outputs provided
- Outputs are TTL compatible
- Permits design of totally isolated touch surfaces, facilitating UL approval

TOUCH CONTROL

GENERAL DESCRIPTION

The S9262 and S9266 TouchControl interface circuits permit almost any control panel containing mechanical switches to be easily replaced by a flat-surface capacitive control panel providing superior styling, reliability, ease of cleaning, and safety. Connecting directly to a screened or etched pattern on the panel's reverse side, these MOS circuits provide outputs to drive a variety of logic systems from household appliances to industrial controls. All system functions are then selected by merely touching the flat conductive Touch-Control "switch" areas that have been deposited on the panel's front surface in practically any configuration desired.

These circuits can operate up to 32 TouchControl switches, and their outputs are encoded for easy interfacing with microprocessors. For applications requiring an individual output for each TouchControl switch, refer to AMI's S9260, S9261, S9263, S9264 and S9265.

FUNCTIONAL DESCRIPTION

Fabricated with P-channel ion implanted MOS/LSI technology, AMI TouchControl integrated circuits* are designed to interface with a variety of touch panel switches and provide a high degree of flexibility in the selection of touch panel materials, layout of touch pad configurations, and design of switching functions. These parts are designed to address an array of TouchControl switches in either a 2 x 7 matrix (S9262) or a 2 x 16 matrix (S9266) to interface with a total of either 14 or 32 switches. The outputs are binary encoded for easy interfacing with microprocessors or TTL, CMOS or MOS logic.

Both momentary and "push on — push off" (toggle) switching operations are available on AMI TouchControl circuits and are electrically selected by the logic level of the M/T input pin. To ensure reliable switch action, a built in delay is incorporated in all circuits requiring a minimum touch time for switch response.

TYPICAL APPLICATIONS

- Appliance Control Panels
- Home Entertainment Systems
- Power Tool Controls
- Televisions
- Automotive Controls

- Telephones
- Games
- Fast Food Waterproof Keyboards
- Moisture Proofing
- Industrial Controllers
- Computer Terminals

- Keyboards
- Instrumentation
- 16 to 1 Multiplexers
- Microprocessor Interface
- Vending Machines
- Cash Registers

ABSOLUTE MAXIMUM RATINGS

Voltage on any pin except EXT relative to V_{SS}:	+ 0.3V to - 20V	Operating temperature range:	0°C to + 70°C
Voltage on EXT pin relative to V_{SS}:	+ 0.3V to - 27V	Storage temperature (Ambient)	- 65°C to + 150°C

*For non-multiplexed TouchControl circuits see AMI S9260, S9261, S9263, S9264, S9265

CONSUMER

ELECTRICAL CHARACTERISTICS

($0^{\circ}C \leqslant T_A \leqslant 70^{\circ}C$; $V_{SS} = 0V$; $V_{DD} = -13.5V$ to $-18.0V$ unless otherwise specified.)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNITS	CONDITIONS
V_{IL}	Input logic 0 level — all except "I" inputs.	+ 0.3	0	- 1.5	Volts	Note: M/T and $\overline{ENA}$ inputs are internally pulled up to V_{SS}.
V_{IH}	Input logic 1 level — all except "I" inputs.	- 10.0	- 12.0	- 18.0	Volts	
f_{RC}	Internal oscillator frequency measured at RC input.	50		100	kHz	
T_S	Switch delay time	65		135	msec	Frequency measured at
T_{RST}	Time to reset all latches using M/T input.		100	135	msec	RC Input = 50 kHz.
V_{OL}	Output low voltage.	V_{SS}		- 1.0	Volts	$V_{BB} = V_{SS}$; 10K resis-
V_{OH}	Output high voltage			V_{DD}		tive load to V_{DD}.
V_{OL}	Output low voltage.	V_{SS}		$V_{SS} - 0.5$	Volts	$V_{SS} = +5V$; $V_{BB} = 0V$
V_{OH}	Output high voltage	$V_{BB} + 0.4$		V_{BB}		$V_{DD} = -12V$; 2800Ω resistive load to V_{SS}.
SC1, SC2	Scan clock output.					Max. capacitive load-
	Output low voltage	V_{SS}		- 1.5		ing $\leqslant 150$ pF.
	Output high voltage.			V_{DD}		
I_{DD}	Supply Current		7.0	15.0	ma	Outputs unconnected

OPERATION

Device operation can be understood by referring to Figure 1, depicting a typical application of the S9266. Each of the 32 pairs of series capacitors labeled S1 — S32 is one touch switch located on a TouchControl panel constructed of glass, printed circuit board, epoxy, or other dielectric material. (For details on touch panel configuration and operation, see the TouchControl application note included in this APD.) In each capacitor pair, the two common plates represent the conductive area on the control panel surface that is to be touched. The other two plates are formed by two conductive surfaces parallel to the touched surface and located directly under it on the reverse side of the panel. Referring again to Figure 1, the S9266 generates a clock signal on output SC1 and a similar signal on output SC2. The SC1 clock output is connected to the common

conductors of 16 of the 32 touch switches; the SC2 clock connects to the remaining 16 switches. For each touch switch the clock signal passes through the two series capacitors and is detected in the MOS circuit. When a panel switch surface is touched, the signal level into the chip diminishes, and the on-chip differential amplifier senses the change and performs the appropriate switching function.

I INPUTS

Inputs from the touch switch pads to the TouchControl circuit are labeled I0 through I15 (S9266), or I0 through I6 (S9262). The I inputs in conjunction with SC1 and SC2 outputs form a touch switch matrix of 2 x 16 or 2 x 7, respectively. In both these parts the outputs are binary coded and will be described later.
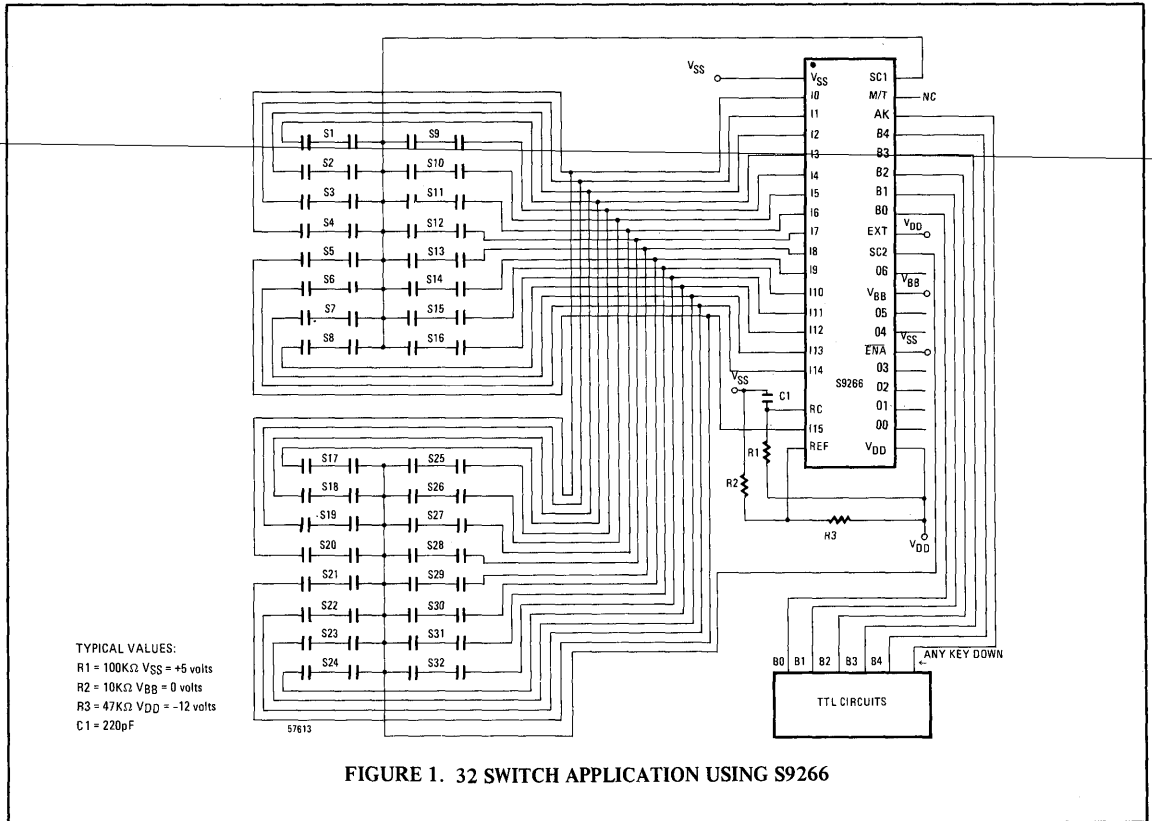
FIGURE 1. 32 SWITCH APPLICATION USING S9266

TYPICAL VALUES:
R1 = 100KΩ V_{SS} = +5 volts
R2 = 10KΩ V_{BB} = 0 volts
R3 = 47KΩ V_{DD} = -12 volts
C1 = 220pF

57613

RC INPUT

A resistor connected to V_{DD} and a capacitor connected to V_{SS} are connected to the RC input pin to establish the on-chip clock frequency that controls the rate of multiplexing and the touch switch delay time. Nominal values for these components are suggested in Figure 1, but they may be varied to change clock frequency over a range of 50kHz to 100 kHz.

REF INPUT

In order to allow flexibility in the choice of TouchControl panel materials, switch layout, and switch size, AMI Touch-Control inputs have been designed to detect a differential change rather than an absolute change in level. To obtain a reference level, two resistors are connected to input REF, one connected to input REF, one connected to V_{SS} and the other to V_{DD}.

V_{BB} SUPPLY

The sources of all output devices (both "O" and "B" outputs) are common and connected to pin V_{BB}. This allows TTL compatibility as shown in Figure 1, as well as the ability to drive higher level signals. For instance, if V_{SS} = 0 volts, V_{DD} = - 16 volts, and V_{BB} = V_{SS}, then active outputs would drive a load connected to V_{DD} towards V_{SS}.

M/T INPUT

The M/T input pin selects the mode of switch operation, either momentary or toggle. Applying V_{SS} to the M/T pin selects momentary operation in which appropriate outputs are active only for the duration of touching a switch. In this mode, no output is active when no switch is touched. A V_{DD} level applied to M/T causes the circuit to operate in the toggle mode
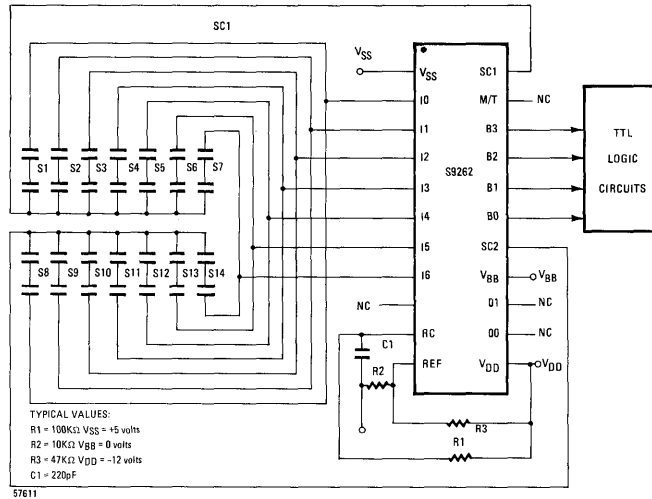
FIGURE 2. 14 SWITCH APPLICATION USING S9262

for "push-on, push-off" operation. Subsequent activation of the switch will toggle the corresponding output on and off alternately. It should be noted that each input should be cleared to the off state before selecting a new input to obtain meaningful data from the binary outputs. To reset all outputs when the toggle mode is selected, a pulse of V_{SS} level may be applied to the M/T input.

SC1 and SC2 OUTPUTS

The S9262 and S9266 have multiplexed inputs, using 2 x 7 and 2 x 16 matrices, respectively, to provide 14 and 32 input states. Clock signals SC1 and SC2 are used along with the "I" inputs to form these matrices as connected in the schematic of Figure 1.

O OUTPUTS

Each output pin labeled "O" corresponds to an input pin labeled "I". Whenever an input is selected, the output becomes active and will drive an external load toward supply voltage V_{BB}. This is true for momentary operation only; toggle operation is described in the section labeled "MT input." When "O" outputs are not active, they are high impedance open drain.

B AND AK OUTPUTS

The S9262 has four and the S9266 has five outputs labeled "B." These supply a binary code relating to the state of the inputs. Fourteen unique states are available on S9262 and thirty-two on S9266. The output configuration is identical to the "O" outputs. An extra output labeled AK is available on the S9266 and is active whenever any key is selected.

ENA INPUT

Available on the S9266, the ENA input allows the outputs to be bussed and may be gated off by application of a logic 1 level. V_{SS} applied to the input enables all five outputs and AK.

EXT

The EXT pin is used in the output circuitry and should be connected to V_{DD}.

SCAN OUTPUT	TOUCHED INPUT	"B" OUTPUTS				"O" OUTPUTS	
		B0	B1	B2	B3	O0	O1
SC1	I0	0	0	0	0	1	0
SC1	I1	1	0	0	0	0	1
SC1	I2	0	1	0	0	0	0
SC1	I3	1	1	0	0	0	0
SC1	I4	0	0	1	0	0	0
SC1	I5	1	0	1	0	0	0
SC1	I6	0	1	1	0	0	0
SC2	I0	1	1	1	0	0	0
SC2	I1	0	0	0	1	0	0
SC2	I2	1	0	0	1	0	0
SC2	I3	0	1	0	1	0	0
SC2	I4	1	1	0	1	0	0
SC2	I5	0	0	1	1	0	0
SC2	I6	1	0	1	1	0	0
–	None	1	1	1	1	0	0

TABLE 1. OUTPUT ENCODING (V_{BB} = 0 VOLTS)

SCAN OUTPUT	TOUCHED INPUT	"B" OUTPUTS					"O" OUTPUTS							AK OUTPUT
		B0	B1	B2	B3	B4	O0	O1	O2	O3	O4	O5	O6	
SC1	I0	0	0	0	0	0	1	0	0	0	0	0	0	1
SC1	I1	1	0	0	0	0	0	1	0	0	0	0	0	1
SC1	I2	0	1	0	0	0	0	0	1	0	0	0	0	1
SC1	I3	1	1	0	0	0	0	0	0	1	0	0	0	1
SC1	I4	0	0	1	0	0	0	0	0	0	1	0	0	1
SC1	I5	1	0	1	0	0	0	0	0	0	0	1	0	1
SC1	I6	0	1	1	0	0	0	0	0	0	0	0	1	1
SC1	I7	1	1	1	0	0	0	0	0	0	0	0	0	1
SC1	I8	0	0	0	1	0	0	0	0	0	0	0	0	1
SC1	I9	1	0	0	1	0	0	0	0	0	0	0	0	1
SC1	I10	0	1	0	1	0	0	0	0	0	0	0	0	1
SC1	I11	1	1	0	1	0	0	0	0	0	0	0	0	1
SC1	I12	0	0	1	1	0	0	0	0	0	0	0	0	1
SC1	I13	1	0	1	1	0	0	0	0	0	0	0	0	1
SC1	I14	0	1	1	1	0	0	0	0	0	0	0	0	1
SC1	I15	1	1	1	1	0	0	0	0	0	0	0	0	1
SC2	I0	0	0	0	0	1	0	0	0	0	0	0	0	1
SC2	I1	1	0	0	0	1	0	0	0	0	0	0	0	1
SC2	I2	0	1	0	0	1	0	0	0	0	0	0	0	1
SC2	I3	1	1	0	0	1	0	0	0	0	0	0	0	1
SC2	I4	0	0	1	0	1	0	0	0	0	0	0	0	1
SC2	I5	1	0	1	0	1	0	0	0	0	0	0	0	1
SC2	I6	0	1	1	0	1	0	0	0	0	0	0	0	1
SC2	I7	1	1	1	0	1	0	0	0	0	0	0	0	1
SC2	I8	0	0	0	1	1	0	0	0	0	0	0	0	1
SC2	I9	1	0	0	1	1	0	0	0	0	0	0	0	1
SC2	I10	0	1	0	1	1	0	0	0	0	0	0	0	1
SC2	I11	1	1	0	1	1	0	0	0	0	0	0	0	1
SC2	I12	0	0	1	1	1	0	0	0	0	0	0	0	1
SC2	I13	1	0	1	1	1	0	0	0	0	0	0	0	1
SC2	I14	0	1	1	1	1	0	0	0	0	0	0	0	1
SC2	I15	1	1	1	1	1	0	0	0	0	0	0	0	1
–	None	1	1	1	1	1	0	0	0	0	0	0	0	0

TOUCHCONTROL APPLICATION NOTES

PANEL CONSTRUCTION

A TouchControl switch panel consists of a single sheet of a rigid material with conductive surfaces applied on both sides as shown in Figure 3.

A number of materials may be used for touch panels, the selection of the material most suited for a particular application being dependent on such things as durability, appearance, ease of assembly, cost, and dielectric constant of the material.

Regardless of the selected panel material, a touch switch is formed by applying a single conductive surface to its front surface with two other conductive surfaces applied directly in line on the reverse side of the panel. Figure 3 shows three views of a typical touch panel containing two TouchControl switches. On switch one, conductive surface A is applied to the front of the panel and is the surface to be touched to effect a switch closure. Surfaces B and C are applied directly in line with A on the opposite side of the panel. A should cover completely and may overlap surfaces B and C.

FIGURE 3. CONSTRUCTION OF A TWO SWITCH TOUCHCONTROL PANEL WITH EQUIVALENT ELECTRICAL CIRCUIT.

The application of the conductive surfaces depends on selection of the panel materials. If glass is used, for example, it is common to apply a coating of tin oxide, which is then fired on for durability; rear surface conductors may be screened on with a conductive ink. Touch panels may be made more simply from double-sided printed circuit boards in which the conductive TouchControl surfaces are created by standard etching. For breadboarding purposes, a number of conductive tapes and paints are available and may be applied to a variety of touch panel materials.

ELECTRICAL OPERATION

The three conductive surfaces in a TouchControl switch combine to form two capacitors connected in series, as shown in the schematic diagram of Figure 3. An AC signal generated in the MOS circuit is applied to the rear conductive surface labeled C. This signal is coupled through to surface A by the capacitor formed by C and A. The signal is then coupled to surface B by the capacitor formed by A and B and applied to one of the inputs of the MOS circuit, which detects the signal's presence. When surface A is touched, the amplitude of the signal is significantly decreased because of body capacitance. This is sensed by the MOS circuit, and the appropriate switching function is performed.

TOUCH SWITCH LAYOUT GUIDELINES

AMI TouchControl circuits have been designed to interface with a variety of touch switch configurations. However, there are several guidelines that must be observed to insure a satisfactory TouchControl system.

The size of a TouchControl switch is dependent on the amount of capacitance needed to couple the clock signal to the "I" inputs of the MOS circuits. Because the input capacitance associated with the circuit input is typically five picofarads, it is advisable that each of the two series capacitors formed by the three conductive TouchControl panel surfaces be no less than seven picofarads. Since the capacitance in picofarads can be calculated by $C = 0.22 \in A \div d$, where $\in$ is the

dielectric constant, A is area, and d is the material's thickness, it is apparent that minimum switch size is dependent on the thickness and dielectric constant of the panel material. If, for example, the panel is made from 1/8" thick glass with a dielectric constant of 8, then the minimum area of each of the two rear surface conductors is 0.5 sq. inches. Since the touch surface must cover the entire area of the two rear conductors, it must, then, be at least 1.0 sq. inch. It is desirable to separate the two rear-surface conductors by at least 0.125 inches, so the touch surface would be somewhat larger than 1.0 sq. inch. Higher capacitance, and thus smaller touch switches, can be obtained by using epoxy printed circuit material; though the dielectric constant is lower (around 5.0) the thickness can be decreased substantially.

CIRCUIT TO PANEL CONNECTIONS

There are a number of ways to make the necessary connections between TouchControl circuits and panels. A simple approach is to use a printed circuit board for the touch panel. In this case, the connections to the circuit are made by the etched copper pattern. In laying out a printed circuit, it is important to keep the copper traces running to the individual touch pads separated from each other as much as possible. In most instances a minimum spacing of 0.125" between traces is acceptable, though wider spacing might be necessary in cases where traces will run parallel to each other for distances of over six inches. It is also important to keep the clock output (SC1) at least 0.75 inches away from any input trace. These spacing requirements are guidelines to be followed regardless of the touch panel material.

With glass touch panels, a simple method for breadboarding systems is to fasten individual wires onto the conductive surfaces with a conductive epoxy. For production situations, it is possible to locate the electronic circuitry on a separate printed circuit board. Contact to the glass touch panel can be made through spring contacts mounted in the appropriate locations on the circuit board. An alternate approach is to route the traces on the glass to an edge of the glass, making connection through an edge connector, keeping in mind the spacing requirements between traces.

TOUCH ■■
CONTROL

SWITCHING

The AMI TouchControl Kit
TCK-100

Instructions for Assembly and Operation

INTRODUCTION

The AMI TouchControl kit demonstrates the ease with which this unique system of capacitive switching may be implemented. Included in the kit are a printed circuit board and AMI's newly developed S9263 TouchControl circuit. The printed wiring board, which has 16 touch switches etched onto its top surface, contains on its reverse side all the interconnection necessary to interface the S9263 inputs with the 16 touch switches and the S9263 outputs with 16 light emitting diodes. As the touch switches are activated, the corresponding diodes are lighted to indicate the output states of the S9263. If desired, external logic may be operated by connecting a cable directly to the S9263 outputs.

Additional components required for the kit are readily available, and assembly of the kit should take less than an hour's time. The circuit board may be mounted either on standoffs or on a standard aluminum chassis box.

PARTS LIST FOR AMI TOUCHCONTROL KIT:

QUANTITY REQUIRED	DESCRIPTION	QUANTITY REQUIRED	DESCRIPTION
1	S9263 TouchControl circuit (Included)	16	3.3KΩ Resistor ¼ Watt
1	Printed wiring board (Included)	1	Transistor 2N3569 or equivalent
1	Transformer, 12.6 volt 300mA	1	500μF capacitor/20 volts
	Radio Shack P/N 273-1385 or equivalent	1	0.33μF capacitor
1	Line cord	1	220 pF capacitor
1	Diode IN920 or equivalent	16	Light emitting diode — MV5023
2	100KΩ Resistor ¼ Watt		or equivalent
1	60KΩ Resistor ¼ Watt	1	Aluminum chassis box — 15″ x 9″
1	15KΩ Resistor ¼ Watt		Bud # AC1421 or equivalent
1	10KΩ Resistor ¼ Watt		(optional)

ASSEMBLY

The circuit board may be assembled easily by referring to Figure 2, a view of the reverse side of the board. For appearance, it is recommended that all components except the LED's and the S9263 be mounted on the reverse side of the board, with all leads cut off flush with the board's top surface.

For convenience, a 15 volt power supply is provided on the circuit board, so that the system may be plugged into a standard 110 volt outlet. If desired, an external DC supply of 15 volts may be used, connecting the positive and negative outputs to the corresponding holes designated for C1. If a DC supply is used, the transformer, diode, and C1 may be eliminated.

OPERATION

The AMI TouchControl kit provides sixteen touch switches that interface with the S9263 to activate sixteen light emitting diodes. Each of the switches numbered from one to fifteen has a light associated with it which is labeled with the same number. The switch labeled "T" is used to select the mode of operation of the S9263, either momentary or toggle. When the LED labeled "T" is off, touch pads one through fifteen operate as momentary switches, and any switch's corresponding LED will turn on when the switch is touched, remaining on only for the duration of touching the switch. If "T" is touched, the "T" LED will turn on and stay on even after "T" is untouched. The S9263 is now operating in a toggle mode, and the brief touch of any switch from one through fifteen will cause its corresponding LED to turn on and latch. Subsequent activations of the switch will turn the LED

off and on alternately. Touching "T" once again causes the "T" LED to turn off, and the S9263 once again operates in the momentary mode. By removing the 0.33μF capacitor, it is possible to use the "T" pad as a clear switch. In this mode, all numbered pads function as "push on, push off" switches. Touching the "T" pad turns off all LED's corresponding to the numbered switches.

To operate external logic systems with the TouchControl kit, a cable may be soldered, using a grounded soldering iron, directly to the outputs of the S9263. The voltage on an output that is turned off (corresponding LED is off) is − 15 volts (or V_{DD}). When turned on, the output will rise towards ground (V_{SS}). Appropriate loading conditions are specified in the advanced product description for this part.
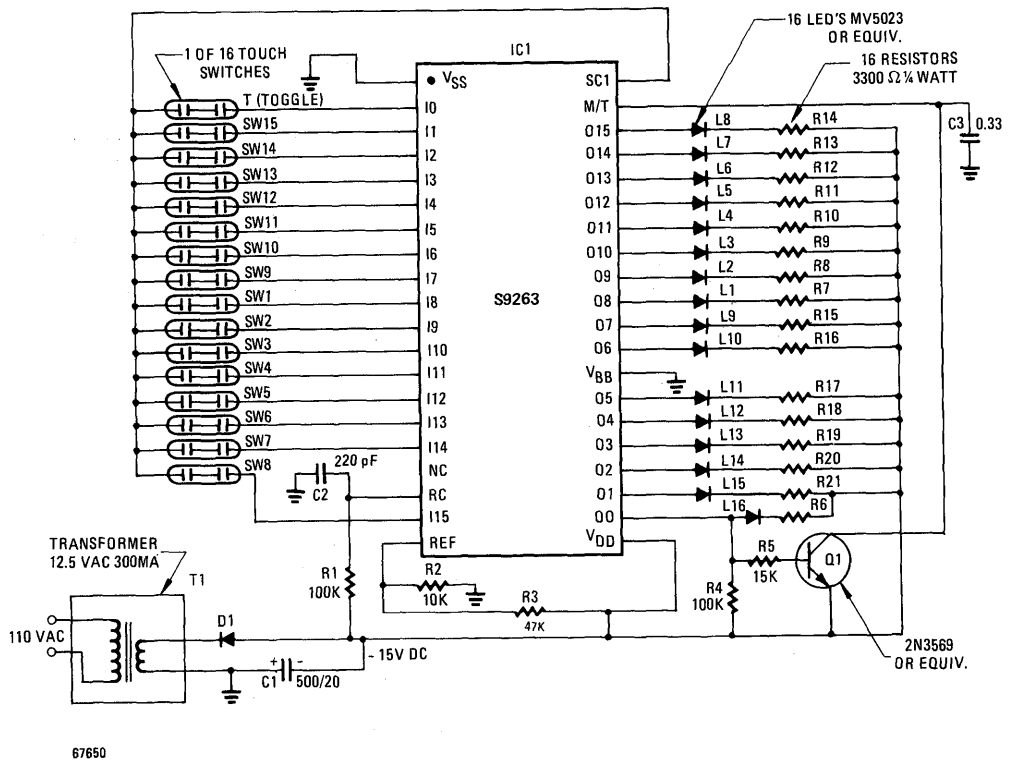
Figure 1. Schematic Diagram of TCK-100

PARTS LIST FOR ASSEMBLING TCK – 100 KIT:

PART NUMBER	PART DESCRIPTION	PART NUMBER	PART DESCRIPTION
R1, R4	100 KΩ ¼ Watt resistor	Q1	NPN transistor 2N3569 or equivalent
R2	10 KΩ ¼ Watt resistor	D1	Diode IN920 or equivalent
R3	47KΩ ¼ Watt resistor	L1 thru L16	Light emitting diode — MV5023 or
R5	15 KΩ ¼ Watt resistor		equivalent
R6 thru R21	3.3 KΩ ¼ Watt resistor	IC1	AMI integrated circuit S9263
C1	500 µF capacitor 20 Volts	T1	Transformer 12. 6 VAC @ 300 mA.
C2	220 pF capacitor		Radio Shack P/N 273-1385
C3	0.33 µF capacitor		or equivalent
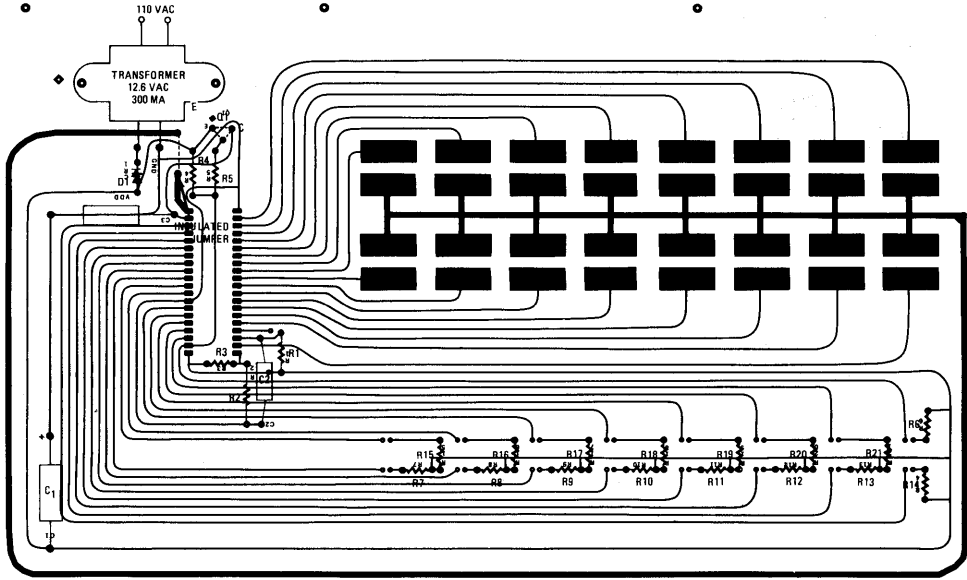
Figure 2. Rear of Circuit Board

Figure 3. Front of Panel

AMI

AMERICAN MICROSYSTEMS, INC.

S1856
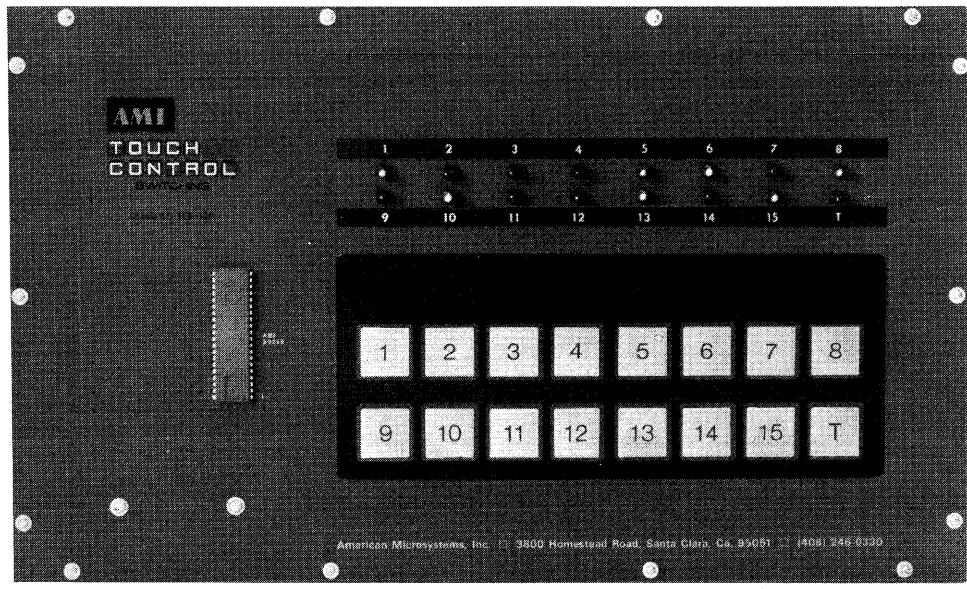
MOS DIGITAL CLOCK

Features

- ☐ 262,144 External Quartz Crystal
- ☐ Has 20 Hr. Resettable Elapsed Time Counter
- ☐ Direct LCD or Tung-sol DT1704 Tube Interface
- ☐ Electrically Selectable Multiplexed LED Output
- ☐ Minute and Hour SET Controls
- ☐ Separate Display Supply Allows Display Turn Off for Reduced Battery Current Drain
- ☐ 1024Hz Outputs for Voltage Doubler
- ☐ Calendar Advancing or AM/PM Output

General Description

The S1856 Digital Clock provides the circuitry to implement a 4-digit time keeper with separate elapsed time counter. It is an MOS/LSI circuit consisting of down counters, combinational logic, BCD to 7-segment decoder and output buffer transistors

in a 40-pin DIP. The circuit has a separate output pin to drive each segment of a Liquid Crystal Display directly. However if the LED mode of operation is selected, only the HRS×10 and F3 through A3 outputs are used to provide segment drive current. In this mode of operation segment drivers F3 through A3 are multiplexed at 25% duty cycle to provide MINUTES, 10's of MINUTES and HOURS information.

The ELAPSED TIME COUNTER can be reset and displayed separately without affecting the state of the time keeper. The ELAPSED TIME COUNTER has the added feature of displaying SECONDS, 10's of SECONDS and MINUTES automatically during the first 10 minutes after a reset has occurred. The counter will then display MINUTES, 10's of MINUTES, HOURS and 10's of HOURS for the remainder for its 20 hours capacity.
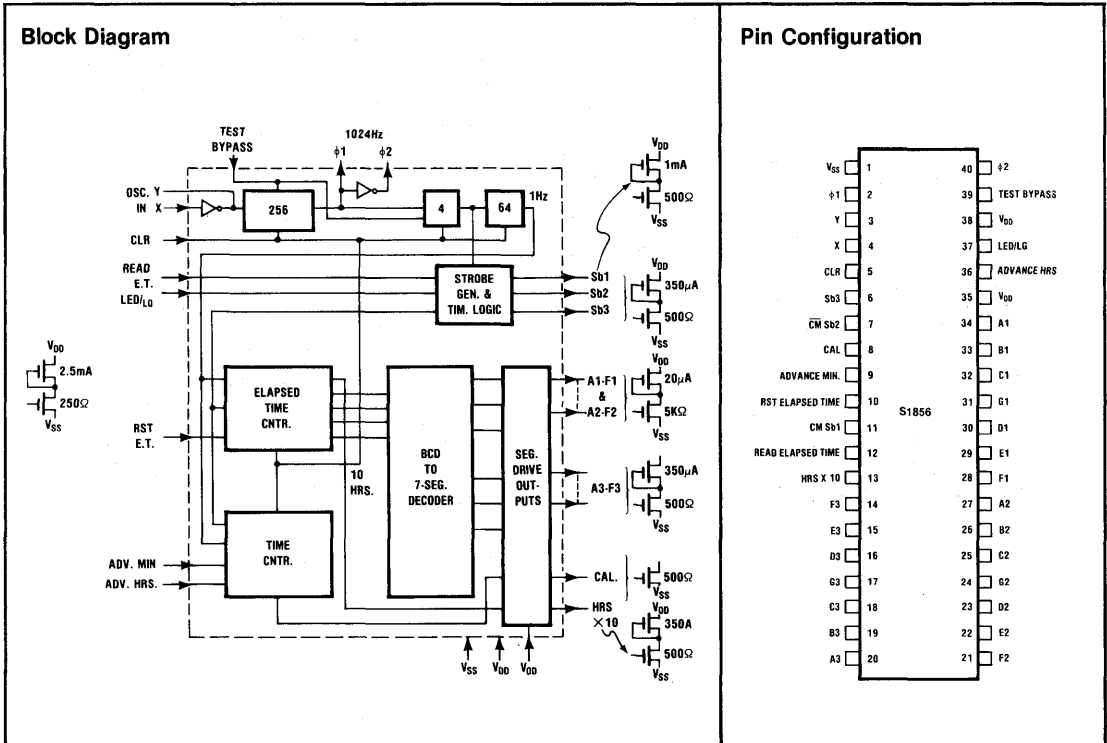
Block Diagram

Pin Configuration

3.32

Absolute Maximum Ratings

Positive Voltage on any Pin .... $V_{SS} + 0.3V$

Negative Voltage on any Pin .... $V_{SS} - 28V$

Storage Temperature .... $-65°C$ to $+150°C$

Operating Temperature .... $-40°C$ to $+100°C$

Dynamic Characteristics: $T_A = -40°C$ to $+70°C$, $V_{SS} = 0V$, $V_{DD} - 6V$ to $-16V$, $V_{OD} - 5V$ to $-28V$

Symbol	Min.	Typ.	Max.	Units	Conditions
V_{IL}(OSC X)	V_{DD}		$V_{SS} - 6$	V	An Internal resistor of 700KΩ
V_{IH}	$V_{SS} - 1$		$V_{SS} + 0.3$	V	(typical) to V_{DD} is provided
V_{IH}(Control)	$V_{SS} - 0.5$		$V_{SS} + 0.3$	V	for all control inputs.
V_{IL}	V_{DD}		$V_{SS} - 6$	V	
V_{OH}(Outputs)	$V_{SS} - 1$			V	Open circuit
V_{OL}			V_{DD}	V	Open circuit
I_{DD}		10	15	mA	$V_{DD} - 14V$
I_{DD}		10		mA	$V_{DD} - 6V$

Figure 1. Typical Performance Characteristics
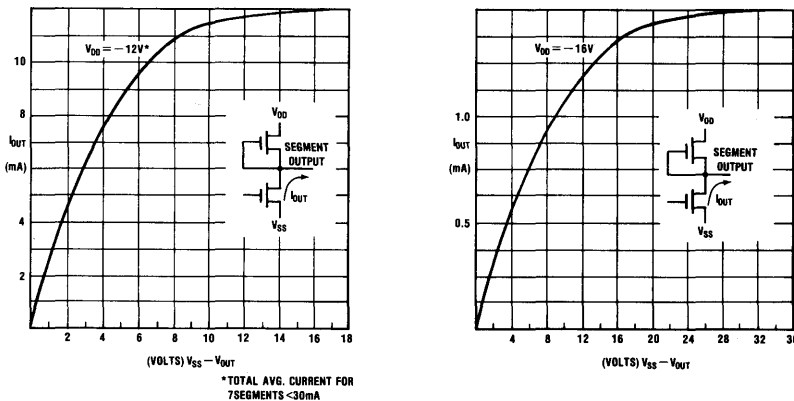
Typical Applications

- Automotive Clock
- Household Clock With Auxiliary Battery for Accurate Time Keeping During Power Interruptions
- Appliance Timers
- Industrial Timers
- Photographic Timers
- Avionics Timers
- Portable Clock

Operational Description

The Clock circuit block diagram is shown on the previous page. The input transistor of the circuit forms an oscillator circuit with an external quartz crystal and a few other components (see application drawings). The resultant 262.144kHz signal is amplified and clipped in the input stage. A chain of binary down counters divides the square wave frequency by 256 to supply two complemen-

tary outputs, φ1 and φ2 at 1024Hz. These low impedance outputs can drive an external voltage doubler as well as allow an accurate frequency tuning on the oscillator.

Next a divide by four stage produces a 64Hz signal from which the three strobes Sb1, Sb2, and Sb3 are generated. The strobe generator also contains logic to synchronize the display outputs with the external strobes as well as control the segments for Liquid Crystal Display operation. The 64Hz signal also inputs to a divide by 64-stage to produce a 1 Hz signal which inputs to both the TIME COUNTER and the ELAPSED TIME COUNTER.

The TIME COUNTER contains the binary stages and the decoding logic to generate the BCD code for MINUTES, HOURS and HRS × 10. This data is strobed into the BCD to 7-segment DECODER and loaded into the output buffers in synchronization with the appropriate strobe, Sb1, Sb2 or Sb3.

The ELAPSED TIME COUNTER functions similarly to the TIME COUNTER with the additional decoding of SECONDS and 10's of SECONDS to the display instead of HRS and HRS × 10 during the first 10 minutes after reset.

An internal connection to V_{DD} supply at pin 37 holds the clock in the liquid crystal mode and the outputs are interfaced directly with the LCD as shown in Figure 2.

Figure 2. LCD Output Drive
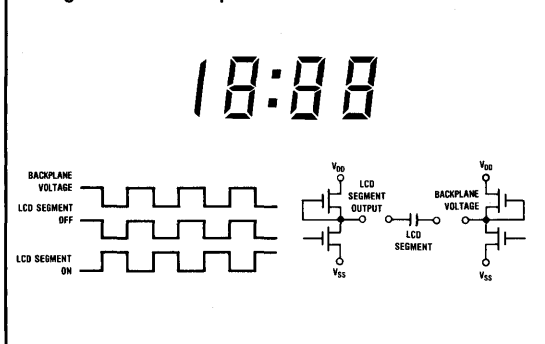
To assure longevity of the LCD display, a 64Hz signal is applied to the individual segments. When the applied segment signal is in-phase with the 64Hz backplane (LCD common terminal) voltage, no visibility occurs. When the applied signal is 180° out of phase with the backplane voltage, visibility occurs. The waveforms shown in Figure 2 represent these conditions.

The backplane voltage is generated by buffering the signal which drives the timing counters. This assures that visibility of the display will not occur through synchronizing problems or rise and fall time differences.

The phase of the segment outputs is generated from the contents of data latches and buffer circuits. This provides an active pull-up or pull-down to both terminals of the segments at all times, thus eliminating the effect of capacitive coupling across the LCD segment. (See Figure 2.)

When pin 37 is connected to V_{SS} the multiplexed mode of operation is selected. An ON segment in this mode is driven by a pull-down to V_{SS} which is true during its appropriate strobe time as shown in Figure 3 below.

Figure 3. Strobe Time
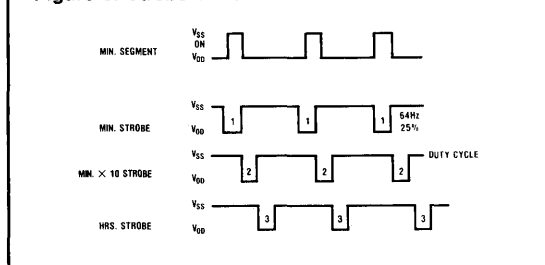
A typical LED interface circuit is shown below in Figure 4. In this mode the HRS × 10-digit is a steady state DC output and can be used at any of the 3 strobe times.

Figure 4. MOS/LED Interface

Functional Description of Inputs

V_{SS}	Positive voltage supply return line for circuit.
Y	Oscillator pull-up resistor connection. A 10KΩ resistor to V_{CC} from this pin serves as the 262.144kHz oscillator load.
X	Oscillator input pin. Provides amplification at oscillation frequency of the output from the external crystal and RC network.
CLR	Master Clear. Resets all counters to zero when connected to V_{SS}.
ADV. MIN.	Sets MINUTES with carry to MINUTES ×10 at a one per second rate when connected to V_{SS}.
RST ET	Displays contents of ELAPSED TIME COUNTER when connected to V_{SS}, otherwise time of day displayed.
V_{OD}	Negative power supply input for output buffers only. Allows display to be turned off while internal clock counters continue to operate.
ADV. HRS.	Sets HRS, with carry to HRS ×10, at a one per second rate connected to V_{SS}.
LED/LQ	Mode select pin. When connected to V_{SS} the LED mode is selected. In this mode the three strobe outputs are used to multiplex outputs A3 through F3 to drive MINUTES, MINUTES ×10 and HRS ×10 digits. This occurs at 64Hz 25% duty rate. In this mode outputs A1 through F1 and A2 through F2 remain off at negative supply level, V_{OD}.
V_{DD}	Negative power supply input for internal logic can be connected to V_{OD} for single supply operation.
TEST BYPASS	When connected to V_{SS} time counters advance at 1024 × normal rate. Used for automatic testing of the clock circuitry.

Functional Description of Outputs

φ1	Voltage doubler and frequency check output. This supplies a 1024Hz square wave signal which swings between the V_{SS} and V_{DD} voltage levels.
φ2	Same as φ1 but 180° out of phase.
Sb3	Strobe signal for HRS digit. 64Hz 25% duty cycle with voltage swing from V_{SS} to V_{OD}. Used only in LED mode.
$\overline{CM}$ Sb2	Drives colon in Liquid Crystal mode and serves as MIN ×10 digit strobe in LED mode. Voltage swing V_{SS} to V_{OD}.
CAL OUT	Calendar advance output. This pin has internal pull-down to V_{SS} only for stepping motor interface. An external 30kΩ resistor may be connected to V_{OD} to drive an external latch for AM-PM display.
CM Sb1	Drives display backplane in LIQUID CRYSTAL mode and serves as MINUTES digit strobe in LED mode. Voltage swing V_{SS} to V_{OD}.

Figure 5. 7-Segment Call Out
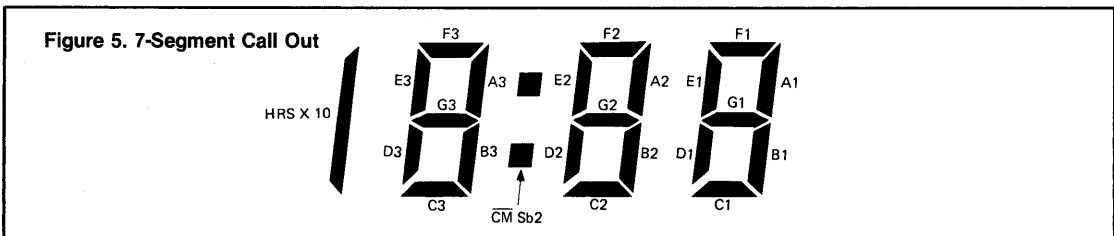
Figure 6. Application Data

AUTOMOBILE CLOCK
WITH LED DISPLAY

HOUSEHOLD CLOCK
WITH AUXILIARY BATTERY

AMI
AMERICAN MICROSYSTEMS, INC.

S2709
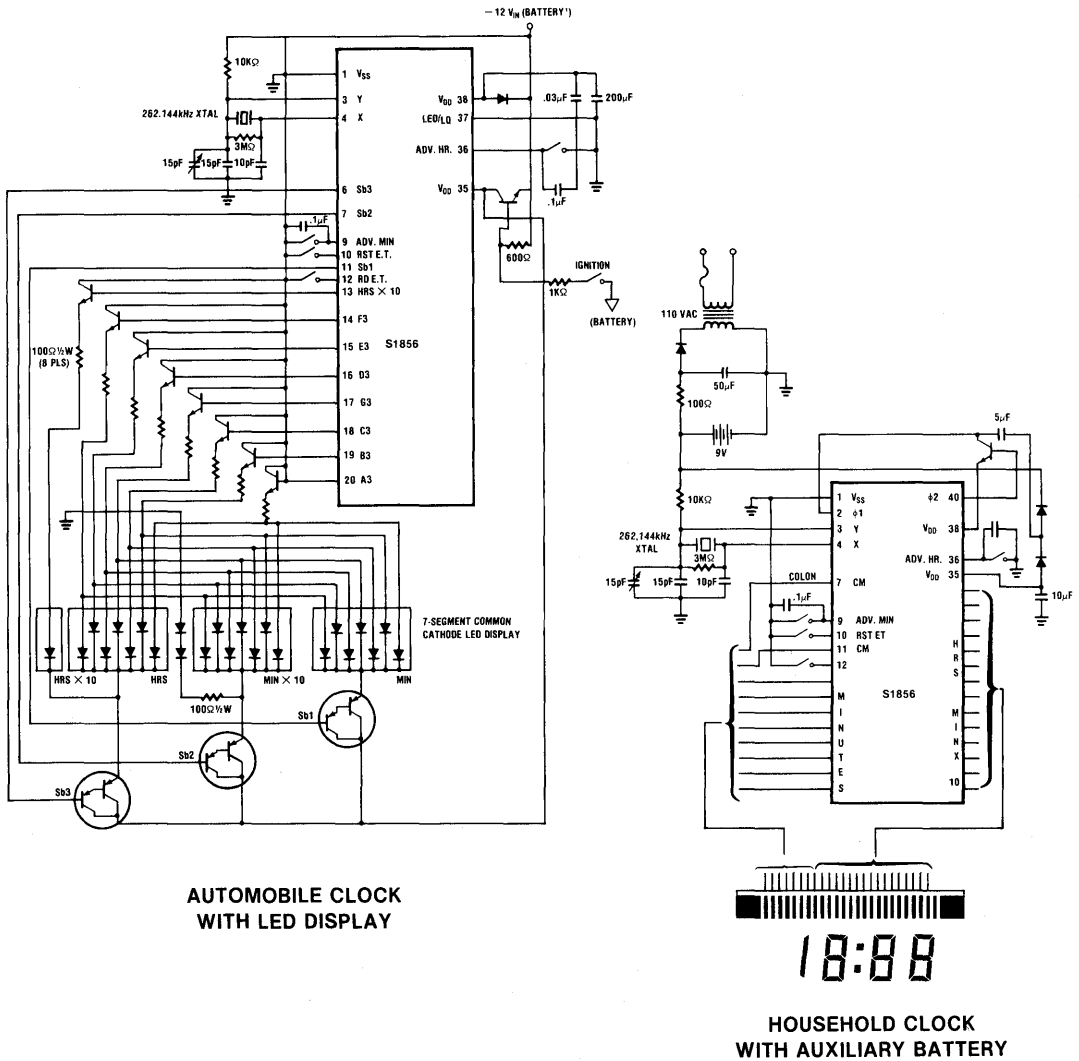
VACUUM FLUORESCENT DIGITAL CLOCK FOR AUTOMOTIVE APPLICATIONS

Features

☐ Uses Inxpensive 4MHz Crystal
☐ Direct Drive to Green or Blue Vacuum Fluorescent Display
☐ Low Standby Power Dissipation When Display is Switched Off With Ignition
☐ Variable Brightness Tracks Other Dash Lights

Applications

☐ In Dash Automobile Clocks
☐ Tape Players, CB Radio Units
☐ Automotive After Market Clocks
☐ Aircraft, Marine Panel Clocks
☐ Portable Instrumentation Clocks

Functional Description

The S2709 vacuum fluorescent clock is a monolithic MOS integrated circuit utilizing P-Channel low threshold, enhancement mode and ion-implanted depletion mode devices. The circuit interfaces directly with 4 digit multiplexed vacuum fluorescent displays and requires only a single nominal 12V power supply. The timekeeping function operates from a 4MHz crystal controlled input. The display format is 12 hours with colon and leading zero blanking. An up-converter output is provided by the circuit to generate increased display driving voltage. A brightness control input allows variation of the display intensity. An ignition monitor input controls the upconverter operation and inhibits time setting. The S2709 is normally supplied in a 22-lead plastic dual-inline package.

Block Diagram

Pin Configuration

SEGMENT G	1	22 OSCILLATOR OUTPUT
SEGMENT F	2	21 OSCILLATOR INPUT
DIGIT G_4	3	20 TIME SET
SEGMENT E	4	19 V_{DD}
SEGMENT D	5	18 TEST
DIGIT G_3	6	17 V_{SS}
SEGMENT C	7	16 IGNITION MONITOR
DIGIT G_2	8	15 DAY/NIGHT
SEGMENT B	9	14 DIMMING CONTROL
SEGMENT A	10	13 PULSE (UPCONVERTER)
COLON	11	12 DIGIT G_1
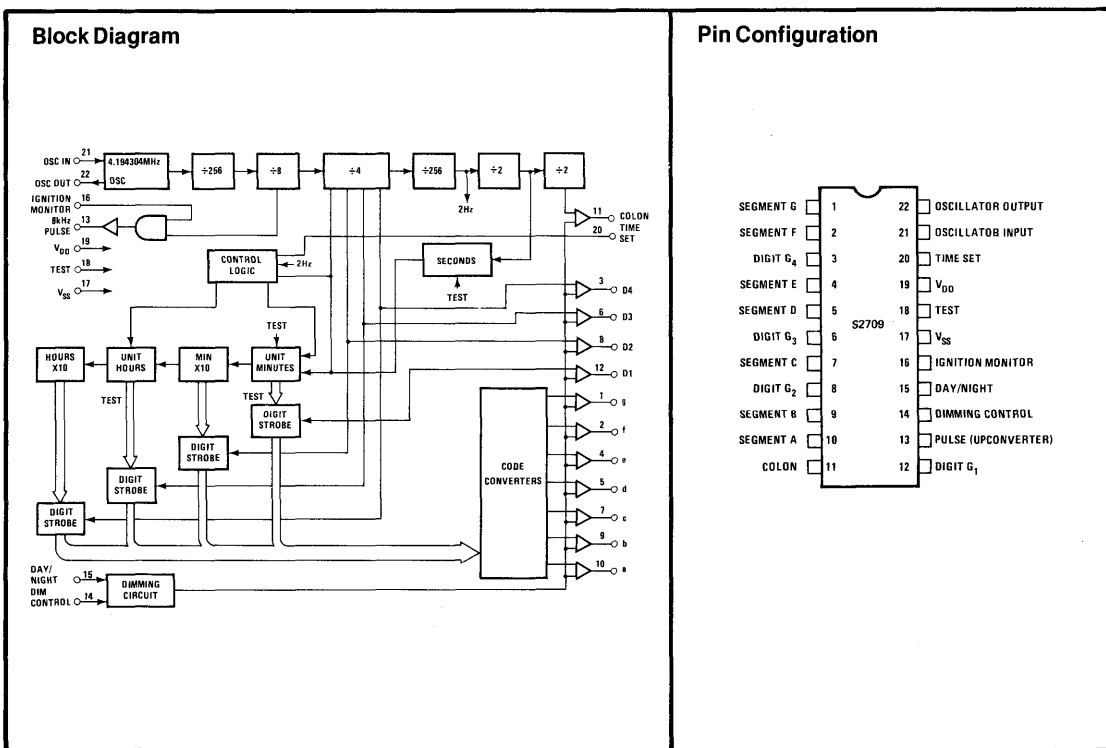
Operational Description

Refer to the block diagram and Figure 1, Typical Application.

Oscillator Input (Pin 21) and Output (Pin 22)—The crystal controlled oscillator operates at a frequency of 4.194304 MHz to increase accuracy and reduce external component costs due to the less expensive quartz crystal. The frequency is controlled by a quartz crystal and fixed capacitor upconverter output (pin 13). This method allows accurate frequency tuning of the crystal oscillator without loading down the oscillator circuit. The feedback and phase shift resistors are integrated to further reduce external component costs. The internal oscillator inverter drives a counter chain that performs the timekeeping function.

Time Setting Input (Pin 20)—To prevent tampering, time setting is inhibited until the ignition monitor (pin 16) is held at a logic high level (V_{SS}).

Normal timekeeping is provided by allowing the time set pin to float externally. (Unloaded, this pin will alternate between V_{DD} and V_{SS} in phase with the unit minutes digit strobe [pin 12] during normal timekeeping.) If the time set pin is held at a logic high level (V_{SS}) the minutes counter advances at a 2Hz rate without carry to hours. If the time set pin is held at a logic low level (V_{DD}) the hours counter advances at a 2Hz rate.

It is possible to reset the hours, minutes and internal seconds counter by applying a logic low level (V_{DD}) to the test input (pin 18) during the time that the ignition monitor input is at a logic low level (V_{SS}). This reset state (time 1:00) is used for testing purposes.

Upconverter Pulse Output (Pin 13)—The clock circuit and vacuum fluorescent display drive normally operate at 25V when the ignition monitor pin is held at a logic high level (V_{SS}). The automobile battery voltage (12V) is doubled by an external upconverter circuit triggered by an 8kHz output pulse having a 28% duty cycle. The voltage, whether 12V or 25V, is applied to the circuit via the V_{SS} input (pin 17).

When the ignition monitor pin is held at a logic low level (V_{DD}) the upconverter is disabled. This drops the V_{SS}-supply to 12V allowing the clock to operate while the display drive is decreased, lowering power dissipation. At the battery voltage drops (due to engine starting, cold temperature, or aging) timekeeping is maintained down to approximately 7V with no loss of the memory down to 5V. However, below 9V the upconverter will not be inhibited by the ignition monitor input.

Note that low standby power dissipation (60mW typical @V_{SS}=12V, and no output loads) is accomplished by turning off the filament voltage to the display when the auto ignition switch is off.

Ignition Monitor (Pin 16)—Along with preventing the already mentioned time setting function, the ignition monitor when held at a logic low level (V_{DD}) inhibits the 8kHz upconverter output pulse (pin 13) as long as the supply (V_{SS}) is above 9V. This pin is normally connected to the auto accessory switch.

The ignition monitor input can be protected against power supply transients by using 47KΩ external series resistance (see Figure 1).

Day/Night Display Control Input (Pin 15)—As seen in Figure 2, the display brightness is controlled via both pin 15 and the dimming control input (pin 14). The day/night input is connected to the automobile parking or headlights switch such that when these lights are off (V_{IN} low) the decoded segment and the digit outputs are from V_{SS} to V_{SS}−2.0 volts. When the parking or headlights are switched on (V_{IN} high) the internal day/night logic enables the dimming input to control the segment and digit output voltage and brightness by allowing adjustable current to flow as controlled by the dash lights rheostat.

The day/night input can be protected from power supply transients by using 47KΩ external series resistance (See Figure 1).

Display Dimming Control Input (Pin 14)—The display dimming input is connected to the automobile dashboard light dimming rheostat through a series resistor. This allows the fluorescent display to track the dimming characteristics of the incandescent dashboard light (see Figure 2). The display dimming control is inhibited unless the day/night input (pin 15) is held at a logic high level (V_{SS}).

Display Drivers (Pins 1 through 12)—The 12 hour display format is comprised of four digits with leading zero blanking and a flashing colon. Each digit contains 7 segments with individual segments coded in the conventional manner (see Figure 1). The display is multiplexed with each digit output (G1, G2, G3 and G4) being strobed for a time period of approximately 0.5mS. Figure 3 shows the minimum output current as a function of output voltage for the digit (grid) and segment outputs.

The colon output (pin 11) is designed to have an unobtrusive flash while still indicating that the clock is functioning normally. The colon flash is accomplished in a 2 second period of 1-1/2 seconds on the 1/2 second off.

Electrical Characteristics

Symbol	Characteristics/Conditions	V_{DD} V	0°C to 70°C			Unit
			Min.	Typ.	Max.	
V_{SS}	Operating Supply Range $V_{DD}=0.0V$ (Refer to Upconverter Pulse Output)		7.0		28	V
I_{SS}	Supply Current (No loads on Outputs)	12 25			12 15	mA mA
	Oscillator Frequency			4.194304		MHz
	Display Outputs					
	Multiplex Rate			512		Hz
	Duty Cycle (Each Digit Per Cycle)			18.8		%
	Output Current (Day/Night=LOW)					
I_{OH}	Digits, $V_{OH}=24V$	25			−6.0	mA
I_{OL}	$V_{OL}= 2V$	25	40			μA
I_{OH}	Segments & Colon, $V_{OH}=24V$	25			−1.5	mA
I_{OL}	$V_{OL}= 2V$	25	10			μA
	Output Voltage (V[Pin 14]−V(Digit or Seg)					
	Day/Night=High, V(Pin 14⩾/4V)					
ΔV_O	Digits ($R_L=8.2K\Omega$ to V_{DD})	25			1	V
ΔV_O	Segment ($R_L=100K\Omega$ to V_{DD})	25			1	V
	Upconverter Pulse Output					
	Pulse Frequency			8192		Hz
	Duty Cycle			25		%
	Output Current					
I_{OH}	$V_{OH}=7V$	9			−1.5	mA
I_{OH}	$V_{OH}=23V$	25			−3.0	mA
I_{OL}	$V_{OL}=1V$	25	6.0			μA
	Time Set Input/Output					
	Input Voltage (No Load)					
V_{IH}	High	25	24		1	V
V_{IL}	Low	25	0		1	V
	Output Current					
I_{OH}	$V_{OH}=18V$	25	−6.0		−2.0	mA
	Output Frequency			512		Hz
	Duty Cycle			25		%
	Ignition Monitor Input and Day/Night Input					
	Input Voltage					
V_{IH}	High	9.0 to 25	6.5		V_{SS}	V
V_{IL}	Low	9.0 to 25	0		2.0	V
I_{IH}	Input Current (Pull Down) $V_{IH}=12V$	25	2		20	μA

Figure 1. Typical Application

VF DISPLAY
(FUTABA 4 BT–01 OR EQUIVALENT)

CAR BATTERY
(+12V)

IGNITION
SWITCH

200Ω
1W

2.2mH

47μF

25V

Q1

10K

17 V$_{SS}$

(DISPLAY DRIVERS, PINS 1–12)

13 PULSE
(8kHz)

S2709
VACUUM FLUORESCENT DIGITAL CLOCK

DIM
CONTROL 14

1.2K

DASH LIGHTS
RHEOSTAT
(50Ω POT TO +12V)

19

OSC
OUT

OSC
IN

DAY/
NIGHT

IGN
MON

TIME
SET

22
4.194304
MHz

21

15

16

20

Q1, Q2 – 2N2222 OR EQUIVALENT

47K

V$_{SS}$ (SET MINUTES)

47K

– USE 130Ω, 2W FOR
FOR FUTABE 4BT–01

30pF
NOM

47K

V$_{DD}$ (SET HOURS)

25pF

HEAD LIGHT
SWITCH
TO +12V

IGNITION
SWITCH
TO +12V

UNIVERSAL
DISPLAY DRIVER

Features

☐ **32 Bit Data Storage Register**

☐ **Drives LED, LCD, or Vacuum Fluorescent Displays**

☐ **32 Output Buffers**

☐ **Drives up to 4 Digits**

☐ **Expansion Capability for More Digits**

☐ **Reduced RFI Emanation**

☐ **Wired OR Capability for Higher Current**

General Description

The S2809 Universal Display Driver is a P-channel MOS integrated circuits capable of driving LED, vacuum fluorescent, and liquid crystal displays. Data is clocked serially into a 32-bit master-slave static shift register. This provides static parallel drive to the display segments through display drive buffers. To reduce RFI emanation, capacitors have been integrated on the circuit for reduction of output switching speeds. Serial interconnection of circuits is made possible by the Data Out Output, allowing additional digits to be driven.

Two or more outputs may be wired together for higher sourcing currents; useful in applications such as triac triggering or low voltage incandescent displays. The S2809 can also be used as a parallel output device for μC's such as AMI's S2000 series single chip microcomputer.
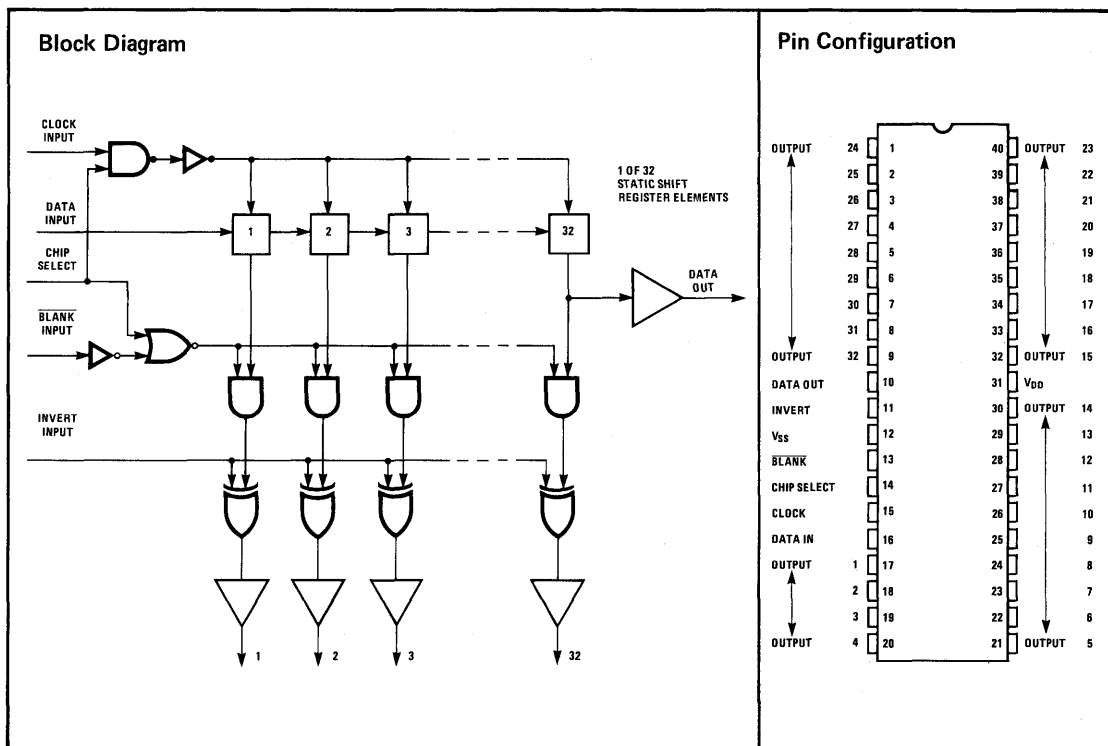
Block Diagram

Pin Configuration

Absolute Maximum Ratings

Operating Ambient Temperature T_A .... 0°C to +70°C
Storage Temperature .... −65°C to +150°C
V_{SS} Supply Voltage .... +25V
Positive Voltage on Any Pin .... V_{SS} + 0.3V

Electrical Characteristics ($V_{DD} = 0V$, $8V < V_{SS} < 22V$, $T_A = 0°C$ to $+70°C$ unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{IH}	Logic 1 Level (Data, Clock, Invert, Chip Select Inputs)	$V_{SS} - 0.7$		$V_{SS} + 0.3$	V	
V_{IL}	Logic 0 Level (Data, Clock Invert, Chip Select Inputs)			$V_{SS} - 7$	V	
V_{BH}	Logic 1 Level ($\overline{Blank}$ Input)	$V_{SS} - 4.0$		$V_{SS} + 0.3$	V	
V_{BL}	Logic 0 Level ($\overline{Blank}$ Input)	V_{DD}		$V_{SS} - 7$	V	
I_B	Current Sinked or Sourced by $\overline{Blank}$ Input			1.0	μA	Voltage applied to $\overline{Blank}$ Input between V_{DD} & V_{SS}
C_B	Capacitance of $\overline{Blank}$ Input			12	pF	
I_{OH}	Output Source Current	9.0			mA	$V_{OUT} = V_{SS} - 3.$
I_{OH}	Output Source Current	4.0			mA	$V_{OUT} = V_{SS} - 1$
I_{OH}	Output Source Current		1.0		mA	$V_{OUT} = V_{SS} - 0$
I_{OH}	Output Source Current	10.0			μA	$V_{OUT} = V_{SS} - 50$
I_{OS}	Sink Current Output Load Device			50	μA	Output voltage $= V_{SS}$
I_{OS}	Sink Current Output Load Device	10			μA	Output voltage $\leq +3V$
I_L	Output Leakage Currrent (Output Off)			10.0	μA	
I_{DD}	Supply Current			3.0	mA	Not including output source and sink current
I_{OM}	Maximum Total Output Loading			300	mA	All outputs on
f_c	Clock Frequency	DC		100K	Hz	
t_{on}	Clock Input Logic/Level Duration	3.0			μs	
t_{off}	Clock Input Logic 0 Level Duration	6.5			μs	
t_{ro}, t_{fo}	Display Output Current Rise and Fall Times	10		150	μs	*Measured between 10% and 90% of output current $V_{SS} < +11V$, $I_{OH} = 9ma$

*NOTE: With supply voltages higher than 11 volts, delay exists before an output rise or fall. This delay will not exceed 100μs with a 22 volt supply.

Functional Description

The 32-bit static shift register stores data to be used for driving 32 output buffers, which may be used to drive display segments or other circuitry. Data is clocked serially into the register by the signal applied to the Clock Input whenever a logic 1 level is applied to the Chip Select Input; during this time, outputs are not driven by the shift register but will go to the logic level of the invert input. With a logic 0 level applied to the Chip Select Input, the 32 outputs are driven in parallel by the 32-bit register. It is possible to connect S2809 circuits in series to drive additional displays by use of the Data Output.

Clock Input

The Clock Input is used to clock data serially into the 32-bit shift register. The signal at the Clock Input may be continuous, since the shift register is clocked only when a logic 1 level is applied to the Chip Select Input. As indicated in Table 1, data is transferred from QN-1 to QN on the negative transition of the Clock Input.

Data Input

Whenever a logic 1 level is applied to the Chip Select Input, data present at the Data Input is clocked into the 32-bit master-slave shift register. Data present at the input to the register is clocked into the master element during the logic 1 clock level and thus must be valid for the duration of the positive clock pulsewidth. This information is transferred to the slave section of each register bit during the clock logic 0 level.

Chip Select

The Chip Select Input is used to enable clocking of the shift register. When a logic 1 level is applied to this input, the register is clocked as described above. During this time, the output buffers are not driven by the register outputs, but will be driven to the logic level present at the Invert Input. With a logic 0 level at the Chip Select Input, clocking of the register is disabled, and the output buffers are driven by the 32 shift register elements.

Blank Input

This input may be used to control display intensity by varying the output duty cycles. With a logic 0 level at the Blank Input, all outputs will turn off (i.e., outputs will go the the logic level of the Invert Input). With a logic 1 level at the Blank Input, outputs are again driven in parallel by the 32 shift register elements (assuming the Chip Select Input is at logic 0).

The Blank Input has been designed with a high threshold to allow the use of a simple RC time constant to control the display intensity. This has been shown in Figure 1.

Invert Input

The Invert Input is used to invert the state of the outputs, if required. With a logic 0 level on this input, the logic level of the outputs is the same as the data clocked into the 32-bit shift register. A logic 1 level on the Invert Input causes all outputs to invert.

This input may also be used when driving liquid crystal displays, as shown in Figure 5.

Data Output

The Data Out signal is a buffered output driven by element 32 of the shift register. It is of the same polarity as this last register bit and may be used to drive the Data Input of another S2809. In this manner, S2809 circuits may be cascaded to drive additional display digits.

Table 1. Logic Truth Table

DATA IN	CLOCK	CHIP SELECT	BLANK	INVERT	Q1	QN	DRIVER OUTPUT
X	X	0	0	0			0
X	X	0	0	1		NO CHANGE	1
X	X	0	1	0			QN
Z	X	0	1	1			$\overline{QN}$
0	$\underline{\Gamma}$	1	X	0	0	QN − 1 → QN	0
1	$\underline{\Gamma}$	1	X	0	1	QN − 1 → QN	0
0	$\underline{\Gamma}$	1	X	1	0	QN − 1 → QN	0
1	$\underline{\Gamma}$	1	X	1	1	QN − 1 → QN	0

Figure 1. Typical Display Intensity Control
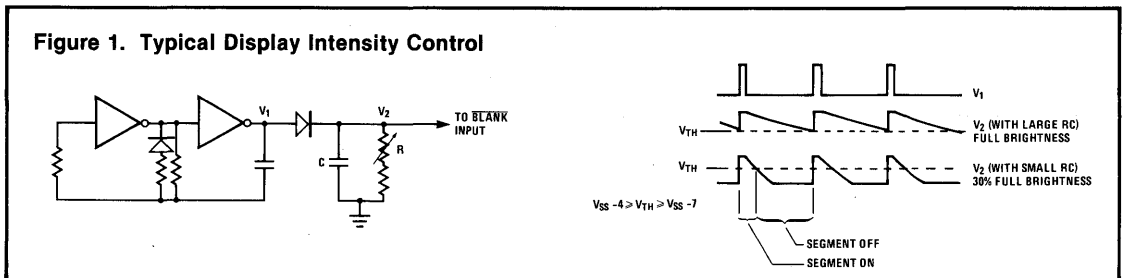
Figure 2. LED Drive — Series
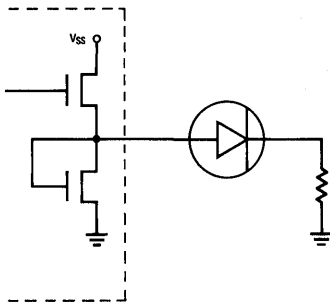
Figure 3. LED Drive — Shunt
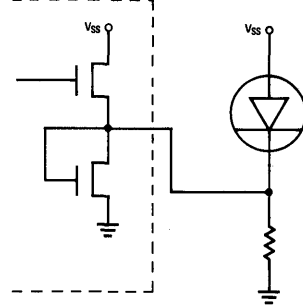
Figure 4. Vacuum Fluorescent Drive
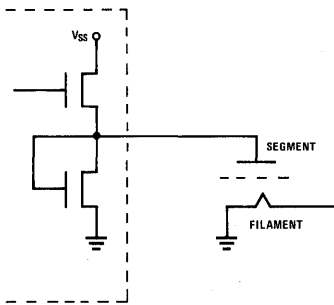
Figure 5. Liquid Crystal Drive
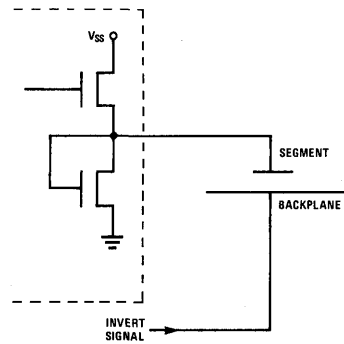
Figure 6. Clock Input Waveform

AMI

AMERICAN MICROSYSTEMS, INC.

ANALOG
SHIFT REGISTER

CONSUMER
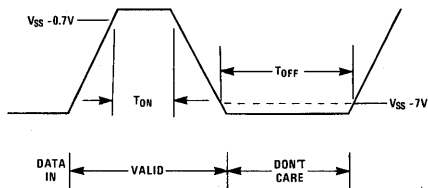
Features

☐ 185 Stage "Bucket Brigade" Delay Line

☐ Delays Audio Signals

☐ Accepts Clock Inputs up to 500 kHz

☐ Variable Delay

☐ Alternate to TCA 350

General Description

The S10110 analog shift register is a monolithic circuit fabricated with P-channel ion-implanted MOS technology. The part differs from a digital shift register, which is capable of only digital input and output information, in that an audio signal is typically supplied as the data input to the analog register, and the output is the same audio signal delayed in time. The amount of signal delay is dependent on the number of bits of delay (185) and the frequency of the two symmetrical clock inputs. Since each negative-going clock edge transfers data from one stage to the next, the analog signal delay equals $185 \div 2 \times$ clock frequency.

Block Diagram
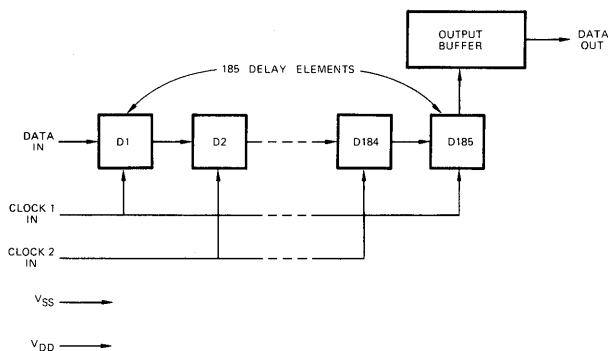
277181

Pin/Package Configuration
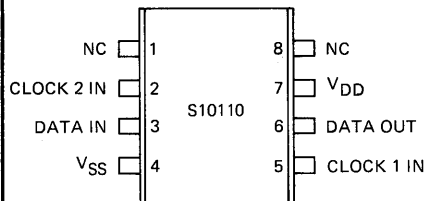
277182
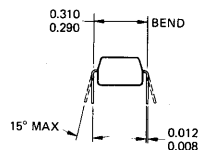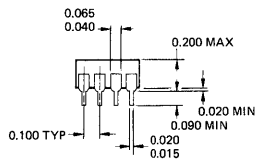
57639

Operation

Device operation may be understood by referring to Figure 1. This is an actual schematic diagram of the analog shift register, or "bucket brigade," showing typical external bias techniques.

Data In Input:

The analog signal, or audio signal, to be delayed is applied to pin 3. This input must be biased to a negative voltage of approximately -8 volts, and two resistors may be used as a voltage divider to provide this bias. They must be chosen so that $(R_1) \pm (R_2) \div (R_1 + R_2)$ is less than 20 KΩ. The input signal applied to this input through series capacitor C_{IN} may be as high as 6 volts peak to peak.

Clock 1 and Clock 2 Inputs:

Applied respectively to pins 5 and 2, Clock 1 and Clock 2 are two symmetrical non-overlaping negative-going clocks used to transfer the analog data along the 185 bit delay line. Although these clocks may have a duty cycle as low as 25% (i.e.: each clock signal is at a negative level for 25% of its period), better output signals will be obtained with both clock duty cycles closer to 50%. It is important, however, that no overlap of the clock signals occurs at a level more negative than $V_{SS} - 0.8$ volts.

Referring again to Figure 1, it can be seen that when Clock 1 is negative, data is transferred from the data input to capacitor C1; likewise, data is transferred from each even-numbered capacitor to the capacitor to its right. When Clock 2 is negative, data is transferred from C1 to C2 and from each other odd-numbered capacitor to the capacitor to its right. In this manner, data is shifted from the input to C185 after a total of 185 negative clock pulses has occurred (i.e.: 93 periods of Clock 1 and 92 periods of Clock 2).

Data Out Output:

The output of the S10110 analog shift register is a single device, T187, with its drain at V_{DD} and its source connected to pin 6. If a 47K resistor to V_{SS} is supplied at this pin, T187 functions as a source follower.

Referring to Figure 3, it can be seen that the output potential during Clock 2 is a constant value near -10 volts. When Clock 1 switches on (negative), the output instantaneously drops to a level of approximately -30 volts; this is caused by the 20 volt swing of Clock 1 and C185. As Clock 1 remains on, device T185 transfers charge from C184 to C185, and the output voltage becomes more positive, depending on the charge previously stored on C184. It is during this part of Clock 1 that the output reflects the analog data stored on C1 185 bits earlier. Since the clock signal now appears on the output, it is necessary to apply the appropriate filtering to obtain the delayed analog signal.

Figure 1. Schematic Diagram and Pinouts of S10110

277183
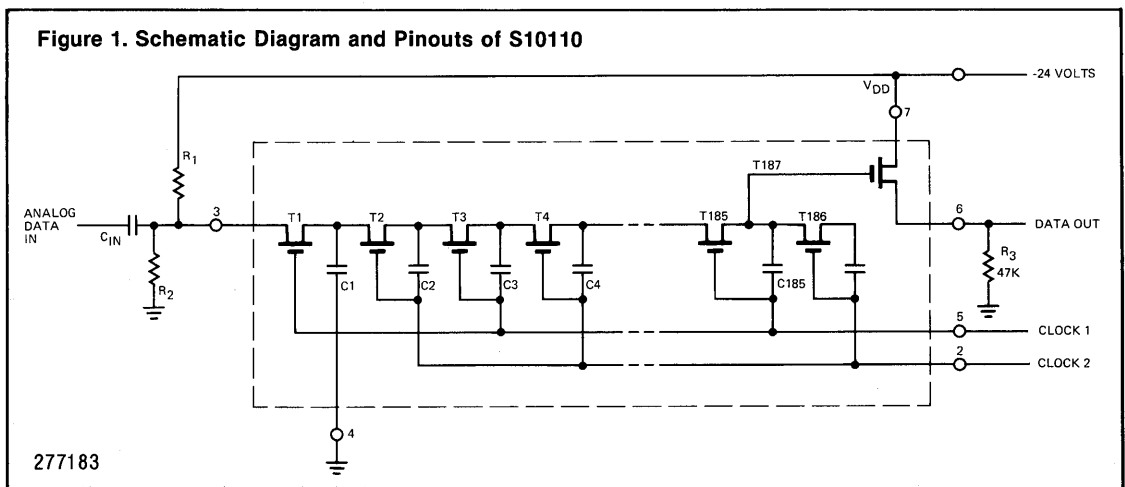
Applications

☐ Delay of Audio Signals
☐ Rotating Speaker Simulation
☐ Electronic Chorus
☐ Electronic Vibrato
☐ String Ensemble
☐ Reverberation

Absolute Maximum Ratings

Voltage on any pin relative to V_{SS}: +0.3V to −30V
Operating temperature range: 0°C to + 70°C
Storage temperature (ambient):   −65°C to +150°C

CONSUMER

Electrical Characteristics

$(0°C < T_A < 70°C; V_{DD} = −24V ± 2V; V_{SS} = OV.)$

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{CLK_L}	CLOCK 1 and CLOCK 2 Inputs Logic Level "0"	V_{SS}		V_{SS} −0.8	Volts	No overlap of signals more negative than V_{SS} - 0.8V
V_{CLK_H}	CLOCK 1 and CLOCK 2 Inputs Logic Level "1"	−18		−20	Volts	See Figure 2
$tCLK_H$	Duration of CLOCK Logic "1" Level	$0.2 \times T_{CLK}$				See Figure 2
f_{CLK}	CLOCK Input Frequency	5		500	kHz	
V_{BIN}	Input Bias Voltage	−7.5		−8.5	Volts	See Figure 1
R_{BIN}	Resistance of the Bias Voltage Source at Input			20	KΩ	$R_{BIN} = (R1) \times (R2) \div (R1 + R2)$ See Figure 1
V_{DIN}	Signal Level at Data In Input			6	Volts P–P	
a	Analog Signal Attenuation			4	dB	
t_D	Signal Delay		$\dfrac{185}{2 \times f_{CLK}}$			
f_{3dB}	3dB Response Point		$0.1 \times f_{CLK}$			

Figure 2. Timing Diagram of Clock 1 and Clock 2 Signals
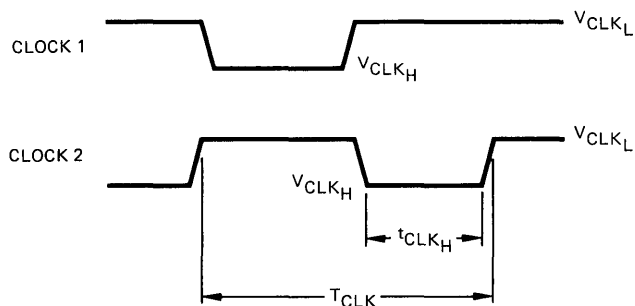
277184

Figure 3. S10110 Output Waveform
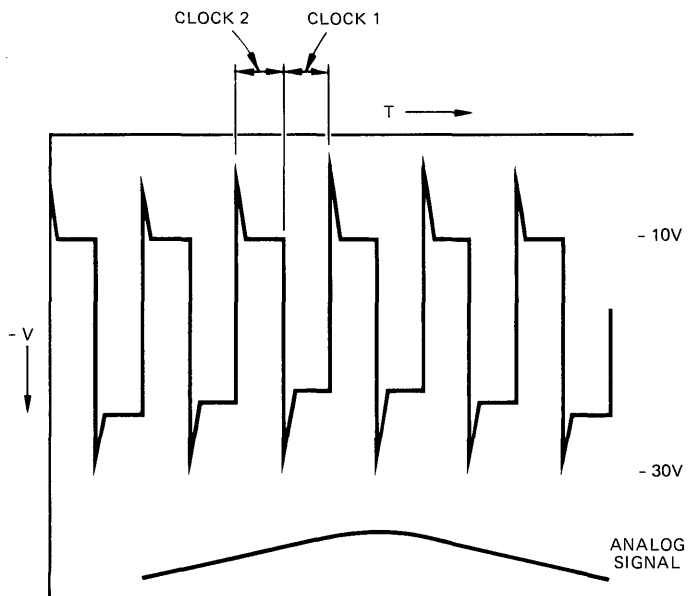
277185

ANALOG
SHIFT REGISTER

Features

☐ 185 Stage "Bucket Brigade" Delay Line
☐ Delays Analog Signals
☐ Single Phase TTL Compatible Clock Input
☐ Accepts Clock Inputs up to 500KHz
☐ Variable Delay

Typical Applications

☐ Delay of Audio Signals
☐ Electronic Chorus
☐ Electronic Vibrato
☐ Reverberation
☐ String Ensemble
☐ Rotating Speaker Simulation
☐ Delay of Analog Signals
☐ Musical Phasing Effects

General Description

The S10111 analog shift register is a monolithic circuit fabricated with P-channel ion-implanted MOS technology. The part differs from a digital shift register, which is capable of only digital input and output information, in that an analog signal is typically supplied as the data input to the register. The register's output is that analog signal delayed in time. Because the two phase driver required to clock this shift register is integrated onto this circuit, the part can be easily driven by a single-phase low capacitance TTL compatible clock signal. Because each level transition of the clock input transfers data to a successive delay element, the amount of delay is equal to the number of delay elements (185) multiplied by half the clock period.
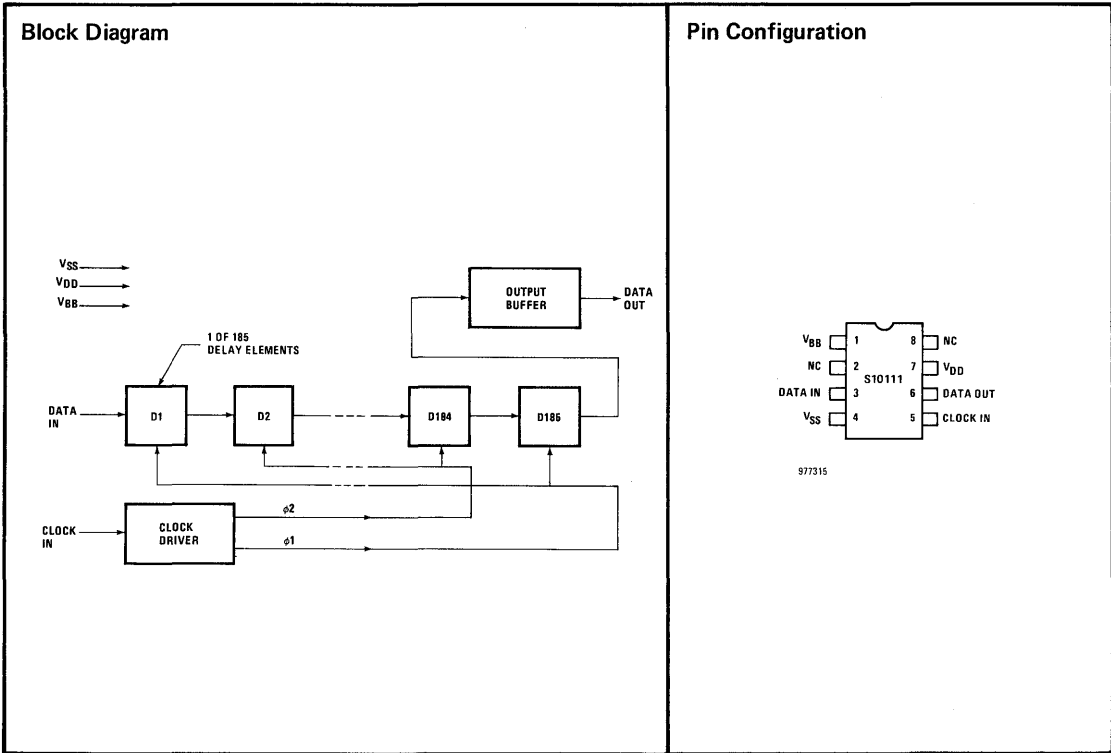
Block Diagram

Pin Configuration

AMI.

Absolute Maximum Ratings

Voltage on any pin relative to V_{SS}: . . . . +0.3V to –30V

Operating temperature range: . . . . 0°C to +70°C

Storage temperature (ambient): . . . . –65°C to +150°C

Electrical Characteristics

$(-20°C < T_A < 60°C; V_{DD} = -24V \pm 2V; V_{SS} = 0V; V_{BB} = +10V \pm 7V)$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{CLK_L}	CLOCK Input Logic Level "0"	V_{SS}		V_{SS} –0.8	Volts	
V_{CLK_H}	CLOCK Input Logic Level "1"	–4.0		–20	Volts	
t_{CLK_H}	Duration of CLOCK Logic "1" Level	48		52	% of Clock Period	
f_{CLK}	CLOCK Input Frequency	5		500	kHz	
V_{BIN}	Input Bias Voltage	–7.5		–8.5	Volts	
R_{BIN}	Resistance of the Bias Voltage Source at Input			20	KΩ	$R_{BIN} = (R1) \times (R2) \div (R1+R2)$ See Figure 2
V_{DIN}	Signal Level at Data In Input			6	Volts P–P	
a	Analog Signal Attenuation			4	dB	
t_D	Signal Delay		$\dfrac{185}{2xf_{CLK}}$			
f_{3dB}	3dB Response Point		$0.1xf_{CLK}$			

Figure 1. Schematic Diagram

977318

CONSUMER

Functional Description

Device operation may be understood by referring to Figure 1, a schematic diagram of the S10111 analog shift register. A suggested connection diagram for the part is shown (Figure 2) along with typical output waveforms (Figure 3).

Data In Input: The analog signal to be delayed is applied to pin 3. This input must be biased to a negative voltage of V_{BIN}, which may be accomplished by a simple resistive divider network. The input peak-to-peak signal level may be as high as V_{DIN}.

Clock Input: The Clock input, pin 5, is used to transfer the analog data from each delay element to the subsequent stage. Because the two-phase clock divider required to operate the delay line is integrated on the circuit, it is not necessary to generate a two-phase clock externally. The single-phase clock is a high impedance input and may be driven with either MOS or TTL voltage levels.

Referring to Figure 1, it can be seen that when the clock input is negative (i.e., $\phi 1$ is negative), data is

transferred from the data input to capacitor C1; likewise, data is transferred from each even-numbered capacitor to the odd-numbered capacitor to its right. When the clock input is positive (and, hence $\phi 2$ is negative), data is transferred from C1 to C2 and from each other odd-numbered capacitor to the capacitor to its right. In this manner, data is shifted from the input to C185 after a total of 185 half periods of the clock input.

Data Out Output: The output stage of the S10111 analog shift register is a single device, T187, with its drain at V_{DD} and source connected to pin 6. Connecting a 47K resistor between the output and V_{SS} causes T187 to function as a source follower.

Typical output waveforms are shown in Figure 3. It is during the negative portion of the clock input that the data on the output reflects the analog information that was present at the data input. Because the clock signal now appears on the output, it is necessary to apply the appropriate filtering to obtain the delayed analog signal.

Figure 2.
Typical External Biasing Method
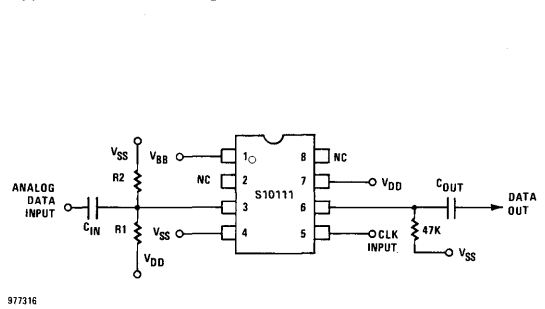
977316

Figure 3.
Typical Output Waveforms (device connected as in Figure 2)

977317
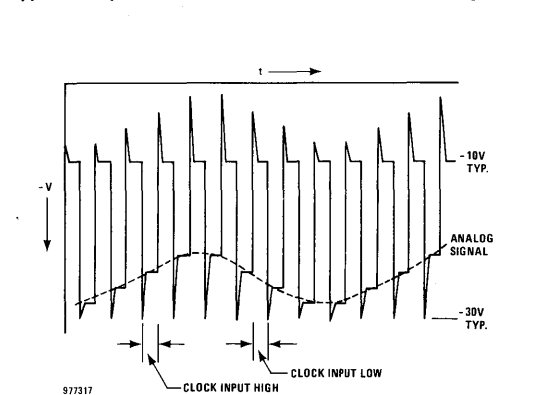
SEVEN STAGE FREQUENCY DIVIDER

Features

☐ **Contains Seven Binary Dividers**

☐ **Triggers on Negative-Going Edge**

☐ **High Impedance Inputs**

☐ **Schmidt Trigger on Inputs**

☐ **No Minimum Input Rise or Fall Time Requirements**

☐ **Low Impedance Push-Pull Outputs**

☐ **Low Power Dissipation**

☐ **Resettable**

Applications

Electronic organ frequency generator, organ pedal frequency generator, electronic music synthesizers, N stage dividers, low frequency generation, binary counters.

General Description

The S10129 is a monolithic frequency divider circuit fabricated with P-Channel ion-implanted MOS technology. The circuit provides seven stages of binary division in a 3-2-1-1 configuration; the S10129 is ideally suited for tone generation in electronic organs.

All inputs to the device are buffered to permit easy triggering of the divider stages. Outputs of each divider are buffered to provide low output impedance in both logic states to drive external circuitry as well as other dividers. The buffers have low standby current and are powered by V_{DD}. This voltage functions as a clamp voltage and thus sets the output amplitudes. Buffering the outputs also provides complete isolation between the dividers and the loads. If a buffer output is short-circuited, the divider will continue to function.

All divider outputs may be reset to a logic low level (V_{SS}) by momentarily applying a logic low level to the V_{GG} supply input. This is particularly desirable in some electronic organs in which phase relationships are important.

Block Diagram

Pin Configuration

Absolute Maximum Ratings

Voltage on Any Pin Relative to V_{SS} .... $+ 0.3V$ to $- 20V$
Voltage on V_{GG} Relative to V_{SS} .... $+ 0.3V$ to $- 30V$
Storage Temperature .... $- 55°C$ to $+ 150°C$
Operating Temperature (ambient) .... $0°C$ to $+ 70°C$

Electrical Characteristics $(0°C \leq T_A \leq 70°C; V_{DD} = - 11V$ to $- 16V; V_{GG} = - 25V$ to $- 29V$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
V_{IL}	Input Clock Low	$V_{SS} + 0.3$		$V_{SS} - 2.0$	V	
V_{IH}	Input Clock High	$V_{SS} - 8$		V_{GG}	V	
f_{IN}	Input Clock Frequency	DC		250	kHz	
T_H, T_L	Input Clock On and Off Times	1.5			μs	
V_R	Voltage Applied to V_{GG} Input to Cause a Reset Condition	V_{SS}		$V_{SS} - 0.5$	V	
T_R	Duration of V_R to Cause Reset	10			μs	50% to 50% point
V_{OH}	Output High Level	$- 11$		V_{DD}	V	$V_{DD} = - 12V$ $V_{GG} = - 26V$ 5.5KΩ load to V_{SS}
V_{OL}	Output Low Level	V_{SS}		$- 1$	V	$V_{DD} = - 12V$ $V_{GG} = - 26V$ 5.5KΩ load to V_{DD}
C_{IN}	Input Capacitance		5	10	pF	Applies to clock inputs
T_{OR}, T_{OF}	Output Rise and Fall Time		1	2	μs	40pF load applied
I_{GG}	V_{GG} Supply Current		2	3	mA	$V_{DD} = - 12V$ $V_{GG} = - 26V$ No load
I_{DD}	V_{DD} Supply Current		5	7	mA	$V_{DD} = - 12V$ $V_{CC} = - 26V$ No load

Timing Characteristics

Physical Dimensions
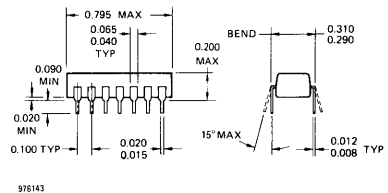
AMERICAN MICROSYSTEMS, INC.

SIX STAGE FREQUENCY DIVIDER

Features

☐ **Contains Six Binary Dividers**

☐ **Triggers on Negative-Going Edge**

☐ **High Impedance Inputs**

☐ **Schmidt Trigger on Inputs**

☐ **No Minimum Input Rise or Fall Time Requirements**

☐ **Low Impedance Push-Pull Outputs**

☐ **Low Power Dissipation**

☐ **Resettable**

Applications

Electronic organ frequency generator, organ pedal frequency generator, electronic music synthesizers, N stage dividers, low frequency generation, binary counters.

General Description

The S10130 is a monolithic frequency divider circuit fabricated with P-Channel ion-implanted MOS technology. The circuit provides six stages of binary division in a 3-2-1 configuration; the S10130 is ideally suited for tone generation in electronic organs.

All inputs to the device are buffered to permit easy triggering of the divider stages. Outputs of each divider are buffered to provide low output impedance in both logic states to drive external circuitry as well as other dividers. The buffers have low standby current and are powered by V_{DD}. This voltage functions as a clamp voltage and thus sets the output amplitudes. Buffering the outputs also provides complete isolation between the dividers and the loads. If a buffer output is short-circuited, the divider will continue to function.

All divider outputs may be reset to a logic low level (V_{SS}) by momentarily applying a logic low level to the V_{GG} supply input. This is particularly desirable in some electronic organs in which phase relationships are important.

Block Diagram

Pin Configuration

AMI®

CONSUMER

Absolute Maximum Ratings

Voltage on Any Pin Relative to V_{SS} .... + 0.3V to − 20V
Voltage on V_{GG} Relative to V_{SS} .... + 0.3V to − 30V
Storage Temperature .... − 55°C to + 150°C
Operating Temperature (ambient) .... 0°C to + 70°C

Electrical Characteristics $(0°C \leq T_A \leq 70°C; V_{DD} = − 11V$ to $− 16V; V_{GG} = − 25V$ to $− 29V$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
V_{IL}	Input Clock Low	$V_{SS} + 0.3$		$V_{SS} − 2.0$	V	
V_{IH}	Input Clock High	$V_{SS} − 8$		V_{GG}	V	
f_{IN}	Input Clock Frequency	DC		250	kHz	
T_H, T_L	Input Clock On and Off Times	1.5			μs	
V_R	Voltage Applied to V_{GG} Input to Cause a Reset Condition	V_{SS}		$V_{SS} − 0.5$	V	
T_R	Duration of V_R to Cause Reset	10			μs	50% to 50% point
V_{OH}	Output High Level	− 11		V_{DD}	V	$V_{DD} = − 12V$ $V_{GG} = − 26V$ 5.5KΩ load to V_{SS}
V_{OL}	Output Low Level	V_{SS}		− 1	V	$V_{DD} = − 12V$ $V_{GG} = − 26V$ 5.5KΩ load to V_{DD}
C_{IN}	Input Capacitance		5	10	pF	Applies to clock inputs
T_{OR}, T_{OF}	Output Rise and Fall Time		1	2	μs	40pF load applied
I_{GG}	V_{GG} Supply Current		2	3	mA	$V_{DD} = − 12V$ $V_{GG} = − 26V$ No load
I_{DD}	V_{DD} Supply Current		5	7	mA	$V_{DD} = − 12V$ $V_{CC} = − 26V$ No load

Timing Characteristics

976139

Physical Dimensions

976143

SIX STAGE FREQUENCY
DIVIDER

Features

☐ **Contains Six Binary Dividers**

☐ **Triggers on Negative-Going Edge**

☐ **High Impedance Inputs**

☐ **Schmidt Trigger on Inputs**

☐ **No Minimum Input Rise or Fall Time Requirements**

☐ **Low Impedance Push-Pull Outputs**

☐ **Low Power Dissipation**

☐ **Resettable**

Applications

Electronic organ frequency generator, organ pedal frequency generator, electronic music synthesizers, N stage dividers, low frequency generation, binary counters.

General Description

The S10131 is a monolithic frequency divider circuit fabricated with P-Channel ion-implanted MOS technology. The circuit provides six stages of binary division in a 2-2-1-1 configuration; the S10131 is ideally suited for tone generation in electronic organs.

All inputs to the device are buffered to permit easy triggering of the divider stages. Outputs of each divider are buffered to provide low output impedance in both logic states to drive external circuitry as well as other dividers. The buffers have low standby current and are powered by V_{DD}. This voltage functions as a clamp voltage and thus sets the output amplitudes. Buffering the outputs also provides complete isolation between the dividers and the loads. If a buffer output is short-circuited, the divider will continue to function.

All divider outputs may be reset to a logic low level (V_{SS}) by momentarily applying a logic low level to the V_{GG} supply input. This is particularly desirable in some electronic organs in which phase relationships are important.

Block Diagram

Pin Configuration

CONSUMER

Absolute Maximum Ratings

Voltage on Any Pin Relative to V_{SS} .... $+0.3V$ to $-20V$

Voltage on V_{GG} Relative to V_{SS} .... $+0.3V$ to $-30V$

Storage Temperature .... $-55°C$ to $+150°C$

Operating Temperature (ambient) .... $0°C$ to $+70°C$

Electrical Characteristics $(0°C \leq T_A \leq 70°C; V_{DD} = -11V$ to $-16V; V_{GG} = -25V$ to $-29V$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
V_{IL}	Input Clock Low	$V_{SS} + 0.3$		$V_{SS} - 2.0$	V	
V_{IH}	Input Clock High	$V_{SS} - 8$		V_{GG}	V	
f_{IN}	Input Clock Frequency	DC		250	kHz	
T_H, T_L	Input Clock On and Off Times	1.5			μs	
V_R	Voltage Applied to V_{GG} Input to Cause a Reset Condition	V_{SS}		$V_{SS} - 0.5$	V	
T_R	Duration of V_R to Cause Reset	10			μs	50% to 50% point
V_{OH}	Output High Level	-11		V_{DD}	V	$V_{DD} = -12V$ $V_{GG} = -26V$ 5.5KΩ load to V_{SS}
V_{OL}	Output Low Level	V_{SS}		-1	V	$V_{DD} = -12V$ $V_{GG} = -26V$ 5.5KΩ load to V_{DD}
C_{IN}	Input Capacitance		5	10	pF	Applies to clock inputs
T_{OR}, T_{OF}	Output Rise and Fall Time		1	2	μs	40pF load applied
I_{GG}	V_{GG} Supply Current		2	3	mA	$V_{DD} = -12V$ $V_{GG} = -26V$ No load
I_{DD}	V_{DD} Supply Current		5	7	mA	$V_{DD} = -12V$ $V_{CC} = -26V$ No load

Timing Characteristics

976139

Physical Dimensions

976143

AMI
AMERICAN MICROSYSTEMS, INC.

ANALOG
SHIFT REGISTER

Features

☐ 186 Stage "Bucket Brigade" Delay Line
☐ Delays Analog Signals
☐ Noise Cancellation Output
☐ Accepts Clock Inputs Up to 500KHz
☐ Variable Delay

Typical Applications

☐ Delay of Audio Signals
☐ Electronic Chorus
☐ Electronic Vibrato
☐ String Ensemble
☐ Rotating Speaker Simulation
☐ Delay of Analog Signals
☐ Musical Phasing Effects

General Description

The S10377 analog shift register is a monolithic circuit fabricated with P-Channel ion-implanted MOS technology. The part differs from a digital shift register, which is capable of only digital input and output information, in that an analog signal is typically supplied as the data input to the register. The register's output is that analog signal delayed in time. To enable cancellation of the clock signal from the analog output, two outputs of opposite phase are provided. Because each level transition of the clock input transfers data to a successive delay element, the amount of delay is equal to the number of delay elements (186) multiplied by half the clock frequency.

Block Diagram
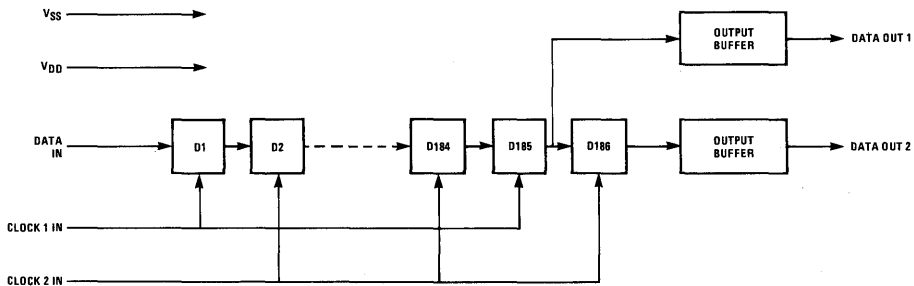
Pin Configuration
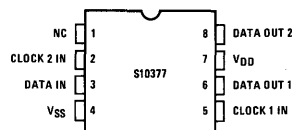
Figure 1. Schematic Diagram
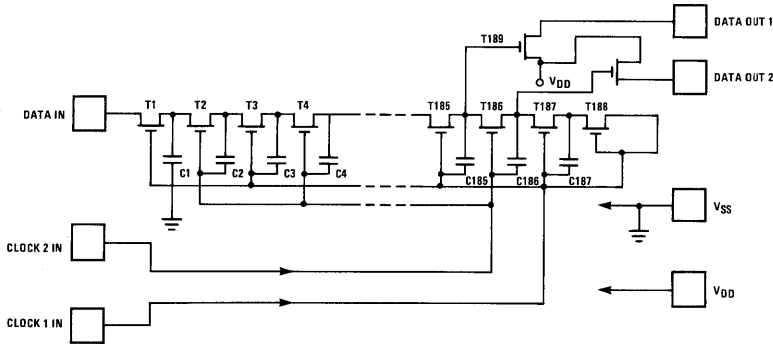
Functional Description

Device operation may be understood by referring to Figure 1. This is an actual schematic diagram of the analog shift register, or "bucket brigade."

Data In Input

The analog, or audio, signal to be delayed is applied to pin 3. This input must be biased to a negative voltage of approximately − 8 volts, and two resistors may be used as a voltage divider to provide this bias. They must be chosen so that (R1) x (R2) ÷ (R1 + R2) is less than 20kΩ. The signal applied to this input through series capacitor C_{IN} may be as high as 6 volts peak to peak. A typical input biasing circuit is shown in Figure 2.

Clock 1 and Clock 2 Inputs

Applied respectively to pins 5 and 2, Clock 1 and Clock 2 are two symmetrical non-overlapping negative-going clocks used to transfer the analog data along the 186-bit delay line. Although these clocks may have a duty cycle as low as 25% (i.e., each clock signal is at a negative level for 25% of its period), better output signals will be obtained with both clock duty cycles closer to 50%. It is important, however, that no overlap of the clock signals occurs at a level more negative than V_{SS} − 0.8 volts.

Referring again to Figure 1, it can be seen that when Clock 1 is negative, data is transferred from the data input to capacitor C1; likewise, data is transferred from each even-numbered capacitor to the capacitor to its right. When Clock 2 is negative, data is transferred from C1 to C2 and from each other odd-numbered capacitor to the capacitor to its right. In this manner, data is shifted from the input to C186 after a total of 186 negative clock pulses have occurred.

Data Out Outputs

Each output of the S10377 analog shift register is a single device with its drain at V_{DD} and its source connected to an output pin. If used separately, each output would provide the delayed analog waveform superimposed on a larger signal which is the clock frequency. This output would need to be low pass filtered to eliminate clock noise. However, since S10377 provides two output signals that are 180° out of phase, this undesirable clock noise can be cancelled by connecting the outputs as shown in Figure 2. Adjustment of the 5K ohm potentiometer balances the output, eliminating the need for excessive low pass filtering.

Absolute Maximum Ratings

Voltage on Any Pin Relative to V_{SS} .... +0.3V to −30V
Operating Temperature Range .... 0°C to +70°C
Ambient Storage Temperature .... −65°C to +150°C

Electrical Characteristics (T_A = 0°C to +70°C, V_{DD} = −24V ±2V; V_{SS} = 0V)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{CLK_L}	CLOCK 1 and CLOCK 2 Inputs, Logic Level "0"	V_{SS}		V_{SS} − 0.8	Volts	No overlap of signals more negative than V_{SS} − 0.8V
V_{CLK_H}	CLOCK 1 and CLOCK 2 Inputs, Logic Level "1"	−18		−20	Volts	See Figure 4
t_{CLK_H}	Duration of CLOCK Logic "1" Level	0.4X t_{CLK}				See Figure 4
f_{CLK}	CLOCK Input Frequency	20		500	kHz	
V_{BIN}	Input Bias Voltage	−7.5		−8.5	Volts	See Figure 1
R_{BIN}	Resistance of the Bias Voltage Source at Input			20	kΩ	R_{BIN} = (R1) x (R2) ÷ (R1 + R2), see Figure 1
V_{DIN}	Signal Level at Data In Input			6	Volts P − P	
a	Analog Signal Attenuation			4	dB	
t_D	Signal Delay		$\dfrac{185}{2 \times f_{CLK}}$			
F_{3dB}	3dB Response Point		$0.1 \times f_{CLK}$			Frequency whose amplitude is 3dB below maximum output amplitude.

Figure 2. Schematic Diagram of Typical Input Biasing and Output Configuration
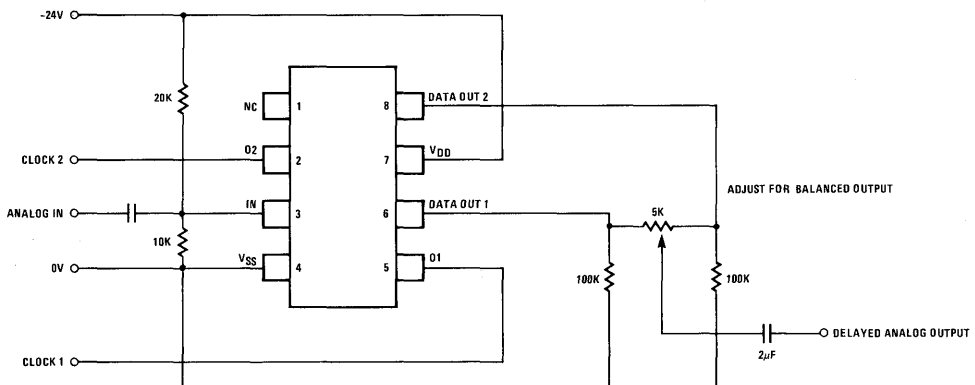
Figure 3. Schematic Diagram of Vibrato Oscillator, VCO, and Clock Drivers for S10377 Analog Delay Line
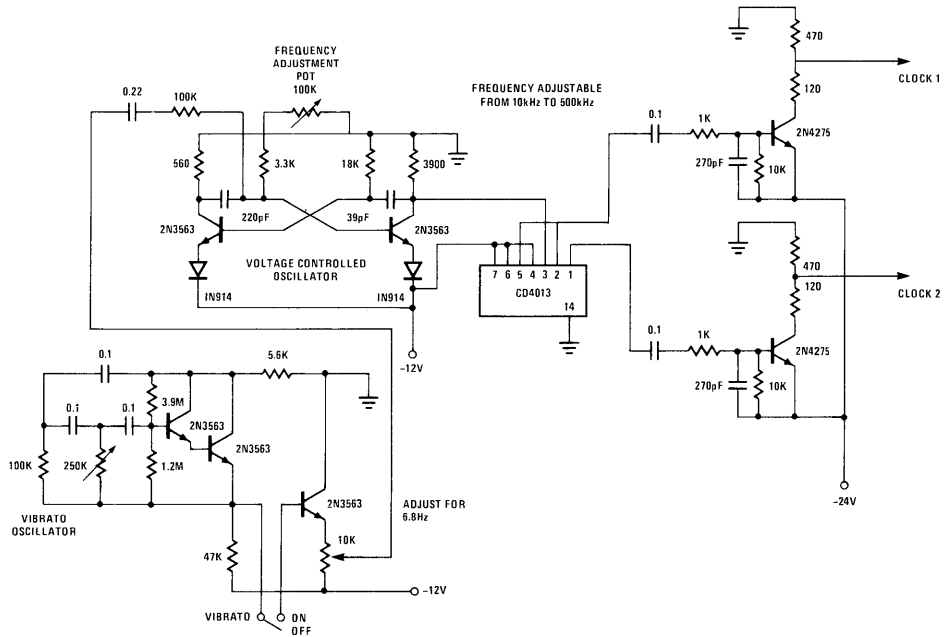
Figure 4. Timing Diagram of Clock 1 and Clock 2 Signals

S10430
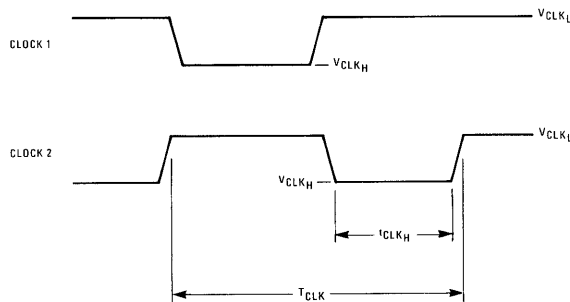
DIVIDER-KEYER

Features

☐ 22 Keyboard Inputs
☐ 88 DC Keyer Circuits
☐ 34 Binary Dividers
☐ Provides Four Pitch Outputs
☐ All Key Inputs Sustainable for Percussion
☐ All Dividers Resettable
☐ Provides "Any Key Down" Indication
☐ Eliminates Multiple-Contact Key Switches

Typical Applications

☐ Generation and Keying of Musical Tones
☐ Standard Spinet Organ Keying (37 or 44 note keyboards)
☐ Keying of Sustained Tones
☐ Percussive Effects
☐ Generating Stair-stepped Waveforms
☐ Electronic Piano

General Description

The S10430 divider-keyer is a monolithic integrated circuit fabricated with P-Channel ion-implanted MOS technology. It is intended for use in spinet organs or other electronic musical instruments having keyboards of up to 44 keys. This device has 22 key inputs, allowing all keying functions for a 44 note manual to be performed by two S10430 circuits. Each S10430 accepts six frequencies from a top octave synthesizer, such as an S50240, and provides squarewave outputs at 16 foot, 8 foot, 4 foot, and 2 foot pitches. For example, if a C key is depressed by itself a low C frequency appears at the 16 foot output, and a C frequency one octave higher appears at the 8 foot output; similarly, the 4 foot and 2 foot outputs provide C frequencies one and two octaves higher, respectively, than the C frequency of the 8 foot output. All appropriate frequency division is performed by the S10430, eliminating the need for external dividers.

Block Diagram

Pin Configuration
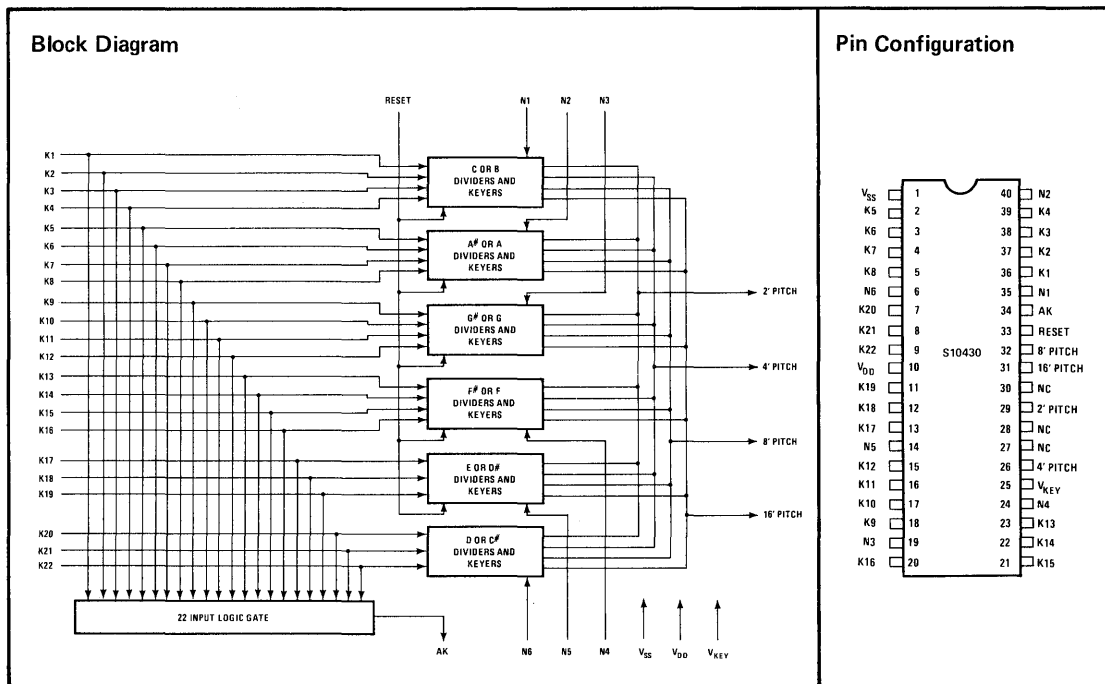
General Description (Continued)

The circuit also eliminates the need for multiple-contact key switches and discrete diode or transistor keyers. Because of the high input impedance of the MOS keyers used in this circuit, long sustain envelopes may be obtained by connecting low-value capacitors to the keying inputs.

Absolute Maximum Ratings

Voltage on any pin relative to V_{SS} .... +0.3V to - 27.0V
Operating temperature (ambient) .... 0°C to 70°C
Storage temperature .... - 65°C to 150°C

Electrical Characteristics

$0°C \leqslant T_A \leqslant 70°C$; $V_{SS} = 0V$; $V_{DD} = -12.6V$ to $-15.4V$; $V_{KEY} = -4.75V$ to $-5.25V$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{IL}	Logic Low Level TOS and Reset Inputs	0.0		0.8	V	
V_{IH}	Logic High Level TOS and Reset Inputs	-4.2		V_{DD}	V	
t_r, t_f	Rise and Fall Times TOS Inputs			50	μsec	Measured between 10% and 90% points
V_{OL}	Logic Low Level AK Output		-0.5	-1.0	V	100KΩ load to V_{DD}
t_{fo}	Transition of AK Output to 10% of V_{DD}			10	μs	100pF and 100KΩ load to V_{DD}
F_T	Operating Frequency TOS Inputs	DC		50K	Hz	
D_O	Output Duty Factor	48		52	%	Measured between 10% and 90% points
I_{PA}	Peak Output Current Absolute (any pitch output with 1 keyer on)	350		650	μA	$V_{DD} = -14V$ $V_{KEY} = -5V$ $V_{EN} = -25V$ $T_A = 25°C$
I_P	Peak Output Current	85		115	%I_{AVE}*	$V_{DD} = -14V$ $V_{KEY} = -5V$ $V_{EN} = -25V$ $T_A = 25°C$
I_P	Peak Output Current	50		75	%I_{AVE}*	$V_{DD} = -14V$ $V_{KEY} = -5V$ $V_{EN} = -15V$ $T_A = 25°C$

*I_{AVE} is the average of all peak output current values within one circuit.

Electrical Characteristics (Continued)

Symbol	Parameter		Typ.	Max.		Conditions
I_P	Peak Output Current	0.5			μA	$V_{DD} = -14V$ $V_{KEY} = -5V$ $V_{EN} = -3.0V$ $T_A = 25°C$
I_P	Peak Output Current			0.5	μA	$V_{DD} = -14V$ $V_{KEY} = -5V$ $V_{EN} = -1.0V$ $T_A = 25°C$

Functional Description

The S10430 Divider-Keyer circuit accepts six frequencies as inputs and uses these to clock six binary divider chains. Four of these chains consist of six binary dividers each and the remaining two have five. The six chains generate all frequencies necessary to obtain 2', 4', 8', and 16' pitches for half of a 44 key keyboard.

The outputs of the divider chains are routed to chopper keyer circuits like the one shown in Figure 2. When a negative voltage is applied to any "K" input, four of these keyer circuits are turned on to route the appropriate frequencies to each of the four pitch outputs.

Figure 1: Typical Time Constants For Sustain Keying

Figure 2: Schematic Diagram of Chopper Keyer Circuit
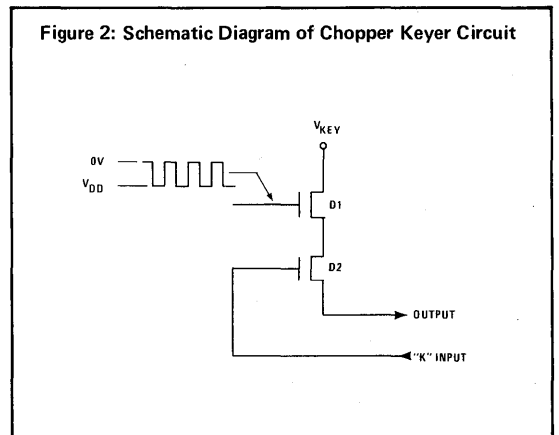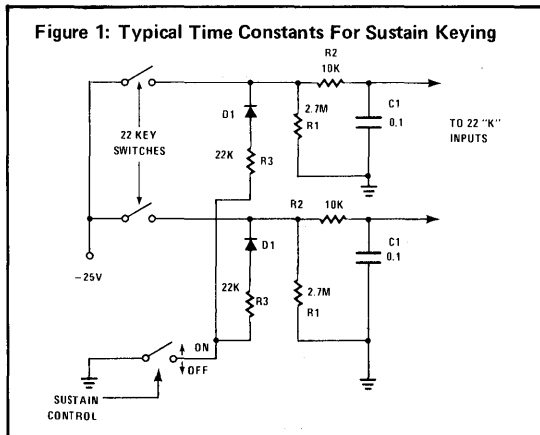
N Inputs

Six of the twelve tempered scale frequencies are applied to the inputs N1 through N6. Typically, these frequencies would be six of the outputs of a top octave synthesizer, such as an S50240. In general, it doesn't matter which frequencies are applied to the N inputs, although this affects which keyboard keys should be connected to the K inputs. One exception to this arises from the fact that a 44 note keyboard contains more of some keys than others. Specifically, there are only three each of the keys, C#, D, D#, and

E, but there are four each of the keys F, F#, G, G#, A, A#, B and C. This results in the requirement that each of the two S10430 divider keyers in a system take two frequencies from the first group, and four from the second group. Stating this another way, the N1, N2, N3, and N4 inputs must have frequencies chosen from the group, F, F#, G, G#, A, A#, B, and C. The N5 and N6 inputs are chosen from the group, C#, D, D#, and E. The example in Figure 4 shows one divider keyer handling the notes, A, A#, B, C, C#, and D while the other does the keying for D#, E, F, F#, G, and G#.

Table 1: Relationship between K and N Inputs

INPUT	PIN NO.	OUTPUT (8' PITCH)* PIN 32	INPUT	PIN NO.	OUTPUT (8' PITCH)* PIN 32
K1	36	N1 ÷ 4	K12	15	N3 ÷ 32
K2	37	N1 ÷ 8	K13	23	N4 ÷ 4
K3	38	N1 ÷ 16	K14	22	N4 ÷ 8
K4	39	N1 ÷ 32	K15	21	N4 ÷ 16
K5	2	N2 ÷ 4	K16	20	N4 ÷ 32
K6	3	N2 ÷ 8	K17	13	N5 ÷ 4
K7	4	N2 ÷ 16	K18	12	N5 ÷ 8
K8	5	N2 ÷ 32	K19	11	N5 ÷ 16
K9	18	N3 ÷ 4	K20	7	N6 ÷ 4
K10	17	N3 ÷ 8	K21	8	N6 ÷ 8
K11	16	N3 ÷ 16	K22	9	N6 ÷ 16

*To determine outputs for 4' pitch: multiply 8' pitch output by 2.
 To determine outputs for 2' pitch: multiply 8' pitch output by 4.
 To determine outputs for 16' pitch: divide 8' pitch output by 2.

K Inputs

The twenty-two inputs are connected either directly to key switches or to an attack/decay circuit, such as the one shown in Figure 1. When a negative voltage is applied to any K input, four chopper keyer circuits are turned on, and the appropriate frequencies appear at the four pitch outputs. The amount of current at the output is determined by the voltage at the K input. As the voltage becomes more negative, more current appears at the output. This will be discussed further in the section on "Pitch Outputs."

Connection of the K inputs to the key switches is dependent on which frequencies are applied to which N inputs. Table 1 shows the relationship between the K and N inputs. If, for example, the top octave frequency F, 5588 Hz, is applied to the N2 input, K5 should then be connected to the highest F key on the keyboard, K6 to the next highest, K7 to the next, and K8 to the lowest F. If the highest F key is depressed, then N2 ÷ 4, or 1397 Hz would appear at the 8' Pitch Output. At the same time, the 16' pitch, 4' pitch and 2' pitch outputs would provide, respectively, 699 Hz, 2794 Hz, and 5588 Hz. An example of K and N input connections is given in Figure 4.

To control attack, decay, and sustain times, a circuit such as the one shown in Figure 1 may be used. When a keyswitch is closed, the K input charges to – 25 volts through the time constant of R2 and C1. This causes the attack time to be about 1ms. If the sustain is on

(sustain switch open), when the keyswitch is opened, the K input will charge slowly back to V_{SS} through the time constant of C1, R1, and R2. This results in a sustain envelope of 271ms. Longer sustains can be obtained with larger capacitors. If the sustain switch is closed, then the decay time is governed by the time constant of C1, R2, and R3 ∥ R1. In this example, this non-sustain decay is about 3ms.

Pitch Outputs

The outputs labeled 2' pitch, 4' pitch, 8' pitch, and 16' pitch provide the appropriate frequencies for these four pitches depending on which K inputs have been selected. The selected frequencies of the outputs are shown in Table 1. The highest octave of frequencies is obtained directly from the N inputs. Although these top octave frequencies are buffered internally, their duty cycle depends on the duty cycle of the N inputs.

Each output is connected to the outputs of 22 of the chopper keyer circuits shown in Figure 2. The chopper device, D1 is much lower in impedance than the keyer device D2. The output voltage amplitude is dependent, therefore, on the ratio of D2 to the output load. Higher output sink resistor values result in higher output signal amplitudes. However, it is important to keep the output sink resistor low in order to minimize the effects of intermodulation distortion between keyers. Figure 3 shows a typical output waveform

with a 100Ω sink resistor. Because of the need for a low value sink resistor and the usual desirability of a high signal amplitude, it may be advisable in some cases to load the pitch outputs with operational amplifiers instead of resistors.

V_{KEY} Input

This supply input is used exclusively for the chopper keyer circuits (Figure 2). It is important that this be a low impedance supply in order to minimize inter-modulation distortion between keyer circuits.

The voltage on the supply is kept low relative to V_{DD} and the K inputs to insure linear operation of the MOS keying circuits.

Reset Input

Applying a V_{SS} level to this input causes all binary dividers to be held in the reset state. A logic 1 applied to Reset causes the dividers to function normally. To prevent possible phase cancellation between upper and lower manual systems, it is suggested that an RC network be connected to this input so that the musical instrument will be locked into proper phase relationships when power is first applied. When in the reset condition, all chopper devices are turned on to facilitate testing.

AK Output

Whenever any key input is selected, the AK output is actively pulled to V_{SS} to indicate that a key is played. This output is open ended (i.e., no pull-up device is provided), and may be left unconnected if not needed.

Figure 3. Typical Keyer Output
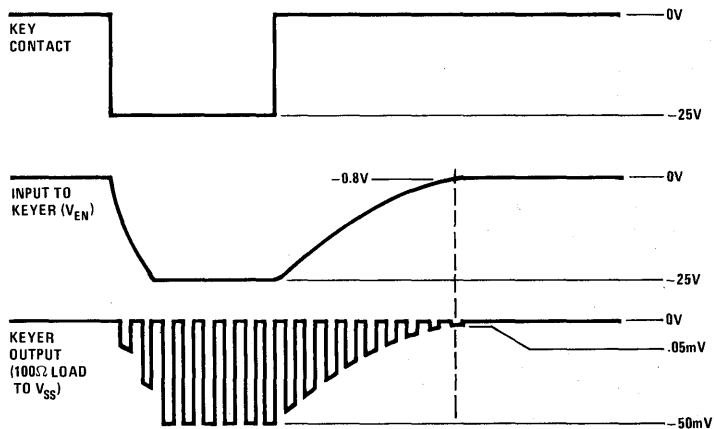
Figure 4. Schematic Diagram of Typical Divider — Keyer Application
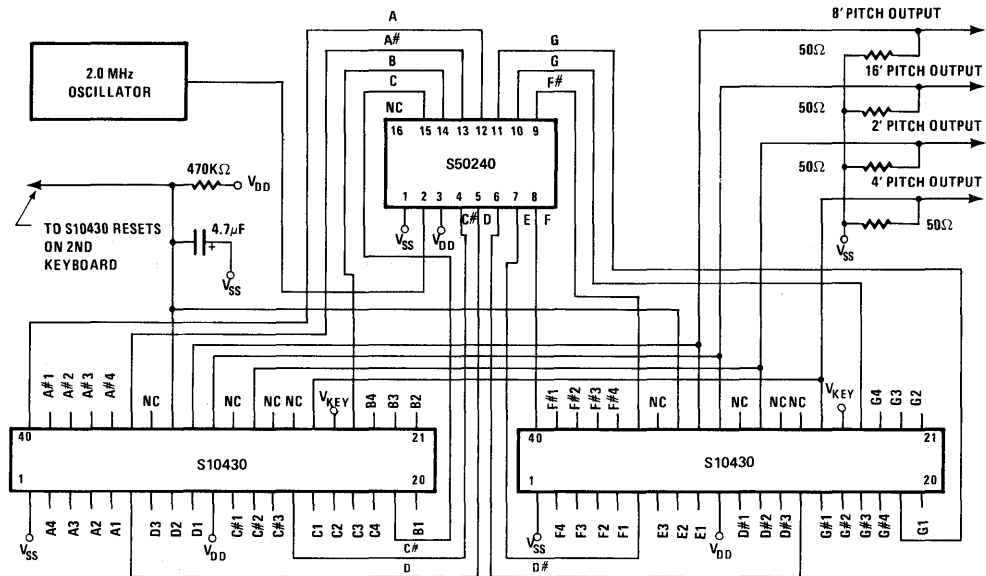
V_{SS} = 0
V_{DD} = -14 VOLTS
V_{KEY} = -5 VOLTS

NOTE: ON ALL K INPUTS, THE LETTER REFERS TO THE KEY NAME, AND THE NUMBER TO ITS LOCATION ON THE KEYBOARD. FOR EXAMPLE, F1 WOULD BE THE LOWEST KEY ON A 44 NOTE MANUAL, AND C4 WOULD BE THE HIGHEST.

AMI
AMERICAN MICROSYSTEMS, INC.

S2567

RESETTABLE
RHYTHM COUNTER

Features

☐ Pin for Pin Equivalent to GEM 567 and MC1181L

☐ Organ Rhythm Sections

☐ Portable Rhythm Sections

☐ Automatic Rhythm Organs

General Description

The S2567 Resettable Rhythm Counter is a six-stage asychronous binary counter designed for driving the count-address inputs of the S2566 Rhythm Generator. The internal partitioning and multiple-reset capability of the S2567 permit simultaneous generation of different meter rhythms. The S2567 Resettable Rhythm Counter is made by P-channel enhancement mode technology and is supplied in a 16-lead dual in-line package.

Block Diagram

Pin Configuration

V_{GC}	1	16	RESET 1B
INPUT 1B	2	15	Q1B
RESET 1A	3	14	Q1A
INPUT 1A	4	13	Q4 (4)
RESET 4	5	12	Q3 (4)
RESET 3	6	11	Q2 (4)
INPUT 4	7	10	Q1 (4)
V_{DD}	8	9	GND

S2567

Physical Dimensions

3.68
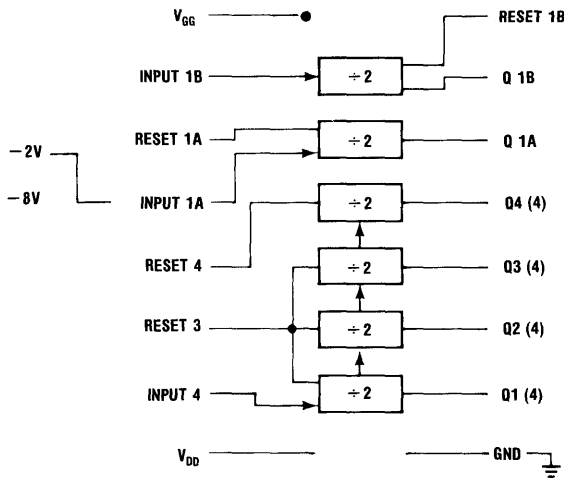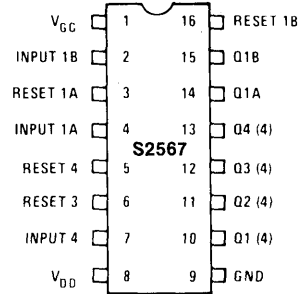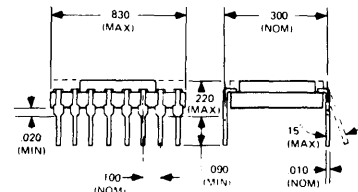
Absolute Maximum Ratings: @25°C, unless otherwise noted
Logic Supply Voltages:

V_{GG} .... +0.3V to −33V
V_{DD} .... +0.3V to −25V
V_I Trigger Voltage .... +0.3V to −18V
P_D Power Dissipation 250mW
T_S Storage Temperature .... −55°C to +100°C
T_A Operating Temperature .... −0°C to +60°C

Dynamic Characteristics: $T_A = −25$°C
Operating Voltage Ranges:

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{GG}		−25	−27	−29	V
V_{DD}		−14	−15	−16	V
Inputs: (Pins 2 thru 7, and 16)					
f_I	Input Frequency	DC		100	kHz
V_{IH}	Logic "0" Level	+0.3		−2.0	V
V_{IL}	Logic "1" Level	−8.0		−18	V
t_r, t_f	Rise and Fall Times			25	μs
PW_I	Pulse Width	2			μs
I_{IL}	Leakage Current ($V_{ILT} = −18$V)			1	μA
Outputs: (Pins 10 thru 15, each loaded 20K to GND and 20K to V_{DD})					
V_{OH}	Logic "0" Level	0		−1.5	V
V_{OL}	Logic "1" Level	−9.0		V_{DD}	V
Reset Propagation Delay				2.0	μA
Supply Currents: (no output loads)					
I_{GG}			4	6	mA
I_{DD}				20	μA

AMI

AMERICAN MICROSYSTEMS, INC.

S2688

DIGITAL
NOISE GENERATOR

Features

☐ Internal Oscillator

☐ Consistent Noise Quality

☐ Consistent Noise Amplitude

☐ Zero State Lockup Prevention

☐ Zeros Can Be Externally Forced Into The Register

☐ Oscillator Can Be Driven Externally

☐ Operates With Single or Dual Power Supplies

☐ Eliminates Noise Preamps

☐ Alternate to MM5837

General Description

The S2688 noise generator circuit is fabricated in P-Channel ion implanted MOS technology and supplied in an eight-lead dual in-line plastic package. The device contains a 17-bit shift register which is continuously clocked by an internal oscillator. Exclusive OR feed-back from the 14th and 17th stages causes the register to generate a pseudo-random noise pattern, and an internal gate is included to prevent the register from reaching an all zero lockup state. To facilitate testing, the device can be easily clocked by an external source.

Block Diagram
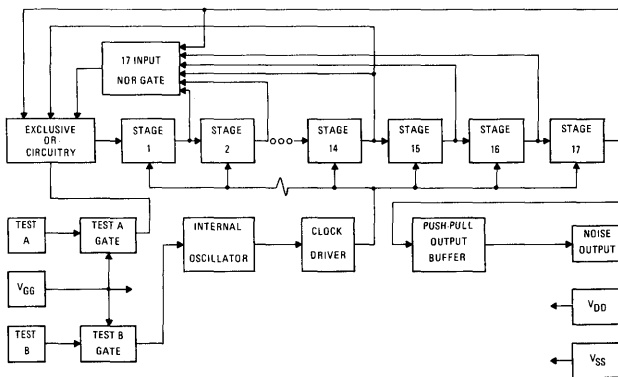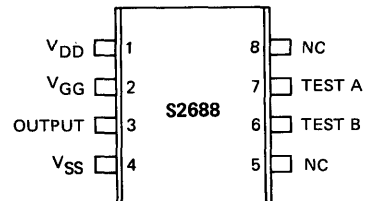
Pin Configuration

277182

3.70

Absolute Maximum Ratings

Positive Voltage on any Pin . . . . $V_{SS} + 0.3V$

Negative Voltage on any pin except V_{GG} . . . . $V_{SS} - 28V$

Negative Voltage on V_{GG} Supply Pin . . . . $V_{SS} - 33V$

Storage Temperature . . . . $-65°C$ to $+150°C$

Operating Ambient Temperature . . . . $0°C$ to $+70°C$

Electrical Specifications ($0°C < T_A < 70°C$; $V_{SS} = 0$ volts; $V_{DD} = -14.0V \pm 1.0V$; $V_{GG} = 27.0V \pm 2V$;
unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{OH}	Output Logic 1 Level	$V_{SS} - 1.5$		V_{SS}	Volts	$20K\Omega$ load to V_{DD}
V_{OL}	Output Logic 0 Level	V_{DD}		$V_{DD} + 1.5$	Volts	$20K\Omega$ load to V_{SS}
V_{OL}	Output Logic 0 Level	V_{DD}		$V_{DD} + 3.5$	Volts	$20K\Omega$ load to V_{SS} $V_{GG} = V_{DD} = -14V \pm 1.0V$
Z_{IN}	Input Impedance (Test Inputs)		10		pF	
I_L	Leakage Current (Test Inputs)			500	nA	
f_O	Frequency of Internal Oscillator		100		kHz	
I_{DD}	V_{DD} Supply Current			4.0	mA	No output load
I_{GG}	V_{GG} Supply Current			500	μA	
f_{TEST}	Test Frequency	80		105	kHz	

Operation

The S2688 is a 17-bit digital shift register driven by an internal oscillator circuit. Outputs from the 14th and 17th stages are connected to an Exclusive OR circuit whose output provides the data input for the register. The 17th stage of the register is connected to a push-pull buffer, which is the circuit's output. This output provides continuous constant amplitude pseudo-random noise; that is, for any time slot, ones and zeroes have an almost equal probability of occurrence.

Typical Applications

☐ Percussion Instrument Voice Generators for Rhythm Units

☐ Electronic Music Synthesizers

☐ Simulated Pipe "Wind" Noise

☐ Acoustics Testing

Power Supplies

The S2688 noise generator may be operated with either one or two power supplies. In applications where a high output drive level is not critical, or where the output is loaded with a resistive load connected to V_{DD}, it is possible to operate the device from a single supply voltage; in this case, the V_{GG} supply pin is connected to the V_{DD} supply voltage. If a low impedance logic "0" level output is required, this can be achieved by connecting the V_{GG} supply pin to a more negative voltage.

Zero State Lockup Prevention

If the outputs of all 17 stages of the shift register were simultaneously to reach a "0" logic level, and no logic were provided to prevent this state from occuring, then the register would remain in the "all-zero" state.

In this condition, the output would lockup and remain at a logic "0" level. This situation could occur when power is initially applied, or when triggered by noise spikes. To prevent this condition, a 17 input NOR gate is provided internally to decode the "all-zero" state and feed a logic "1" level into the register's data input.

Test Inputs

The S2688 has been designed to facilitate testing of the part. In the normal mode of operation, pins 6 and 7 are not used and appear to be open circuits. However, when the V_{GG} pin is connected to V_{SS}, these pins become test pins. Pin 7 (Test A) is used to force zeroes into the register, and pin 6 (Test B) becomes the clock input, driving the internal oscillator network. During the entire test period a 20KΩ load must be tied to V_{DD}.

Package Outline   8-Pin Plastic

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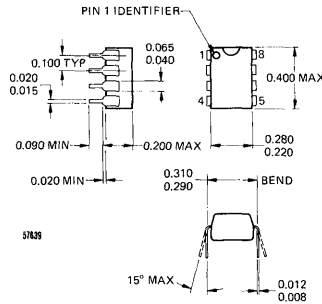
RHYTHM GENERATOR

Features

☐ Drives 9 Instruments

☐ 64 Bit Pattern

☐ 10 Rhythm Patterns per Instrument

☐ 5 Mask Programmable Reset Counts

☐ 7 Segment Count Display Output

☐ Internal Oscillator

Typical Applications

☐ Organ Rhythm Sections

☐ Portable Rhythm Sections

☐ Automatic Rhythm Organs

☐ Music Synthesizer

General Description

The rhythm generator is a counter-ROM specifically designed for electronic organ and other electronic instruments. This product contains an internal oscillator, a 6 bit counter, and a ROM that drives nine rhythm instruments and also drives a seven segment sequence count display.

The oscillator frequency is determined by an external network. The 6 bit counter has control inputs that allow the counter to reset at any one of five counts. Five reset counts are mask programmed to user requirements. The 64th count is normally programmed as the 5th reset selection option. The counter contains

CONSUMER

Block Diagram
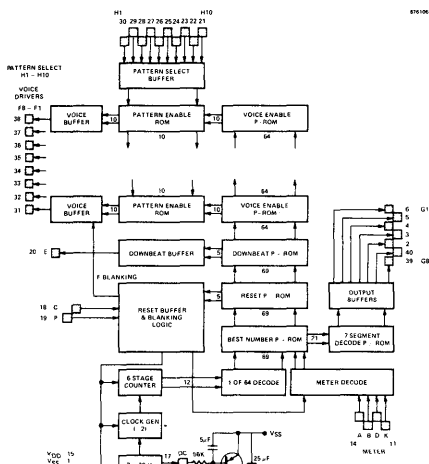
Pin/Package Confiuration
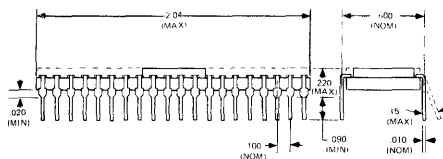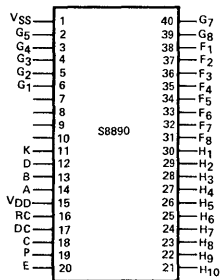
a start input that holds the system in the reset mode until a start command is impressed.

The counter outputs drive a 64 word ROM. The ROM has two types of rhythm instrument outputs and a rhythm count output. The rhythm instrument outputs provide a trigger with up to 64 counts. One of the instrument outputs contains only one rhythm pattern for each reset option. This output can be programmed to generate a downbeat trigger at the beginning of each measure. The remaining eight instrument outputs each contain 10 rhythm patterns which may be simultaneously selected to overlay multiple rhythm patterns.

The rhythm count outputs a seven segment code that can be used as a visual display of the musical timing. For example, if 4/4 timing is provided by the programmable option, and the appropriate control lined (I_R) are activated then the seven segment display will provide the pattern in Figure 2. Four numbers (1, 2, 3 or 4) will be displayed, one for each group of four quarter notes in a 16 note measure. The pattern will repeat for subsequent measures. Other sequences can be programmed for alternate timing schemes.

Internal input pull-up resistors to V_{DD} are provided on all inputs except the oscillator input. Output buffers consist of a single ended device to V_{SS}. The product is fabricated with I^{2TM} technology and is packaged in a 40 lead dual in-line package.

Functional Description of Input/Output Pins

DUMP CHARGE

Provides base current when required through an RC delay of approximately 25 msec to a PNP transistor which should be connected across the capacitor in the oscillator.

Input	Rhythm	Bits/Beat
A	3/4	3
B	5/4	4
D	6/8	4
K	3/4	4
Default	4/4	4

RESET:

C Input

When allowed to approach V_{DD}, the outputs are held disabled and the system is held ready to begin with the first bit of the First measure. The system starts when V_{SS} is applied.

PATTERN SELECT:

H1-H10 Inputs

V_{SS} applied to one enables one combination of the voices in a specific rhythm pattern. Any combination of patterns may be enabled at the same time. The customer must provide the voice pattern as a function of each pattern selected and of each bit time.

OUTPUT DUTY CYCLE:

P Input

When allowed to approach V_{DD}, the voice inputs are held off for one half of each bit time. When held at V_{SS}, the voice outputs are constantly valid. Note that neither option hides the short (<80 μsec) decode spikes.

The chip output functions are as follows.

VOICE DRIVERS:

F1-*F8*

When selected, internally, the outputs provide a low resistance path to V_{SS} which is suitable for driving a transistor interface. The chip input functions are as follows.

METER:

V_{SS} applied to the following inputs sets up the chip with a programmable number of bits per beat, beats per measure and measures before reset. A currently programmed example follows.

Beats/Measure	Measure/Reset	Bits/Reset
3	4	36
5	2	40
6	2	48
3	4	48
4	4	64

BEAT NUMBER DISPLAY:

G1-*G8 (less 6)*

When selected, internally, the outputs provide a low resistance path to V_{SS} suitable for sinking the current required to drive a GE7 segment display tube. The ROM driving these outputs must be programmed to match the meter program.

DOWNBEAT:

$\overline{E}$

When selected internally, the output provides a low resistance path to V_{SS}.

The Oscillator Interconnects are as follows.

RC PAD:

A 25 μF capacitor to V_{SS} and a series combination of a 20 KΩ potentiometer and a 1 KΩ resistor to V_{DD} will allow a range of about 1.5 to 15 bits/second.

P-ROM PROGRAMMING FORMATS

Programming the Rhythm Generator requires 132 IBM cards punched with the data outlined below. Each card should end with CXXXX—NNN where XXXX is a number provided by AMI and NNN is the card number.

DOWNBEAT ROM:

Columns	Contents
1–64	Enter '1' for the first bit of each measure of the given meter. (No gate = '1')
72–80	CXXXX-NNN per above.

Card	Meter
001	N
002	K
003	D
004	B
005	A

RESET ROM:

Columns	Contents
1–64	Enter '1' for the last bit before a reset and for all subsequent bits. (No gate = '1')
72–80	CXXXX-NNN per above.

Card	Meter
006	N (Meter N must not have a reset before 64)
007	K
008	D
009	B
010	A

NOTE: '1' always means an activated output and thus, may represent a gate or a lack of one.

BEAT NUMBER ROM:

Card	Column	Content
A	1–50	Enter '1' for each bit where the NUMBER should be on. (No gate = '1'). Enter the first 50 bits on Card A, last 14 bits on Card B.
B	1–14	
B	16–20	Meter bit pattern
B	22–28	7 Segment Display Pattern
A&B	72–80	CXXXX-NNN per above.

Enter the beat number data on adjacent cards starting with 011 for A and 012 for B and ending on or before 052.

Order data by Meter bit patterns as follows:

first	N	'00001'
first	K	'00010'
first	D	'00100'
first	B	'01000'
last	A	'10000'
unused		00000

Group beat numbers in order within each meter using the following decode for numerical compatibility with GE7 Segment tubes.

Beat Number to be displayed

	1	2	3	4	5	6	7	None
G1 col. 22	0	1	1	0	1	1	1	0
G2 col. 23	0	0	0	1	1	1	0	0
G3 col. 24	0	1	0	0	0	1	0	0
G4 col. 25	0	1	1	1	1	1	0	0
G5 col. 26	0	1	1	0	1	1	0	0
G7 col. 27	1	0	1	1	1	1	1	0
G8 col. 28	1	1	1	1	0	0	1	0

Segments to be activated (Gate='1')

Figure 1. Schematic Diagram

3.76
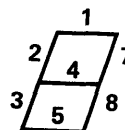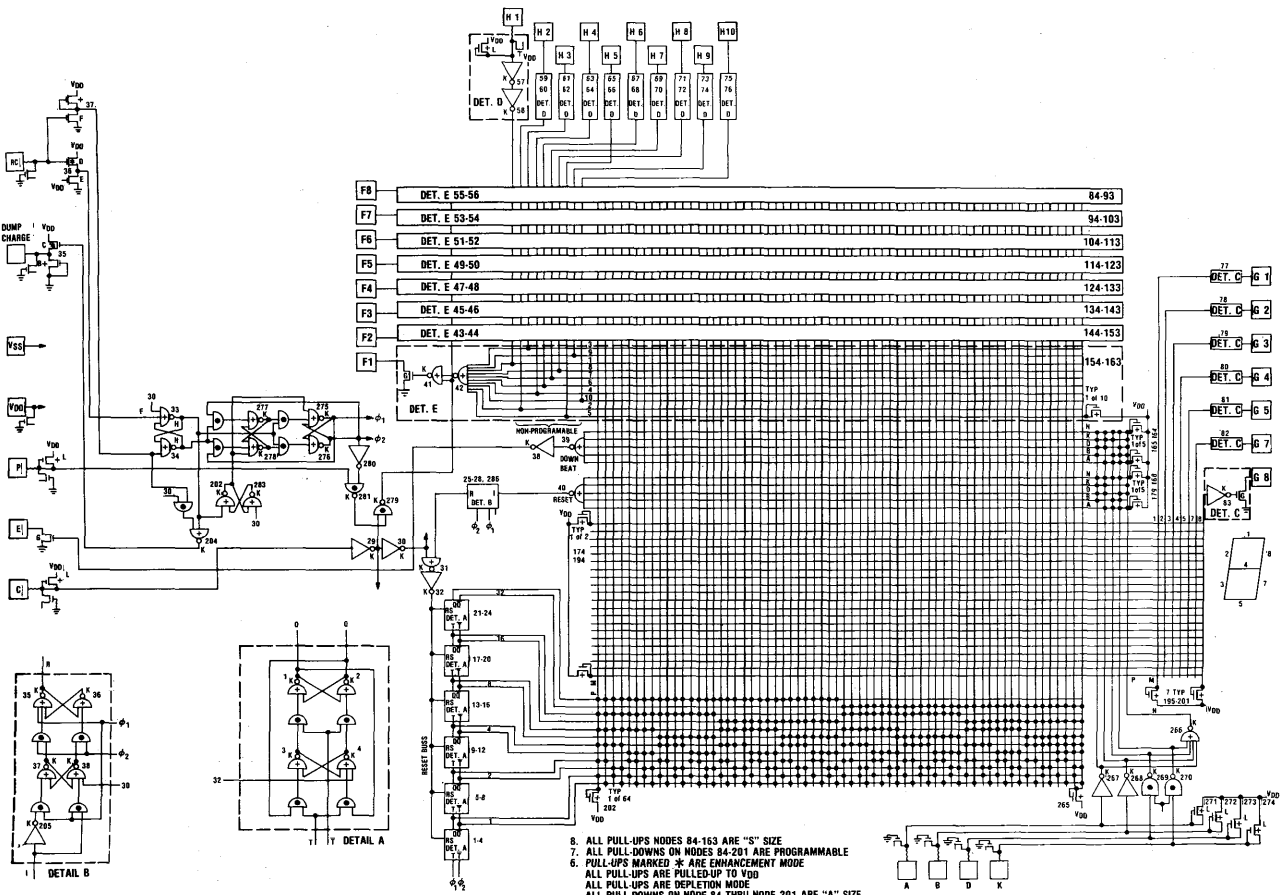
8. ALL PULL-UPS NODES 84-163 ARE "S" SIZE
7. ALL PULL-DOWNS ON NODES 84-201 ARE PROGRAMMABLE
6. PULL-UPS MARKED ✳ ARE ENHANCEMENT MODE
   ALL PULL-UPS ARE PULLED-UP TO V$_{DD}$
   ALL PULL-UPS ARE DEPLETION MODE
   ALL PULL-DOWNS ON NODE 84 THRU NODE 201 ARE "A" SIZE
   ALL PULL-DOWNS ARE "B" SIZE
   All PULL-UPS ARE "H" SIZE
5. UNLESS OTHERWISE NOTED:
4. NUMBER OF NODES: 285
3. NUMBER OF PADS: 36
2. NUMBER OF TRANSISTORS: 8461
1. DIE NUMBER: 9162

NOTES:

S8890

VOICE ENABLE ROM:

Card	Input	Outputs
053–060	H1	F1 through F8 in order
061–068	H2	F1 through F8 in order
069–076	H3	F1 through F8 in order
077–084	H4	F1 through F8 in order
085–092	H5	F1 through F8 in order
093–100	H6	F1 through F8 in order
101–108	H7	F1 through F8 in order
109–116	H8	F1 through F8 in order
117–124	H9	F1 through F8 in order
125–132	H10	F1 through F8 in order

Column	Contents
1-64	Enter a '1' for each bit where the selected H should turn on the selected F. (No gate='1')
67-68	Voice (f) number (2 digit)
72-80	CXXXX-NNN per above.

Absolute Maximum Ratings

Positive Voltage on any Pin	V_{SS} +0.3V
Negative Voltage on any Pin	V_{SS} −28V
Storage Temperature	−65 °C to +150 °C
Operating Ambient Temperature	0 °C to +70 °C

Static Characteristics

(V_{DD} = −12.1 ±5%, V_{SS} = GRD, T = 0° to +70 °C)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
V_{IH}	Input high level	V_{SS} −0.7			Volts	Internal
V_{IL}	Input low level			V_{DD} +2.0	Volts	Resistor to V_D
V_{OH}	Output high level	V_{SS} −2.0			Volts	I_O = 2 mA
V_{OL}	Output low level			V_{DD} +1.0	Volts	External 30 KΩ to V_{DD}
I_{DC}	Dump charge output current	1.0			mA	
V_{RC}	Discharge enable voltage		V_{SS} −7.0		Volts	

Application Data

Figure 2. Beat Number Display ROM

S8890 ROM Program Contents

K A · D B

SAMBA 4/8
SWING 4/8
SHAKE 4/4
WALTZ 3/4
JAZZ WALTZ 3/4
MARCH 6/8
JAZZ 5/4
BOSSA NOVA 4/4
BEGUINE 4/4
RHUMBA 4/4

H1 H2 H3 H4 H5 H6 H7 H8 H9 H10

S8890

F1 F2 F3 F4 F5 F6 F7 F8

BASS DRUM
SNARE DRUM
FLOOR TAM
BONGO
WOOD BLOCK
CLAVE
CYMBAL
TAMBORINE

VOICE FILTERS

Meter   7 Segment

Voice Enable ROM*

```
 1
 2
 3
 4   1           1   1              1 1  1 1      1      1 1      1                  1  1 1
 5
 6
 7
 8   1    1     1       1      1      1      1 1  1 1     1       1        1      1    1      1  1 1
 9
10
11   11111   1 1     1 1   1 1   1 1 1   1 1   1 1 1   1 1   1 1 1   1 1   1 1 1   1 1   1 1
12   1 111    1 1    1 1 1    1 11  1 1 1   1 1    1 1 1  11 1    1 1 1   1 1    111 1   1 1    1 1
13   11111  11111  11111  11111  11111  11111  11111  11111  11111  11111  11111  11111  1111
14   1 1 1   1 1    1 1 1   1 1 1   1 1 1   1 1 1   1 1 1   1 1 1   1 1    1 1    1 1    1 1
15   1 · 1   11 · 1   11 1  1   1   11  1   1111  1   1 1 1    1 1  111 1  1   11  1   1111
16   1       1       1       1       1       1       1 1
17       1       1     1 1 1     1       1       1       1 1 1   1
18   1 1 1    1 1   1 1 1   1 1   1 1 1   1 1   1 1 1   1 1   1 1 1   1 1 1   1 1 1   1 1 1
19   1  1   11  1   11    1 11    1 11    1 1 1   1 1  11   1  11   1 1
20   1  1    1 11    1 1 1111    1 11   11    1 111 1
21
22   1       1       1              1       1       1       1  1
23
24   1       1       1       1       1       1       1       1       1
25             1             1             1             1
26
27
28   1       1       1              1       1       1       1       1
29
30
31
32     1             1             1             1             1
33             1             1             1             1
34       1   1 1       1   1       1 1 1       1   1
35
36
37
38   1  1    1 1    1    1   1 1    1   1       1    1 1       1   1    1 1
39     1    1       1
40       1             1       1
```

*NOTE: Card Data is Presented in a Sequence That Differs from Program Instructions.

Meter 7 Segment

```
41  1                                      1111
42    1     1              1     1              1   1              111 1          11
43                                    11                              1111 1111
44  1     1 1     1           1       1     1       1        1     1     1     1
45              1                     1                 1              1
46
47
48  1        1        1              1     1           1     1              1
49
50                  11
51  1                                                                      1111
52            1     1              1     1           1     1           1      11
53  1                            11                                         1111
54                                               1     1           1
55  1                              1  1
56
57
58  1                   1                 1                 1           1   1  1
59  1                                               1 111
60  1                                   11  1
61     1           1           1           1           1           111 1      1
62    1              1              1              1              1
63     1           1           1           1           1           1        1
64  1     1        1           1           1     1        1     1     1     1
65    1     1        1        1        1     1              1     1   1 111111
66  1   1  1     1 1        1 1   1 1 1   1 1   1 1 1   1      1 111 111
67       1                  1                 1        1  1
68  1        1        1                   1     1           1     1        1
69  1  1     1     1           1        1        1           1 111
70     1     1        1     1        1     1        1 1111 1
71  1   1        1        1        1     1        1 1      1 1        1     1     1   1   1
72  1        1        1        1        1     1     1           1     1        1     1   1     1
73  1   1     1 1   1        11   1        1     1   11     1     1 1 1 1     1
74  1        1 1        1  ·1           1 1        1 1           1 1        1     1   1
75  1        1  1        1        1     1        1     1   11 1 1      1     1   11 1
76  1        1        1        1           1              1 1
77  1              1        1
78  1     1 1        1  1        1  1        1  1        1  1        1 1        1     1
79  1   1     1  1     1     1  1     1   1 11     1     1  1     1  1  1     1     1 1
80  1     1     1        1        1           1        1
```

Down Beat ROM

```
81  1              1              1              1
82  1        1           1              1
83  1        1              1           1
84  1           1        1        1              1
85  1           1           1        1
```

Reset ROM

```
86                                                              1
87                                          111  11111  11111  1111
88                                          111  11111  11111  1111
89                                                         1  1111
90                              11111  11111  11111  11111  11111  1111
```

Beat Number ROM

```
91   1111             1111             111 1           11  11           1          11
92     1 111             1111             1111             111 1        1      1 111 1
93       11 11             111 1          1 111           1111          1     1  1111
94           111 1             11 11          1 111           1111      1      1 1 11
95   111        1 11        11 1        111                           1         11
96     11 1        111        111        111                          1     1 111
97        111        111        1 11       11 1                       1     1  1111
98   111             111             111             111              1          11
99     11 1           11 1           11 1           11 1              1     1 111
100       111             111             111        111              1     1  1111
101          1 11          1 11          11            1 11           1       1 1 11
102             111           111           111           111         1     11 111
103   11111 1       111 111       1 11111       1111 1                1          11
104       1111 11       11 1111       11111 1       111 111           1     1 111 1
105   1111        111 1        1 111        111                       1         11
106     1 111        1111        11 11        1111                    1     1 111 1
107        11 11        1111        111 1        1 111                1     1  1111
108                                                                       1111111
109                                                                       1111111
110                                                                       1111111
111                                                                       1111111
```

3.79

AMI

S9660

RHYTHM GENERATOR

Features

☐ Drives 7 Instruments

☐ 64 Bit Patterns

☐ 9 Rhythm Patterns

☐ 4 Feature Outputs

☐ 5 Programmable Feature Selections

☐ All Rhythm Patterns Additive

☐ 5 Programmable Resets

☐ All Counters and Decoders Internal

☐ All Patterns User Programmable

General Description

The S9660 rhythm generator is a counter-ROM specifically designed for use in rhythm sections of electronic organs and independent electronic rhythm units. This product contains a six stage counter, all internal ROM decoding, a 4K bit pattern ROM, and a 1K bit feature ROM. A total of nine distinct 64-bit rhythm patterns are generated and may be used to control up to seven rhythm instruments. In addition, the feature ROM provides four outputs that may be used for automatic chord gating, walking bass, or to create rhythm pattern variation.

The 6-bit counter may be reset at any bit from 1

Block Diagram
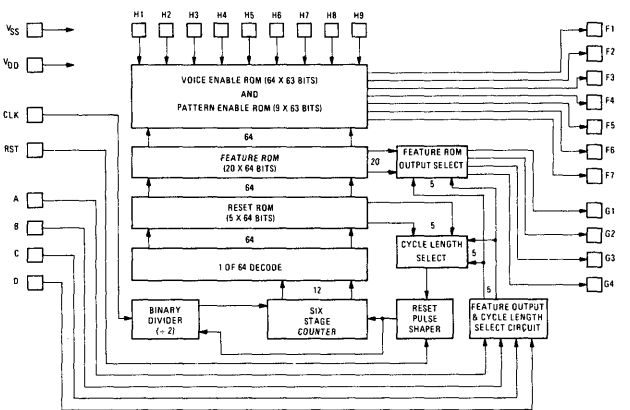
177175

Pin/Package Configuration

177177

87696

3.80
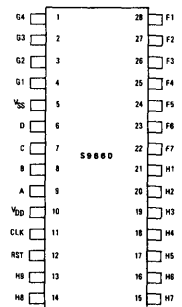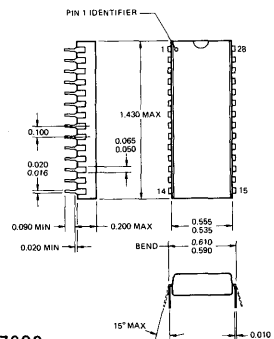
through 64 to obtain any desired counter cycle. This counter cycle control is determined by the user's individually programmed ROM pattern, which allows the electrical selection of up to five different counter cycle lengths in one S9660.

The counter outputs drive a 64 × 63 bit rhythm pattern ROM and a 64 × 20 bit feature ROM. The rhythm pattern ROM drives seven instrument outputs and generates nine rhythm patterns which may be simultaneously selected to overlay multiple rhythm patterns. The feature ROM drives four outputs; depending on which of the five reset conditions is selected, the four outputs each contain five distinct 64 bit patterns. These may be used to drive such features as walking bass, automatic chording, or rhythm variation.

Internal input pull-up resistors to V_{DD} are provided on all inputs, and output buffers consist of open drain devices with source connected to V_{SS}. The product is fabricated with P-channel ion implanted MOS technology and is packaged in a 28 lead dual in-line plastic package.

Typical Applications

Organ Rhythm Sections, Portable Rhythm Units, Automatic Chording Systems, Walking Bass.

Operational Description

A block diagram of the S9660 appears on page 4, along with a typical timing diagram. All rhythm patterns, feature patterns, and counter cycle lengths are user programmable, and detailed instructions for this are given on page 5.

CLK Input (pin 11):

A clock frequency from an external oscillator is supplied to this pin to provide the timing information to the 6 bit rhythm counter. As this frequency is varied, the speed, or tempo, of the generated rhythm is varied.

As indicated in the block diagram, the CLK input is divided by two and then applied to the 6 stage counter. This means that each of the output bit periods is equal to two input clock periods. For example, if the rhythm counter is programmed to recycle every 48 bits, and the cycle is divided into two measures of 4 beats each, then each beat contains 6 bits; if the CLK input frequency is 30 Hz, then, rhythm timing will be 15 bits per second, or 900 bits per minute, or 150 beats per minute.

H Inputs (pins 13 through 21):

Normally pulled to V_{DD}, application of a V_{SS} level to any of the 9 H inputs enables one combination of voices that comprise a specific rhythm pattern. Any combination of patterns may be enabled simultaneously by applying V_{SS} to other H inputs. The user must provide the desired voice pattern as a function of each H pattern selected and of each bit time. This is programmed in the Voice Enable ROM.

RST Input (pin 12):

Normally pulled to V_{DD}, application of a V_{SS} level to the RST input enables the rhythm counter. When RST is left unconnected, the binary divider (÷ 2) and the rhythm counter chain are reset to count one, and all "F" outputs are held in an off condition. When V_{SS} is applied, the bit pattern selected for the first address of the ROM (count one) will activate the appropriate "F" outputs. Subsequent clock pulses at the CLK input will cause the counter to advance its count as indicated in the timing diagram.

A, B, C, D Inputs (pins 9, 8, and 6):

These inputs control two functions, the selection of cycle length (or counter reset bit) and the bit patterns of the four G outputs. Normally pulled to V_{DD}, these outputs may be selected (only one at a time) by applying V_{SS}. A fifth condition called "default," or "N", occurs when none of the four A, B, C, or D inputs is selected.

Up to five reset bits (or counter lengths) may be programmed so that five different counter lengths may be selected by use of A, B, C, or D. These resets are programmed by the Reset ROM. This allows a 4/4 rhythm to contain 64 bits and a 3/4 rhythm to contain 48 bits, for example, so that when switching from a swing beat to a jazz waltz it is not necessary for the player to adjust the tempo control.

For each of the five A, B, C, D, or Default conditions there is a unique pattern supplied on the four G outputs. This information is programmed into the Feature ROM.

F Outputs (pins 22 through 28):

When selected internally by the Voice Enable ROM, these seven open drain outputs provide a low resistance path to V_{SS}. These outputs are suitable for driving a transistor interface to electronic rhythm voice generators. Decode spikes may appear at the F

outputs, though they are of short enough duration ($< 80\,\mu s$) that most instrument voice generators would be unaffected.

G Outputs (pins 1, 2, 3, and 4):

When selected internally by the Feature ROM, the four open drain G outputs provide a low resistance path to V_{SS}. Five distinct patterns are available on each of the outputs and are selected by the A, B, C, D,

inputs. The decode spikes mentioned in the "F" output paragraph may also be present in the "G" outputs.

Absolute Maximum Ratings

Positive voltage on any pin	$V_{SS} + 0.3$ Volts
Negative voltage on any pin	$V_{SS} - 28$ Volts
Storage temperature	$-65°$ to $+150°C$
Operating Ambient Temperature	$0°C$ to $+70°C$

Electrical Specifications

($0°C \leq t_a \leq 70°C; -10$ Volts $\geq V_{DD} \geq -14$ Volts unless otherwise specified)

Symbol	Parameter	Min	Max	Units	Conditions
V_{IL}	Input logic "0"	V_{DD}	$V_{DD} + 2.0$	Volts	See Note 1
V_{IH}	Input logic "1"	$V_{SS} - 0.7$	V_{SS}	Volts	
V_{CLK_L}	Input logic "0" (CLK input)	V_{DD}	$V_{DD} + 1.0$	Volts	
V_{CLK_H}	Input logic "1" (CLK input)	$V_{SS} - 0.7$	V_{SS}	Volts	
t_{cr}, t_{cf}	CLK input rise and fall time		100	μs	Measured at 10% to 90% of V_{DD}
f_c	Clock frequency (CLK input)	DC	5K	Hz	
V_{OL}	Output logic "0"				See Note 2
V_{OH}	Output logic "1"	$V_{SS} - 2.0$	V_{SS}	Volts	$V_{DD} = -12.0$ Volts I out = 1 mA maximum
P	Average power dissipation		300	MW	Measured at 25°C

NOTES: 1. *Internal 5µA minimum pullup to V_{DD} is provided.*
2. *External load to V_{DD} is required.*

Programming Instructions

Programming of the S9660 is a straightforward process requiring the user to supply a total of 110 cards. There are three ROM sections to be programmed, the Reset ROM, the Feature ROM, and the Voice Enable ROM. Detailed instructions for punching the cards required to program these three ROMs are supplied below. In column 72-80 of each card, as described below, two numbers appear-CXXXX and NNN. The CXXXX is a number to be given to the user by AMI prior to punching the card deck, and NNN is the sequence number of the card.

RESET ROM:

A total of five cards are required to program the reset ROM. Their card numbers are 001 through 005. Each card determines at what bit the rhythm counter will

reset (i.e., the number of bits per cycle) for one of the five electrically selected conditions, A, B, C, D, or N (N = ABCD). Card 001 corresponds to N, 002 to D, 003 to C, 004 to B, and 005 to A.

Columns	Contents
1-64	Enter a "1" for the last bit before an internal reset occurs and for all subsequent bits through 64.
72-76	CXXXX—To be assigned by AMI, as stated above.
78-80	Enter number of the card (001 through 005).
Example:	If card 003 has all ones in columns 48 through 64, then whenever the C input is selected, the rhythm generator will reset at the end of bit 48, giving a 48 bit cycle length.

Timing Diagram
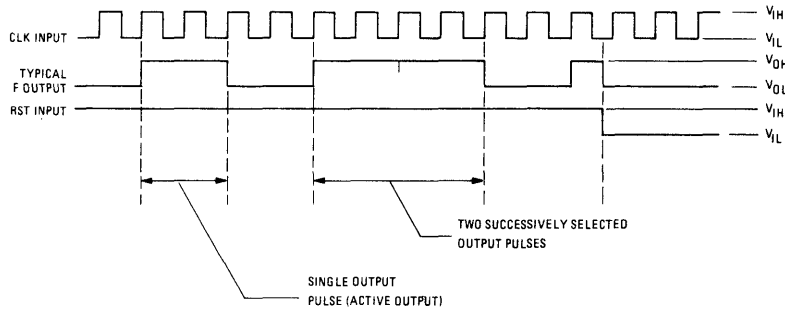
177178

Detailed Block Diagram

177176

ABCD = DEFAULT (OR "N")
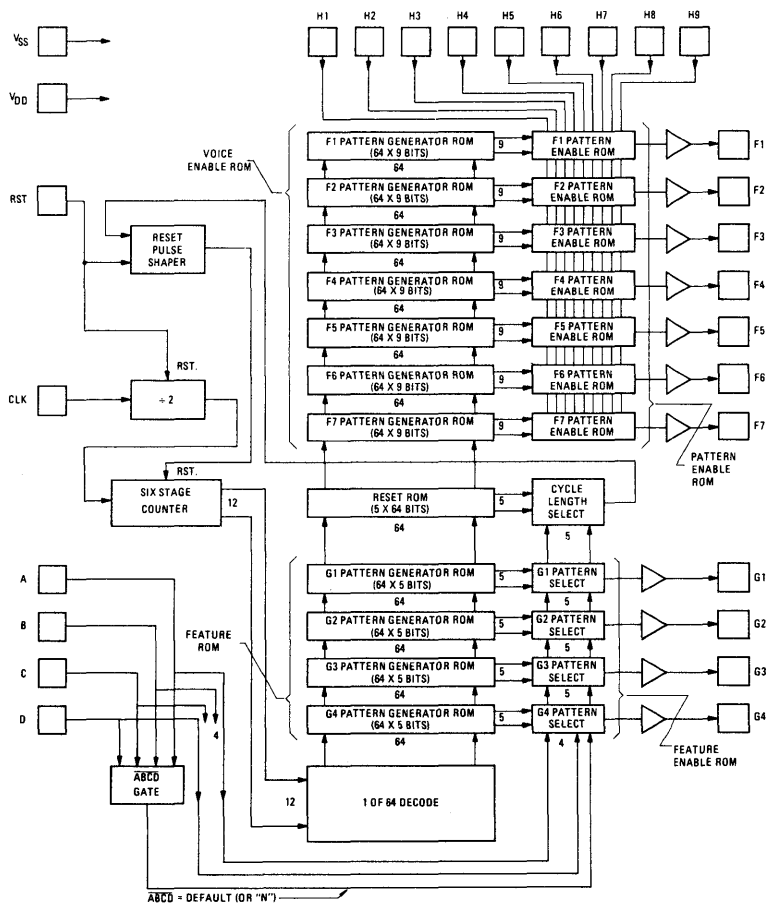
FEATURE ROM:

A total of 42 cards are required to program the feature ROM. The cards are grouped in pairs, and each pair determines the bit pattern that will appear on a given G output for a given A, B, C, D, or N input selection. The G1 output is programmed by cards 6-15, G2 by cards 16-25, G3 by cards 26-35, and G4 by cards 36-45. Cards 46 and 47 must be present, but they are not used to program any G outputs.

The five pairs of cards corresponding to each output are arranged so that the bit pattern programmed by the first pair will be selected by the A input, the second by B, and the third, fourth and fifth by C, D, and N, respectively. For example, if input C is selected, the bit pattern appearing at the G2 output would be that programmed by cards 20 and 21.

First card in pair (21 cards: 6, 7, 10, . . ., 44):
Column 1-50—   First 50 bits of 64; enter a "1" at the location of each bit where an active output is desired.
Second card in pair (21 cards: 7, 9, 11, . . ., 45):
Column 1-14—   Last 14 bits of 64; enter a "1" at the

location of each bit where an active output is desired.

Card 46:
  Columns 1-50—Enter nothing.
Card 47:
  Columns 1-14—Enter nothing.
Column 16-20:
  Cards 7, 17, 27, 37— . . . . Enter "10000."
  Cards 9, 19, 29, 39— . . . . Enter "01000."
  Cards 11, 21, 31, 41— . . . . Enter "00100."
  Cards 13, 23, 33, 43— . . . . Enter "00010."
  Cards 15, 25, 35, 45— . . . . Enter "00001."
  Card 47— . . . . Enter "00000."
Column 22-28:
  Cards 7, 9, 11, 13, 15— . . . . Enter "1000000."
  Cards 17, 19, 21, 23, 25— . . . . Enter "0100000."
  Cards 27, 29, 31, 33, 35— . . . . Enter "0010000."
  Cards 37, 39, 41, 43, 45— . . . . Enter "10001000."
Column 72-76 (all cards)— . . . . Enter CXXXX
                                (as assigned by AMI).
Column 78-80 (all cards)— . . . . . . Enter card number
                                (006 through 047).

VOICE ENABLE ROM:

This ROM is programmed by a total of 63 cards, numbered 048 through 110. The cards are in nine groups (H1, H2, . . ., H9) of seven cards each (F1, F2, . . ., F7).

Card	Input	Outputs	Column	
048-054	H1	F1 through F7 in order	1-64	Enter a "1" for each bit where the
055-061	H2	F1 through F7 in order		selected H should turn on the desired
062-068	H3	F1 through F7 in order		F output.
069-075	H4	F1 through F7 in order	67-68	Voice number (F1, F2, F3, F4, F5, F6,
076-082	H5	F1 through F7 in order		or F7).
083-089	H6	F1 through F7 in order	72-76	Enter CXXXX (as assigned by AMI).
090-096	H7	F1 through F7 in order		
097-103	H8	F1 through F7 in order	78-80	Enter card number (046 through 110).
104-110	H9	F1 through F7 in order		

CUSTOMIZING THE S9660:

The S9660 has been designed to offer a wide variety of features for use in both low cost rhythm units and electronic organs. It is possible, however, in many circumstances to modify this part to fix particular applications.

A few examples of such modifications are the addition of an additional F output in place of an H pattern input

and vice versa, the blanking of 50% of the output pulsewidth, and the addition of more G outputs. To minimize cost, this circuit may be supplied in a smaller package if some of the existing features are not needed.

These modifications may be readily accomplished by minor changes to the bonding of the circuit. To determine if a proposed feature set is feasible, consult AMI's Application Department.

AMERICAN MICROSYSTEMS, INC.

TOP OCTAVE SYNTHESIZER

CONSUMER

Features

☐ Single power supply

☐ Broad supply voltage operating range

☐ Low power dissipation

☐ High output drive capability

☐ S50240—50% output duty cycle

☐ S50241—30% output duty cycle

☐ S50242—50% output duty cycle

General Description

The S5024 is one of a family of ion-implanted, P-channel MOS, synchronous frequency dividers.

Each output frequency is related to the others by a multiple $12\sqrt{2}$ providing a full octave plus one note on the equal tempered scale.

Low threshold voltage enhancement-mode, as well as depletion mode devices, are fabricated on the same chip allowing the S5024 family to operate from a single, wide tolerance supply. Depletion-mode technology also allows the entire circuit to operate on less than 360 mW of power. The circuits are packaged in 16 pin plastic dual-in-line packages.

Block Diagram

Pin Connections
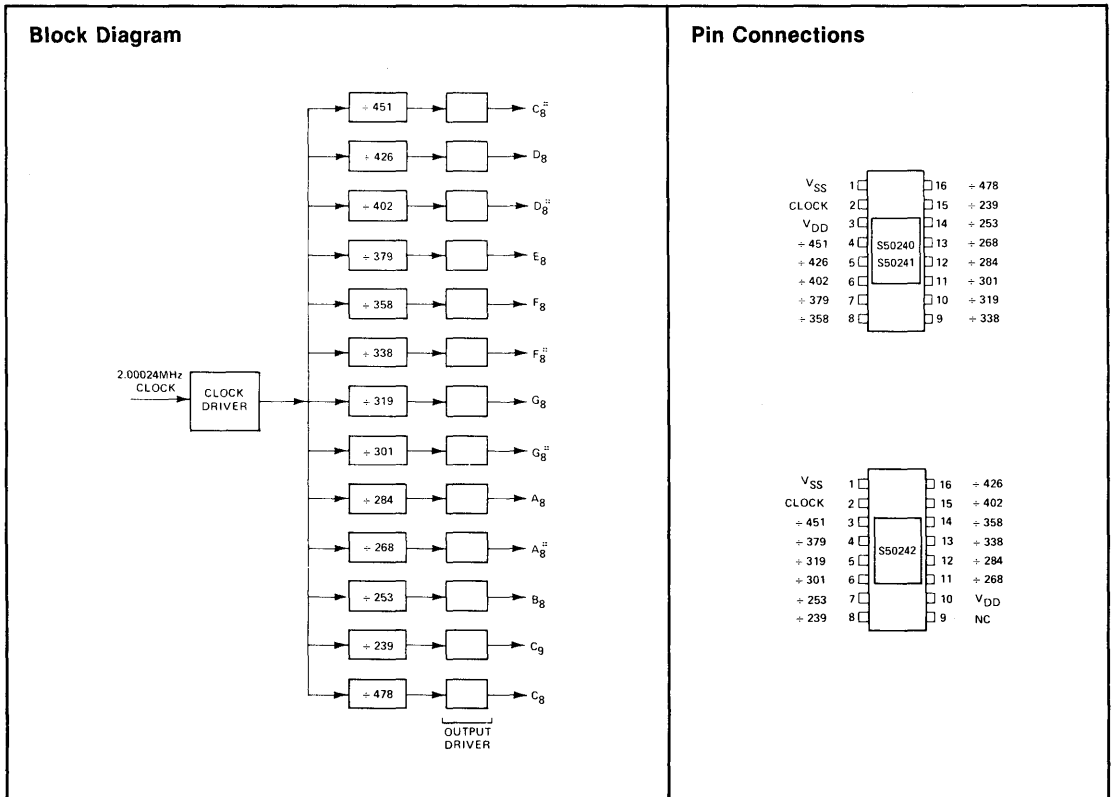
RFI emination and feed-through are minimized by placing the input clock between the V_{DD} and V_{SS} pins. Internally the layout of the chip isolates the output buffer circuitry from the divisor circuit clock lines. Also, the output buffers limit the minimum rise time under no load conditions to reduce the R.F. harmonic content of each output signal.

Absolute Maximum Ratings

Voltage on any pin relative to V_{SS}	$+0.3V$ to $-20V$
Operating Temperature (Ambient)	$0\,°C$ to $50\,°C$
Storage Temperature (Ambient)	$-65\,°C$ to $+150\,°C$

Recommended Operating Conditions

$(0\,°C \le T_A \le 50\,°C)$

Symbol	Parameter	Min	Typ	Max	Units	Figure
V_{SS}	Supply Voltage	0		0	V	
V_{DD}	Supply Voltage	-11.0	-14.0	-16.0	V	

Electrical Characteristics

$(0\,°C \le T_A \le 50\,°C; V_{DD} = -11$ to $-16V$ unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Figure
V_{IL}	Input Clock, Low	0		-1.0	V	Figure 1
V_{IH}	Input Clock, High	-10.0		V_{DD}	V	Figure 1
f_1	Input Clock Frequency	100	2000.240	2500	kHz	
t_r, t_f	Input Clock Rise & Fall Times 10% to 90% @ 2.5MHz			50	nsec	Figure 1
t_{ON}, t_{OFF}	Input Clock On and Off Times @ 2.5MHz		200		nsec	Figure 1
C_I	Input Capacitance		5	10	pF	
V_{OH}	Output, High @ 1.0mA	$V_{DD} +1.5$		V_{DD}	V	Figure 2
V_{OL}	Output, Low @ 1.0 mA	$V_{SS} -1.0$		V_{SS}	V	Figure 2
t_{ro}, t_{fo}	Output Rise & Fall Times, 500 pF Load 10% to 90%	250		2500	nsec	Figure 3
t_{ON}	Output Duty Cycle-S50240, S50242		50		%	
	S50241		30		%	
I_{DD}	Supply Current		14	22	mA	Outputs Unloaded

CONSUMER

Figure 1. Input Clock Waveform

Figure 2. Output Signal DC Loading

MAX SINK CURRENT = 1.0 mA

MAX SOURCE CURRENT = 1.0 mA

I_{SINK} VS V_{OUT}

I_{SOURCE} VS V_{OUT}

SINK CURRENT TO CHIP V_{DD}

SOURCE CURRENT FROM CHIP V_{SS}

– (Operating Area)

– (Current Overload Area)

Figure 3. Output Rise and Fall Times

– 16V

POSITION 1

V_{DD}

OUT

15K

500 pF

POSITION 2

– 16V

V_{SS}

t_{ro} and t_{fo} Tests

TEST	SWITCH
t_{ro}	POSITION 1
t_{fo}	POSITION 2

V_{OL}

10%

V_{OH}

90%

t_{ro}

t_{fo}

AMI
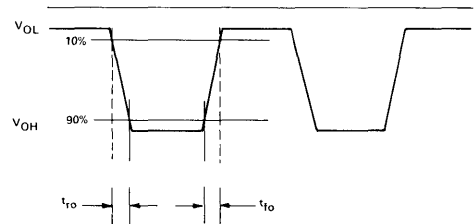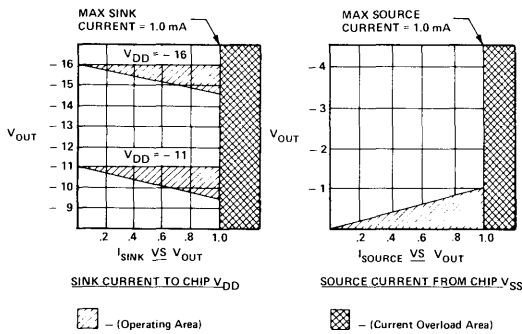
Single-Chip
Microcomputer Family
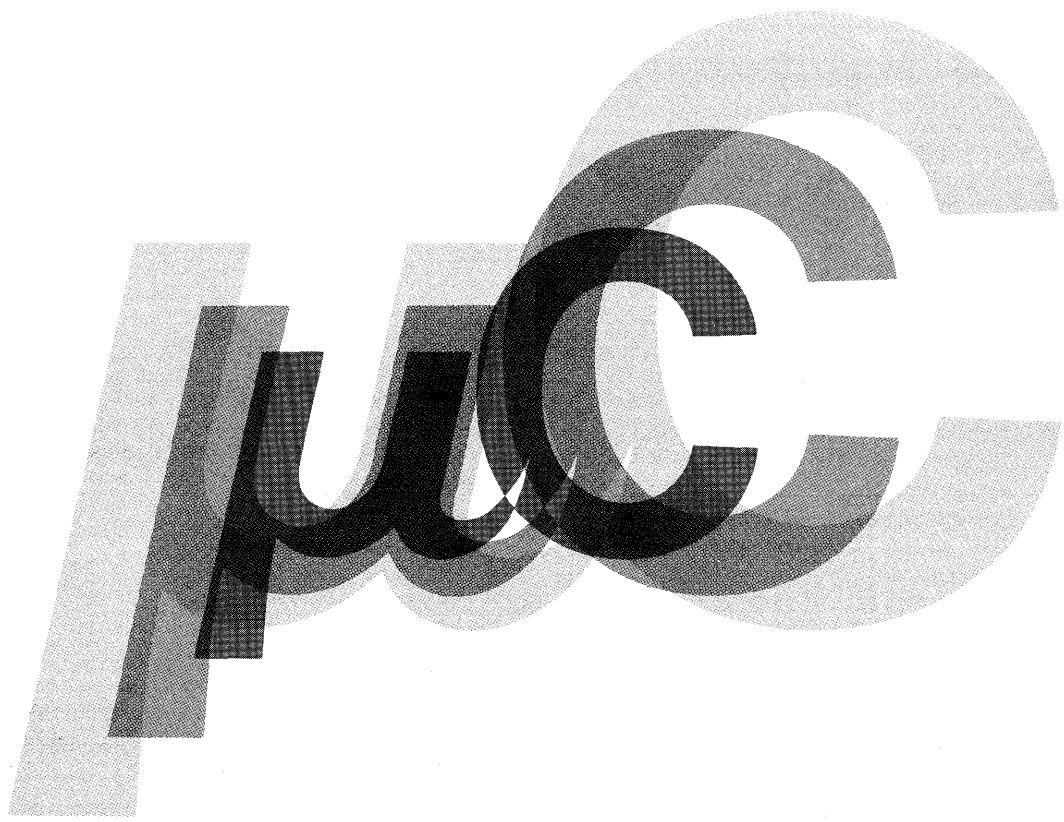
Product Features	S2000	S2000A	S2150	S2150A	S2152[1]	S2200[2]	S2200A	S2210[3]	S2400	S2400A
ROM (Bytes)	1K	1K	1.5K	1.5K	1.5K	2K	2K	2K	4K	4K
RAM (Nibbles)	64	64	80	80	80	128	128	128	128	128
A/D Converter (8-Bit)	—	—	—	—	—	YES	YES	YES	YES	YES
Timer	50/60Hz	50/60Hz	50/60Hz	50/60Hz	Prog÷N	Prog 8Bit	Prog 8Bit	Prog 8Bit	Prog 8Bit	Prog 8Bit
Interrupts	—	—	—	—	—	2	2	2	2	2
Power Fail Detect	—	—	—	—	—	Yes	Yes	Yes	Yes	Yes
High Voltage Outputs	—	Yes	—	Yes	—	—	Yes	—	—	Yes
Crystal Clock Option	—	—	Yes	Yes	—	Yes	Yes	Yes	Yes	Yes
TouchControl Inputs	Yes	Yes	Yes	Yes	—	Yes	Yes	Yes	Yes	Yes
Levels of Subroutine	3	3	3	3	3	3-5	3-5	3-5	3-5	3-5
# of Flags	2	2	2	2	2	262	262	262	262	262
Table Look-up	—	—	—	—	—	Yes	Yes	Yes	Yes	Yes
Power-Down RAM Option	—	—	—	—	—	Yes	Yes	Yes	Yes	Yes
D/A Converter Option	—	—	—	—	—	Yes	Yes	Yes	Yes	Yes
Zero—Crossing Detect	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
Cycle Time (μsec)	4.5	4.5	4.5	4.5	4.5	4.5	4.5	4.5	4.5	4.5
Instructions — Total	51	51	51	51	51	63	63	63	63	63
Single Cycle & Byte	49	49	49	49	49	52	52	52	52	52
Voltage (volts)	9	9/32	9	9/35	9	5	5/35	5	5	5/35
User Definable 7-Segment PLA	No	No	No	No	No	Yes	Yes	Yes	Yes	Yes
Development Support										
Tektronix 8002A[4]	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
In-Circuit Emulator	—	—	—	—	—	Yes	Yes	Yes	Yes	Yes
Hardware Emulator	SES 2150	SES 2150A	SES 2150	SES 2150A	SES 2150	SES 2400	SES 2400A	SES 2400	SES 2400	SES 2400A

1. Has digital-to-frequency converter (4-bit) for enhanced sound generation.
2. Also available in an 8-bit bus-compatible version — S2220.
3. CMOS
4. Motorola Exorcisor and Intel Intellec Development System Support for the S2000 Family also available.

AMI's S2000 Family of single-chip microcomputers brings the advantages of microprocessor control to low-cost, multi-feature keyboard/display systems. These circuits are optimized to reduce systems cost while at the same time providing the user with the ability to select from a variety of architectural features. Versatile input/output and an instruction set optimized for its intended applications make an S2000 Family member preferable to expensive multiple-chip solutions. Dramatic cost reductions are possible during product design, manufacture, testing, and maintenance. Two versions are available for the members of the S2000 Family: The standard version for direct drive of LED displays and the "A" version for direct drive of fluorescent displays.

Features

The S2000 Family members are entire computers on a chip, suitable for volume keyboard/display applications which require control in a minimum space at a minimum cost.

They are ideally suited for systems with the following requirements:

☐ Analog-to-digital and digital-to-analog conversion
☐ Time-of-day and interval timer control
☐ AC line synchronization
☐ Display drive
☐ Keyboard inputs (ohmic or TouchControl)
☐ Arithmetic operations
☐ Single power supply
☐ Program expandability and testability
☐ Triac drive

Applications

The S2000 can lower the cost and enhance the performance of control circuits in applications such as the following:

☐ Vehicle instrumentation and systems control
☐ Major household appliances
☐ CB radios, stereo receivers, tape decks
☐ Electronic scales
☐ Toys and games
☐ Lab instruments
☐ Telephone equipment
☐ Programmable calculators
☐ Data sampling devices
☐ Data logging devices
☐ Test equipment
☐ Keyboard devices
☐ Display devices
☐ Remote monitors
☐ Security systems
☐ Set-back thermostats

Functional Description

The basic S2000 has an on-chip 1024-instruction ROM; other family members have ROMs ranging up to 4096 instructions (see tables). If necessary, additional program memory can be added externally up to a maximum of 8192 instructions. The Program Counter is a pointer to the next instruction to be executed. The Program Counter Stack holds return addresses during execution of subroutines or interrupts.

The scratchpad RAM holds the temporary values of 4-bit data words, typically numeric quantities. The BA, BU and BL registers are used to access RAM words. The E Register can be used as a general purpose register or as an index limit register for controlling RAM access.

The ALU—Arithmetic Logic Unit—performs data operations, using the Accumulator and the Carry Register. Software can set reset and test Flags as temporary indicators.

The Control Logic includes three inputs and three outputs for interfacing external devices. The Oscillator generates all clocking signals and needs only an external RC circuit to set its rate. Optionally a crystal may be used to precisely control the oscillator frequency.

The K Lines range from a voltage comparator, Schmitt-trigger, and timer inputs on the S2000, to a full bi-directional port on the S2200 supporting A/D and D/A converters, interrupts, and a programmable counter/timer.

The eight bi-directional three-state D Lines are general-purpose data signals. The thirteen A Lines are outputs for displays, keyboard strobes, control signals, or address lines for external ROM.

"A" Versions for Vacuum Fluorescent Display

The "A" versions of the S2000 Family provide high voltage fluorescent display capability but are otherwise identical to their non-"A", LED counterparts. The output buffer drive (V_{DD}) is changed to a vacuum fluorescent drive (V_{FD}) and typically tied to 35 volts. The D_0 through D_7 and A_0 through A_4 are changed from LED drivers (nominal 5 volts) to vacuum fluorescent drivers (nominal 26 to 35 volts).

CMOS Version—S2210

For those applications which require micropower, the S2210 is a CMOS version of the S2200. The S2210 is functionally identical and software compatible to the S2200.

Microprocessor Bus-Compatible Version—S2220

The S2220 bus-compatible version of the S2200 can be used as a user programmable peripheral or multi-processor systems. This processor is software compatible with all the other members of the family and is functionally identical (with the exception of some control lines and the D-line interface) to all the other members.

Development Support Tools

For information on support tools, both hardware and software, see the Development System Support section of this catalog.

S2000

AMI

AMERICAN MICROSYSTEMS, INC.

SINGLE-CHIP MICROCOMPUTERS

Features

- [ ] 1024×8 Program ROM On-Chip; Externally Expandable to 8192×8—S2000
- [ ] 1536×8 Program ROM On-Chip; Externally Expandable to 8192×8—S2150
- [ ] 64×4 Scratchpad RAM On-Chip—S2000
- [ ] 80×4 Scratchpad RAM On-Chip—S2150
- [ ] 14 Outputs, 8 Inputs, Plus 8 Bi-Directional Three-State Lines
- [ ] TouchControl Capacitive Touchplate Interface
- [ ] Seconds Timer for Both 60Hz and 50Hz Lines
- [ ] 7-Segment Decoder

- [ ] LED Display Drivers—S2000/S2150
- [ ] Vacuum Fluorescent Display Drivers—S2000/S2150A
- [ ] Single +9V Supply
- [ ] Fast 4.5μs Execution Cycle
- [ ] Three-Level Subrouting Stack
- [ ] TTL-Compatible Outputs
- [ ] Reset, Test, and Single Step Modes
- [ ] Crystal Input for Accurate Clocking—S2150
- [ ] S2152:D-To-F Converter Programmable Divide-by-N Counter/Timer

Block Diagram
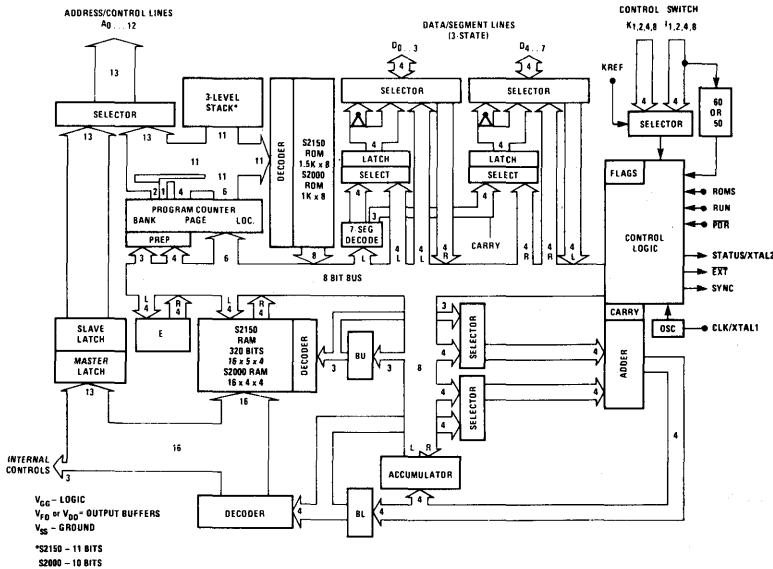
Pin Configuration
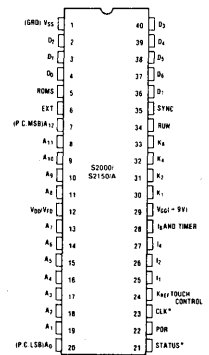
Functional Description

The S2000/S2150 are ideal for a wide range of appliance and process control designs. Versatile input/output and an instruction set optimized for its intended applications make the S2000 preferable to expensive multiple-chip solutions with dramatic cost reductions during product design, manufacture, testing, and maintenance.

The S2000/S2150 have an on-chip 1024/1536 instruction ROM. If necessary, additional program memory can be added externally up to a maximum of 8192 instructions. The Program Counter is a pointer to the next instruction to be executed. The Subroutine Stack holds return addresses during execution of subroutines.

The scratchpad RAM holds the temporary values of 64/80 4-bit data words, typically numeric quantities. The BU and BL registers are used to access RAM words. The E Register can be used as a general purpose register or as an index limit register for controlling RAM accesses.

The ALU—Arithmetic Logic Unit—performs data operations, using the Accumulator and the Carry Register. Software can set and test two Flags as temporary indicators.

The Control Logic includes three inputs and three outputs for interfacing external devices. The Oscillator generates all clocking signals and needs only an external RC circuit to set its rate. The KREF Input is the analog reference for TouchControl and similar interfaces. Software decision-making instructions sample the four K Inputs and the four I Inputs, one of which can be used as a line-frequency counter.

The eight bi-directional three-state D Lines are general-purpose data signals. The thirteen A Lines are outputs for displays, keyboard strobes, control signals, or address lines for external ROM.

General Description for S2152

The S2152 is an extension of the S2000/S2150 and is software compatible with them. It has the following enhanced features:

☐ Digital-To-Frequency Converter (4-Bit)
☐ Programmable Divide-by-N Counter/Timer
☐ 15 Outputs, 4 Inputs, and 8 Bi-Directional Three-State Lines
☐ One Open Drain Output, and
☐ High Current Outputs

S2000/S2150/A/S2152
Instruction Set Summary

ADCS	ACC+RAM+CARRY, Skip if Sum ≤ 15	RF1	Reset Flag 1
ADD	ACC+RAM	RF2	Reset Flag 2
ADIS X	ACC+X, Skip if Sum ≤ 15	RSC	Reset Carry
AND	ACC "AND" RAM	RSM Z	Reset RAM Bit Z
CMA	Complement ACC	RT	Return from Subroutine
DISB	Display Number in Binary Format	RTS	Return from Subroutine and Skip
DISN	Display Number in Seven Segment Format		
		SAM	Skip if ACC=RAM
EUR	(European) SET 50/60Hz and Display Latch Polarity	SBE	Skip if BL=E
		SF1	Set Flag1
		SF2	Set Flag2
INP	Input 8 Bits from D Lines	SOS	Skip if Seconds Flag Set
		STC	Set Carry
JMP X	Jump	STM Z	Set RAM Bit Z
JMS X	Jump to Subroutine	SZC	Skip if Carry=0
		SZI	Skip if I=0
LAB	Load ACC with BL	SZK	Skip if K=0
LAE	Load ACC with E	SZM Z	Skip if RAM Bit Z=0
LAI X	LOAD ACC with X		
LAM Y	LOAD ACC with RAM then BU "XOR"Y	TF1	Skip if Flag1=1
		TF2	Skip if Flag2=1
LBE Y	Load BL with E and BU with Y		
LBF Y	Load BL with 15 and BU with Y	XAB	Exchange ACC with BL
LBEP Y	Load BL with E+1 and BU with Y	XABU	Exchange ACC with BU
LBZ Y	Load BL with 0 and BU with Y	XAE	Exchange ACC with E
		XC Y	Exchange ACC with RAM then BU "XOR"Y
MVS	Move Master Latch to Slave Latch	XCD Y	Exchange ACC and RAM, BU "XOR"Y, Decrement BL, and Skip if BL=0 Before Decrementing
NOP	No Operation		
		XCI Y	Exchange ACC and RAM, BU "XOR"Y, Increment BL, and Skip if BL=0 After Incrementing
OUT	Output 8 Bits to D Lines		
PP X	Prepare Page (or Bank)		
PSH	Preset Master Strobe High		
PSL	Preset Master Strobe Low	XOR	ACC "Exclusive-OR" RAM

SINGLE-CHIP MICROCOMPUTERS

Features

- ☐ 8-Bit A/D Converter with 8 Inputs
- ☐ 8-Bit D/A Converter
- ☐ 2048×8 Program ROM On-Chip and Expandable to 8192×8 (S2200/S2200A/S2210)
- ☐ 4096×8 Program ROM On-Chip and Expandable to 8192×8 (S2400/S2400A)
- ☐ 128×4 Scratchpad RAM On-Chip with Power-Down Mode
- ☐ Two-Level Maskable Priority Interrupt System with Provision for Software Interrupt
- ☐ Programmable 8-Bit Timer/Event Counter On-Chip
- ☐ 14 Outputs, 8 Bidirectional Three-State Lines, TTL-Compatible, Plus 8 Independently Software-Defined I/O Lines
- ☐ TouchControl Capacitive Switch Interface
- ☐ Seven-Segment Display Decoder/Drivers:

S2200/S2400/S2210—LED
S2200A/S2400A—Vacuum Fluorescent

- ☐ Single +5V Power Supply
- ☐ 4.5μs Cycle Time
- ☐ 63 Instructions—52 Single Byte and Single Cycle
- ☐ 3-Level Subroutine Stack (5-Level if Interrupts Not Used)
- ☐ 2-Level Interrupt Stack
- ☐ Built-In Production Test Mode
- ☐ Single Step Capability
- ☐ Power Failure Detection and Power-On-Reset Circuitry
- ☐ Up to 256 General Purpose Flags (RAM Bank 1)
- ☐ 6 Special Flags
- ☐ Table Look-Up Ability
- ☐ S2210—CMOS Version of the S2200
- ☐ S2220—Microprocessor Bus-Compatible Version of S2200

Block Diagram
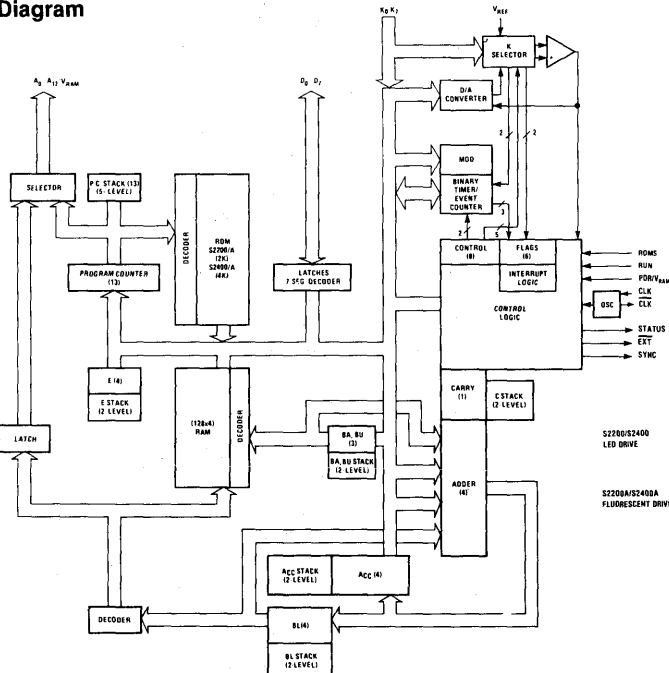
Pin Configuration
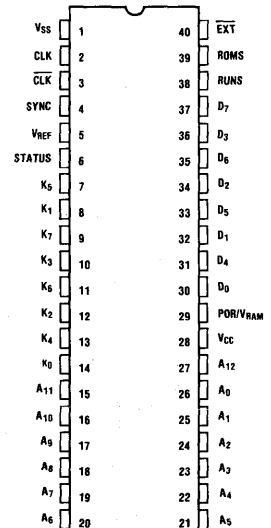
General Description

The S2200/S2400 provides a quantum jump in chip features beyond the S2000. In addition to all the features the S2000 offers, the S2200 gives the added flexibility of interrupts and the sophistication of an on-chip A/D and/or D/A converter capable of analog data making it suitable for a wide range of applications.

The 128×4 scratchpad RAM holds the temporary values of 4-bit data words, typically numeric quantities. The BA, BU and BL registers are used to access RAM words. The E Register can be used as a general purpose register or as an index limit register for controlling RAM access.

The ALU—Arithmetic Logic Unit—performs data operations, using the Accumulator and the Carry Register. Software can set reset and test Flags as temporary indicators.

The PLA which defines the 7-segment outputs of a DISN is user definable. The Control Logic includes three inputs and three outputs for interfacing external devices. The Oscillator generates all clocking signals and needs only an external RC circuit to set its rate. Optionally a crystal may be used to precisely control the oscillator frequency.

The K Lines are a full bi-directional port on the S2200 supporting A/D and D/A converters, interrupts, and a programmable counter/timer.

The eight bi-directional three-state D Lines are general-purpose data signals. The $\overline{EXT}$ signal is an output data strobe for the D Lines. On the S2220, the D Lines become the data bus interface. The thirteen A Lines are outputs for displays, keyboard strobes, control signals, or address lines for external ROM.

S2200/S2400/A/S2210
Instruction Set Summary

ADCS	ACC+RAM+CARRY, Skip if Sum ≤ 15	RANG	Read Analog Reg
ADD	ACC+RAM	RAR	Rotate ACC Right
ADIS X	ACC+X, Skip if Sum ≤ 15	RBIN	Read Binary Counter
AND	ACC "AND" RAM	RCTL	Read Control Reg
		RFLG W	Reset Flag W
CMA	Complement ACC	RSC	Reset Carry
DEV	Skip Always	RSM Z	Reset RAM Bit Z
DISB	Display Number in Binary Format	RSMI W	Reset RAM Bit W in Bank 1
DISN	Display Number in Seven Segment Format	RT	Return from Subroutine
		RTI	Return from Interrupt
IBLS	Increment BL and Skip if BL=0 after Incrementing	RTS	Return from Subroutine and Skip
IND	Input 8 Bits from D Lines	SAM	Skip if ACC=RAM
INK	Input 8 Bits from K Lines	SANG	Start A/D Conversion
		SBE	Skip if BL=E
JMP X	Jump	SCTL	Set Control Reg
JMS X	Jump to Subroutine	SFLG W	Set Flag W
JMSI	Jump to Subroutine Indexed	STA	Store ACC in RAM
		STC	Set Carry
LAB	Load ACC from BL	STM Z	Set RAM Bit Z
LAE	Load ACC from E	STMI Z	Set RAM Bit W in Bank 1
LAI X	LOAD ACC with X	SWI	Software Interrupt
LAM Y	LOAD ACC with RAM then BU "XOR"Y	SZC	Skip if Carry=0
LAM Y	Load ACC from RAM then BU "XOR"Y	SZK	Skip if K=0
LANG	Load Analog Reg	SZMI W	Skip if RAM Bit W in Bank 1=0
LBE Y	Load BL with E and BU with Y	SZM Z	Skip if RAM Bit Z=0
LBZ Y	Load BL with 0 and BU with Y		
LMOD	Load Modules Reg	TFLG W	Test Flag W
LRAI W	Modify RAM Address	TLU	Table Look-Up
MVS	Move Master Latch to Slave Latch	XAB	Exchange ACC and BL
		XABU	Exchange ACC and BA, BU
NOP	No Operation	XAE	Exchange ACC and E
		XAK	Exchange ACC and KSR
OUTD	Output 8 Bits to D Lines	XC Y	Exchange ACC and RAM, then BU "XOR"Y
OUTK	Output 8 Bits to K Lines	XCD Y	Exchange ACC and RAM, Decrement BL, BU
PP X	Prepare Page (or Bank)		"XOR"Y, and Skip if BL=0 Before
PSH	Preset Master Strobe High		Decrementing
PSL	Preset Master Strobe Low	XOR	ACC "Exclusive-OR" RAM

S2000/S2150 Appliance/Outlet Controller
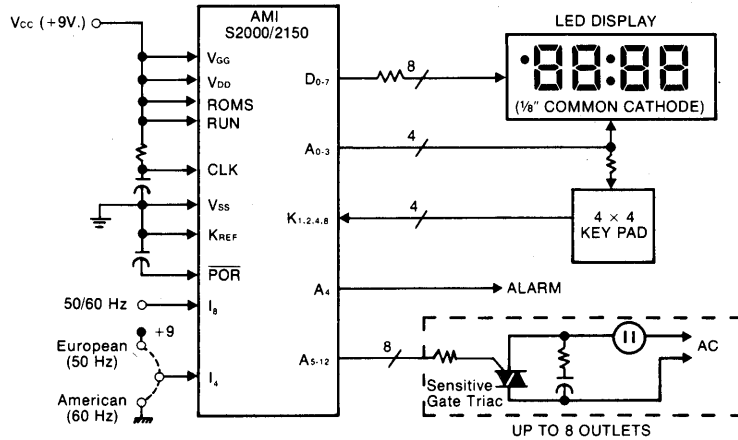
S2200A Microwave Oven Controller
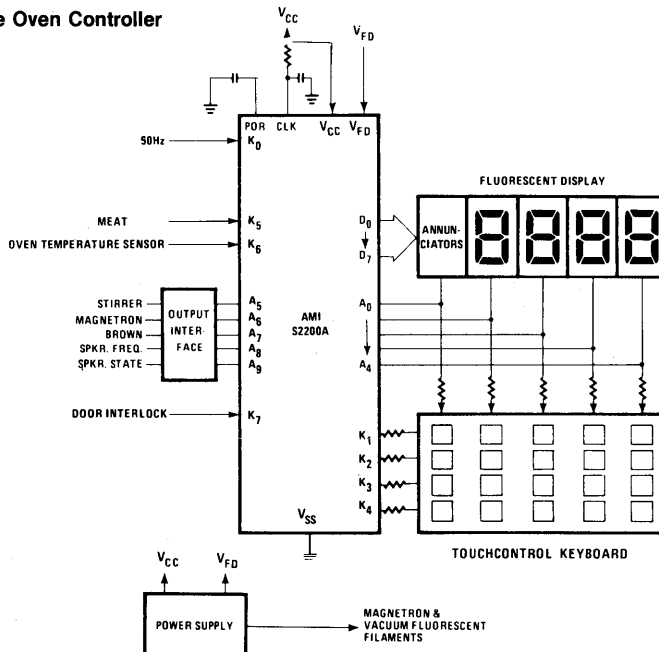
The S2000/S2200 Family has several options which need to be specified before an order can be placed. The forms on the following two pages call out by part number which options are available and what must be specified, e.g., package type, operating temperature range, pin count, etc. For most options, simply circle the appropriate response. However, for the 28 pin package option, Table 1 details which pins cannot be deleted and which pins *may* be deleted. To assure that the customer's pin configuration can be bonded within the package, always consult with Microcomputer Product Marketing before placing an order.

S2000 Family
Mask Option Specification Form
For the S2000/S2000A, S2150/S2150A/S2152   DATE _____

COMPANY   NAME _____

CONTACT _____ PHONE NUMBER (_____)_____EXT._____

P.O.# _____ S.O.#(For Factory Use Only) _____

FILE NAME (For Diskette Only)_____

I. S2000/S2000A:

     A. PACKAGE (circle one):   PLASTIC   CERAMIC   DIE

     B. OPERATING TEMPERATURE RANGE (circle one):   T1   T2   T3   T4

     C. PIN COUNT (circle one):   28   40

         IF 28, SPECIFY PINS (see Table 1): _____

T1 = 0°C to +55°C; T2 = 0°C to +70°C; T3 = 0°C to +85°C; T4 = −40°C to +85°C

II. S2150/S2150A/S2152:

     A. PACKAGE (circle one):   PLASTIC   CERAMIC   DIE

     B. OPERATING TEMPERATURE RANGE (circle one):   T1   T2   T3   T4

     C. PIN COUNT (circle one):   28   40

         IF 28, SPECIFY PINS (see Table 1): _____

     D. Clock (circle one):   Crystal   R-C

Table 1. Optional/Required Pin Table for S2000/S2200 Families

S2000/S2150				S2200				CONDITIONS/REASONS
PIN#	NAME	REQ.	OPT.	PIN#	NAME	REQ.	OPT.	
1	V_{SS}	X		1	V_{SS}	X		Power supply-Ground
29	V_{GG}	X		28	V_{CC}	X		Power supply-most positive: +9V or +5V
2,3,4, 36-40	D_0-D_7	X		30-37	D_0-D_7	X		Internal ROM Test
7-11, 36-40	A_0-A_{12}		X					Program Counter Monitor, comprises skip, stack & jump test cannot reliably test if all lines deleted
				15-27	A_0-A_{11}, A_{12}		X	
5	ROMS	X		39	ROMS	X		Internal ROM test
6	$\overline{EXT}$		X	40	$\overline{EXT}$		X	Optional if SOS, OUTD instructions not used
35	SYNC	X		4	SYNC	X		Required
34	RUN	X		38	RUN	X		Required
22	POR	X		29	POR/	X		Required
					VRAM		X	Mask Option
23	CLK	X		2	CLK	X		
				3	$\overline{CLK}$		X	Required only if crystal option is exercised
21	Status		X	6	Status/V_{FD}		X	
24	K_{REF}		X	5	V_{REF}		X	
				7-14	K_0-K_7	X		
12	V_{DD}/V_{FD}	X						Cannot be internally bonded to V_{GG}
25-28	I_1-I_8		X	30-33	K_1-K_8		X	
30-33	K_1-K_8		X					

This table shows which pins are required and optional for S2000/S2200 family devices. Those pins which are optional may be deleted in any mix to make a 28-pin package. If possible, pins should be deleted in as even a manner as possible to facilitate bonding the die to lead frame.

S2000 Family
Mask Option Specification Form
For the S2200/S2210/S2220/S2400

DATE _____

COMPANY NAME _____

CONTACT _____ PHONE NUMBER (_____)_____EXT._____

P.O.# _____ S.O.#(For Factory Use Only) _____

FILE NAME (For Diskette Only)_____

II. S2200/S2210/S2200/S2400

A. PACKAGE (circle one): PLASTIC   CERAMIC   DIE

B. PIN COUNT (circle one): 28   40

IF 28, SPECIFY PINS (see Table 1): _____

_____

_____

C. R = _____   F. D = _____

G. C = _____

D. P = _____   H. W = _____

E. I = _____   I. B. = _____

J. V_{FD}: Yes   No   ("A" Version)

K. OPERATING TEMPERATURE RANGE (circle one):   T1   T2   T3   T4

T1 = 0°C to +55°C; T2 = 0°C to +70°C; T3 = 0°C to +85°C; T4 = −40°C to +85°C

NAME OF OPTION	CODE		
RAM POWER	R	R = 1 TO 16:	RAM power is supplied from the $\overline{POR}/V_{RAM}$ Pin (see S2200 PDS)
		R = 0:	RAM is supplied from V_{CC}.
POWER-FAIL DETECTION	P	P = 1:	A non-maskable interrupt (jump to address 0400 HEX) occurs when $V_{CC} \leqslant V_{POR}$
		P = 0:	No interrupt for low V_{CC}
LOW-PRIORITY	I	I = 0:	K_6 & K_7 not connected to interrupt logic
INTERRUPT — K_7		I = 1:	K_6 only connected to interrupt logic
HI-PRIORITY		I = 2:	K_7 only connected to interrupt logic
INTERRUPT — K_6		I = 3:	Both K_6 & K_7 connected to interrupt logic
D/A OUTPUT	D	D = 1:	Digital-to-analog converter output appears at K_5
CLOCK OSCILLATOR	C	C = 1:	On-chip master oscillator configured to accept a piezoelectric crystal; can be driven by an external oscillator
		C = 0:	On-chip oscillatory uses an external resistor and capacitor; or can be driven by an external oscillator
RESET STATE OF A-LINE	W	W = 1:	Whenever the chip enters power-on reset, the "A" outputs are all set to ones
		W = 0:	"A" outputs are all zeroes after POR.
BUS COMPATIBILITY	B	B = 1:	Bus compatible option (S2220)
		B = 0:	Standard
			See Chapter 3 of PDS for S2200/S2400 et al.

Choice of wide operating temperature ranges may require slight derating of some electrical parameters; please consult with the factory.

AMI

AMERICAN MICROSYSTEMS, INC.

S6800

Microprocessor
Component Family

S6800

Eight Bit

μP

MICROPROCESSORS

S6800/S68A00/S68B00	8-Bit Microprocessor (1.0/1.5/2.0MHz XTAL)
S68H00	High Speed S6800 (2MHz Clock)
S6801/S6801E	Single Chip Microcomputer 2K ROM, 128×8 RAM, 31 I/O Lines, Enhanced Instruction Set (External [E] or Internal Clock)
S6802/S68A02	Microprocessor with Clock and RAM (1.0/1.5MHz Clock)
S6803/S6803N/R	S6801 Without ROM (N/R Model — No ROM and/or RAM)
S6805	Single Chip Microcomputer 1,152×8 ROM, 64×8 RAM, Clock, Pre-scaler, Bit Level Instructions.
S6808/S68A08	S6800 with Clock (1.0/1.5MHz Clock)
S6809(E)/S68A09(E)/S68B09(E)	Pseudo 16-Bit Microprocessor (1.0/1.5/2.0MHz Clock) (E Models — External Clock Mode)

PERIPHERALS

S1602	Universal Asynchronous Receiver/Transmitter (UART)
S2350	Universal Synchronous Receiver/Transmitter (USRT)
S6821/S68A21/S68B21	Peripheral Interface Adapter (PIA) (1.0/1.5/2.0MHz Clock)
S68H21	High Speed Peripheral Interface Adapter (PIA) (2.5MHz Clock)
S6840/S68A40/S68B40	Programmable Timer (1.0/1.5/2.0MHz)
S68045	CRT Controller (CRTC)
S6846	2K ROM, Parallel I/O, Programmable Timer
S68047	Video Display Generator (VDG)
S6850/S68A50/S68B50	Asynchronous Communication Interface Adapter 800 Bus Compatible
S6852/S68A52/S68B52	Asynchronous Communication Interface (1.0/1.5/2.0MHz Clock) (ACIA)
S6854/S68A54/S68B54	Advanced Data Link Controller (ADLC) (1.0/1.5/2.0MHz Clock)
S68488	IEEE — 488 Bus Interface
S6894	Data Encryption Unit (DEU)

MEMORIES

S6810/S68A10/S68B10	128×8 Static RAM (450/360/250ns Access Time)
S6810-1	Low Cost S6810 (575ns Access Time)

AMI
AMERICAN MICROSYSTEMS, INC.

S6800/S68A00/S68B00

8-BIT
MICROPROCESSOR

Features

- [ ] Eight-Bit Parallel Processing
- [ ] Bi-Directional Data Bus
- [ ] Sixteen-Bit Address Bus — 65536 Bytes of Addressing
- [ ] 72 Instructions — Variable Length
- [ ] Seven Addressing Modes — Direct, Relative Immediate, Indexed, Extended, Implied and Accumulator
- [ ] Variable Length Stack
- [ ] Vectored Restart
- [ ] 2 Microsecond Instruction Execution
- [ ] Maskable Interrupt Vector

- [ ] Separate Non-Maskable Interrupt — Internal Registers Saved in Stack
- [ ] Six Internal Registers — Two Accumulators, Index Register, Program Counter, Stack Pointer and Condition Code Register
- [ ] Direct Memory Access (DMA) and Multiple Processor Capability
- [ ] Clock Rates — S6800 — 1.0MHz
                — S68A00 — 1.5MHz
                — S68B00 — 2.0MHz
- [ ] Simple Bus Interface Without TTL
- [ ] Halt and Single Instruction Execution Capability

S6800

Block Diagram

Pin Configuration

Absolute Maximum Ratings

Supply Voltage V_{CC} .... -0.3 to $+7.0V$
Input Voltage V_{IN} .... $-0.3V$ to $+7.0V$
Operating Temperature Range T_A .... $0°C$ to $+70°C$
Storage Temperature Range T_{stg} .... $-55°C$ to $+150°C$

Electrical Characteristics

($V_{CC} = 5.0V$, $\pm 5\%$, $V_{SS} = 0$, T_A unless otherwise noted.)

Symbol	Characteristics		Min.	Typ.	Max.	Unit
V_{IH} V_{IHC}	Input High Voltage (Normal Operating Levels)	Logic $\phi1, \phi2$	$V_{SS} + 2.0$ $V_{CC} - 0.6$	— —	V_{CC} $V_{CC} + 0.3$	Vdc
V_{IL} V_{ILC}	Input Low Voltage (Normal Operating Levels)	Logic $\phi1, \phi2$	$V_{SS} - 0.3$ $V_{SS} - 0.3$	— —	$V_{SS} + 0.8$ $V_{SS} + 0.4$	Vdc
I_{IN}	Input Leakage Current ($V_{IN} = 0$ to $5.25V$, $V_{CC} = $ Max) ($V_{IN} = 0$ to $5.25V$, $V_{CC} = 0.0V$)	Logic* $\phi1, \phi2$	— —	1.0 —	2.5 100	μAdc
I_{TSI}	Three-State (Off State) Input Current $V_{IN} = 0.4$ to $2.4V$, $V_{CC} = $ Max	D0 — D7 A0 — A15, R/W	— —	2.0 —	10 100	μAdc
V_{OH}	Output High Voltage ($I_{LOAD} = 205\mu$Adc, $V_{CC} = $ Min) ($I_{LOAD} = 145\mu$Adc, $V_{CC} = $ Min) ($I_{LOAD} = -100\mu$Adc, $V_{CC} = $ Min)	D0 — D7 A0 — A15, R/W, VMA BA	$V_{SS} + 2.4$ $V_{SS} + 2.4$ $V_{SS} + 2.4$	— — —	— — —	Vdc
V_{OL}	Output Low Voltage ($I_{LOAD} \leq 1.6m$Adc, $V_{CC} = $ Min)		—	—	$V_{SS} + 0.4$	Vdc
P_D	Power Dissipation		—	0.5	1.0	W
C_{IN}	Capacitance# ($V_{IN} = 0$, $T_A = 25°C$, f = 1.0MHz)	$\phi1$ $\phi2$ D0 — D7 Logic Inputs	— — — —	— — 10 6.5	35 70 12.5 10	pF
C_{OUT}		A0 — A15, R/W, VMA	—	—	12	pF
f	Frequency of Operation	S6800 S68A00 S68B00	0.1 0.1 0.1	— — —	1.0 1.5 2.0	MHz
t_{CYC}	Clock Timing (Figure 1) Cycle Time	S6800 S68A00 S68B00	1.000 0.666 0.50	— — —	10 10 10	μs
$PW_{\phi H}$	Clock Pulse Width Measured at $V_{CC} - 0.6V$	$\phi1, \phi2$ — S6800 $\phi1, \phi2$ — S68A00 $\phi1, \phi2$ — S68B00	400 230 800	— — —	9500 9500 9500	ns ns
t_{UT}	Total $\phi1$ and $\phi2$ Up Time	S6800 S68A00 S68B00	900 600 440	— — —	— — —	ns
$t_{\phi r}, t_{\phi f}$	Rise and Fall Times Measured between $V_{SS} + 0.4$ and $V_{CC} - 0.6$		5.0	—	100	ns
t_d	Delay Time or Clock Separation Measured at $V_{OV} = V_{SS} + 0.6V$		0	—	9100	ns

*Except $\overline{IRQ}$ and $\overline{NMI}$, Which require $K\Omega$ pullup load resistor for wire-OR capability at optimum operation.
#Capacitances are periodically sampled rather than 100% tested.

S6800

Read/Write Timing

Symbol	Characteristics	S6800			S68A00			S68B00			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{AD}	Address Delay										ns
	C = 90pF	—	—	270	—	—	180	—	—	150	
	C = 30pF	—	—	250	—	—	165	—	—	135	
t_{ACC}	Periph. Read Access Time $t_{AC} = t_{UT} - (t_{AD} + t_{DSR})$	—	—	530	—	—	360	—	—	250	ns
t_{DSR}	Data Setup Time (Read)	100	—	—	60	—	—	40	—	—	ns
t_H	Input Data Hold Time	10	—	—	10	—	—	10	—	—	ns
t_H	Output Data Hold Time	10	25	—	10	25	—	10	25	—	ns
t_{AH}	Address Hold Time (Address, R/W, VMA)	30	50	—	10	75	—	10	75	—	ns
t_{EH}	Enable High Time for DBE Input	450	—	—	280	—	—	220	—	—	ns
t_{DDW}	Date Delay Time (Write)	—	—	225	—	165	200	—	—	160	ns
t_{PCS}	Processor Controls Proc. Control Setup Time	200	—	—	200	—	—	200	—	—	ns
$t_{PCr}; t_{PCf}$	Processor Control Rise and Fall Time	—	—	100	—	—	100	—	—	100	ns
t_{BA}	Bus Available Delay	—	—	250	—	—	270	—	—	270	ns
t_{TSE}	Three-State Enable	—	—	270	—	—	40	—	—	40	ns
t_{TSD}	Three-State Delay	—	—	—	—	—	270	—	—	270	ns
$t_{\overline{DBE}}$	Data Bus Enable Down Time During φ1 Up Time	150	—	—	150	—	—	70	—	—	ns
t_{DBEr}, t_{DBEf}	Data Bus Enable Rise and Fall Times	—	—	25	—	—	25	—	—	25	ns

Measurement point for φ1 and φ2 are shown below. Other measurements are the same as for MC6800.

Figure 1. Clock Timing Waveform

Figure 2. Read/Write Timing Waveform

Figure 3. Read Data From Memory or Peripherals

Figure 4. Write Data In Memory or Peripherals

Figure 5. Initialization of MPU After Restart

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S68H00

S6800
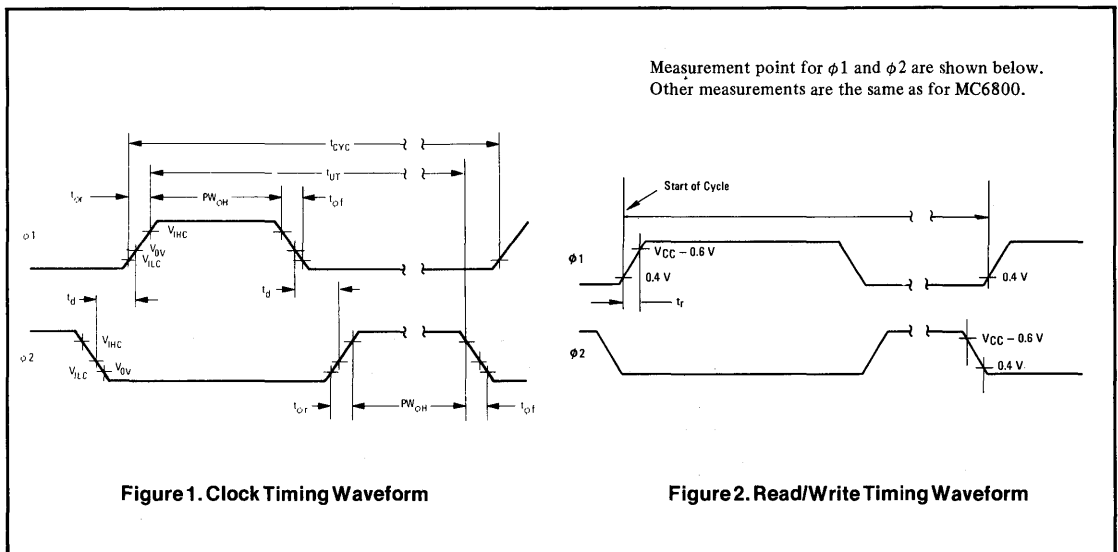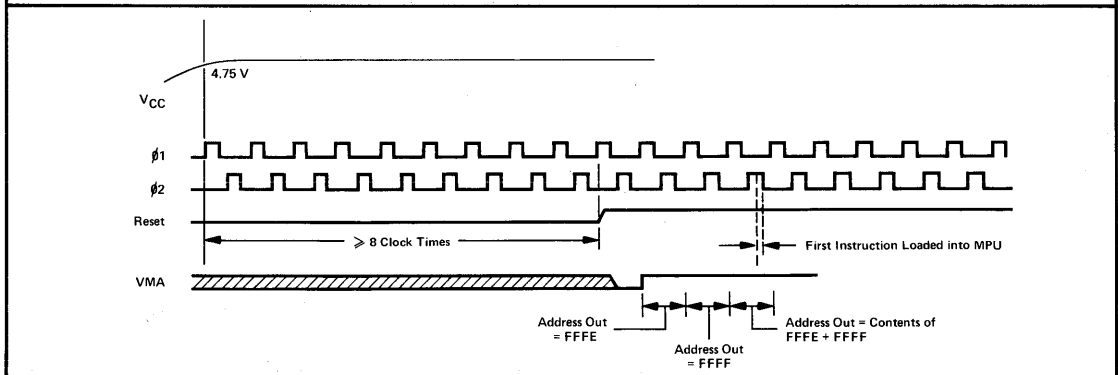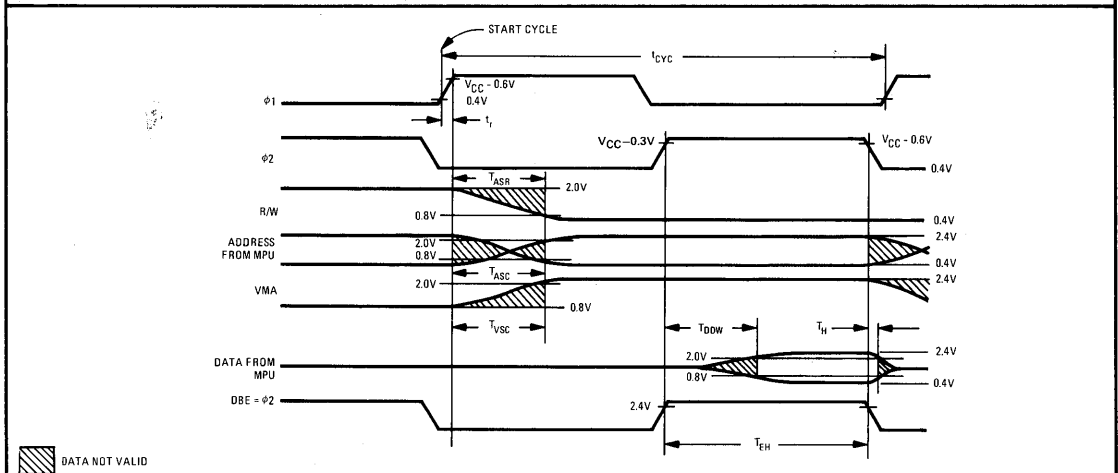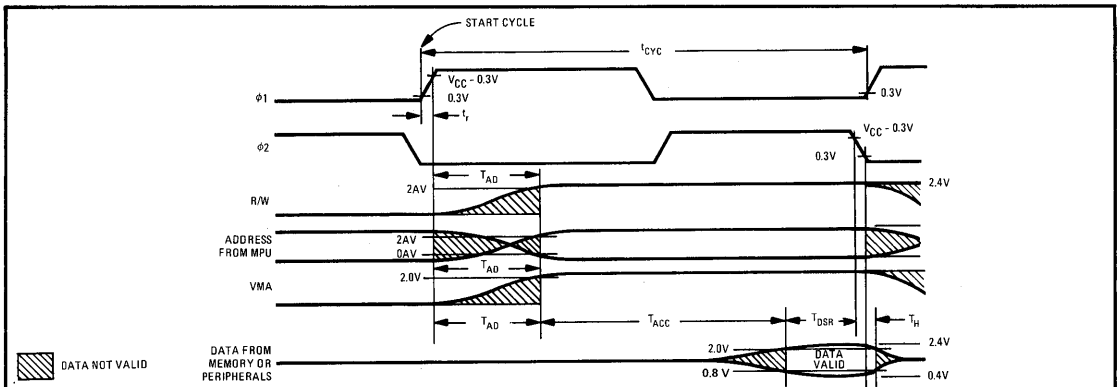
8-BIT
HIGH SPEED MICROPROCESSOR

Features

- Eight-Bit Parallel Processing
- Bi-Directional Data Bus
- Sixteen-Bit Address Bus — 65536 Bytes of Addressing
- 72 Instructions — Variable Length
- Seven Addressing Modes — Direct, Relative Immediate, Indexed, Extended, Implied and Accumulator
- Variable Length Stack
- Vectored Restart
- 400nsec Instruction Execution

- Maskable Interrupt Vector
- Separate Non-Maskable Interrupt — Internal Registers Saved in Stack
- Six Internal Registers — Two Accumulators, Index Register, Program Counter, Stack Pointer and Condition Code Register
- Direct Memory Access (DMA) and Multiple Processor Capability
- Clock Rate 2.5MHz
- Simple Bus Interface Without TTL
- Halt and Single Instruction Execution Capability

Block Diagram

Pin Configuration

5.7

Absolute Maximum Ratings

Supply Voltage V_{CC} .... -0.3 to $+7.0V$

Input Voltage V_{IN} .... $-0.3V$ to $+7.0V$

Operating Temperature Range T_A .... $0°C$ to $+70°C$

Storage Temperature Range T_{stg} .... $-55°C$ to $+150°C$

Electrical Characteristics

($V_{CC} = 5.0V$, $\pm 5\%$, $V_{SS} = 0$, T_A unless otherwise noted.)

Symbol	Characteristics		Min.	Typ.	Max.	Unit
V_{IH} V_{IHC}	Input High Voltage (Normal Operating Levels)	Logic $\phi1, \phi2$	$V_{SS}+2.0$ $V_{CC}-0.6$	— —	V_{CC} $V_{CC}+0.3$	Vdc
V_{IL} V_{ILC}	Input Low Voltage (Normal Operating Levels)	Logic $\phi1, \phi2$	$V_{SS}-0.3$ $V_{SS}-0.3$	— —	$V_{SS}+0.8$ $V_{SS}+0.4$	Vdc
I_{IN}	Input Leakage Current ($V_{IN} = 0$ to $5.25V$, $V_{CC} = $ Max) ($V_{IN} = 0$ to $5.25V$, $V_{CC} = 0.0V$)	Logic* $\phi1, \phi2$	— —	1.0 —	2.5 100	μAdc
I_{TSI}	Three-State (Off State) Input Current $V_{IN} = 0.4$ to $2.4V$, $V_{CC} = $ Max	D0 — D7 A0 — A15, R/W	— —	2.0 —	10 100	μAdc
V_{OH}	Output High Voltage ($I_{LOAD} = 205μAdc$, $V_{CC} = $ Min) ($I_{LOAD} = 145μAdc$, $V_{CC} = $ Min) ($I_{LOAD} = -100μAdc$, $V_{CC} = $ Min)	D0 — D7 A0 — A15, R/W, VMA BA	$V_{SS}+2.4$ $V_{SS}+2.4$ $V_{SS}+2.4$	— — —	— — —	Vdc
V_{OL}	Output Low Voltage ($I_{LOAD} = 1.6mAdc$, $V_{CC} = $ Min)		—	—	$V_{SS}+0.4$	Vdc
P_D	Power Dissipation		—	0.5	1.0	W
C_{IN}	Capacitance# ($V_{IN} = 0$, $T_A = 25°C$, $f = 1.0MHz$)	$\phi1$ $\phi2$ D0 — D7 Logic Inputs	— — — —	— — 10 6.5	35 70 12.5 10	pF
C_{OUT}		A0 — A15, R/W, VMA	—	—	12	pF
f	Frequency of Operation	S68H00	0.1	—	2.5	MHz
t_{CYC}	Clock Timing (Figure 1) Cycle Time	S68H00	0.4 —	— —	10 10	μs
$PW_{\phi H}$	Clock Pulse Width Measured at $V_{CC}-0.6$	$\phi1, \phi2$ — S68H00	165 —	— —	9500 9500	ns ns
t_{UT}	Total $\phi1$ and $\phi2$ Up Time	S68H00	4.20	—	—	ns
$t_{\phi r}, t_{\phi f}$	Rise and Fall Times Measured between $V_{SS}+0.4$ and $V_{CC}-0.6$		5.0	—	100	ns
t_d	Delay Time or Clock Separation Measured at $V_{OV} = V_{SS}+0.6$		0	—	9100	ns

*Except $\overline{IRQ}$ and $\overline{NMI}$, Which require $K\Omega$ pullup load resistor for wire-OR capability at optimum operation.

#Capacitances are periodically sampled rather than 100% tested.

Read/Write Timing

Symbol	Characteristics		Min	Typ	Max	Unit
t_{AD}	Address Delay					ns
		$C = 90pF$	—	—	140	
		$C = 30pF$	—	—	125	
t_{ACC}	Periph. Read Access Time $t_{AC} = t_{UT} - (t_{AD} + t_{DSR})$		—	—	235	ns
t_{DSR}	Data Setup Time (Read)		35	—	—	ns
t_H	Input Data Hold Time		10	—	—	ns
t_H	Output Data Hold Time		10	25	—	ns
t_{AH}	Address Hold Time (Address, R/W, VMA)		10	75	—	ns
t_{EH}	Enable High Time for DBE Input		205	—		ns
t_{DDW}	Date Delay Time (Write)		—	165	155	ns
	Processor Controls					
t_{PCS}	Proc. Control Setup Time		200	—	—	ns
$t_{PCr}; t_{PCf}$	Processor Control Rise and Fall Time		—	—	100	ns
t_{BA}	Bus Available Delay		—	—	270	ns
t_{TSE}	Three-State Enable		—	—	40	ns
t_{TSD}	Three-State Delay		—	—	270	ns
$t_{\overline{DBE}}$	Data Bus Enable Down Time During $\phi1$ Up Time		65	—	—	ns
$t_{DBEr}; t_{DBEf}$	Data Bus Enable Rise and Fall Times		—	—	25	ns

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Measurement point for $\phi1$ and $\phi2$ are shown below.
Other measurements are the same as for MC6800.

Figure 1. Clock Timing Waveform   Figure 2. Read/Write Timing Waveform

AMI
AMERICAN MICROSYSTEMS, INC.
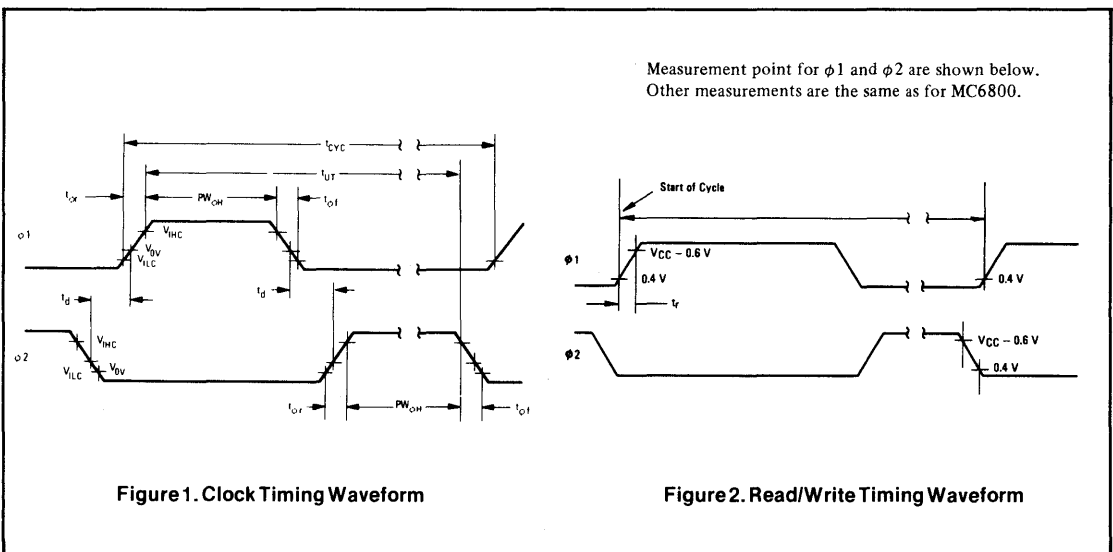
SINGLE CHIP
MICROCOMPUTER

Features

- Instruction and Addressing Compatible
- Object Code Compatible
- 16-Bit Programmable Timer
- Single Chip or Expandable to 65K Words
- On-Chip Serial Communications Interface (SCI)
  - Simplex
  - Half Duplex
    - Mark/Space (NRZ)
    - Biphase (FM)
  - Port Expansion
    - Full/Half Duplex
- Four Internal Baud Rates Available:
  $\phi 2 \div 16, 128, 1024, 4096$
- 2K Bytes of ROM
- 128 Bytes of RAM
  (64 Bytes Power Down Retainable)

- 31 Parallel I/O Lines
- Divide-by-Four Internal Clock
- Hardware 8×8 Multiply
- Three Operating Modes
  - Single Chip
  - Expanded Multiplex (up to 65K Addressing)
  - Expanded Non-Multiplex
- S6801E Operating Modes
  - Peripheral Controller
  - Expanded Non-Multiplexed
  - Expanded Multiplex
- Expanded Instruction Set
- Interrupt Capability
- Low Cost Versions
  - S6803—No ROM Version
  - S6803NR—No ROM or RAM
- TTL-Compatible with Single 5 Volt Supply

Block Diagram

Pin Configuration
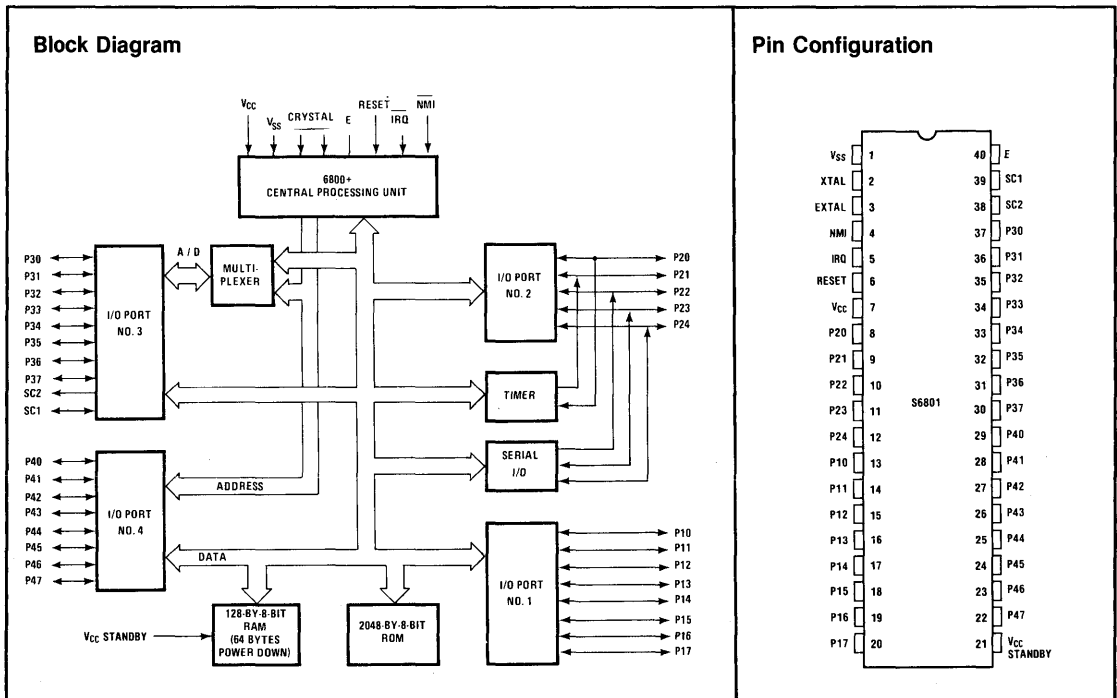
General Description

The S6801 MCU is an 8-bit single-chip microcomputer system which is compatible with the S6800 family of parts. The S6801 is object code compatible with the S6800 instruction set.

The S6801 features improved execution times of key S6800 instructions including Jump to Subroutine (JSR) and all Conditioned Branches (BRA, etc.). In addition, several new 16-bit and 8-bit instructions have been added including Push/Pull to/from Stack, Hardware 8×8 Multiply, and store concatenated A and B accumulators (D accumulator).

The S6801 MCU can be operated in three modes: Single-Chip, Expanded Multiplex (up to 65K Byte Addressing), and Expanded Non-Multiplex. In addition, the S6801 is available with two mask options: an on-chip (÷4) Clock, or an external (÷1) Clock. The external mode is especially useful in Multiprocessor Applications. The S6801E can be configured as a peripheral by using the Read/Write (R/$\overline{W}$), Chip Select (CS), and Register Select (RS). The Read/Write line controls the direction of data on Port 3

and the Register Select (RS) allows for access to either Port 3 data register or control register.

The S6801 Serial Communications Interface (SCI) permits full serial communication using no external components in several operating modes—Full and/or Half Duplex operation—and two formats—Standard Mark/ Space for typical Terminal/Modem interfaces and the Bi-Phase (FM, F2F, and Manchester) Format primarily for use between processors. Four software addressable registers are provided to configure the Serial Port; to provide status information; and as transmit/receive data buffers.

The S6801 includes a 16-bit timer with three effectively independent timing functions: (1) Variable pulse width measurement, (2) Variable pulse width generation, and (3) A Timer Overflow—Find Time Flag. This makes the S6801 ideal for applications such as Industrial Controls, Automotive Systems, A/D or D/A Converters, Modems, Real-Time Clocks, and Digital Voltage Controlled Oscillators (VCO).

The S6801 is fully TTL-compatible and requires only a single +5 volt supply.

Absolute Maximum Ratings

Supply Voltage, V_{CC} .... −0.3V to +7.0V
Input Voltage, V_{IN} .... −0.3V to +7.0V
Operating Temperature Range, T_A .... 0° to +70°C
Storage Temperature Range, T_{stg} .... −55°C to +150°C
Thermal Resistance, θ_{JA}
  Plastic .... 100°C/W
  Ceramic .... 50°C/W

This device contains circuitry to protect the inputs against damage due to high static voltage or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation it is recommended that V_{IN} and V_{OUT} be constrained to the range V_{SS} (V_{IN} or V_{OUT}) V_{DD}.

Electrical Characteristics: $V_{CC} = 5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = T_L$ to T_H unless otherwise noted

Symbol	Characteristic	Min.	Typ.	Max.	Unit
V_{IH}	Input High Voltage	$V_{SS} + 2.0$		V_{CC}	Vdc
	$\overline{Reset}$	$V_{SS} + 4.0$		V_{CC}	
V_{IL}	Input Low Voltage	$V_{SS} - 0.3$		$V_{SS} + 0.8$	Vdc
I_{TSI}	Three-State (Off State) Input Current P10-P17		2.0	10	μAdc
I_{TSI}	($V_{IN} = 0.4$ to 2.4 Vdc) P20-P24, P30-P37		2.0	10	μAdc
V_{OH}	Output High Voltage All Outputs Except XTAL 1 and EXTAL 2 $I_{LOAD} = -200\mu$Adc	$V_{SS} + 2.4$			Vdc
V_{OL}	Output Low Voltage All Outputs Except XTAL 1 and EXTAL 2 $I_{LOAD} = 1.6$mAdc			$V_{SS} + 0.4$	Vdc

Electric Characteristics (Continued)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
P_D	Power Dissipation			1200	mW
C_{IN}	Capacitance $V_{IN}=0$, $T_A=25\,°C$, $f=1.0MHz$ P10-P17, P20-P24, P40-P47, P30-P37 Reset SC1, SC2, IRQ			12.5 10 7.5	pF
t_{PDSU}	Peripheral Data Setup Time (Figure 3)	200			ns
t_{PDH}	Peripheral Data Hold Time (Figure 3)	0			ns
t_{OSD1}	Delay Time, Enable negative transition to OS3 Neg. Trans.			1.0	μs
t_{OSD2}	Delay Time, Enable neg. trans. to OS3 positive transition			1.0	μs
t_{PWD}	Delay Time, Enable negative transition to Peripheral Data Valid (Figure 4)			350	ns
t_{CMOS}	Delay Time, Enable negative transition to Peripheral Data Valid ($V_{SS}-30\%$ V_{CC}, P20-P24 (Figure 4)			2.0	μs
I_{OH}	Darlington Drive Current $V_O=1.5Vdc$ — P10-P17	-1.0	-2.5	-10	mAdc
V_{SBB} V_{SB}	Standby Voltage (Not Operating) (Operating)	4.00 4.75		5.25 5.25	Vdc

NOTE: *The above electricals satisfy Ports 1 and 2 always, and Ports 3 and 4 in the single chip mode only.*

Bus Timing (Figure 7)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
t_{CYC}	Cycle Time	1000			ns
P_{WASH}	Address Strobe Pulse Width High	220			ns
t_{ASR}	Address Strobe Rise Time			50	ns
t_{ASF}	Address Strobe Fall Time			50	ns
t_{ASD}	Address Strobe Delay Time	60			ns
t_{ER}	Enable Rise Time			50	ns
t_{EF}	Enable Fall Time			50	ns
P_{WEH}	Enable Pulse Width High Time	450			ns
P_{WEL}	Enable Pulse Width Low Time	450			ns
t_{ASED}	Address Strobe to Enable Delay Time	60			ns
t_{AD}	Address Delay Time			270	ns
t_{DDW}	Data Delay Write Time			225	ns
t_{DSR}	Data Set-up Time	100			ns
t_{HR}	Hold Time Read	20		100	ns
t_{HW}	Hold Time Write	20			ns
t_{ADL}	Address Delay Time for Latch			200	ns
t_{AHL}	Address Hold Time for Latch	20			ns
PW_O	Pulse Width	370	370		ns
t_{AH}	Address Hold Time	20			ns
t_{UT}	Total Up Time	750			ns

MCU Signal Description

This section gives a description of the MCU signals for the various modes. General pin assignments for the signals are shown on page 1. SC1 and SC2 are signals which vary with the mode that the chip is in. Table 1 gives a summary of their function.

Table 1. Mode and Port Summary

MODE	PORT 1 EIGHT LINES	PORT 2 FIVE LINES	PORT 3 EIGHT LINES	PORT 4 EIGHT LINES	SC1	SC2
SINGLE CHIP	I/O	I/O	I/O	I/O	$\overline{IS3}$(I)	$\overline{OS3}$(O)
EXPANDED MUX	I/O	I/O	ADDRESS BUS (A0-A7) DATA BUS D0-D7	ADDRESS BUS* (A8-A15)	AS(O)	R/$\overline{W}$(O)
EXPANDED NON-MUX	I/O	I/O	DATA BUS D0-D7	ADDRESS BUS* (A0-A7)	$\overline{IOS}$(O)	R/$\overline{W}$(O)

*THESE LINES CAN BE SUBSTITUTED FOR I/O (INPUT ONLY) STARTING WITH THE MOST SIGNIFICANT ADDRESS LINE.

I = INPUT	IS = INPUT STROBE	SC = STROBE CONTROL
0 = OUTPUT	OS = OUTPUT STROBE	AS = ADDRESS STROBE
R/$\overline{W}$ = READ/$\overline{WRITE}$	IOS = I/O SELECT	

Read/Write Timing for Ports 3 and 4 (Figures 1-2)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
t_{AD}	Address Delay			270	ns
t_{ACC}	Peripheral Read Access Time $t_{ACC} = t_{UT} - (t_{AD} + t_{DSR})$			530	ns
t_{DSR}	Data Setup Time (Read)	100			ns
t_{HR}	Input Data Hold Time	10			ns
t_{HW}	Output Data Hold Time	20			ns
t_{AH}	Address Hold Time (Address, R/W)	20			ns
t_{DDW}	Data Delay Time (Write)		165	225	ns
t_{PCS} t_{PCr}, t_{PCf}	Processor Controls Processor Control Setup Time Processor Control Rise and Fall Time (Measured between 0.8V and 2.0V)	200		100	ns ns

Port 3 Strobe Timing (Figures 5-6)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
t_{DSD1}	Output Strobe Delay 1			100	μs
t_{OSD2}	Output Strobe Delay 2			100	μs
PW_{IS}	Input Strobe Pulse Width	200			ns
t_{IH}	Input Data Hold Time	20			ns
t_{IS}	Input Data Setup Time	100			ns

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**Figure 1. Read Data From Memory or Peripherals
           Expanded Non-Multiplexed**
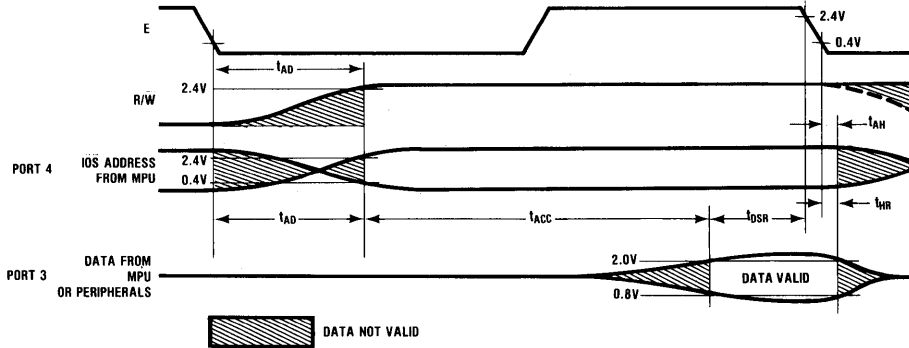
**Figure 2. Write Data In Memory or Peripherals
           Expanded Non-Multiplexed**
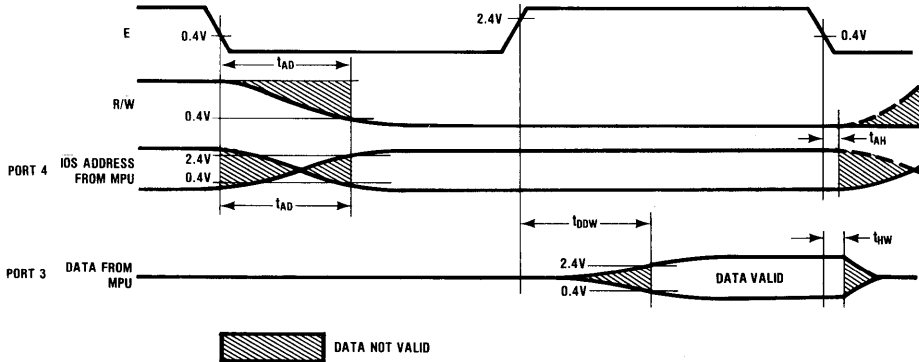
Ports 1 and 2, and Ports 3 and 4 in the Single Chip Mode

**Figure 3. Peripheral Data Setup and Hold Times
           (Read Mode)**
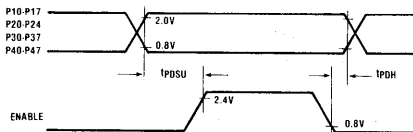
**Figure 4. Peripheral CMOS Data Delay Times
           (Write Mode)**

Figure 5. Output Strobe Timing — Single Chip Mode

Figure 6. Input Strobe Timing — Single Chip Mode

Figure 7. Multiplexed Bus Timing

S6800

Figure 8. CMOS Load

TEST POINT ○——————

30pF
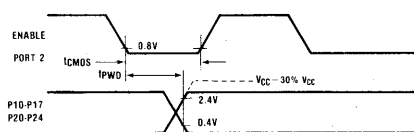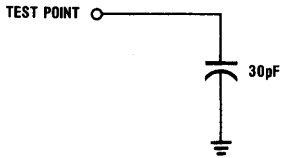
Figure 9. Bus Timing Test Load and Ports 1, 3 and 4 for Single Chip Mode

Vcc

$R_L = 2.2K$

TEST POINT ○

MMD6150
OR EQUIV.

C   R

MMD7000
OR EQUIV.

C = 90pF FOR P30-P37, P40-P47, E, SC1, SC2
R = 16.5KΩ FOR P30-P37, P40-P47, E, SC1, SC2
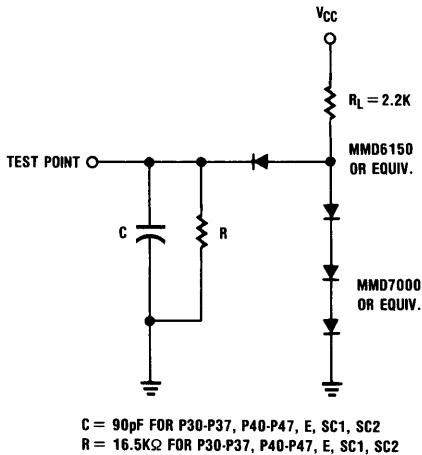
Figure 10. Test Loads for Port 1 Darlington Load (P10-P17)

Vcc

R_L

I_1

TEST POINT ○

V_1

MMD6150
OR EQUIV.

C   R

MMD7000
OR EQUIV.

C = 40 R_L, R = 12K
ADJUST R_L SO THAT I_1 = 3.2mA
WITH V_1 = 0.4V and V_{CC} = 5.25V
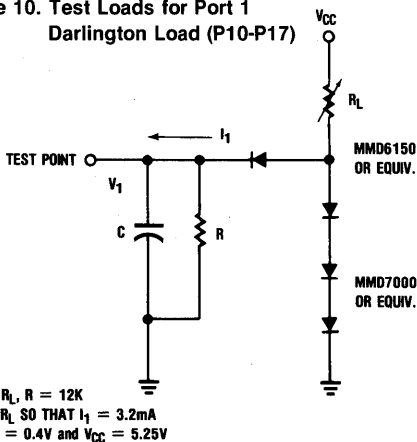
Figure 11. Typical Data Bus Output Delay versus Capacitive Loading

I_{OH} = 205µA MAX @ 2.4V
I_{OL} = 1.6mA MAX @ 0.4V
V_{CC} = 5.0V
T_A = 25°C

DELAY TIME (ns)

C_L INCLUDES STRAY CAPACITANCE

C_L LOAD CAPACITANCE (pF)
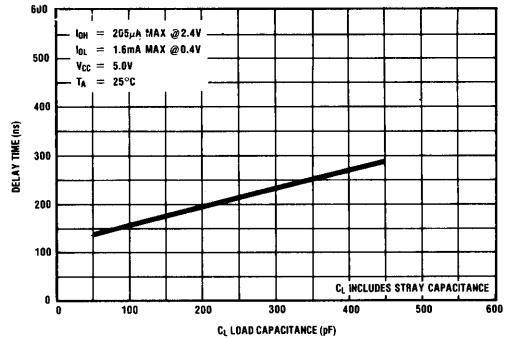
Figure12. Typical Read/Write, VMA, and Address Output Delay Versus Capacitive Loading

I_{OH} = 145µA MAX @ 2.4V
I_{OL} = 1.6mA MAX @ 0.4V
V_{CC} = 5.0V
T_A = 25°C

DELAY TIME (ns)

ADDRESS, VMA

R/W

C_L INCLUDES STRAY CAPACITANCE

C_L LOAD CAPACITANCE (pF)
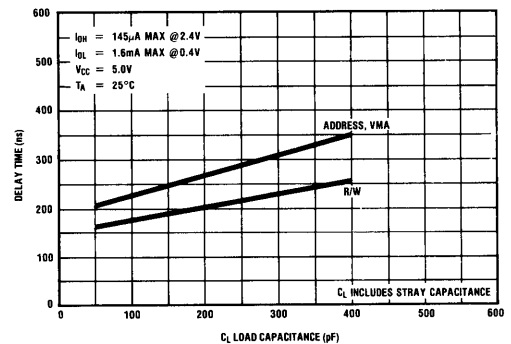
Signal Descriptions

V_{CC} and V_{SS}

These two pins are used to supply power and ground to the chip. The voltage supplied will be +5 volts±5%.

XTAL 1 and EXTAL 2

These connections are for a parallel resonant fundamental crystal, AT cut. Divide by 4 circuitry is included with the internal clock, so a 4 MHz crystal may be used to run the system at 1MHz. The divide by 4 circuitry allows for use of the inexpensive 3.56 MHz Color TV crystal for non-time critical applications. Two 27pF capacitors are needed from the two crystal pins to ground to insure reliable operation. EXTAL 2 may be driven by an external clock source at a 4 MHz rate to run at 1 MHz with a 40/60% duty cycle. It is not restricted to 4 MHz. XTAL 1

must be grounded if an external clock is used. The following are the recommended crystal parameters:

> AT = Cut Parallel Resonance Crystal
> $C_0 = 7pF$ Max
> FREQ = 4.0 MHz @ $C_L = 24pF$
> $R_S = 50$ ohms Max
> Frequency Tolerance = ±5% to ±0.02%
> The best E output "Worst Case
> Design" tolerance is ±0.05% (500ppM)
> using a ±0.02% crystal.

V_{CC} Standby

This pin will supply +5 volts ±5% to the standby RAM on the chip. The first 64 bytes of RAM will be maintained in the power down mode with 8 mA current max in the ROM version. The circuit of Figure 15 can be utilized to assure that V_{CC} Standby does not go below V_{SBB} during power down.

To retain information in the RAM during power down the following procedure is necessary:

1) Write "0" into the RAM enable bit, RAM E. RAM E is bit 6 of the RAM Control Register at location $0014. This disables the standby RAM, thereby protecting it at power down.

2) Keep V_{CC} Standby greater than V_{SBB}.

Figure 13. Battery Backup for V_{CC} Standby

V_{CC} STANDBY o———————o V_{CC}

5.25V
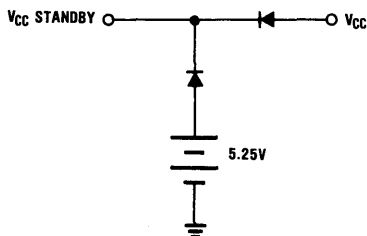
Reset

This input is used to reset and start the MPU from a power down condition, resulting from a power failure or an initial startup of the processor. On power up, the reset must be held low for at least 20 ms. During operation, $\overline{Reset}$, when brought low, must be held low at 3 clock cycles.

When a high level is detected, the MPU does the following:

a) All the higher order address lines will be forced high.

b) I/O Port 2 bits, 2, 1, and 0 are latched into programmed control bits PC2, PC1 and PC0.

c) The last two (FFFE, FFFF) locations in memory will be used to load the program addressed by the program counter.

d) The interrupt mask bit is set, must be cleared before the MPU can recognize maskable interrupts.

Enable (E)

This supplies the external clock for the rest of the system when the internal oscillator is used. It is a single phase, TTL compatible clock, and will be the divide by 4 result of the crystal frequency. It will drive one TTL load and 90pF.

Non-Maskable Interrupt ($\overline{NMI}$)

A low-going edge on this input requests that a non-maskable-interrupt sequence be generated within the processor. As with the Interrupt Request signal, the processor will complete the current instruction that is being executed before it recognizes the $\overline{NMI}$ signal. The interrupt mask bit in the Condition Code Register has no effect on $\overline{NMI}$.

In response to an $\overline{NMI}$ interrupt, the Index Register, Program Counter, Accumulators, and Condition Code Register are stored on the stack. At the end of the sequence, a 16-bit address will be loaded that points to a vectoring address located in memory locations FFFC and FFFD. An address loaded at these locations causes the MPU to branch to a non-maskable interrupt service routine in memory.

A 3.3 KΩ external resistor to V_{CC} should be used for wire-OR and optimum control of interrupts.

Inputs $\overline{IRQ}$ and $\overline{NMI}$ are hardware interrupt lines that are sampled during E and will start the interrupt routine on the clock bar following the completion of an instruction.

Interrupt Request ($\overline{IRQ}$)

This level sensitive input requests that an interrupt sequence be generated within the machine. The processor will wait until it completes the current instruction that is being executed before it recognizes the request. At that time, if the interrupt mask bit in the Condition Code Register is not set, the machine will begin an interrupt sequence. The Index Register, Program Counter, Accumulators, and Condition Code Register are stored on the

stack. Next the MPU will respond to the interrupt request by setting the interrupt mask bit high so that no further maskable interrupts may occur. At the end of the cycle, a 16-bit address will be loaded that points to a vectoring address which is located in memory locations FFF8 and FFF9. An address loaded at these locations causes the MPU to branch to an interrupt routine in memory.

The IRQ requires a 3.3KΩ external resistor to V_{CC} which should be used for wire-OR and optimum control of interrupts. Internal Interrupts will use an internal interrupt line (IRQ2). This Interrupt will operate the same as IRQ except that it will use the vector address of FFF0 and FFF7. IRQ1 will have priority over IRQ2 if both occur at the same time. The Interrupt Mask Bit in the condition mode register masks both interrupts. (See Figure 23.)

The following pins are available in the Single Chip Mode, and are associated with Port 3 only.

Input Strobe ($\overline{IS3}$) (SC1)

This sets an interrupt for the processor when the IS3 Enable bit is set. As shown in Figure 6 Input Strobe Timing, IS3 will fall T_{IS} minimum after data is valid on Port 3. If IS3 Enable is set in the I/O Port Control/Status Register, an interrupt will occur. If the latch enable bit in the I/O Control Status Register is set, this strobe will latch the input data from another device when that device has indicated that it has valid data.

Output Strobe ($\overline{OS3}$) (SC2)

This signal is used by the processor to strobe an external device, indicating valid data is on the I/O pins. The timing for the Output Strobe is shown in Figure 5. I/O Port Control/Status Register is discussed in the following section.

The following pins are available in the Expanded Modes.

Read Write (R/W) (SC2)

This TTL compatible output signals the peripherals and memory devices whether the MPU is in a Read (high) or a Write (low) state. The normal standby state of this signal is Read (high). This output is capable of driving one TTL load and 90pF.

I/O Strobe ($\overline{IOS}$) (SC1)

In the expanded non-multiplexed mode of operation, $\overline{IOS}$ internally decodes A9 through A15 as zero's and A8 as a one. This allows external access of the 256 locations from $0100 to $01FF. The timing diagrams are shown as Figures 1 and 2.

Address Strobe (AS) (SC1)

In the expanded multiplexed mode of operation address strobe is output on this pin. This signal is used to latch the 8 LSB's of address which are multiplexed with data on Port 3. An 8-bit latch is utilized in conjunction with Address Strobe, as shown in Figure 27. Expanded Multiplexed Mode. Address Strobe signals the latch when it is time to latch the address lines so the lines can become data bus lines during the E pulse. The timing for this signal is shown in the MC6801 Bus Timing Figure 7. This signal is also used to disable the address from the multiplexed bus allowing a deselect time, T_{ASD} before the data is enabled to the bus.

S6801 Ports

There are four I/O ports on the S6801MCU; three 8-bit ports and one 5-bit port. There are two control lines associated with one of the 8-bit ports. Each port has an associated write only Data Direction Register which allows each I/O line to be programmed to act as an input or an output. *A "1" in the corresponding Data Direction Register bit will cause that I/O line to be an output A "0" in the corresponding Data Direction Register bit will cause the I/O line to be an input. There are four ports: Port 1, Port 2, Port 3, and Port 4. Their addresses and the addresses of their Data Direction registers are given in Table 2.

*The only exception is bit 1 of Port 2, which can either be data input or Timer output.

Table 2. Port and Data Direction Register Addresses

Ports	Port Address	Data Direction Register Address
I/O Port 1	$0002	$0000
I/O Port 2	$0003	$0001
I/O Port 3	$0006	$0004
I/O Port 4	$0007	$0005

I/O Port 1

This is an 8-bit port whose individual bits may be defined as inputs or outputs by the corresponding bit in its data direction register. The 8 output buffers have three-state capability, allowing them to enter a high impedance state when the peripheral data lines are used as inputs. In

order to be read properly, the voltage on the input lines must be greater than 2.0 volts for a logic "1" and less than 0.6 volt for a logic "0". As outputs, these lines are TTL compatible and may also be used as a source of up to 1 mA at 1.5 volts to directly drive a Darlington base. After Reset, the I/O lines are configured as inputs. In all three modes, Port 1 is always parallel I/O.

I/O Port 2

This port has five lines that may be defined as inputs or outputs by its data direction register. The 5 output buffers have three-state capability, allowing them to enter a high impedance state when used as an input. In order to be read properly, the voltage on the input lines must be greater than 2.0 volts for a logic "1" and less than 0.8 volt for a logic "0". As outputs, this port has no internal pullup resistors but will drive TTL inputs directly. For driving CMOS inputs, external pullup resistors are required. After Reset, the I/O lines are configured as inputs. Three pins on Port 2 (pins 10, 9 and 8 of the chip) are used to program the mode of operation during reset. The values of these pins at reset are latched into the three MSB's (bits 7, 6, and 5) of Port 2 which are read only. This is explained in the Mode Selection Section.

In all three modes, Port 2 can be configured as I/O and provides access to the Serial Communications Interface and the Timer. Bit 1 is the only pin restricted to data input or Timer output.

I/O Port 3

This is an 8-bit port that can be configured as I/O, a data bus, or an address bus multiplexed with the data bus — depending on the mode of operation hardware programmed by the user at reset. As a data bus, Port 3 is bi-directional. As an input for peripherals, it must be supplied regular TTL levels, that is, greater than 2.0 volts for a logic "1" and less than 0.5 volt for a logic "0".

Its TTL compatible three-state output buffers are capable of driving one TTL load and 90pF. In the Expanded Modes, after reset, the data direction register is inhibited and data flow depends on the state of the R/W line. The input strobe (IS3) and the output strobe (OS3) used for handshaking are explained later.

In the three modes Port 3 assumes the following characteristics:

Single Chip Mode: Parallel Inputs/Outputs as programmed by its associated Data Direction Register. There are two control lines associated with this port in

this mode, an input strobe and an output strobe, that can be used for handshaking. They are controlled by the I/O Port Control/Status Register explained at the end of this section.

Expanded Non-Multiplexed Mode: In this mode Port 3 become the data bus (D7-D0).

Expanded Multiplexed Mode: In this mode Port 3 becomes both the data bus (D7-D0) and lower bits of the address bus (A7-A0). An address strobe output is true when the address is on the port.

I/O Port 3 Control/Status Register

	7	6	5	4	3	2	1	0
$000F	IS3 FLAG	IS3 ENABLE	X	OSS	LATCH ENABLE	X	X	X

Bit 0 Not used.
Bit 1 Not used.
Bit 2 Not used.
Bit 3 Latch Enable. This controls the input latch for I/O Port 3. If this bit is set high the input data will be latched with the falling edge of the Input Strobe, IS3. This bit is cleared by reset, or CPU Read Port 3.
Bit 4 (OSS) Output Strobe Select. This bit will select if the Output Strobe should be generated by a write to I/O Port 3 or a read of I/O Port 3. When this bit is cleared the strobe is generated by a read Port 3. When this bit is set the strobe is generated by a write Port 3.
Bit 5 Not used.
Bit 6. IS3 ENABLE. This bit will be the interrupt caused by IS3. When set to a low level the IS3 FLAG will be set by input strobe but the interrupt will not be generated. This bit is cleared by reset.
Bit 7 IS3 FLAG. This is a read only status bit that is set by the failing edge of the input strobe, IS3. It is cleared by a read of the Control/Status Register followed by a read or write of I/O Port 3. Reset will clear this bit.

I/O Port 4

This is an 8-bit port that can be configured as I/O or as address lines depending on the mode of operation. In order to be read properly, the voltage on the input lines must be greater than 2.0 volts for a logic "1" and less

than 0.8 volt for a logic "0". As outputs, each line is TTL compatible and can drive 1 TTL load and 90pF. After reset, the lines are configured as inputs. To use the pins as addresses, therefore, they should be programmed as outputs in the three modes. Port 4 assumes the following characteristics.

Single Chip Mode: Parallel Inputs/Outputs as programmed by its associated Data Direction Register.

Expanded Non-Multiplexed Mode: In this mode Port 4 is configured as the lower order address lines (A7-A0) by writing one's to the data direction register. When all eight address lines are not needed, the remaining line starting with the most significant bit, may be used as I/O (inputs only).

Expanded Multiplexed Mode: In this mode Port 4 is configured as the high order address lines (A15-A8) by writing one's to the data direction register. When all eight address lines are not needed, the remaining line, starting with the most significant bit, may be used as I/O (inputs only).

Mode Selection

The mode of operation that 6801 will operate in after Reset is determined by hardware that the user must wire on pins 10, 9, and 8 of the chip. These pins are the three LSB's (I/O2, I/O1, and I/O0 respectively) of Port 2. They are latched into programmed control bits PC2, PC1, and PC0 when reset goes high. I/O Port 2 Register is shown below.

$0003	7	6	5	4	3	2	1	0
	PC2	PC1	PC0	I/O4	I/O3	I/O2	I/O1	I/O0

An example of external hardware that could be used in the Expanded Non-Multiplexed Mode is given in Figure 14. In the Expanded Non-Multiplexed Mode, pins 10, 9 and 8 are programmed Hi, Lo, Hi respectively as shown.

Couplers between the pins on Port 2 and the peripherals attached may be required. If the lines go to devices which require signals at power up differing from the signals needed to program the 6801's mode, couplers are necessary.

The 14066B can be used to provide this isolation between the peripheral device and the MCU during reset. Figure 15 shows the logic diagram and xxxxx? for the MC14066B. It is bidirectional and requires no external logic to determine the direction of the information flow.

The logic shown insures that the data on the peripheral will not change before it is latched into the MCU and the MCU has started the reset sequence.

Figure 14. Diode Configuration for the Expanded Non-Multiplexed Mode

AS BITS 5, 6 AND 7 OF PORT 2 ARE READ ONLY, THE MODE CANNOT BE CHANGED THROUGH SOFTWARE. THE MODE SELECTIONS ARE SHOWN IN TABLE 3.
P20 REFERS TO PORT 2, BIT 0.
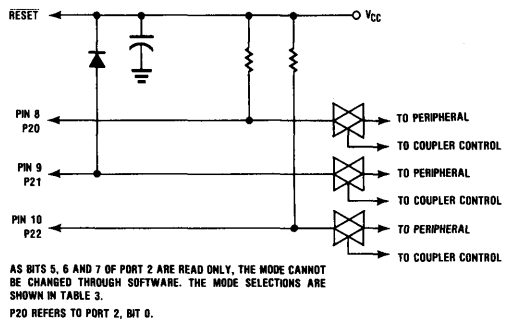
Figure 15. Quad Analog, Switch/Multiplexer In a Typical S6801 Circuit

CONTROL	SWITCH
0	OFF
1	ON

V CONTROL	V$_{IN}$ TO V$_{OUT}$ RESISTANCE
V$_{SS}$	>10^9 OHMS TYP.
V$_{DD}$	300 OHMS TYP.
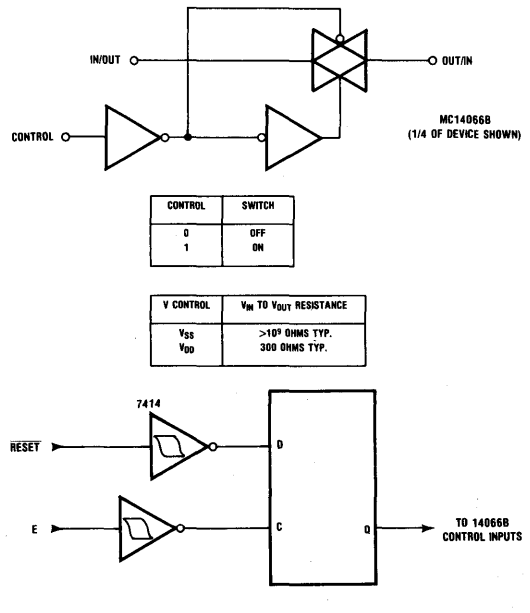
S6801 Basic Modes

The S6801 is capable of operating n three basic modes, (1) Single Chip Mode, (2) Expanded Multiplexed Mode (compatible with S6800 peripheral family, (3) Expanded Non-Multiplexed Mode.

Single Chip Mode
Both mask options will operate in this mode. In the Single Chip Mode the parts are configured for I/O.

Internal Clock/Divide-by-Four (S6801)—This mask op-

tion is shown in Figure 16. In this mode, Port 3 has two associated control lines, an input strobe and an output strobe for handshaking data.

External Clock/Divide-by-One (S6801E)—This mask option is shown in Figure 16a. The Read/Write (R/W) line, Chip Select (CS), and Register Select (RS) are associated with Port 3 only. The Read/Write (R/W) line controls the direction of data on Port 3 and Chip Select (CS) enables Port 3. The Register Select (RS) allows for the access of Port 3 data register or Port 3 control register.

Figure 16. S6801 MCU Single Chip Mode

Figure 16a. S6801E MCU Single-Chip Mode
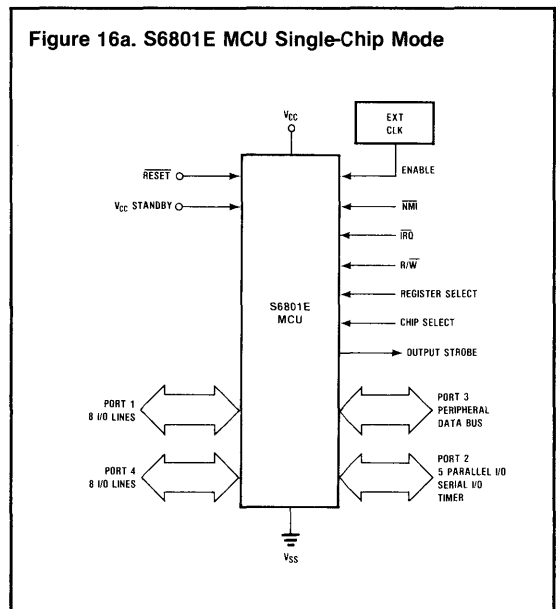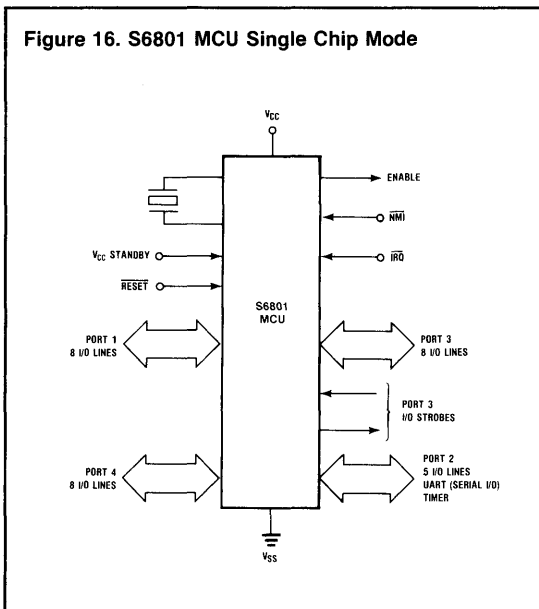
Expanded Non-Multiplexed Mode

In this mode the S6801 will directly address S6800 peripherals with no external logic. In this mode Port 3 becomes the data bus. Port 4 becomes the A7-A0 address bus or partial address and I/O (inputs only). Port 2 can be parallel I/O, serial only. In this mode the S6801 is expandable to 256 locations. The eight address lines associated with Port 4 may be substituted for I/O (inputs only) if a fewer number of address lines will satisfy the application.

Internal Clock/Divide-by-Four—This mask option is shown in Figure 17. The Internal Clock requires only the addition of a crystal for operation. This input will also accept an external TTL or CMOS input, but in either case, the clock frequency will be divided by four for this mask option.

External Clock/Divide-by-One—This mask option is shown in Figure 17a. The External Clock/Divide-by-One allows for an external clock to be applied to the Enable Pin. This is a divide-by-one input only.

Expanded Multiplexed Mode

In this mode Port 4 becomes higher order address lines with an alternative of substituting some of the address lines for I/O (inputs only). Port 3 is the data bus multiplexed with the lower order address lines differentiated by an output called Address Strobe. Port 2 is 5 lines of Parallel I/O, SC1, Timer, or any combination thereof. Port 1 is 8 Parallel I/O lines. In this mode it is expandable to 65K words.

Internal Clock/Divide-by-Four—This mask option is shown in Figure 18. Only an external crystal is required for operation.

External Clock/Divide-by-One—This mask option is shown in Figure 18a. This accepts an external clock input to the enable pin.

Figure 17. S6801 MCU Expanded
Non-Multiplexed Mode

Figure 17a. S6801E MCU Expanded
Non-Multiplexed-Mode

Figure 18. S6801 MCU Expanded
Multiplexed Mode

Figure 18a. S6801E MCU Expanded
Multiplexed-Mode
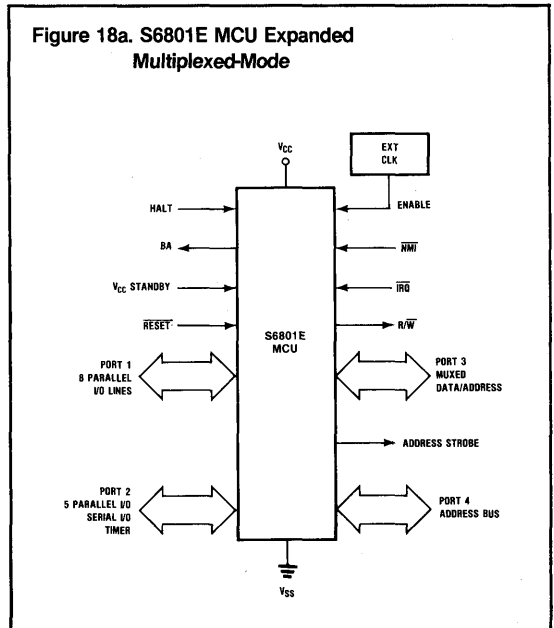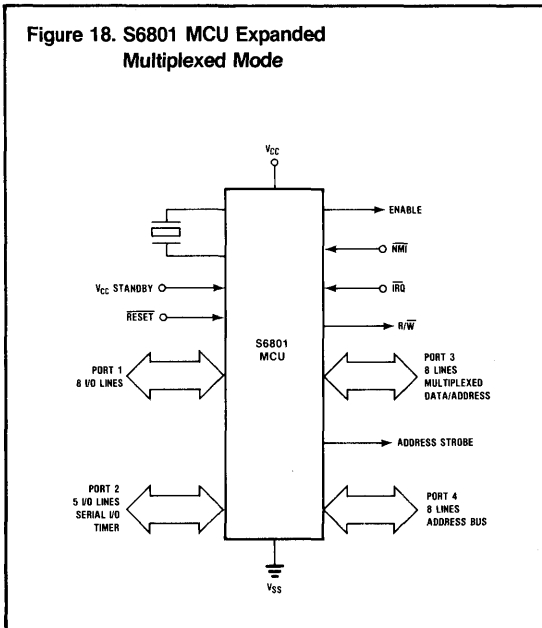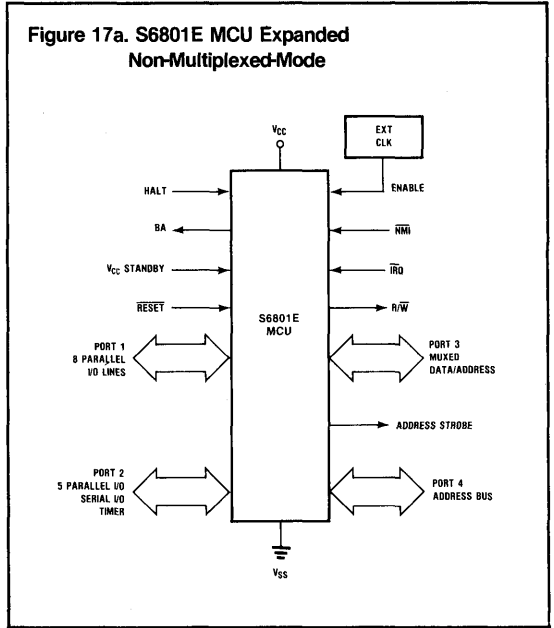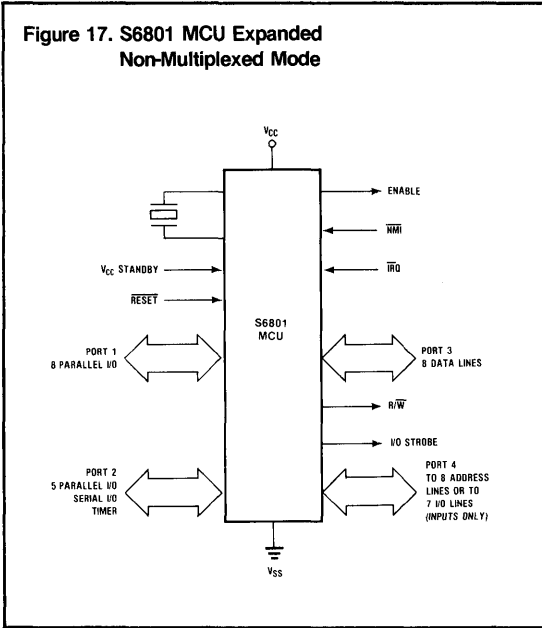
Table 3. Mode Selects

MODE		PROGRAM CONTROL			ROM	RAM	INTERRUPT VECTORS	BUS
7	Single Chip	Hi	Hi	Hi	I	I	I	I
6	Expanded Multiplexed	Hi	Hi	Lo	I	I	I	Ep/M
5	Expanded Non-Multiplexed	Hi	Lo	Hi	I	I	I	Ep
4	Single Chip Test	Hi	Lo	Lo	I(2)	I(1)	I	I
3	64K Address I/O	Lo	Hi	Hi	E	E	E	Ep/M
2	Ports 3 & 4 External	Lo	Hi	Lo	E	I	E	Ep/M
1		Lo	Lo	Hi	I	I	E	Ep/M
0	Test Data Outputted from ROM & ROM to I/O Port 3	Lo	Lo	Lo	I	I	I*	Ep/M

E—EXTERNAL all vectors are external
I—INTERNAL
Ep—EXPANDED MULTIPLEXED

*First two addresses read from external after reset
(1) Address for RAM XX80-XXFF
(2) ROM disabled

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Lower Order Address Bus Latches

Since the data bus is multiplexed with the lower order address bus in Port 3, latches are required to latch those address bits. The SN74LS373 Transparent octal D-type latch can be used with the S6801 to latch the least significant address byte. Figure 19 shows how to connect the latch to the S6801. The output control to the LS373 may be connected to ground.

Figure 19. Latch Connection
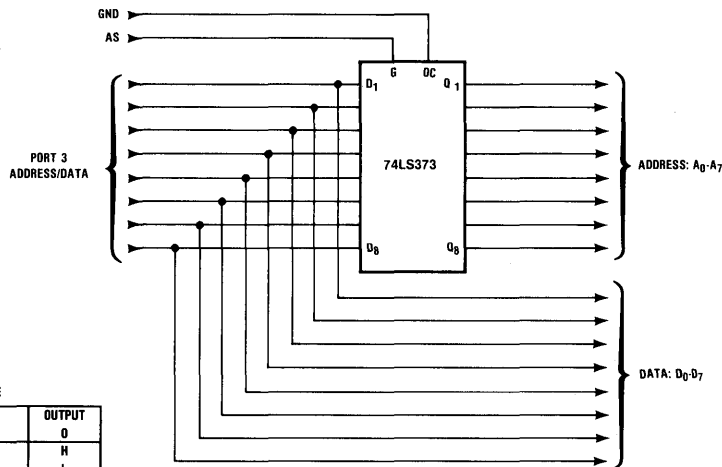
FUNCTION TABLE			
OUTPUT CONTROL	ENABLE G	D	OUTPUT Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

Programmable Timer

The S6801 contains an on-chip 16-bit programmable timer which may be used to perform measurements on an input waveform while independently generating an output waveform. Pulse widths for both input and output signals may vary from a few microseconds to many seconds. The timer hardware consists of

- an 8-bit control and status register
- a 16-bit free running counter
- a 16-bit output compare register, and
- a 16-bit input capture register

A block diagram of the timer registers is shown in Figure 20.

Figure 20. Block Diagram of Timer Registers
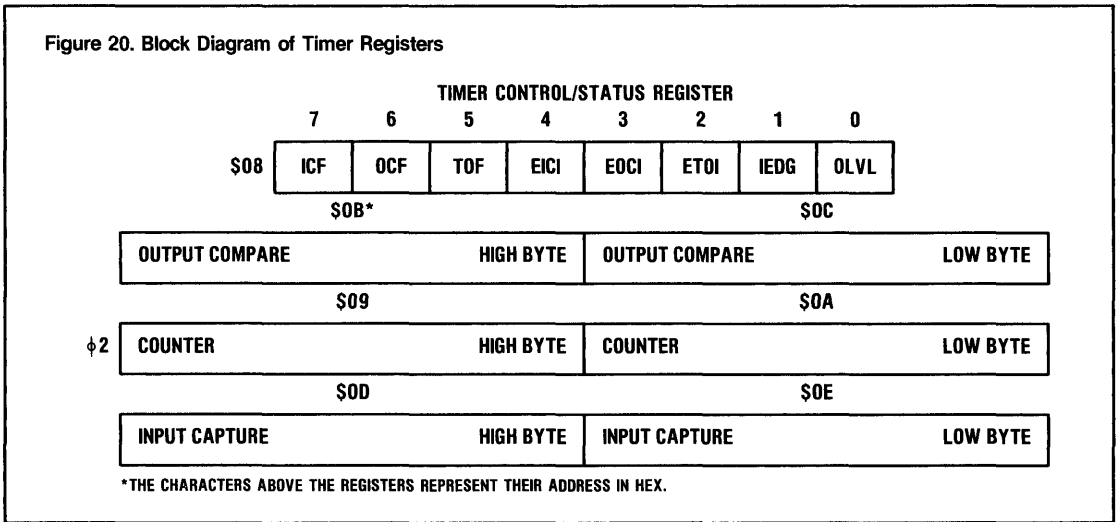
Free Running Counter ($0009:000A)

The key element in the programmable timer is a 16-bit free running counter which is driven to increasing values by the MPUϕ. The counter value may be read by the MPU software at any time. The counter is cleared to zero on RESET and may be considered a read-only register with one exception. Any MPU write to the counter's address ($09) will always result in a preset value of $FFF8 being loaded into the counter regardless of the value involved in the write. The preset feature is intended for testing operation of the part, but may be of value in some applications.

Output Compare Register ($000B:000C)

The Output Compare Register is a 16-bit read/write register which is used to control an output waveform. The contents of this register are constantly compared with the current value of the free running counter. When a match is found a flag is set (OCF) in the Timer Control and Status Register (TCSR) and the current value of the Output Level bit (OLVL) in the TCSR is clocked to the output level register. Providing the

Data Direction Register for Port 2, Bit 1 contains a "1" (output), the output level register value will appear on the pin for Port 2 Bit 1. The values in the Output Compare Register and Output level bit may then be changed to control the output level on the next compare value. The Output Compare Register is set to $FFFF during RESET. The Compare function is inhibited for one cycle following a write to the high byte of the Output Compare Register to insure a valid 16-bit value is in the register before a compare is made.

Input Capture Register ($000D:000E)

The Input Capture Register is a 16-bit read-only register used to store the current value of the free running counter when the proper transition of an external input signal occurs. This input transition change required to trigger the counter transfer is controlled by the input Edge bit (EDG) in the TOSR. The Data Direction Register bit for Port 1 Bit 0 should *be clear (zero) in order to gate in the external input signal to the edge defect unit in the timer.

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*With Port 2 Bit 0 configured as an output and set to "1". the external input will still be seen by the edge detect unit.

Timer Control and Status Register (TCSR) ($0008)

The Timer Control and Status Register consists of an 8-bit register of which all 8 bits are readable but only the low order 5 bits may be written. The upper three bits contain read-only timer status information and indicate that:
  • a proper transition has taken place on the input pin with a subsequent transfer of the current counter value to the input capture register.

  • a match has been found between the value in the free running counter and the output compare register, and
  • when $0000 is in the free running counter.

Each of the flags may be enabled onto the S6801 internal bus (RO2) with an individual Enable bit in the tCSR. If the 1-bit in the S6801 Condition Code Register has been cleared, a priority vectored interrupt will occur corresponding to the flag bit(s) set. A description for each bit follows:

	7	6	5	4	3	2	1	0	
TIMER CONTROL AND STATUS REGISTER	ICF	OCF	TOF	EICI	EOCI	ETOI	IEDG	OLVL	$0008
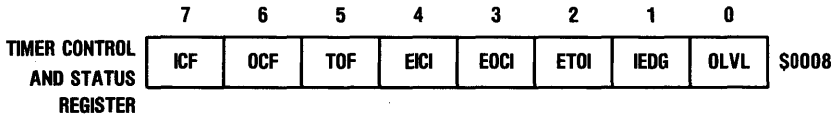
Bit 0 OLVL   **Output Level**—This value is clocked to the output level register on an output compare. If the DDR for Port 2 bit 1 is set, the value will appear on the output pin.

Bit 1 IEDG   **Input Edge**—This bit controls which transition of an input will trigger a transfer of the counter to the input capture register. The DDR for Port 2 Bit 0 must be clear for this function to operate.
IEDG = 0 Transfer takes place on a negative (high-to-low transition).
IEDG = 1 Transfer takes place on a positive edge (low-to-high transition).

Bit 2 ETOI   **Enable Timer Overflow Interrupt**—When *set*, this bit enables IRQ2 to occur on the internal bus for a TOF Interrupt; when *clear* the interrupt is inhibited.

Bit 3 EOCI   **Enable Output Compare Interrupt**—When *set*, this bit enables IRQ2 to appear on the internal bus for an input capture interrupt; when *clear* the interrupt is inhibited.

Bit 4 EICI   **Enable Input Capture Interrupt**—When *set*, this bit enables IRQ2 to occur on the internal bus for an input capture interrupt; when *clear* the interrupt is inhibited.

Bit 5 TOF   **Timer Overflow Flag**—This read-only bit is *set* when the counter contains $0000. It is *cleared* by a read of the TCSR (with TOF set) followed by an MPU read of the Counter ($09).

Bit 6 OCF   **Output Compare Flag**—This read-only bit is *set* when a match is found between the output compare register and the free running counter. It is *cleared* by a read of the TCSR (with ODF set) followed by an MPU write to the output compare register ($0B or $0C).

Bit 7 CF   **Input Capture Flag**—This read-only status bit is *set* by a proper transition on the input to the edge detect unit; it is *cleared* by a read of the TCSR (with ICF set) followed by an MPU read of the input Capture Register ($0D).

Serial Communications Interface

The S6801 contains a full-duplex asynchronous serial communications interface (SCI) on board. Two serial data formats (standard mark/space [NRZ] or Bi-phase) are provided at several different data rates. The controller comprises a transmitter and a receiver which operate independently or each other but in the same data format and at the same data rate. Both transmitter and receiver communicate with the MPU via the data bus and with the outside world via pins 2, 3, and 4 of Port 2. The hardware, software, and registers are explained in the following paragraphs.

Wake-up Feature

In a typical multi-processor application, the software protocol will usually contain a destination address in the initial byte(s) of the message. In order to permit non-

selected MPU's to ignore the remainder of the message, a wake-up feature is included whereby all further interrupt processing may be optionally inhibited until the beginning of the next message. When the next messge appears, the hardware re-enables (or "wakes-up") for the next message. The "wake-up" is automatically triggered by a string of ten consecutive 1's which indicates an idle transmit line. The software protocol must provide for the short idle period between any two consecutive messages.

Programmable Options

The following features of the S6801 serial I/O section have programmable:

- format—standard mark/space (NRZ) or Bi-phase
- clock—external or internal
- baud rate—one of 14 per given MPUϕ2 clock frequency or external clock X8 input
- wake-up feature—enabled or disabled

- interrupt requests—enabled or masked indivually for transmitter and receiver data registers
- clock output—internal clock enabled or disabled to Port 2 (Bit 2)
- Port 2 (bits 3 and 4)—dedicated or not dedicated to serial I/O individually for transmitter and receiver

Serial Communications Hardware

The serial communications hardware is controlled by 4 registers as shown in Figure 21. The registers include:

- an 8-bit control and status register
- a 4-bit rate and mode control register (write only)
- an 8-bit read-only receive data register and
- an 8-bit write-only transmit data register

In addition to the four registers, the serial I/O section utilizes bit 3 (serial input) and bit 4 (serial output) or Port 2. Bit 2 of Port 2 is utilized if the internal-clock-out or external-clock-in options are selected.

Figure 21. Serial I/O Registers

CONTROL AND STATUS REGISTER $0011, READ/WRITE
EXCEPT "*" (READ ONLY)

7	6	5	4	3	2	1	0
RDRF	ORFE	TDRE	RIE	RE	TIE	TE	WU

RATE AND MODE REGISTER $0010, WRITE ONLY

X	X	X	X	CC1	CC0	S1	S0
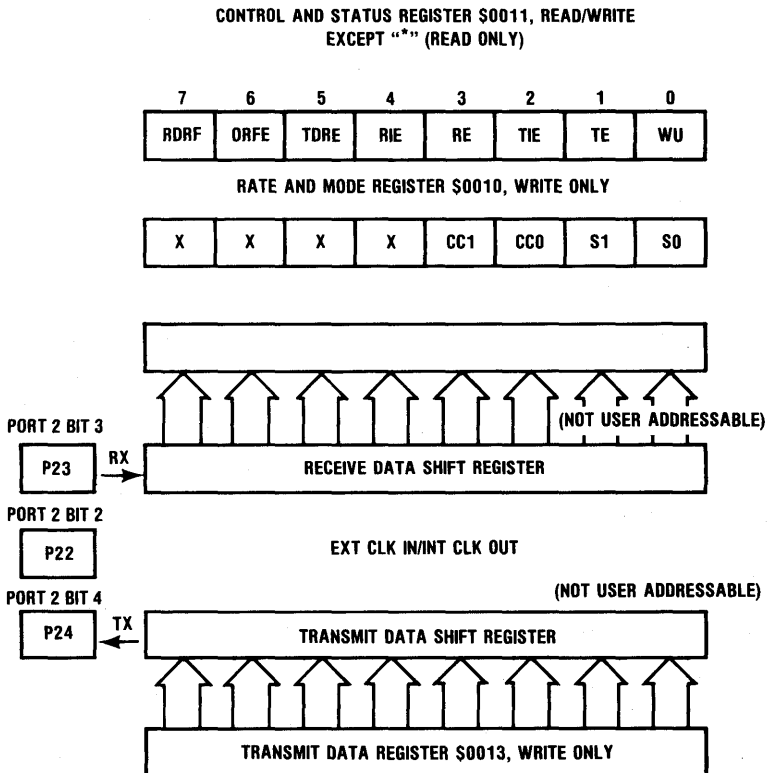
Transmit/Receive Control and Status (TRCS) Register

The TRCS register consists of an 8-bit register of which all 8 bits may be read while only bits 0-4 may be written. The register is initialized to $20 on $\overline{\text{RESET}}$. The bits in the TRCS register are defined as follows:

7	6	5	4	3	2	1	0	
RDRE	ORFE	TDRE	RIE	RE	TIE	TE	WU	ADDR. $0011

Bit 0 WU "Wake-up on Next Message—set by S6801 software cleared by hardware on receipt of ten consecutive 1's.

Bit 1 TE Transmit Enable—set by S6801 to produce preamble of nine consecutive 1's and to enable gating of transmitter output to Port 2, bit 4 regardless of the DDR value corresponding to this bit; when clear, serial I/O has no effect on Port 2 bit 4.

Bit 2 TIE Transmit Interrupt Enable—when set, will permit an $\overline{\text{IRQ2}}$ interrupt to occur when bit 5 (TDRE) is set; when clear, the TDRE value is masked from the bus.

Bit 3 RE Receiver Enable—when set, gates Port 2 bit 3 to input of receiver regardless of DDR value for this bit; when clear, serial I/O has no effect on Port 2 bit 3.

Bit 4 RIE Receiver Interrupt Enable—when set, will permit an $\overline{\text{IRQ2}}$ interrupt to occur when bit 7 (RDRF) or bit 6 (OR) is set; when clear, the interrupt is masked.

Bit 5 TDRE Transmit Data Register Empty—set by hardware when a transfer is made from the transmit data register to the output shift register. The TDRE bit is cleared by reading the status register, then writing a new byte into the transmit data register, TDRE is initialized to 1 by $\overline{\text{RESET}}$.

Bit 6 ORFE Over-Run-Framing Error—set by hardware when an overrun or framing error occurs (receive only). An overrun is defined as a new byte received with last byte still in Data Register/Buffer. A framing error has occured when the byte boundaries in bit stream are not synchronized to bit counter. The ORFE bit is cleared by reading the status register, then reading the Receive Data Register, or by $\overline{\text{RESET}}$.

Bit 7 RDRF Receiver Data Register Full—set by hardware when a transfer from the input shift register to the receiver data register is made. The RDRF bit is cleared by reading the status register, then reading the Receive Data Register, or by $\overline{\text{RESET}}$.

Rate and Mode Control Register

The Rate and Mode Control register controls the following serial I/O variables:

- Baud rate
- format
- Clocking source, and
- Port 2 bit 2 configuration

The register consists of 4 bits all of which are write-only and cleared on $\overline{\text{RESET}}$. The 4 bits in the register may be considered as a pair of 2-bit fields. The two low order bits control the bit rate for internal clocking and the remaining two bits control the format and clock select logic. The register definition is as follows:

7	6	5	4	3	2	1	0	
X	X	X	X	CC1	CC0	S1	S0	ADDR. $0010

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Bit 0 S0   **Speed Select**—These bits select the Baud rate for the internal clock. The four rates which may be
Bit 1 S1   selected are a function of the MPU $\phi 2$ clock frequency. Table 4 lists the available Baud rate.

Bit 2 CC0   **Clock Control and Format Select**—This 2-bit field controls the format and clock select logic. Table
Bit 3 CC1   5 defines the bit field.

Table 4. SCI Internal Baud Rates

S1, S0	XTAL	4.0MHz	4.9152MHz	2.5476MHz
	$\phi 2$	1.0MHz	1.2288MHz	0.6144MHz
00	$\phi 2 \div 16$	62.5K BITS/S	76.8K BITS/S	38.4K BITS/S
01	$\phi 2 \div 128$	7,812.5 BITS/S	9,600 BITS/S	4,800 BITS/S
10	$\phi 2 \div 1024$	976.6 BITS/S	1,200 BITS/S	600 BITS/S
11	$\phi 2 \div 4096$	244.1 BITS/S	300 BITS/S	150 BITS/S

Table 5. Bit Field

CC1, CC0	FORMAT	CLOCK SOURCE	PORT 2 BIT 2	PORT 2 BIT 3	PORT 2 BIT 4
00	BI-PHASE	INTERNAL	NOT USED	**	**
01	NRZ	INTERNAL	NOT USED	**	**
10	NRZ	INTERNAL	OUTPUT*	SERIAL INPUT	SERIAL OUTPUT
11	NRZ	EXTERNAL	INPUT	SERIAL INPUT	SERIAL OUTPUT

*CLOCK OUTPUT IS AVAILABLE REGARDLESS OF VALUES FOR BITS RE AND TE.
**BIT 3 IS USED FOR SERIAL INPUT IF RE = "1" IN TRCS; BIT 4 IS USED FOR SERIAL OUTPUT IF TE = "1" IN TRCS.

Internally Generated Clock

If the user wishes for the serial I/O to furnish a clock, the
following requirements are applicable:
- the values of RE and TE are immaterial
- CC1, CC0 must be set to 10
- the maximum clock rate will be $\phi \div 16$
- the clock will be at 1X the bit rate and will have a
rising edge at mid-bit

Externally Generated Clock

If the user wishes to provide an external clock for the
serial I/O, the following requirements are applicable:
- the CC1, CC0, field in the Rate and Mode Control
Register must be set to 11.
- the external clock must be set to 8 times (X8) the
desired baud rate and
- the maximum external clock frequency is 1.2MHz.

Serial Operations

The Serial I/O hardware should be initialized by the
S6801 software prior to operation. This sequence will nor-
mally consist of:
- writing the desired operation control bits to the Rate
and Mode Control Register and
- writing the desired operational control bits in the
Transmit/Receive Control and Status Register.

The Transmitter Enable (TE) and Receiver Enable (RE)
bits may be left set for dedicated operations.

Transmit Operations

The transmit operation is enabled by the TE bit in the
Transmit/Receive Control and Status Register. This bit
when set, gates the output of the serial transmit shift
register to Port 2 Bit 4 and takes unconditional control

over the Data Direction Register value for Port 2, Bit 4.

Following a $\overline{\text{RESET}}$, the user should configure both the Rate and Mode Control Register and the Transmit/Receiver Control and Status Register for desired operation. Setting the TE bit during this procedure initiates the serial output by first transmitting a ten-bit preamble of 1's. Following the preamble, internal synchronization is established and the transmitter section is ready for operation.

At this point one of two situations exist:

a) if the Transmit Data Register is empty (TDRE = 1), a continuous string of ones will be sent indicating an idle line, or

b) if data has been loaded into the Transmit Data Register (TDRE = 0), the word is transferred to the output shift register and transmission of the data word will begin.

During the transfer itself, the 0 start bit is first transmitted. Then the 8 data bits (beginning with bit 0) followed by the stop bit, are transmitted. When the Transmitter Data Register has been emptied, the hardware sets the TDRE flag bit.

If the S6801 fails to respond to the flag within the proper time, (TDRE is still set when the next normal transfer from the parallel data register to the serial output register should occur) then a 1 will be sent (instead of a 0) at "Start" bit time, followed by more 1's until more data is supplied to the data register. No 0's will be sent while TDRE remains a 1.

The Bi-phase mode operates as described above except that the serial output toggles each bit time, and on 1/2 bit times when a 1 is sent.

Receive Operation

The receive operation is enabled by the RE bit which gates in the serial input through Port 2 Bit 3. The receiver section operation is conditioned by the contents of the Transmit/Receive Control and Status Register and the Rate and Mode Control Register.

The receiver bit interval is divided into 8 sub-intervals for internal synchronization. In the standard, non-Bi-phase mode, the received bit stream is synchronized by the first 0 (space) encountered.

The approximate center of each bit time is strobed during the next 10 bits. If the tenth bit is not a 1 (stop bit) a framing error is assumed, and bit ORFE is set. If the tenth bit is 1, the data is transferred to the Receiver Data Register, and interrupt flag RDRF is set. If RDRF is still set at the next tenth bit time, ORFE will be set, indica-

ting an over-run has occurred. When the S6801 responds to either flag (RDRF or ORFE) by reading the status register followed by reading the Data Register RDRF (or ORFE) will be cleared.

Ram Control Register

This register, which is addressed at $0014, gives status information about the standby RAM. A 0 in the RAM enable bit (RAM E) will disable the standby RAM, thereby protecting it at power down if V_{CC} is held greater than V_{SBB} volts, as explained previously in the signal description for V_{CC} Standby.

$0014	STAND-BY BIT	RAM E	X	X	X	X	X	X

Bit 1   Not used.
Bit 2   Not used.
Bit 3   Not used.
Bit 4   Not used.
Bit 5   Not used
Bit 6   The RAM ENABLE control bit allows the user the ability to disable the standby RAM. This bit is set to a logic "one" by reset which enables the standby RAM and can be written to or zero under program control. When the RAM is disabled, logic "zero", data is read from external memory.
Bit 7   The STANDBY BIT of the control register, $0014, is cleared when the standby voltage is removed. This bit is a read/write status flag that the user can read which indicates that the standby RAM voltage has been applied, and the data in the standby RAM is valid.

The S6801 provides up to 65K bytes of memory for program and/or data storage. The memory map is shown in Figure 22.

Locations $0020 through $007F access external RAM or I/O Internal RAM is accessed at $0080 through $00FF. The RAM may be alternately selected by mask programming at location $A000. However, if the user desires to access external RAM at those locations he may do so by clearing the RAM ENABLE control bit of the RAM Control Register. In this way an extra 126 bytes of external RAM are available. The first 64 bytes of the 128 bytes of on-chip RAM are provided with a separate power supply. This will maintain the 64 bytes of RAM in the power down mode as explained in the pin description for V_{CC} Standby.

Figure 22. Memory Map

Address		Region
$0000		SPECIAL PURPOSE REGISTER
$001F		
$0020		EXTERNAL RAM OR I/O
$007F		
$0080		INTERNAL RAM
$00FF		
$0100		EXTERNAL RAM OR I/O FOR NON-MULTIPLEXED MODE
$01FF		
$0200		EXTERNAL RAM OR ROM OR I/O
$F7FF		
$F800		INTERNAL ROM OR EROM
$FFFF		
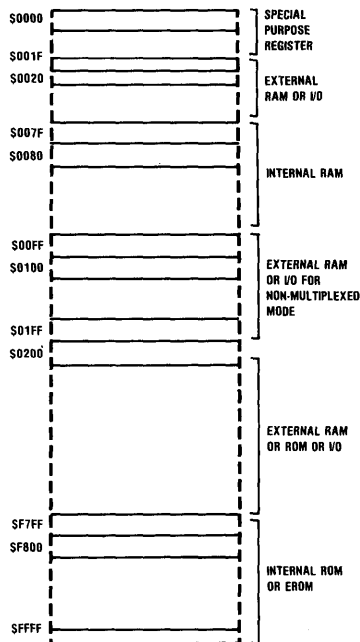
Locations $0100 through $01FF are available in the Expanded Non-Multiplexed Mode. The eight address lines of Port 4 make this 256 word expandability possible. Those not needed for address lines can be used as input lines instead.

The full range of addresses available to the user is in the Expanded Multiplexed Mode. Locations $0200 through $F7FF can be used as external RAM, external ROM, or I/O. Any higher order bit not required for addressing can be used as I/O as in the Expanded Non-Multiplexed Mode.

The internal ROM is located at $F800 through $FFFF. The decoder for the ROM may be mask programmed on A12, and A13 as zeros or one's to provide for $C800, $D800, $E800 for the ROM address. A12 and A13 may also be don't care in this decoder. The primary address for the ROM will be $F800.

The first 32 bytes are for the special purpose registers as shown in Table 6.

Table 6. Special Registers

HEX ADDRESS	REGISTER
00	DATA DIRECTION 1
01	DATA DIRECTION 2
02	I/O PORT 1
03	I/O PORT 2
04	DATA DIRECTION 3
05	DATA DIRECTION 4
06	I/O PORT 3
07	I/O PORT 4
08	TCSR
09	COUNTER HIGH BYTE
0A	COUNTER LOW BYTE
0B	OUTPUT COMPARE HIGH BYTE
0C	OUTPUT COMPARE LOW BYTE
0D	INPUT CAPTURE HIGH BYTE
0E	INPUT CAPTURE LOW BYTE
0F	I/O PORT 3 C/S REGISTER
10	SERIAL RATE AND MODE REGISTER
11	SERIAL CONTROL AND STATUS REGISTER
12	SERIAL RECEIVER DATA REGISTER
13	SERIAL TRANSMIT DATA REGISTER
14	RAM/EROM CONTROL REGISTER
15-1F RESERVED	

Figure 23. Memory Map for Interrupt Vectors

	VECTOR		DESCRIPTION
	MS	LS	
Highest Priority	FFFE,	FFFF	Restart
	FFFC,	FFFD	Non-Maskable Interrupt
	FFFA,	FFFD	Software Interrupt
	FFF8,	FFF9	IRQ1/Interrupt Strobe S
	FFF6,	FFF7	IRQ2/Timer Input Capture
	FFF4,	FFF5	IRQ2/Timer Output Compare
	FFF2,	FFF3	IRQ2/Timer Overflow
Lowest Priority	FFF0,	FFF1	IRQ2/Serial I/O Interrupt

S6800

General Description of Instruction Set

The S6801 is upward object code compatible with the S6800 as it implements the full S6800 instruction set. The execution times of key instructions have been reduced to increase throughput. In addition, new instructions have been added; these include 16-bit operations and a hardware multiply.

Included in the instruction set section are the following:

- MPU Programming Model (Figure 24)
- Addressing modes
- Accumulator and memory instructions—Table 7
- New instructions
- Index register and stack manipulations—Table 8
- Jump and branch instructions—Table 9
- Special operations—Figure 25
- Condition code register manipulation instructions—Table 10
- Instruction Execution times in machine cycles—Table 11
- Summary of cycle by cycle operation—Table 12

MPU Programming Model

The programming model for the S6801 is shown in Figure 24. The double (D) accumulator is physically the same as the A Accumulator concatenated with the B Accumulator so that any operation using accumulator D will destroy information in A and B.

Figure 24. MCU Programming Model

MPU Addressing Modes

The S6801 eight-bit microcomputer unit has seven address modes that can be used by a programmer, with the addressing mode a function of both the type of instruction and the coding within the instruction. A summary of the addressing modes for a particular instruction can be found in Table 11 along with the associated instruction execution time that is given in machine cycles. With a clock frequency of 4MHz, these times would be microseconds.

Accumulator (ACCX) Addressing—In accumulator only addressing, either accumulator A or accumulator B is specified. These are one-byte instructions.

Immediate Addressing—In immediate addressing, the operand is contained in the second byte of the instruction except LDS and LDX which have the operand in the second and third bytes of the instruction. The MCU addresses this location when it fetches the immediate instruction for execution. These are two or three-byte instructions.

Direct Addressing—In direct addressing, the address of the operand is contained in the second byte of the instruction. Direct addressing allows the user to directly address the lowest 256 bytes in the machine i.e., locations zero through 255. Enhanced execution times are achieved by storing data in these locations. In most configurations, it should be a random access memory. These are two-byte instructions.

Extended Addressing—In extended addressing, the address contained in the second byte of the instruction is used as the higher eight-bits of the address of the operand. The third byte of the instruction is used as the lower eight-bits of the address for the operand. This is an absolute address in memory. These are three-byte instructions.

Indexed Addressing—In indexed addressing, the address contained in the second byte of the instruction is added to the index register's lowest eight bits in the MCU. The carry is then added to the higher order eight bits of the index register. This result is then used to address memory. The modified address is held in a temporary address register so there is no change to the index register. These are two-byte instructions.

Implied Addressing—In the implied addressing mode the instruction gives the address (i.e., stack pointer, index register, etc.). These are one-byte instructions.

Relative Addressing—In relative addressing, the address contained in the second byte of the instruction is added to the program counter's lowest eight bits plus two. The carry or borrow is then added to the high eight bits. This allows the user to address data within a range of −125 to +120 bytes of the present instruction. These are two-byte instructions.
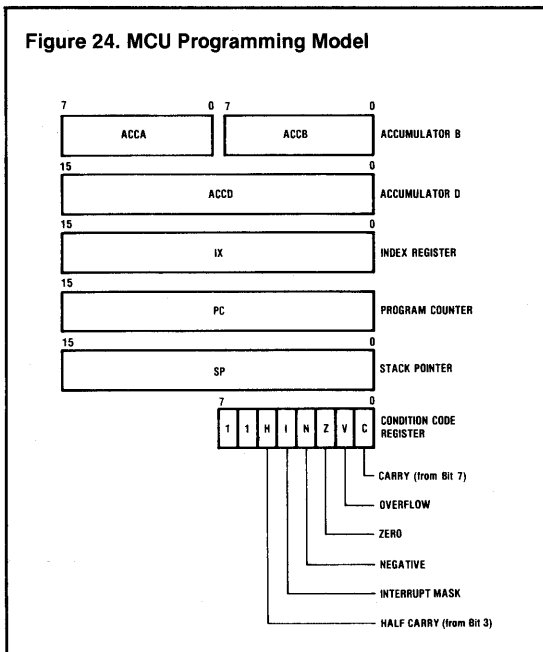
Table 7. Accumulator & Memory Instructions

ACCUMULATOR AND MEMORY Operations	MNEMONIC	IMMED. OP	~	#	DIRECT OP	~	#	INDEX OP	~	#	EXTEND OP	~	#	INHERENT OP	~	#	Boolean/Arithmetic Operation	H (5)	I (4)	N (3)	Z (2)	V (1)	C (0)
ADD	ADDA	8B	2	2	9B	3	2	AB	4	2	BB	4	3				$A + M \rightarrow A$	↕	•	↕	↕	↕	↕
	ADDB	CB	2	2	DB	3	2	EB	4	2	FB	4	3				$B + M \rightarrow B$	↕	•	↕	↕	↕	↕
ADD DOUBLE	ADDD	C3	4	3	D3	5	2	E3	6	2	F3	6	3				$A{:}B + M{:}M + 1 \rightarrow A{:}B$	•	•	↕	↕	↕	↕
ADD ACCUMULATORS	ABA													1B	2	1	$A + B \rightarrow A$	↕	•	↕	↕	↕	↕
ADD WITH CARRY	ADCA	89	2	2	99	3	2	A9	4	2	B9	4	3				$A + M + C \rightarrow A$	↕	•	↕	↕	↕	↕
	ADCB	C9	2	2	D9	3	2	E9	4	2	F9	4	3				$B + M + C \rightarrow B$	↕	•	↕	↕	↕	↕
AND	ANDA	84	2	2	94	3	2	A4	4	2	B4	4	3				$A \cdot M \rightarrow A$	•	•	↕	↕	R	•
	ANDB	C4	2	2	D4	3	2	E4	4	2	F4	4	3				$B \cdot M \rightarrow B$	•	•	↕	↕	R	•
BIT TEST	BIT A	85	2	2	95	3	2	A5	4	2	B5	4	3				$A \cdot M$	•	•	↕	↕	R	•
	BIT B	C5	2	2	D5	3	2	E5	4	2	F5	4	3				$B \cdot M$	•	•	↕	↕	R	•
CLEAR	CLR							6F	6	2	7F	6	3				$00 \rightarrow M$	•	•	R	S	R	R
	CLRA													4F	2	1	$00 \rightarrow A$	•	•	R	S	R	R
	CLRB													5F	2	1	$00 \rightarrow B$	•	•	R	S	R	R
COMPARE	CMPA	81	2	2	91	3	2	A1	4	2	B1	4	3				$A - M$	•	•	↕	↕	↕	↕
	CMPB	C1	2	2	D1	3	2	E1	4	2	F1	4	3				$B - M$	•	•	↕	↕	↕	↕
COMPARE ACCUMULATORS	CBA													11	2	1	$A - B$	•	•	↕	↕	↕	↕
COMPLEMENT, 1'S	COM							63	6	2	73	6	3				$\overline{M} \rightarrow M$	•	•	↕	↕	R	S
	COMA													43	2	1	$\overline{A} \rightarrow A$	•	•	↕	↕	R	S
	COMB													53	2	1	$\overline{B} \rightarrow B$	•	•	↕	↕	R	S
COMPLEMENT, 2'S	NEG							60	6	2	70	6	3				$0C - M \rightarrow M$	•	•	↕	↕	①	②
(NEGATE)	NEGA													40	2	1	$00 - A \rightarrow A$	•	•	↕	↕	①	②
NEGB														50	2	1	$00 - B \rightarrow B$	•	•	↕	↕	①	②
DECIMAL ADJUST, A	DAA													19	2	1	Converts binary add of BCD characters into BCD format	•	•	↕	↕	↕	③
DECREMENT	DEC							6A	6	2	7A	6	3				$M - 1 \rightarrow M$	•	•	↕	↕	④	•
	DECA													4A	2	1	$A - 1 \rightarrow A$	•	•	↕	↕	④	•
	DECB													5A	2	1	$B - 1 \rightarrow B$	•	•	↕	↕	④	•
EXCLUSIVE OR	EORA	88	2	2	98	3	2	A8	4	2	B8	4	3				$A \oplus M \rightarrow A$	•	•	↕	↕	R	•
	EORB	C8	2	2	D8	3	2	E8	4	2	F8	4	3				$B \oplus M \rightarrow B$	•	•	↕	↕	R	•
INCREMENT	INC							9C	6	2	7C	6	3				$M + 1 \rightarrow M$	•	•	↕	↕	⑤	•
	INCA													4C	2	1	$A + 1 \rightarrow A$	•	•	↕	↕	⑤	•
	INCB													5C	2	1	$B + 1 \rightarrow B$	•	•	↕	↕	⑤	•
LOAD ACCUMULATOR	LDAA	86	2	2	96	3	2	A6	4	2	B6	4	3				$M \rightarrow A$	•	•	↕	↕	R	•
	LDAB	C6	2	2	D6	3	2	E6	4	2	F6	4	3				$M \rightarrow B$	•	•	↕	↕	R	•
LOAD DOUBLE ACCUMULATOR	LDAD	CC	3	3	DC	4	2	EC	5	2	FC	5	3				$M + A \cdot M + 1 \rightarrow B$	•	•	↕	↕	R	•
MULTIPLY UNSIGNED	MUL													3D	10	1	$A \times B \rightarrow AB$	•	•	•	•	•	⑫
OR, INCLUSIVE	ORAA	8A	2	2	9A	3	2	AA	4	2	BA	4	3				$A + M \rightarrow A$	•	•	↕	↕	R	•
	ORAB	CA	2	2	DA	3	2	EA	4	2	FA	4	3				$B + M \rightarrow B$	•	•	↕	↕	•	•

The Condition Code Register notes are listed after Table 10.

Table 7. Accumulator & Memory Instructions (Continued)

ACCUMULATOR AND MEMORY Operations	MNEMONIC	IMMED. OP	~	#	DIRECT OP	~	#	INDEX OP	~	#	EXTEND OP	~	#	INHERENT OP	~	#	Boolean/Arithmetic Operation	H	I	N	Z	V	C
PUSH DATA	PSHA													36	3	1	A→M$_{SP}$ SP−1→SP	•	•	•	•	•	•
	PSHB													37	3	1	B→M$_{SP}$ SP−1→SP	•	•	•	•	•	•
PULL DATA	PULA													33	4	1	SP+1→SP, M$_{SP}$→A	•	•	•	•	•	•
	PULB													33	4	1	SP+1→SP, M$_{SP}$→B	•	•	•	•	•	•
ROTATE LEFT	ROL							69	6	2	79	6	3				M	•	•	↕	↕	(6)	↕
	ROLA													49	2	1	A	•	•	↕	↕	(6)	↕
	ROLB													59	2	1	B	•	•	↕	↕	(6)	↕
ROTATE RIGHT	ROR							66	6	2	76	6	3				M	•	•	↕	↕	(6)	↕
	RORA													46	2	1	A	•	•	↕	↕	(6)	↕
	RORB													56	2	1	B	•	•	↕	↕	(6)	↕
SHIFT LEFT Arithmetic	ASL							66	6	2	78	6	3				M	•	•	↕	↕	(6)	↕
	ASLA													48	2	1	A	•	•	↕	↕	(6)	↕
	ASLB													58	2	1	B	•	•	↕	↕	(6)	↕
DOUBLE SHIFT LEFT, Arithmetic	ASLD													05	3	1	ACC A / ACC B →0	•	•	↕	↕	(6)	•
SHIFT RIGHT Arithmetic	ASR							67	6	2	77	6	3				M	•	•	↕	↕	(6)	↕
	ASRA													47	2	1	A	•	•	↕	↕	(6)	↕
	ASRB													57	2	1	B	•	•	↕	↕	(6)	↕
SHIFT RIGHT, LOGICAL	LSR							64	6	2	74	6	3				M	•	•	R	↕	(6)	↕
	LSRA													44	2	1	A	•	•	R	↕	(6)	↕
	LSRB													54	2	1	B			↕	↕		↕
DOUBLE SHIFT RIGHT LOGICAL	LSRD													04	3	1	0→ ACC A / ACC B →C	•	•	R	↕	(6)	↕
STORE ACCUMULATOR	STAA				97	3	2	A7	4	2	B7	4	3				A→M	•	•	↕	↕	R	•
	STAB				D7	3	2	E7	4	2	B7	4	3				B→M	•	•	↕	↕	R	•
STORE DOUBLE ACCUMULATOR	STAD				DD	4	2	ED	5	2	FD	5	3				A→M B→M+1	•	•	↕	↕	R	•
SUBTRACT	SUBA	80	2	2	90	3	2	A0	4	2	B0	4	3				A−M→A	•	•	↕	↕	↕	↕
	SUBB	C0	2	2	D0	3	2	E0	4	2	F0	4	3				B−M→B	•	•	↕	↕	↕	↕
DOUBLE SUBTRACT	SUBD	83	4	3	93	5	2	A3	6	2	B3	6	3				A:B − M:M+1→AB	•	•	↕	↕	↕	↕
SUBTRACT ACCUMULATORS	SBA													10	2	1	A − B→A	•	•	↕	↕	↕	↕
SUBTRACT WITH CARRY	SBCA	82	2	2	92	3	2	A2	4	2	B2	4	3				A − M − C→A	•	•	↕	↕	↕	↕
	SBCD	C2	2	2	D2	2	2	E2	4	2	F2	4	3				B − M − C→B	•	•	↕	↕	↕	↕
TRANSFER ACCUMULATORS	TAB													16	2	1	A→B	•	•	↕	↕	R	•
	TBA													16	2	1	A→B	•	•	↕	↕	R	•
TEST ZERO OR MINUS	TST							6D	6	2	7D	6	3				M − 00	•	•	↕	↕	R	R
	TSTB													5D	2	1	B − 00	•	•	↕	↕	R	R

The Condition Code Register notes are listed after Table 10.

Added Instructions

In addition to the existing S6800 Instruction Set, the following new instructions are incorporated in the S6801 Micro-computer.

ABX   Adds the 8-bit unsigned accumulator B to the 16-bit X-Register taking in-to account the possible carry out of the low order byte of the X-Register.

$IX \leftarrow IX + ACCB$

ADDD   Adds the double precision ACCD* to the double precision value M:M + 1 and places the results in ACCD.

$ACCD \leftarrow (ACCD) + (M:M + 1)$

ASLD   Shifts all bits of ACCAB one place to the left. Bit 0 is loaded with zero. The C bit is loaded from the most significant bit of ACCD.

LDD   Loads the contents of double precision memory location into the double accumulator A:B. The condition codes are set according to the data.

$ACCD \leftarrow (M:M + 1)$

LSRD   Shifts all bits of ACCD one place to the right. Bit 15 is loaded with zero. The C bit is loaded from the least significant bit to ACCD.

MUL   Multiplies the 8 bits in accumulator A with the 8 bits in accumulator B to obtain a 16-bit unsigned number in A:B. ACCA contains MSB of result.

$ACCD \leftarrow ACCA * ACCB$

PSHX   The contents of the index register is pushed onto the stack at the address contained in the stack pointer. The stack pointer is decremented by 2.

$\downarrow(IXL), SP \leftarrow (SP) - 1$
$\downarrow(IXL), SP \leftarrow (SP) - 1$

PULX   The index register is pulled from the stack beginning at the current address contained in the stack pointer + 1. The stack pointer is incremented by 2 in total.

$SP \leftarrow (SP) + 1; IXH$
$SP \leftarrow (SP) + 1; IHL$

STD   Stores the contents of double accumulator A:B in memory. The contents of ACCD remain unchanged.

$M:M + 1 \leftarrow (ACCD)$

*ACCD is the 16-bit register (A:B) formed by concatenating the A and B accumulators. The A-accumulator is the most significant byte.

Table 8. Index Register and Stack Manipulation Instructions

POINTER OPERATIONS	MNEMONIC	IMMED. OP	~	#	DIRECT OP	~	#	INDEX OP	~	#	EXTEND OP	~	#	IMPLIED OP	~	#	Boolean/Arithmetic Operation	COND. CODE REG. 5 H	4 I	3 N	2 Z	1 V	0 C
Compare Index Reg	CPX	8C	4	3	9C	5	2	AC	6	2	BC	6	3				$X_H - M, X_L - (M + 1)$	•	•	⑦	‡	⑧	•
Decrement Index Reg	DEX													09	3	1	$X - 1 \rightarrow X$	•	•	•	‡	•	•
Decrement Stack Pointer	DES													34	3	1	$SP - 1 \rightarrow SP$	•	•	•	•	•	•
Increment Index Reg	INX													08	3	1	$X + 1 \rightarrow X$	•	•	•	‡	•	•
Increment Stack Pointer	INS													31	3	1	$1SP + 1 \rightarrow SP$	•	•	•	•	•	•
Load Index Reg	LDX	CE	3	3	DE	4	2	EE	5	2	FE	5	3				$M \rightarrow X_H, (M + 1) \rightarrow X_L$	•	•	⑨	‡	R	•
Load Stack Pointer	LDS	8E	3	3	9E	4	2	AE	5	2	BE	5	3				$M \rightarrow SP_H, (M + 1) \rightarrow SP_L$	•	•	⑨	‡	R	•
Store Index Reg	STX				DF	4	2	EF	5	2	FF	5	3				$X_H \rightarrow M, X_L \rightarrow (M + 1)$	•	•	⑨	‡	R	•
Store Stack Pointer	STS				9F	5	2	AF	7	2	BF	6	3				$SP_H \rightarrow M, SP_L \rightarrow (M + 1)$	•	•	⑨	‡	R	•
Index Reg → Stack Pointer	TXS													35	3	1	$X - 1 \rightarrow SP$	•	•	•	•	•	•
Stack Pointer → Index Reg	TSX													30	3	1	$SP + 1 \rightarrow X$	•	•	•	•	•	•
Add	ABX													3A	3	1	$B + X \rightarrow X$	•	•	•	•	•	•
Push Data	PSHX													3C	3	1	$X_L \rightarrow M_{SP}, SP - 1 \rightarrow SP$ $X_H \rightarrow H_{SP}, SP - 1 \rightarrow SP$	•	•	•	•	•	•
Pull Data	PULX													30	5	1	$SP + 1 \rightarrow SP, M_{SP} \rightarrow X_H$ $SP + 1 \rightarrow SP, M_{SP} \rightarrow X_L$	•	•	•	•	•	•

The Condition Code Register notes are listed after Table 10

Table 9. Jump and Branch Instructions

OPERATIONS	MNEMONIC	RELATIVE OP	~	#	INDEX OP	~	#	EXTND OP	~	#	IMPLIED OP	~	#	BRANCH TEST	COND. CODE REG. 5 H	4 I	3 N	2 Z	1 V	0 C
Branch Always	BRA	20	4	2										None	•	•	•	•	•	•
Branch If Carry Clear	BCC	24	4	2										C = 0	•	•	•	•	•	•
Branch If Carry Set	BCS	25	4	2										C = 1	•	•	•	•	•	•
Branch If = 0	BEO	27	4	2										Z = 1	•	•	•	•	•	•
Branch If ⩾ Zero	BGE	2C	4	2										N ⊕ V = 0	•	•	•	•	•	•
Branch If >Zero	BGT	2E	4	2										Z + (N ⊕ V) = 0	•	•	•	•	•	•
Branch If Higher	BHI	22	4	2										C + Z = 0	•	•	•	•	•	•
Branch If⩽Zero	BLE	2F	4	2										Z + (N ⊕ V) = 1	•	•	•	•	•	•
Branch If Lower Or Same	BLS	23	4	2										C + Z = 1	•	•	•	•	•	•
Branch If< Zero	BLT	2D	4	2										N ⊕ V = 1	•	•	•	•	•	•
Branch If Minus	BMI	28	4	2										N = 1	•	•	•	•	•	•
Branch If Not Equal Zero	BNE	20	4	2										Z = 0	•	•	•	•	•	•
Branch If Overflow Clear	BVC	28	4	2										V = 0	•	•	•	•	•	•
Branch If Overflow Set	BVS	29	4	2										V = 1	•	•	•	•	•	•
Branch If Plus	BPL	2A	4	2										N = 0	•	•	•	•	•	•
Branch To Subroutine	BSR	8D	8	2											•	•	•	•	•	•
Jump	JMP				6E	4	2	7E	3	3				See Special Operations	•	•	•	•	•	•
Jump To Subroutine	JSR				AD	8	2	8D	9	3					•	•	•	•	•	•
No Operation	NOP										01	2	1	Advances Prog. Cntr. Only	•	•	•	•	•	•
Return From Interrupt	RTI										3B	10	1		⑩					
Return From Subroutine	RTS										39	5	1		•	•	•	•	•	•
Software Interrupt	SWI										3F	12	1	See Special Operations	•	•	•	•	•	•
Wait For Interrupt*	WAI										3E	9	1		•	⑪	•	•	•	•

Table 10. Condition Code Register Manipulation Instructions

OPERATIONS	MNEMONIC	IMPLIED OP	~	#	BOOLEAN OPERATION	COND. CODE REG. 5 H	4 I	3 N	2 Z	1 V	0 C
Clear Carry	CLC	0C	2	1	0→C	•	•	•	•	•	R
Clear Interrupt Mask	CLI	0E	2	1	0→1	•	R	•	•	•	•
Clear Overflow	CLV	0A	2	1	0→V	•	•	•	•	R	•
Set Carry	SEC	0D	2	1	1→C	•	•	•	•	•	S
Set Interrupt Mask	SEI	0F	2	1	1→1	•	S	•	•	•	•
Set Overflow	SEV	0B	2	1	1→V	•	•	•	•	S	•
Accumulator A→CCR	TAP	06	2	1	A→CCR	⑫					
CCR→Accumulator A	TPA	07	2	1	CCR→A	•	•	•	•	•	•

CONDITION CODE REGISTER NOTES: (Bit set if test is true and cleared otherwise).

1 (Bit V) Test Result = 10000000?
2 (Bit C) Test Result = 00000000?
3 (Bit C) Test: Decimal value of most significant BCD Character greater than nine? (Not cleared if previously set.)
4 (Bit V) Test: Operand = 10000000 prior to execution?
5 (Bit V) Test: Operand = 01111111 prior to execution?
6 (Bit V) Test: Set equal to result of N⊕C after shift has occurred.

7 (Bit N) Test: Sign Bit of most significant (MS) byte = 1?
8 (Bit V) Test: 2's complement overflow from subtraction of MS bytes?
9 (Bit N) Test: Result less than zero? (Bit 15 = 1)
10 (All) Load Condition Code Register from Stack. (See Special Operations)
11 (Bit I) Set when interrupt occurs. If previously set, a Non-Maskable Interrupt as required to exit the wait state.
12 (All) Set according to the contents of Accumulator A.

Figure 25. Special Operations

JSR, JUMP TO SUBROUTINE:

INDXD
PC	MAIN PROGRAM
n	AD = JSR
n + 1	K = OFFSET*
n + 2	NEXT MAIN INSTR.

*K = 8-BIT UNSIGNED VALUE

SP	STACK
SP – 2	
SP – 1	(n + 2) H
SP	(n + 2) L

$(n + 2)_H$ AND $(n + 2)_L$ FORM n + 2

PC	SUBROUTINE
INX + K	1ST. SUBR. INSTR.

EXTND
PC	MAIN PROGRAM
n	BD = JSR
n + 1	SH = SUBR. ADDR.
n + 2	SL = SUBR. ADDR.
n + 3	NEXT MAIN INSTR.

SP	STACK
SP – 2	
SP – 1	(n + 3) H
SP	(n + 3) L

→ = STACK POINTER
AFTER EXECUTION

PC	SUBROUTINE
S	1ST. SUBR. INSTR.

(S FORMED FROM S_H AND S_L)

BSR, BRANCH TO SUBROUTINE:

PC	MAIN PROGRAM
n	8D = BSR
n + 1	± K = OFFSET*
n + 2	NEXT MAIN INSTR.

*K = 7-BIT SIGNED VALUE:

SP	STACK
SP – 2	
SP – 1	(n + 2) H
SP	(n + 2) L

n + 2 FORMED FROM
$(n + 2)_H$ AND $(n + 2)_L$

PC	SUBROUTINE
n + 2 + K	1ST. SUBR. INSTR.

JMP, JUMP;

INDXD
PC	MAIN PROGRAM
n	6E = JMP
n + 1	K = OFFSET
⋮	
X + K	NEXT INSTRUCTION

EXTENDED
PC	SUBROUTINE
n	7E = JMP
n+1	K_H = NEXT ADDRESS
n+2	K_L = NEXT ADDRESS
⋮	
K	NEXT INSTRUCTION

RTS, RETURN FROM SUBROUTINE:

PC	SUBROUTINE
S	39 = RTS

SP	STACK
SP	
SP + 1	N_H
SP + 2	N_L

PC	MAIN PROGRAM
n	NEXT MAIN INSTR.

RTI, RETURN FROM INTERRUPT:

PC	INTERRUPT PROGRAM
S	3B = RTI

SP	STACK
SP	
SP + 1	CONDITION CODE
SP + 2	ACMLTR B
SP + 3	ACMLTR A
SP + 4	INDEX REGISTER (X_H)
SP + 5	INDEX REGISTER (X_L)
SP + 6	N_H
SP + 7	N_L

PC	MAIN PROGRAM
n	NEXT MAIN INSTR.

Table 11. Instruction Execution Times in Machine Cycle

	ACCX	IMMEDIATE	DIRECT	EXTENDED	INDEXED	INHERENT	RELATIVE
ABA	•	•	•	•	•	2	•
ABX	•	•	•	•	•	3	•
ADC	•	2	3	4	4	•	•
ADD	•	2	3	4	4	•	•
ADDD	•	4	5	6	6	•	•
AND	•	2	3	4	4	•	•
ASL	2	•	•	6	6	•	•
ASLD	•	•	•	•	•	3	•
ASR	2	•	•	6	6	•	•
BCC	•	•	•	•	•	•	3
BCS	•	•	•	•	•	•	3
BEQ	•	•	•	•	•	•	3
BGE	•	•	•	•	•	•	3
BGT	•	•	•	•	•	•	3
BHI	•	•	•	•	•	•	3
BIT	•	2	3	4	4	•	•
BLE	•	•	•	•	•	•	3
BLS	•	•	•	•	•	•	3
BLT	•	•	•	•	•	•	3
BMI	•	•	•	•	•	•	3
BNE	•	•	•	•	•	•	3
BPL	•	•	•	•	•	•	3
BRA	•	•	•	•	•	•	3
BSR	•	•	•	•	•	•	6
BVC	•	•	•	•	•	•	3
BVS	•	•	•	•	•	•	3
CBA	•	•	•	•	•	2	•
CLC	•	•	•	•	•	2	•
CLI	•	•	•	•	•	2	•
CLR	2	•	•	6	6	•	•
CLV	•	•	•	•	•	2	•
CMP	•	2	3	4	4	•	•
COM	2	•	•	6	6	•	•
CPX	•	4	5	6	6	•	•
DAA	•	•	•	•	•	2	•
DEC	2	•	•	6	6	•	•
DES	•	•	•	•	•	3	•
DEX	•	•	•	•	•	3	•
EOR	•	2	3	4	4	•	•
INC	2	•	•	6	6	•	•
INS	•	•	•	•	•	3	•

	ACCX	IMMEDIATE	DIRECT	EXTENDED	INDEXED	INHERENT	RELATIVE
INX	•	•	•	•	•	3	•
JMP	•	•	•	3	3	•	•
JSR	•	•	5	6	6	•	•
LDA	•	2	3	4	4	•	•
LDD	•	3	4	5	5	•	•
LDS	•	3	4	5	5	•	•
LDX	•	3	4	5	5	•	•
LSR	2	•	•	6	6	•	•
LSRD	•	•	•	•	•	3	•
MUL	•	•	•	•	•	10	•
NEG	2	•	•	6	6	•	•
NOP	•	•	•	•	•	2	•
ORA	•	2	3	4	4	•	•
PSH	3	•	•	•	•	•	•
PSHX	•	•	•	•	•	4	•
PUL	4	•	•	•	□	•	•
PULX	•	•	•	•	•	5	•
ROL	2	•	•	6	6	•	•
ROR	2	•	•	6	6	•	•
RTI	•	•	•	•	•	10	•
RTS	•	•	•	•	•	6	•
SBA	•	•	•	•	•	2	•
SBC	•	2	3	4	4	•	•
SEC	•	•	•	•	•	2	•
SEI	•	•	•	•	•	2	•
SEV	•	•	•	•	•	2	•
STA	•	•	3	4	4	•	•
STD	•	•	4	5	5	•	•
STS	•	•	4	5	6	•	•
STX	•	•	4	5	5	•	•
SUB	•	4	5	6	6	•	•
SUBD	•	4	5	6	6	•	•
SWI	•	•	•	•	•	12	•
TAB	•	•	•	•	•	2	•
TAP	•	•	•	•	•	2	•
TBA	•	•	•	•	•	2	•
TPA	•	•	•	•	•	2	•
TST	•	•	•	6	6	•	•
TSX	•	•	•	•	•	2	•
TXS	•	•	•	•	•	3	•
WAI	•	•	•	•	•	9	•

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Summary of Cycle by Cycle Operation

Table 12 provides a detailed description of the information present on the Address Bus, Data Bus, and the Read/Write line (R/W) during each cycle for each instruction.

This information is useful in comparing actual with expected results during debug of both software and hardware as the control program is executed. The information is categorized in groups according to addressing mode and number of cycles per instruction. (In general, instructions with the same addressing mode and number of cycles execute in the same manner; exceptions are indicated in the table).

Table 12. Cycle by Cycle Operation

ADDRESS MODE & INSTRUCTIONS	CYCLE	CYCLE #	ADDRESS BUS	R/W LINE	DATA BUS
IMMEDIATE					
ADC EOR ADD LDA AND ORA BIT SBC CMP SUB	2	1 2	OP CODE ADDRESS OP CODE ADDRESS + 1	1 1	OP CODE OPERAND DATA
LDS LDX	3	1 2 3	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2	1 1 1	OP CODE OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte)
CPX SUBD ADDD	4	1 2 3 4	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 ADDRESS BUS FFFF	1 1 1 1	OP CODE OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte) LOW BYTE OF RESTART VECTOR
DIRECT					
ADC EOR ADD LDA AND ORA BIT SBC CMP SUB	3	1 2 3	OP CODE ADDRESS OP CODE ADDRESS + 1 ADDRESS OF OPERAND	1 1 1	OP CODE ADDRESS OF OPERAND OPERAND DATA
STA	3	1 2 3	OP CODE ADDRESS OP CODE ADDRESS + 1 DESTINATION ADDRESS	1 1 0	OP CODE DESTINATION ADDRESS DATA FROM ACCUMULATOR
LDS LDX LDD	4	1 2 3 4	OP CODE ADDRESS OP CODE ADDRESS + 1 ADDRESS OF OPERAND OPERAND ADDRESS + 1	1 1 1 1	OP CODE ADDRESS OF OPERAND OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte)
STS STX STD	4	1 2 3 4	OP CODE ADDRESS OP CODE ADDRESS + 1 ADDRESS OF OPERAND ADDRESS OF OPERAND + 1	1 1 0 0	OP CODE ADDRESS OF OPERAND REGISTER DATA (High Order Byte) REGISTER DATA (Low Order Byte)
CPX SUBD ADDD	5	1 2 3 4 5	OP CODE ADDRESS OP CODE ADDRESS + 1 OPERAND ADDRESS OPERAND ADDRESS + 1 ADDRESS BUS FFFF	1 1 1 1 1	OP CODE ADDRESS OF OPERAND OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte) LOW BYTE OF RESTART VECTOR
JSR	5	1 2 3 4 5	OP CODE ADDRESS OP CODE ADDRESS + 1 SUBROUTINE ADDRESS STACK POINTER STACK POINTER + 1	1 1 1 0 0	OP CODE IRRELEVANT DATA FIRST SUBROUTINE OP CODE RETURN ADDRESS (High Order Byte) RETURN ADDRESS (Low Order Byte)

(continued)

Table 12. Cycle by Cycle Operation (continued)

ADDRESS MODE & INSTRUCTIONS	CYCLE	CYCLE #	ADDRESS BUS	R/W LINE	DATA BUS
INDEXED					
JMP	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OFFSET
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
ADC EOR	4	1	OP CODE ADDRESS	1	OP CODE
ADD LDA		2	OP CODE ADDRESS + 1	1	OFFSET
AND ORA		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
BIT SBC		4	INDEX REGISTER PLUS OFFSET	1	OPERAND DATA
CMP SUB					
STA	4	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OFFSET
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
		4	INDEX REGISTER PLUS OFFSET	0	OPERAND DATA
LDS	5	1	OP CODE ADDRESS	1	OP CODE
LDX		2	OP CODE ADDRESS + 1	1	OFFSET
LDD		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
		4	INDEX REGISTER PLUS OFFSET	1	OPERAND DATA (High Order Byte)
		5	INDEX REGISTER + 1	1	OPERAND DATA (Low Order Byte)
STS	5	1	OP CODE ADDRESS	1	OP CODE
STX		2	OP CODE ADDRESS + 1	1	OFFSET
STD		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
		4	INDEX REGISTER PLUS OFFSET	0	OPERAND DATA (High Order Byte)
		5	INDEX REGISTER PLUS OFFSET	0	OPERAND DATA (Low Order Byte)
ASL LSR	6	1	OP CODE ADDRESS	1	OP CODE
ASR NEG		2	OP CODE ADDRESS + 1	1	OFFSET
CLR ROL		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
COM ROR		4	INDEX REGISTER PLUS OFFSET	1	CURRENT OPERAND DATA
DEC TST (1)		5	ADDRESS BUS FFFF	1	CURRENT OPERAND DATA
INC		6	INDEX REGISTER PLUS OFFSET	0	NEW OPERAND DATA
CPX	6	1	OP CODE ADDRESS	1	OP CODE
SUBD		2	OP CODE ADDRESS + 1	1	OFFSET
ADDD		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
		4	INDEX REGISTER + OFFSET	1	OPERAND DATA (High Order Byte)
		5	INDEX REGISTER + OFFSET	1	OPERAND DATA (Low Order Byte)
		6	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
JSR	6	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OFFSET
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
		4	INDEX REGISTER + OFFSET	1	FIRST SUBROUTINE OP CODE
		5	STACK POINTER	0	RETURN ADDRESS (Low Order Byte
		6	STACK POINTER + 1	0	RETURN ADDRESS (High Order Byte)
EXTENDED					
JMP	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	JUMP ADDRESS (High Order Byte)
		3	OP CODE ADDRESS	1	JUMP ADDRESS (Low Order Byte)

(continued)

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Table 12. Cycle by Cycle Operation (continued)

ADDRESS MODE & INSTRUCTIONS	CYCLE	CYCLE #	ADDRESS BUS	R/W LINE	DATA BUS
EXTENDED					
ADC EOR ADD LDA AND ORA BIT SBC CMP SUB	4	1 2 3 4	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 ADDRESS OF OPERAND	1 1 1 1	OP CODE ADDRESS OF OPERAND ADDRESS OF OPERAND (Low Order Byte) OPERAND DATA
STA A STA B	4	1 2 3 4	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 OPERAND DESTINATION ADDRESS	1 1 1 0	OP CODE DESTINATION ADDRESS (High Order Byte) DESTINATION ADDRESS (Low Order Byte) DATA FROM THE ACCUMULATOR
LDS LDX LDD	5	1 2 3 4 5	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 ADDRESS OF OPERAND ADDRESS OF OPERAND + 1	1 1 1 1 1	OP CODE ADDRESS OF OPERAND (High Order Byte) ADDRESS OF OPERAND (Low Order Byte) OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte)
STS STX STD	5	1 2 3 4 5	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 ADDRESS OF OPERAND ADDRESS OF OPERAND	1 1 1 0 0	OP CODE ADDRESS OF OPERAND (High Order Byte) ADDRESS OF OPERAND (Low Order Byte) OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte)
ASL LSR ASR NEG CLR ROL COM ROR DEC TST (1) INC	6	1 2 3 4 5 6	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 ADDRESS OF OPERAND ADDRESS BUS FFFF ADDRESS OF OPERAND	1 1 1 1 1 0	OP CODE ADDRESS OF OPERAND (High Order Byte) ADDRESS OF OPERAND (Low Order Byte) CURRENT OPERAND DATA LOW BYTE OF RESTART VECTOR NEW OPERAND DATA
CPX SUBD ADDD	6	1 2 3 4 5 6	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 OPERAND ADDRESS OPERAND ADDRESS + 1 ADDRESS BUS FFFF	1 1 1 1 1	OP CODE OPERAND ADDRESS OPERAND ADDRESS (Low Order Byte) OPERAND DATA (High Order Byte) OPERAND DATA (Low Order Byte) LOW BYTE OF RESTART VECTOR
JSR	6	1 2 3 4 5 6	OP CODE ADDRESS OP CODE ADDRESS + 1 OP CODE ADDRESS + 2 SUBROUTINE STARTING ADDRESS STACK POINTER STACK POINTER − 1	1 1 1 1 0 0	OP CODE ADDRESS OF SUBROUTINE (High Order Byte) ADDRESS OF SUBROUTINE (High Order Byte) OP CODE OF NEXT INSTRUCTION RETURN ADDRESS (Low Order Byte ADDRESS OF OPERAND (High Order Byte)
INHERENT					
ABA DAA SEC ASL DEC SEI ASR INC SEV CBA LSR TAB CLC NEG TAP CLI NOP TBA CLR ROL TPA CLV ROR TST COM SBA	2	1 2	OP CODE ADDRESS OP CODE ADDRESS + 1	1 1	OP CODE OP CODE OF NEXT INSTRUCTION

(continued)

Table 12. Cycle by Cycle Operation (continued)

ADDRESS MODE & INSTRUCTIONS	CYCLE	CYCLE #	ADDRESS BUS	R/W LINE	DATA BUS
INHERENT					
ABX	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	IRRELEVANT DATA
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
ASLD LSRD	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	IRRELEVANT DATA
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
DES INS	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OP CODE OF NEXT INSTRUCTION
		3	PREVIOUS REGISTER CONTENTS	1	IRRELEVANT DATA
INX DEX	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OP CODE OF NEXT INSTRUCTION
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
PSHA PSHB	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OP CODE OF NEXT INSTRUCTION
		3	STACK POINTER	0	ACCUMULATOR DATA
ISX	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OP CODE OF NEXT INSTRUCTION
		3	STACK POINTER	1	IRRELEVANT DATA
TXS	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OP CODE OF NEXT INSTRUCTION
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
PULA PULB	4	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	OP CODE OF NEXT INSTRUCTION
		3	STACK POINTER	1	IRRELEVANT DATA
		4	STACK POINTER	1	
PSHX	4	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	IRRELEVANT DATA
		3	STACK POINTER	0	INDEX REGISTER (Low Order Byte)
		4	STACK POINTER − 1	0	INDEX REGISTER (High Order Byte)
PULX	5	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	IRRELEVANT DATA
		3	STACK POINTER	1	IRRELEVANT DATA
		4	STACK POINTER + 1	1	INDEX REGISTER (High Order Byte)
		5	STACK POINTER + 2	1	INDEX REGISTER (Low Order Byte)
BCC BHT BNE BCS BLE BPL BEQ BLS BRA BGE BLT BVC BGT BMT BVS	3	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	BRANCH OFFSET
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
BSR	6	1	OP CODE ADDRESS	1	OP CODE
		2	OP CODE ADDRESS + 1	1	BRANCH OFFSET
		3	ADDRESS BUS FFFF	1	LOW BYTE OF RESTART VECTOR
		4	SUBROUTINE STARTING ADDRESS	1	RETURN ADDRESS (Low Order Byte)
		5	STACK POINTER	0	RETURN ADDRESS (Low Order Byte)
		6	STACK POINTER − 1	0	RETURN ADDRESS (High Order Byte)

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Figure 26. S6801E MCU Single-Chip Mode
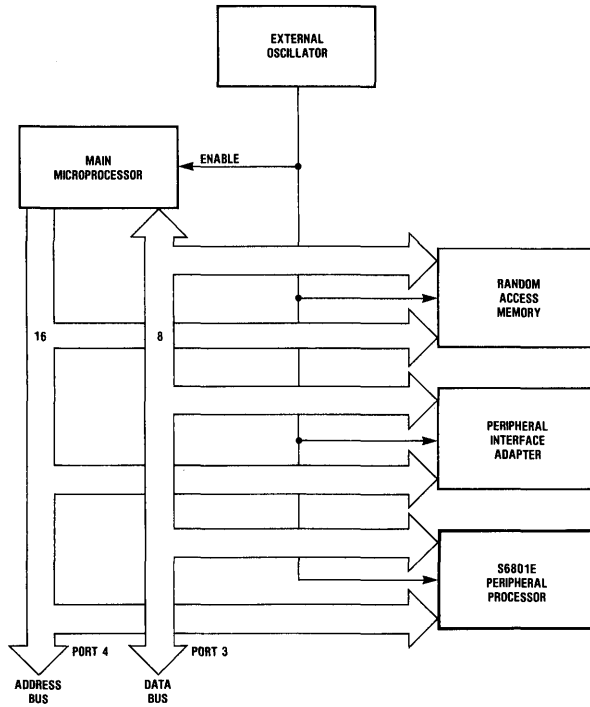
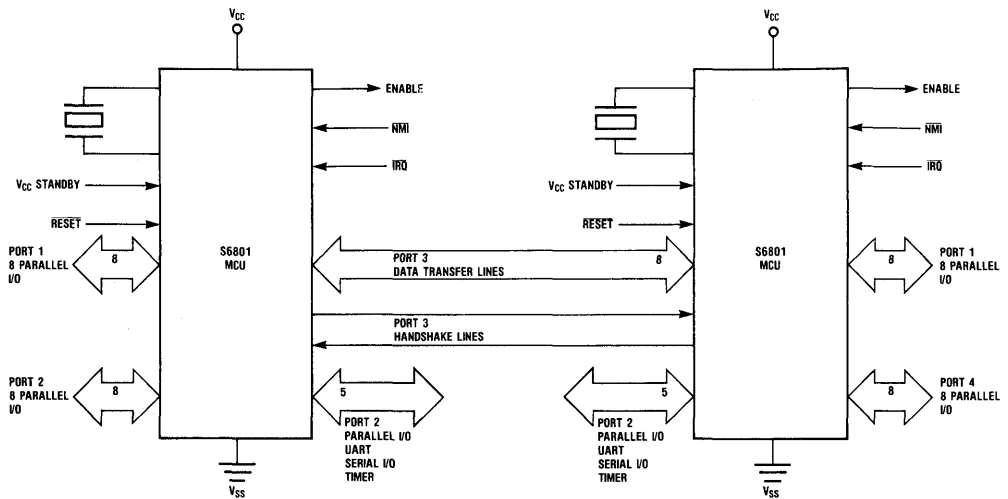**Figure 27. S6801 MCU Single-Chip Dual Processor Configuration**

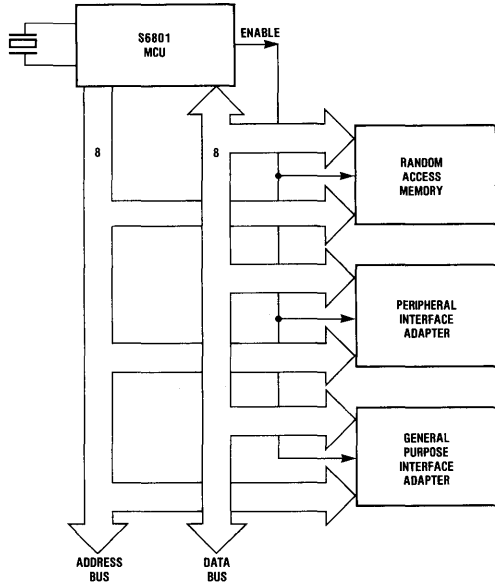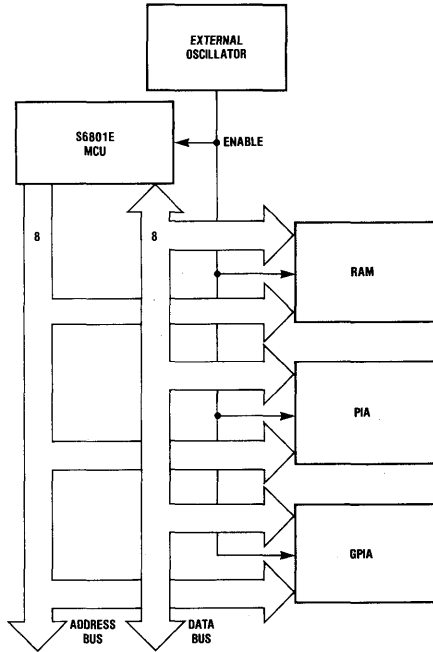Figure 28. S6801 MCU Expanded Non-Multiplexed Mode

Figure 30. S6801E Expanded Non-Multiplexed Mode
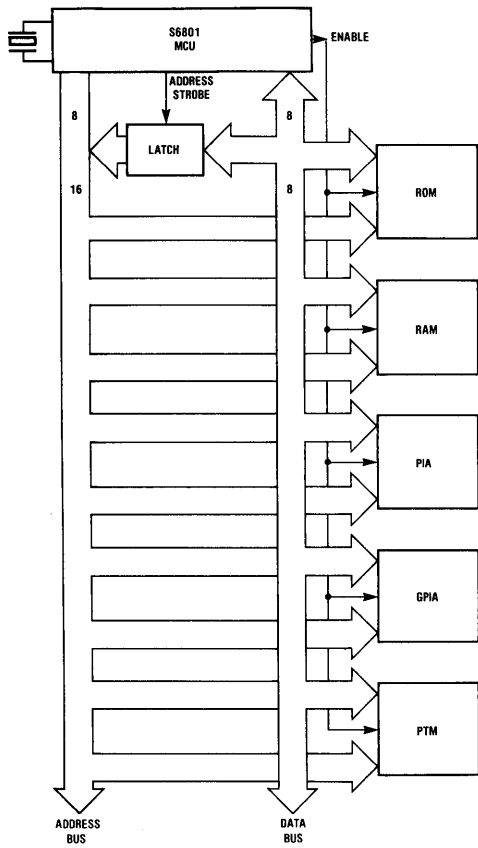
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Figure 31. S6801 MCU Expanded
Multiplexed Mode
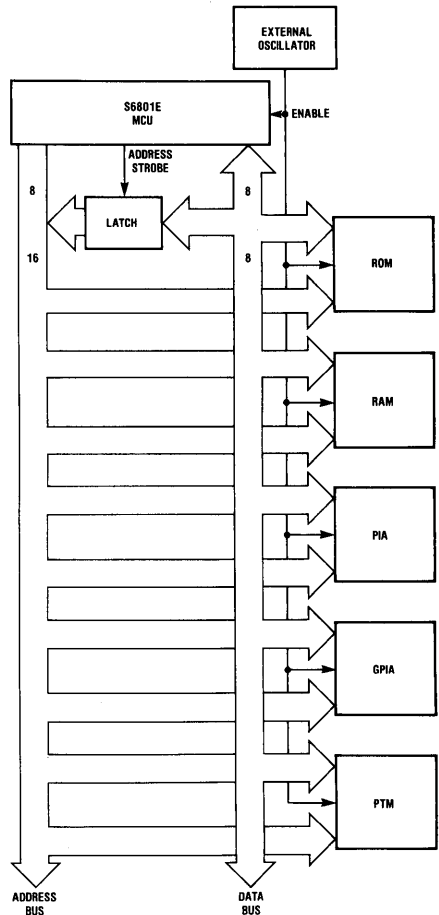
Figure 31. S6801E Expanded
Multiplexed Mode

Table 13. Mode and Port Summary

MCU	MODE	PORT 1 Eight Lines	PORT 2 Five Lines	PORT 3 Eight Lines	PORT 4 Eight Lines	CC1	CC2	SC1	SC2
S6801	SINGLE CHIP	I/O	I/O	I/O	I/O	XTAL1(I)	XTAL2(I)	IS3(O)	OS3(O)
	EXPANDED MUX	I/O	I/O	ADDRESS BUS (A0-A7) DATA BUS (D0-D7)	ADDRESS BUS* (A8-A15)	XTAL1(I)	XTAL2(I)	AS(O)	R/$\overline{W}$(O)
	EXPANDED NON-MUX	I/O	I/O	DATA BUS (D0-D7)	ADDRESS BUS* (A0-A7)	XTAL1(I)	XTAL2(I)	IOS(O)	R/$\overline{W}$(O)
S6801E	SINGLE CHIP	I/O	I/O	DATA BUS (D0-D7)	I/O	R/$\overline{W}$(I)	RS0(I)	CS3(I)	OS3(O)
	EXPANDED MUX	I/O	I/O	ADDRESS BUS (A0-A7) DATA BUS (D0-D7)	ADDRESS BUS* (A8-A15)	$\overline{HALT}$(I)	BA(O)	AS(O)	R/$\overline{W}$(O)
	EXPANDED NON-MUX	I/O	I/O	DATA BUS (D0-D7)	ADDRESS BUS* (A0-A7)	$\overline{HALT}$(I)	BA(O)	IOS(O)	R/$\overline{W}$(O)

*These lines can be substituted for I/O (Input Only) starting with the most significant address line.

I = Input	IS = Input Strobe
O = Output	OS = Output Strobe
BA = Bus Available	IOS = I/O Select
R/$\overline{W}$ = Read/$\overline{Write}$	CS = Chip Select
CC = Crystal Control	AS = Address Strobe
	SC = Strobe Control

S6800

MICROPROCESSOR
WITH CLOCK AND RAM

Features

☐ On-Chip Clock Circuit

☐ 128 x 8 Bit On-Chip RAM

☐ 32 Bytes of RAM Are Retainable

☐ Software-Compatible with the S6800

☐ Expandable to 65K Words

☐ Standard TTL-Compatible Inputs and Outputs

☐ 8-Bit Word Size

☐ 16-Bit Memory Addressing

☐ Interrupt Capability

☐ Clock Rates:
   S6802 — 1.0MHz
   S68A02 — 1.5MHz

General Description

The S6802/S68A02 are monolithic 8-bit micropro-cessors that contain all the registers and accumulators of the present S6800 plus an internal clock oscillator and driver on the same chip. In addition, the S6802/S68A02 both have 128 bytes of RAM on board located at hex addresses 0000 to 007E. The first 32 bytes of RAM, at addresses 0000 to 001F, may be retained in a low power mode by utilizing V_{CC} standby, thus facilitating memory retention during a power-down situation.

The S6802/S68A02 are completely software compat-ible with the S6800 as well as the entire S6800 family of parts. Hence, the S6802/S68A02 are expandable to 65K words. When the S6802 is interfaced with the S6846 ROM — I/O — Timer chip, as shown in the Block Diagram below, a basic 2-chip microcomputer system is realized.

Typical Microcomputer Block Diagram

BLOCK DIAGRAM OF A TYPICAL COST EFFECTIVE MICROCOMPUTER. THE MPU IS THE CENTER OF THE MICROCOMPUTER SYSTEM AND IS SHOWN IN A MINIMUM SYSTEM INTERFACING WITH A ROM COMBINATION CHIP. IT IS NOT INTENDED THAT THIS SYSTEM BE LIMITED TO THIS FUNCTION BUT THAT IT BE EXPANDABLE WITH OTHER PARTS IN THE S6800 MICROCOMPUTER FAMILY.

Pin Configuration

Absolute Maximum Ratings

Supply Voltage, V_{CC} .... $-0.3V$ to $+7.0V$
Input Voltage, V_{IN} .... $-0.3V$ to $+7.0V$
Operating Temperature Range, T_A .... $0°$ to $+70°C$
Storage Temperature Range, T_{stg} .... $-55°C$ to $+150°C$
Thermal Resistance, θ_{JA}
 Plastic .... $100°C/W$
 Ceramic .... $50°C/W$

This device contains circuitry to protect the inputs against damage due to high static voltage or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

D.C. Electrical Characteristics (V_{CC} = 5.0V ± 5%, V_{SS} = 0, T_A = 0°C to +70°C unless otherwise noted.)

Symbol	Parameter		Min.	Typ.	Max.	Unit
V_{IH}	Input High Voltage	Logic, EXtal $\overline{\text{Reset}}$	V_{SS} +2.0 V_{SS} +4.0	— —	V_{CC} V_{CC}	V
V_{IL}	Input Leakage Voltage	Logic, EXtal, $\overline{\text{Reset}}$	V_{SS} − 0.3	—	V_{SS} + 0.8	V
I_{IN}	Input Leakage Current (V_{IN} = 0 to 5.25V, V_{CC} = Max)	Logic*	—	1.0	2.5	μA
V_{OH}	Output High Voltage					V
	(I_{LOAD} = − 205μA, V_{CC} = Min)	D0 − D7	V_{SS} +2.4	—	—	V
	(I_{LOAD} = − 145μA, V_{CC} = Min)	A0−A15, R/$\overline{W}$, VMA, E	V_{SS} +2.4	—	—	V
	(I_{LOAD} = − 100μA, V_{CC} = Min)	BA	V_{SS} +2.4	—	—	V
V_{OL}	Output Low Voltage (I_{LOAD} = 1.6mA, V_{CC} = Min)		—	—	V_{SS} + 0.4	V
P_D **	Power Dissipation		—	0.600	1.2	W
C_{IN}	Capacitance #					pF
	(V_{IN} = 0, T_A=25°C, f=1.0MHz	D0 − D7	—	10	12.5	
		Logic Inputs, EXtal	—	6.5	10	
C_{OUT}		A0 − A15, R/$\overline{W}$, VMA	—	—	12	pF
V_{CC} Standby	V_{CC} Standby		4.0	—	5.25	V
I_{DD} Standby	I_{DD} RAM Standby		—	—	8.0	mA

Clock Timing (V_{CC} = 5.0V ± 5%, V_{SS} = 0, T_A = 0°C to +70°C unless otherwise noted)

Symbol	Parameter		S6802			S68A02			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
f	Frequency of Operation	Input Clock ÷4	0.1	—	1.0	0.1	—	1.5	MHz
f_{Xtal}		Crystal Frequency	1.0	—	4.0	1.0	—	6.0	
t_{CYC}	Cycle Time		1.0	—	10	1.0	—	6.6	μs
PW$_{\phi Hs}$ PW$_{\phi L}$	Clock Pulse Width Measured at 2.4V		450	—	4500	300	—	3000	ns
t_ϕ	Fall Time Measured between V_{SS} + 0.4V and V_{SS} −2.4V		—	—	25	—	—	25	ns

*Except $\overline{\text{IRQ}}$ and $\overline{\text{NMI}}$, which require 3KΩ pullup load resistors for wire-OR capability at optimum operation. Does not include EXtal and Xtal, which are crystal inputs.
**In power-down mode, maximum power dissipation is less than 40mW.
Capacitances are periodically sampled rather than 100% tested.

Read/Write Timing (Figures 1 through 5; Load Circuit of Figure 3).
(V_{CC} = 5.0V ± 5%, V_{SS} = 0, T_A = 0°C to +70°C unless otherwise noted.)

Symbol	Parameter	S6802			S68A02			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
t_{AD}	Address Delay							ns
	C = 90pF		100	270			180	
	C = 30pF						165	
t_{ACC}	Peripheral Read Access Time			575			360	ns
	$t_{AC} = t_{UT} - (t_{AD} + t_{DSR})$							
t_{DSR}	Data Setup Time (Read)	100			60			ns
t_H	Input Data Hold Time	10	30		10			ns
t_{AH}	Address Hold Time							
	(Address, R/W, VMA)	20			10	75		ns
t_{DDW}	Data Delay Time (Write)		165	225		165	200	ns
	Processor Controls							
t_{PCS}	Processor Control							
	Setup Time			200	200			ns
t_{PC_r}; t_{PC_f}	Processor Control							
	Rise and Fall Time						100	ns

Figure 1. Read Data From Memory or Peripherals
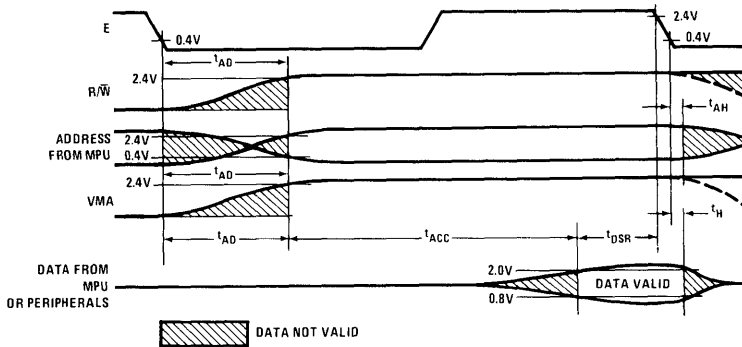
Figure 2. Write Data In Memory or Peripherals
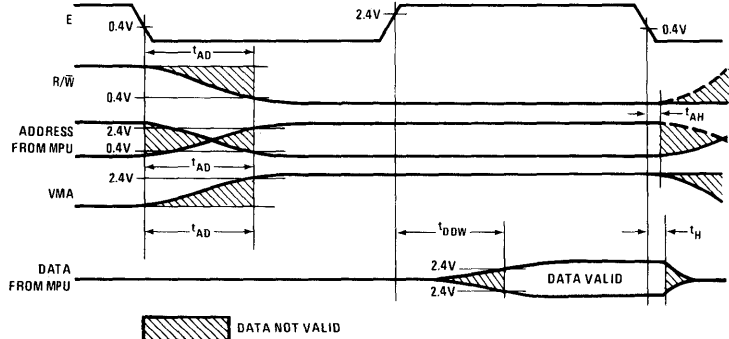
Figure 3. Bus Timing Test Load
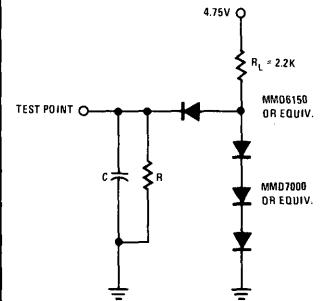
C = 130pF FOR DO – D7, E
 = 90pF FOR AO – A15, R/W, AND VMA
 = 30pF FOR BA
R = 11.7 KΩ FOR DO – D7, E
 = 16.5KΩ FOR AO – A15, R/W, AND VMA
 = 24KΩ FOR BA

Figure 4. Typical Data Bus Output Delay Versus Capacitive Loading

$I_{OH} = -205\,\mu A$ MAX @ 2.4V
$I_{OL} = 1.6mA$ MAX @ 0.4V
$V_{CC} = 5.0V$
$T_A = 25°C$

(S6802, S68A02)

C_L INCLUDES STRAY CAPACITANCE

DELAY TIME (ns)

C_L, LOAD CAPACITANCE (pF)
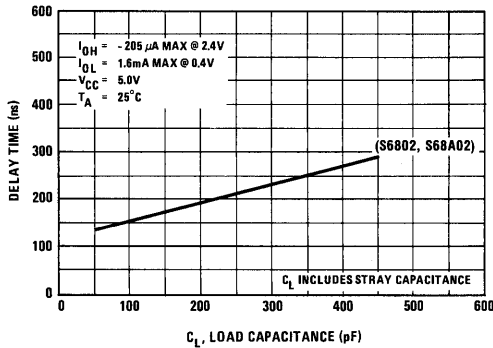
Figure 5. Typical Read/Write, VMA, and Address Output Delay Versus Capacitive Loading

$I_{OH} = -145\,\mu A$ MAX @ 2.4V
$I_{OL} = 1.6mA$ MAX @ 0.4V
$V_{CC} = 5.0V$
$T_A = 25°C$

ADDRESS, VMA (S6802 ONLY)

R/W (S6802, S68A02)

ADDRESS, VMA (S68A02)

C_L INCLUDES STRAY CAPACITANCE

DELAY TIME (ns)

C_L LOAD CAPACITANCE (pF)

S6800
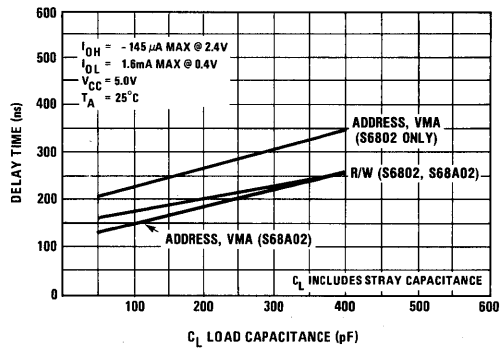
Figure 6. S6802 Expanded Block Diagram

S6805

AMERICAN MICROSYSTEMS, INC.
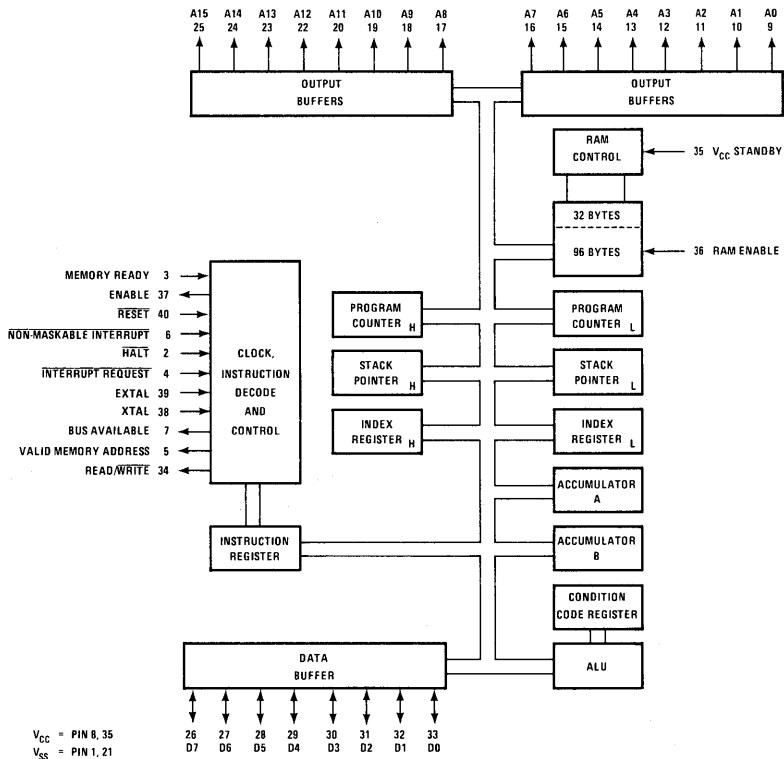
MICROCOMPUTER

Features

☐ **Hardware**
- 8-Bit Architecture
- 64 Bytes RAM
- 1100 Bytes ROM
- 116 Bytes of Self Check ROM
- 28 Pin Package
- Memory Mapped I/O
- Internal 8-Bit Timer with 7-Bit Prescaler
- Vectored Interrupts — External, Timer, Software, Reset
- 20 TTL/CMOS Compatible I/O Line 8 Lines LED Compatible
- On-Chip Clock Circuit
- Self-Check Capability
- Low Voltage Inhibit
- 5 Vdc Single Supply

☐ **Software**
- Similar to 6800
- Byte Efficient Instruction Set
- Versatile Interrupt Handling
- True Bit Manipulation
- Bit Test and Branch Instruction
- Indexed Addressing for Tables
- Memory Usable as Registers/Flags
- 10 Addressing Modes
- Powerful Instruction Set
  - All 6800 Arithmetic Instructions
  - All 6800 Logical Instructions
  - All 6800 Shift Instructions
  - Single Instruction Memory Examine/Change
  - Full Set of Conditional Branches

Block Diagram

Pin Configuration
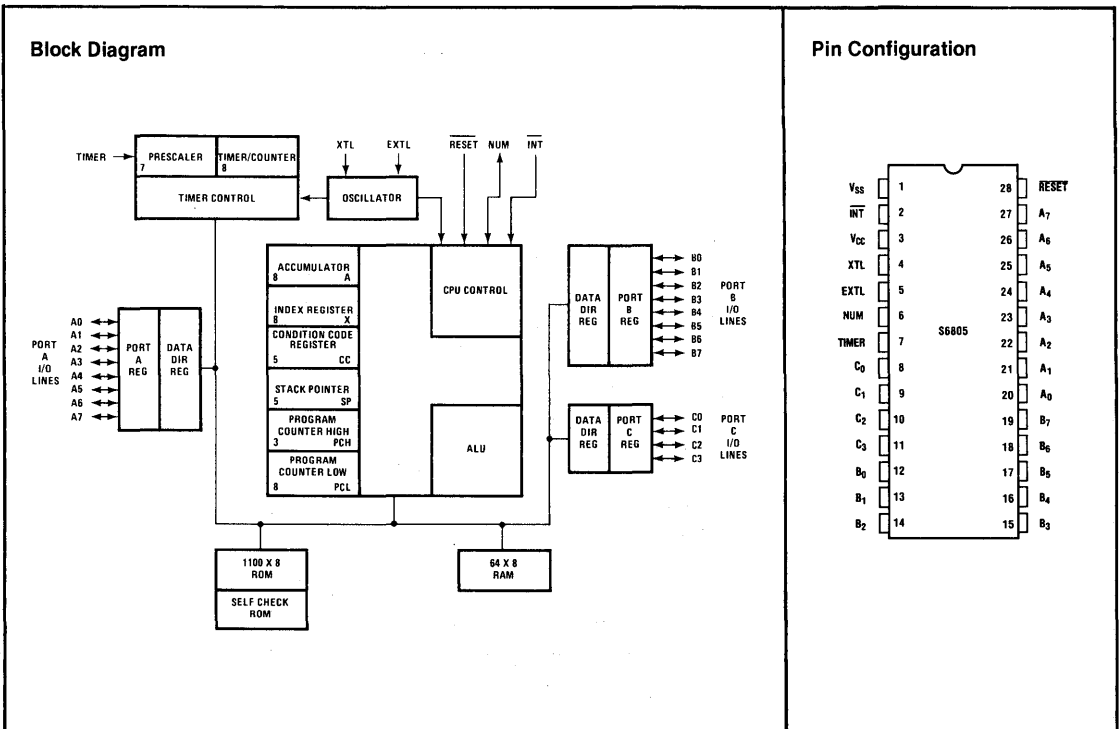
General Description

The S6805 is an 8-bit single chip microcomputer. It is the first member of the growing microcomputer family that contains a CPU, on-chip clock, ROM, RAM, I/O and timer. A basic feature of the 6805 is an instruction set very similar to the S6800 family of microprocessors. Although the 6805 is not strictly source nor object code compatible, an experienced 6800 user can easily write 6805 code. Also a 6805 user will have no trouble moving up to the 6801 or 6809 for more complex tasks.

Absolute Maximum Ratings

Supply Voltage, V_{CC} .... $-0.3V$ to $+7.0V$
Input Voltage, V_{IN} .... $-0.3V$ to $+7.0V$
Operating Temperature Range, T_A .... $0°$ to $+70°C$
Storage Temperature Range, T_{stg} .... $-55°C$ to $+150°C$
Thermal Resistance, θ_{JA}
  Plastic .... $85°C/W$
  Ceramic .... $50°C/W$
  CerDIP .... $51°C/W$

This device contains circuitry to protect the inputs against damage due to high static voltage or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation it is recommended that V_{IN} and V_{OUT} be constrained to the range $V_{SS} \leq (V_{IN}$ or $V_{OUT})$ V_{CC}

Electrical Characteristics: $V_{CC} = +5.25$ Vdc $\pm$ Vdc, $V_{SS} = $ GND, $T_A = 0° - 70°C$ unless otherwise noted

Symbol	Characteristic		Min.	Typ.	Max.	Unit
V_{IH}	Input High Voltage	$\overline{RESET}$	4.0	—	V_{CC}	Vdc
V_{IH}		$\overline{INT}$	—	2.2	—	Vdc
V_{IH}		All Other	$V_{SS} + 2.0$	—	V_{CC}	Vdc
V_{IH}	Input High	Timer Mode	$V_{SS} + 2.0$	—	V_{CC}	Vdc
V_{IH}	Voltage Timer	Self-Check Mode	—	9.0	15.0	Vdc
V_{IL}	Input Low Voltage	$\overline{RESET}$	$V_{SS} - 0.3$	—	0.8	Vdc
V_{IL}		$\overline{INT}$	—	2.0	—	Vdc
V_{IL}		All Other	$V_{SS} - 0.3$	—	$V_{SS} + 0.8$	Vdc
V_H	$\overline{INT}$ Hysteresis		—	100	—	mV_{CC}
P_D	Power Dissipation		—	350	—	mW
C_{IN}	Input Capacitance	EXTL	—	20	—	pF
C_{IN}		All Other	—	10	—	pF
LVR	Low Voltage Recover		—	—	4.75	Vdc
LVI	Low Voltage Inhibit		—	4.5	—	

Switching Characteristics: $V_{CC} = +5.25$ V ± 0.5 Vdc, $V_{SS} = $ GND, $T_A = 0° - 70°C$ unless otherwise noted

Symbol	Characteristic	Min.	Typ.	Max.	Unit
f_{cl}	Clock Frequency	0.4	—	4.0	MHz
t_{CYC}	Cycle Time	1.0	—	10	μs
t_{IWL}	$\overline{INT}$ Pulse Width	$t_{CYC} + 250$	—	—	ns
t_{RWL}	$\overline{RESET}$ Pulse Width	$t_{CYC} + 250$	—	—	ns
t_{RHL}	Delay Time Reset (External Cap. $= 0.47\mu F$)	20	50	—	ms

Port Electrical Characteristics: $V_{CC} = +5.25$ Vdc ± 0.5 Vdc, $V_{SS} = GND$, $T_A = 0° - 70°C$ unless otherwise noted

Symbol	Characteristic	Min.	Typ.	Max.	Unit	Condition
			Port A			
V_{OL}	Output Low Voltage	—	—	0.4	Vdc	$I_{LOAD} = 1.6$mAdc
V_{OH}	Output High Voltage	2.4	—	—	Vdc	$I_{LOAD} = 100\mu$Adc
V_{OH}	Output High Voltage	3.5	—	—	Vdc	$I_{LOAD} = -10\mu$Adc
V_{IH}	Input High Voltage	$V_{SS} + 2.0$	—	V_{CC}	Vdc	$I_{LOAD} = -300\mu$Adc (max)
V_{IL}	Input Low Voltage	$V_{SS} - 0.3$	—	$V_{SS} + 0.8$	Vdc	$I_{LOAD} = -500\mu$Adc (max)
			Port B			
V_{OL}	Output Low Voltage	—	—	0.4	Vdc	$I_{LOAD} = 3.2$mAdc
V_{OL}	Output Low Voltage	—	—	1.0	Vdc	$I_{LOAD} = 10$mAdc(sink)
V_{OH}	Output High Voltage	2.4	—	—	Vdc	$I_{LOAD} = -200\mu$Adc
I_{OH}	Darlington Current Drive (Source)	-1.0	—	-10	mAdc	$V_O = 1.5$Vdc
V_{IH}	Input High Voltage	$V_{SS} + 2.0$	—	V_{CC}	Vdc	
V_{IL}	Input Low Voltage	$V_{SS} - 0.3$	—	$V_{SS} + 0.8$	Vdc	
			Port C			
V_{OL}	Output Low Voltage	—	—	0.4	Vdc	$I_{LOAD} = 1.6$mAdc
V_{OH}	Output High Voltage	2.4	—	—	Vdc	$I_{LOAD} = -100\mu$Adc
V_{IH}	Input High Voltage	$V_{SS} + 2.0$	—	V_{CC}	Vdc	
V_{IL}	Input Low Voltage	$V_{SS} - 0.3$	—	$V_{SS} + 0.8$	Vdc	
			Off-State Input Current			
I_{TSI}	Three-State Ports B & C	—	2	20	μAdc	
			Input Current			
I_{IN}	Timer at $V_{IN} = (0.4$ to 2.4 Vdc)	—	—	20	μAdc	

Figure 1. TTL Equiv. Test Load (Port B)   **Figure 2. CMOS Equiv. Test Load (Port A)**   **Figure 3. TTL Equiv. Test Load (Ports A and C)**
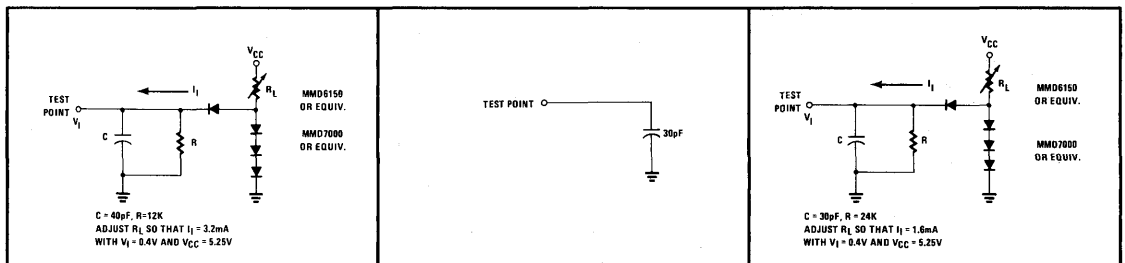
Pin Description

Pin	Symbol	Description
1 and 3	V_{CC} and V_{SS}	Power is supplied to the MCU using these two pins. V_{CC} is $5.25V \pm .5V$, and V_{SS} is the ground connection.
2	$\overline{INT}$	External Interrupt provides capability to apply an external interrupt to the MCU.
4 and 5	XTL and EXTL	Provide control input for the on-chip clock circuit. The use of crystal (at cut 4MHz maximum), a resistor or a wire jumper is sufficient to drive the internal oscillator with varying degrees of stability. (See Internal Oscillator Options for recommendations) An internal divide by 4 prescaler scales the frequency down to the appropriate $\phi 2$ clock rate (1MHz maximum).
6	NUM	This pin is not for user application and should be connected to ground.
7	TIMER	Allows an external input to be used to decrement the internal timer circuitry. See TIMER for detailed information about the timer circuitry.
8-11 12-19 20-27	C0-C3 B0-B7 A0-A7	Input/Output lines (A0-A7, B0-B7, C0-C3). The 20 lines are arranged into two 8-bit ports (A and B) and one 4-bit port (C). All lines are programmed as either inputs or outputs under software control of the data direction registers. See Inputs/Outputs for additional information.
28	$\overline{RESET}$	This pin allows resetting of the MCU. A low voltage detect feature responds to a dip in voltage by forcing a RESET condition to clear all Data Direction Registers, so that all I/O pins are set as inputs.

Memory

The MCU memory is configured as shown in Figure 4. During the processing of an interrupt, the contents of the MCU registers are pushed onto the stack in the order shown in Figure 5. Since the stack pointer decrements during pushes, the low order byte (PCL) of the program counter is stacked first, then the high order three bits (PCH) are stacked first, then the high order three bits (PCH) are stacked. This ensures that the program counter is loaded correctly as the stack pointer increments when it pulls data from the stack. A subroutine call will cause only the program counter (PCH, PCL) contents to be pushed onto the stack.

Figure 4. MCU Memory Configuration
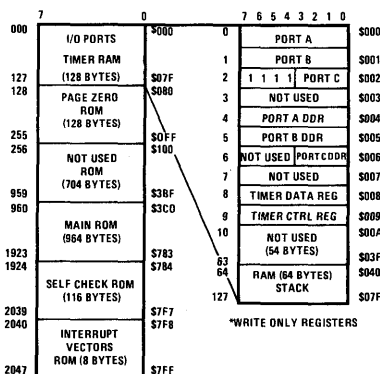
Figure 5. Interrupt Stacking Order

S6800
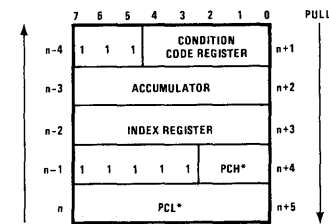
Figure 6. Programming Model
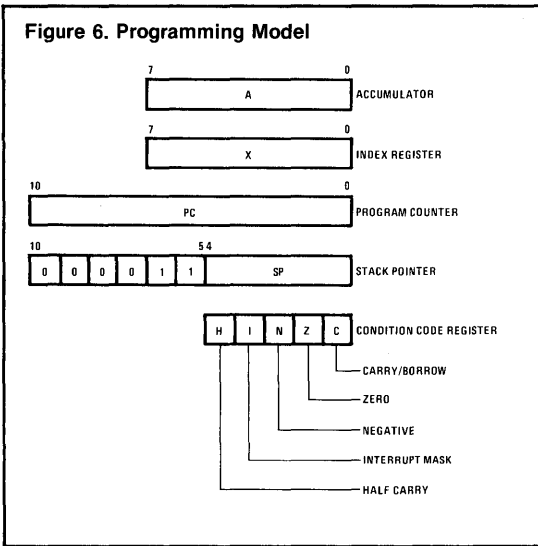
Registers

The S6805 MCU contains two 8-bit registers (A and X), one 11-bit register (PC), two 5-bit registers (SP and CC) that are visible to the programmer (see Figure 6).

Accumulator (A)

The A-register is an 8-bit general purpose accumulator used for arithmetic calculations and data manipulation.

Index Register (X)

This 8-bit register is used for the indexed addressing mode. It provides an 8-bit address that may be added to an offset to create an effective address. The index register can also be used for limited calculations and data manipulations when using the read/modify/write instructions. In code sequences not employing the index register it can be used as a temporary storage area.

Program Counter (PC)

This 11-bit register contains the address of the next instruction to be executed.

Stack Pointer (SP)

The stack pointer is an 11-bit register that contains the address of the next free location on the stack. Initially, the stack pointer is set to location $07F and is decremented as data is being pushed onto the stack and incremented as data is being pulled from the stack. The six most significant bits of the stack pointer are permanently set to 000011. During an MCU reset or the reset stack pointer (RSP) instruction, the stack pointer is set

to location $07F. Subroutines and interrupts may be nested down to location $061 which allows the programmer to use up to 15 levels of subroutine calls. A 16th subroutine call would save the return address correctly, but the stack pointer would not remain pointing into the stack area and there would be no way to return from any of the subroutines.

Condition Code Register (CC)

The condition code register is a 5-bit register in which each bit is used to indicate or flag the results of the instruction just executed. These bits can be individually tested by a program and specific action taken as a result of their state. Each individual condition code register bit is explained in the following paragraphs.

HALF CARRY (H)—Used during arithmetic operations (ADD and ADC) to indicate that a carry occurred between bits 3 and 4.

INTERRUPT (I)—This bit is set to mask the timer and external interrupt ($\overline{INT}$). If an interrupt occurs while this bit is set it is latched and will be processed as soon as the interrupt bit is reset.

NEGATIVE (N)—USED TO INDICATE that the result of the last arithmetic, logical or data manipulation was negative (bit 7 in result equal to a logical one).

ZERO (Z)—Used to indicate that the result of the last arithetic, logical or data manipulation was zero.

CARRY/BORROW (C)—Used to indicate that a carry or borrow out of the arithmetic logic unit (ALU) occurred during the last arithmetic operation. This bit is also affected during bit test and branch instructions, shifts and rotates.

Timer

The MCU timer circuitry is shown in Figure 7. The 8-bit counter is loaded under program control and counts down toward zero as soon as the clock input is applied. When the timer reaches zero the timer interrupt request bit (bit 7) in the timer control register is set. The MCU redsponds to this interrupt by saving the present MCU state in the stack, fetching the timer interrupt vector from locations $7F8 and $7F9 and executing the interrupt routine. The timer interrupt can be masked by setting the timer interrupt mask bit (bit 6) in the timer control register. The interupt bit (bit 1) in the condition code register will also prevent a timer interrupt from being processed.

The clock input to the timer can be from an external source applied to the TIMER input pin or it can be the internal $\phi 2$ signal. Note that when $\phi 2$ signal is used as the source it can be gated by an input applied to the TIMER

input pin allowing the user to easily perform pulse-width measurements. The source of the clock input is one of the options that has to be specified before manufacture of the MCU. A prescaler option can be applied to the clock input that extends the timing interval up to a maximum of 128 counts before being applied to the counter. This prescaling option must also be specified before manufacturing begins. The timer continues to count past zero and its present count can be monitored at any time by monitoring the timer data register. This allows a program to determine the length of time since a timer interrupt has occurred and not disturb the counting process.

At power up or reset the prescaler and counter are initialized with all logical ones; the timer interrupt request bit (bit 7) is cleared and the timer request mask bit (bit 6) is set.

Self Check Mode:

The MCU includes a non-user mode pin that replaces the normal operating mode with one in which the internal data and address buses are available at the I/O ports. The ports are configured as follows in the test mode (some multiplexing of the address and data lines is necessary):

• The internal ROM and RAM are disabled and Port A becomes the input data bus on the $\phi2$ of the clock and can be used to supply instructions of data to the MCU.

• Port B is also multiplexed. When $\phi2$ is high, Port B is the output data bus, and when $\phi2$ is low Port B is the address lines. The output data bus can be used to monitor the internal ROM or RAM.

• Port C becomes the last three address lines and a read/write control line.

The MCU incorporates a self test program within a 116 byte non-user accessible test program and some control logic on-chip. These 116 bytes of ROM test every addressing mode and nearly every CPU instruction (95% of the total microprocessor capability) while only adding 1% to the total overall die size.

To perform the self test, the MCU output lines of Port A and B must be externally interconnected (Figure 7) and LED's are connected to Port C to provide both a pass/fail indication (3Hz square wave).
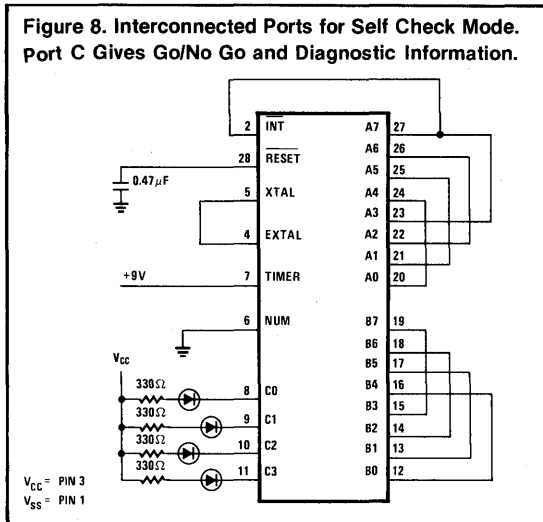
The flowchart for the self test program (Figure 8) runs four tests:

• **I/O TEST**: Tests for I/O lines that are stuck in high, low, shorted state, or are missing a connection. The I/O lines are all externally wired together so that the program can look for problems by testing for the correct operation of the lines as inputs and outputs and for shorts between two adjacent lines.

• **ROM ERROR**: (Checksum wrong). The checksum value of the user program must be masked into the self check ROM when the microcomputer is built. The self check program then tests the user ROM by computing the checksum value, which should be equal to the masked checksum if all the bits in the ROM are properly masked. Address and data lines that are stuck high, low or to each other are also detected by this test. An inoperable ROM will (in most cases) prevent the running of the self check program.

Figure 7. Timer Block Diagram
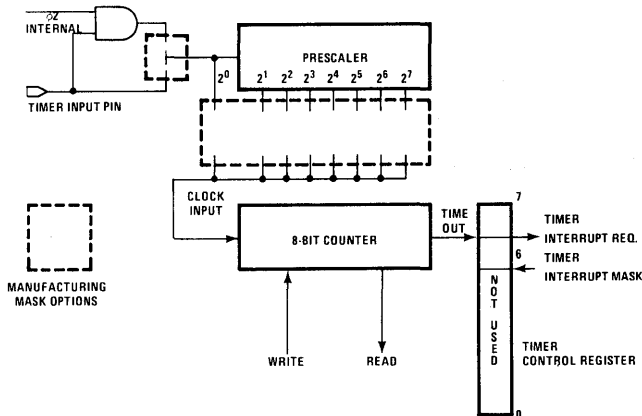
• **RAM Bits Non-Functional**: The RAM is tested by the use of a walking bit pattern that is written into memory and then verified. Every in RAM is set to one and then to zero by using 9 different patterns as shown in Figure 9.

Figure 8. Interconnected Ports for Self Check Mode. Port C Gives Go/No Go and Diagnostic Information.

Self Test Routines

Program performs four main tests in the major loops and provides an output signal to indicate that the part is functional.

Interrupt Logic Failure: Using an I/O line the interrupt pin is toggled to create an interrupt. The main program runs long enough to allow the timer to underflow and causes the timer interrupt to be enabled.

If all of these tests are successful the program, then loops back to the beginning and starts testing again.

The self check program initially tries to get the MCU out of the reset state to indicate that the processor is at least working. The non-functional parts are thus immediately eliminated, and if the part fails at this first stage the program provides a means of determining the faulty section.

To place the MCU in the self check mode the voltage on the timer input (Figure 7) is raised to 8 volts which causes several operations to take place:

• The clocking source for the timer is shunted to the MCU internal clock to insure that the timer will run an underflow during the course of the program, no matter which clocking rate is masked.

• The address of the interrupt vectors (including the reset vector) are mapped into the self check ROM area. This allows the self check to test the interrupt structure.

Figure 9. Flowchart of Self Test Routines

5.56
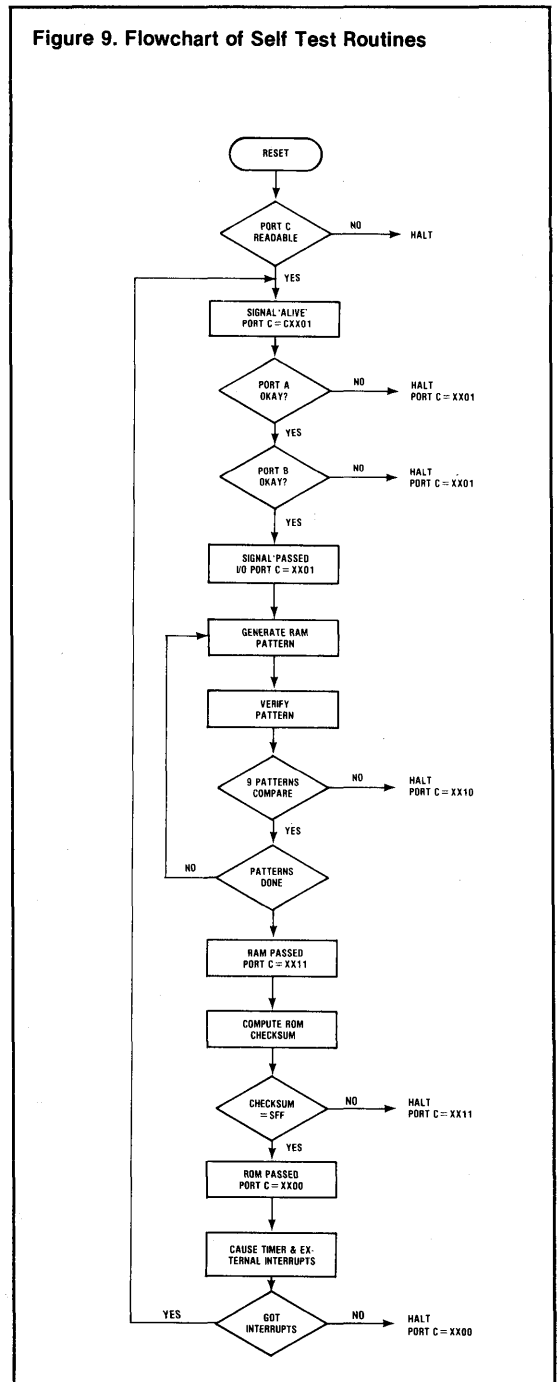
The self check program is started by the reset signal instead of the normal program because the vectors (including the reset vector) have been overlaid. The self check program runs in an endless loop testing and retesting the processor as long as there are no errors. Signals on the I/O lines indicate that the test has passed, and if any test fails, the program stops by executing a branch to self instruction. The output lines then cease to toggle and two of the I/O lines will indicate the cause of failure.

RAM Test Pattern

"Walking bit" patterns test sequence sets and resets every bit in memory. (See Figure 10.)

Low Voltage Inhibit

As soon as the voltage at pin 3 (V_{CC}) falls to 4.5 volts, all I/O lines are put into a high impedance state. This prevents erroneous data from being given to an external device. When V_{CC} climbs back up to 4.6 volts a vectored reset is performed.

Table 1. Cause of Chip Failure as Shown in Bits 0 and 1 of I/O Port C

BIT 1	BIT 0	REASON FOR FAILURE
0	0	INTERRUPTS
0	1	I/O PORTS A OR B
1	0	RAM
1	1	ROM

Figure 10. RAM Test Pattern

PATTERN #1

PATTERN #2

PATTERN #8

PATTERN #9
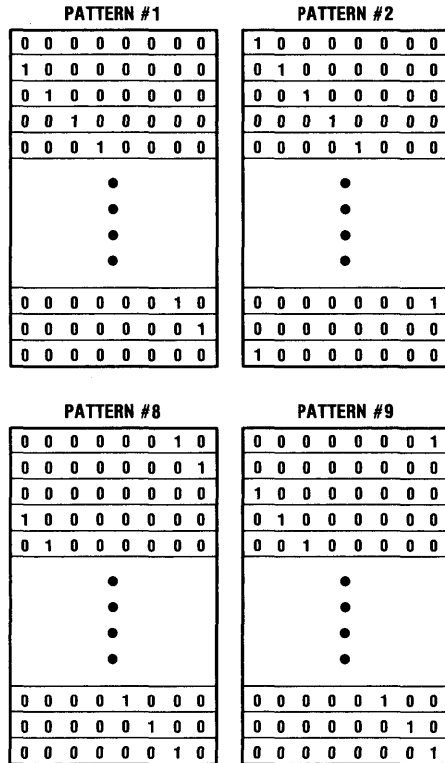
Figure 11. Power Up and Reset Timing
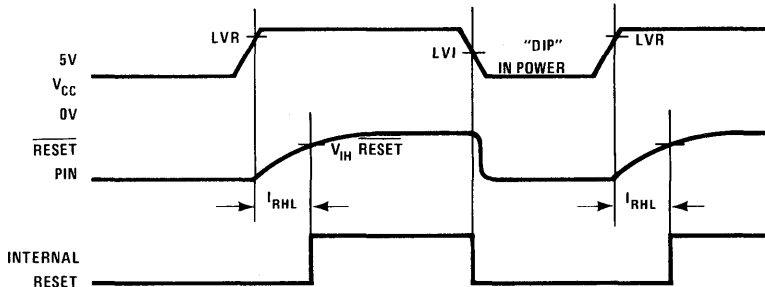
Resets

The MCU can be reset three ways; by the external reset input (RESET), by the internal low voltage detect circuit already mentioned, and during the power up time. (See Figure 11.)

Upon power up, a minimum of 20 milliseconds is needed before allowing the reset input to go high. This time allows the internal oscillator to stabilize. Connecting a capacitor to the RESET input as shown in Figure 12 will provide sufficient delay.

Internal Oscillator Options

The internal oscillator circuit has been designed to require a minimum of external components. The use of a crystal (AT cut, 4MHz max) or a resistor is sufficient to drive the internal oscillator with varying degrees of stability. A manufacturing mask option is available to provide better matching between the external components and the internal oscillator.

The different connection methods are shown in Figure 13. Crystal specifications are given in Figure 14. A resistor selection graph is given in Figure 15.

Figure 12. Power Up Reset Delay Circuit
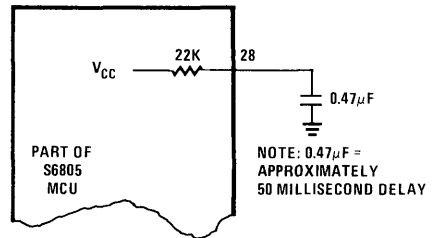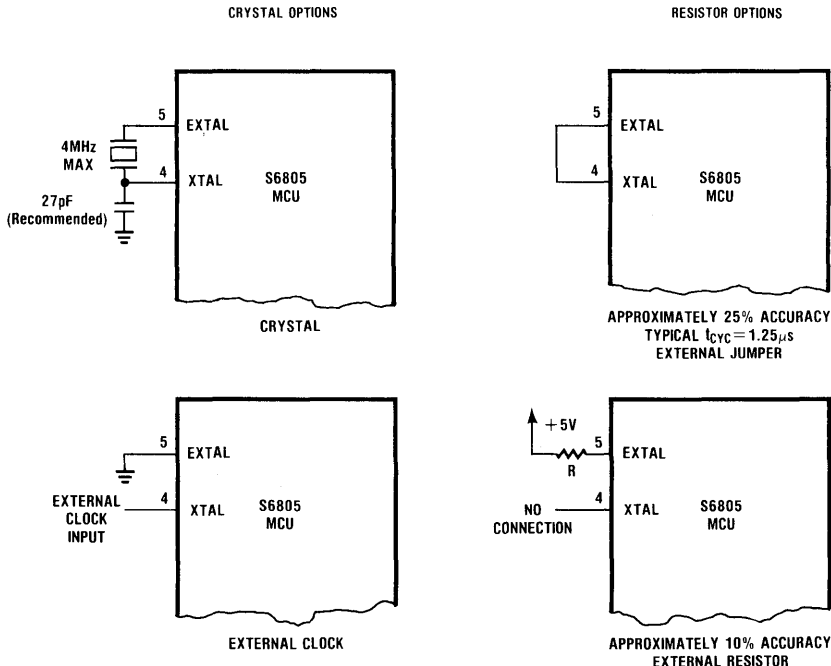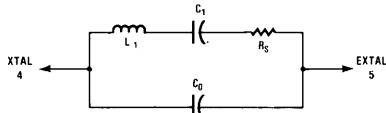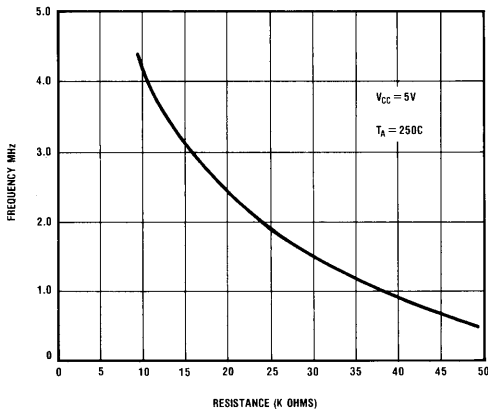

Figure 13. Internal Oscillator Options

Figure 14. Crystal Parameters

AT−CUT PARALLEL RESONANCE CRYSTAL.
$C_0 = 7pF$ MAX
FREQ $= 4.0$MHz@$C_L = 24$pF
$R_S = 50$ OHMS MAX

Figure 15. Typical Resistor Selection Graph

$V_{CC} = 5V$

$T_A = 250C$

Interrupts

The MCU can be interrupted three different ways; through the external interrupt ($\overline{INT}$) input pin, the internal timer interrupt request, and a software interrupt instruction (SWI). When any interrupt occurs, processing is suspended, the present MCU state is pushed onto the stack, the interrupt bit (I) in the condition code register is set, the address of the interrupt routine is obtained from the appropriate interrupt vector address, and the interrupt routine is executed. The interrupt service routines normally end with a return from interrupt (RTI) instruction which allows the MCU to resume processing of the program prior to the interrupt. Table 1 provides a listing of the interrupts, their priority, and the vector address that contain the starting address of the appropriate interrupt routine.

A sinusodial signal (1kHz maximum) can be used to generate an external interrupt ($\overline{INT}$) as shown in Figure 16.

A flowchart of the interrupt processing sequence is given in Figure 17.

Table 1. Interrupt Priorities

Interrupt	Priority	Vector Address
$\overline{RESET}$	1	$7FE AND $7FF
SWI	2	$7FC AND $7FD
$\overline{INT}$	3	$7FA AND $7FB
TIMER	4	$7F8 AND $7F9

Input/Output

There are 20 input/output pins. All pins are programmable as either inputs or outputs under software control of the data direction registers. When programmed as outputs, all I/O pins read latched output data regardless of the logic level at the output pin due to output loading (see Figure 18). When port B is programmed for outputs, it is capable of sinking 10 milliamperes on each pin (one volt maximum). All input/output lines are TTL compatible as both inputs and outputs. Port A lines are CMOS compatible as outputs while Port B and C lines are CMOS compatible as inputs. Figure 19 provides some examples of port connections.
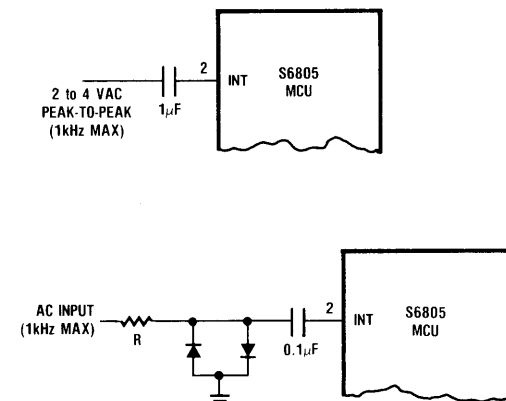
Figure 16. Typical Sinusodial Interrupt Circuits

2 to 4 VAC
PEAK-TO-PEAK $1\mu F$
(1kHz MAX)

$\overline{INT}$ S6805 MCU

AC INPUT
(1kHz MAX)
R
$0.1\mu F$
$\overline{INT}$ S6805 MCU

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Figure 17. Interrupt Processing Flowchart
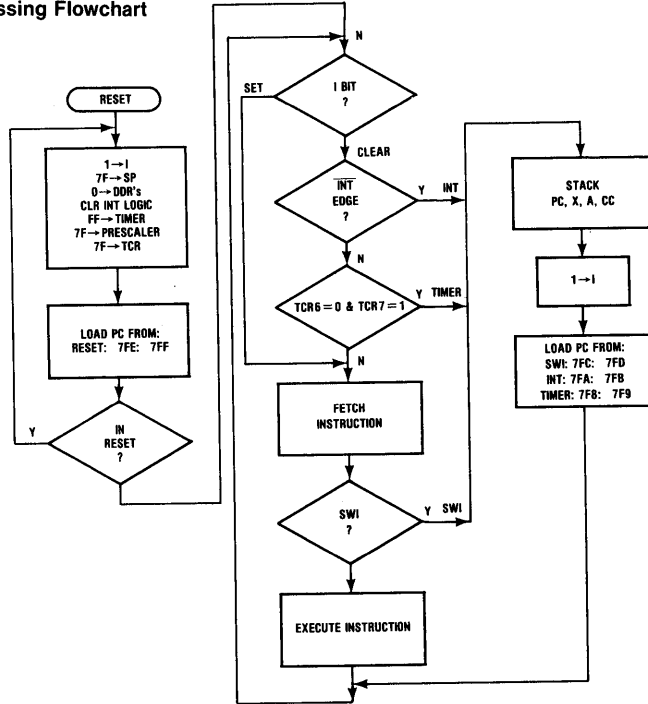
Figure 18. Typical Port I/O Circuitry

DATA DIRECTION REGISTER BIT	OUTPUT DATA BIT	OUTPUT STATE	INPUT TO MCU
1	0	0	0
1	1	1	1
0	X	3-STATE	PIN

Figure 19. Typical Port Connections

PORT A PROGRAMMED AS OUTPUT(S) DRIVING CMOS AND
TTL LOAD DIRECTLY
(a)

PORT B PROGRAMMED AS OUTPUT(S) DRIVING
DARLINGTON BASE DIRECTLY
(b)

PORT B PROGRAMMED AS OUTPUT(S) DRIVING LED(s) DIRECTLY
(c)

PORT C PROGRAMMED AS OUTPUT(S) DRIVING
CMOS USING EXTERNAL PULL-UP RESISTORS
(D)

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Bit Manipulation

The MCU has the ability to set or clear any single random access memory or input/output bit (except the data direction registers) with a single instruction (BSET, BCLR). Any bit in the page zero read only memory can be tested, using the BRSET and BRCLR instructions, and the program branches as a result of its state. This capability to work with any bit in RAM, ROM or I/O allows the user to have individual flags in RAM or to handle single I/O bits as control lines. The example in Figure 20 illustrates the usefulness of the bit manipulation and test instructions. Assume that bit 0 of port A is connected to a zero crossing detector circuit and that bit 1 of port A is connected to the trigger of a TRIAC which powers the controlled hardware.

This program, which uses only seven ROM locations, provides turn-on of the TRIAC within 14 microseconds of the zero crossing. The timer could also be incorporated to provide turn-on at some later time which would permit pulse-width modulation of the controlled power.

Addressing Modes

The MCU has ten addressing modes available for use by the programmer. They are explained and illustrated briefly in the following paragraphs.

Figure 20. Bit Manipulation Example

```
              •
              •
              •
              •
              •
   SELF 1  BRCLR 0, PORTA, SELF 1
           BSET 1, PORTA
           BCLR 1, PORTA
              •
              •
              •
              •
              •
```

Immediate—Refer to Figure 21. The immediate addressing mode accesses constants which do not change during program execution. Such instructions are two bytes long. The effective address (EA) is the PC and the operand is fetched from the byte following the opcode.

Direct—Refer to Figure 22 in direct addressing, the address of the operand is contained in the second byte of the instruction. Direct addressing allows the user to directly address the lowest 256 bytes in memory. All RAM space, I/O registers and 128 bytes of ROM are located in page zero to take advantage of this efficient memory addressing mode.

Extended—Refer to Figure 23. Extended addressing is used to reference any location in memory space. The EA is the contents of the two bytes following the opcode. Extended addressing instructions are three bytes long.

Relative—Refer to Figure 24. The relative addressing mode applies only to the branch instructions. In this mode the contents of the byte following the opcode is added to the program counter when the branch is taken. EA = (PC) + 2 + Rel. Rel is the contents of the location following the instruction opcode with bit 7 being the sign bit. If the branch is not tken Rel = 0, when a branch takes place, the program goes to somewhere within the range of + 129 bytes to − 127 of the present instruction. These instructions are two bytes long.

Indexed (No Offset)—Refer to Figure 25. This mode of addressing accesses the lowest 256 bytes of memory. These instructions are one byte long and their EA is the contents of the index register.

Indexed (8-Bit Offset)—Refer to Figure 26. The EA is calculated by adding the contents of the byte following

the opcode to the contents of the index register. In this mode, 511 low memory locations are accessible. These instructions occupy two bytes.

Indexed (16-Bit Offset)—Refer to Figure 27. This addressing mode calculates the EA by adding the contents of the two bytes following the opcode to the index register. Thus, the entire memory space may be accessed. Instructions which use this addressing mode are three bytes long.

Bit Set/Clear—Refer to Figure 28. This mode of addressing applies to instructions which can set or clear any bit on page zero. The lower three bits in the opcode specify the bit to be set or cleared while the byte following the opcode specifies the address in page zero.

Bit Test and Branch—Refer to Figure 29. This mode of addressing applies to instructions which can test any bit in the first 256 locations ($00-$FF) and branch to any location relative to the PC. The byte to be tested is addressed by the byte following the opcode. The individual bit within that byte to be tested is addressed by the lower three bits of the opcode. The third byte is the relative address to be added to the program counter if the branch condition is met. These instructions are three bytes long. The value of the bit tested is written to the carry bit in the condition code register.

Inherent—Refer to Figure 30. The inherent mode of addressing has no EA. All the information necessary to execute an instruction is contained in the opcode. Direct operations on the accumulator and the index register are included in this mode of addressing. In addition, control instructions such as SWI. RTI belong to this group. All inherent addressing instructions are one byte long.
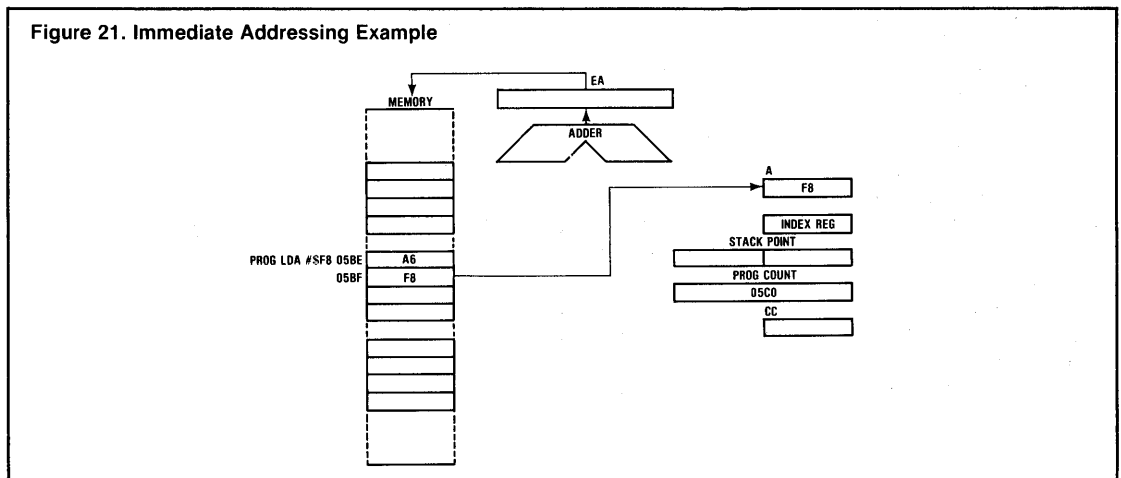
Figure 21. Immediate Addressing Example

Figure 22. Direct Addressing Example
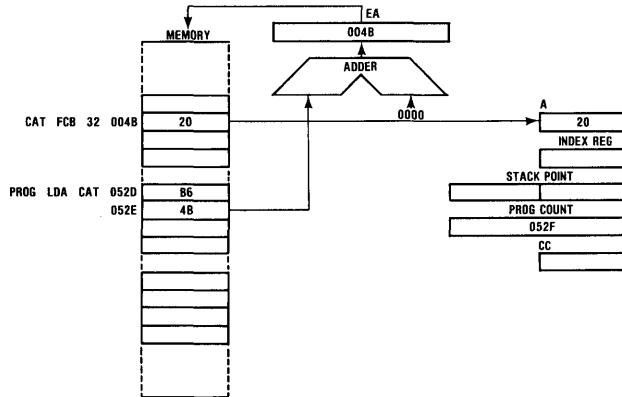

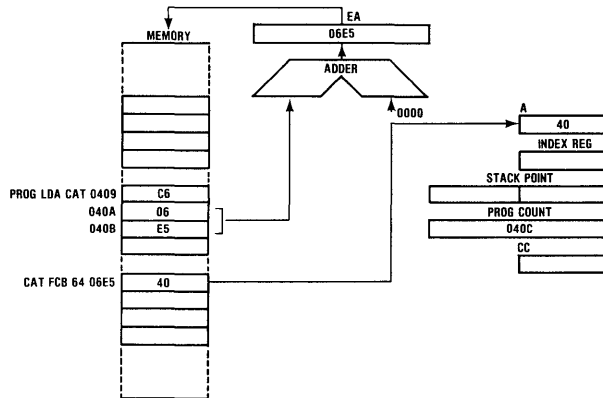**Figure 23. Extended Addressing Example**

Figure 24. Relative Addressing Example
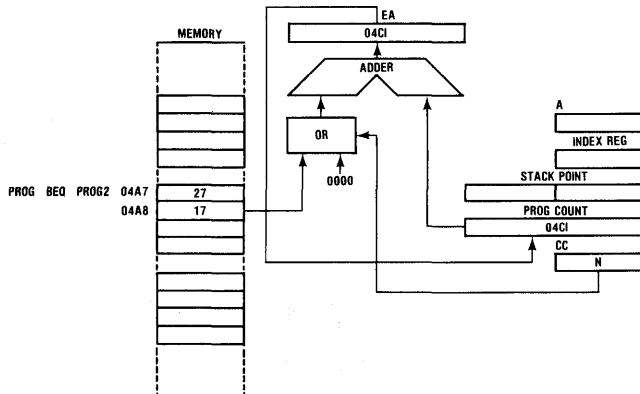
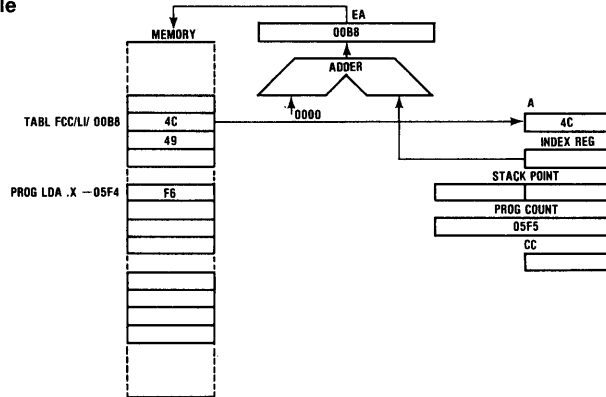Figure 25. Indexed (No Offset)
          Addressing Example

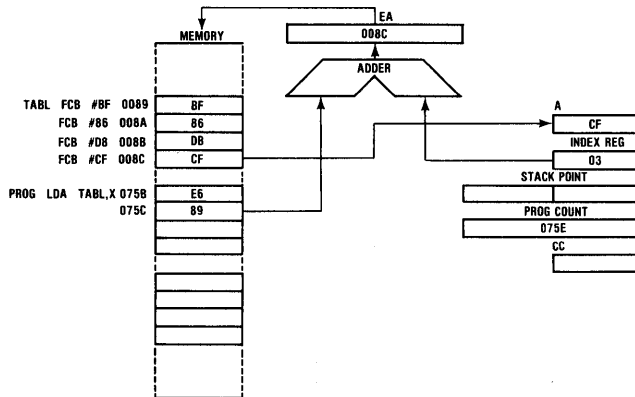Figure 26. Indexed (8-Bit Offset) Addressing Example

Figure 27. Indexed (16-Bit Offset)
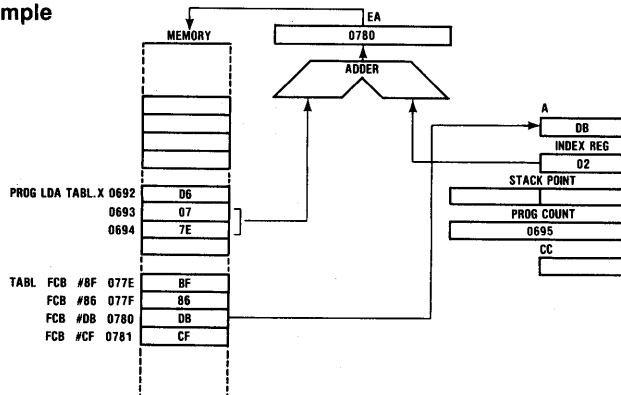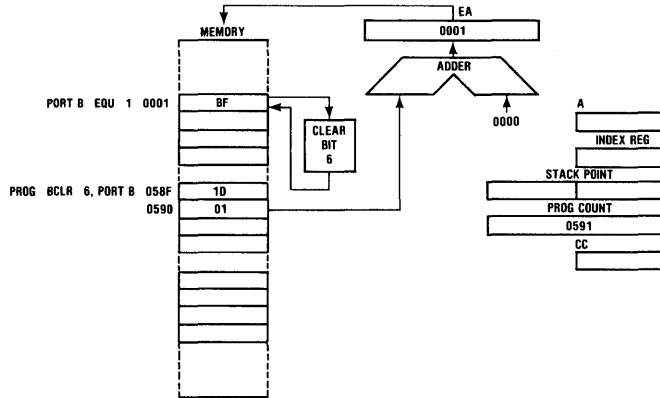   Addressing Example

Figure 28. Bit Set/Clear Addressing Example
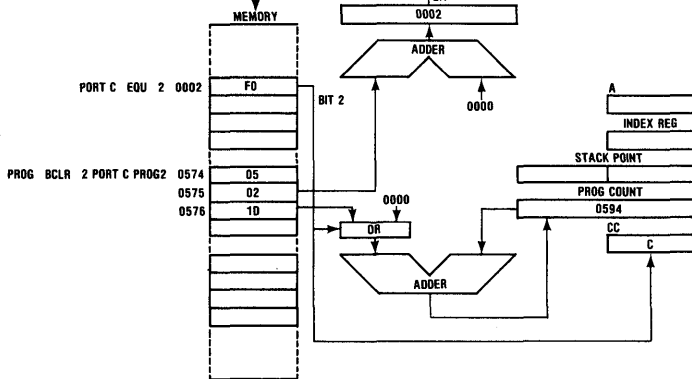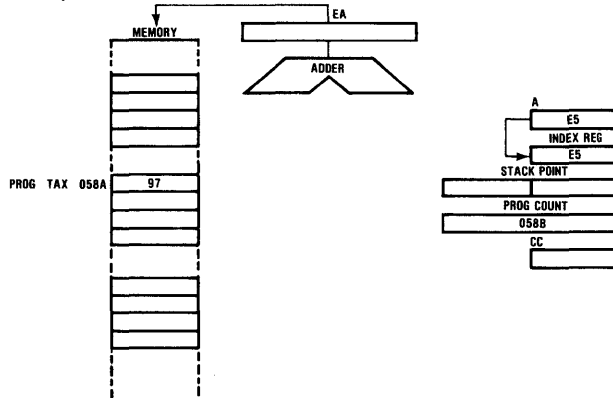

Figure 29. Bit Test and Branch Addressing Example

Figure 30. Inherent Addressing Example

Instruction Set

The MCU has a set of 59 basic instructions. They can be divided into five different types: register/memory, read/modify/write, branch, bit manipulation, and control. The following paragraphs briefly explain each type. All the instructions within a given type are presented in individual tables.

Register/Memory Instructions—Most of these instructions use two operands. One operand is either the accumulator or the index register. The other operand is obtained from memory using one of the addressing modes. The jump unconditional (JMP) and jump to subroutine (JSR) instructions have no register operand. Refer to Table 2.

Read/Modify/Write Instructions—These instructions read a memory location or a register, modify or test its contents, and write the modified value back to memory or to the register. The test for negative or zero (TST) instruc-

tion is an exception to the read/modify/write instructions since it does not perform the write. Refer to Table 3.

Branch Instructions—The branch instructions cause a branch from the program when a certain condition is met. Refer to Table 4.

Bit Manipulation Instructions—These instructions are used on any bit in the first 256 bytes of the memory. One group either sets or clears. The other group performs the bit test and branch operations. Refer to Table 5.

Control Instructions—The control instructions control the MCU operations during program execution. Refer to Table 6.

Alphabetical Listing—The complete instruction set is given in alphabetical order in Table 7.

Opcode Map—Table 8 is an opcode map for the instructions used on the MCU.

Table 2. Register/Memory Instructions

		ADDRESSING MODES																	
		IMMEDIATE			DIRECT			EXTENDED			INDEXED (No Offset)			INDEXED (8-Bit Offset)			INDEXED (16-Bit Offset)		
Function	Mnemonic	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles
LOAD A FROM MEMORY	LDA	A6	2	2	B6	2	4	C6	3	5	F6	1	4	E6	2	5	D6	3	6
LOAD X FROM MEMORY	LDX	AE	2	2	BE	2	4	CE	3	5	FE	1	4	EE	2	5	DE	3	6
STORE A IN MEMORY	STA	—	—	—	B7	2	5	C7	3	6	F7	1	5	E7	2	6	D7	3	7
STORE X IN MEMORY	STX	—	—	—	BF	2	5	CF	3	6	FF	1	5	EF	2	6	DF	3	7
ADD MEMORY TO A	ADD	AE	2	2	BB	2	4	CB	3	5	FB	1	4	EB	2	5	DB	3	6
ADD MEMORY AND CARRY TO A	ADC	A9	2	2	B9	2	4	C9	3	5	F9	1	4	E9	2	5	D9	3	6
SUBTRACT MEMORY	SUB	A0	2	2	B0	2	4	C0	3	5	F0	1	4	E0	2	5	D0	3	6
SUBTRACT MEMORY FROM A WITH BORROW	SBC	A2	2	2	B2	2	4	C2	3	5	F2	1	4	E2	2	5	D2	3	6
AND MEMORY TO A	AND	A4	2	2	B4	2	4	C4	3	5	F4	1	4	E4	2	5	D4	3	6
OR MEMORY WITH A	ORA	AA	2	2	BA	2	4	CA	3	5	FA	1	4	EA	2	5	DA	3	6
EXCLUSIVE OR MEMORY WITH A	EOR	A8	2	2	B8	2	4	C8	3	5	F8	1	4	E8	2	5	D8	3	6
ARITHMETIC COMPARE A WITH MEMORY	CMP	A1	2	2	B1	2	4	C1	3	5	F1	1	4	E1	2	5	D1	3	6
ARITHMETIC COMPARE X WITH MEMORY	CPX	A3	2	2	B3	2	4	C3	3	5	F3	1	4	E3	2	5	D3	3	6
BIT TEST MEMORY WITH A (Logical Compare)	BIT	A5	2	2	B5	2	4	C5	3	5	F5	1	4	E5	2	5	D5	3	6
JUMP UNCONDITIONAL	JMP	—	—	—	BC	2	3	CC	3	4	FC	1	3	EC	2	4	DC	3	5
JUMP TO SUBROUTINE	JSR	—	—	—	BD	2	7	CD	3	8	FD	1	7	ED	2	8	DD	3	9

Table 3. Read/Modify/Write Instructions

| | | ADDRESSING MODES | | | | | | | | | | | | | | |
| | | INHERENT (A) | | | INHERENT (X) | | | DIRECT | | | INDEXED (No Offset) | | | INDEXED (8-Bit Offset) | | |
Function	Mnemonic	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles	OP Code	# Bytes	OP Code	# Bytes	# Cycles		
INCREMENT	INC	4C	1	4	5C	1	4	3C	2	6	7C	1	6	6C	2	7	
DECREMENT	DEC	4A	1	4	5A	1	4	3A	2	6	7A	1	6	6A	2	7	
CLEAR	CLR	4F	1	4	5F	1	4	3F	2	6	7F	1	6	6F	2	7	
COMPLEMENT	COM	43	1	4	53	1	4	33	2	6	73	1	6	63	2	7	
NEGATE (2's COMPLEMENT)	NEG	40	1	4	50	1	4	30	2	6	70	1	6	60	2	7	
ROTATE LEFT THRU CARRY	ROL	49	1	4	59	1	4	39	2	6	79	1	6	69	2	7	
ROTATE RIGHT THRU CARRY	ROR	46	1	4	56	1	4	36	2	6	76	1	6	66	2	7	
LOGICAL SHIFT LEFT	LSL	48	1	4	58	1	4	38	2	6	78	1	6	68	2	7	
LOGICAL SHIFT RIGHT	LSR	44	1	4	54	1	4	34	2	6	74	1	6	64	2	7	
ARITHMETIC SHIFT RIGHT	ASR	47	1	4	57	1	4	37	2	6	77	1	6	67	2	7	
TEST FOR NEGATIVE OR ZERO	TST	4D	1	4	5D	1	4	3D	2	6	7D	1	6	6D	2	7	

Table 4. Branch Instructions

| | | RELATIVE ADDRESSING MODE | | |
Function	Mnemonic	OP Code	# Bytes	# Cycles
BRANCH ALWAYS	BRA	20	2	4
BRANCH NEVER	BRN	21	2	4
BRANCH IFF HIGHER	BHI	22	2	4
BRANCH IFF LOWER OR SAME	BLS	23	2	4
BRANCH IFF CARRY CLEAR	BCC	24	2	4
(BRANCH IFF HIGHER OR SAME)	(BHS)	24	2	4
BRANCH IFF CARRY SET	BCS	25	2	4
(BRANCH IFF LOWER)	(BLO)	25	2	4
BRANCH IFF NOT EQUAL	BNE	26	2	4
BRANCH IFF EQUAL	BEQ	27	2	4
BRANCH IFF HALF CARRY CLEAR	BHCC	28	2	4
BRANCH IFF HALF CARRY SET	BHCS	29	2	4
BRANCH IFF PLUS	BPL	2A	2	4
BRANCH IFF MINUS	BMI	2B	2	4
BRANCH IFF INTERRUPT MASK BIT IS CLEAR	BMC	2C	2	4
BRANCH IFF INTERRUPT MASK BIT IS SET	BMS	2D	2	4
BRANCH IFF INTERRUPT LINE IS LOW	BIL	2E	2	4
BRANCH IFF INTERRUPT LINE IS HIGH	BIH	2F	2	4
BRANCH TO SUBROUTINE	BSR	AD	2	8

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Table 5. Bit Manipulation Instructions

		ADDRESSING MODES					
Function	Mnemonic	OP Code	# Bytes	# Cycles	OP Code	# Bytes	# Cycles
BRANCH IFF BIT n IS SET	BRSET n(n = 0 . . . . 7)	—	—	—	2•n	3	10
BRANCH IFF BIT n IS CLEAR	BRCLR n(n = 0 . . . . 7)	—	—	—	01 + 2•n	3	10
SET BIT n	BSET n(n = 0 . . . . 7)	10 + 2•n	2	7	—	—	—
CLEAR BIT n	BCLR n(n = 0 . . . . 7)	11 + 2•n	2	7	—	—	—

Table 6. Control Instructions

		INHERENT		
Function	Mnemonic	OP Code	# Bytes	# Cycles
TRANSFER A TO X	TAX	97	1	2
TRANSFER X TO A	TXA	9F	1	2
SET CARRY BIT	SEC	99	1	2
CLEAR CARRY BIT	CLC	98	1	2
SET INTERRUPT MASK BIT	SBI	9B	1	2
CLEAR INTERRUPT MASK BIT	CLI	9A	1	2
SOFTWARE INTERRUPT	SWI	83	1	11
RETURN FROM SUBROUTINE	RIS	81	1	6
RETURN FROM INTERRUPT	RTI	80	1	9
RESET STACK POINTER	RSP	9C	1	2
NO OPERATION	NOP	9D	1	2

Table 7. Instruction Set

	Addressing Modes								Bit Set/ Clear	Bit Test & Branch	Condition Code				
Mnemonic	Inherent	Immediate	Direct	Extended	Relative	Indexed (No Offset)	Indexed (8 Bits)	Indexed (16 Bits)			H	I	N	Z	C
ADC		X	X	X		X	X	X			∧	●	∧	∧	∧
ADD		X	X	X		X	X	X			∧	●	∧	∧	∧
AND		X	X	X		X	X	X			●	●	∧	∧	●
ASL	X		X			X	X				●	●	∧	∧	∧
ASR	X		X			X	X				●	●	∧	∧	∧
BCC					X						●	●	●	●	●
BCLR									X		●	●	●	●	●
BCS					X						●	●	●	●	●
BEQ					X						●	●	●	●	●
BHCC					X						●	●	●	●	●
BHCS					X						●	●	●	●	●
BHI					X						●	●	●	●	●
BHS					X						●	●	●	●	●
BIH					X						●	●	●	●	●
BIL					X						●	●	●	●	●
BIT		X	X	X		X	X	X			●	●	∧	∧	●
BLO					X						●	●	●	●	●
BLS					X						●	●	●	●	●
BMC					X						●	●	●	●	●

CONDITION CODE SYMBOLS:
H HALF CARRY (FROM BIT 3)   Z ZERO   ∧ TEST AND SET IF TRUE.
I   INTERRUPT MASK   C CARRY BORROW   CLEARED OTHERWISE
N NEGATIVE (SIGN BIT)   ● NOT AFFECTED

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Table 7. Instruction Set (Continued)

Mnemonic	Inherent	Immediate	Direct	Extended	Relative	Indexed (No Offset)	Indexed (8 Bits)	Indexed (16 Bits)	Bit Set/Clear	Bit Test & Branch	H	I	N	Z	C
BMI											•	•	•	•	•
BMS											•	•	•	•	•
BNE											•	•	•	•	•
BPL											•	•	•	•	•
BRA											•	•	•	•	•
BRN											•	•	•	•	•
BRCLR										X	•	•	•	•	∧
BRSET										X	•	•	•	•	∧
BSET									X		•	•	•	•	•
BSR					X						•	•	•	•	•
CLC	X										•	•	•	•	•
CLI	X										•	•	•	•	•
CLR	X		X			X	X				•	•	•	I	•
CMP		X	X	X		X	X	X			•	•	∧	∧	∧
COM	X		X			X	X				•	•	∧	∧	I
CPX		X	X	X		X	X	X			•	•	∧	∧	∧
DEC	X		X			X	X				•	•	∧	∧	•
EOR		X	X	X		X	X	X			•	∧	∧	•	•
INC	X		X			X	X				•	•	∧	∧	•
JMP			X	X		X	X	X			•	•	•	•	•
JSR			X	X		X	X	X			•	•	•	•	•
LDA		X	X	X		X	X	X			•	•	∧	∧	•
LDX		X	X	X		X	X	X			•	•	∧	∧	•
LSL	X		X			X	X				•	•	∧	∧	∧
LSR	X		X			X	X				•	•	•	∧	∧
NEQ	X		X			X	X				•	•	∧	∧	∧
NOP	X										•	•	•	•	•
ORA		X	X	X		X	X	X			•	•	∧	∧	•
ROL	X		X			X	X				•	•	∧	∧	∧
RSP	X										•	•	•	•	•
RTI	X										?	?	?	?	?
RTS	X										•	•	•	•	•
SBC		X	X	X		X	X	X			•	•	∧	∧	∧
SEC	X										•	•	•	•	I
SEI	X										•	I	•	•	•
STA			X	X		X	X	X			•	•	∧	∧	•
STX			X	X		X	X	X			•	•	∧	∧	•
SUB		X	X	X		X	X	X			•	•	∧	∧	∧
SWI	X										•	I	•	•	•
TAX	X										•	•	•	•	•
TST	X		X			X	X				•	•	∧	∧	•
TXA	X										•	•	•	•	•

CONDITION CODE SYMBOLS:
H   HALF CARRY (FROM BIT 3)
I   INTERRUPT MASK
N   NEGATIVE (SIGN BIT)

Z   ZERO
C   CARRY BORROW
?   LOAD CC REGISTER FROM STACK

∧   TEST AND SET IF TRUE.
     CLEARED OTHERWISE
●   NOT AFFECTED

Table 8. Opcode Map

	Bit Manipulation		Bmch	Read/Modify/Write					Control		Register/Memory							
	Test & Branch	Set/Clear	Rel	DIR	A	X	.X1	.X0	INH	INH	IMM	DIR	EX	.X2	.X1	.X0	←	HIGH
	0	1	2	3	4	5	6	7	8	8	A	B	C	D	E	F		
0	BRSET0	BSET0	BRA	NEQ					RTI*	—	SUB						0	
1	BRCLR0	BCLR0	BRN	—					RIS*	—	CMP						1	
2	BRSET1	BSET1	BHI	—					—	—	SBC						2	
3	BRCLR1	BCLR1	BLS	COM					SWI*	—	CMPX/CPX						3	L
4	BRSET2	BSET2	BCC	LSR					—	—	AND						4	O
5	BRCLR2	BCLR2	BCS	—					—	—	BIT						5	W
6	BRSET3	BSET3	BNE	ROR					—	—	LDA						6	
7	BRCLR3	BCLR3	BEQ	ASR					—	TAX	—	STA(+1)					7	
8	BRSET4	BSET4	BHCC	LSL/ASL					—	CLC	EOR						8	
9	BRCLR4	BCLR4	BHCS	ROL					—	SEC	ADC						9	
A	BRSET5	BSET5	BPL	DEC					—	CLI	ORA						A	
B	BRCLR5	BCLR5	BMI	—					—	SEI	ADD						B	
C	BRSET6	BSET6	BMC	INC					—	RSP	—	JMP(−1)					C	
D	BRCLR6	BCLR6	BMS	TST					—	NOP	BSR*	JSR(+3)					D	
E	BRSET7	BSET7	BIL	—					—	—	LDX						E	
F	BRCLR7	BCLR7	BIH	CLR					—	TXA	—	STX(+1)					F	
	3/10	2/7	2/4	2/6	1/4	1/4	2/7	1/6	1/*	1/2	2/2	2/4	3/5	3/6	2/5	1/40		

NOTES:

UNDEFINED OPCODES ARE MARKED WITH "—"

THE NUMBERS AT THE BOTTOM OF EACH COLUMN DENOTE THE NUMBER OF BYTES AND THE NUMBER OF CYCLES REQUIRED (BYTES/CYCLES)

NMEMONICS FOLLOWED BY A "*" REQUIRE A DIFFERENT NUMBER OF CYCLES AS FOLLOWS

RTI 9
RTS 6
SWI 11
BSR 8

( ) INDICATE THAT THE NUMBER IN PARENTHESIS MUST BE ADDED TO THE CYCLE COUNT FOR THAT INSTRUCTION.

Table 9. S6805 Family of Microprocessors

	S6805	S6805C	S6805N	S6805C1
TECHNOLOGY	NMOS	CMOS	NMOS	CMOS
NUMBER OF PINS	28	40	40	40
ON-CHIP RAM (BYTES)	64	112	64	112
ON CHIP USER ROM (BYTES)	1.1K	NONE	2K	2.2K
EXPANSION BUS	NONE	YES	NONE	NONE
BIDIRECTIONAL I/O LINES	20	16	32	32
I/O OPTIONS	NONE	NONE	A/D CONVERTER	NONE
SOFTWARE COMPATIBILITY	YES	YES	YES	YES
TRUE BIT MANIPULATION	YES	YES	YES	YES
INSTRUCTIONS	59	61	59	61
TEN ADDRESSING MODES	YES	YES	YES	YES

S6800

Ordering Information

Option List — *Select the options for your MCU from the following list. A manufacturing mask will be generated from this information.*

Timer Clock Source

☐ Internal $\phi2$ clock   ☐ TIMER input, pin 7

Timer Prescaler

☐ 2^0 (divide by 1)   ☐ 2^3 (divide by 8)   ☐ 2^6 (divide by 64)

☐ 2^1 (divide by 2)   ☐ 2^4 (divide by 16)   ☐ 2^7 (divide by 128)

☐ 2^2 (divide by 4)   ☐ 2^5 (divide by 32)

Internal Oscillator Input

☐ Crystal   ☐ Resistor

Low Voltage Inhibit

☐ Enable   ☐ Disable

ROM Specifications

How are the records specified?

☐ AMI Hex   ☐ Intellec Hex   ☐ BPNF   ☐ Anything else (include precise description of format)

What form will the data be transmitted in?

I.   9-track NRZ unlabeled magnetic tape?   ☐

If you choose mag tape, please answer the following questions:

A.   Which is it coded in?   ☐ EBCDIC   ☐ ASCII

B.   What is the parity?   ☐ ODD   ☐ EVEN

C.   What is the recording density?   ☐ 556 BPI   ☐ 800 BPI   ☐ 1600 BPI

D.   Is is unblocked? (One record per block)   ☐ YES   ☐ NO

If blocked, how many records per block? _____

 II.   FDOS floppy disk file?   ☐

III.   Paper tape?   ☐

IV.   Card deck   ☐

 V.   EPROM?   ☐

No matter what physical means is chosen, try to include two machine readable forms along with a listing. If only one form of the data is available, a listing is imperative.

Two blank EPROM's should be included with the ordering information. These EPROM's will be programmed from the mask tapes and returned for approval before the first silicon trial run.

AMI

AMERICAN MICROSYSTEMS, INC.

MICROPROCESSOR WITH CLOCK

Features

- ☐ On-Chip Clock
- ☐ Software-Compatible with the S6800
- ☐ Expandable to 65K Words
- ☐ Standard TTL-Compatible Inputs and Outputs
- ☐ 8-Bit Word Size
- ☐ 16-Bit Memory Addressing
- ☐ Interrupt Capability

General Description

The S6808 is a monolithic 8-bit microprocessor that contains all the registers and accumulators of the present S6800 plus an internal clock oscillator and driver on the same chip.

This very cost-effective MPU allows the designer to use the S6808 in consumer as well as industrial applications without sacrificing industrial specifications.

S6800

Typical Microprocessor Interface

Pin Configuration

AMI
AMERICAN MICROSYSTEMS, INC.
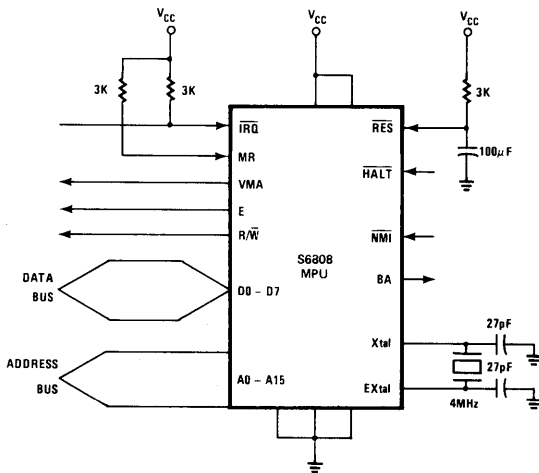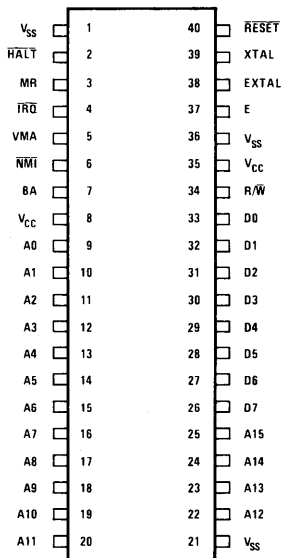
8-BIT
MICROPROCESSING UNIT

Features

☐ **Interfaces with All S6800 Peripherals**

☐ **Upward Compatible Instruction Set and Addressing Modes**

☐ **Upward Source Compatible Instruction Set and Addressing Modes**

☐ **Two 8-Bit Accumulators Can Be Concatenated Into One 16-Bit Accumulator**

☐ **On-Chip Crystal Oscillator (4 Time XTAL)**

General Description

The S6809 is an advanced processor within the S6800 family offering greater throughput, improved byte efficiency, and increased adaptability to various software disciplines. These include position independence, reentrancy, recursion, block structuring, and high level language generation.

Because the S6809 generates *position-independent* code, software can be written in modular form for easy user expansion as system requirements increase. The S6809 is hardware compatible with all S6800 peripherals, and any assembly language code prepared for the S6800 can be passed through the S6809 assembler to produce code which will run on the S6809.

Block Diagram
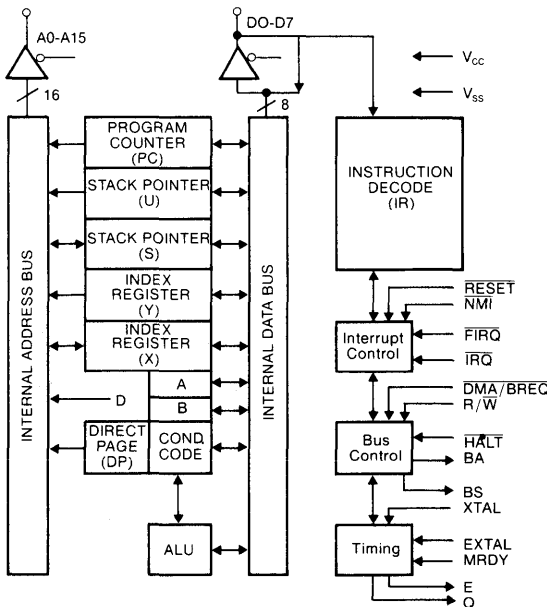
Pin Configuration
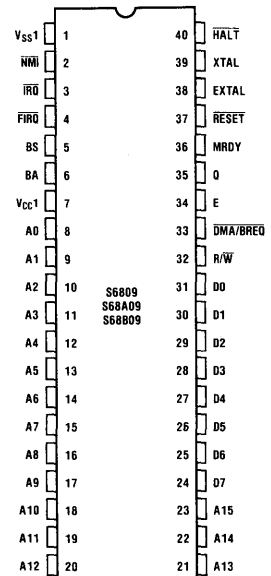
S6809 Hardware Features

- ☐ **On-Chip Oscillator**
- ☐ **MRDY Input Extends Access Time**
- ☐ **DMA/BREQ for DMA and Memory Refresh**
- ☐ **Fast Interrupt Request Input: Stacks Only Program Counter and Condition Code**
- ☐ **Interrupt Acknowledge Output Allows Vectoring by Devices**
- ☐ **Three Vectored Priority Interrupt Levels**
- ☐ **SYNC Acknowledge Output Allows for Synchronization to External Event**
- ☐ **NMI Blocked after RESET until after First Load of Stack Pointer**
- ☐ **Early Address Valid Allows Use with Slow Memories**

S6809E Hardware Features

- ☐ **Last Instruction Cycle Output (LIC) for Identification Output Fetch**
- ☐ **Busy Output Eases Multiprocessor Design**

Instruction Set

- ☐ **Extended Range Branches**
- ☐ **Load Effective Address**
- ☐ **16-Bit Arithmetic**
- ☐ **8x8 Unsigned Multiply (Accumulator A*B)**
- ☐ **SYNC Instruction — Provides Software Sync with an External Hardware Process**
- ☐ **Push and Pull on 2 Stacks**
- ☐ **Push/Pull Any or All Registers**
- ☐ **Index Registers May Be Used as Stack Pointer**
- ☐ **Transfer/Exchange All Registers**

Addressing Modes

- ☐ **All 6800 Modes Plus PC Relative, Extended Indirect, Indexed Indirect, and PC Relative Indirect**
- ☐ **Direct Addressing Available Anywhere in Memory Map**
- ☐ **PC Relative Addressing: Byte Relative (± 32, 768 Bytes from PC)**
- ☐ **Complete Indexed Addressing Including Automatic Increment and Decrement, Register Offsets, and Four Indexable Registers (X, Y, U and S)**
- ☐ **Expanded Index Addressing**
  — 0, 5, 8, 16-Bit Constant Offset
  — 8, 16-Bit Accumulator Offsets

The S6809 gives the user 8 and 16-bit word capability with several hardware enhancements in the design such as the Fast Interrupt ($\overline{FIRQ}$), Memory Ready (MRDY), and Quadrature (Qout) and System Clock Outputs (Eout). With the Fast Interrupt Request ($\overline{FIRQ}$) the S6809 places *only* the Program Counter and Condition Code Register on the stack prior to accessing the $\overline{FIRQ}$ vector location. The Memory Ready ($\overline{MRDY}$) input allows extension of the data access time for use with slow memories. The System Clock (Eout) operates at the basic processor frequency and can be as the synchronization signal for the entire system. The Quadrature Output (Qout) provides additional system timing by signifying that address and data are stable.

The External Clock mode of the S6809E is particularly useful when synchronizing the processor to an externally generated signal. The Three-State Control input ($\overline{TSC}$) places the Address and R/$\overline{W}$ line in the high impedance state for DMA or Memory Refresh. The last Instruction Cycle (LIC) is activated during the last cycle of any instruction. This signifies that the next instruction cycle is the opcode fetch. The Processor Busy signal (BUSY) facilitates multiprocessor applications by allowing the designer to insure that flags being modified by one processor are not accessed by another simultaneously.

The S6809 features a family of addressing capabilities which can use any of the four index registers and stack pointers as a pointer to the operand (or the operand address). This pointer can have a fixed or variable signed offset that can be automatically incremented or decremented. The eight-bit direct page register permits a user to determine which page of memory is accessed by the instructions employing "page zero" addressing. This quick access to any page is especially useful in Multi-tasking Applications.

The S6809 has three vectored priority-interrupt levels, each of which automatically disables the lower priority interrupt while leaving the higher priority interrupt enabled.

The S6809 gives the system designer greater flexibility (through modular relocatable code) to enable the user to reduce system software costs while at the same time increasing software reliability and efficiency.

Absolute Maximum Ratings

Supply Voltage, V_{CC}	$- 0.3V$ to $+ 7.0V$
Input Voltage, V_{IN}	$- 0.3V$ to $+ 7.0V$
Operating Temperature Range, T_A	$0°C$ to $+ 70°C$
Storage Temperature Range, T_{stg}	$- 55°C$ to $+ 150°C$
Thermal Resistance, θ_{JA}	
Plastic	$100°C/W$
Ceramic	$50°C/W$

This device contains circuitry to protect the inputs against damage due to high static voltage or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

S6800

AMI

Electrical Characteristics ($V_{CC} = 5.0V \pm 5\%$; $V_{SS} = 0$, $T_A = 0°C$ to $+70°C$ unless otherwise noted)

Symbol	Parameter		Min.	Typ.	Max.	Unit	Condition
V_{IH}	Input High Voltage	Logic, EXtal	$V_{SS} + 2.0$		V_{DD}	Vdc	
		$\overline{RESET}$	$V_{SS} + 4.0$		V_{DD}		
V_{IL}	Input Low Voltage	Logic EXtal, $\overline{RESET}$	$V_{SS} - 0.3$		$V_{SS} + 0.8$	Vdc	
I_{in}	Input Leakage Current	Logic		1.0	2.5	μAdc	$V_{in} = 0$ to 5.25V, $V_{CC} = $ max
V_{OH}	Output High Voltage	D0-D7	$V_{SS} + 2.4$			Vdc	$I_{Load} = -205\mu$Adc, $V_{CC} = $ min
	A0-A15, R/$\overline{W}$, Q, E		$V_{SS} + 2.4$				$I_{Load} = -145\mu$Adc, $V_{CC} = $ min
		BA, BS	$V_{SS} + 2.4$				$I_{Load} = -100\mu$Adc, $V_{CC} = $ min
V_{OL}	Output Low Voltage				$V_{SS} + 0.5$	Vdc	$I_{Load} = 2.0$mAdc, $V_{CC} = $ min
P_D	Power Dissipation				1.0	W	
C_{in}	Capacitance #	D_0-D_7		10	15	pF	$V_{in} = 0$, $T_A = 25°C$, f = 1.0MHz
	Logic Inputs, EXtal			7	10		
C_{out}	A_0-A_{15}, R/$\overline{W}$				12		
f	Frequency of Operation	S6809			4	MHz	
f_{XTAL}		S68A09			6		
f_{XTAL}	(Crystal or External Input)	S68B09			8		
I_{TSI}	Three-State (Off State) Input Current	D_0-D_7		2.0	10	μAdc	$V_{in} = 0.4$ to 2.4V, $V_{CC} = $ max
	A_0-A_{15}, R/W				100		

Read/Write Timing (Reference Figures 1 and 2)

Symbol	Parameter	S6809			S68A09			S68B09			Unit	Condition
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.		
t_{CYC}	Cycle Time	1000			667			500			ns	
t_{UT}	Total Up Time	975			640			480			ns	$t_{acc} = t_{ut} - t_{AD} - t_{DSR}$
t_{ACC}	Peripheral Read Access Time	695			440			320			ns	$t_{ut} = t_{CYC} - t_{EF}$
t_{DSR}	Data Setup Time (Read)	80			60			40			ns	
t_{DHR}	Input Data Hold Time	10			10			10			ns	
t_{DHW}	Output Data Hold Time	30			30			30			ns	
t_{AH}	Address Hold Time (Address, R/$\overline{W}$)	30			30			30			ns	
t_{AD}	Address Delay			200			140			110	ns	
t_{DDW}	Data Delay Time (Write)			225			180			145	ns	
t_{AVS}	E_{low} to Q_{high} Time			250			165			125	ns	
t_{AQ}	Address Valid to Q_{high}	25			25			15			ns	
t_{PWEL}	Processor Clock Low	450			295			210			ns	
t_{PWEH}	Processor Clock High	450			280			220			ns	
t_{PCSR}	MRDY Set Up Time	60			60			60			ns	
t_{PCS}	Interrupts Set Up Time	200			140			110			ns	
t_{PCSH}	$\overline{HALT}$ Set Up Time	200			140			110			ns	
t_{PCSR}	$\overline{RESET}$ Set Up Time	200			140			110			ns	
t_{PCSD}	$\overline{DMA/BREQ}$ Set Up Time	125			125			125			ns	
t_{rc}	Crystal Osc Start Time	100			100			100			ms	
t_{ER}, t_{EF}	E Rise and Fall Time	5		25	5		25	5		20	ns	
t_{PCR}, t_{PLF}	Processor Control Rise/Fall			100			100			100	ns	
t_{QR}, t_{QF}	Q Rise and Fall Time	5		25	5		25	5		20	ns	
t_{PWQH}	Q Clock High	450			280			220			ns	

Figure 1. Read Data From Memory or Peripherals

NOT VALID
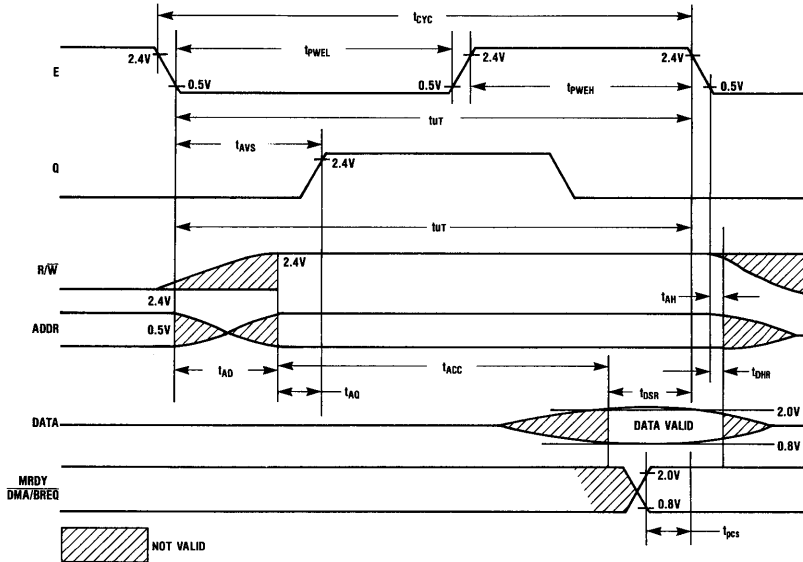
Figure 2. Write Data to Memory or Peripherals

NOT VALID

Figure 3. Bus Timing Test Load

4.75V

$R_L = 2.2K$

TEST POINT

MMD6150
OR EQUIV.

C

R

MMD7000
OR EQUIV.

C = 30pF FOR BA, BS   R = 11.7kΩ FOR D0-D7
    130pF FOR D0-D7, E, Q   16.5kΩ FOR A0-A15, E, Q
    90pF FOR A0-A15, R/W   24kΩ FOR BA, BS
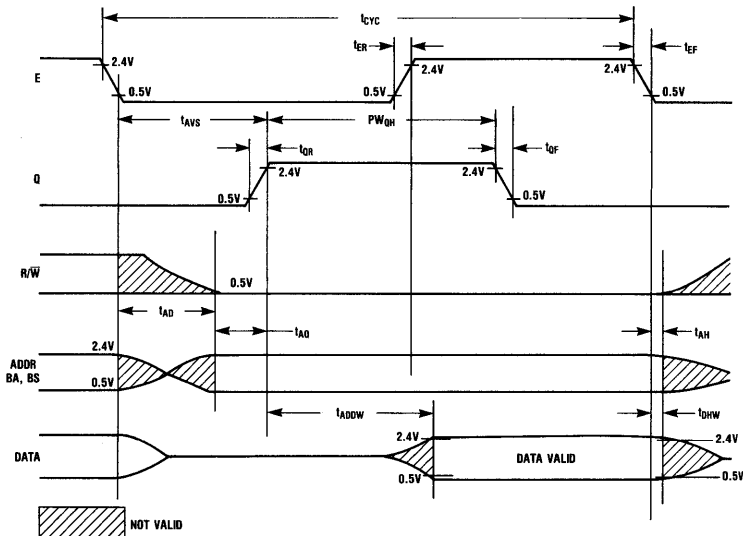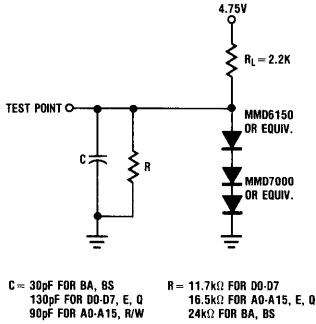
Programming Model

As shown in Figure 4, the S6809 adds three registers to the set available in the S6800. The added registers include a direct page register, the User Stack pointer and a second Index Register.

Accumulators (A, B, D)

The A and B registers are general purpose accumulators which are used for arithmetic calculations and manipulation of data.

Certain instructions concatenate the A and B registers to form a single 16-bit accumulator. This is referred to as the D register, and is formed with the A register as the most significant byte.

Direct Page Register (DP)

The Direct Page Register of the S6809 serves to enhance the Direct Addressing Mode. The content of this register appears at the higher address outputs (A_8-A_{15}) during direct Addressing Instruction execution. This

Figure 4. Programming Model of the Microprocessing Unit

15   0

| X — INDEX REGISTER |
| Y — INDEX REGISTER |
| U — USER STACK POINTER |
| S — HARDWARE STACK POINTER |

POINTER REGISTERS

| PC |

PROGRAM COUNTER

| A | B |

ACCUMULATORS

D

7   0

| DP | DIRECT PAGE REGISTER

7   0

| E | F | H | I | N | Z | V | C | CC — CONDITION CODE REGISTER
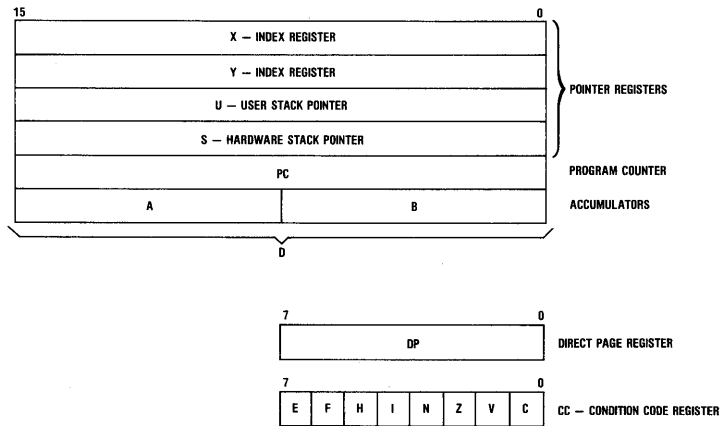
Figure 5. Condition Code Register Format
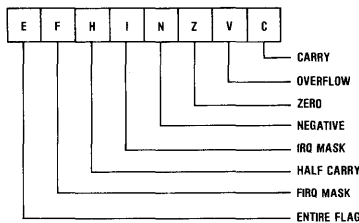
allows the direct mode to be used at any place in memory, under program control. To allow 6800 compatibility, all bits of this register are cleared during Processor Reset.

Index Registers (X, Y)

The Index Registers are used in indexed mode of addressing. The 16-bit address in this register takes part in the calculation of effective addresses. This address may be used to point to data directly or may be modified by an optional constant or register offset. During some indexed modes, the contents of the index register are incremented and decremented to point to the next item of tabular type data. All four pointer registers (X, Y, U, S) may be used as index registers.

Stack Pointers (U, S)

The Hardware Stack Pointer (S) is used automatically by the processor during subroutine calls and interrupts. The stack pointers of the S6809 point to the top of the stack, in contrast to the S6800 stack pointer which pointed to the next free location on the stack. The User Stack Pointer (U) is controlled exclusively by the programmer thus allowing arguments to be passed to and from subroutines with ease. Both Stack Pointers have the same indexed mode addressing capabilities as the X and Y registers, but also support **Push** and **Pull** instructions. This allows the S6809 to be used efficiently as a stack processor, greatly enhancing its ability to support higher level languages and modular programming.

Program Counter

The Program Counter is used by the processor to point to the address of the next instruction to be executed by the processor. Relative Addressing is provided allowing the Program Counter to be used like an index register in some situations.

Condition Code Register

The condition code register defines the State of the Processor at any given time, see Figure 5.

Bit 0 (C)

Bit 0 is the Carry Flag, and is usually the carry from the binary ALU. C is also used to represent a 'borrow' from subtract like instructions (CMP, NEG, SUB, SBC). Here the carry flag is the complement of the carry from the binary ALU.

Bit 1 (V)

Bit 1 is the overflow flag, and is set to a one by an operation which causes a signed two's complement arithmetic overflow. This overflow is detected in an operation in which the carry from the MSB in the ALU does not match the carry from the MSB-1.

Bit 2 (Z)

Bit 2 is the zero flag, and is set to a one if the result of the previous operation was identically zero.

Bit 3 (N)

Bit 3 is the negative flag, which contains exactly the value of the MSB of the result of the preceding operation. Thus, a negative two's-complement result will leave N set to a one.

Bit 4 (I)

Bit 4 is the $\overline{\text{IRQ}}$ mask bit. The processor will not recognize interrupts from the IRQ line if this bit is set to a one. $\overline{\text{NMI}}$, $\overline{\text{FIRQ}}$, $\overline{\text{IRQ}}$, $\overline{\text{RESET}}$, and SWI all set I to a one; SWI2 and SWI3 do not affect I.

Bit 5 (H)

Bit 5 is the half-carry bit, and is used to indicate a carry from bit 3 in the ALU as a result of an 8-bit addition only (ADC or ADD). This bit is used by the DAA instruction to perform a BCD decimal add adjust operation. The state of this flag is undefined in all subtract-like instructions.

Bit 6 (F)

Bit 6 is the $\overline{FIRQ}$ mask bit. The processor will not recognize interrupts from the FIRQ line if this bit is a one. $\overline{NMI}$, $\overline{FIRQ}$, SWI, and $\overline{RESET}$ all set F to a one. $\overline{IRQ}$, SWI2 and SWI3 do not affect F.

Bit 7 (E)

Bit 7 is the entire flag, and when set to a one indicates that the complete machine state (all the registers) was stacked, as opposed to the subset state (PC and CC). The E bit of the *stacked* CC is used on a return from interrupt (RTI) to determine the extent of the unstacking. Therefore, the current E left in the Condition Code Register represents past action.

S6809 MPU Signal Description

Power (V$_{SS}$, V$_{CC}$)

Two pins are used to supply power to the part: V$_{SS}$ is ground or 0 volts, while V$_{CC}$ is $+5.0V \pm 5\%$.

Address Bus (A$_0$-A$_{15}$)

Sixteen pins are used to output address information from the MPU onto the Address Bus. When the processor does not require the bus for a data transfer, it will output address FFFF$_{16}$, R/$\overline{W}$ = 1, and BS = 0. Addresses are valid on the rising edge of Q (see Figures 1 and 2). All address bus drivers are made high-impedance when output Bus Available (BA) is high. Each pin will drive one Schottky TTL load and typically 90pF.

Data Bus (D$_0$-D$_7$)

These eight pins provide communication with the system bi-directional data bus. Each pin will drive one Schottky TTL load and typically 130pF.

Read/Write (R/$\overline{W}$)

This signal indicates the direction of the data transfer on the data bus. A low indicates that the MPU is writing data onto the data bus. R/$\overline{W}$ is made high impedance when BA is high. R/$\overline{W}$ is valid on the rising edge of Q, refer to Figures 1 and 2.

$\overline{RESET}$

A low level on this Schmitt-trigger input for greater than one bus cycle will reset the MPU as shown in Figure 6. The Reset vectors are fetched from locations FFFE$_{16}$ and FFFF$_{16}$ (Table 1) when Interrupt Acknowledge is true, (BA$\wedge$BS = 1). During initial power-on, the Reset line should be held low until the clock oscillator is fully operational; see Figure 7.

Because the S6809 Reset pin has a Schmitt-trigger input with a threshold voltage higher than that of standard peripherals, a simple R/C network may be used to reset the entire system. This higher threshold voltage insures that all peripherals are out of the reset state before the Processor.

$\overline{HALT}$

A low level on this input pin will cause the MPU to stop running at the end of the present instruction and remain halted indefinitely without loss of data. When Halted, the BA output is driven high indicating the buses are high-impedance. BS is also high which indicates the processor is in the Halt or Bus Grant state. While halted, the MPU will not respond to external real-time requests ($\overline{FIRQ}$, $\overline{IRQ}$) although $\overline{DMA/BREQ}$ will always be accepted, and $\overline{NMI}$ or $\overline{RESET}$ will be latched for later response. During the Halt state Q and E continue to run normally. If the MPU is not running ($\overline{RESET}$, $\overline{DMA/BREQ}$), a halted state (BA and BS = 1) can be achieved by pulling $\overline{HALT}$ low while $\overline{RESET}$ is still low. If $\overline{DMA/BREQ}$ and $\overline{HALT}$ are both pulled low, the processor will reach the last cycle of the instruction (by reverse cycle stealing) where the machine will then become halted. See Figure 8.

Bus Available, Bus Status (BA, BS)

The Bus Available output is an indication of an internal control signal which makes the MOS buses of the MPU high-impedance. This signal does not imply that the bus will be available for more than one cycle. When BA goes low, an additional dead cycle will elapse before the MPU acquires the bus.

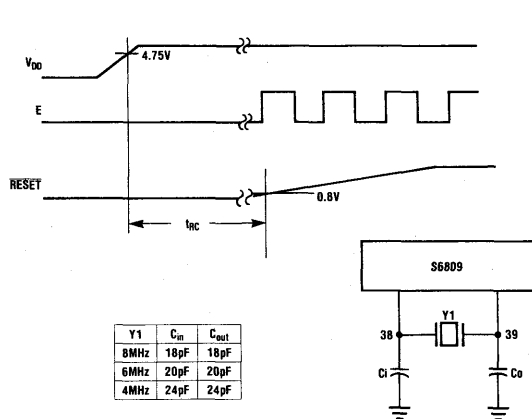The Bus Status output signal, when decoded with BA, represents the MPU state (valid with leading edge of Q):

MPU State		
BA	BS	
0	0	Normal (Running)
0	1	Interrupt Acknowledge
1	0	SYNC Acknowledge
1	1	HALT or Bus Grant

Figure 6. RESET Timing
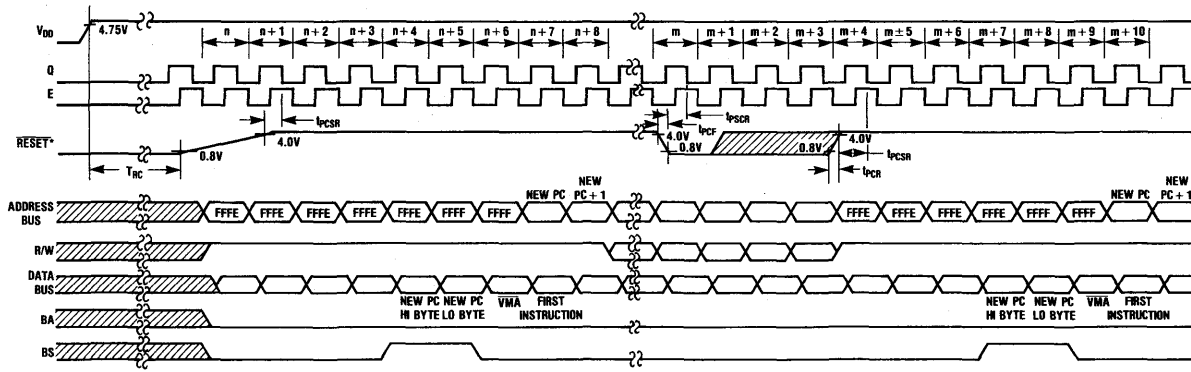
*NOTE: PARTS WITH DATE CODES PREFIXED BY 7F WILL COME OUT OF RESET ONE CYCLE SOONER THAN SHOWN

Figure 7. Crystal Connections and Oscillator Start Up

6809 Crystal Parameters*

	3.58MHz	4.00MHz	6.0MHz	8.0MHz
RS	60Ω	50Ω	30-50Ω	20-40Ω
C_0	3.5pF	6.5pF	4-6pF	4-6pF
C_1	.015pF	.025pF	.01-.02pF	.01-.02pF
C_{in}-C_{out}	25pF	25pF	25pF	25pF
Q	40K	≅30K	≅20K	≅20K

All Parameters Are ± 10%.
*Note: These are representative AT-cut crystal parameters only.
Crystals of other types of cut that work may also be used.

Y1	C_{in}	C_{out}
8MHz	18pF	18pF
6MHz	20pF	20pF
4MHz	24pF	24pF

S6800
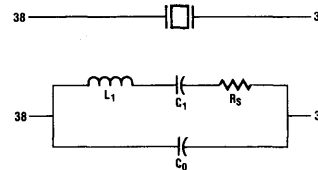
Figure 8. HALT and Single Instruction Execution for System Debug
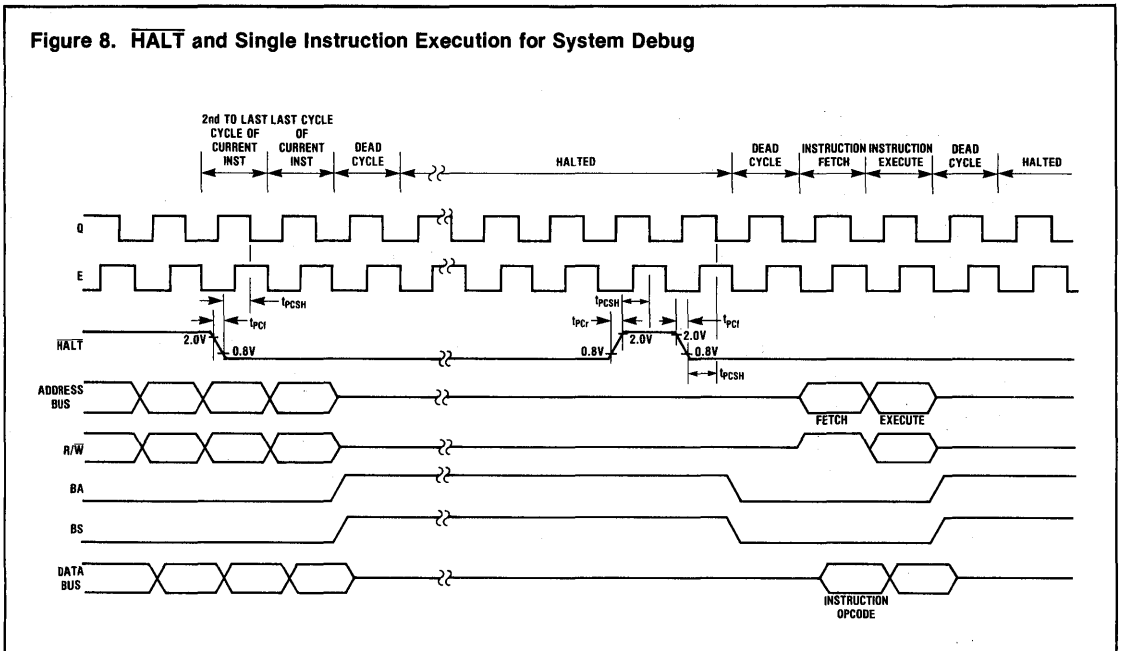
Interrupt Acknowledge is indicated during both cycles of a hardware-vector-fetch (RESET, NMI, FIRQ, IRQ, SWI, SWI2, SWI3). This signal, plus decoding of the lower 4 address lines can provide the user with an indication of which interrupt level is being serviced and allow vectoring by device (see Table 1).

Sync Acknowledge is indicated while the MPU is waiting for external synchronization on an interrupt line.

Halt/Bus Grant is true when the S6809 is in a Halt or Bus Grant condition.

Table 1. Memory Map for Interrupt Vectors

Memory Map for Vector Location		Interrupt Vector Description
MS	**LS**	
FFFE	FFFF	RESET
FFFC	FFFD	NMI
FFFA	FFFB	SWI
FFF8	FFF9	IRQ
FFF6	FFF7	FIRQ
FFF4	FFF5	SWI2
FFF2	FFF3	SWI3
FFF0	FFF1	Reserved

*NOTE: NMI, FIRQ and IRQ requests are latched by the falling edge of every Q except during cycle stealing operations (e.g., DMA) where only NMI is latched. From this point, a delay of at least one bus cycle will occur before the interrupt is serviced by the MPU.

Non-Maskable Interrupt (NMI)

A negative edge on this input requests that a non-maskable interrupt sequence be generated. A non-maskable interrupt cannot be inhibited by the program, and also has a higher priority than FIRQ, IRQ or software interrupts. During recognition of an NMI, the entire machine state is saved on the hardware stack. After reset, an NMI will not be recognized until the first program load of the Hardware Stack Pointer (S). The pulse width of NMI low must be at least one E cycle. If the NMI input does not meet the minimum set up with respect to Q, the interrupt will not be recognized until the next cycle. See Figure 9.

Fast-Interrupt Request (FIRQ)

A low level on this input pin will initiate a fast interrupt sequence, provided its mask bit (F) in the CC is clear. This sequence has priority over the standard Interrupt Request (IRQ), and is fast in the sense that it stacks only the contents of the condition code register and the program counter. The interrupt service routine should clear the source of the interrupt before doing an RTI. See Figure 10.

Figure 9. $\overline{IRQ}$ and $\overline{NMI}$ Interrupt Timing

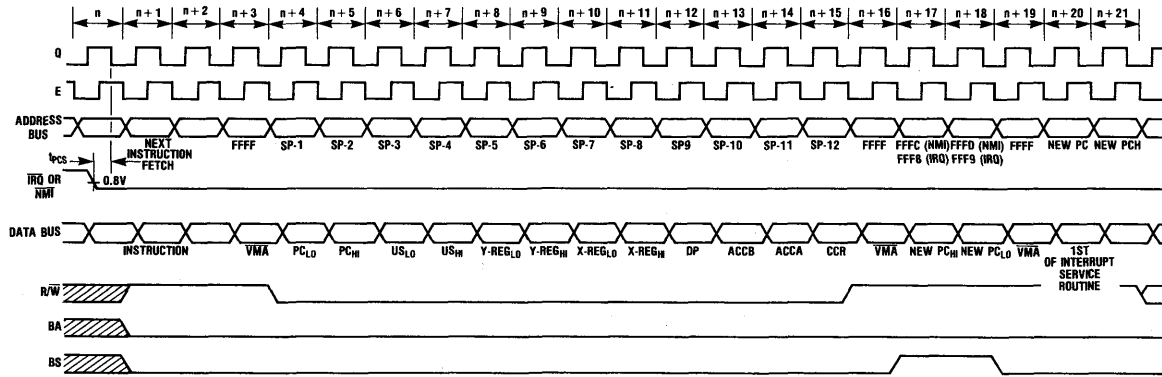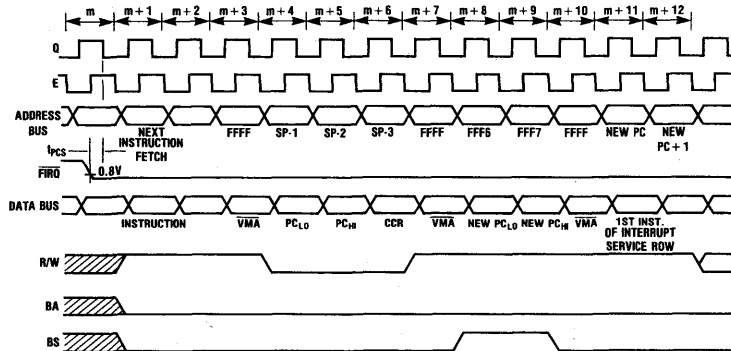**Figure 10. $\overline{FIRQ}$ Interrupt Timing**

Interrupt Request (IRQ)

A low level input on this pin will initiate an Interrupt Request sequence provided the mask bit (I) in the CC is clear. Since IRQ stacks the entire machine state it provides a slower response to interrupts than FIRQ. IRQ also has a lower priority than FIRQ. Again, the interrupt service routine should clear the source of the interrupt before doing an RTI. See Figure 9.

XTAL, EXTAL

These input pins are used to connect the on-chip oscillator to an external parallel-resonant crystal. Alternately, the pin EXTAL may be used as a TTL level input for external timing by grounding XTAL. The crystal or external frequency is 4 times the bus frequency, see Figure 7. Proper RF layout techniques should be observed in the layout of printed circuit boards.

E, Q

E is similar to the S6800 bus timing signal $\phi2$; Q is a quadrature clock signal which leads E. Q has no parallel on the S6800. Addresses from the MPU will be valid with the leading edge of Q. Data is latched on the falling edge of E. Timing for E and Q is shown in Figure 11.

MRDY

This input control signal allows stretching of E to extend data-access time. When MRDY is high, E will be in normal operation. When MRDY is low, E may be stretched integral multiples of quarter (¼) bus cycles, thus allowing interface to slow memories as shown in Figure 12. A maximum stretch is 10 microseconds. During non-valid memory accesses (VMA cycles). MRDY has no effect on stretching E. This inhibits slowing the processor speed during "don't care" bus accesses.

DMA/BREQ

The DMA/BREQ input provides a method of suspending execution and acquiring the MPU bus for another use as shown in Figure 13. Typical uses include DMA and dynamic memory refresh.

Transition of DMA/BREQ should occur during Q. A low level on this pin will stop instruction execution at the end of the current cycle. The MPU will acknowledge DMA/BREQ by setting BA and BS to a one. The requesting device will now have up to 15 bus cycles before the MPU retrieves the bus for self-refresh. Self-refresh requires one bus cycle with a leading and trailing dead cycle, see Figure 14.

Typically, the DMA controller will request to use the bus by asserting the DMA/BREQ pin low on the leading edge of E. When the MPU replies with BA = BS = 1, that cycle will be a dead cycle used to transfer control to the DMA controller.

False memory accesses should be prevented during any dead cycles. When BA is cleared (either as a result of
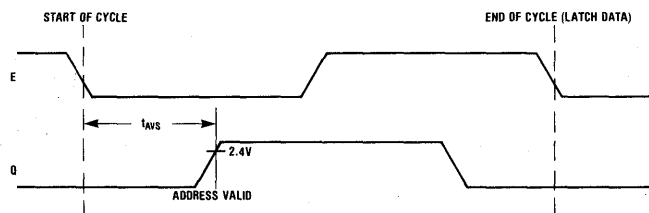
Figure 11. E/Q Relationship
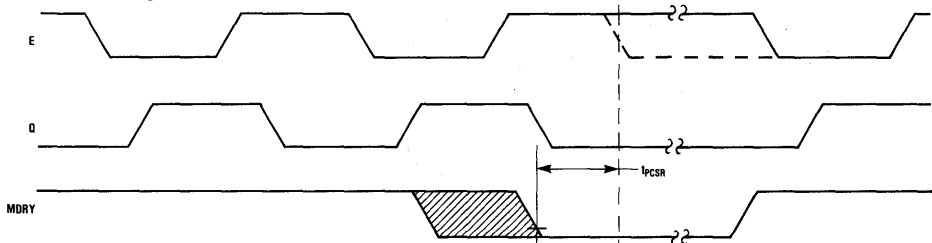

Figure 12. MRDY Timing
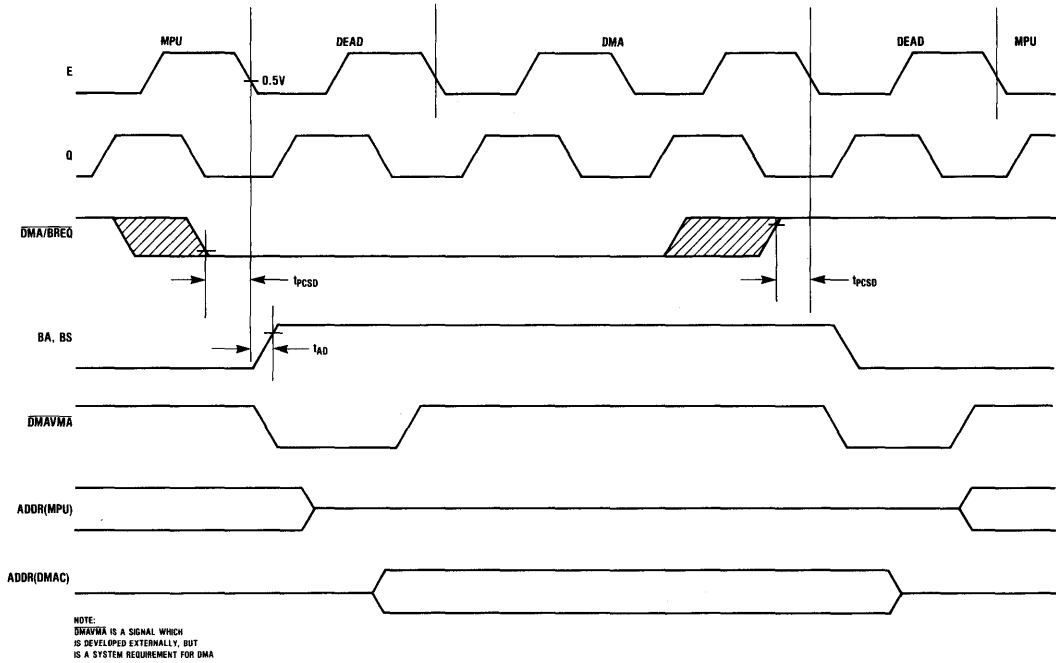
Figure 13. Typical DMA Timing (<14 Cycles)

NOTE:
DMAVMA IS A SIGNAL WHICH
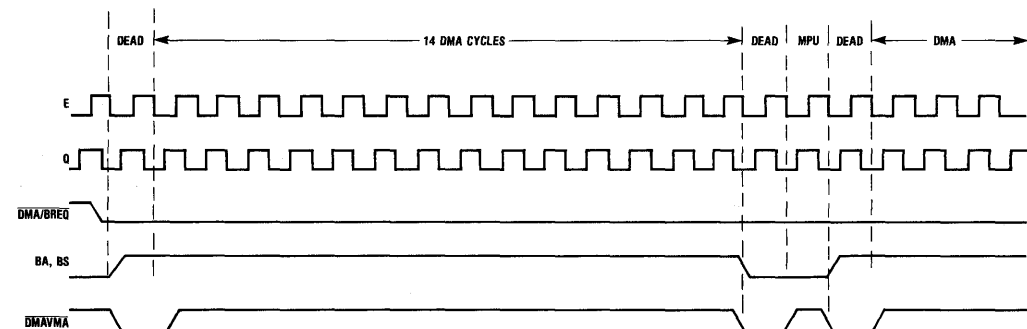IS DEVELOPED EXTERNALLY, BUT
IS A SYSTEM REQUIREMENT FOR DMA

Figure 14. Auto-Refresh DMA Timing (<14 Cycles)

$\overline{\text{DMA}/\text{BREQ}}$ = HIGH or MPU self-refresh), the DMA device should be taken off the bus.

Another dead cycle will elapse before the MPU is allowed a memory access to transfer control without contention.

MPU Operation

During normal operation, the MPU fetches an instruction from memory and then executes the requested function. This sequence begins at $\overline{\text{RESET}}$ and is repeated indefinitely unless altered by a special instruction or hardware occurrence. Software instructions that alter normal MPU operation are: SWI, SWI2, SWI3, CWAI, RTI and SYNC. An interrupt, $\overline{\text{HALT}}$ or $\overline{\text{DMA}/\text{BREQ}}$ can also alter the normal execution of instructions. Figure 15 illustrates the flowchart for the S6809. The left-half of the flowchart represents normal operation; the right-half represents the flow when an interrupt when an interrupt or special instruction occurs.

Addressing Modes

The basic instructions of any computer are greatly enhanced by the presence of powerful addressing modes. The S6809 has the most complete set of addressing modes available on any microcomputer today. For example, the S6809 has 59 basic instructions, however it recognizes 1464 different variations of instructions and addressing modes. The new addressing modes support modern programming techniques. The following addressing modes are available on the S6809:

Inherent (Includes Accumulator)
Immediate
Extended
  Extended Indirect
Direct
Register
Indexed
  Zero-Offset
  Constant Offset
  Accumulator Offset
  Auto Increment/Decrement
  Indexed Indirect
Relative
  Short/Long Relative Branching
  Program Counter Relative Addressing

Inherent (Includes Accumulator)

In this addressing mode, the opcode of the instruction contains all the address information necessary. Examples of Inherent Addressing are: ABX, DAA, SWI, ASRA, and CLRB.

Immediate Addressing

In Immediate Addressing, the effective addressing of the data is the location immediately following the opcode; the data to be used in the instruction immediately follows the opcode of the instruction. The S6809 uses both 8 and 16-bit immediate values depending on the size of argument specified by the opcode. Examples of instructions with Immediate Addressing are:

    LDA #$20
    LDX #$F000
    LDY #CAT

Note: # signifies Immediate addressing, $ signifies hexadecimal value.

Extended Addressing

In Extended Addressing the contents of the two bytes immediately following the opcode fully specify the 16-bit effective address used by the instruction. Note that the address generated by an extended instruction defines an absolute address and is not position independent. Examples of Extended Addressing include:

    LDA CAT
    STX MOUSE
    LDD $2000

Extended Indirect

As a special case of indexed addressing (discussed below), one level of indirection may be added to Extended Addressing. In Extended Indirect, the two bytes following the postbyte of an Indexed instruction contains the address of the address of the data.

    LDA [CAT]
   LDX [$FFFE]
    STU [DOG]

Direct Addressing

Direct addressing is similar to extended addressing except that only one byte of address follows the opcode. This byte specifies the lower 8 bits of the address to be used. The upper 8 bits of the address are supplied by the direct page register. Since only one byte of address is required in direct addressing, this mode requires less memory and executes faster than extended addressing. Of course, only 256 locations (one page) can be accessed without redefining the contents of the DP register. Since the DP register is set to $00 on Reset, direct addressing on the S6809 is compatible with direct addressing on the S6800. Indirection is not allowed in direct addressing. Some examples of direct addressing are:

    LDA $30
    SETDP $10 (Assembler directive)
    LDB $1030
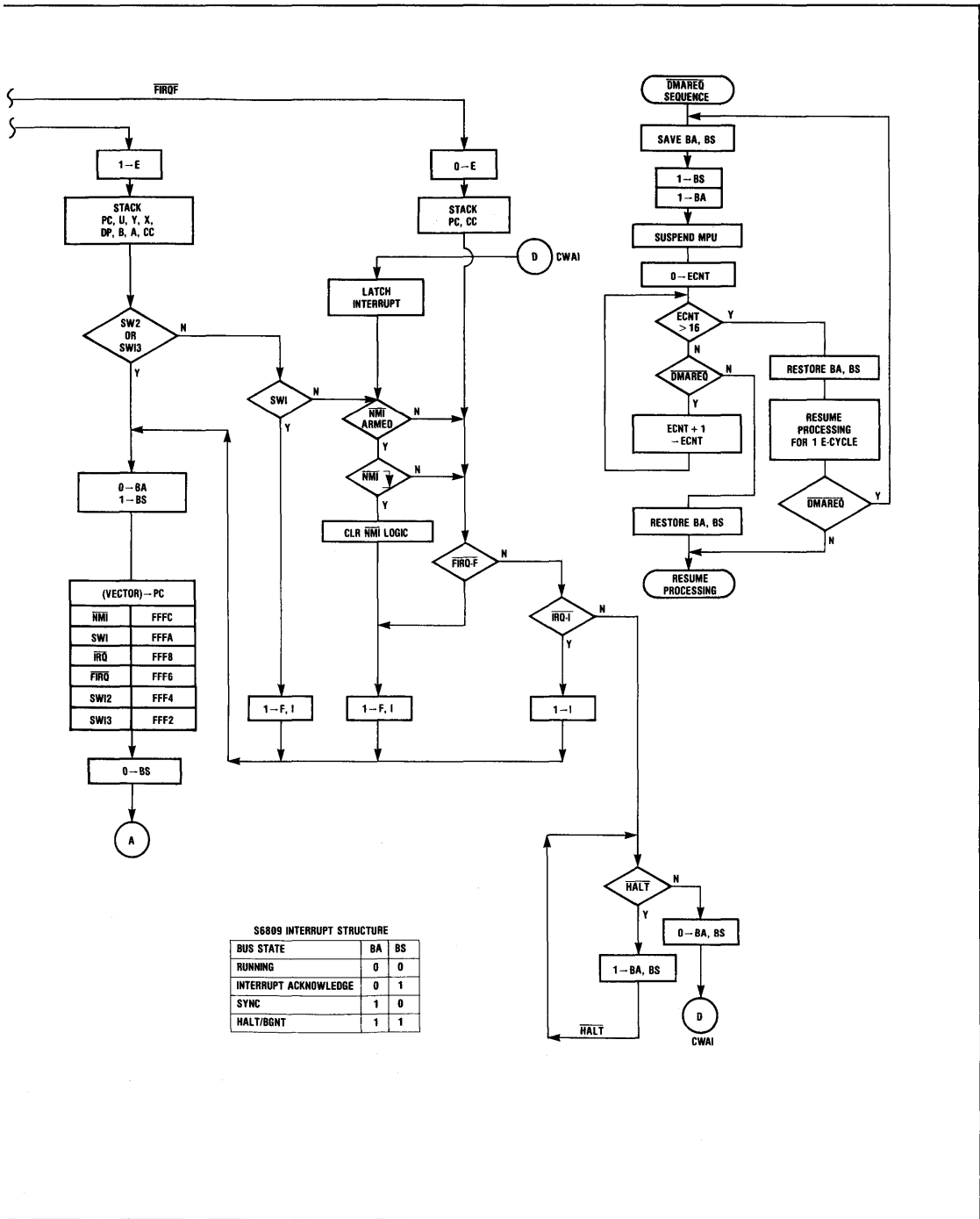   LDD   <CAT

Note: < is an assembler directive which forces direct addressing.

Figure 15. MPU Flow Chart
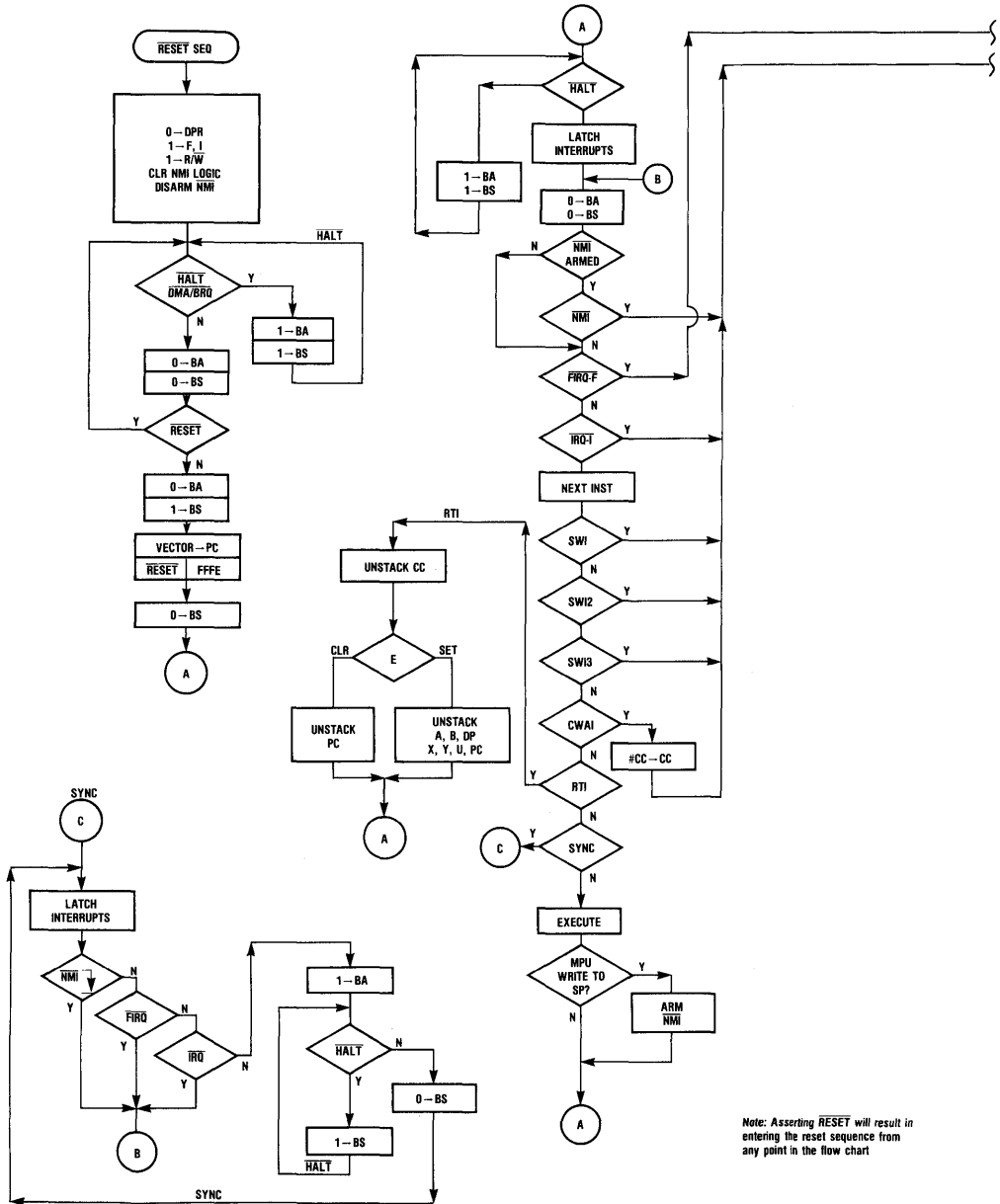
S6800

S6809 INTERRUPT STRUCTURE

BUS STATE	BA	BS
RUNNING	0	0
INTERRUPT ACKNOWLEDGE	0	1
SYNC	1	0
HALT/BGNT	1	1

Register Addressing

Some opcodes are followed by a byte that defines a register or set of registers to be used by the instruction, this is called a POSTBYTE. Some examples of register addressing are:

TFR	X,Y	Transfers X into Y
EXG	A,B	Exchanges A with B
PSHS	A,B,X,Y	Push onto S Y,X,B, then A
PULU	X,Y,D	Pull from U D,X, then Y

Indexed Addressing

In all indexed addressing one of the pointer registers (X, Y, U, S, and sometimes PC) is used in a calculation of the effective address of the operand to be used by the instruction. Five basic types of indexing are available and are discussed below. The postbyte of an indexed instruction specifies the basic type and variation of the addressing mode as well as the pointer register to be used. Figure 16 lists the legal formats for the postbyte. Table 2 gives the assembler form and the number of cycles and bytes added to the basic values for indexed addressing for each variation.

Zero-Offset Indexed — In this mode, the selected pointer register contains the effective address of the data to be used by the instruction. This is the fastest indexing mode.

Examples are:
    LDD 0,X
    LDA 0,S

Constant Offset Indexed — In this mode a two's-complement offset and the contents of one of the pointer registers are added to form the effective address of the operand. The pointer register's initial content is unchanged by the addition.

Three sizes of offsets are available:
    ± 4-bit (− 16 to + 15)
    ± 7-bit (− 128 to + 127)
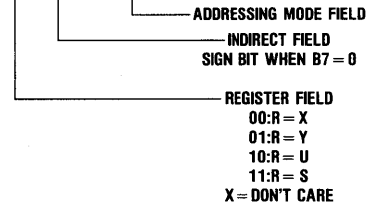   ± 15-bit (− 32768 to + 32767)

The two's complement 5-bit offset is included in the postbyte and therefore is most efficient in use of bytes and cycles. The two's complement 8-bit offset is contained in a single byte following the postbyte. The two's complement 16-bit offset is in the two bytes following the postbyte. In most cases the programmer need not be concerned with the size of this offset since the assembler will select the optional size automatically.

Examples of constant-offset indexing are:
    LDA 23,X
    LDX -2,S
    LDY 300,X
    LDU CAT,Y

Figure 16. Indexed Addressing Postbyte Register Bit Assignments

POST—BYTE REGISTER BIT								INDEXED ADDRESSING MODE
7	6	5	4	3	2	1	0	
0	R	R	X	X	X	X	X	EA = ,R ± 4-BIT OFFSET
1	R	R	0	0	0	0	0	,R+
1	R	R	I	0	0	0	1	,R+ +
1	R	R	0	0	0	1	0	, −R
1	R	R	I	0	0	1	1	, − − R
1	R	R	I	0	1	0	0	EA = ,R ± 0 OFFSET
1	R	R	I	0	1	0	1	EA = ,R ± ACCB OFFSET
1	R	R	I	0	1	1	0	EA = ,R ± ACCA OFFSET
1	R	R	I	1	0	0	0	EA = ,R ± 7-BIT OFFSET
1	R	R	I	1	0	0	1	EA = ,R ± 15-BIT OFFSET
1	R	R	I	1	0	1	1	EA = ,R ± D OFFSET
1	X	X	I	1	1	0	0	EA = ,PC ± 7-BIT OFFSET
1	X	X	I	1	1	0	1	EA = ,PC ± 15-BIT OFFSET
1	R	R	1	1	1	1	1	EA = ,ADDRESS

ADDRESSING MODE FIELD
INDIRECT FIELD
SIGN BIT WHEN B7 = 0
REGISTER FIELD
    00:R = X
    01:R = Y
    10:R = U
    11:R = S
    X = DON'T CARE

Accumulator-Offset Indexed — This mode is similar to constant offset indexed except that the two's complement value in one of the accumulators (A, B or D) and the content of one of the pointer registers are added to form the effective address of the operand. The contents of both the accumulator and the pointer register are unchanged by the addition. The postbyte specifies which accumulator to use as an offset and no additional bytes are required. The advantage of an accumulator offset is that the value of the offset can be calculated by a program at run-time.

Some examples are:
    LDA B,Y
    LDX D,Y
    LEAX B,X

Auto Increment/Decrement Indexed — In the auto increment addressing mode, the pointer register contains the address of the operand. Then, after the pointer register is used it is incremented by one or two. This addressing mode is useful in stepping through tables, moving data, or for the creation of software stacks. In auto

S6800

Table 2. Indexed Addressing Modes

Type	Forms	Non Indirect				Indirect			
		Assembler Form	Postbyte OP Code	+ ~	+ #	Assembler Form	Postbyte OP Code	+ ~	+ #
Constant Offset From R (Signed Offsets)	No Offset	,R	1RR00100	0	0	[,R]	1RR10100	3	0
	5-Bit Offset	n, R	0RRnnnnn	1	0	defaults to 8-bit			
	8-Bit Offset	n, R	1RR01000	1	1	[n, R]	1RR11000	4	1
	16-Bit Offset	n, R	1RR01001	4	2	[n, R]	1RR11001	7	2
Accumulator Offset From R (Signed Offsets)	A — Register Offset	A, R	1RR00110	1	0	[A, R]	1RR10110	4	0
	B — Register Offset	B, R	1RR00101	1	0	[B, R]	1RR10101	4	0
	D — Register Offset	D, R	1RR01011	4	0	D, R]	1RR11011	7	0
Auto Increment/Decrement R	Increment By 1	,R+	1RR00000	2	0	not allowed			
	Increment By 2	,R++	1RR00001	3	0	[,R++]	1RR10001	6	0
	Decrement By 1	,−R	1RR00010	2	0	not allowed			
	Decrement By 2	,−−R	1RR00011	3	0	[,−−R]	1RR10011	6	0
Constant Offset From PC	8-Bit Offset	n, PCR	1XX01100	1	1	[n, PCR]	1XX11100	4	1
	16-Bit Offset	n, PCR	1XX01101	5	2	[n, PCR]	1XX11101	8	2
Extended Indirect	16-Bit Address	—	—	—	—	[n]	10011111	5	2

+ and + indicate the number of additional cycles and bytes for the particular variation.
~   #

R = X, Y, U or S   X = 00   Y = 01
X = Don't Care   U = 10   S = 11

decrement, the pointer register is decremented prior to use as the address of the data. The use of auto decrement is similar to that of auto increment but the tables, etc. are scanned from the high to low addresses. The size of the increment/decrement can be either one or two to allow for tables of either 8 or 16-bit data to be accessed and is selectable by the programmer. The predecrement, post-increment nature of these modes allow them to be used to create additional software stacks that behave identically to the U and S stacks.

Some examples of the auto increment/decrement addressing modes are:

    LDA ,X +
    STD ,Y + +
    LDBL ,– Y
    LDX ,– – S

Indexed Indirect

All of the indexing modes with the exception of auto increment/decrement by one, or a ± 4-bit offset may have an additional level of indirection specified. In Indirect addressing, the effective address is contained at the location specified by the content of the Index register plus any offset. In the example below, the A accumulator is loaded indirectly using an effective address calculated from the Index register and an offset.

                        Before Execution
                        A = XX (don't care)
                            X = $F000
    $0100 LDA   [10,X] EA is now $F010
    $F010 $F1   F150 is now the new EA
    $F011 $50
    $F150 $AA
                         After Execution
                        A = $AA Actual Data Loaded

All modes of indexed indirect are included except those which are meaningless (e.g., auto increment/decrement by 1 indirect). Some examples of indexed indirect are:

    LDA   [,X]
    LDD   [10,S]
    LDA   [B,Y]
    LDD   [,X + +]

Relative Addressing

The byte(s) following the branch opcode is (are) treated as a signed offset which is added to the program counter. If the branch condition is true then the calculated address (PC + signed offset) is loaded into the program counter. Program execution continues at the new location as indicated by the PC; Short (1 byte offset) and long (2 bytes offset) relative addressing modes are available. All of memory can be reached in long relative addressing as an effective address is interpreted modulo 2^{16}. Some examples of relative addressing are:

```
          BEQ    CAT      (short)
          BGT    DOG      (short
CAT       LBEQ   RAT      (long)
DOG       LBGT   RABBIT   (long)
           •
           •
           •
RAT    NOP
RABBIT NOP
```

Program Counter Relative

The PC can be used as the pointer register with 8 or 16-bit signed offsets. As in relative addressing the offset is added to the current PC to create the effective address. The effective address is then used as the address of the operand or data. Program Counter Relative Addressing is used for writing position independent programs. Tables related to a particular routine will maintain the same relationship after the routine is moved, if referenced relative to the Program Counter. Examples are:

```
LDA     CAT,PCR
LEAX    TABLE, PCR
```

Since program counter relative is a type of indexing, an additional level of indirection is available.

```
LDA     [CAT,PCR]
LDU     (DOG,PCR)
```

S6809 Instruction Set

The instruction set of the S6809 is similar to that of the S6800 and is upward compatible at the source code level. The number of opcodes has been reduced from 72 to 59, but because of the expanded architecture and additional addressing modes, the number of available opcodes (with different addressing modes) has risen from 197 to 1464.

Some of the new instructions and addressing modes are described in detail below:

PSHU/PSHS

The push instructions have the capability of pushing onto either the hardware stack (S) or user stack (U) any or all of the MPU registers with a single instruction.

PULU/PULS

The pull instructions have the same capability of the push instruction, in reverse order. The byte immediately following the push or pull opcode determines which register or registers are to be pushed or pulled. The actual PUSH/PULL sequence is fixed; each bit defines a unique register to push or pull as shown in Figure 17.

TFR/EXG

Within the S6809, any register may be transferred to or exchanged with another of like-size, i.e., 8-bit to 8-bit or 16-bit to 16-bit. Bits 4-7 of postbyte define the source register, while bits 0-3 represent the destination register. These are denoted as follows:

```
0000 — D    0101 — PC
0001 — X    1000 — A
0010 — Y    1001 — B
0011 — U    1010 — CC
0100 — S    1011 — DP
```

Note: All other combinations are undefined and INVALID.

Load Effective Address

The LEA works by calculating the effective address used in an indexed instruction and stores that address value, rather than the data at that address, in a pointer register. This makes all the features of the internal addressing hardware available to the programmer. Some of the implications of this instruction are illustrated in the following table of examples:

The LEA Instruction also allows the user to access data in a position independent manner. For example:

```
     LEAX   MSG1, PCR
     LBSR   PDATA (Print message routine)

MSG1 FCC  'MESSAGE'
```

Figure 17. Push/Pull Postbyte

```
            —PULL ORDER    PUSH ORDER—
PC    U    Y    X    DP    B    A    CC    PSHS/PULS
  FFFF...... —INCREASING MEMORY ADDRESS→ ...... 0000
PC    S    Y    X    DP    B    A    CC    PSHU/PULU
```

Table 3. LEA Examples

Instruction	Operation	Comment
LEAX 10, X	X + 10 →X	Adds 5-bit constant 10 to X
LEAX 500, X	X + 500 →X	Adds 6-bit constant 500 to X
LEAY A, Y	Y + A →Y	Adds 8-bit accumulator to Y
LEAY D, Y	Y + D →Y	Adds 16-bit D accumulator to Y
LEAU −10, U	U − 10 →U	Subtracts 10 from U
LEAS −10, S	S − 10 →S	Used to reserve area on stack
LEAS 10, S	S + 10 →S	Used to 'clean up' stack
LEAX 5, S	S + 5 →X	Transfers as well as adds

This sample program prints "message." By writing MSG1,PCR, the assembler computes the distance between the present address and MSG1. This result is placed as a constant into the LEAX instruction which will be indexed from the PC value at the time of execution. No matter where the code is located, when it is executed, the computed offset from the PC will put the absolute address of MSG1 into the X pointer register. This code is totally position independent.

MUL

Multiplies the unsigned binary numbers in the A and B accumulator and places the unsigned result into the 16-bit D accumulator. This unsigned multiply also allows multiple-precision multiplications.

Long and Short Relative Branches

The S6809 has the capability of program counter relative branching throughout the entire memory map. In this mode, if the branch is to be taken, the 8 or 16-bit signed offset is added to the value of the program counter to be used as the effective address. This allows the program to branch anywhere in the 64K memory map. Position independent code can be easily generated through the use of relative branching. Both short (8-bit) and long (16-bit) branches are available.

Sync

After encountering a Sync operation, the MPU enters a Sync state, stops processing instructions and waits for an interrupt. If the pending interrupt is non-maskable ($\overline{NMI}$) or maskable ($\overline{FIRQ}$, $\overline{IRQ}$) with its mask bit (F or I) clear, the processor will clear the Sync state and perform the normal interrupt stacking and service routine. Since $\overline{FIRQ}$ and $\overline{IRQ}$ are not edge-triggered, a low level with a minimum duration of three cycles is required to assure that the interrupt will be taken. If the pending interrupt is maskable ($\overline{FIRQ}$, $\overline{IRQ}$) with its mask bit (F

or I) set, the processor will clear the Sync state and continue processing in sequence. Figure 18 depicts Sync timing.

Software Interrupts

A Software Interrupt is an instruction which will cause an interrupt, and its associated vector fetch. These Software Interrupts are useful in operating system calls, software debugging, trace operations, memory mapping, and software development systems. Three levels of SWI are available on this S6809, and are prioritized in the following order: SWI, SWI2, SWI3.

16-Bit Operations

The S6809 has the capability of processing 16-bit data. These instructions include loads, stores, compares, adds, subtracts, transfers, exchanges, pushes and pulls.

Cycle-by-Cycle Operation

The address bus cycle-by-cycle performance chart illustrates the memory-access sequence corresponding to each possible instruction and addressing mode in the S6809. Each instruction begins with an opcode fetch. While that opcode is being internally decoded, the next program byte is always fetched. (Most instructions will use the next byte, so this technique considerably speeds throughput). Next, the operation of each opcode will follow the flowchart. $\overline{VMA}$ is an indication of $FFFF_{16}$ on the address bus, $R/\overline{W} = 1$ and BS = 0. The following examples illustrate the use of the chart; see Figure 19.
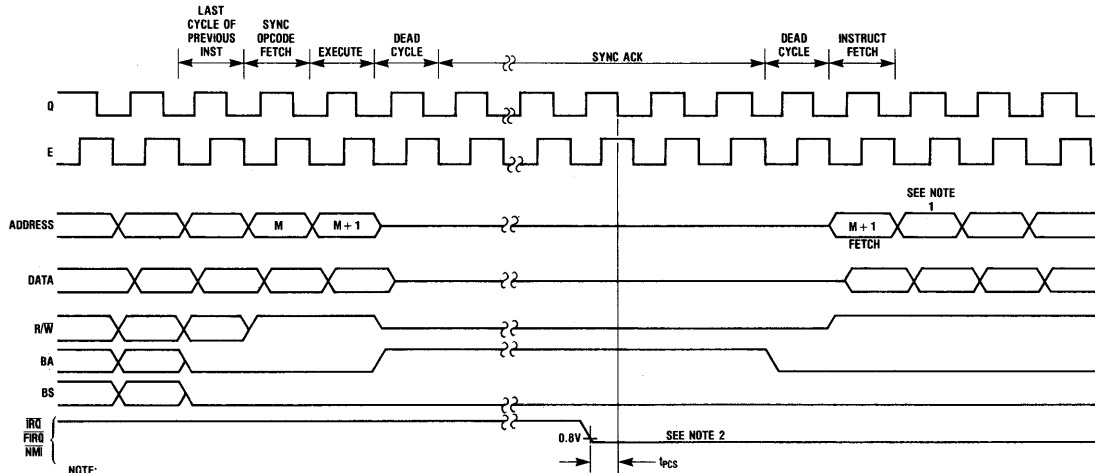
LBSR (Branch taken)
Cycle #
  1   opcode Fetch
  2   opcode +
  3   opcode +
  4    $\overline{VMA}$
  5    $\overline{VMA}$
  6   ADDR
  7    $\overline{VMA}$
  8   STACK (write)
  9   STACK (write)
DEC (Extended)
  1   opcode Fetch
  2   opcode +
  3   opcode +
  4    $\overline{VMA}$
  5   ADDR (read)
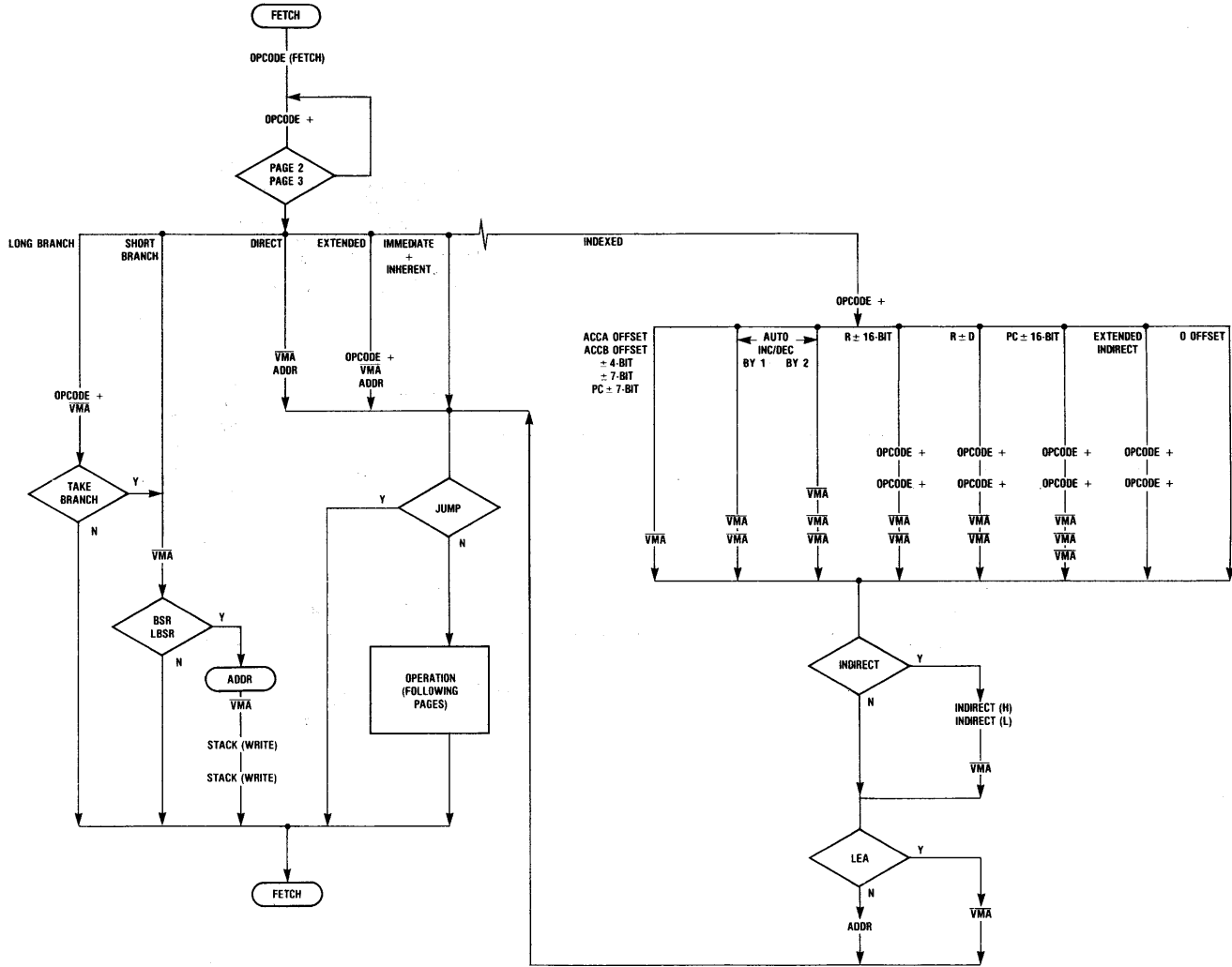 6 $\overline{VMA}$
  7   ADDR (write)
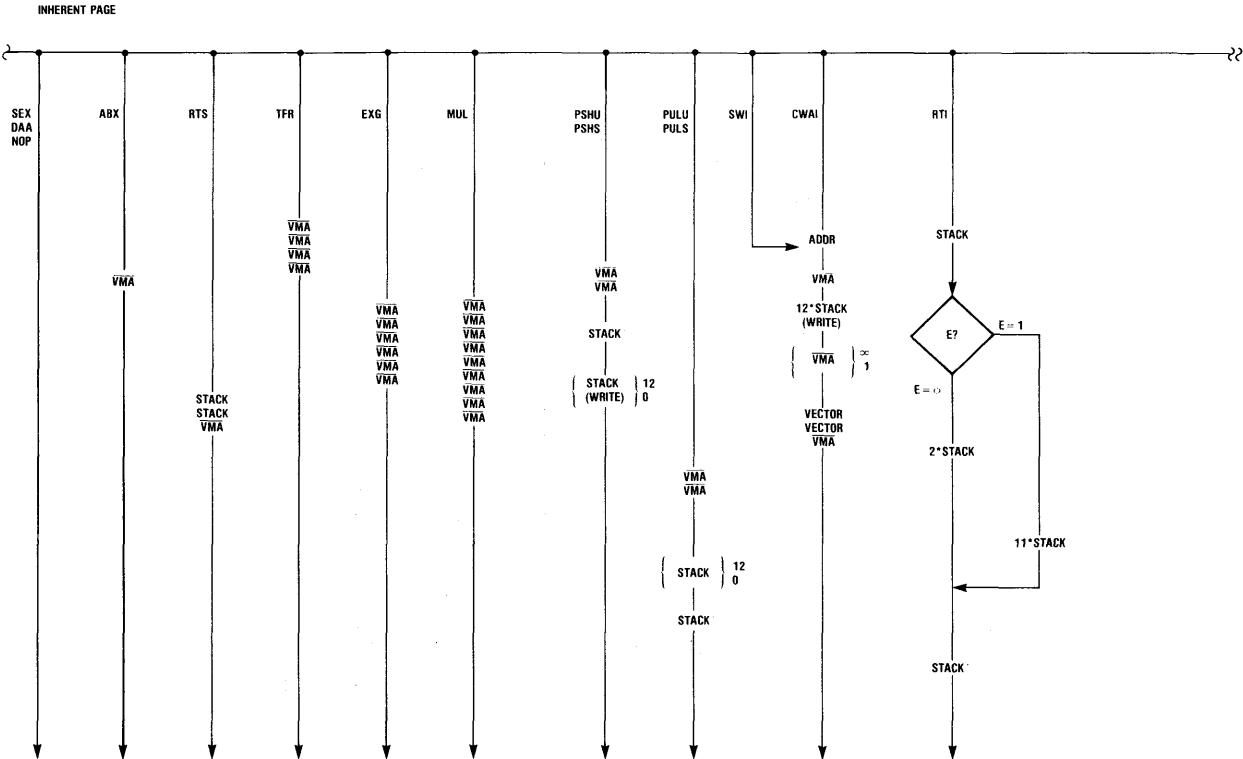
Figure 18. SYNC Timing

NOTE:
1. IF THE MASK BIT IS SET WHEN THE INTERRUPT IS REQUESTED PROCESSING WILL CONTINUE WITH INSTRUCTION EXECUTION FETCHED FROM PREVIOUS STEP. HOWEVER, IF AN NMI OR AN UNMASKED FIRQ OR IRQ CAUSED INTERRUPT, THE ADDRESS PLACED ON BUS FROM PREVIOUS CYCLE (M + 1) REMAINS ON BUS AND PROCESSING CONTINUES WITH THIS CYCLE AS (m + 1) OR (n + 1) OF INTERRUPT TIMING.
2. IF MASK BITS ARE CLEAR IRQ & FIRQ MUST BE HELD LOW FOR THREE CYCLES TO GUARANTEE INTERRUPT TO BE TAKEN, ALTHOUGH ONLY ONE CYCLE IS NECESSARY TO BRING THE PROCESSOR OUT OF SYNC.

S6809/S68A09/S68B09

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Figure 19. Address Bus Cycle-by-Cycle Performance

FETCH

OPCODE (FETCH)

OPCODE +

PAGE 2
PAGE 3

LONG BRANCH   SHORT BRANCH   DIRECT   EXTENDED   IMMEDIATE + INHERENT   INDEXED

OPCODE +

ACCA OFFSET
ACCB OFFSET
± 4-BIT
± 7-BIT
PC ± 7-BIT

AUTO INC/DEC
BY 1   BY 2

R ± 16-BIT

R ± D

PC ± 16-BIT

EXTENDED INDIRECT

0 OFFSET

VMA
ADDR

OPCODE +
VMA
ADDR

OPCODE +
VMA

OPCODE +   OPCODE +   OPCODE +   OPCODE +

OPCODE +   OPCODE +   OPCODE +   OPCODE +

TAKE BRANCH   Y

N

VMA

JUMP
Y

N

VMA   VMA   VMA
VMA   VMA   VMA

VMA   VMA   VMA
VMA   VMA   VMA

VMA
VMA

BSR
LBSR   Y

N

ADDR
VMA

OPERATION
(FOLLOWING PAGES)

STACK (WRITE)

STACK (WRITE)

INDIRECT   Y

N

INDIRECT (H)
INDIRECT (L)

VMA

LEA   Y

N

ADDR

VMA

FETCH

Figure 19. Address Bus Cycle-by-Cycle Performance (Continued)

INHERENT PAGE

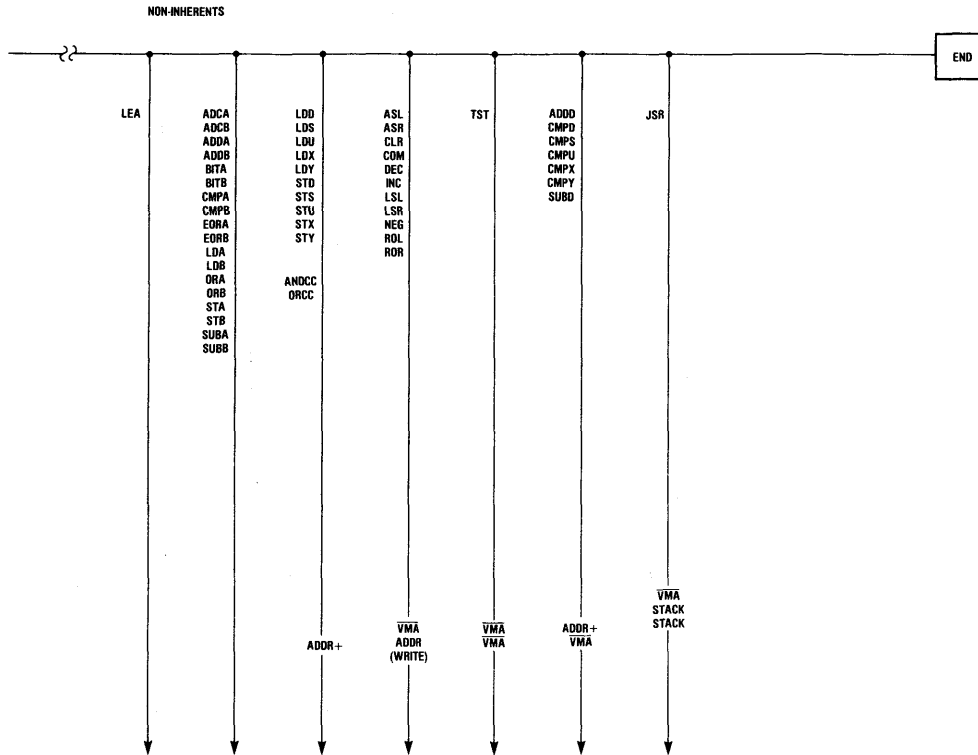| SEX DAA NOP	ABX	RTS	TFR	EXG	MUL	PSHU PSHS	PULU PULS	SWI	CWAI	RTI

S6800

Figure 19. Address Bus Cycle-by-Cycle Performance (Cont.)

Figure 19. Address Bus Cycle-by-Cycle Performance (Cont.)

NON-INHERENTS

END

| LEA | ADCA
ADCB
ADDA
ADDB
BITA
BITB
CMPA
CMPB
EORA
EORB
LDA
LDB
ORA
ORB
STA
STB
SUBA
SUBB | LDD
LDS
LDU
LDX
LDY
STD
STS
STU
STX
STY

ANDCC
ORCC | ASL
ASR
CLR
COM
DEC
INC
LSL
LSR
NEG
ROL
ROR | TST | ADDD
CMPD
CMPS
CMPU
CMPX
CMPY
SUBD | JSR |

ADDR+ | VMA
ADDR
(WRITE) | VMA
VMA | ADDR+
VMA | VMA
STACK
STACK

S6809 Instruction Set Tables

The instructions of the S6809 have been broken down into six different categories. They are as follows:

8-Bit Operation (Table 4)
16-Bit Operation (Table 5)
Index Register/Stack Pointer Instructions (Table 6)
Relative Branches (Long and Short) (Table 7)
Miscellaneous Instructions (Table 8)
Hexadecimal Value Instructions (Table 9)

Table 4. 8-Bit Accumulator and Memory Instructions

Mnemonic(s)	Operation
ADCA, ADCB	Add memory to accumulator with carry
ADDA, ADDB	Add memory to accumulator
ANDA, ANDB	And memory with accumulator
ASL, ASLA, ASLB	Arithmetic shift of accumulator or memory left
ASR, ASRA, ASRB	Arithmetic shift of accumulator or memory right
BITA, BITB	Bit test memory with accumulator
CLR, CLRA, CLRB	Clear accumulator or memory location
CMPA, CMPB	Compare memory from accumulator
COM, COMA, COMB	Complement accumulator or memory location
DAA	Decimal adjust A-accumulator
DEC, DECA, DECB	Decrement accumulator or memory location
EORA, EORB	Exclusive OR memory with accumulator
EXG R1, R2	Exchange R1 with R2 (R1, R2 = A, B, CC, DP)
INC, INCA, INCB	Increment accumulator or memory location
LDA, LDB	Load accumulator from memory
LSL, LSLA, LSLB	Logical shift left accumulator or memory location
LSR, LSRA, LSRB	Logical shift right accumulator or memory location
MUL	Unsigned multiply (A x B→D)
NEG, NEGA, NEGB	Negate accumulator or memory
ORA, ORB	OR memory with accumulator
ROL, ROLA, ROLB	Rotate accumulator or memory left
ROR, RORA, RORB	Rotate accumulator or memory right
SBCA, SBCB	Subtract memory from accumulator with borrow
STA, STB	Store accumulator to memory
SUBA, SUBB	Subtract memory from accumulator
TST, TSTA, TSTB	Test accumulator or memory location
TFR, R1, R2	Transfer R1 to R2 (R1, R2 = A, B, CC, DP)

NOTE: A, B, CC, or DP may be pushed to (pulled from) either stack with PSHS, PSHU, (PULS, PULU) instructions.

Table 5. 16-Bit Accumulator and Memory Instructions

Mnemonic(s)	Operation
ADDD	Add memory to D accumulator
CMPD	Compare memory from D accumulator
EXG D, R	Exchange D with X, Y, S, U or PC
LDD	Load D accumulator from memory
SEX	Sign Extend B accumulator into A accumulator
STD	Store D accumulator to memory
SUBD	Subtract memory from D accumulator
TFR D, R	Transfer D to X, Y, S, U or PC
TFR R, D	Transfer X, Y, S, U or PC to D

Table 6. Index Register/Stack Pointer Instructions

Mnemonic(s)	Operation
CMPS, CMPU	Compare memory from stack pointer
CMPX, CMPY	Compare memory from index register
EXG R1, R2	Exchange D, X, Y, S, U or PC with D, X, Y, S, U or PC
LEAS, LEAU	Load effective address into stack pointer
LEAX, LEAY	Load effective address into index register
LDS, LDU	Load stack pointer from memory
LDX, LDY	Load index register from memory
PSHS	Push any register(s) onto hardware stack (except S)
PSHU	Push any register(s) onto user stack (except U)
PULS	Pull any register(s) from hardware stack (except S)
PULU	Pull any register(s) from hardware stack (except U)
STS, STU	Store stack pointer to memory
STX, STY	Store index register to memory
TFR R1, R2	Transfer D, X, Y, S, U or PC to D, X, Y, S, U or PC
ABX	Add B accumulator to X (unsigned)

Table 7. Branch Instructions

Mnemonic(s)	Operation
BCC, LBCC	Branch if carry clear
BCS, LBCS	Branch if carry set
BEQ, LBEQ	Branch is equal
BGE, LBGE	Branch if greater than or equal (signed)
BGT, LBGT	Branch if greater (signed)
BHI, LBHI	Branch if higher (unsigned)
BHS, LBHS	Branch is higher or same (unsigned)
BLE, LBLE	Branch if less than or equal (signed)
BLO, LBLO	Branch if lower (unsigned)
BLS, LBLS	Branch if lower or same (unsigned)
BLT, LBLT	Branch if less than (signed)
BMI, LBMI	Branch if minus
BNE, LBNE	Branch if not equal
BPL, LBPL	Branch is plus
BRA, LBRA	Branch always
BRN, LBRN	Branch never
BSR, LBSR	Branch to subroutine
BVC, LBVC	Branch if overflow clear
BVS, LBVS	Branch if overflow set

Table 8. Miscellaneous Instructions

Mnemonic(s)	Operation
ANDCC	AND condition code register
CWAI	AND conditon code register, then wait for interrupt
NOP	No operation
ORCC	OR condition code register
JMP	Jump
JSR	Jump to subroutine
RTI	Return from interrupt
RTS	Return from subroutine
SWI, SWI2, SWI3	Software interrupt (absolute indirect)
SYNC	Synchronize with interrupt line

S6809/S68A09/S68B09

Table 9. Hexadecimal Values of Machine Codes

OP Mnem	Mode	~	#	OP Mnem	Mode	~	#	OP Mnem	Mode	~	#
00 NEG	Direct	6	2	30 LEAX	Indexed	4+	2+	60 NEG	Indexed	6+	2+
01 *				31 LEAY		4+	2+	61 *			
02 *				32 LEAS		4+	2+	62 *			
03 COM		6	2	33 LEAU	Indexed	4+	2+	63 COM		6+	2+
04 LSR		6	2	34 PSHS	Inherent	5+	2	64 LSR		6+	2+
05 *				35 PULS		5+	2	65 *			
06 ROR		6	2	36 PSHU		5+	2	66 ROR		6+	2+
07 ASR		6	2	37 PULU		5+	2	67 ASR		6+	2+
08 ASL/LSL		6	2	38 *				68 ASL/LSL		6+	2+
09 ROL		6	2	39 RTS		5	1	69 ROL		6+	2+
0A DEC		6	2	3A ABX		3	1	6A DEC		6+	2+
0B *				3B RTI		6/15	1	6B *			
0C INC		6	2	3C CWAI		20	2	6C INC		6+	2+
0D TST		6	2	3D MUL		11	1	6D TST		6+	2+
0E JMP		3	2	3E *				6E JMP		3+	2+
0F CLR	Direct	6	2	3F SWI	Inherent	19	1	6F CLR	Indexed	6+	2+
10 Page 2	—	—	—	40 NEGA	Inherent	2	1	70 NEG	Extended	7	3
11 Page 3	—	—	—	41 *				71 *			
12 NOP	Inherent	2	1	42 *				72 *			
13 SYNC	Inherent	2	1	43 COMA		2	1	73 COM		7	3
14 *				44 LSRA		2	1	74 LSR		7	3
15 *				45 *				75 *			
16 LBRA	Relative	5	3	46 RORA		2	1	76 ROR		7	3
17 LBSR	Relative	9	3	47 ASRA		2	1	77 ASR		7	3
18 *				48 ASLA/LSLA		2	1	78 ASL/LSL		7	3
19 DAA	Inherent	2	1	49 ROLA		2	1	79 ROL		7	3
1A ORCC	Immed	3	2	4A DECA		2	1	7A DEC		7	3
1B *				4B *				7B *			
1C ANDCC	Immed	3	2	4C INCA		2	1	7C INC		7	3
1D SEX	Inherent	2	1	4D TSTA		2	1	7D TST		7	3
1E EXG		8	2	4E *				7E JMP		4	3
1F TFR	Inherent	6	2	4F CLRA	Inherent	2	1	7F CLR	Extended	7	3
20 BRA	Relative	3	2	50 NEGB	Inherent	2	1	80 SUBA	Immed	2	2
21 BRN		3	2	51 *				81 CMPA		2	2
22 BHI		3	2	52 *				82 SBCA		2	2
23 BLS		3	2	53 COMB		2	1	83 SUBD		4	3
24 BHS/BCC		3	2	54 LSRB		2	1	84 ANDA		2	2
25 BLO/BCS		3	2	55 *				85 BITA		2	2
26 BNI		3	2	56 RORB		2	1	86 LDA		2	2
27 BEQ		3	2	56 RORB		2	1	87 *			
28 BVC		3	2	57 ASRA		2	1	88 EORA		2	2
29 BVS		3	2	58 ASLB/LSLB		2	1	89 ADCA		2	2
2A BPL		3	2	59 ROLB		2	1	8A ORA		2	2
2B BMI		3	2	5A DECB		2	1	8B ADDA		2	2
2C BGE		3	2	5B *				8C CMPX	Immed	4	3
2D BLT		3	2	5C INCB		2	1	8D BSR	Relative	7	2
2E BGT		3	2	5D TSTB		2	1	8E LDX	Immed	3	3
2F BLE	Relative	3	2	5E *				8F *			
				5F CLRB	Inherent	2	1				

NOTE: All unused opcodes are both undefined and illegal

Legend

~ Number of MPU cycles (less possible push/pull or indexed-mode cycles)

Number of program bytes

* Denotes unused opcode

AMI.

S6800 (side tab)

Table 9. Hexadecimal Values of Machine Codes (Continued)

OP Mnem	Mode	~	#
90 SUBA	Direct	4	2
91 CMPA		4	2
92 SBCA		4	2
93 SUBD		6	2
94 ANDA		4	2
95 BITA		4	2
96 LDA		4	2
97 STA		4	2
98 EORA		4	2
99 ADCA		4	2
9A ORA		4	2
9B ADDA		4	2
9C CMPX		6	2
9D JSR		7	2
9E LDX		5	2
9F STX	Direct	5	2
A0 SUBA	Indexed	4+	2+
A1 CMPA		4+	2+
A2 SBCA		4+	2+
A3 SUBD		6+	2+
A4 ANDA		4+	2+
A5 BITA		4+	2+
A6 LDA		4+	2+
A7 STA		4+	2+
A8 EORA		4+	2+
A9 ADCA		4+	2+
AA ORA		4+	2+
AB ADDA		4+	2+
AC CMPX		6+	2+
AD JSR		7+	2+
AE LDX		5+	2+
AF STX	Indexed	5+	2+
B0 SUBA	Extended	5	3
B1 CMPA		5	3
B2 SBCA		5	3
B3 SUBD		7	3
B4 ANDA		5	3
B5 BITA		5	3
B6 LDA		5	3
B7 STA		5	3
B8 EORA		5	3
B9 ADCA		5	3
BA ORA		5	3
BB ADDA		5	3
BC CMPX		7	3
BD JSR		8	3
BE LDX		6	3
BF STX	Extended	6	3
C0 SUBB	Immed	2	2
C1 CMPB		2	2
C2 SBCB	Immed	2	2

OP Mnem	Mode	~	#
C3 ADDD	Immed	4	3
C4 ANDB		2	2
C5 BITB		2	2
C6 LDB		2	2
C7 *			
C8 EORB		2	2
C9 ADCB		2	2
CA ORB		2	2
CB ADDB		2	2
CC LDD		3	3
CD *			
CE LDU	Immed	3	3
CF *			
D0 SUBB	Direct	4	2
D1 CMPB		4	2
D2 SBCB		4	2
D3 ADDD		6	2
D4 ANDB		4	2
D5 BITB		4	2
D6 LDB		4	2
D7 STB		4	2
D8 EORB		4	2
D9 ADCB		4	2
DA ORB		4	2
DB ADDB		4	2
DC LDD		5	2
DD STD		5	2
DE LDU		5	2
DF STU	Direct	5	2
E0 SUBB	Indexed	4+	2+
E1 CMPB		4+	2+
E2 SBCB		4+	2+
E3 ADDD		6+	2+
E4 ANDB		4+	2+
E5 BITB		4+	2+
E6 LDB		4+	2+
E7 STB		4+	2+
E8 EORB		4+	2+
E9 ADCB		4+	2+
EA ORB		4+	2+
EB ADDB		4+	2+
EC LDD		5+	2+
ED STD		5+	2+
EE LDU		5+	2+
EF STU	Indexed	5+	2+
F0 SUBB	Extended	5	3
F1 CMPB		5	3
F2 SBCB		5	3
F3 ADDD		7	3
F4 ANDB		5	3
F5 BITB	Extended	5	3

OP Mnem	Mode	~	#
F6 LDB	Extended	5	3
F7 STB		5	3
F8 EORB		5	3
F9 ADCB		5	3
FA ORB		5	3
FB ADDB		5	3
FC LDD		6	3
FD STD		6	3
FE LDU		6	3
FF STU	Extended	6	3
1021 LBRN	Relative	5	4
1022 LBHI		5(6)	4
1023 LBLS		5(6)	4
1024 LBHS/LBCC		5(6)	4
1025 LBCS/LBLO		5(6)	4
1026 LBNE		5(6)	4
1027 LBEQ		5(6)	4
1028 LBVC		5(6)	4
1029 LBVS		5(6)	4
102A LBPL		5(6)	4
102B LBMI		5(6)	4
102C LBGE		5(6)	4
102D LBLT	Relative	5(6)	4
102E LBGT	Relative	5(6)	4
102F LBLE	Relative	5(6)	4
103F SWI/2	Inherent	20	2
1083 CMPD	Immed	5	4
108C CMPY		5	4
108E LDY	Immed	4	4
1093 CMPD	Direct	7	3
109C CMPY		7	3
109E LDY		6	3
109F STY	Direct	6	3
10A3 CMPD	Indexed	7+	3+
10AC CMPY		7+	3+
10AE LDY		6+	3+
10AF STY	Indexed	6+	3+
10B3 CMPD	Extended	8	4
10BC CMPY		8	4
10BE LDY		7	4
10BF STY	Extended	7	4
10CE LDS	Immed	4	4
10DE LDS	Direct	6	3
10DF STS	Direct	6	3
10EE LDS	Indexed	6+	3+
10EF STS	Indexed	6+	3+
10FE LDS	Extended	7	4
10FF STS	Extended	7	4

NOTE: All unused opcodes are both undefined and illegal

Table 9. Hexadecimal Values of Machine Codes (Continued)

OP Mnem	Mode	~	#	OP Mnem	Mode	~	#	OP Mnem	Mode	~	#
113F SWI/3	Inherent	20	2	1193 CMPU	Direct	7	3	11AC CMPS	Indexed	7+	3+
1183 CMPU	Immed	5	4	119C CMPS	Direct	7	3	11B3 CMPU	Extended	8	4
118C CMPS	Immed	5	4	11A3 CMPU	Indexed	7+	3+	11BC CMPS	Extended	8	4

NOTE: All unused opcodes are both undefined and illegal

AMI

AMERICAN MICROSYSTEMS, INC.

UNIVERSAL ASYNCHRONOUS RECEIVER/TRANSMITTER

Features

☐ **Full or Half Duplex Operation — Can Receive and Transmit Simultaneously at Different Baud Rates.**

☐ **Completely Programmable — Data Word Length, Number of Stop Bits, Parity.**

☐ **Start Bit Generated Automatically**

☐ **Data and Clock Synchronization Performed Automatically**

☐ **Double Buffered—Eliminates Timing Difficulties**

☐ **Completely Static Circuitry**

☐ **Fully TTL Compatible.**

☐ **Three-state Output Capability**

☐ **Single Power Supply: +5V**

☐ **Standard 40-Pin Dual-in-Line Package**

☐ **Plug In Compatible with Western Digital TR1602A, TR1863, Fujitsu 8868A**

S6800

Block Diagram

Pin Configuration

V_{CC}	1	40	TRC
*N.C.	2	39	EPE
V_{SS}	3	38	WLS_1
RRD	4	37	WLS_2
RR_8	5	36	SBS
RR_7	6	35	PI
RR_6	7	34	CRL
RR_5	8	33	TR_8
RR_4	9	32	TR_7
RR_3	10	31	TR_6
RR_2	11	30	TR_5
RR_1	12	29	TR_4
PE	13	28	TR_3
FE	14	27	TR_2
OE	15	26	TR_1
SFD	16	25	TR_0
RRC	17	24	TRE
$\overline{DRR}$	18	23	$\overline{THRL}$
DR	19	22	THRE
RI	20	21	MR
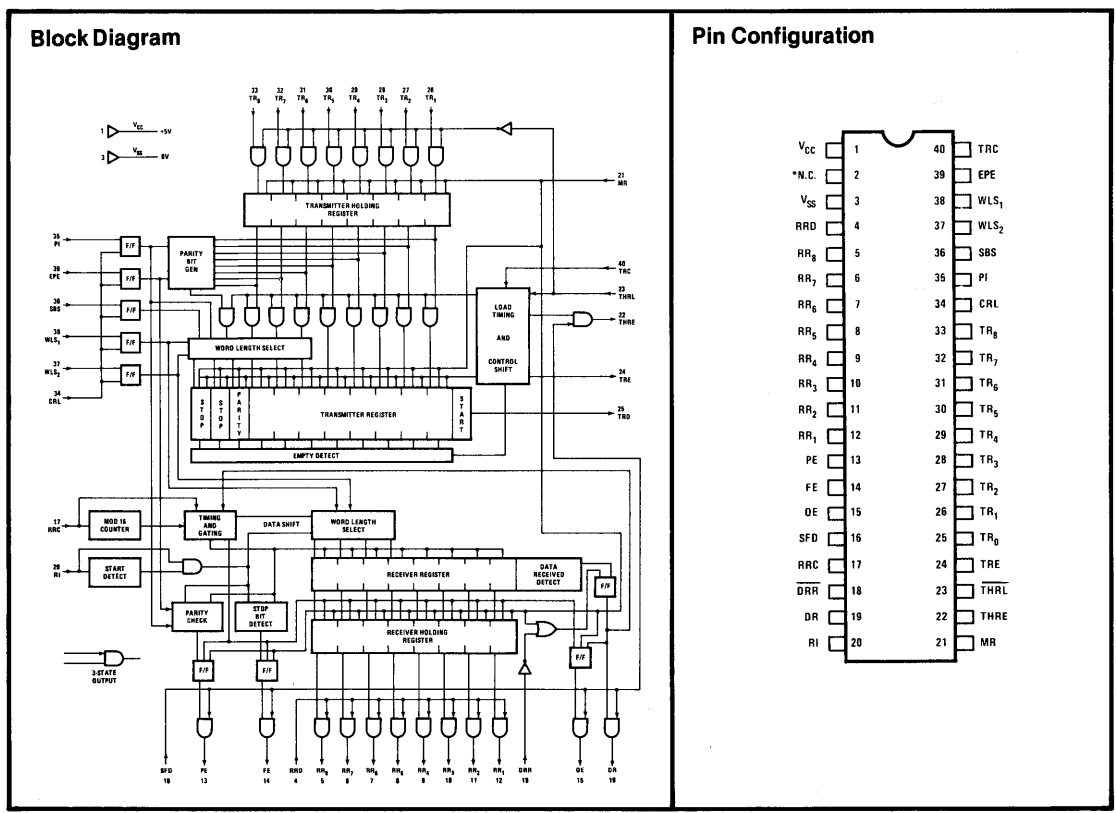
General Description

The AMI S1602 is a programmable Universal Asynchronous Receiver/Transmitter (UART) fabricated with N-Channel silicon gate MOS technology. All control pins, input pins and output pins are TTL compatible, and a single +5 volt power supply is used. The UART interfaces asynchronous serial data from terminals or other peripherals, to parallel data for a microprocessor, computer, or other terminal. Parallel data is converted by the trans-

mitter section of the UART into a serial word consisting of the data as well as start, parity, and stop bit(s). Serial data is converted by the receiver section of the UART into parallel data. The receiver section verifies correct code transmission by parity checking and receipt of a valid stop bit. The UART can be programmed to accept word lengths of 5, 6, 7, or 8 bits. Even or odd parity can be set. Parity generation checking can be inhibited. The number of stop bits can be programmed for one, two, or one and one-half when transmitting a 5-bit code.

Absolute Maximum Ratings*

V_{CC} Pin Potential to V_{SS} Pin .... $-0.3V$ to $++7.0V$
Input Voltage .... $-0.3V$ to $+7.0V$
Operating Temperature .... $0°C$ to $+70°C$
Storage Temperature .... $-55°C$ to $+150°C$

Note: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheets. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Capacitance: $T_A = 25°$; f=1MHz; $V_{IN}=0V$

Symbol	Parameter	Typ.	Max.	Unit
C_{IN}	Input Capacitance for all Inputs	10	—	pF

Guaranteed Operating Conditions (Referenced to V_{SS})

Symbol	Parameter	Operating Temperature	Min.	Typ.	Max.	Unit
V_{CC}	Supply Voltage	$0°C$ to $+70°C$	4.75	5.0	5.25	V
V_{SS}			0.0	0.0	0.0	V
V_{IH}	Logic Input High Voltage	$0°C$ to $+70°C$	2.2	—	V_{CC}	V
V_{IL}	Logic Input Low Voltage	$0°C$ to $+70°C$	-0.3	—	$+0.8$	V

D.C. Characteristics (Guaranteed Operating Ranges Unless Otherwise Noted.)

Symbol	Parameter	Min.	Typ.	Max.	Unit
I_{IL}	Input Leakage Current ($V_{IN}=0$ to 5.25V, $V_{CC}=5.25V$)	—	—	1.4	mA
I_{LZ}	Output Leakage Current for 3-State ($V_{OUT}=0V$ to V_{CC}, SFD = RRD = V_{IH})	-20	—	$+20$	μA
V_{OL}	Output Low Voltage ($I_{OL}=1.8mA$)	—	—	0.4	V
V_{OH}	Output High Voltage ($I_{OL}=-200\mu A$)	2.4	—	—	V
I_{CC}	V_{CC} Supply Current	—	70	—	mA

A.C. Characteristics (Guaranteed Operating Ranges Unless Otherwise Noted.)

Symbol	Parameter	Min.	Typ.	Max.	Unit
f_C	Clock Frequency for RRC and TRC (Duty Cycle = 50%)	DC	—	800	kHz
t_{PWC}	CRL Pulse Width, High	200	—	—	ns
t_{PWT}	THRL Pulse Width, Low	180	—	—	ns
t_{PWR}	DRR Pulse Width, Low	180	—	—	ns
t_{PWM}	MR Pulse Width, High	150	—	—	ns
t_C	Coincidence Time (Figure 3 and Figure 8)	180	—	—	ns
t_{HOLD}	Hold Time (Figure 3 and Figure 8)	20	—	—	ns
t_{SET}	Setup Time (Figure 3 and Figure 8)	0	—	—	ns
t_{PD0}	Propagation Delay Time High to Low, Output ($C_L = 130pF + 1TTL$)	—	—	350	ns
t_{PD1}	Propagation Delay Time Low to High, Output ($C_L = 130pF + 1TTL$)	—	—	350	ns

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Pin Description

Pin	Label	Function
1	V_{CC}	**Power Supply** — normally at +5V.
2	N.C.	**No connection.** On the S1602 this is an unconnected pin. On the TR1602A this is a −12V supply. −12V is not needed on the S1602 and thus the N.C. pin allows the S1602 to be compatible with the TR1602A.
3	V_{SS}	This is normally at 0V or ground.
4	RRD	**Receive Register Disconnect.** A high logic level, V_{IH}, on this pin disconnects the Receiver Holding Register outputs from the data outputs $RR_8 - RR_1$ on pin 5 − 12.
5 − 12	$RR_8 - RR_1$	**Receiver Holding Register Data.** These are the parallel outputs from the Receiver Holding Register if the RRD input is low (V_{IL}). Data is (LSB) right justified for character formats of less than eight bits, with RR_1 being the least significant bit. Unused MSBs are forced to a low logic output level, V_{OL}.
13	PE	**Parity Error.** This output pin goes to a high level if the received parity does not agree with that programmed by the Even Parity Enable input (pin 39). This output is updated as each character is transferred to the Receiver Holding Register. The Status Flag Disconnect input (pin 16) allows additional PE lines to be tied together by providing an output disconnect capability.
14	FE	**Framing Error.** This output pin goes high if the received character has no valid stop bit. Each time a character is transferred to the Receiver Holding Register, this output is updated. The Status Flag Disconnect input (pin 16) allows additional FE lines to be tied together by providing an output disconnect capability.
15	OE	**Overrun Error.** This output pin goes high if the Data Received Flag (pin 19) did not get reset before the next character was transferred to the Receive Holding Register. The Status Flag Disconnect input (pin 16) allows additional OE lines to be tied together providing an output disconnect capability.
16	SFD	**Status Flag Disconnect.** When this input is high, PE, FE, OE, DR and THRE outputs are forced to high impedance Three State allowing bus sharing capability.

Pin Description (Continued)

Pin	Label	Function
17	RRC	**Receive Register Clock.** This clock input is 16x the desired receiver shift rate.
18	$\overline{DRR}$	**Data Received Reset.** A low level input, V_{IL}, clears the Data Received (DR) line.
19	DR	**Data Received.** When a complete character has been received and transferred to the Receiver Holding Register, this output goes to the high level, V_{OH}.
20	RI	**Receiver Input.** Serial input data enters on this line. It is transfered to the Receiver Register as determined by the character length, parity and number of stop bits. When data is not being received, this input must remain high, V_{IH}.
21	MR	**Master Reset.** A high level pulse, V_{IH}, on this input clears the internal logic. The transmitter and Receive Registers, Receiver Holding Registers, FE, OE, PE, DRR are reset. In addition, the serial output line is set to a high level, V_{OH}.
22	THRE	**Transmitter Holding Register Empty.** This output will go high when the Transmitter Holding Register completes transfer of its contents to the Transmitter Register. The high level indicates a new character may be loaded into the Transmitter Holding Register.
23	$\overline{THRL}$	**Transmitter Holding Register Load.** When a low level, V_{IL}, is applied to this input, a character is loaded into the Transmitter Holding Register. The character is transferred to the Transmitter Register on a low to high level, V_{IH}, transition as long as the Transmitter Register is not currently in the process of transmitting a character. If a character is being transmitted, the transfer is delayed until the transmission is completed. The new character is then transferred simultaneously with the start of the serial transmission of the new character.
24	TRE	**Transmitter Register Empty.** Goes high when the Transmitter Register has completed the serial transmission of a full character including the required number of stop bits. A high will be maintained until the start of transmission of the next character.
25	TRO	**Transmitter Register Output.** Transmits the Transmitter Register contents (Start bit, Data bits, Parity bit and Stop bit(s)) serially. Remains high, V_{OH}, when no data is being transmitted. Therefore, start of transmission is determined by transition of the Start bit from high to low level voltage, V_{OL}.
26–33	$TR_1 - TR_8$	**Transmitter Register Data Inputs.** The THRL strobe loads the character on these lines into the Transmitter Holding Register. If WLS_1 and WLS_2 have selected a character of less than 8 bits, the character is right justified to the least significant bit, TR_1 with the excess bits not used. A high input level, V_{IH}, will cause a high output level, V_{OH}, to be transmitted.
34	CRL	**Control Register Load.** The control bits, (WLS_1, WLS_2, EPE, PI, SBS), are loaded into the Control Register when the input is high. This input may be either strobed or hard wired to the high level.
35	PI	**Parity Inhibit.** Parity generation and verification circuitry are inhibited when this input is high. The PE output will be held low as well. When in the inhibit condition the Stop bit(s) will follow the last data bit on transmission.
36	SBS	**Stop Bit(s) Select.** A high level will select two Stop bits, and a low level selects one Stop bit. If 5-bit words are selected, a high level will generate one and one-half Stop bits.

Pin Description (Continued)

Pin	Label	Function
37, 38	WLS$_2$, WLS$_1$	**Word Length Select.** The state of these two (2) inputs determines the character length (exclusive of parity) as follows:
39	EPE	**Even Parity Enable.** A high voltage level, V_{IH}, on this input will select even parity, while a low voltage level, V_{IL}, selects odd parity.
40	TRC	**Transmitter Register Clock.** The frequency of this clock input should be 16 times the desired baud rate.

WLS$_2$	WLS$_1$	WORD LENGTH
LOW	LOW	5 bits
LOW	HIGH	6 bits
HIGH	LOW	7 bits
HIGH	HIGH	8 bits

S6800

Figure 1. Receiver Operating Timing
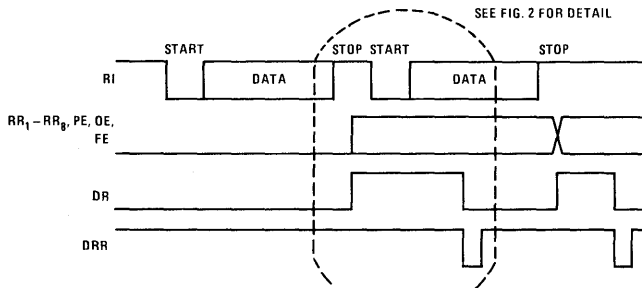
Figure 2. Timing for Status Flags, RR$_1$ thru RR$_8$ and DR
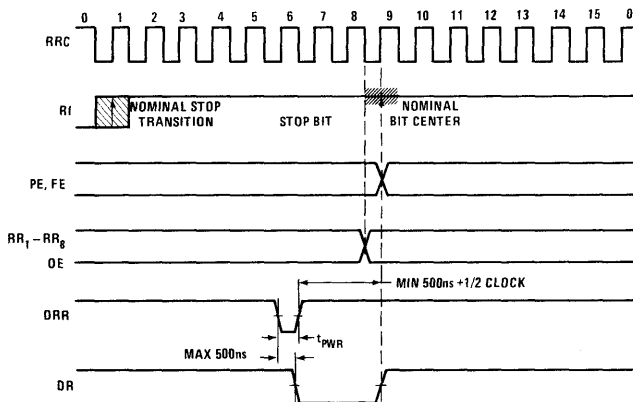
Figure 3. Transmitter Operating Timing
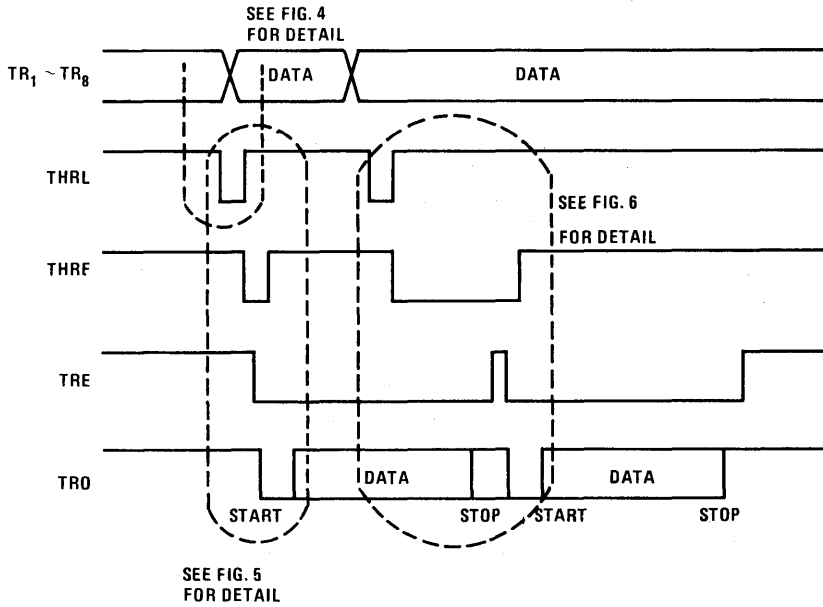
Figure 4. Data Input Load Cycle
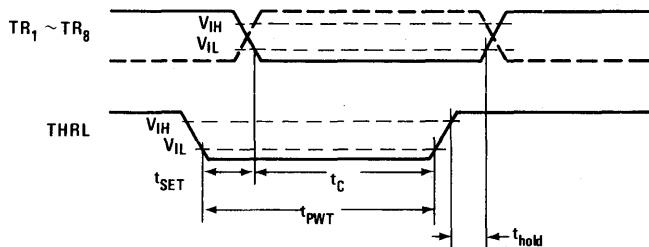
Figure 5. Transmitter Output Timing (1)

INPUT TRC

CR1 CF1 CR2 CF2 CR3 CF3 CR4 CF4

TO TRANSMITTER REGISTER WHEN EMPTY

INPUT THRL

V_{IH} V_{IL}

V_{OH}

TO TRANSMITTER HOLDING REGISTER

OUTPUT THRE

①

V_{OL} V_{OH}

OUTPUT TRE

② MAX 500ns ⑤ MAX 500ns

V_{OL}

OUTPUT TRO

MAX 500ns ③

V_{OL}

MAX 500ns ④
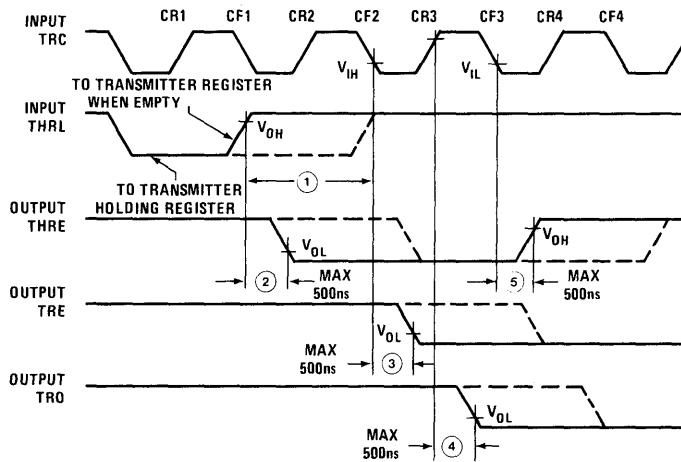
NOTES:

1. When the positive transition of THRL is 500ns or more before the falling edge of TRC (CF2 in the figure), TRE is enabled at CF2. But, when 500ns>①>0ns, TRE is invalid between CF2 and CF3.
2. THRE goes to low during 500ns Max. from the positive transition of THRL.
3. TRE goes to low during 500ns Max. from the first falling edge of TRC after THRE goes to low with TRE high.
4. TRO goes to low (START BIT) during 500ns Max. from the first rising edge of TRC after TRE goes to low.
5. THRE goes to high during 500ns Max. from the falling edge of TRC after START BIT is enabled.

Figure 6. Transmitter Output Timing (2)

INPUT TRC

$CR_0 CF_0 CR_1 CF_1$ CR_{14} CF_{15} CF_{14} CR_{15} $CR'_0 CF'_0 CR'_1 CF'_1$

V_{IH} V_{IH} V_{IH} V_{IL} V_{IL}

INPUT THRL

V_{IH}

OUTPUT THRE

V_{OL}

② MAX 500ns

MAX 500ns ⑤ MAX 500ns V_{OH}

⑥ V_{OH}

OUTPUT TRE

V_{OH}

V_{OL}

OUTPUT TRO

15 CLOCK

DATA STOP BIT

MAX 500ns ③ V_{OL}

MAX 500ns ④
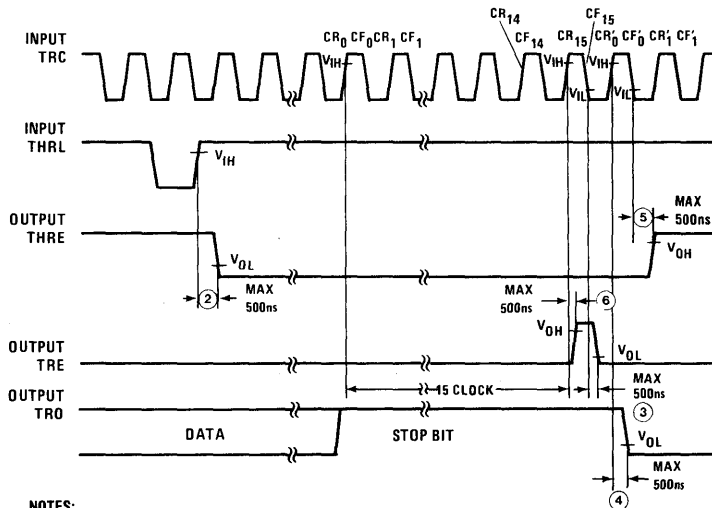
NOTES:

2-5, refer to Figure 5.

6. TRANSMITTER REGISTER EMPTY goes to high during 500ns Max. from the 15th rising edge of TRC after STOP BIT is enables.

Figure 7. Input After Master Reset
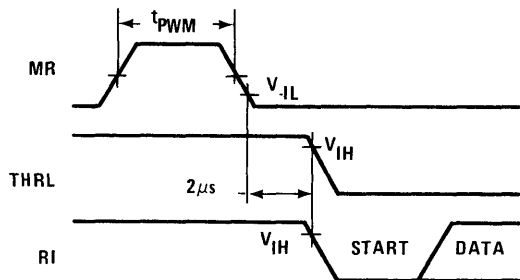
Figure 9. Status Flag Output
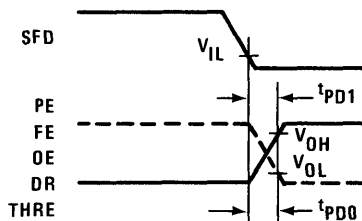
Figure 8. Control Register Load Cycle
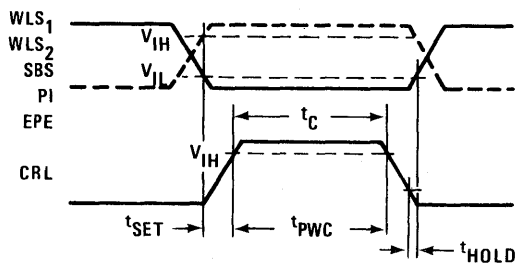
Figure 10. Data Output
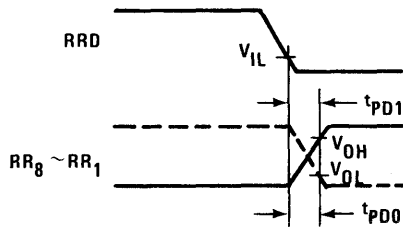
Figure 11. Transmitting Sequence Flowchart (Note that the S1602 can simultaneously transmit and receive at two different baud rates)
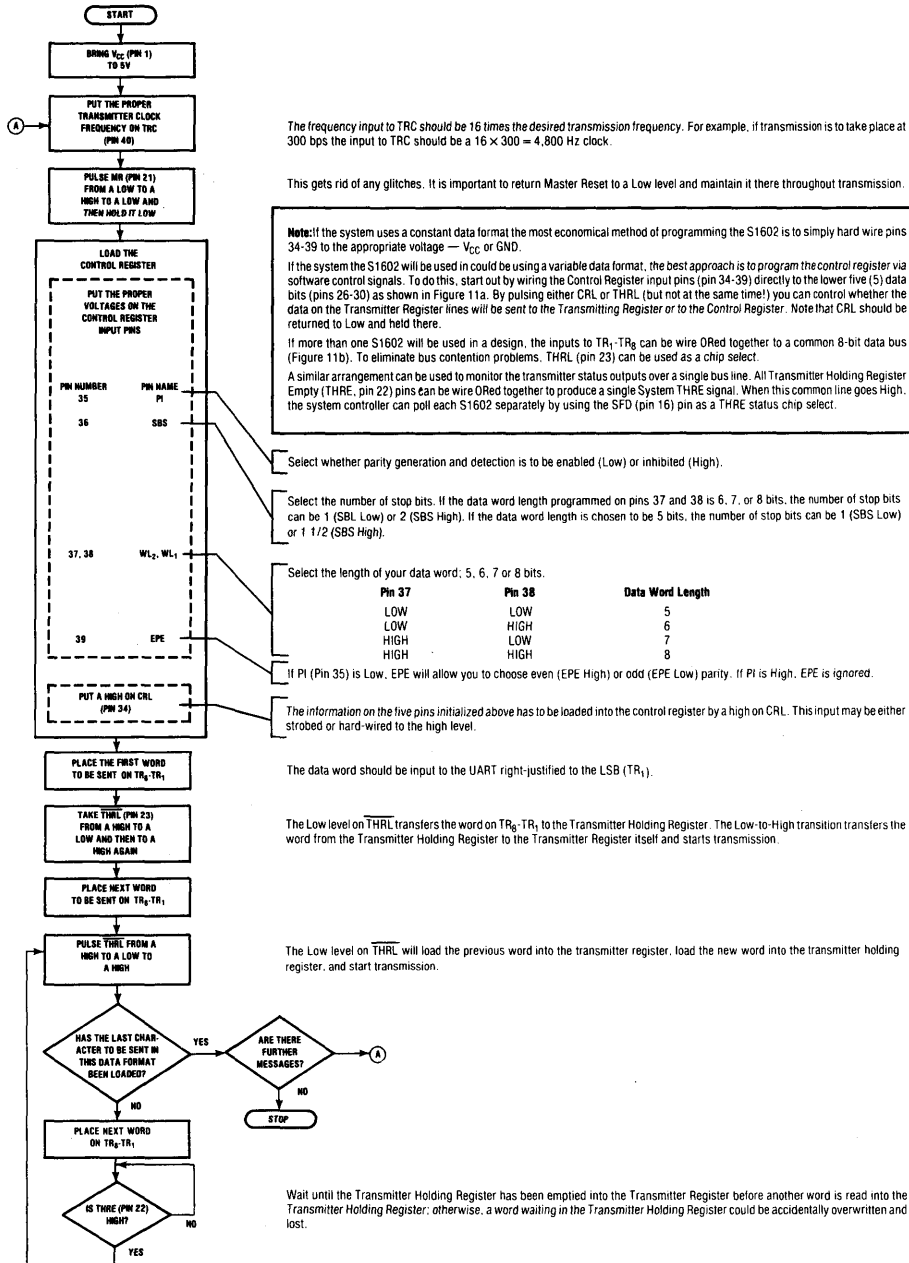
The frequency input to TRC should be 16 times the desired transmission frequency. For example, if transmission is to take place at 300 bps the input to TRC should be a $16 \times 300 = 4,800$ Hz clock.

This gets rid of any glitches. It is important to return Master Reset to a Low level and maintain it there throughout transmission.

Note: If the system uses a constant data format the most economical method of programming the S1602 is to simply hard wire pins 34-39 to the appropriate voltage — V_{CC} or GND.

If the system the S1602 will be used in could be using a variable data format, the best approach is to program the control register via software control signals. To do this, start out by wiring the Control Register input pins (pin 34-39) directly to the lower five (5) data bits (pins 26-30) as shown in Figure 11a. By pulsing either CRL or THRL (but not at the same time!) you can control whether the data on the Transmitter Register lines will be sent to the Transmitting Register or to the Control Register. Note that CRL should be returned to Low and held there.

If more than one S1602 will be used in a design, the inputs to TR_1-TR_8 can be wire ORed together to a common 8-bit data bus (Figure 11b). To eliminate bus contention problems, THRL (pin 23) can be used as a chip select.

A similar arrangement can be used to monitor the transmitter status outputs over a single bus line. All Transmitter Holding Register Empty (THRE, pin 22) pins can be wire ORed together to produce a single System THRE signal. When this common line goes High, the system controller can poll each S1602 separately by using the SFD (pin 16) pin as a THRE status chip select.

Select whether parity generation and detection is to be enabled (Low) or inhibited (High).

Select the number of stop bits. If the data word length programmed on pins 37 and 38 is 6, 7, or 8 bits, the number of stop bits can be 1 (SBL Low) or 2 (SBS High). If the data word length is chosen to be 5 bits, the number of stop bits can be 1 (SBS Low) or 1 1/2 (SBS High).

Select the length of your data word; 5, 6, 7 or 8 bits.

Pin 37	Pin 38	Data Word Length
LOW	LOW	5
LOW	HIGH	6
HIGH	LOW	7
HIGH	HIGH	8

If PI (Pin 35) is Low, EPE will allow you to choose even (EPE High) or odd (EPE Low) parity. If PI is High, EPE is ignored.

The information on the five pins initialized above has to be loaded into the control register by a high on CRL. This input may be either strobed or hard-wired to the high level.

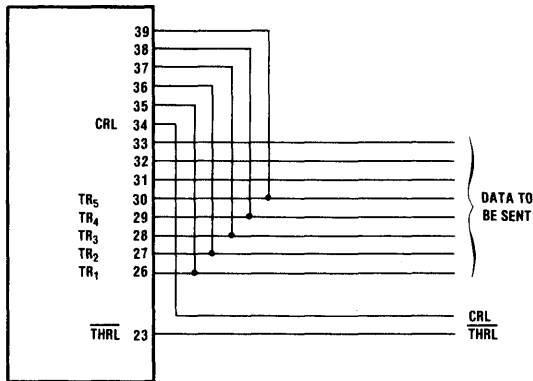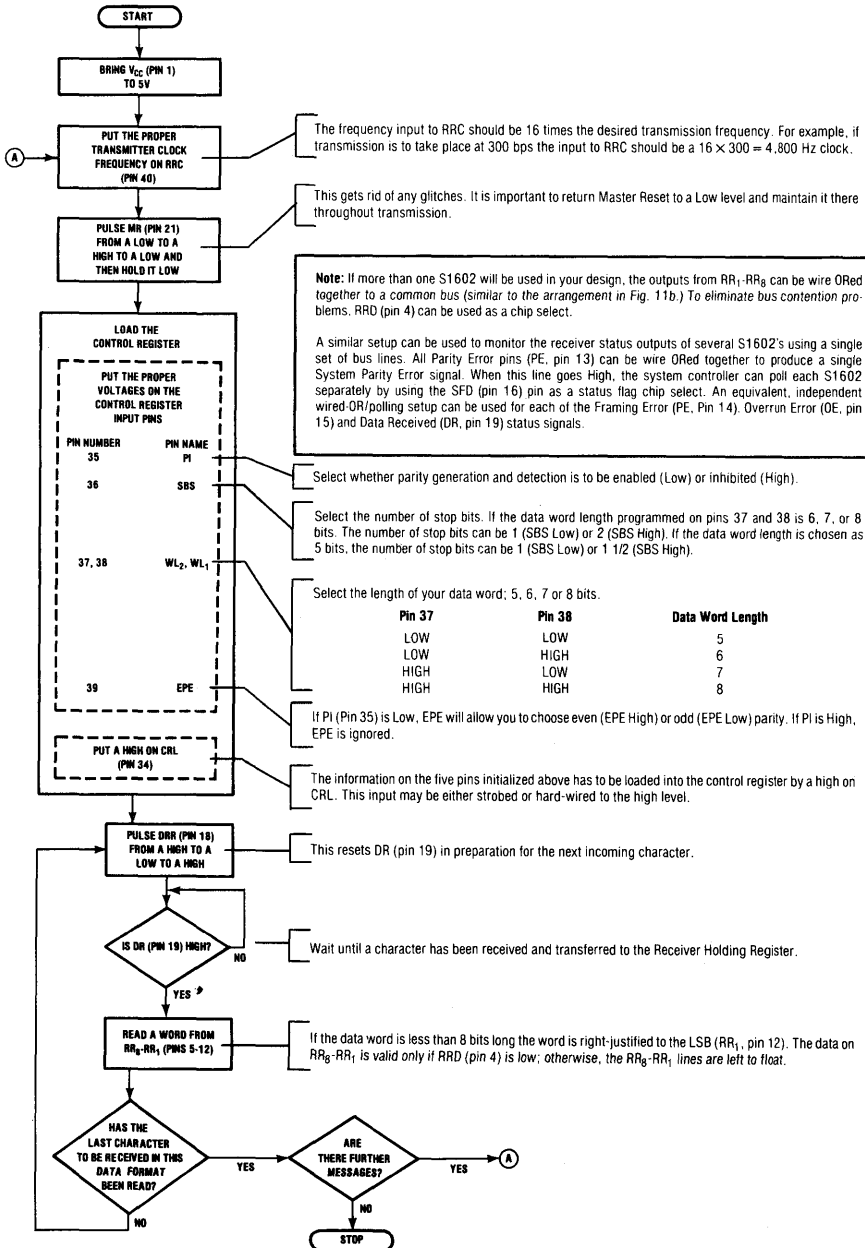The data word should be input to the UART right-justified to the LSB (TR_1).

The Low level on $\overline{THRL}$ transfers the word on TR_8-TR_1 to the Transmitter Holding Register. The Low-to-High transition transfers the word from the Transmitter Holding Register to the Transmitter Register itself and starts transmission.

The Low level on $\overline{THRL}$ will load the previous word into the transmitter register, load the new word into the transmitter holding register, and start transmission.

Wait until the Transmitter Holding Register has been emptied into the Transmitter Register before another word is read into the Transmitter Holding Register; otherwise, a word waiting in the Transmitter Holding Register could be accidentally overwritten and lost.

Flowchart boxes:

START

BRING V_{CC} (PIN 1) TO 5V

(A) PUT THE PROPER TRANSMITTER CLOCK FREQUENCY ON TRC (PIN 40)

PULSE MR (PIN 21) FROM A LOW TO A HIGH TO A LOW AND THEN HOLD IT LOW

LOAD THE CONTROL REGISTER

PUT THE PROPER VOLTAGES ON THE CONTROL REGISTER INPUT PINS

PIN NUMBER	PIN NAME
35	PI
36	SBS
37, 38	WL_2, WL_1
39	EPE

PUT A HIGH ON CRL (PIN 34)

PLACE THE FIRST WORD TO BE SENT ON TR_8-TR_1

TAKE THRL (PIN 23) FROM A HIGH TO A LOW AND THEN TO A HIGH AGAIN

PLACE NEXT WORD TO BE SENT ON TR_8-TR_1

PULSE THRL FROM A HIGH TO A LOW TO A HIGH

HAS THE LAST CHARACTER TO BE SENT IN THIS DATA FORMAT BEEN LOADED? — YES → ARE THERE FURTHER MESSAGES? → (A)

NO → STOP

NO → PLACE NEXT WORD ON TR_8-TR_1

IS THRE (PIN 22) HIGH? — NO

YES

5.109

Figure 11a.

If the system uses a constant data format the most economical method of programming the S1602 is to simply hard wire pins 34-39 to the appropriate voltage — V_{CC} or GND.

If the system the S1602 will be used in could be using a variable data format, the best approach is to program the control register via software control signals. To do this, start out by wiring the Control Register input pins (pin 34-39) directly to the lower five (5) data bits (pins 26-30) as shown above. By pulsing either CRL or THRL (but not at the same time!) you can control whether the data on the Transmitter Register lines will be sent to the Transmitting Register or to the Control Register. Note that CRL should be returned to Low and held there.

If more than one S1602 will be used in a design, the inputs to TR_1-TR_8 can be wire ORed together to a common 8-bit data bus to eliminate bus contention problems, THRL (pin 23) can be used as a chip select.

A similar arrangement can be used to monitor the transmitter status outputs over a single bus line. All Transmitter Holding Register Empty (THRE, pin 22) pins can be wire ORed together to produce a single System THRE signal. When this common line goes High, the system controller can poll each S1602 separately by using the SFD (pin 16) pin as a THRE status chip select.

Figure 11b.
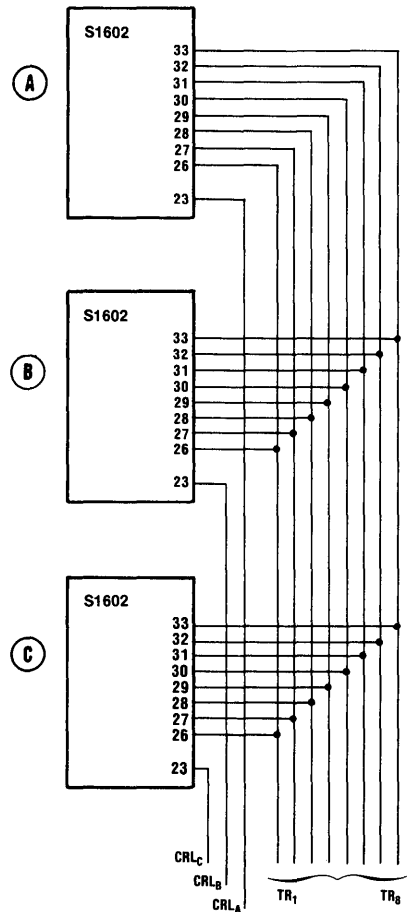
This example illustrates how to string the inputs to several 1602's together in a wired-OR situation, using a function enable pin as chip select.

A lay-out much like this one can be used to string the output signals (either data or status messages) from several 1602's together on a common bus.

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Figure 12. Receiving Sequence Flowchart
(Note that the S1602 can simultaneously transmit and receive at two different baud rates)

START

BRING V$_{CC}$ (PIN 1) TO 5V

PUT THE PROPER TRANSMITTER CLOCK FREQUENCY ON RRC (PIN 40)

The frequency input to RRC should be 16 times the desired transmission frequency. For example, if transmission is to take place at 300 bps the input to RRC should be a $16 \times 300 = 4,800$ Hz clock.

PULSE MR (PIN 21) FROM A LOW TO A HIGH TO A LOW AND THEN HOLD IT LOW

This gets rid of any glitches. It is important to return Master Reset to a Low level and maintain it there throughout transmission.

Note: If more than one S1602 will be used in your design, the outputs from RR$_1$-RR$_8$ can be wire ORed together to a common bus (similar to the arrangement in Fig. 11b.) To eliminate bus contention problems, RRD (pin 4) can be used as a chip select.

A similar setup can be used to monitor the receiver status outputs of several S1602's using a single set of bus lines. All Parity Error pins (PE, pin 13) can be wire ORed together to produce a single System Parity Error signal. When this line goes High, the system controller can poll each S1602 separately by using the SFD (pin 16) pin as a status flag chip select. An equivalent, independent wired-OR/polling setup can be used for each of the Framing Error (PE, Pin 14), Overrun Error (OE, pin 15) and Data Received (DR, pin 19) status signals.

LOAD THE CONTROL REGISTER

PUT THE PROPER VOLTAGES ON THE CONTROL REGISTER INPUT PINS

PIN NUMBER	PIN NAME
35	PI
36	SBS
37, 38	WL$_2$, WL$_1$
39	EPE

Select whether parity generation and detection is to be enabled (Low) or inhibited (High).

Select the number of stop bits. If the data word length programmed on pins 37 and 38 is 6, 7, or 8 bits, the number of stop bits can be 1 (SBS Low) or 2 (SBS High). If the data word length is chosen as 5 bits, the number of stop bits can be 1 (SBS Low) or 1 1/2 (SBS High).

Select the length of your data word; 5, 6, 7 or 8 bits.

Pin 37	Pin 38	Data Word Length
LOW	LOW	5
LOW	HIGH	6
HIGH	LOW	7
HIGH	HIGH	8

If PI (Pin 35) is Low, EPE will allow you to choose even (EPE High) or odd (EPE Low) parity. If PI is High, EPE is ignored.

PUT A HIGH ON CRL (PIN 34)

The information on the five pins initialized above has to be loaded into the control register by a high on CRL. This input may be either strobed or hard-wired to the high level.

PULSE DRR (PIN 18) FROM A HIGH TO A LOW TO A HIGH

This resets DR (pin 19) in preparation for the next incoming character.

IS DR (PIN 19) HIGH? NO

Wait until a character has been received and transferred to the Receiver Holding Register.

YES

READ A WORD FROM RR$_8$-RR$_1$ (PINS 5-12)

If the data word is less than 8 bits long the word is right-justified to the LSB (RR$_1$, pin 12). The data on RR$_8$-RR$_1$ is valid only if RRD (pin 4) is low; otherwise, the RR$_8$-RR$_1$ lines are left to float.

HAS THE LAST CHARACTER TO BE RECEIVED IN THIS DATA FORMAT BEEN READ? — YES → ARE THERE FURTHER MESSAGES? — YES → A

NO

NO

STOP

Universal Synchronous Receiver/Transmitter

Features

- ☐ **500kHz Data Rates**
- ☐ **Internal Sync Detection**
- ☐ **Fill Character Register**
- ☐ **Double Buffered Input/Output**
- ☐ **Bus Oriented Outputs**
- ☐ **5-8 Bit Characters**
- ☐ **Odd/Even or No Parity**
- ☐ **Error Status Flags**
- ☐ **Single Power Supply (+5V)**
- ☐ **Input/Output TTL-Compatible**

General Description

The S2350 Universal Synchronous Receiver Transmitter (USRT) is a single chip MOS/LSI device that totally replaces the serial-to-parallel and parallel-to-serial conversion logic required to interface a word parallel controller or data terminal to a bit-serial, synchronous communication network.

The USRT consists of separate receiver and transmitter sections with independent clocks, data lines and status. Common with the transmitter and receiver are word length and parity mode. Data is transmitted and received in a NRZ format at a rate equal to the respective input clock frequency.

Block Diagram

Pin Configuration

AMI
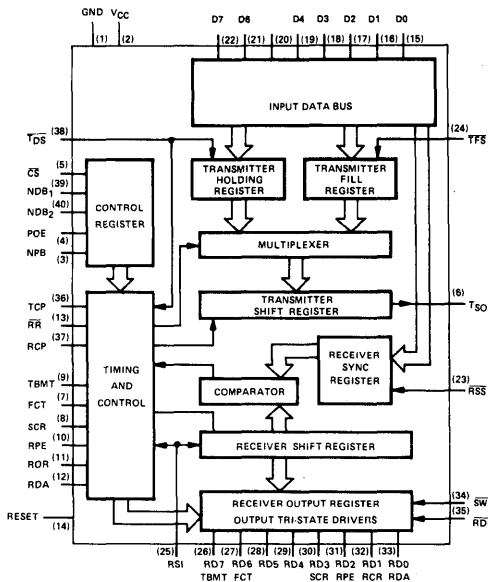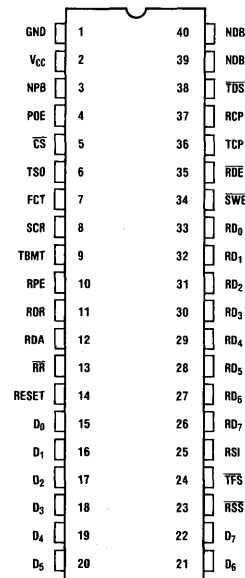
Data messages are transmitted as a contiguous character stream, bit synchronous with respect to a clock and character synchronous with respect to framing or "sync" characters initializing each message. The USRT receiver compares the contents of the internal Receiver Sync Register with the incoming data stream in a bit transparent mode. When a compare is made, the receiver becomes character synchronous formatting a 5, 6, 7, or 8-bit character for output each character time. The receiver has an output buffer register allowing a full character time to transfer the data out. The receiver status outputs indicate received data available (RDA), receiver overrun (ROR), receive parity error (RPE) and sync character received (SCR). Status bits are available on individual output lines and can also be multiplexed onto the output data lines for bus organized systems. The data lines have tri-state outputs.

The USRT transmitter outputs 5, 6, 7, or 8-bit characters with correct parity at the transmitter serial output

(TSO). The transmitter is buffered to allow a full character time to respond to a transmitter buffer empty (TBMT) request for data. Data is transmitted in a NRZ format changing on the positive transition of the transmitter clock (TCP). The character transmitter fill register is inserted into the data message if a data character is not loaded into the transmitter after a TBMT request.

Typical Applications

☐ Computer Peripherals
☐ Communication Concentrators
☐ Integrated Modems
☐ High Speed Terminals
☐ Time Division Multiplexing
☐ Industrial Data Transmission

S6800

Absolute Maximum Ratings

Ambient Temperature Under Bias . . . . 0°C to +70°C
Storage Temperature . . . . −65°C to +150°C
Positive Voltage on any Pin with Respect to GROUND . . . . +7V
Negative Voltage on any Pin with Respect to GROUND . . . . −0.5V
Power Dissipation 0.75W

D.C. (Static) Electrical Characteristics* ($V_{CC} = 5.0V \pm 5\%$; $T_A = 0°C$ to $+70°C$ unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
V_{IH}	Input High Voltage	2.0		V_{CC}	V	
V_{IL}	Input Low Voltage	−0.5		+0.8	V	
I_{IL}	Input Leakage Current			10	μA	$V_{IN} = O_{TO} V_{CC}$ V
V_{OH}	Output High Voltage	2.4			V	$I_{OH} = -100\mu A$
V_{OL}	Output Low Voltage			+0.4	V	$I_{OL} = 1.6mA$
C_{IN}	Input Capacitance			10	pF	$V_{IN} = 0V$; f = 1.0MHz
C_{OUT}	Output Capacitance			12	pF	$V_{IN} = 0V$; f = 1.0MHz
I_{CC}	V_{CC} Supply Current			100	mA	No Load; $V_{CC} = 5.25V$

*Electrical characteristics included in this advanced product description are objective specifications and may be subject to change.

A.C. (Dynamic) Electrical Characteristics* ($V_{CC} = 5.0V \pm 5\%$; $T_A = 0°C$ to $+70°C$ unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
TCP, RCP	Clock Frequency	DC		500	kHz	

Input Pulse Widths

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
P_{TCP}	Transmit Clock	900			nsec	$CL = 20pF$
P_{RCP}	Receive Clock	900			nsec	1TTL Load
P_{RST}	Reset	500			nsec	
P_{TDS}	Transmit Data Strobe	200			nsec	
P_{TFS}	Transmit Fill Strobe	200			nsec	
P_{RSS}	Receive Sync Strobe	200			nsec	
P_{CS}	Control Strobe	200			nsec	
P_{RDE}	Receive Data Enable	400			nsec	Note 1
P_{SWE}	Status Word Enable	400			nsec	Note 1
P_{RR}	Receiver Restart	500			nsec	

Switching Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
T_{TSO}	Delay, TCP Clock to Serial Data Out			700	nsec	
T_{TBMT}	Delay, TCP Clock to TBMT Output			1.4	μsec	
T_{TBMT}	Delay, TDS to TBMT			700	nsec	
T_{STS}	Delay, SWE to Status Reset			700	nsec	
T_{RDO}	Delay, SWE, RDE to Data Outputs			400	nsec	1TTL Load
T_{HRDO}	Hold Time SWE, RDE to Off State			400	nsec	$C_L = 130pF$
T_{DTS}	Data Set Up Time TDS, TFS, RSS, CS	0			nsec	
T_{DTH}	Data Hold Time TDS	700			nsec	
T_{DTI}	Data Hold Time TFS, RSS	200			nsec	
T_{CNS}	Control Set Up Time NDB1, NDB2, NPB, POE	0			nsec	
T_{CNH}	Control Hold Time NDB1, NDB2, NPB, POE	200			nsec	
T_{RDA}	Delay RDE to RDA Output	700			nsec	

NOTE 1: Required to reset status and flags.

Figure 1. Timing Waveform
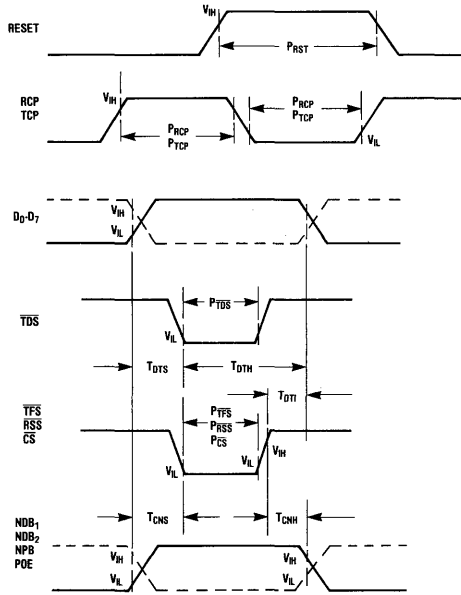
Figure 2. Timing Waveform

S6800

AMI.
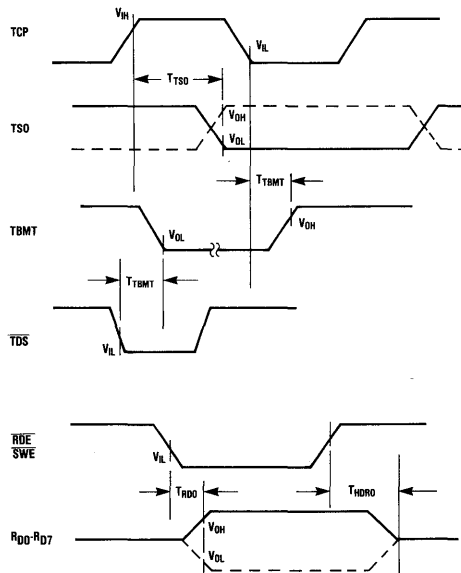
Figure 3. Transmitter Timing Diagram
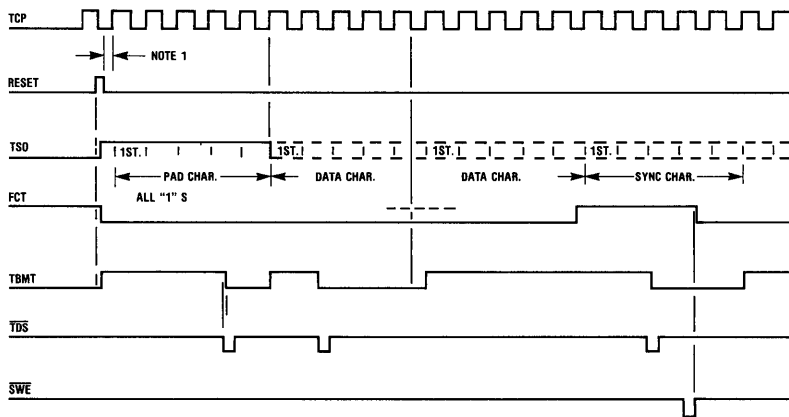
NOTE 1 DATA TRANSMISSION WILL START ON THE FIRST LOW TO HIGH TRANSITION OF TCP AFTER
RESET IS LOW. THE INITIAL RESET PULSE SHOULD NOT OCCUR UNTIL 100 MICROSECONDS
AFTER POWER IS APPLIED.

Figure 4. Receiver Timing Diagram
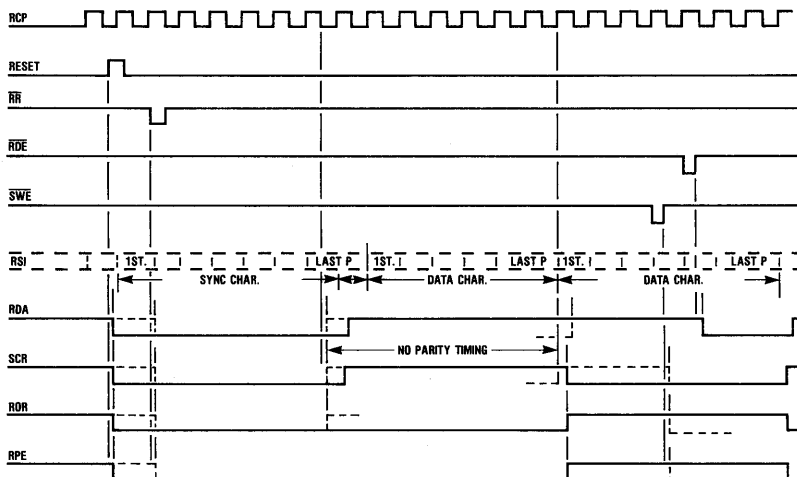
Pin Definitions

Pin	Label	Function
(1)	GND	Ground
(2)	V_{CC}	+ 5 Volts ± 5%
(14)	RESET	MASTER RESET. A V_{IH} initializes both the receiver and transmitter. The Transmitter Shift Register is set to output a character of all logic 1's. FCT is reset to V_{OL} and TBMT set to V_{OH} indicating the Transmitter Holding Register is empty. The receiver status is initialized to a V_{OL} on RPE, SCR, and RDA. The sync character detect logic is inhibited until a RR pulse is received.
(15−22)	D0−D7	DATA INPUTS. Data on the eight data lines are loaded into the Transmitter Holding Register by $\overline{TDS}$, the Transmitter Fill Register by $\overline{TFS}$, and the Receiver Sync Register by $\overline{RSS}$. The character is right justified with the LSB at D0. For word lengths less than 8 bits, the unused inputs are ignored. Data transmission is LSB first.
(38)	$\overline{TDS}$	TRANSMIT DATA STROBE. A V_{IL} loads data on D0-D7 into the Transmitter Holding Register and resets TBMT to a V_{OL}.
(24)	$\overline{TFS}$	TRANSMIT FILL STROBE. A V_{IL} loads data on D0-D7 into the Transmitter Fill Register. The character in the Transmitter Fill Register is transmitted whenever a new character is not loaded in the allotted time.
(23)	$\overline{RSS}$	RECEIVER SYNC STROBE. A V_{IL} loads data on D0-D7 into the Receiver Sync Register. SCR is set to V_{OH} whenever data in the Receiver Shift Register compares with the character in the Receiver Sync Register.
(9)	TBMT	TRANSMIT BUFFER EMPTY. A V_{OH} indicates the data in the Transmitter Holding Register has been transferred to the Transmitter Shift Register and new data may be loaded. TBMT is reset to V_{OL} by a V_{IL} on $\overline{TDS}$. A V_{IH} on RESET sets TBMT to a V_{OH}. TBMT is also multiplexed onto the RD7 output (26) when $\overline{SWE}$ is at V_{IL} and $\overline{RDE}$ is at V_{IH}.
(6)	TSO	TRANSMITTER SERIAL OUTPUT. Data entered on D0-D7 are transmitted serially, least significant bit first, on TSO at a rate equal to the Transmit Clock frequency, TCP. Source of the data to the transmitter shift register is the Transmitter Holding Register or Transmitter Fill Register.
(36)	TCP	TRANSMIT CLOCK. Data is transmitted on TSO at the frequency of the TCP input in a NRZ format. A new data bit is started on each negative to positive transition (V_{IL} to V_{IH}) of TCP.
(26−33)	RD7−RD0	RECEIVED DATA OUTPUTS RD0-RD7 contain data from the Receiver Output Register or selective status conditions depending on the state of $\overline{SWE}$ and $\overline{RDE}$ per the following table:

(34)	(35)	(33)	(32)	(31)	(30)	(39)	(28)	(27)	(26)
$\overline{SWE}$	$\overline{RDE}$	RD0	RD1	RD2	RD3	RD4	RD5	RD6	RD7
V_{IL}	V_{IL}	X	X	X	X	X	X	X	X
V_{IL}	V_{IH}	RDA	ROR	RPE	SCR	V_{OL}	V_{OL}	FCT	TBMT
V_{IH}	V_{IL}	DB0	BD1	DB2	DB3	DB4	DB5	DB6	DB7
V_{IH}	V_{IH}	X	X	X	X	X	X	X	X

X — Output is in the OFF or Tri-State condition
DB0 — LSB of Receiver Output Register
DB7 — MSB of Receiver Output Register
The two unused outputs are held at V_{OL} in the output status condition.

Pin Definitions (continued)

Pin	Label	Function
(35)	$\overline{\text{RDE}}$	RECEIVE DATA ENABLE. A V_{IL} enables the data in the Receiver Output Register onto the output data lines RD0 – RD7. The trailing edge (V_{IL} to V_{IH} transition) of $\overline{\text{RDE}}$ resets RDA to the V_{OL} condition.
(7)	FCT	FILL CHARACTER TRANSMITTED. A V_{OH} on FCT indicates data from the Transmitter Fill Register has been transferred to the Transmitter Shift Register.
		FCT is reset to V_{OL} when data is transferred from the Transmitter Holding Register to the Transmitter Shift Register, or on the trailing edge (V_{IL} to V_{IH}) of the $\overline{\text{SWE}}$ pulse, or when RESET is V_{IH}.
		FCT is multiplexed onto the RD6 output (27) when $\overline{\text{SWE}}$ is at V_{IL} and $\overline{\text{RDE}}$ is at V_{IH}.
(25)	RSI	RECEIVER SERIAL INPUT. Serial data is clocked into the Receiver Shift Register, least significant bit first, on RSI at a rate equal to the Receive Clock frequency RCP.
(37)	RCP	RECEIVE CLOCK. Data is transferred from RSI input to the Receiver Shift Register at the frequency of the RCP input. Each data bit is entered on the positive to negative transition (V_{IH} to V_{IL}) of RCP.
(12)	RDA	RECEIVED DATA AVAILABLE. A V_{OH} indicates a character has been transferred from the Receiver Shift Register to the Receiver Output Register.
		RDA is reset to V_{OL} on the trailing edge (V_{IL} to V_{IH} transition) of $\overline{\text{RDE}}$, by a V_{IL} on $\overline{\text{RR}}$ or a V_{IH} on RESET.
		RDA is multiplexed onto the RD0 output (33) when $\overline{\text{SWE}}$ is V_{IL} and $\overline{\text{RDE}}$ is V_{IH}.
(8)	SCR	SYNC CHARACTER RECEIVED. A V_{OH} indicates the data in the Receiver Shift Register is identical to the data in the Receiver Sync Register.
		SCR is reset to a V_{OL} when the character in the Receiver Shift Register does not compare to the Receiver Sync Register, on the trailing edge (V_{IL} to V_{IH} transition) of $\overline{\text{SWE}}$, by a V_{IL} on $\overline{\text{RR}}$ or a V_{IH} on RESET.
		SCR is multiplexed onto the RD3 output (30) when $\overline{\text{SWE}}$ is a V_{IL} and $\overline{\text{RDE}}$ is V_{IH}.
(34)	$\overline{\text{SWE}}$	STATUS WORD ENABLE. A V_{IL} enables the internal status conditions onto the output data lines RD0 – RD7.
		The trailing edge of $\overline{\text{SWE}}$ pulse resets FCT, ROR, RPE, and SCR to V_{OL}.
(11)	ROR	RECEIVER OVERRUN. A V_{OH} indicates data has been transferred from the Receiver Shift Register to the Receiver Output Register when RDA was still set to V_{OH}. The last data in the Output Register is lost.
		ROR is reset by the trailing edge (V_{IL} to V_{IH}) of $\overline{\text{SWE}}$, a V_{IL} on $\overline{\text{RR}}$, a V_{IH} on RESET or a V_{OL} to V_{OH} transition of RDA.
		ROR is multiplexed onto the RD1 output (32) when $\overline{\text{SWE}}$ is V_{IL} and $\overline{\text{RDE}}$ is V_{IH}.
(10)	RPE	RECEIVER PARITY ERROR. A V_{OH} indicates the accumulated parity on the received character transferred to the Output Register does not agree with the parity selected by POE. RPE is reset with the next received character with correct parity, the trailing edge (V_{IL} to V_{IH}) of $\overline{\text{SWE}}$, a V_{IL} on $\overline{\text{RR}}$ or a V_{IH} on RESET.
		RPE is multiplexed onto the RD2 output (31) when $\overline{\text{SWE}}$ is V_{IL} and $\overline{\text{RDE}}$ is V_{IH}.

Pin Definitions (continued)

Pin	Label	Function
(13)	$\overline{RR}$	RECEIVER RESTART. A V_{IL} resets the receiver section by clearing the status RDA, SCR, ROR, and RPE to V_{OL}. The trailing edge of $\overline{RR}$ (V_{IL} to V_{IH}) also puts the receiver in a bit transparent mode to search for a comparison, each bit time, between the contents of the Receiver Shift Register and the Receiver Sync Register. The number of data bits per character for the comparison is set by NDB1 and NDB2. After a compare is made SCR is set to V_{OH}, the sync character is transferred to the Receiver Output Register, and the receiver enters a word synchronous mode framing an input character each word time. **NOTE:** Parity is not checked on the first sync character but is enabled for every succeeding character.
(39)	NDB1	NUMBER DATA BITS. The number of Data Bits per character are determined by NDB1 and NDB2. The number of data bits does not include the parity bit.

NDB2	NDB1	CHARACTER LENGTH
V_{IL}	V_{IL}	5 Bits
V_{IL}	V_{IH}	6 Bits
V_{IH}	V_{IL}	7 Bits
V_{IH}	V_{IH}	8 Bits

Pin	Label	Function
		For character length less than 8 bits, unused inputs are ignored and unused outputs are held to V_{OL}. Data is always right justified with D0 and RD0 being the least significant bits.
(3)	NPB	NO PARITY BIT. A V_{IH} eliminates generation of a parity bit in the transmitter and checking of parity in the receiver. With parity disabled, the RPE status bit is held at V_{OL}.
(4)	POE	PARITY ODD/EVEN. A V_{IH} directs both the transmitter and receiver to operate with even parity. A V_{IL} forces parity operation. NPB must be V_{IL} for parity to be enabled.
(5)	$\overline{CS}$	CONTROL STROBE. A V_{IL} loads the control inputs NDB1, NDB2, POE, and NPB into the Control Register. For static operation, $\overline{CS}$ can be tied directly to ground.

S6800

PERIPHERAL INTERFACE
ADAPTER (PIA)

Features

☐ 8-Bit Bidirectional Bus for Communication with the MPU

☐ Two Bidirectional 8-Bit Buses for Interface to Peripherals

☐ Two Programmable Control Registers

☐ Two Programmable Data Direction Registers

☐ Four Individually-Controlled Interrupt Input Lines; Two Usable as Peripheral Control Outputs

☐ Handshake Control Logic for Input and Output Peripheral Operation

☐ High-Impedance Three-State and Direct Transistor Drive Peripheral Lines

☐ Program Controlled Interrupt and Interrupt Disable Capability

☐ CMOS Compatible Peripheral Lines

☐ Two TTL Drive Capability on all A and B Side Buffers

☐ TTL Compatible

☐ Static Operation

General Description

The S6821/S68A21/S68B21 are peripheral Interface Adapters that provide the universal means of interfacing peripheral equipment to the S6800/S68A00/S68B00 Microprocessing Units (MPU). This device is capable of interfacing the MPU to peripherals through two 8-bit bidirectional peripheral data buses and four control lines. No external logic is required for interfacing to most peripheral devices.

The functional configuration of the PIA is programmed by the MPU during system initialization Each of the peripheral data lines can be programmed to act as an

Block Diagram

Pin Configuration
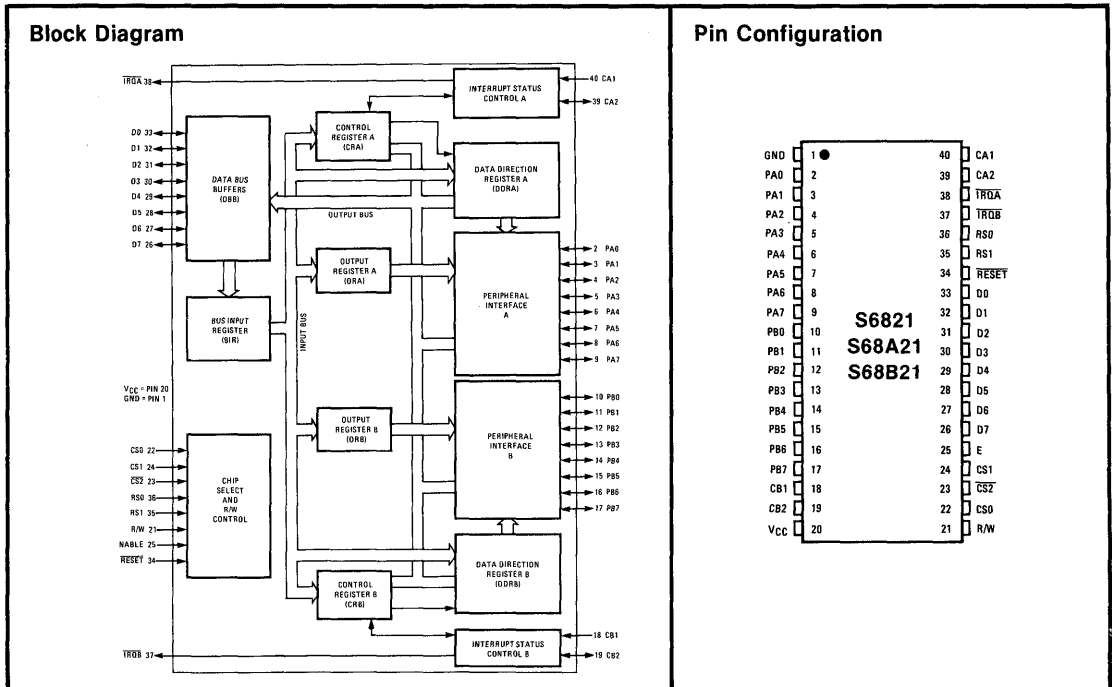
General Description (Continued)

input or output, and each of the four control/interrupt lines may be programmed for one of several control modes. This allows a high degree of flexibility in the overall operation of the interface.

The PIA interfaces to the S6800/S68A00/S68B00 MPUs with an eight-bit bidirectional data bus, three chip select lines, two register select lines, two interrupt request lines, read/write line, enable line and reset line. These signals, in conjunction with S6800/S68A00/S68B00 VMA output, permit the MPU to have complete control over the PIA. VMA may be utilized to gate the input signals to the PIA.

Absolute Maximum Ratings:

Symbol	Rating	Value	Unit
V_{CC}	Supply Voltage	-0.3 to $+7.0$	Vdc
V_{IN}	Input Voltage	-0.3 to $+7.0$	Vdc
T_A	Operating Temperature Range	$0°$ to $+70°$	°C
T_{stg}	Storage Temperature Range	$-55°$ to $+150°$	°C
θ_{ja}	Thermal Resistance	82.5	°C/W

Note:
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Electrical Characteristics

$V_{CC} = 5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = T_L$ to T_H unless otherwise noted.

Symbol	Characteristic	Min.	Typ.	Max.	Unit	Conditions
Bus Control Inputs (R/$\overline{W}$, Enable, $\overline{Reset}$, RS0, RS1, CS0, CS1, $\overline{CS2}$)						
V_{IH}	Input High Voltage	$V_{SS}+2.0$	—	V_{CC}	Vdc	
V_{IL}	Input Low Voltage	$V_{SS}-0.8$	—	$V_{SS}+0.8$	Vdc	
I_{IN}	Input Leakage Current	—	1.0	2.5	μAdc	$V_{IN}=0$ to 5.25 Vdc
C_{IN}	Capacitance	—	—	7.5	pF	$V_{IN}=0$, $T_A=25°C$, f=1.0MHz
Interrupt Outputs ($\overline{IRQA}$, $\overline{IRQB}$)						
V_{OL}	Output Low Voltage	—	—	$V_{SS}+0.4$	Vdc	$I_{LOAD}=3.2$ mAdc
I_{LOH}	Output Leakage Current (Off State)	—	1.0	10	μAdc	$V_{OH}=2.4$ Vdc
C_{OUT}	Capacitance	—	—	5.0	pF	$V_{IN}=0$, $T_A=25°C$, f=1.0MHz
Data Bus (D0–D7)						
V_{IH}	Input High Voltage	$V_{SS}+2.0$	—	V_{CC}	Vdc	
V_{IL}	Input Low Voltage	$V_{SS}-0.3$	—	$V_{SS}+0.8$	Vdc	
I_{TSI}	Three State (Off State) Input Current	—	2.0	10	μAdc	$V_{IN}=0.4$ to 2.4 Vdc
V_{OH}	Output High Voltage	$V_{SS}+2.4$	—	—	Vdc	$I_{LOAD}=-205\mu$Adc
V_{OL}	Output Low Voltage	—	—	$V_{SS}+0.4$	Vdc	$I_{LOAD}=1.6$mAdc
C_{IN}	Capacitance	—	—	12.5	pF	$V_{IN}=0$, $T_A=25°C$ f=1.0MHz

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Electrical Characteristics (Continued)

Symbol	Characteristic		Min.	Typ.	Max.	Unit	Conditions
Peripheral Bus (PA0–PA7, PB0–PB7, CA1, CA2, CB1, CB2)							
I_{IN}	Input Leakage Current	R/$\overline{W}$, $\overline{Reset}$, RS0, CS0, CS1, $\overline{CS2}$, CA1, CB1, Enable		1.0	2.5	μAdc	$V_{IN}=0$ to 5.25 Vdc
I_{TSI}	Three-State (Off State) Input Current	PB0–PB7, CB2		2.0	10	μAdc	$V_{IN}=0.4$ to 2.4 Vdc
I_{IH}	Input High Current	PA0–PA7, CA2	−200	−400		μAdc	$V_{IH}=2.4$ Vdc
I_{OH}	Darlington Drive Current	PB0–PB7, CB2	−1.0		.10	mAdc	$V_O=1.5$ Vdc
I_{IL}	Input Low Current	PA0–PA7, CA2		−1.3	−2.4	mAdc	$V_{IL}=0.4$Vdc
V_{OH}	Output High Voltage PA0–P7, PB0–PB7, CA2, CB2 PA0–PA7, CA2		$V_{SS}+2.4$ $V_{CC}-1.0$			Vdc	$I_{LOAD}=-200$μAdc $I_{LOAD}=-10$μAdc
V_{OL}	Output Low Voltage				$V_{SS}+0.4$	Vdc	$I_{LOAD}=3.2$mAdc
C_{IN}	Capacitance				10	pF	$V_{IN}=0$, $T_A=25°C$, $f=1.0$MHz
Power Requirements							
P_D	Power Dissipation				550	mW	

A.C. (Dynamic) Characteristics Loading $=30$pF and one TTL load for PA0–PA7, PB0–PB7, CA2, CB2
$=130$pF and one TTL load for D0–D7, $\overline{IRQA}$, $\overline{IRQB}$
($V_{CC}=+5.0$V$\pm5\%$, $T_A=0°C$ to $+70°C$ unless otherwise noted)

Peripheral Timing Characteristics: $V_{CC}-5.0$V$\pm5\%$, $V_{SS}=0$V, $T_A=T_L$ to T_H unless otherwise specified

Symbol	Parameter	S6821		S68A21		S68B21		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{PDSU}	Peripheral Data Setup Time	200		135		100		ns
t_{PDH}	Peripheral Data Hold Time	0		0		0		ns
t_{CA2}	Delay Time, Enable Negative Transition to CA2 Negative Transition		1.0		0.670		0.5	μs
t_{RS1}	Delay Time, Enable Negative Transition to CA2 Positive Transition		1.0		0.670		0.50	μs
t_r, t_f	Rise and Fall Times for CA1 and CA2 Input Signals		1.0		1.0		1.0	μs
t_{RS2}	Delay Time from CA1 Active Transition to CA2 Positive Transition		2.0		1.35		1.0	μs
t_{PDW}	Delay Time, Enable Negative Transition to Peripheral Data Valid		1.0		0.670		0.5	μs
t_{CMOS}	Delay Time, Enable Negative Transition to Peripheral CMOS Data Valid PA0-PA7, CA2		2.0		1.35		1.0	μs

Peripheral Timing Characteristics (Continued)

Symbol	Parameter	S6821 Min.	S6821 Max.	S68A21 Min.	S68A21 Max.	S68B21 Min.	S68B21 Max.	Units
t_{CB2}	Delay Time, Enable Positive Transition to CB2 Negative Transition		1.0		0.670		0.5	μs
t_{DC}	Delay Time, Peripheral Data Valid to CB2 Negative Transition	2.0		20		20		ns
t_{RS1}	Delay Time, Enable Positive Transition to CB2 Positive Transition		1.0		0.670		0.5	μs
PW$_{CT}$	Peripheral Control Output Pulse Width, CA2/CB2	550		550		550		ns
t_r, t_f	Rise and Fall Times for CB1 and CB2 Input Signals		1.0		1.0		1.0	μs
t_{RS2}	Delay Time, CB1 Active Transition to CB2 Positive Transition		2.0		1.35		1.0	μs
t_{IR}	Interrupt Release Time, $\overline{IRQA}$ and $\overline{IRQB}$		1.60		1.1		0.85	μs
t_{RS3}	Interrupt Response Time		1.0		1.0		1.0	μs
PW$_I$	Interrupt Input Pulse Width	500		500		500		ns
t_{RL}	Reset Low Time*	1.0		0.66		0.5		μs

*The Reset line must be high a minimum of 1.0μs before addressing the PIA.

Figure 1. Enable Signal Characteristics
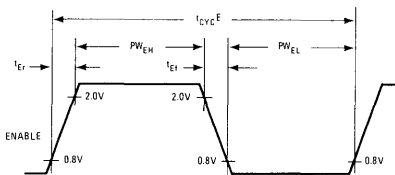
Figure 2. Bus Read Timing Characteristics (Read Information from PIA)
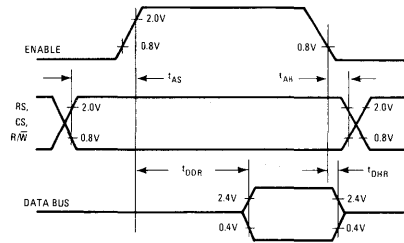
Figure 3. Bus Write Timing Characteristics (Write Information into PIA)
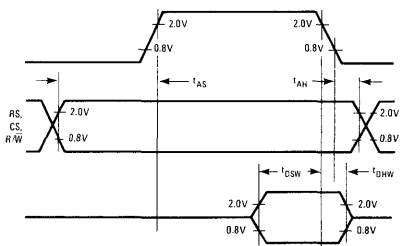
Figure 4. Bus Timing Test Loads
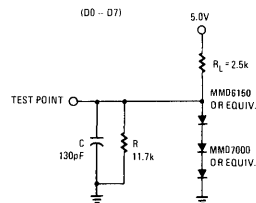
S6800

Bus Timing Characteristics ($V_{CC} = +5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = T_L$ to T_H unless otherwise noted.)

Symbol	Parameter	S6821		S68A21		S68B21		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{cyc(E)}$	Enable Cycle Time	1000		666		500		ns
PW_{EH}	Enable Pulse Width, High	450		280		220		ns
PW_{EL}	Enable Pulse Width, Low	430		280		210		ns
t_{Er}, t_{Ef}	Enable Pulse Rise and Fall Times		25		25		25	ns
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{DDR}	Data Delay Time, Read		320		220		180	ns
t_{DHR}	Data Hold Time, Read	10		10		10		ns
t_{DSW}	Data Setup Time, Write	195		80		60		ns
t_{DHW}	Data Hold Time, Write	10		10		10		ns

Figure 5. TTL Equiv. Test Load	Figure 6. CMOS Equiv. Test Load	Figure 7. NMOS Equiv. Test Load

Figure 5. TTL Equiv. Test Load
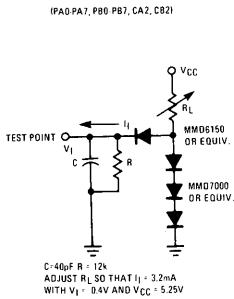
Figure 6. CMOS Equiv. Test Load
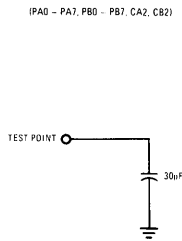
Figure 7. NMOS Equiv. Test Load
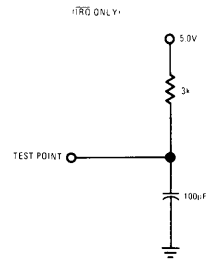
Figure 8. Peripheral Data Setup and Hold Times (Read Mode)
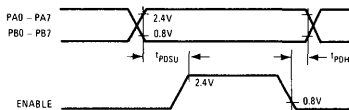
Figure 9. CA2 Delay Time (Read Mode; CRA-5 = CRA-3 = 1, CRA-4 = 0)
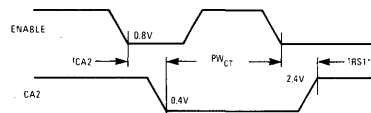
*Assumes part was deselected during the previous E pulse.

Figure 10. CA2 Delay Time
(Read Mode; CRA-5 = 1, CRA-3 = CRA-4 = 0)
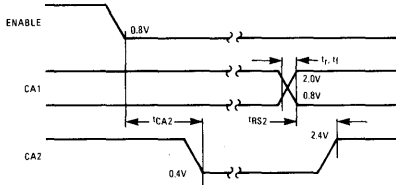
Figure 11. Peripheral CMOS Data Delay Times
(Write Mode; CRA-5 = CRA-3 = 1, CRA-4 = 0)
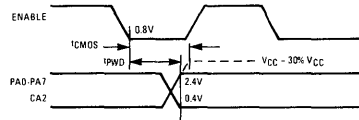
Figure 12. Peripheral Data and CB2 Delay Times
(Write Mode; CRB-5 = CRB-3 = 1, CRB-4 = 0)
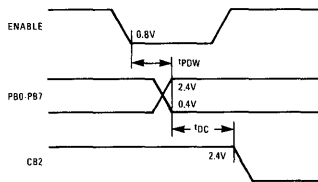
CB2 Note:
CB2 goes low as a result of the positive transition of Enable.

Figure 13. CB2 Delay Time
(Write Mode; CRB-5 = CRB-3 = 1. CRB-4 = 0)
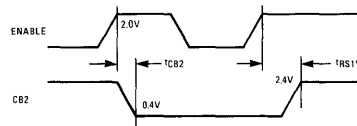
Figure 14. CB2 Delay Time
(Write Mode; CRB-5 = 1, CRB-3 = CRB-4 = 0)
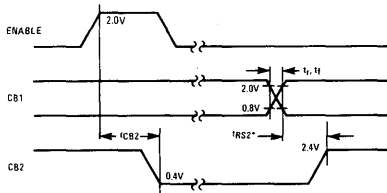
*Assumes part was deselected during any previous E pulse.

Figure 15. Interrupt Pulse Width and IRQ Response
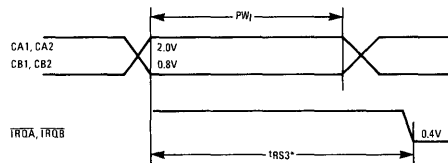
*Assumes Interrupt Enable Bits are set.

Figure 16. IRQ Release Time
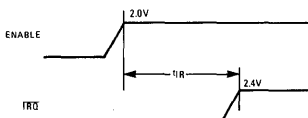
Figure 17. Reset Low Time.
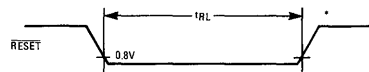
*The Reset line must be a V_{IH} for a minimum of 1.0µs
before addressing the PIA.

S6800

AMI
AMERICAN MICROSYSTEMS, INC.

S68H21

PERIPHERAL INTERFACE ADAPTER (PIA)

Features

- 8-Bit Bidirectional Bus for Communication with the MPU
- Two Bidirectional 8-Bit Buses for Interface to Peripherals
- Two Programmable Control Registers
- Two Programmable Data Direction Registers
- Four Individually-Controlled Interrupt Input Lines: Two Usable as Peripheral Control Outputs
- Handshake Control Logic for Input and Output Peripheral Operation
- High-Impedance Three-State and Direct Transistor Drive Peripheral Lines
- Program Controlled Interrupt and Interrupt Disable Capability
- CMOS Compatible Peripheral Lines

General Description

The S68H21 is a peripheral Interface Adapter that provides the universal means of interfacing peripheral equipment to the S68H00 Microprocessing Unit (MPU). This device is capable of interfacing the MPU to peripherals through two 8-bit bidirectional peripheral data buses and four control lines. No external logic is required for interfacing to most peripheral devices.

The functional configuration of the PIA is programmed by the MPU during system initialization. Each of the peripheral data lines can be programmed to act as an input or output, and each of the four control/interrupt lines may be programmed for one of several control modes. This allows a high degree of flexibility in the overall operation of the interface.

Block Diagram

Pin Configuration
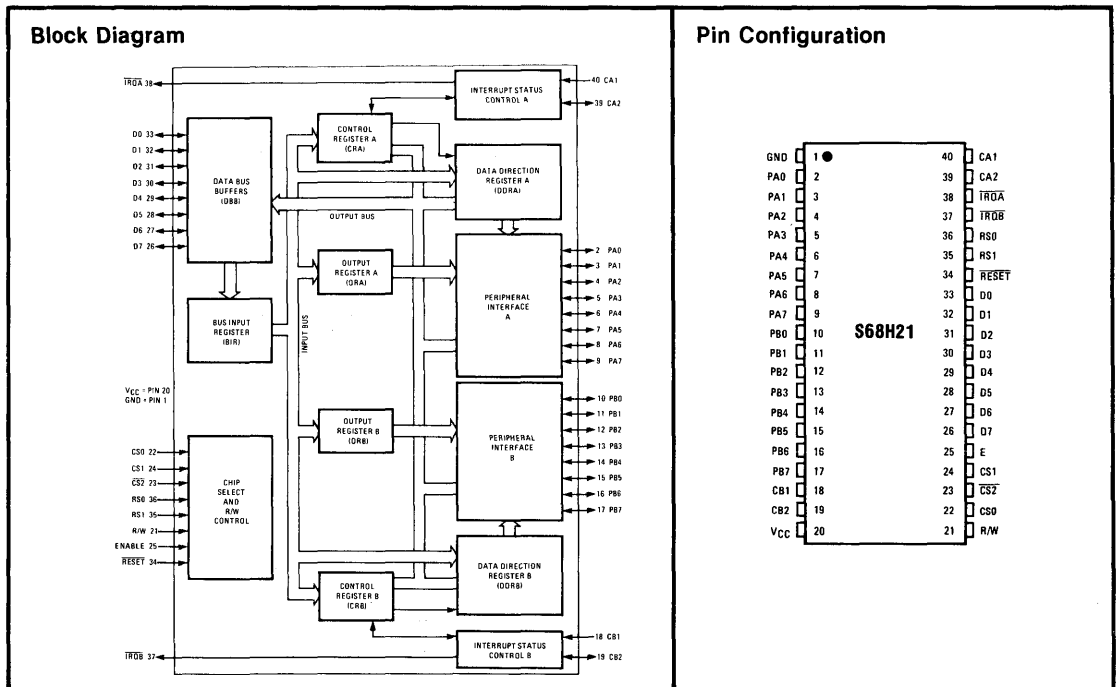
General Description (Continued)

The PIA interfaces to the S68H00 with an eight-bit bidirectional data bus, three chip chip select lines, two interrupt request lines, read/write line, enable line and reset line. These signals, in conjunction with the S68H00 output, permit the MPU to have complete control over the PIA. VMA may be utilized to gate the input signals to the PIA.

Absolute Maximum Ratings

Supply Voltage .... −0.3 to +7.0V
Input Voltage .... −0.3 to +7.0V
Operating Temperature Range .... 0° to +70°C
Storage Temperature Range .... −55° to +150°C

Note:
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Electrical Characteristics

$V_{CC} = 5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to $+70°C$ unless otherwise noted.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
V_{IH}	Input High Voltage	$V_{SS}+2.0$		V_{CC}	Vdc	
V_{IL}	Input Low Voltage	$V_{SS}-0.8$		$V_{SS}+0.8$	Vdc	
I_{IN}	Input Leakage Current R/W, $\overline{Reset}$, RS0, RS1, CS0, $\overline{CS2}$, CS1, CA1, CB1, Enable		1.0	2.5	μAdc	$V_{IN}=0$ to 5.25 Vdc
I_{TSI}	Three State (Off State) Input Current D0-D7, PB0-PB7, CB2		2.0	10	μAdc	$V_{IN}=0.4$ to 2.4 Vdc
I_{IH}	Input High Current PA0-PA7, CA2	−200	−400		μAdc	$V_{IH}=2.4$Vdc
I_{IL}	Input Low Current PA0-PA7, CA2		−1.3	−2.4	mAdc	$V_{IL}=0.4$Vdc
V_{OH}	Output High Voltage D0-D7 Other Output	$V_{SS}+2.4$ $V_{SS}+2.4$			Vdc Vdc	$I_{LOAD}=-205\mu$Adc $I_{LOAD}=-200\mu$Adc
V_{OL}	Output Low Voltage D0-D7 Other Outputs			$V_{SS}+0.4$ $V_{SS}+0.4$	Vdc Vdc	$I_{LOAD}=1.6$mAdc $I_{LOAD}=3.2$mAdc
I_{OH}	Output High Current Sourcing D0-D7 Other Outputs PB0-PB7, CB2	−205 −100 −1.0	−2.5	−10	μAdc μAdc mAdc	$V_{OH}=2.4$Vdc $V_0=1.5$Vdc, the current for driving other than TTL, e.g., Darlington Base
I_{LOH}	Output Leakage Current $\overline{IRQA}$, $\overline{IRQB}$		1.0	10	μAdc	$V_{OH}=2.4$Vdc
P_D	Power Dissipation			550	mW	
C_{IN}	Capacitance D0-D7 PA0-PA7, PB0-PB7, CA2, CB2 Enable, R/W, $\overline{Reset}$, RS0, RS1, CS0, CS1, $\overline{CS2}$, CA1, CB1			12.5 10 7.5	pF pF pF	$V_{IN}=0$, $T_A=+25°C$, f=1.0MHz
C_{OUT}	$\overline{IRQA}$, $\overline{IRQB}$			5.0	pF	

Note: The PA0-PA7 Peripheral Data lines and the CA2 Peripheral Control line can drive two standard TTL loads. In the input mode, the internal pullup resistor on these lines represents a maximum of 1.5 standard TTL loads.

A.C. (Dynamic Characteristics

Loading = 30pF and one TTL load for PA0-PA7, PB0-PB7, CA2, CB2
      = 130pF and one TTL load for D0-D7, $\overline{\text{IRQA}}$, $\overline{\text{IRQB}}$
(V_{CC} = 5.0V ± 5%, T_A = 0°C to + 70°C unless otherwise noted.)

Read Timing Characteristics (Figure 1)

Timing Characteristics (V_{CC} = 5.0V ± 5%, V_{SS} = 0, T_A = 0°C to + 70°C unless otherwise noted.)

Symbol	Parameter	Min.	Max.	Units	Conditions
t_{PDSU}	Peripheral Data Setup Time	90		ns	
t_{PDH}	Peripheral Data Hold Time	0		ns	
t_{CA2}	Delay Time, Enable Negative Transition to CA2 Negative Transition		0.4	μs	
t_{RS1}	Delay Time, Enable Negative Transition to CA2 Positive Transition		0.4	μs	
t_r, t_f	Rise and Fall Times for CA1 and CA2 Input Signals		1.0	μs	
t_{RS2}	Delay Time from CA1 Active Transition to CA2 Positive Transition		0.85	μs	
t_{PDW}	Delay Time, Enable Negative Transition to Peripheral Data Valid		0.4	μs	
t_{CMOS}	Delay Time, Enable Negative Transition to Peripheral CMOS PA0-PA7, CA2 Data Valid		0.85	μs	$V_{CC}-30\%\ V_{CC}$; Figure 6, Load C
t_{CB2}	Delay Time, Enable Positive Transition to CB2 Negative Transition		0.4	μs	
t_{DC}	Delay Time, Peripheral Data Valid to CB2 Negative Transition	2.0		ns	
t_{RS1}	Delay Time, Enable Positive Transition to CB2 Positive Transition		0.4	μs	
PW_{CT}	Peripheral Control Output Pulse Width, CA2/CB2	550		ns	
t_r, t_f	Rise and Fall Times for CB1 and CB2 Input Signals		1.0	μs	
t_{RS2}	Delay Time, CB1 Active Transition to CB2 Positive Transition		0.85	μs	
t_{IR}	Interrupt Release Time, $\overline{\text{IRQA}}$ and $\overline{\text{IRQB}}$		0.70	μs	
t_{RS3}	Interrupt Response Time		1.0	μs	
PW_1	Interrupt Input Pulse Width	500		ns	
t_{RL}	Reset Low Time*	0.4		μs	

*The Reset line must be high a minimum of 1.0μs before addressing the PIA.

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Bus Timing Characteristics

($V_{CC} = 5.0V \pm 5\%$, $T_A = 0°C$ to $+70°C$ unless otherwise noted.)

Read

Symbol	Parameter	Min.	Max.	Units
$t_{CYC(E)}$	Enable Cycle Time	0.4		μs
PW_{EH}	Enable Pulse Width, High	0.18		μs
PW_{EL}	Enable Pulse Width, Low	0.18		ns
t_{AS}	Setup Time, Address and R/W to Enable Positive Transition	55		ns
t_{DDR}	Data Delay Time		160	ns
t_H	Data Hold Time	10		ns
t_{AH}	Address Hold Time	10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25	ns

Write

Symbol	Parameter	Min.	Max.	Units
$t_{CYC(E)}$	Enable Cycle Time	0.4		μs
PW_{EH}	Enable Pulse Width, High	0.18		μs
PW_{EL}	Enable Pulse Width, Low	0.18		ns
t_{AS}	Setup Time, Address and R/W to Enable Positive Transition	55		ns
t_{DSW}	Data Setup Time	50		ns
t_H	Data Hold Time	10		ns
t_{AH}	Address Hold Time	10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25	ns

S6800

Figure 1. Peripheral Data Setup Time (Read Mode)
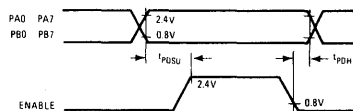
Figure 2. CA2 Delay Time (Read Mode; CRA-5 = CRA-351, CRA-4 = 0)

*Assumes part was deselected during the previous E pulse.

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S6840/S68A40/S68B40
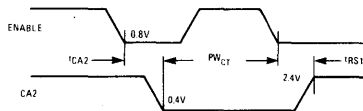
PROGRAMMABLE TIMER

Features

- ☐ Operates from a Single 5 Volt Supply
- ☐ Fully TTL Compatible
- ☐ Single System Clock Required (Enable)
- ☐ Selectable Prescaler on Time 3 Capable of 4MHz for the S6840, 6MHz for the S68A40 and 8MHz for the S68B40
- ☐ Programmable Interrupts ($\overline{\text{IRQ}}$) Output to MPU
- ☐ Readable Down Counter Indicates Counts to Go to Time-Out
- ☐ Selectable Gating for Frequency or Pulse-Width Comparison
- ☐ $\overline{\text{RESET}}$ Input
- ☐ Three Asynchronous External Clock and Gate/ Trigger Inputs Internally Synchronized
- ☐ Three Maskable Outputs

General Description

The S6840 is a programmable subsystem component of the S6800 family designed to provide variable system time intervals.

The S6840 has three 16-bit binary counters, three corresponding control registers and a status register. These counters are under software control and may be used to cause system interrupts and/or generate output signals. The S6840 may be utilized for such tasks as frequency measurements, event counting, interval measuring and similar tasks. The device may be used for square wave generation, gated delay signals, single pulses of controlled duration, and pulse width modulation as well as system interrupts.

Block Diagram

Pin Configuration
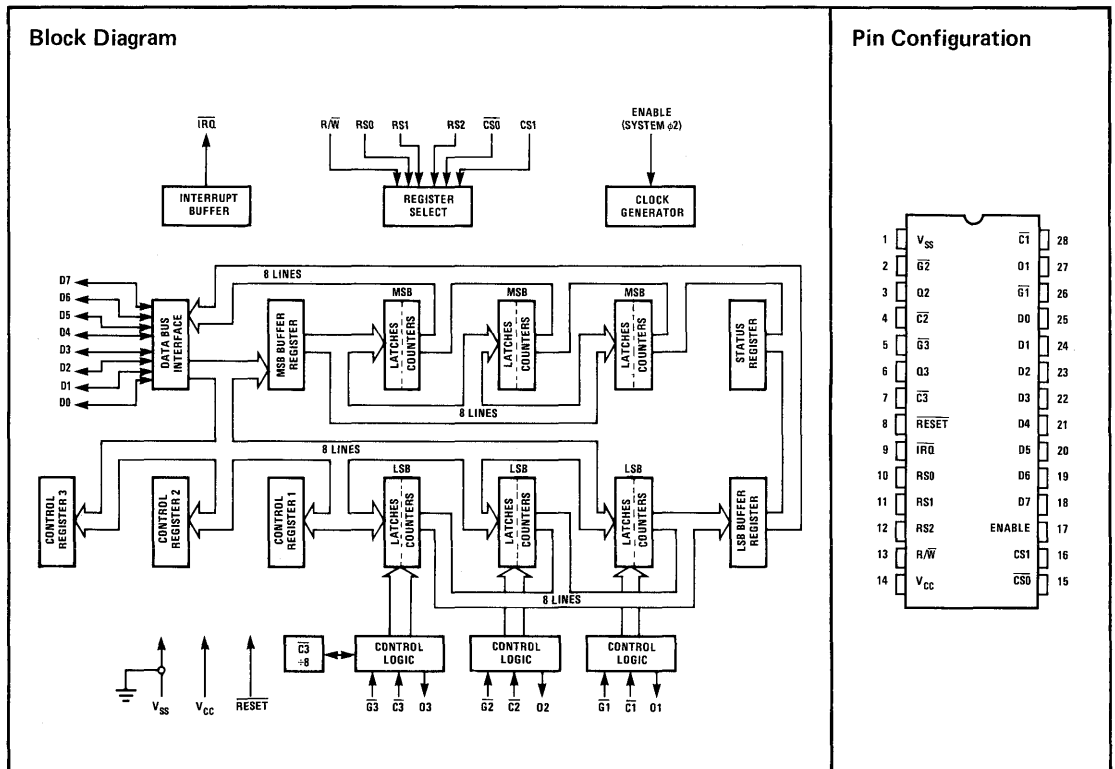
Absolute Maximum Ratings

Supply Voltage V_{CC} .... -0.3 to $+7.0V$
Input Voltage V_{IN} .... -0.3 to $+7.0V$
Operating Temperature Range T_A .... $0°$ to $+70°C$
Storage Temperature Range T_{stg} .... $-55°$ to $+150°C$
Thermal Resistance θ_{JA} .... $82.5°C/W$

Note:
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Electrical Characteristics

$V_{CC} = 5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to $+70°C$ unless otherwise noted.

Symbol	Parameter		Min.	Typ.	Max.	Unit	Conditions
V_{IH}	Input High Voltage		$V_{SS}+2.0$		V_{CC}	V	
V_{IL}	Input Low Voltage		$V_{SS}-0.3$		$V_{SS}+0.8$	V	
I_{IN}	Input Leakage Current			1.0	2.5	μA	$V_{IN}=0$ to 5.25 V
I_{TSI}	Three State (Off State) Input Current	D0-D7		2.0	10	μA	$V_{IN}=0.4$ to 2.4 V
V_{OH}	Output High Voltage	D0-D7	$V_{SS}+2.4$			V	$I_{LOAD}=-205\mu A$
		Other Outputs	$V_{SS}+2.4$			V	$I_{LOAD}=-200\mu A$
V_{OL}	Output Low Voltage	D0-D7			$V_{SS}+0.4$	V	$I_{LOAD}=1.6mA$
		$01-03$, $\overline{IRQ}$			$V_{SS}+0.4$	V	$I_{LOAD}=3.2mA$
I_{LOH}	Output Leakage Current (Off State)	$\overline{IRQ}$		1.0	10	μA	$V_{OH}=2.4V$
P_D	Power Dissipation				550	mW	
C_{IN}	Capacitance	D0-D7			12.5	pF	$V_{IN}=0$, $T_A=+25°C$,
		All Others			7.5		$f=1.0MHz$
C_{OUT}		$\overline{IRQ}$			5.0	pF	$V_{IN}=0$, $T_A=+25°C$,
		01, 02, 03			10		$f=1.0MHz$

Bus Timing Characteristics
Read (See Figure 1)

Symbol	Characteristic	S6840		S68A40		S68B40		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{CYCE}	Enable Cycle Time	1.0	10	0.666	10	0.5	10	μs
PW_{EH}	Enable Pulse Width, High	0.45	4.5	0.280	4.5	0.22	4.5	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.280		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DDR}	Data Delay Time		320		220		180	ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

Bus Timing Characteristics (Continued)
Read (See Figure 1)

Symbol	Characteristic	S6840 Min.	S6840 Max.	S68A40 Min.	S68A40 Max.	S68B40 Min.	S68B40 Max.	Unit
t_{CYCE}	Enable Cycle Time	1.0	10	0.666	10	0.5	10	μs
PW_{EH}	Enable Pulse Width, High	0.45	4.5	0.280	4.5	0.22	4.5	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.280		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DSW}	Data Setup Time	195		80		60		ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

AC Operating Characteristics
(See Figures 3 and 7)

Symbol	Characteristic	S6840 Min.	S6840 Max.	S68A40 Min.	S68A40 Max.	S68B40 Min.	S68B40 Max.	Unit
t_r, t_f	Input Rise and Fall Times (Figures 4 and 5) $\overline{C}$, $\overline{G}$ and $\overline{Reset}$		1.0		0.666*		0.500*	μs
PW_L	Input Pulse Width (Figure 4) (Asynchronous Mode) $\overline{C}$, $\overline{G}$ and $\overline{Reset}$	$t_{CYCE}+t_{su}+t_{hd}$		$t_{CYCE}+t_{su}+t_{hd}$		$t_{CYCE}+t_{su}+t_{hd}$		ns
PW_H	Input Pulse Width (Figure 5) (Asynchronous Mode) $\overline{C}$, $\overline{G}$ and $\overline{Reset}$	$t_{CYCE}+t_{su}+t_{hd}$		$t_{CYCE}+t_{su}+t_{hd}$		$t_{CYCE}+t_{su}+t_{hd}$		ns
t_{su}	Input Setup Time (Figure 6) (Synchronous Mode) $\overline{C}$, $\overline{G}$ and $\overline{Reset}$ $\overline{C3}$ ($\div$8 Prescaler Mode only)	200		120		75		ns
t_{hd}	Input Hold Time (Figure 6) (Synchronous Mode) $\overline{C}$, $\overline{G}$ and $\overline{Reset}$ $\overline{C3}$ ($\div$8 Prescaler Mode only)	50		50		50		ns
PW_L, PW_H	Input Pulse Width (Synchronous Mode) $\overline{C3}$ ($\div$8 Prescaler Mode only)	125		84		62.5		ns
t_{co} t_{cm} t_{cmos}	Output Delay, O1-O3 (Figure 7) (V_{OH}=2.4V, Load B) TTL (V_{OH}=2.4V, Load D) MOS (V_{OH}=0.7 V_{DD}, Load D) CMOS		700 450 2.0		460 450 1.35		340 340 1.0	ns ns μs
t_{IR}	Interrupt Release Time		1.2		0.9		0.7	μs

* t_r and $t_f \leqslant t_{CYCE}$

S6800

Figure 1. Bus Read Timing Characteristics
         (Read Information from PTM)
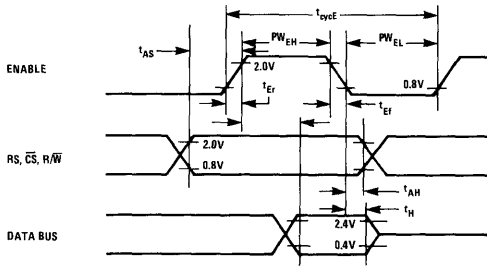
Figure 2. Bus Write Timing Characteristics
         (Write Information into PTM)
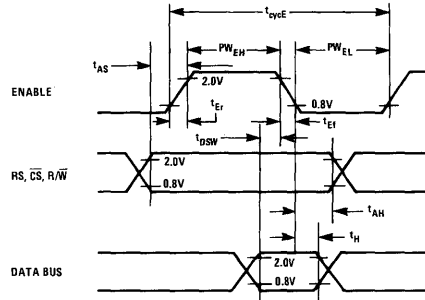
Figure 3. Input Pulse Width Low
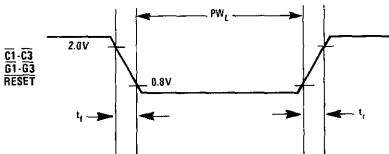
Figure 4. Input Pulse Width High
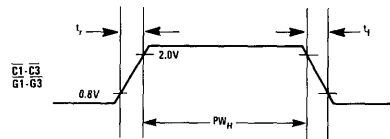

Figure 5. Input Setup and Hold Times
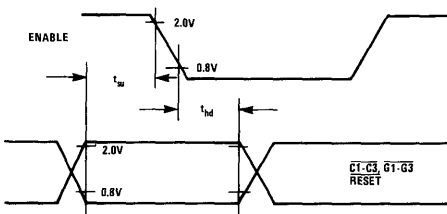
Figure 6. Output Delay
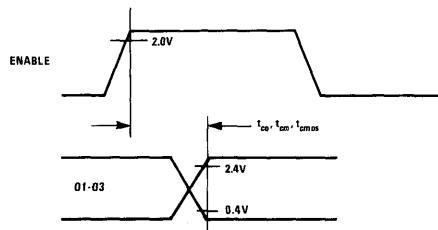
Figure 7. IRQ Release Time
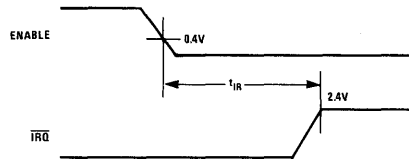
Figure 8. Bus Timing Test Loads

LOAD A
(D0-D7)

LOAD B
(D1, D2, D3)

LOAD C
(IRQ ONLY)

LOAD D
(CMOS LOAD)

![AMI logo]

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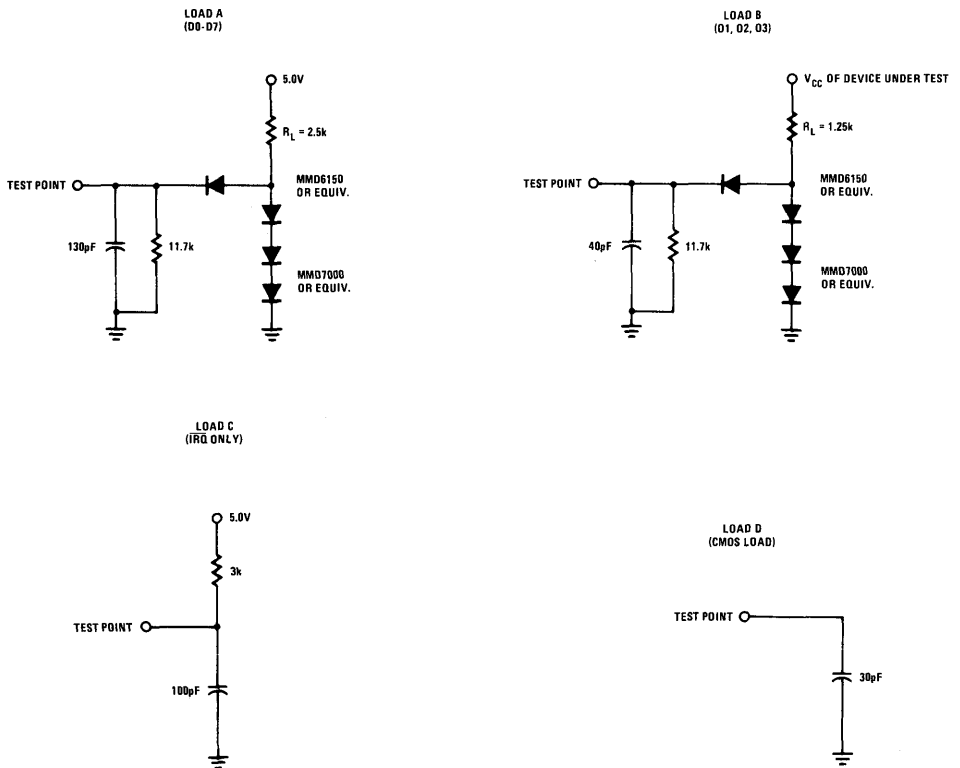
CRT CONTROLLER (CRTC)

Features

- ☐ Generates Refresh Addresses and Row Selects
- ☐ Generates Video Monitor Inputs: Horizontal and Vertical Sync and Display Enable
- ☐ Low Cost; MC6845/SY6545 Pin Compatible
- ☐ Text Can Be Scrolled on a Character, Line or Page Basis
- ☐ Addresses 16K Bytes of Memory
- ☐ Screen Can Be Up to 128 Characters Tall By 256 Wide
- ☐ Character Font Can Be 32 Lines High With Any Width
- ☐ Two Complete ROM Programs

- ☐ Cursor and/or Display Can Be Delayed 0, 1 or 2 Clock Cycles
- ☐ Four Cursor Modes:
  - – Non-Blink
  - – Slow Blink
  - – Fast Blink
  - – Reverse Video With Addition of a Single TTL Gate
- ☐ Three Interlace Modes
  - – Normal Sync
  - – Interlace Sync
  - – Interlace Sync and Video
- ☐ Full Hardware Scrolling
- ☐ NMOS Silicon Gate Technology
- ☐ TTL-Compatible, Single +5 Volt Supply

S6800

Block Diagram

Pin Configuration
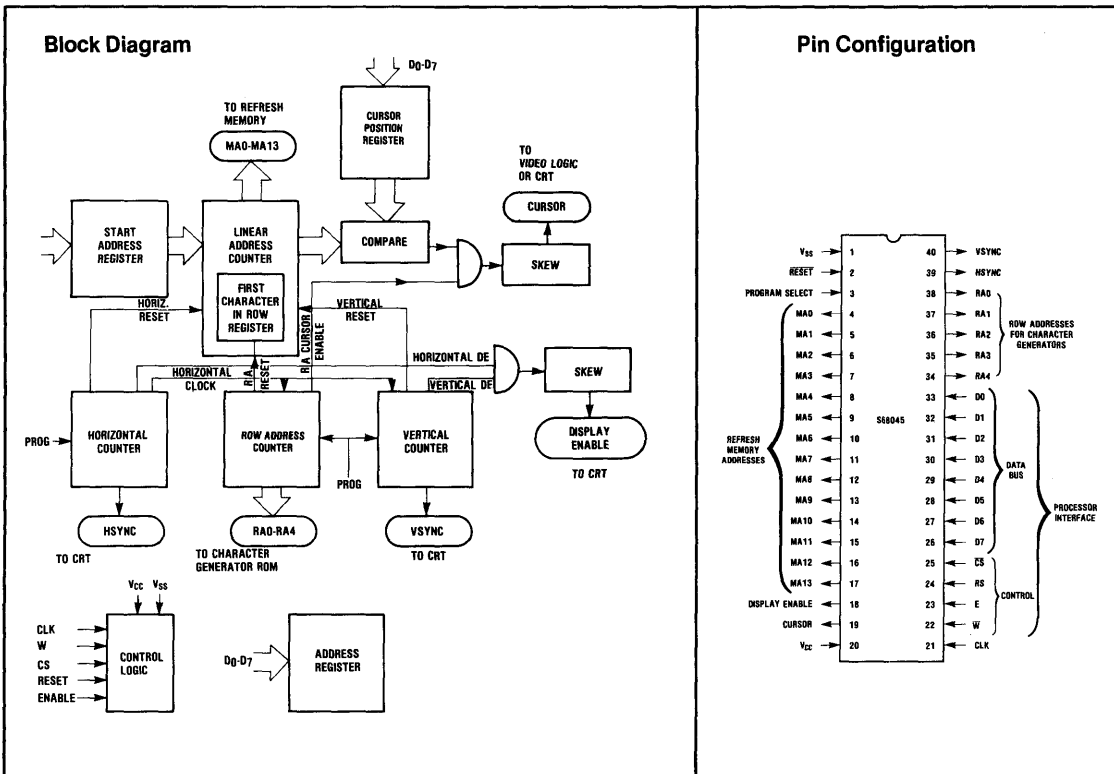
General Description

The S68045 CRT Controller performs the complex interface between an S6800 Family microprocessor and a raster scan display CRT system. The S68045 is designed to be flexible yet low cost. It is configured to both simplify the development and reduce the cost of equipment such as intelligent terminals, word processing, and information display devices.

The CRT Controller consists of both horizontal and vertical counting circuits, a linear address counter, and control registers. The horizontal and vertical counting circuits generate the Display Enable, HSYNC, VSYNC, and RA0-RA4 signals. The RA0-RA4 lines are scan line count signals to the external character generator ROM. The number of characters per character row, scan lines per character row, character rows per screen, and the

horizontal and vertical SYNC position and width are all mask programmable. The S68045 is capable of addressing 16K of memory for display. The CRT may be scrolled or paged through the entire display memory under MPU control. The cursor control register determines the cursor location on the screen, and the cursor format can be programmed for fast blink, slow-blink, or non-blink appearance, with programmable size. By adding a single TTL gate, the cursor can even be reversed video. The device features two complete, independent programs implemented in user-specified ROM. Either set of programmable variables (50/60Hz refresh rate, screen format, etc.) is available to the user at any time.

The S68045 is pin compatible with the MC6845, operates from a single 5-volt supply, and is designed using the latest in minimum-geometry NMOS technology.

Absolute Maximum Ratings

Supply Voltage V_{CC} .... $-0.3°C$ to $+7.0°C$
Input Voltage V_{IN} .... $-0.3V$ to $+7.0V$
Operating Temperature Range T_A .... $0°C$ to $+70°C$
Storage Temperature Range T_{stg} .... $-55°C$ to $+150°C$

Bus Timing Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
t_{CYCE}	Enable Cycle Time	1.0			µs	
PW_{EH}	Enable Pulse Width, High	0.45		25	µs	
PW_{EL}	Enable Pulse Width, Low	0.43			µs	
t_{AS}	Setup Time, CS and RS Valid to Enable Positive Transition	160			ns	
t_H	Data Hold Time	10			ns	
t_{AH}	Address Hold Time	10			ns	
t_{Er}, t_{Ef}	Rise and Fall for Enable Input			25	ns	
t_{DSW}	Data Setup Time	195			ns	

Electrical Characteristics

$V_{CC}=5.0V\pm5\%$; $V_{SS}=0$, $T_A=0°C$ to $+70°C$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
V_{IH}	Input High Voltage	2.0		V_{CC}	Vdc	
V_{IL}	Input Low Voltage	-0.3		0.8	Vdc	
I_{IN}	Input Leakage Current		1.0	2.5	μAdc	
V_{OH}	Output High Voltage	2.4			Vdc	$I_{LOAD}=-100\mu A$
V_{OL}	Ouput Low Voltage			0.4	Vdc	$I_{LOAD}=1.6mA$
P_D	Power Dissipation		600		mW	
C_{IN}	Input Capacitance D0-D7 All Others			12.5 10	pF pF	
C_{OUT}	Output Capacitance All Outputs			10	pF	
P_{WCL}	Minimum Clock Pulse Width, Low	160			ns	
P_{WCH}	Clock Pulse Width, High	200		10,000	ns	
f_c	Clock Frequency			2.5	MHz	
t_{cr}, t_{cf}	Rise and Fall Time for Clock Input			20	ns	
t_{MAD}	Memory Address Delay Time			160	ns	
t_{RAD}	Raster Address Delay Time			160	ns	
t_{DTD}	Display Timing Delay Time			300	ns	
t_{HSD}	Horizontal Sync Delay Time			300	ns	
t_{VSD}	Vertical Sync Delay Time			300	ns	
t_{CDD}	Cursor Display Timing Delay Time			300	ns	

S68000

Systems Operation

The S68045 CRTC generates all of the signals needed for the proper operation of a CRT system including HSYNC, VSYNC, Display Enable, Cursor control signals (refer to Figure 1), the refresh memory addresses (MA0-MA13) and row addresses (RA0-RA4). The CRTC's timing is derived from the CLK input, which is divided down from the dot rate counter.

The CRTC, which is compatible with the 6800 family, communicates with the MPU by means of the standard 8-bit data bus. This primary data bus uses a buffered interface for writing information to the display refresh RAM by means of a separate secondary data bus. This arrangement allows the MPU to forget about the display except for those time periods when data is actually being changed on the screen. The address bus for the refresh RAM is continuously multiplexed between the MPU and the CRTC.

Since the MPU is allowed transparent read/write access to the display memory, the refresh RAM appears as just another RAM to the processor. This means that the refresh memory can also be used for program storage. Care should be taken by the system designer, however, to insure that the portion of memory being used for program storage is not actively displayed.

Displayed Data Control

Display Refresh Memory Addresses (MA0-MA13) — 14 bits of address provide the CRTC with access of up to 16K of memory for use in refreshing the screen.

Row Addresses (RA0-RA4) — 5 bits of data that provide the output from the CRTC to the character generator ROM. They allow up to 32 scan lines to be included in a character.

Cursor — This TTL compatible, active high output indicates to external logic that the cursor is being displayed.

Figure 1. Typical CRT Controller System
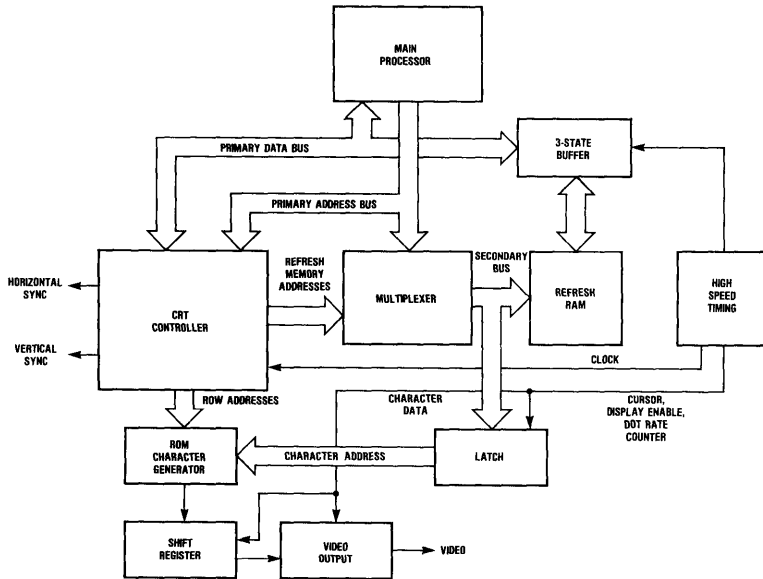
The character address of the cursor is held in a register, so the cursor's position is not lost even when scrolled off the screen.

CRT Control

All three CRT control signals are TTL compatible, active high outputs.

Display Enable — Indicates that valid data is being clocked to the CRT for the active display area.

Vertical Sync (VSYNC) — Makes certain the CRTC and the CRT's vertical timing are synchronized so the picture is vertically stable.

Horizontal Sync (HSYNC) — Makes certain the CRTC and the CRT's horizontal timing are synchronized so the picture is horizontally stable.

Processor Interface

All processor interface lines are three state, TTL/MOS compatible inputs.

Chip Select ($\overline{CS}$)—The $\overline{CS}$ line selects the CRTC when low to write to the internal Register File. This signal should only be active when there is a valid stable address being decoded from the processor.

Register Select — The RS line selects either the Address Register (RS= "0") or one of the Data Registers (RS= "1") of the internal Register File.

To address one of the software programmable registers (R12, R13, R14 or R15 in Table 2) first access the Address Register ($\overline{CS}=0$, RS=0) and write the number of the desired register. Then write into the actual register by addressing the data register section ($\overline{CS}=0$, RS=1) and enter the appropriate data.

Write ($\overline{W}$) — The $\overline{W}$ line allows a write to the internal Register File.

Data Bus (D0-D7) — The data bus lines (D0-D7) are write-only and allow data transfers to the CRTC internal register file.

Enable (E) — The Enable signal enables the data bus input buffers and clocks data to the CRTC. This signal is usually derived from the processor clock, and the high to low transition is the active edge.

S68045 Control Clock (CLK) — The clock signal is a high impedance, TTL/MOS compatible input which assures the CRTC is synchronized with the CRT itself. The CLK signal is divided down by external circuitry from the dot rate counter. The CLK frequency is equal to

the dot rate frequency divided by the width of a single character block (including framing) expressed in dots, CLK is equal to the character rate.

Program (PROG) — The voltage on this pin determines whether the screen format in ROM 0 (PROG LOW) or ROM 1 (PROG HIGH) is being used.

Reset ($\overline{\text{RES}}$) — The $\overline{\text{RES}}$ input resets the CRTC. An (active) low input on this line forces these actions:

a) MA0-MA13 are loaded with the contents of R12/R13 (the start address register).

b) The horizontal, vertical, and raster address counter are reset to the first raster line of the first displayed character in the first row.

c) All other outputs go low.

Note that none of the internal registers are affected by $\overline{\text{RES}}$.

$\overline{\text{RES}}$ on the CRTC differs from the reset for the rest of the 6800 family in the following aspects:

a) MA0-MA13 and RA0-RA4 go to the start addresses, instead of FFFF.

b) Display recommences immediately after $\overline{\text{RES}}$ goes high.

Internal Register Description — There is a bank of 15 control registers in the 68045, most of which are mask programmed. The exceptions are the Address Register, the two Start Address Registers (R12 & R13) and the Cursor Location Registers (R14 & R15). All software programmable registers are write only. The Address Register is 5 bits long. The software programmable registers are made available to the data lines whenever the chip select ($\overline{\text{CS}}$) goes low. When $\overline{\text{CS}}$ goes high, the data lines show a high impedance to the microprocessor.

Horizontal Total Register (R0) — The full horizontal period, expressed in character times, is masked in R0. (See Figure 2a.)

Horizontal Displayed Register (R1) — This register contains the number of characters to be actually displayed in a row. (See Figure 2a.)

Horizontal SYNC Position Register (R2) — The contents of R2 (also in character times) should be slightly larger than the value in R1 to allow for a non-displayed right border. (See Figure 2a.)

Sync Width Register (R3) — The width of the HSYNC pulse expressed in character times is masked into the lower four bits of R3. The width of the HSYNC pulse has to be non-zero.

The width of the VSYNC pulse is masked into the upper

Figure 2a. Approximate Timing Diagram
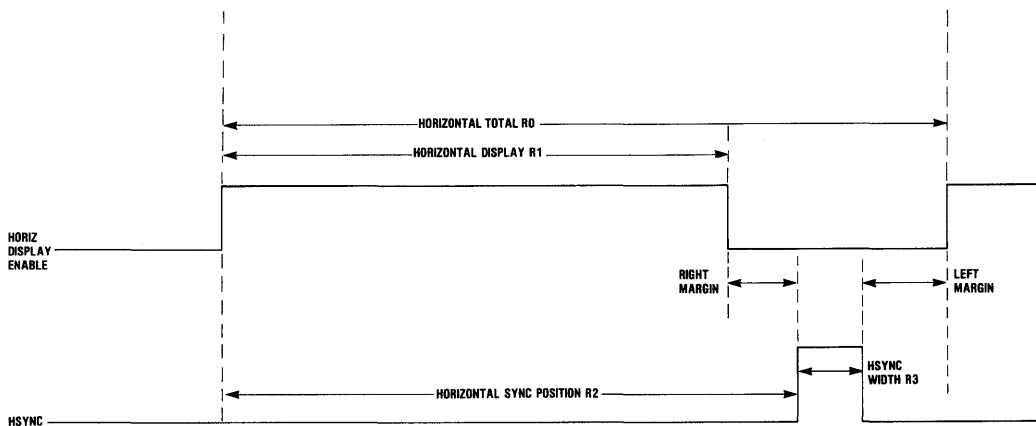
FOR MORE EXACT DIAGRAMS REFER TO THE BACK OF THE DATA SHEET. THE HORIZONTAL DISPLAY ENABLE IS ANDED WITH THE VERTICAL DISPLAY ENABLE TO PRODUCE THE DISPLAY ENABLE AT PIN 18. NOTE THE (a) FIGURE IS TIMED IN TERMS OF INDIVIDUAL CHARACTERS, WHEREAS THE (b) FIGURE IS TIMED IN TERMS OF CHARACTER ROWS.

four bits of R3 without any modification, with the exception that all zeroes will make VSYNC 16 characters wide.

Vertical Total Register (R4) — This register contains the total number of character rows — both displayed and non-displayed — per screen. This number is just the total number of scan lines used divided by the number of scan lines in a character row. If there is a remainder, it is placed in R5. (See Figure 2b).

Vertical Total Adjust Register (R5) — See description of R4. A fractional number of character row times is used to obtain a refresh rate which is exactly 50HZ, 60HZ, or some other desired frequency. (See Figure 2b).

Vertical Displayed Register (R6) — This register contains the total number of character rows that are actually displayed on the CRT screen. (See Figure 2b).

Vertical SYNC Position (R7) — R7 contains the position of the vertical SYNC pulse in character row times with respect to the top character row. Increasing the value shifts the data up. (See Figure 2b).

Interlace Mode Register (R8) — R8 controls which of the three available raster scan modes will be used (See Figure 3).

— Non-interlace or Normal sync mode
— Interlaced sync mode
— Interlaced sync and Video mode

The Cursor and Display Enable outputs can be delayed (skewed) 0, 1 or 2 clock cycles with respect to the refresh memory address outputs (MA0-MA13). The amount the cursor is delayed is independent of how much the Display Enable signal is delayed. This feature allows the system designer to account for memory address propagation delay through the RAM, ROM, etc.

Maximum Scan Line Register (R9) — Determines the number of scan lines per character row including top and bottom spacing.

Cursor Start Register (R10) — Contains the raster line where the cursor start (see Figure 4). The cursor start line can be anywhere from line 0 to line 31.

The cursor can be in one of the following formats.

— Non-blinking
— Slow blinking (1/16) the vertical refresh rate)
— Fast blinking (1/32 the vertical refresh rate)
— Reverse video (non-blinking, slow blinking, or fast blinking)

The reverse video cursor needs an external TTL XOR gate to be placed in the video circuit.

To implement the reverse video cursor, the cursor start line (R10) should be set to line 0 and the cursor end line (R11) should be set to whatever is in R9 so that the cursor covers the entire block. On the circuit level, the output from the Cursor pin (pin 19) should be taken through the XOR gate along with the output from the shift register. (See Figure 5.) With this setup the character whose memory address is in the cursor register (R14/R15) will have it's background high (because Cursor along is high) but the character itself will be off (because both cursor and the character are both high.
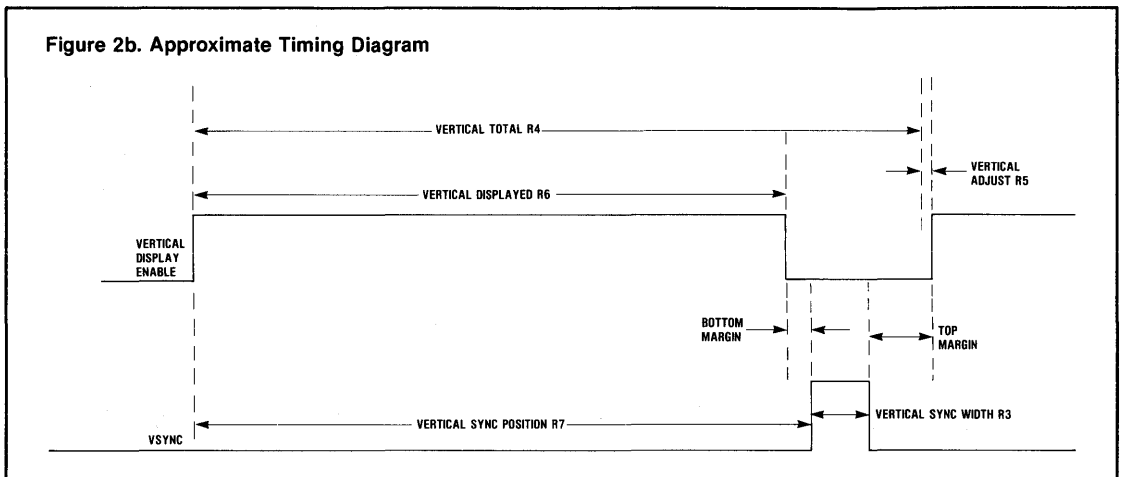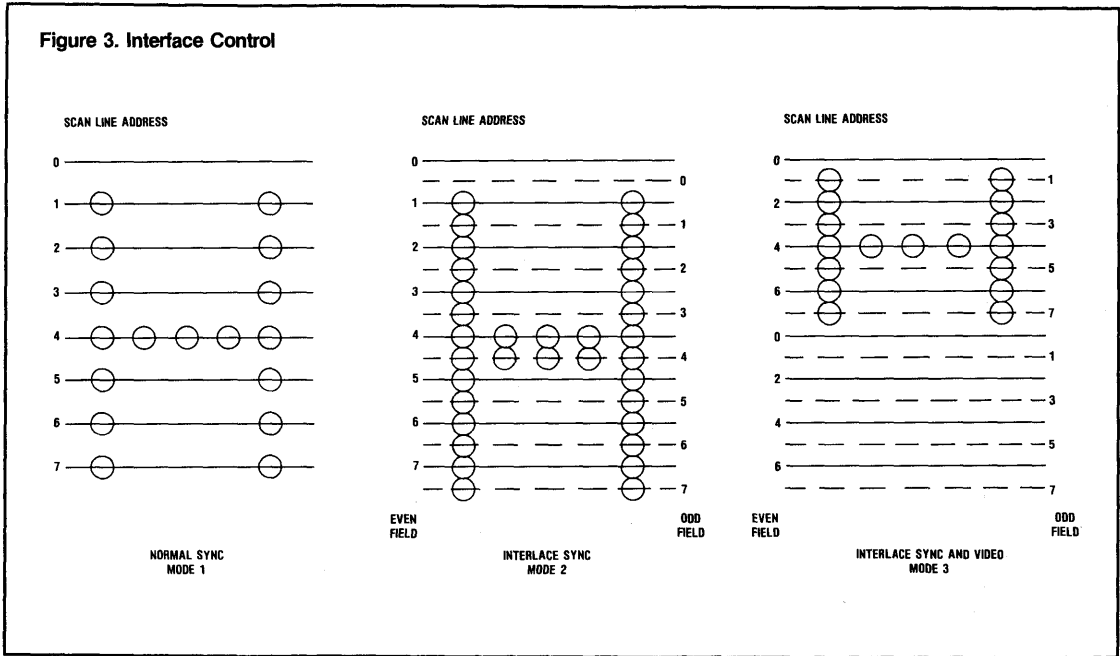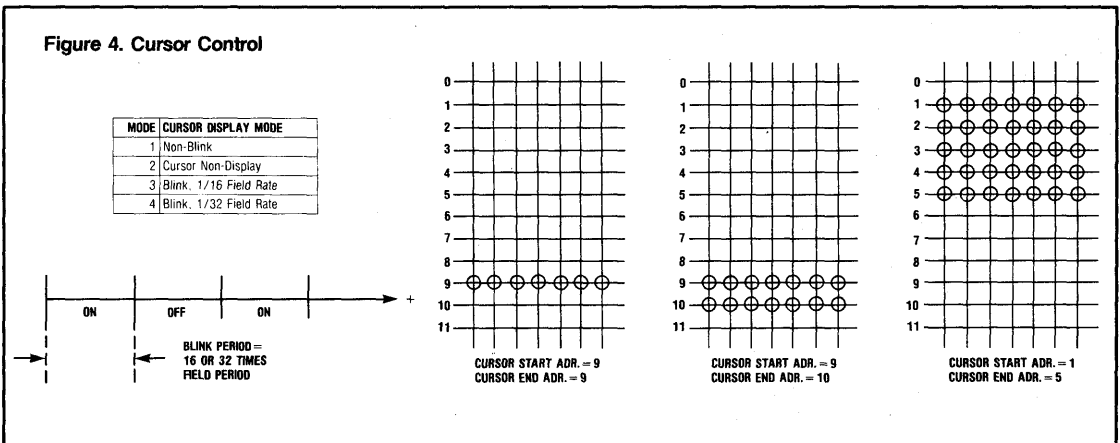

Figure 2b. Approximate Timing Diagram

Figure 3. Interface Control

NORMAL SYNC
MODE 1

INTERLACE SYNC
MODE 2

INTERLACE SYNC AND VIDEO
MODE 3

Figure 4. Cursor Control

MODE	CURSOR DISPLAY MODE
1	Non-Blink
2	Cursor Non-Display
3	Blink, 1/16 Field Rate
4	Blink, 1/32 Field Rate

BLINK PERIOD =
16 OR 32 TIMES
FIELD PERIOD

CURSOR START ADR. = 9
CURSOR END ADR. = 9

CURSOR START ADR. = 9
CURSOR END ADR. = 10

CURSOR START ADR. = 1
CURSOR END ADR. = 5

Memory Start Address Register (R12/R13) — These two software programmable, write-only registers taken together contain the memory address of the first character displayed on the screen. Register R12 contains the upper six bits of the fourteen refresh memory address bits, while R13 contains the lower eight bits. The Linear Address Generator begins counting from the address in R12/R13. By changing the starting address, the display can be scrolled up or down through the 16K memory block by character, line or page. If the value in R12/R13 is near the end of the 16K block the display will wrap around to the front.

Cursor Address Register (R14/R15) — These two software programmable, write-only registers, taken together, contain the address in memory of the cursor character.

Figure 5. Implementation of a Reversed Video Cursor
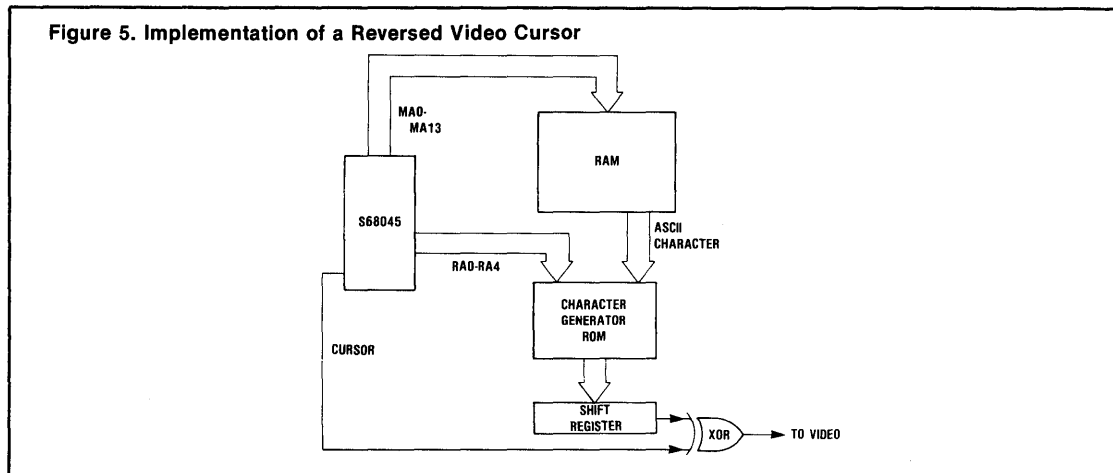
Register R14 contains the upper six bits and register R15 contains the lower eight bits of the character. Cursor position is associated with an address in memory rather than with a position on the screen. This way cursor position is not lost when the display is scrolled.

Address Register — The five bit address register is unique in that it does not store any CRT-related information, but is used as the address storage register in an indirect access of the other registers. When the Register Select pin (RS) is low, the address register is accessed by D0-D4. When RS is high, the register whose address is in the address register is accessed.

CRTC Internal Description

There are four counters which determine what the CRTC's output will be (see Block Diagram):

1) Horizontal Counter
2) Vertical Counter
3) Row Address Counter
4) Linear Address Counter

The first two counters, and to some extent the third, take care of the physical operation of the monitor. The Linear Address Counter, on the other hand, is responsible for the data that is displayed on the screen.

Surrounding these counters are the registers R0-R15. Coincidence logic continuously compares the contents of each counter with the contents of the register(s) associated with it. When a match is found, appropriate action is taken; the counter is reset to a fixed or dynamic value, or a flag (such as VSYNC) is set, or both.

Two sets of registers — The start Address Register (R12/R13) and the Cursor Position Register (R14/R15) — are programmable via the Data lines (D0-D7). The other registers are all mask programmed. There are two ROM programs available on each chip. Selection of which ROM program will be accessed is performed by the PROG pin.

Horizontal Counter

The Horizontal Counter produces four output flags: HSYNC, Horizontal Display Enable, Horizontal Reset to the Linear Address Counter, and the horizontal clock.

The Horizontal Counter is driven by the character rate clock, which was derived from the dot rate clock (see Table 1). Immediately after the valid display area is entered the Horizontal Counter is reset to zero but continues incrementing.

HSYNC is the only one of the four signals which is fed to an external device (the CRT). The Horizontal Counter is compared to registers R0, R2 and R3 to give an HSYNC of the desired frequency (R0), position (R2) and width (R3). (See Figure 2a.)

Horizontal Display Enable is an internal flag which, when ANDed with Vertical DE, is output at the Display Enable pin. The Horizontal Counter determines the proper frequency (R0), and width (R1).

The Horizontal Reset and the horizontal clock are actually identical signals: the only difference is the way they are used. Both are pulsed once for each scan line, so their frequency is equal to the character rate clock frequency divided by the entire horizontal period (display, non-display and retrace) expressed in character times

Table 1. Comparison of all CRTC Clocks

NAME	LOCATION OF CLOCK	DIVIDED BY:	CONTROLLING REGISTER	PRODUCES
DOT RATE CLOCK	EXTERNAL	TOTAL WIDTH OF A CHARACTER BLOCK IN DOTS	EXTERNAL	CHARACTER RATE CLOCK
CHARACTER RATE CLOCK	EXTERNAL INPUT	TOTAL NUMBER OF CHARACTERS IN A ROW	R0	HORIZONTAL CLOCK
HORIZONTAL CLOCK	INTERNAL	TOTAL NUMBER OF SCAN LINES IN A CHARACTER ROW	R9	ROW ADDRESS CLOCK
ROW ADDRESS CLOCK	INTERNAL	TOTAL NUMBER OF CHARACTER ROWS PER SCREEN	R4, R5	VERTICAL CLOCK

Table 2. CRTC Internal Register Assignment

$\overline{CS}$	RS	ADDRESS REGISTER					REGISTER#	REGISTER FILE
		4	3	2	1	0		
							R0	HORIZONTAL TOTAL
							R1	HORIZONTAL DISPLAYED
							R2	HORIZONTAL SYNC POSITION
							R3	HORIZONTAL SYNC WIDTH
							R4	VERTICAL TOTAL
		MASK PROGRAMMABLE					R5	VERTICAL TOTAL ADJUST
							R6	VERTICAL DISPLAYED
							R7	VERTICAL SYNC POSITION
							R8	INTERLACE MODE
							R9	MAX SCAN LINE ADDRESS
							R10	CURSOR START
							R11	CURSOR END
0	1	0	1	1	0	0	R12	START ADDRESS (H)
0	1	0	1	1	0	1	R13	START ADDRESS (L)
0	1	0	1	1	1	0	R14	CURSOR (H)
0	1	0	1	1	1	1	R15	CURSOR (L)
0	0	X	X	X	X	X	X	ADDRESS REGISTER

X DON'T CARE

(which is stored in R0). The horizontal clock drives the Vertical and Row address Counters. The horizontal reset is discussed with the Linear Address Counter.

Vertical Counter

The Vertical Counter produces three output flags: VSYNC, Vertical Display Enable, and Vertical Reset to the Linear Address Counter. The Vertical Counter is driven by the horizontal clock. Immediately after vertical retrace the Vertical Counter is reset to zero but continues incrementing.

VSYNC is the only one of the three signals which is fed to an external device (the CRT). The Vertical Counter is compared to registers R3, R4, R5 and R7 to give a VSYNC of the desired frequency (R4, R5), position (R7) and width (R3). (See Figure 2b.)

Vertical Display Enable is an internal flag which, when ANDed with Horizontal DE, is output at the Display Enable pin. The Vertical Counter determines the proper frequency (R4, R5) and width (R6).

Vertical Reset is pulsed once for each screen. The frequency of Vertical Reset is equal to the horizontal clock frequency divided by the total number of scan lines in a screen (which is equal to $(R4 \times R9) + R5$). It will be discussed with the Linear Address Counter.

Figure 6. Bus Write Timing

Figure 6. Bus Write Timing
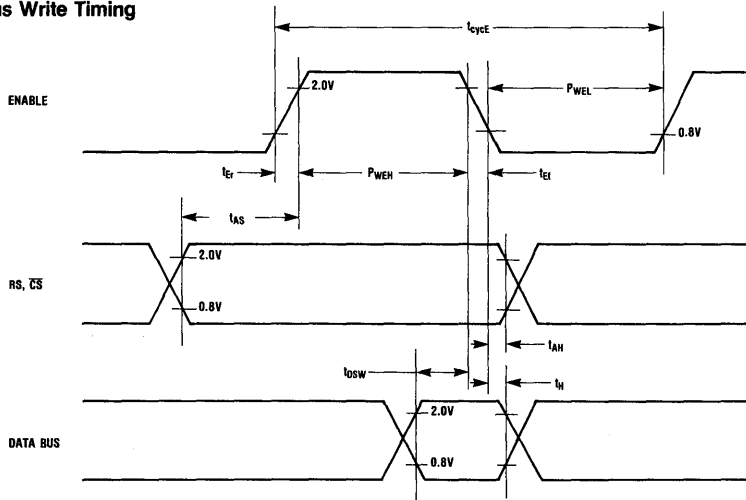
Row Address Counter

The Row Address Counter produces three sets of output: the five Row Address lines (RA0-RA4), the Row Address Cursor Enable flag and the Row Address Reset flag. The Row Address Counter is driven by the horizontal clock. Immediately after a full character row has been completed by the Row Address Counter is reset to zero but continues incrementing. Note that the Row Address Counter actually counts scan lines, which are different from character rows. A full character row consists of however many scan lines are in register R9.

The Row Address Lines, RA0-RA4, are the only data lines from the Row Address Counter that are fed to an external device (the character generator ROM). The Row Address lines just carry the count that is currently in the Row Address Counter. The counter is reset whenever the count equals the contents of the Maximum Scan Line Register (R9.)

Row Address Cursor Enable is a flag going to the Cursor output AND gate. The Row Address Cursor Enable flag goes high whenever the count in the Row Address Counter is greater than or equal to the Cursor Start Register (R10) but less than or equal to the Cursor End Register (R11). The other input to the Cursor output AND gate goes high whenever the address in the Linear

Address Counter is equal to the address in the Cursor Position Reister (R14/R15).

Row Address Reset is pulsed whenever the Row Address Counter is reset. It will be discussed with the Linear Address Counter.

Linear Address Counter

The Linear Address Counter (LAC) produces only one set of outputs: The Refresh Memory Address lines (MA0-MA13). These fourteen bits are fed externally to the Refresh RAM and internally to the Cursor Position coincidence circuit. The LAC is driven by the character rate clock and continuously increments during the display, non-display and retrace portions of the screen. It contains an internal read/write register which stores the memory address of the first displayed character in the current row.
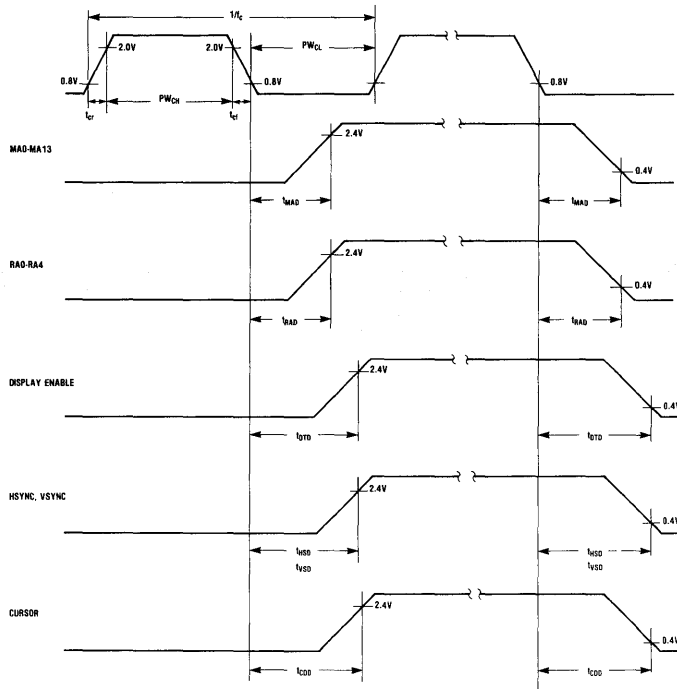
When any of the three Reset flags already mentioned (Horizontal, Row Address and Vertical) is pulsed, the value in the internal register is loaded into the counter. If the reset is a Horizontal Reset the value in the internal register is not modified before the load. If the reset is a Row Address Reset, the value in the internal "first character" register is first increased by the number of characters displayed on a single character row (register

R1). The new contents of the internal register are then loaded into the Linear Address Counter.

If the reset is a Vertical Reset, the value in Start Address Register (R12/R13) is first loaded into the internal register, and then into the Linear Address Counter.
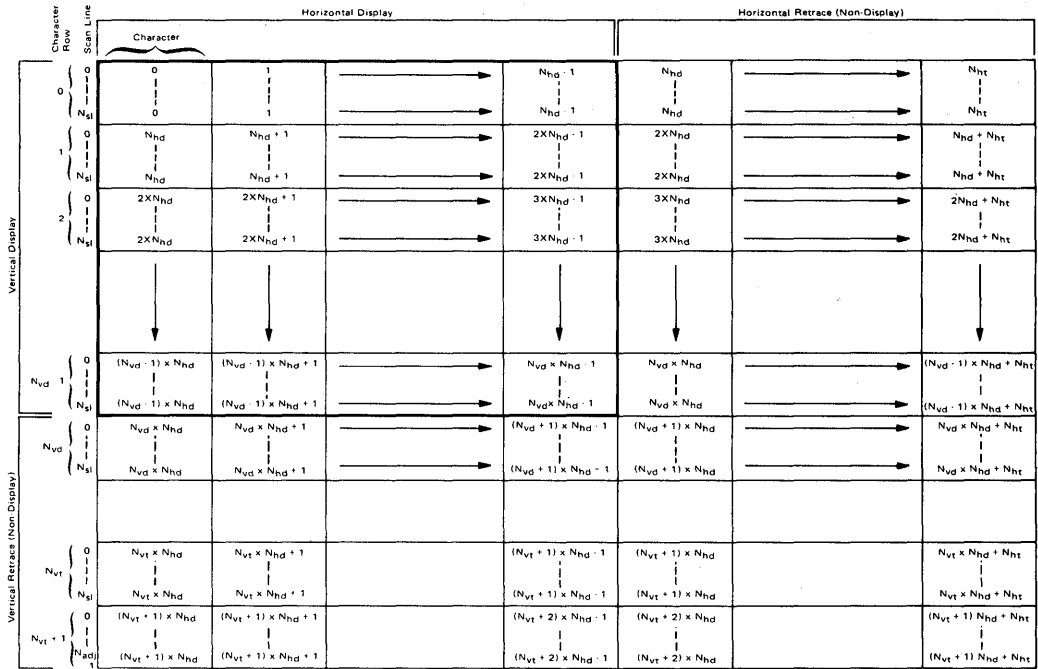
The fourteen output lines allow 16K of memory to be accessed. By incrementing or decrementing the number in the Start Address Register, the screen can be scrolled forward or backward through Display Refresh RAM on a character, line, or page basis.
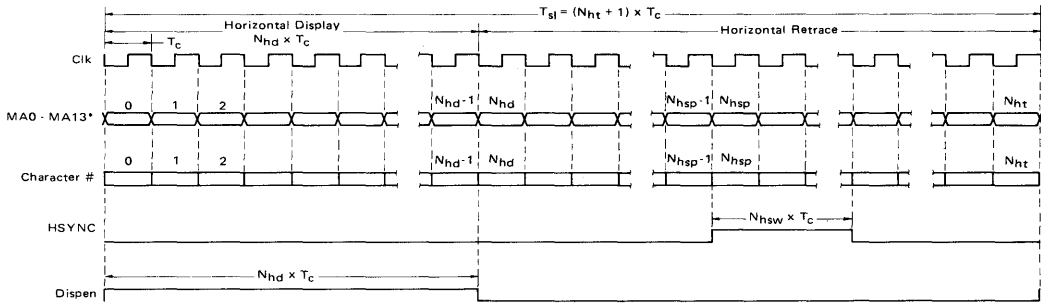
Figure 7. Bus Timing Character

Figure 8. Refresh Memory Addressing (MA0-MA13) State Chart

	Character Row	Scan Line	Horizontal Display					Horizontal Retrace (Non-Display)		
			Character							
Vertical Display	0	0	0	1	⟶	$N_{hd}-1$	N_{hd}	⟶	N_{ht}	
		N_{sl}	0	1	⟶	$N_{hd}-1$	N_{hd}	⟶	N_{ht}	
	1	0	N_{hd}	$N_{hd}+1$	⟶	$2 \times N_{hd}-1$	$2 \times N_{hd}$	⟶	$N_{hd}+N_{ht}$	
		N_{sl}	N_{hd}	$N_{hd}+1$	⟶	$2 \times N_{hd}-1$	$2 \times N_{hd}$	⟶	$N_{hd}+N_{ht}$	
	2	0	$2 \times N_{hd}$	$2 \times N_{hd}+1$	⟶	$3 \times N_{hd}-1$	$3 \times N_{hd}$	⟶	$2N_{hd}+N_{ht}$	
		N_{sl}	$2 \times N_{hd}$	$2 \times N_{hd}+1$	⟶	$3 \times N_{hd}-1$	$3 \times N_{hd}$	⟶	$2N_{hd}+N_{ht}$	
	$N_{vd}-1$	0	$(N_{vd}-1) \times N_{hd}$	$(N_{vd}-1) \times N_{hd}+1$	⟶	$N_{vd} \times N_{hd}-1$	$N_{vd} \times N_{hd}$	⟶	$(N_{vd}-1) \times N_{hd}+N_{ht}$	
		N_{sl}	$(N_{vd}-1) \times N_{hd}$	$(N_{vd}-1) \times N_{hd}+1$	⟶	$N_{vd} \times N_{hd}-1$	$N_{vd} \times N_{hd}$	⟶	$(N_{vd}-1) \times N_{hd}+N_{ht}$	
	N_{vd}	0	$N_{vd} \times N_{hd}$	$N_{vd} \times N_{hd}+1$	⟶	$(N_{vd}+1) \times N_{hd}-1$	$(N_{vd}+1) \times N_{hd}$	⟶	$N_{vd} \times N_{hd}+N_{ht}$	
		N_{sl}	$N_{vd} \times N_{hd}$	$N_{vd} \times N_{hd}+1$		$(N_{vd}+1) \times N_{hd}-1$	$(N_{vd}+1) \times N_{hd}$		$N_{vd} \times N_{hd}+N_{ht}$	
Vertical Retrace (Non Display)	N_{vt}	0	$N_{vt} \times N_{hd}$	$N_{vt} \times N_{hd}+1$		$(N_{vt}+1) \times N_{hd}-1$	$(N_{vt}+1) \times N_{hd}$		$N_{vt} \times N_{hd}+N_{ht}$	
		N_{sl}	$N_{vt} \times N_{hd}$	$N_{vt} \times N_{hd}+1$		$(N_{vt}+1) \times N_{hd}-1$	$(N_{vt}+1) \times N_{hd}$		$N_{vt} \times N_{hd}+N_{ht}$	
	$N_{vt}+1$	0	$(N_{vt}+1) \times N_{hd}$	$(N_{vt}+1) \times N_{hd}+1$		$(N_{vt}+2) \times N_{hd}-1$	$(N_{vt}+2) \times N_{hd}$		$(N_{vt}+1) N_{hd}+N_{ht}$	
		$N_{adj}-1$	$(N_{vt}+1) \times N_{hd}$	$(N_{vt}+1) \times N_{hd}+1$		$(N_{vt}+2) \times N_{hd}-1$	$(N_{vt}+2) \times N_{hd}$		$(N_{vt}+1) N_{hd}+N_{ht}$	

NOTE 1 The initial MA is determined by the contents of start address register, R12/R13. Timing is shown for R12/R13 = 0. Only Non-Interlace and Interlace Sync Modes are shown.
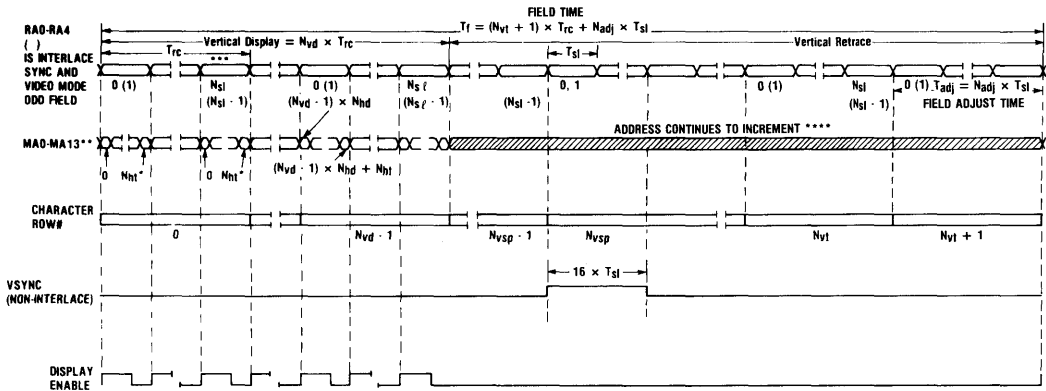
5.146

Figure 9. CRTC Horizontal Timing

$T_{sl} = (N_{ht} + 1) \times T_c$

Horizontal Display
$N_{hd} \times T_c$

Horizontal Retrace

Clk — T_c

MA0 - MA13* — 0 1 2 ... N_{hd}-1 N_{hd} ... N_{hsp}-1 N_{hsp} ... N_{ht}

Character # — 0 1 2 ... N_{hd}-1 N_{hd} ... N_{hsp}-1 N_{hsp} ... N_{ht}

HSYNC — $N_{hsw} \times T_c$

Dispen — $N_{hd} \times T_c$

*Timing is shown for first displayed scan row only.
See Chart in Figure 16 for other rows. The initial
MA is determined by the contents of Start Address
Register, R12/R13. Timing is shown for R12/R13 = 0.

Figure 10. CRTC Vertical Timing

FIELD TIME

$T_f = (N_{vt} + 1) \times T_{rc} + N_{adj} \times T_{sl}$

RA0-RA4
( )
IS INTERLACE
SYNC AND
VIDEO MODE
ODD FIELD

Vertical Display = $N_{vd} \times T_{rc}$ — T_{rc} — Vertical Retrace — T_{sl}

0 (1) N_{sl} 0 (1) $N_{s\ell}$ 0, 1 0 (1) N_{sl} 0 (1) $T_{adj} = N_{adj} \times T_{sl}$
(N_{sl} - 1) (N_{vd} - 1) $\times N_{hd}$ ($N_{s\ell}$ - 1) (N_{sl} -1) (N_{sl} - 1) FIELD ADJUST TIME

ADDRESS CONTINUES TO INCREMENT ****

MA0-MA13** — 0 N_{ht}* 0 N_{ht}* (N_{vd} - 1) $\times N_{hd}$ + N_{ht}

CHARACTER ROW# — 0 N_{vd} - 1 N_{vsp} - 1 N_{vsp} N_{vt} N_{vt} + 1

VSYNC (NON-INTERLACE) — 16 $\times T_{sl}$

DISPLAY ENABLE

* N_{ht} - there must be an even number of character times for both interlace modes.

** Initial MA is determined by R12/R13 (Start Address Register), which is zero
in this timing example.

*** N_{ht} must be an even number of scan lines for Interlace Sync and Video Mode.

S68800

Figure 11. Cursor Timing
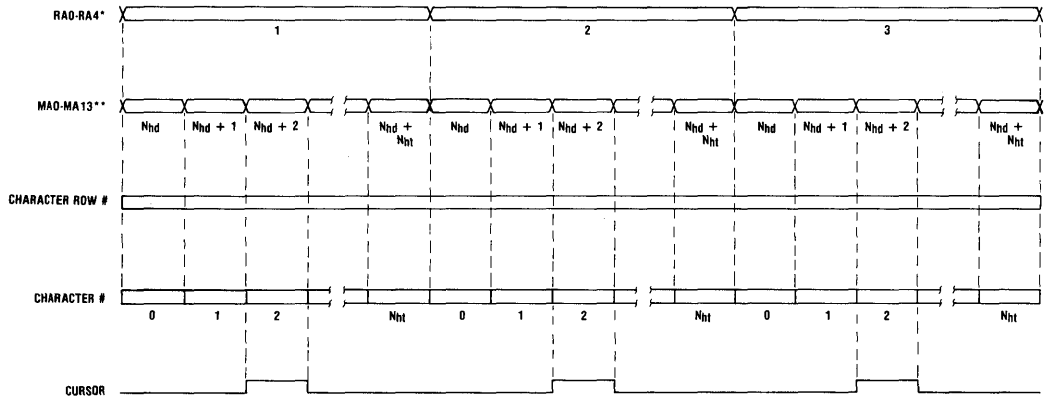
* Timing is shown for non-interlace and interlace sync modes.
  Example shown has cursor programmed as:
      Cursor Register = $N_{hd} + 2$
      Cursor Start   = 1
      Cursor End   = 3

** The initial MA is determined by the contents of Start
  Address Register, R12/R13. Timing is shown for
  R12/R13 = 0.

S68045 ROM Program Worksheet

The value in each register of the MC6845 or SY6545 should be entered without any modifications. AMI will take care of translating into the appropriate format.

☐ All numbers are in decimal.   ☐ All numbers are in hex.

	ROM Program Zero	ROM Program One
R0	_____	_____
R1	_____	_____
R2	_____	_____
R3	_____	_____
R4	_____	_____
R5	_____	_____
R6	_____	_____
R7	_____	_____
R8	_____	_____
R9	_____	_____
R10	_____	_____
R11	_____	_____

Which controller was used to develop the system?

Synertek or Rockwell 6545 ☐
Motorola MC6845 Original ☐   R Version ☐   S Version ☐

S6800

AMI

AMERICAN MICROSYSTEMS, INC.

S6846

ROM-I/O-TIMER

Features

☐ 2048x8-Bit Bytes of Mask-Programmable ROM

☐ 8-Bit Bidirectional Data Port for Parallel Interface Plus Two Control Lines

☐ Programmable Interval Timer-Counter Functions

☐ Programmable I/O Peripheral Data, Control and Direction Registers

☐ Compatible with the Complete S6800 Microcomputer Product Family

☐ TTL-Compatible Data and Peripheral Lines

☐ Single 5 Volt Power Supply

General Description

The S6846 combination chip provides the means, in conjunction with the S6802, to develop a basic 2-chip microcomputer system. The S6846 consists of 2048 bytes of mask-programmable ROM, an 8-bit bidirectional data port with control lines, and a 16-bit programmable timer-counter.

This device is capable of interfacing with the S6802 (basic S6800, clock and 128 bytes of RAM) as well as the S6800 if desired. No external logic is required to interface with most peripheral devices.

The S6846 combination chip may be partitioned into three functional operating sections: programmed storage, timer-counter functions, and a parallel I/O port.

Block Diagram

Pin Configuration
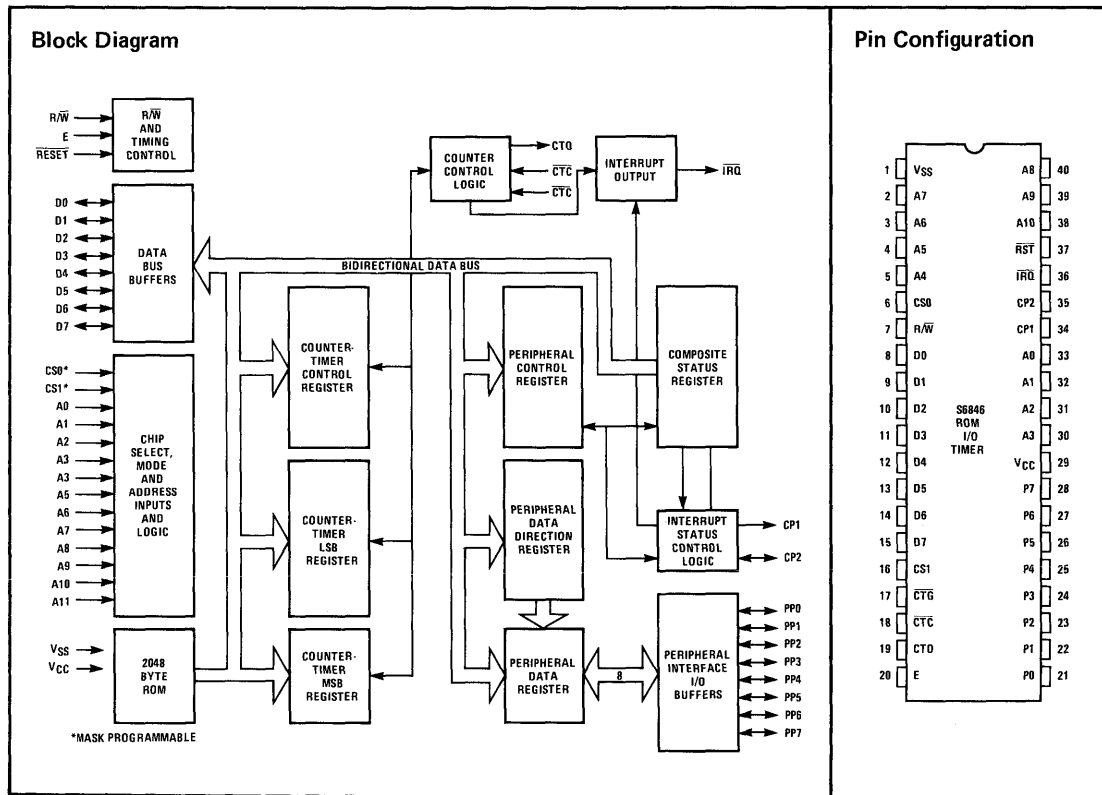
General Description (Continued)

Programmed Storage

The mask-programmable ROM section is similar to other AMI ROM products. The ROM is organized in a 2048 by 8-bit array to provide read only storage for a minimum microcomputer system. Two mask-programmable chip selects are available for user definition.

Address inputs A0-A10 allow any of the 2048 bytes of ROM to be uniquely addressed. Internal registers associated with the I/O functions may be selected with A0, A1 and A2. Bidirectional data lines (D0-D7) allow the transfer of data between the MPU and the S6846.

Timer-Counter Functions

Under software control this 16-bit binary counter may be programmed to count events, measure frequencies and time intervals, or similar tasks. It may also be used for square wave generation, single pulses of controlled duration, and gated delayed signals. Interrupts may be generated from a number of conditions selectable by software programming.

The timer-counter control register allows control of the interrupt enables, output enables, and selection of an internal or external clock source. Input pin $\overline{CTC}$ (counter-timer clock) will accept an asynchronous pulse to be used as a clock to decrement the internal register for the counter-timer. If the divide-by-8 prescaler is used, the maximum clock rate can be four times the master clock frequency with a maximum of 4 MHz. Gate input ($\overline{CTG}$) accepts an asynchronous TTL-compatible signal which may be used as a trigger or gating function to the counter-timer. A counter-timer output ($\overline{CTO}$) is also available and is under software control via selected bits in the timer-counter control register. This mode of operation is dependent on the control register, the gate input, and the external clock.

Parallel I/O Port

The parallel bidirectional I/O port has functional operational characteristics similar to the B port on the S6821 PIA. This includes 8 bidirectional data lines and two handshake control signals. The control and operation of these lines are completely software programmable.

The interrupt input (CP1) will set the interrupt flags of the peripheral control register. The peripheral control (CP2) may be programmed to act as an interrupt input or as a peripheral control output.

Figure 1. Typical Microcomputer
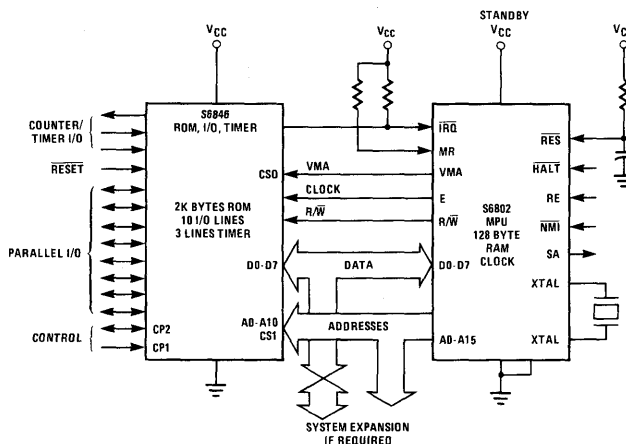
Figure 1 is a block diagram of a typical cost effective microcomputer. The MPU is the center of the microcomputer system and is shown in a minimum system interfacing with a ROM combination chip. It is not intended that this system be limited to this function but that it be expandable with other parts in the S6800 Microcomputer family if desired.

Absolute Maximum Ratings

Supply Voltage .... −0.3Vdc to +7.0Vdc

Input Voltage .... −0.3Vdc to +7.0Vdc

Operating Temperature Range .... 0°C to +70°C

Storage Temperature Range .... −55°C to +150°C

Thermal Resistance .... 70°C/W

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields: however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

Electrical Characteristics (V_{CC} = 5.0V ± 5%, V_{SS} = 0, T_A = 0°C to +70°C unless otherwise noted.)

Symbol	Parameter		Min.	Typ.	Max.	Unit	Conditions
V_{IH}	Input High Voltage	All Inputs	V_{SS} + 2.0		V_{CC}	Vdc	
V_{IL}	Input Low Voltage	All Inputs	V_{SS} −0.3		V_{SS} + 0.8	Vdc	
V_{OS}	Clock Overshoot/Undershoot — Input High Level — Input Low Level		V_{CC} −0.5 V_{SS} −0.5		V_{CC} + 0.5 V_{SS} + 0.5	Vdc	
I_{in}	Input Leakage Current	R/$\overline{W}$, $\overline{Reset}$, CS0, CS1 CP1, $\overline{CTG}$, $\overline{CTC}$, E, A0-A11		1.0	2.5 100	µAdc	V_{in} = 0 to 5.25Vdc
I_{TSI}	Three-State (Off State) Input Current	D0-D7 PP0-PP7, CR2		2.0	10 100	µAdc	V_{in} 0.4 to 2.4Vdc
V_{OH}	Output High Voltage	D0-D7 CP2, PP0-PP7 Other Outputs	V_{SS} + 2.4 V_{SS} + 2.4 V_{SS} + 2.4			Vdc Vdc	I_{Load} = −205µAdc, I_{Load} = −145µAdc, I_{Load} = −100µAdc
V_{OL}	Output Low Voltage	D0-D7 Other Outputs			Vdc V_{SS} + 0.4 V_{SS} + 0.4		I_{Load} = 1.6mAdc I_{Load} = 3.2mAdc
I_{OH}	Output High Current (Sourcing)	D0-D7 Other Outputs CP2, PP0-PP7	−205 −200 −1.0		−10	µAdc mADC	V_{OH} = 2.4Vdc V_O = 1.5Vdc, the current for driving other than TTL, e.g., Darlington Base
I_{OL}	Output Low Current (Sinking)	D0-D7 Other Outputs	1.6 3.2			mAdc	V_{OL} = 0.4Vdc
I_{LOH}	Output Leakage Current (Off State)	$\overline{IRQ}$			10	µAdc	V_{OH} = 2.4Vdc
P_D	Power Dissipation				1000	mW	
C_{in}	Capacitance	 D0-D7 PP0-PP7, CP2 A0-A10, R/$\overline{W}$, $\overline{Reset}$, CS0, CS1, CP1, $\overline{CTC}$, $\overline{CTG}$ $\overline{IRQ}$			20 12.5 10 7.5	pF	V_{in} = 0, T_A = 25°C, f = 1.0MHz
C_{out}		PP0-PP7, CP2, CTO			5.0 10	pF	
f	Frequency of Operation		0.1		1.0	MHz	
t_{cycE} t_{RL} t_{IR}	Clock Timing Cycle Time Reset Low Time Interrupt Release		1.0 2		 1.6	µs µs µs	

AMI

Read/Write Timing

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
PW_{EL}	Enable Pulse Width, Low	430			ns	
PW_{EH}	Enable Pulse Width, High	430			ns	
t_{AS}	Set Up Time (Address CS0, CS1, R/W)	160			ns	
t_{DDR}	Data Delay Time			320	ns	
t_H	Data Hold Time	10			ns	
t_{AH}	Address Hold Time	10			ns	
t_{Ef}, t_{Er}	Rise and Fall Time			25	ns	
t_{DSW}	Data Set Up Time	195			ns	

Bus Timing
Peripheral I/O Lines

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
t_{PDSU}	Peripheral Data Setup	200			ns	
t_{Pr}, t_{Pc}	Rise and Fall Times CP1, CP2			1.0	μs	
t_{CP2}	Delay Time E to CP2 Fall			1.0	μs	
t_{DC}	Delay Time I/O Data CP2 Fall	20			μs	
t_{RS1}	Delay Time E to CP2 Rise			1.0	μs	
t_{RS2}	Delay Time CP1 to CP2 Rise			2.0	μs	
t_{PDW}	Peripheral Data Delay			1.0	μs	

Timer-Counter Lines

t_{CR}, t_{CF}	Input Rise and Fall Time CTC and CTG			100	ns	
t_{PWH}	Input Pulse Width High (Asynchronous Mode)	$t_{cyc} + 250$			ns	
t_{PWL}	Input Pulse Width Low (Asynchronous Mode)	$t_{cyc} + 250$			ns	
t_{su}	Input Setup Time (Synchronous Mode)	200			ns	
t_{hd}	Input Hold Time (Synchronous Mode)	50			ns	
t_{CTO}	Output Delay			1.0	μs	

S6800

Figure 2. Bus Read Timing
(Read Information from S6846)
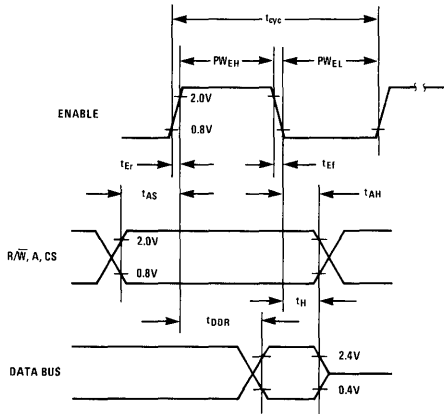
Figure 3. Bus Write Timing
(Write Information from MPU)
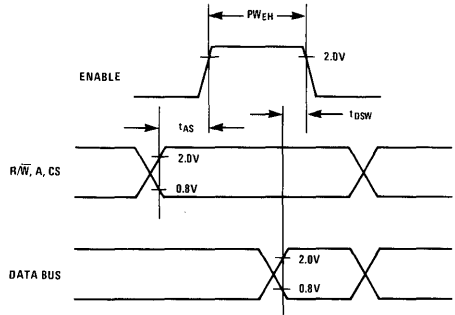
Figure 4. Peripheral Data and CP2 Delay
(Control Mode PCR5 = 1, PCR4 = 0, PCR3 = 1)
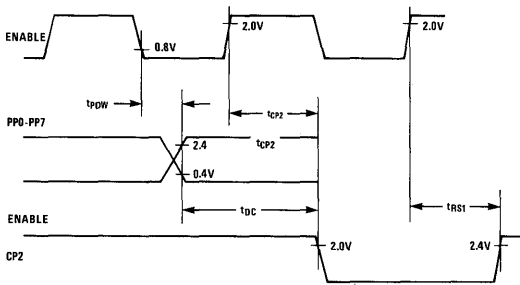
Figure 5. IRQ Release Time
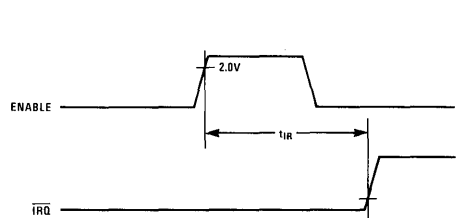
Figure 6. Peripheral Port Setup Time
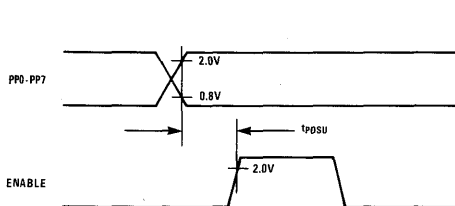
Figure 7. CP2 Delay Time
(PCR5 = 1, PCR4 = 0, PCR3 = 0)
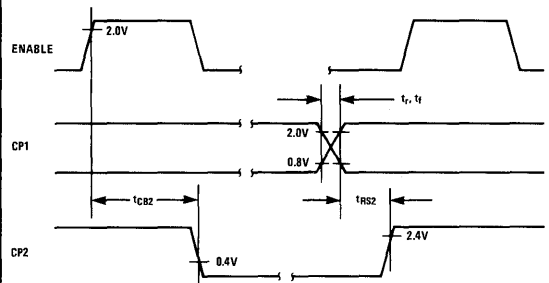
Figure 8. Input Pulse Widths
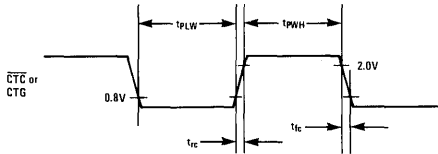
Figure 9. Input Setup and Hold Times
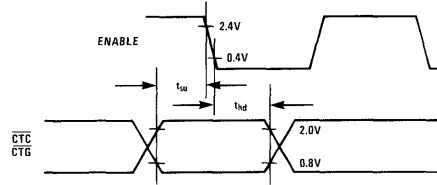
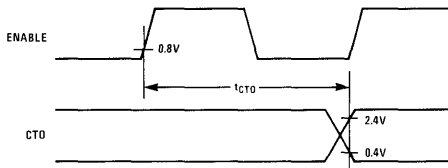NOTE: *This mode is valid only for synchronous operation.*

Figure 10. Output Delay

Figure 11. Bus Timing Test Loads

C = 130pF for D0-D7
= 30pF for CT0, CP2, PP0-PP7
R = 11.7kΩ for D0-D7
= 24kΩ for CT0, CP2, PP0-PP7

S6800
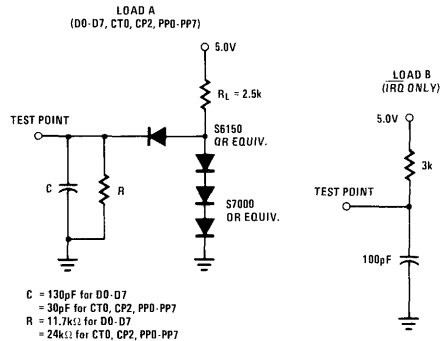
VIDEO DISPLAY GENERATOR

Features

- ☐ 32 x 16 (512 total) Alphanumeric Two Color Display on Black Background with Internal or External Character Generator ROM.
- ☐ Two Semigraphics Modes with Display Densities Ranging from 64 x 32 to 64 x 48 in 8 and 4 Color Sets Respectively, plus Black.
- ☐ Full Graphics Modes with Display Densities Ranging from 64 x 64 to 256 x 192 in 2 and 4 Colors.
- ☐ Full NTSC Compatible Composite Video with Choice of Interlaced and Non-interlaced Display Versions.
- ☐ Provides Microprocessor Compatible Interface Signals.
- ☐ Generates Display Refresh RAM Addresses.
- ☐ NMOS Device, Single 5V Supply, TTL Compatible Logic Levels.
- ☐ Color Set Select Pin Can Give 8 Color Displays in Full Graphics Mode.

General Description

The S68047 Video Display Generator (VDG) is designed to produce composite video suitable for display on a standard American NTSC compatible black/white television or color televison or monitor.

There are three major types of display which the S68047 can generate. These include an alphanumerics mode of which there are two types, each with normal or inverted video; a semigraphics mode of which there are also two types; and full graphics mode of which there are eight types.

Alphanumeric Modes

The alphanumeric modes, internal and external, enable the S68047 to display a matrix of 32 x 16 (512 total) characters. The internal mode utilizes an on-chip 64 ASCII character ROM to display each character in a 5 x 7 dot matrix font. In the external alphanumeric

Block Diagram

Pin Configuration
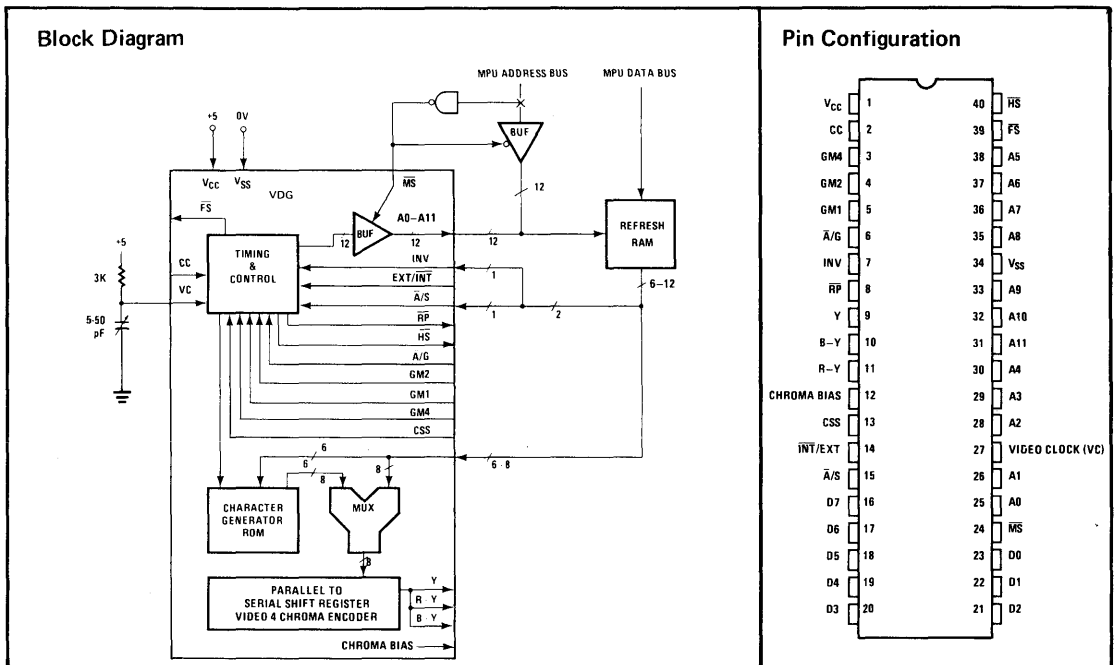
General Description (Continued)

mode, an external memory is required, either ROM or RAM, which is used to display the 32 x 16 character matrix with each character located within an 8 x 12 dot matrix of customized font. Switching between internal and external alphanumerics modes and normal and inverted video can be accomplished on a character by character basis.

Semigraphic Modes

The two semigraphic modes, semigraphic 4 (SG4) and semigraphic 6 (SG6), subdivide each of the 512 (32 x 16) character blocks of 8 x 12 dots each into 2 x 2 and 2 x 3 smaller blocks respectively. In SG4 each block is created from 4 x 6 dots and in SG6 each block consists of 4 x 4 dots. In addition the SG4 and SG6 modes can each be displayed in 8 and 4 colors plus black.

Display switching from alphanumerics to semigraphics modes or vice versa during a raster display is called minor mode switching and can take place on a character basis.

Graphics Modes

The eight full graphics modes are divided into two major groups, 4 color and 2 color. The 4 color graphics provide 4 display densities ranging from 64 x 64 for Graphics 0 through to 128 x 192 elements for Graphics 6. The 2 color graphics also provide 4 display densities ranging from 128 x 64 for Graphics 1 through to 256 x 192 elements for Graphics 7. The latter display has the highest density of the eight graphics modes. The amount of display memory increases proportionately with increasing density of display to a maximum of 6K bytes for Graphics 7. Switching between either the alphanumeric modes or semigraphics modes and any of the full graphics modes is called major mode switching. Major mode switching can only occur at the end of every twelfth raster line scan.

Applications

Anywhere data can be more usefully presented graphically on a CRT and for a minimum cost, the VDG in conjunction with a microprocessor based controller can utilize a standard American NTSC compatible TV or monitor for such a purpose. Applications are extremely broad ranging from educational systems, video games, small low cost business/home computers to process control monitors and medical diagnostic displays.

The different modes of operation permit various cost/display presentation tradeoffs. The alphanumerics modes allow use of the TV screen as a video teletype at the most limited level of operation. Only 512 bytes, one for each character, need to be stored, each byte being a minimum of six bits wide per the ASCII code. If video inversion switching or alpha to semigraphics switching is required per character then two extra bits are required in the display RAM as shown in Fig. 5. The semigraphics modes each offer an intermediate range of graphics densities with tradeoffs in density versus color. Typical semigraphics display capabilities are bar graphs, charts, mini displays, etc. which with minor mode switching to alphanumerics modes allow annotation or captioning of the resultant display. The various graphics modes provide greater density displays with greater freedom of display presentations. The tradeoffs in increasing density are with increasing display memory size and color versus density. A minimum Graphics 0 provides a display density of 64 x 64 (4096) elements, each element being composed of a matrix of 12 (4 x 3) dots with a selection of four colors per element. Since each of the even numbered 4 color graphics modes map two bits of the data word to one picture element, each data word of memory provides four picture elements. Thus Graphics 0 requires 4096/4 = 1024 bytes of display RAM, Graphics 2 requires 8192/4 = 2048 and so on. Graphics 1, like all the odd numbered 2 color graphics modes, maps one bit of data word to one picture element. Each data word therefore maps eight picture elements. Graphics 1 density of 128 x 8 (8192) elements therefore requires 8192/8 = 1024 bytes of display RAM and Graphics 7, the densest display, requires 49, 152/8 = 6144 bytes of RAM. At the higher density graphics displays, the rate of change of elements approaches the maximum dot frequency of 6MHz. This video rate taxes the capabilities of most commercially available television sets and thus the quality of the display system (television or monitor) should be commensurate with the highest video rate to be used.

Electrical Specifications
Absolute Maximum Ratings

Supply Voltage	7.0V
Input Voltage	- 0.3V to +7.0V
Operating Temperature	0°C to 70°C
Storage Temperature	- 65°C to 150°C

DC (Static) Characteristics (V_{CC} = 5.0V ± 5% ; T_A = 25°C, unless otherwise specified).

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
V_{IH}	Input Voltage High	2.0		V_{CC}	V	
V_{IH}	Input Voltage High (Color Clock only)	4.0		V_{CC}	V	
V_{IL}	Input Voltage Low	– 0.3		+0.6	V	
I_{IN}	Input Leakage Current (all inputs)		1.0	2.5	μA	V_{IN} = 0 – 5.25V; V_{CC} = 0V
$I_{L(TS)}$	Tri-State Output Leakage Current (A0 — A11)			10	μA	V_{CC} = 5.25V; $\overline{MS}$ = 0V; V_{IN} = 0.4 – 2.4V
I_{LO}	Output Leakage Current ($\overline{HS}$, $\overline{FS}$, $\overline{RP}$)			10	μA	V_{IN} = 2.4V; V_{CC} = 0V
V_{OH}	Output Voltage High (A0 — A11, $\overline{HS}$, $\overline{FS}$, $\overline{RP}$)	2.4			V	I_{OH} = – 100μA ($\overline{HS}$, $\overline{FS}$, $\overline{RP}$); 0μA (A0 – A11); CL = 30pF
V_{OL}	Output Voltage Low (A0 — A11, $\overline{HS}$, $\overline{FS}$, $\overline{RP}$)			0.4	V	I_{OL} = 1.6mA ($\overline{HS}$, $\overline{FS}$, $\overline{RP}$); 0mA (A0 – A11); CL = 30pF
I_{CC}	V_{CC} Supply Current		45		mA	V_{CC} = 5V; T_A = 25°C
C_{IN}	Input Capacitance			10	pF	V_{IN} = 0, T_A = 25°C; f = 1.0MHz
C_{OUT}	Output Capacitance			12	pF	V_{IN} = 0, T_A = 25°C; f = 1.0MHz

AC Electrical Characteristics (V_{CC} = 5.0V ± 5%; T_A = 0 – 70°C except where noted).

Alpha Internal Mode (Figure 1)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
f_{vc}	Video Clock Frequency	5.6	6.0	6.4	MHz	
t_{ch}	Character Time	1.43	1.33	1.25	μs	
t_{ACC}	Access-Time of External Refresh RAM			0.7	μs	
t_{dot}	Dot Time	178	166	156	ns	

Alpha External Mode (Figure 1)
NOTE: All parameters are the same as in Alpha Internal Mode except t_{ACC}

t_{ACC}	Access-time of Refresh RAM + Access-time of External ROM			0.7	μs	

Semigraphics Mode (Figure 1)

t_{pic}	Picture Element Duration	712	664	624	ns	

NOTE: All other parameters are the same as in Alpha Internal Mode.

Color Sub-carrier Input

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
f_{CC}	Frequency		3.579545 ±10 Hz		MHz	
t_r	Rise Time			10	ns	
t_f	Fall Time			10	ns	
PW_{CC}	Pulse Width		140		ns	
V_{IL}	Zero Level			0.6	V	
V_{IH}	One Level	4.0			V	
DR	Duty Ratio	40%	50%	60%		

Figure 1. Refresh RAM Interface Timing
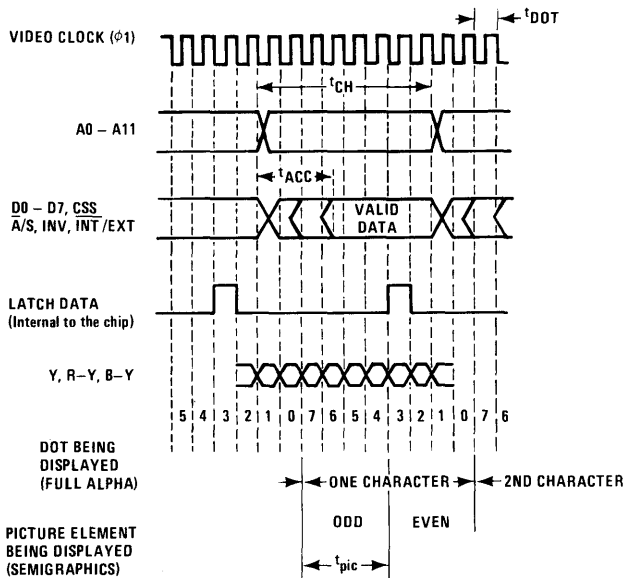
Composite Video Timing (Figure 2)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
t_{SYNC}	Sync duration		4.888889		μs	
t_{fp}	Front Porch duration		1.536508		μs	
t_{BLANK}	Horizontal Blank Duration			11.44	μs	
t_{rs}, t_{fs}	Rise time and Fall time of Horizontal Sync			250	ns	
t_{rv}, t_{fv}	Rise time and Fall time of Horizontal Blank			340	ns	

Figure 2. Composite Video Timing on Y Pin
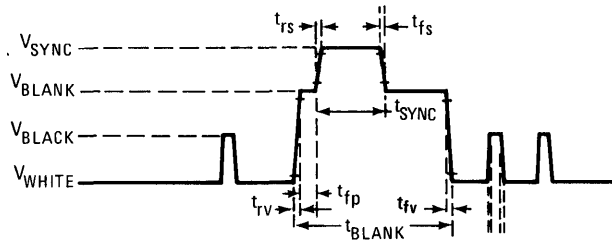
Chroma R and Chroma B Output Timing; $C_L = 10pF$; 1K Load (Figure 3.)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
t_{rB}, t_{fB} t_{rR}, t_{fR}	Color Signals rise and fall time		50		ns	Load = R-Y, B-Y input of LM1889
t_{scB}	Color Burst to Sync lag		410		ns	
t_{BURST}	Color Burst Duration		2.45		μs	
t_{fcB}, t_{rcB}	Color Burst rise and fall times		175		ns	
t_{cL1}, t_{cL2}	Video to color signals lag		75		ns	

Voltage Levels

Video (Y) and Chroma (R—Y, B—Y) Output Levels (Figure 3.) $C_L = 10pF$; Video Clock = 5.6MHz; $T_A = 25°C$; $V_{CC} = 5V \pm 5\%$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{SYNC}	Sync Voltage	0	0.1	0.5	V	
V_{BLANK}	Blanking Level		1.5		V	
V_{BLACK}	Black Level		1.7		V	
V_{WHITE}	White level	2.4	4.0	V_{CC}	V	
V_{B1}, V_{R1}		2.4	4.0	V_{CC}	V	
V_{B0}, V_{R0}			2.0		V	
V_{B3}, V_{R3}		0	0.1	0.5	V	
V_{BURST}			0.4		V	
$V_{CHROMA\ BIAS}$			2.0		V	

Figure 3. Chroma Timing
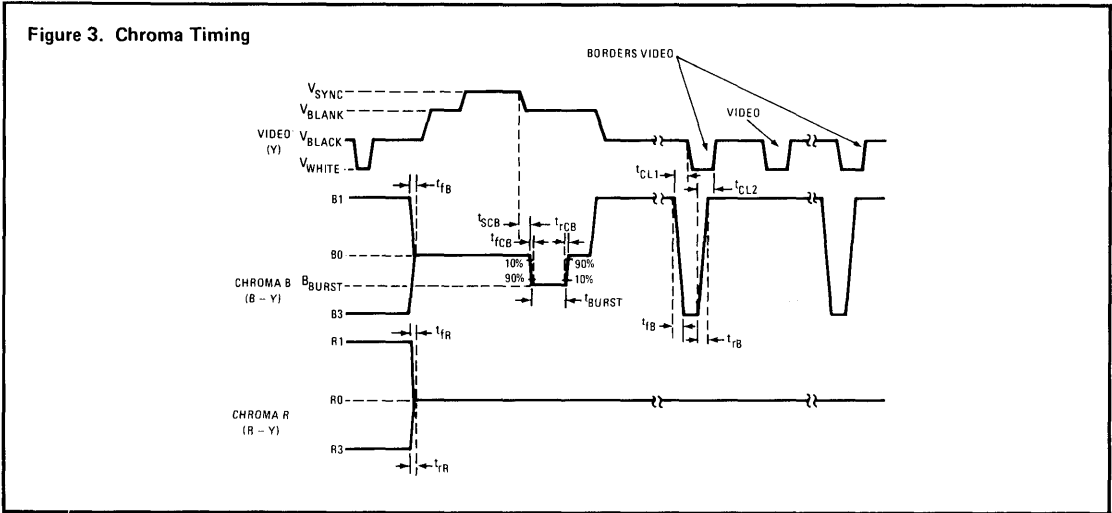
Video Display Format Timing (Figure 4.)

Symbol	Parameter	Typ.	Units	Conditions
H	Horizontal Scan Time	63.55557	μs	
V	Field Time	16.683337	ms	
F	Frame Time	33.366674	ms	
I/V	Field Rate	59.94004	sec^{-1}	
t_{ACTIVE}	Active Display Duration	41	μs	
t_{VIDEO}	Active Display + Border Duration	52.8	μs	
t_{RP}	Row Preset Period (12 Horizontal Scans)	762.66684	μs	

Figure 4. Video Display Format
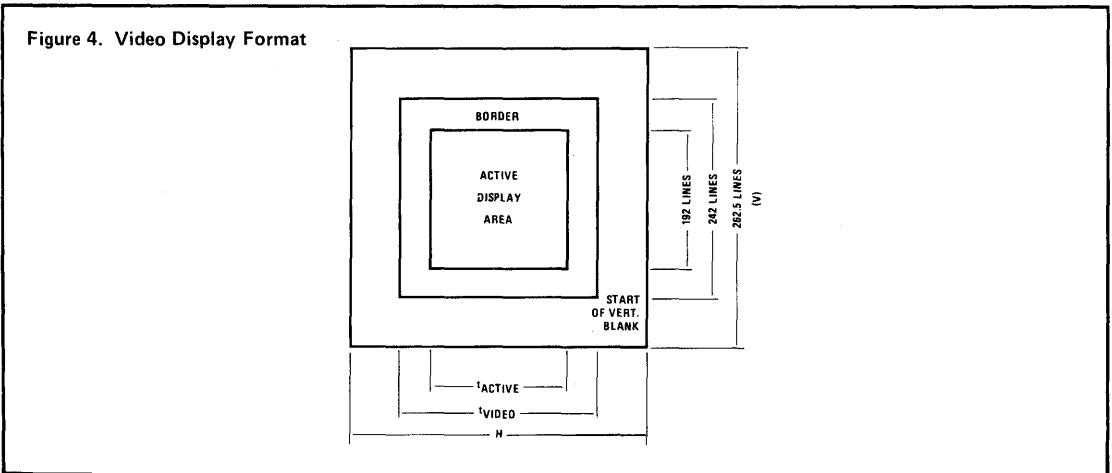
Pin Description (Figure 2.)

V_{CC}	+5V
V_{SS}	0V
CC	(Color Burst Clock 3.579545 MHz)
VC	(Video Clock Oscillator $\cong$ 6MHz)
A0 — A11	(Address Lines to Display Memory; high-impedance during $\overline{MS}$ low)
D0 — D5	(Data from Display Memory RAM or ROM; D4 — D6 — Color Data in Semigraphics)
D6, D7	(Data from Display Memory in GRAPHIC Mode; Data also in ALPHANUMERIC Mode; Color Data in ALPHA SEMIGRAPHIC — 6)
R — Y, B — Y, Y	(Color and Composite Video)
CHB	(Chroma Bias; References R — Y and B — Y Levels)
$\overline{RP}$	(Row Preset in any ALPHA Mode; goes low in all modes every 12 lines)
$\overline{HS}$	(Horizontal Sync)
INV	(Inverts Video in all FULL ALPHA Modes; no effect in Semigraphics or Graphics Mode)
EXT/$\overline{INT}$	(Switches to External ROM in ALPHA Mode; between SEMIG — 4 and SEMIG — 6 in Semigraphics; no effect in all Graphics Modes)
$\overline{A}$/S	(Alpha/Semigraphics: Selects between FULL ALPHA and SEMIGRAPHICS in ALPHA Modes; no effect in all Graphics Modes)
$\overline{MS}$	(Memory Select; forces VDG Address Buffers to high-impedance state; also used as a strobe in TEST and RESET functions). The TV screen is forced black when $\overline{MS}$ = low
$\overline{A}$/G	(Switches between ALPHA and GRAPHIC Modes)
$\overline{FS}$	(Field Synchronization; LOW during vertical blanking time)
CSS	(Color Set Select: Selects between two ALPHA Display Colors; between two Color Sets in SEMIGRAPHICS — 6 and FULL GRAPHICS: selects Border Color in 8 Graphic Modes)
GM1, GM2 GM4	(Graphics Mode Select; select one of eight Graphic Modes; no affect in Alpha and Semigraphic Modes; GM1, GM2 select TEST and RESET mode when $\overline{A}$/G = 0 and $\overline{MS}$ pin is strobed low)

Internal Description

Internally the VDG is the combination of four integrated subsystems (timing and control, MUX, address buffers and shift registers to form the VDG function. A block diagram of the VDG is shown on Page 1. Each subsystem is described below.

Timing and Control

The timing and control subsystem of the VDG uses the 3.58MHz color frequency to generate timing information. It accepts the color clock (generated off-chip) (CC) input and generates timing for the horizontal sync, horizontal blank, field sync, vertical blank and row preset signal ($\overline{RP}$) for external character generator ROM. The video clock is generated on-chip by ex-

ternal RC and generates addresses A0 — A11 to address the external refresh RAM.

The color-set-select (CSS) input to the Timing and Control subsystem of the VDG is used to determine the color-set of the display.

The EXT/$\overline{INT}$ input has two functions. In the full alphanumeric mode, it is used to select either internal ROM or external ROM. It is also used to select between semigraphic 4 and semigraphic 6 mode in semigraphic modes ($\overline{A}$/S = 1).

The INV input is utilized by the timing and control subsystem to invert the display while in full alpha mode.

Internal Description (Continued)

$\overline{A}/G$, $\overline{A}/S$, GM1, GM2, GM4 inputs to the timing and control subsystem determine which of the fourteen VDG modes is to be used (Table 1).

MUX

The MUX provides the function of selecting the data source to be displayed. The source can be either internal ROM or external ROM or RAM. For the internal alphanumeric mode, the data source is the internal ROM. For all other modes (semigraphic and graphics) the data source is external ROM/RAM.

Address Buffers

The address buffers provide the buffering required for external drive (ROM/RAM). The buffers are tri-stated when the $\overline{MS}$ pin goes low and tri-states the buffers so that VDG does not interfere with the MPU operation. The $\overline{FS}$ pin (output) from the VDG signals to the MPU that the TV is in the vertical retrace mode and the MPU can directly change the data in the display memory during that time with no interruption to displayed data.

Shift Registers

The two shift registers serialize bytes coming from internal/external ROM/RAM for conversion to data

on the TV screen. The shift registers output also goes to the chroma encoder circuitry to determine the color of each individual dot. Each shift register has 4-bits.

VDG

The VDG has fourteen modes, grouped in three sets. They are:

4 Alphanumerics Modes   2 Semigraphics Modes

☐ Normal internal alpha   ☐ Semigraphics 4
☐ Inverted internal alpha   ☐ Semigraphics 6
☐ Normal external alpha
☐ Inverted external alpha

8 Full-graphics Modes

☐ 4 Graphics four-color modes
☐ 4 Graphics two-color modes

The six alphanumeric modes can be switched among themselves on a character-by-character basis. Switching within the six alphanumeric modes is referred to as minor-mode switching. All other mode switching is referred to as major-mode switching.

The display can be major-mode switched on after any multiple of twelve rows have been completed. This is signalled to the MPU by $\overline{RP}$ output going low. Switching among the full-graphics modes is permitted at the end of every twelfth row just as in major-mode switching.

Table 1 tabulates the modes of the VDG. The data structures for each mode are listed in Table 7. Table 2 and Table 3 show the Alpha Select Mode and Graphic Select Mode configurations respectively. Table 4 gives the Two-color Graphics and Full-alpha Color Specification. Table 5 shows the semigraphics and Four-color Graphics Color Specification.

Table 1. VDG Modes

	Mode	Description	Memory
I.	ALPHA INTERNAL	32 x 16 BOXES: 5 x 7 CHARACTER	512 x 7 – 8
II.	ALPHA INTERNAL INVERTED	IN 8 x 12 BOX	
III.	ALPHA EXTERNAL	32 x 16 BOXES: 5 x 7 OR 7 x 9 CHARACTERS	512 x 7 – 8
IV.	ALPHA EXTERNAL INVERTED	IN 8 x 12 BOX OR FULL 8 x 12 LIMITED GRAPHICS	
V.	ALPHA SEMIGRAPHICS 4	32 x 16 BOXES: 2 x 2 ELEMENTS PER BOX; EIGHT COLORS PLUS BLACK	512 x 4 – 7
VI.	ALPHA SEMIGRAPHICS 6	32 x 16 BOXES 2 x 3 ELEMENTS PER BOX; FOUR COLORS PLUS BLACK	512 x 6 – 8
VII.	GRAPHICS 0	64 x 64 ELEMENTS: FOUR COLORS PER ELEMENT	1K x 8
VIII.	GRAPHICS 1	128 x 64 ELEMENTS: TWO COLORS PER ELEMENT	1K x 8
IX.	GRAPHICS 2	128 x 64 ELEMENTS: FOUR COLORS PER ELEMENT	2K x 8
X.	GRAPHICS 3	128 x 96 ELEMENTS: TWO COLORS PER ELEMENT	1.5K x 8
XI.	GRAPHICS 4	128 x 96 ELEMENTS: FOUR COLORS PER ELEMENT	3K x 8
XII.	GRAPHICS 5	256 x 96 ELEMENTS: TWO COLORS PER ELEMENT	3K x 8
XIII.	GRAPHICS 6	128 x 192 ELEMENTS: FOUR COLORS PER ELEMENT	6K x 8
XIV.	GRAPHICS 7	256 x 192 ELEMENTS: TWO COLORS PER ELEMENT	6K x 8

Table 7. Detailed Description of VDG Model

VDG PINS								COLOR				TV SCREEN			COMMENTS
A/G	A/S	INT/EXT	GM4	GM2	GM1	CSS	INV	CHARACTER COLOR	BACK-GROUND	BORDER	DISPLAY MODE	DETAIL	VDG DATA BUS		
0	0	0	X	0	0	0 / 1	0 / 1	Green / Black	Black / Green	Black	32 Characters in columns				ALPHANUMERIC INTERNAL mode uses internal character generator with on-chip 64 ASCII character ROM to display each character in 5x7 dot matrix font.
						1	0 / 1	Blue / Black	Black / Blue	Black	16 Characters in rows				
0	0	1	X	0	0	0 / 1	0 / 0	Green / Black	Black / Green	Black	32 Characters in columns				ALPHANUMERIC EXTERNAL mode uses external ROM or RAM to display 512 characters in custom fonts each in 8x12 dot matrix.
						1	0 / 1	Green / Black	Black / Green	Black	16 Characters in rows				
0	1	0	X	0	0	X	X	L_x C_2 C_1 C_0 Color: 0 X X X Black, 1 0 0 0 Green, 1 0 0 1 Yellow, 1 0 1 0 Cyan, 1 0 1 1 Red, 1 1 0 0 Blue, 1 1 0 1 Cyan/Blue, 1 1 1 0 Magenta, 1 1 1 1 Orange		Black	64 Display elements in columns / 32 Display elements in rows				SEMIGRAPHICS 4 mode subdivides each of the 512 (32x16) character blocks of 8x12 dots into four equal parts. The dominance of each block is determined by the corresponding bit (L0-L3) on the VDG data bus. Color of each block is determined by 3 bits (C0-C2).
0	1	1	X	0	0	0 / 1	X	L_x C_1 C_0: 0 0 0 Black, 1 0 0 Green, 1 0 1 Yellow, 1 1 0 Cyan, 1 1 1 Red, 1 0 0 Blue, 1 0 1 Cyan/Blue, 1 1 0 Magenta, 1 1 1 Orange		Black	64 Display elements in columns / 48 Display elements in rows				SEMIGRAPHICS 6 mode subdivides each of the 512 (32x16) character blocks of 8x12 dots into six equal parts. The luminance of each part is determined by the corresponding bits (L0-L5) on the VDG bus. Color of each block is determined by 2 bits (C0, C1).
1	X	X	0	0	0	0 / 1	X	C_1 C_0: 0 0 Green, 0 1 Yellow, 1 0 Cyan, 1 1 Red, 0 0 Blue, 0 1 Cyan/Blue, 1 0 Magenta, 1 1 Orange		Green / Cyan/Blue	64 Display elements in columns / 64 Display elements in rows	EX = C1C0			GRAPHICS 0 mode uses a maximum of 1024 bytes of display RAM in which one pair of bits (C0, C1) specifies on picture element. (Ex.).
1	X	X	0	0	1	0 / 1	X	L_x: 0 Color, 1 Green, 0 Black, 1 Cyan/Blue	Black / Green / Black / Blue	Green / Cyan/Blue	128 Display elements in columns / 64 Display elements in rows				GRAPHICS 1 mode uses a maximum of 1024 bytes of display RAM in which one bit (Lx) specifies one picture element.
1	X	X	1	0	0	0 / 1	X	Same color as Graphics 0		Green / Cyan/Blue	128 Display elements in columns / 64 Display elements in rows				GRAPHICS 2 mode uses a maximum of 2048 bytes of display RAM in which one pair of bits (C0, C1) specifies one picture element (Ex.).
1	X	X	0	1	1	0 / 1	X	Same color as Graphics 1		Green / Cyan/Blue	128 Display elements in columns / 96 Display elements in rows				GRAPHICS 3 mode uses a maximum of 1536 bytes of display RAM in which one bit (Lx) specifies one picture element.
1	X	X	0	1	0	0 / 1	X	Same color as Graphics 0		Green / Cyan/Blue	128 Display elements in columns / 96 Display elements in rows				GRAPHICS 4 mode uses a maximum of 3072 bytes of display RAM in which one pair of bits (C0, C1 specifies one picture element (Ex.)
1	X	X	1	0	1	0 / 1	X	Same color as Graphics 1		Green / Cyan/Blue	256 Display elements in columns / 96 Display elements in rows				GRAPHICS 5 mode uses a maximum of 3072 bytes of display RAM in which one bit (Lx) specifies one picture element.
1	X	X	1	1	0	0 / 1	X	Same color as Graphics 0		Green / Cyan/Blue	128 Display elements in columns / 192 Display elements in rows				GRAPHICS 6 mode uses a maximum of 6144 bytes of display RAM in which one pair of bits (C0, C1) specifies one picture element (Ex.).
1	X	X	1	1	1	0 / 1	X	Same color as Graphics 1		Green / Cyan/Blue	256 Display elements in columns / 192 Display elements in rows				GRAPHICS 7 mode uses a maximum of 6144 bytes of display RAM in which one bit (Lx) specifies one picture element.

Table 2. Alpha Mode Select

GM2	GM1	A̅/G	A̅/S	INT̅/EXT	INV	MS̅	MODE
X	0	0	0	0	0		INTERNAL ALPHANUMERICS
X	0	0	0	0	1		INTERNAL INV. ALPHA
X	0	0	0	1	0		EXTERNAL ALPHA
X	0	0	0	1	1		EXTERNAL INV. ALPHA
X	0	0	1	0	X		SEMIGRAPHICS – 4
X	0	0	1	1	X		SEMIGRAPHICS – 6
0	1	0	X	X	X	STROBED LOW	TEST ROM
1	1	0	X	X	X	STROBED LOW	RESET

NOTES:
1) GM4 pin has no effect when A̅/G = 0.
2) Invert pin has no effect except in Internal Alpha or External Alpha.
3) Under normal operation, care should be taken not to take GM1 pin HIGH, when A̅/G pin is LOW. If this happens, any of the following conditions will occur depending on the status of MS̅ and GM2 pin:
   a) The VDG might go to TEST mode.
   b) The VDG might be reset.
   The VDG will not return to normal operation unless A̅/G and GM1 pins are returned to LOW level and MS̅ pin is strobed.
4) X = Don't care.

Table 3. Graphic Mode Select

	A̅/G	GM4	GM2	GM1	MODE
GRAPHICS 0	1	0	0	0	64 x 64 4 – COLOR
GRAPHICS 1	1	0	0	1	128 x 64 2 – COLOR
GRAPHICS 2	1	0	1	0	128 x 64 4 – COLOR
GRAPHICS 3	1	0	1	1	128 x 96 2 – COLOR
GRAPHICS 4	1	1	0	0	128 x 96 4 – COLOR
GRAPHICS 5	1	1	0	1	256 x 96 2 – COLOR
GRAPHICS 6	1	1	1	0	128 x 192 4 – COLOR
GRAPHICS 7	1	1	1	1	256 x 192 2 – COLOR

NOTE: A̅/S, INT̅/EXT, INV pins have no effect when A̅/G = 1.

Table 4. Two-Color Graphics and Full-Alpha Color Specification

	CSS PIN	COLOR OF 'ON' DOTS
	0	GREEN
	1	CYAN-BLUE

Table 5. Semigraphics and Four-Color Graphics Color Specification

4-COLOR GRAPHICS	SEMI-GRAPHICS – 6	SEMI-GRAPHICS – 4
EVEN BIT	D6	D4
ODD BIT	D7	D5
CSS	CSS	CSS

COLOR SET 1	0	0	0	GREEN
	0	0	1	YELLOW
	0	1	0	CYAN
	0	1	1	RED
COLOR SET 2	1	0	0	BLUE
	1	0	1	CYAN/BLUE
	1	1	0	MAGENTA
	1	1	1	ORANGE

NOTE: In Semigraphics—6, if any bit D0—D5 is '0', then the picture element corresponding to that bit would be black. In Semigraphics—4, if any bit D0—D3 is zero, then the picture element corresponding to that dot will be black.

Table 6. Two-Color Graphics and Four-Color Graphics Border Color Specification

CSS PIN	BORDER COLOR
0	GREEN
1	CYAN-BLUE

Typical System: A typical S6800 microprocessor based S68047 system is shown on Figure 6. This system has the capability of displaying internally and externally generated characters, semigraphics 4 and 6 modes with mode switching control from the microcomputer input/output ports. A full graphics system configuration would be similar in complexity with possibly additional display RAM for the denser graphics modes. The National Semiconductor LM1889RF modulator shown, has an on-chip 3.58MHz oscillator which can provide the microcomputer system clock as well as the color burst reference for the S68047. Other RF modulators are available through various commercial channels. Only 512 bytes are needed to display the 512 character blocks on a TV screen. However, because of current static RAM configurations (i.e., 1Kx1 & 1Kx4) the extra 512 bytes available in the 1Kx9 RAM shown can be used as scratchpad by the host microcomputer system.

Figure 5.

GRAPHICS 6 AND GRAPHICS 7 REQUIRE CK OF DISPLAY RAM, THUS THIRTEEN ADDRESS LINES THE VDG PROVIDES A_0—A_{11}. HOWEVER A_{12} MUST BE GENERATED EXTERNALLY AS SHOWN IN FIGURE 5.
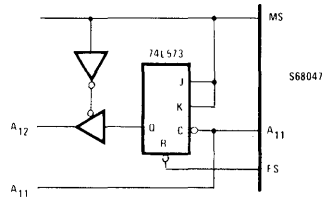
Ordering Information

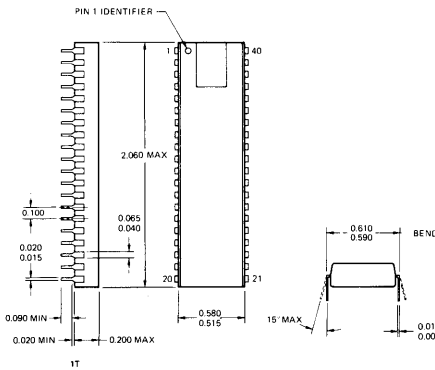| Ordering Number	Number Pins	Package	Temp. Range	Description
S68047	40	Ceramic	0–70°C	VDG non-interlaced
S68047P	40	Plastic	0–70°C	VDG non-interlaced
S68047Y	40	Ceramic	0–70°C	VDG interlaced
S68047YP	40	Plastic	0–70°C	VDG interlaced

S6800

Figure 6. Typical System (Alphanumeric Internal/External & Semigraphics 4 and 6 Modes.)
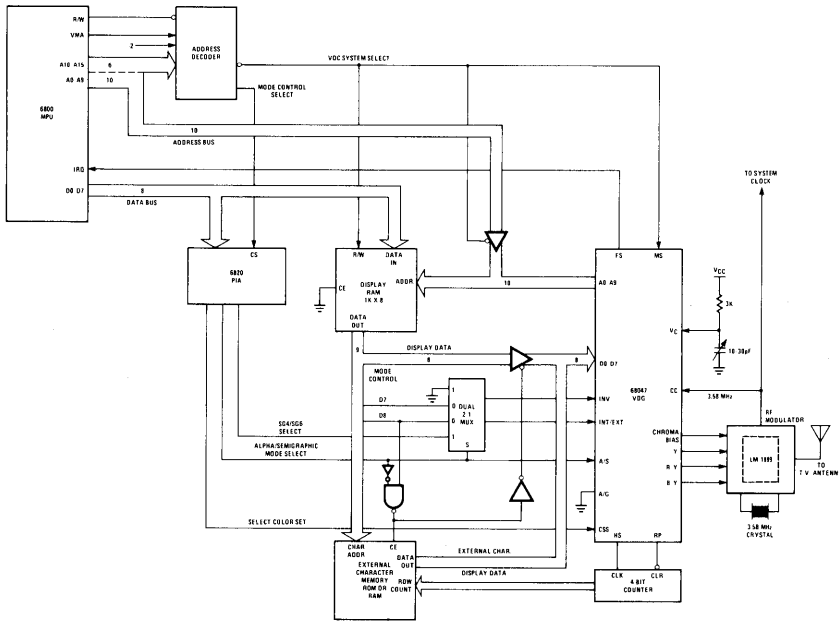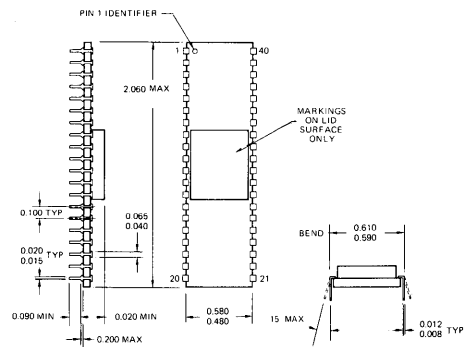

Physical Dimensions

40-Pin Plastic

40-Pin SLAM

# ASYNCHRONOUS COMMUNICATION INTERFACE ADAPTER (ACIA)

Features

- 8 Bit Bidirectional Data Bus for Communication with MPU
- False Start Bit Deletion
- Peripheral/Modem Control Functions
- Double Buffered Receiver and Transmitter
- One or Two Stop Bit Operation
- Eight and Nine-Bit Transmission with Optional Even and Odd Parity
- Parity, Overrun and Framing Error Checking
- Programmable Control Register
- Optional ÷1, ÷16, and ÷64 Clock Modes
- Up to 500,000 bps Transmission

General Description

The S6850/S68A50/S68B50 Asynchronous Communications Interface Adapater (ACIA) provices the data formatting and control to interface serial asynchronous data communications to bus organized systems such as the S6800/S68A00/S68B00 Microprocessing Units.

The S6850/S68A50/S68B50 includes select enable, read/write, interrupt and bus interface logic to allow data transfer over an eight-bit bidirectional data bus. The parallel data of the bus system is serially transmitted and received by the asynchronous data interface, with proper formatting and error checking. The functional configuration of the ACIA is programmed via the data bus during system initialization. Word lengths, clock division ratios and transmit control through the Request-to-Send output may be programmed. For modem operation three control lines are provided.
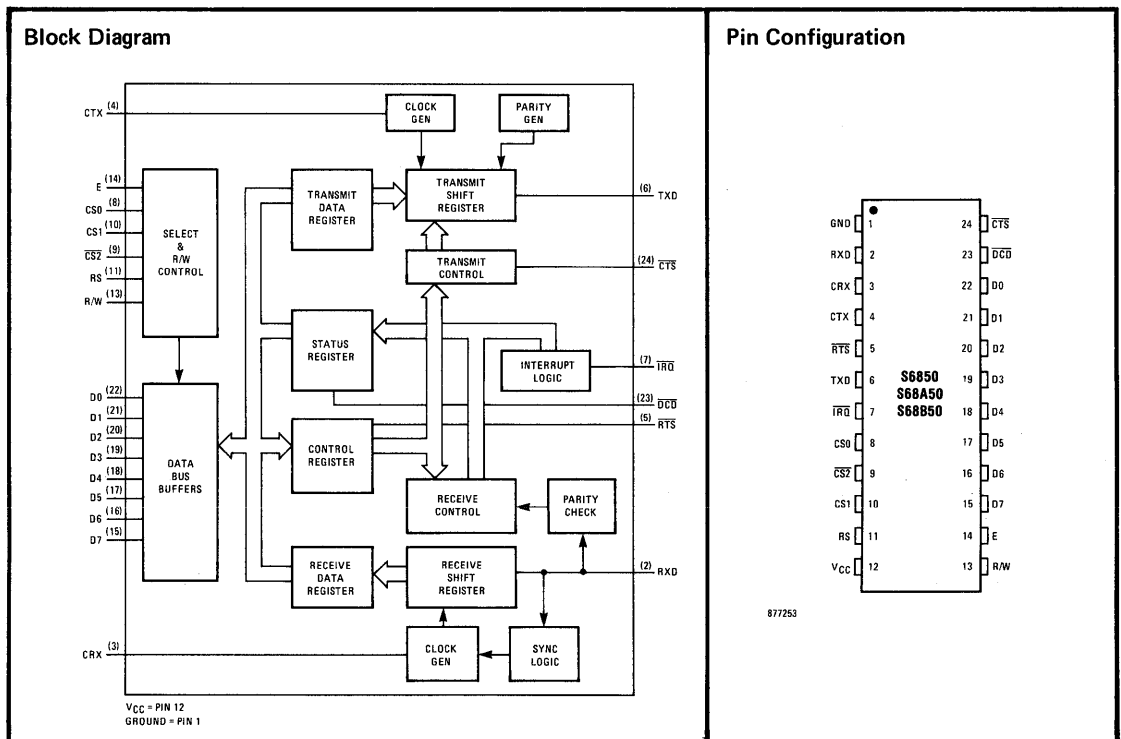
Block Diagram

Pin Configuration

Absolute Maximum Ratings

Supply Voltage .... −0.3V to +7.0V
Input Voltage .... −0.3V to +7.0V
Operating Temperature Range .... 0°C to +70°C
Storage Temperature Range .... −55°C to +150°C

Note:
This device contains circuitry to protect the inputs against damage due to high static voltages or electrical fields, however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Electrical Characteristics (V_{CC} = +5.0V ±5%, V_{SS} = 0, T_A = 0°C to +70°C unless otherwise noted.)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{IH}	Input High Voltage (normal operating level)	V_{SS}+2.0		V_{CC}	Vdc	
V_{IL}	Input Low Voltage (normal operating level)	V_{SS}−0.3		V_{SS}+0.8	Vdc	
I_{IN}	Input Leakage Current R/W, ES, CS0, CS1, $\overline{CS2}$, Enable		1.0	2.5	μAdc	V_{IN} = 0Vdc to 5.25Vdc
I_{TSI}	Three-State (Off State) Input Current D0-D7		2.0	10	μAdc	V_{IN} = 0.4Vdc to 2.4Vdc
V_{OH}	Output High Voltage (all outputs except IRQ) D0-D7	V_{SS}+2.4			Vdc	I_{LOAD} = −205μAdc, Enable Pulse Width <25μs
	Tx Data, $\overline{RTS}$	V_{SS}+2.4			Vdc	I_{LOAD} = −100μAdc, Enable Pulse Width <25μs
V_{OL}	Output Low Voltage (Enable pulse width < 25μs)			V_{SS}+0.4	Vdc	I_{LOAD} = 1.6mAdc, Enable Pulse Width <25μs
I_{LOH}	Output Leakage Current (Off State) $\overline{IRQ}$		1.0	10	μAdc	V_{OH} = 2.4Vdc
P_D	Power Dissipation		300	525	mW	
C_{IN}	Input Capacitance D0-D7		10	12.5	pF	
	E,Tx,CLK,Rx Clk,R/W,RS,Rx Data, CS0,$\overline{CS1}$,$\overline{CS2}$,RXD,CTS,$\overline{DCD}$,CTX,CRX		7.0	7.5	pF	V_{IN} = 0, T_A = 25°C, f = 1.0MHz
C_{OUT}	Output Capacitance $\overline{RTS}$,Tx Data			10	pF	
	$\overline{IRQ}$			5.0	pF	
PW_{CL}	Minimum Clock Pulse Width, Low ÷16, ÷64 Modes	600			ns	
PW_{CH}	Minimum Clock Pulse Width, High ÷16, ÷64 Modes	600			ns	
f_C	Clock Frequency ÷1 Mode			500	kHz	
	÷16, ÷64 Modes			800	kHz	
t_{TDD}	Clock-to-Data Delay for Transmitter			1.0	μs	
t_{RDSU}	Receive Data Setup Time ÷1 Mode	500			ns	
t_{RDH}	Receive Data Hold Time ÷1 Mode	500			ns	
t_{IR}	Interrupt Request Release Time			1.2	μs	
t_{RTS}	Request-to-Send Delay Time			1.0	μs	
t_r,t_f	Input Transition Times (Except Enable)			1.0*	μs	

*1.0μ or 10% of the pulse width, whichever is smaller.

Bus Timing Characteristics ($V_{CC} = +5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to $+70°C$ unless otherwise noted.)

Read

Symbol	Characteristic	S6850 Min.	S6850 Max.	S68A50 Min.	S68A50 Max.	S68B50 Min.	S68B50 Max.	Unit
t_{CYCF}	Enable Cycle Time	1.0		0.666		0.50		μs
PW_{EH}	Enable Pulse Width, High	0.45		0.28		0.22	25	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.28		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DDR}	Data Delay Time		320		220		180	ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

Write

Symbol	Characteristic	S6850 Min.	S6850 Max.	S68A50 Min.	S68A50 Max.	S68B50 Min.	S68B50 Max.	Unit
t_{CYCE}	Enable Cycle Time	1.0		0.666		0.50		μs
PW_{EH}	Enable Pulse Width, High	0.45		0.28		0.22	25	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.28		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DSW}	Data Setup Time	195		80		60		ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

Figure 1. Clock Pulse Width, Low State
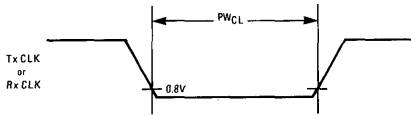
Tx CLK
or
Rx CLK

PW_{CL}

0.8V

Figure 2. Clock Pulse Width, High State

Tx CLK
or
Rx CLK

2.0V

PW_{CH}

Figure 3. Transmit Data Output Delay

Tx CLK

0.8V

t_{TDD}

Tx DATA

2.4V

0.4V
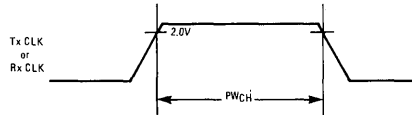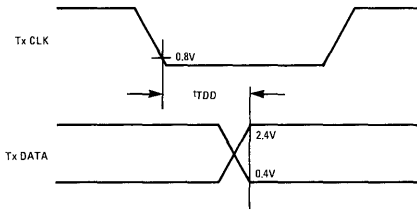
Figure 4. Receive Data Setup Time
(÷1 Mode)

Rx DATA

2.0V

0.8V

t_{RDSU}

Rx CLOCK

0.8V
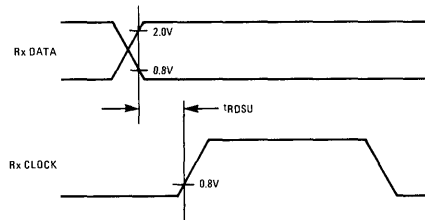
Figure 5. Receive Data Hold Time
(÷1 Mode)

Rx CLK

2.0V

t_{RDH}

Rx DATA

2.0V

0.8V
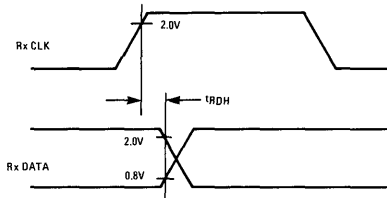
Figure 6. Request-to Send Delay and
Interrupt-Request Release Times

ENABLE

0.8V

t_{RTS}

$\overline{RTS}$

2.4V

0.4V

t_{IR}

$\overline{IRQ}$

2.4V
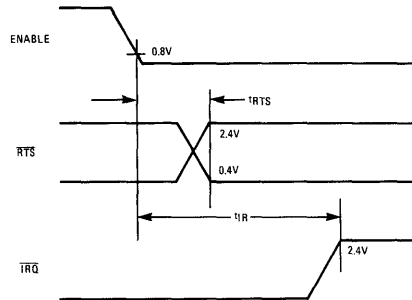
Figure 7. Bus Read Timing Characteristics
(Read Information from ACIA)

t_{cycE}

t_{AS}

ENABLE

PW_{EH}

PW_{EL}

2.0V

0.8V

t_{Er}

t_{Ef}

t_{DDR}

RS, CS, R/W

2.0V

0.8V

t_{AH}

t_H

DATA BUS

2.4V

0.4V
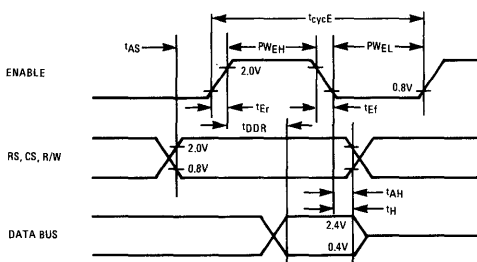
Figure 8. Bus Write Timing Characteristics
(Write Information into ACIA)

t_{cycE}

t_{AS}

ENABLE

PW_{EH}

PW_{EL}

2.0V

0.8V

t_{Er}

t_{Ef}

t_{DSW}

RS, CS, R/W

2.0V

0.8V

t_{AH}

t_H

DATA BUS

2.0V

0.8V

S6800

Bus Timing Test Loads

LOAD A
(D0-D7, $\overline{RTS}$, Tx DATA)

LOAD B
($\overline{IRQ}$ ONLY)

5.0V

R_L = 2.5k

TEST POINT

MMD6150
OR EQUIV.

C   R

MMD7000
OR EQUIV.

5.0V

3k

TEST POINT

100pF

877251

C = 130pF FOR D0-D7
= 30pF FOR $\overline{RTS}$ AND Tx DATA

R = 11.7kΩ FOR D0-D7
= 24kΩ FOR $\overline{RTS}$ AND Tx DATA

Expanded Block Diagram

TRANSMIT CLOCK 4

ENABLE 14

READ/WRITE 13

CHIP SELECT 0 8

CHIP SELECT 1 10

$\overline{CHIP\ SELECT\ 2}$ 9

REGISTER SELECT 11

CHIP SELECT AND READ/WRITE CONTROL

CLOCK GEN

PARITY GEN

TRANSMIT DATA REGISTER

TRANSMIT SHIFT REGISTER

6 TRANSMIT DATA

TRANSMIT CONTROL

24 $\overline{CLEAR\text{-}TO\text{-}SEND}$

D0 22

D1 21

D2 20

D3 19

D4 18

D5 17

D6 16

D7 15

DATA BUS BUFFERS

STATUS REGISTER

INTERRUPT LOGIC

7 $\overline{INTERRUPT\ REQUEST}$

23 $\overline{DATA\ CARRIER\ DETECT}$

5 $\overline{REQUEST\text{-}TO\text{-}SEND}$

CONTROL REGISTER

RECEIVE CONTROL

PARITY CHECK

V_{DD} = PIN 12
V_{SS} = PIN 1

RECEIVE DATA REGISTER

RECEIVE SHIFT REGISTER

2 RECEIVE DATA

RECEIVE CLOCK 3

CLOCK GEN

SYNC LOGIC

877252

5.172

AMERICAN MICROSYSTEMS, INC.

SYNCHRONOUS SERIAL DATA ADAPTER (SSDA)

Features

☐ Programmable Interrupts from Transmitter, Receiver, and Error Detection Logic

☐ Character Synchronization on One or Two Sync Codes

☐ External Synchronization Available for Parallel-Serial Operation

☐ Programmable Sync Code Register

☐ Up to 600kbps Transmission

☐ Peripheral/Modem Control Functions

☐ Three Bytes of FIFO Buffering on Both Transmit and Receive

☐ Seven, Eight, or Nine Bit Transmission

☐ Optional Even and Odd Parity

☐ Parity, Overrun, and Underflow Status

☐ Clock Rates:
1.0MHz
1.5MHz
2.0MHz

General Description

The S6852 Synchronous Serial Data Adapter provides a bi-directional serial interface for synchronous data information interchange. It contains interface logic for simultaneously transmitting and receiving standard synchronous communications characters in bus organized systems such as the S6800 Microprocessor systems.

The bus interface of the S6852 includes select, enable, read/write, interrupt, and bus interface logic to allow data transfer over an 8-bit bi-directional data bus. The parallel data of the bus system is serially transmitted and received by the synchronous data interface with synchronization, fill character insertion/deletion, and error checking. The functional configuration of the SSDA is programmed via the data bus during system initialization. Programmable control registers provide control for variable word lengths, transmit control, receive control, synchronization control, and interrupt control. Status, timing and control lines provide peripheral or modem control.

Typical applications include floppy disk controllers, cassette or cartridge tape controllers, data communications terminals, and numerical control systems.

S6800

Block Diagram

Pin Configuration

	S6852 S68A52 S68B52	
1 Vss		CTS 24
2 Rx DATA		DCD 23
3 Rx Clk		D0 22
4 Tx Clk		D1 21
5 SM/DTR		D2 20
6 Tx DATA		D3 19
7 IRQ		D4 18
8 TUF		D5 17
9 RESET		D6 16
10 CS		D7 15
11 RS		E 14
12 VDD		R/W 13
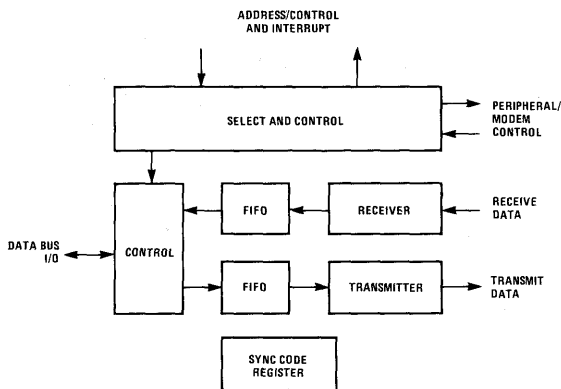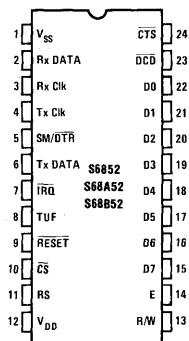
Absolute Maximum Ratings:

Supply Voltage .... −0.3 to +7.0
Input Voltage .... −0.3 to +7.0V
Operating Temperature Range .... 0° to +70°C
Storage Temperature Range .... −55° to +150°C
Thermal Resistance .... +70°C/W

Note:
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Electrical Characteristics ($V_{CC} = 5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to $70°C$ unless otherwise noted.)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
V_{IH}	Input High Voltage	$V_{SS}+2.0$			Vdc
V_{IL}	Input Low Voltage			$V_{SS}+0.8$	Vdc
I_{IN}	Input Leakage Current $\quad$ TxClk, Rx Clk, Rx Data, Enable ($V_{IN}=0$ to 5.25Vdc) $\quad$ $\overline{Reset}$, RS, R/$\overline{W}$, $\overline{CS}$, $\overline{DCD}$, $\overline{CTS}$		1.0	2.5	μAdc
I_{TSI}	Three State (Off State) Input Current $\quad$ D0-D7 ($V_{IN}=0.4$ to 2.4Vdc, $V_{CC}=5.25$Vdc)		2.0	10	μAdc
V_{OH}	Output High Voltage $\quad$ $I_{LOAD}=-205$μAdc, Enable Pulse Width < 25μs $\quad$ D0-D7 $\quad$ $I_{LOAD}=-100$μAdc, Enable Pulse Width < 25μs $\quad$ Tx Data, $\overline{DTR}$, TUF	$V_{SS}+2.4$ $V_{SS}+2.4$			Vdc Vdc
V_{OL}	Output Low Voltage $\quad$ $I_{LOAD}=1.6$mAdc, Enable Pulse Width < 25μs			$V_{SS}+0.4$	Vdc
I_{LOH}	Output Leakage Current (Off State) $\quad$ $\overline{IRQ}$ $\quad$ $V_{OH}=2.4$Vdc		1.0	10	μAdc
P_D	Power Dissipation		300	525	mW
C_{IN}	Input Capacitance $\quad$ ($V_{IN}=0,T_A=25°C$, f=1.0MHz) $\quad$ D0-D7 $\quad$ All Other Inputs			12.5 7.5	pF
C_{OUT}	Output Capacitance $\quad$ Tx Data, SM/$\overline{DTR}$, TUF $\quad$ ($V_{IN}=0$, $T_A=25°C$, f=1.0MHz) $\quad$ $\overline{IRQ}$			10 5.0	pF

Electrical Characteristics ($V_{CC} = 5.0V \pm 5\%$, $T_A = T_L$ to T_H unless otherwise noted.)

Symbol	Characteristic	S6852		S68A52		S68B52		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
PW_{CL}	Minimum Clock Pulse Width, Low (Figure 1)	700		400		280		ns
PW_{CH}	Minimum Clock Pulse Width, High (Figure 2)	700		400		280		ns
f_C	Clock Frequency		600		1000		1500	kHz
t_{RDSU}	Receive Data Setup Time (Figure 3, 7)	350		200		160		ns
t_{RDH}	Receive Data Hold Time (Figure 3)	350		200		160		ns
t_{SM}	Sync Match Delay Time (Figure 3)		1.0		0.666		0.500	μs
t_{TDD}	Clock-to-Data Delay for Transmitter (Figure 4)		1.0		0.666		0.500	μs

*10μs or 10% of the pulse width, whichever is smaller.

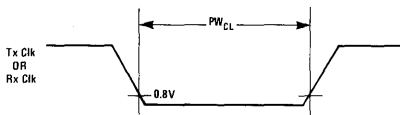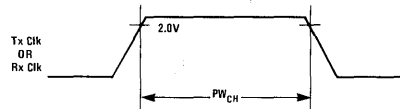| Figure 1. Clock Pulse Width, Low-State	Figure 2. Clock Pulse Width, High-State

Figure 1. Clock Pulse Width, Low-State

Figure 2. Clock Pulse Width, High-State

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Electrical Characteristics-Continued (V_{CC} = 5.0V ± 5%, T_A = T_L to T_H unless otherwise noted.)

Symbol	Characteristic	S6852 Min.	S6852 Max.	S68A52 Min.	S68A52 Max.	S68B52 Min.	S68B52 Max.	Unit
t_{TUF}	Transmitter Underflow (Figure 4, 6)		1.0		0.666		0.500	μs
t_{DTR}	DTR Delay Time (Figure 5)		1.0		0.666		0.500	μs
t_{IR}	Interrupt Request Release Time (Figure 5)		1.2		0.800		0.600	μs
t_{Res}	Reset Minimum Pulse Width	1.0		0.666		0.500		μs
t_{CTS}	CTS Setup Time (Figure 6)	200		150		120		ns
t_{DCD}	DCD Setup Time (Figure 7)	500		350		250		ns
t_r, t_f	Input Rise and Fall Times (except Enable) (0.8V to 2.0V)		1.0		1.0		1.0	μs

Bus Timing Characteristics

Symbol	Characteristic	S6852 Min.	S6852 Max.	S68A52 Min.	S68A52 Max.	S68B52 Min.	S68B52 Max.	Unit
Read								
t_{CYCE}	Enable Cycle Time	1.0		0.666		0.5		μs
PW_{EH}	Enable Pulse Width, High	0.45	25	0.28	25	0.22	25	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.28		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DDR}	Data Delay Time		320		220		180	ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns
Write								
t_{CYCE}	Enable Cycle Time	1.0		0.666		0.5		μs
PW_{EH}	Enable Pulse Width, High	0.45	25	0.28	25	0.22	25	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.28		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DSW}	Setup Time	195		80		60		ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

Figure 3. Receive Data Setup and Hold Times and Sync Delay Time
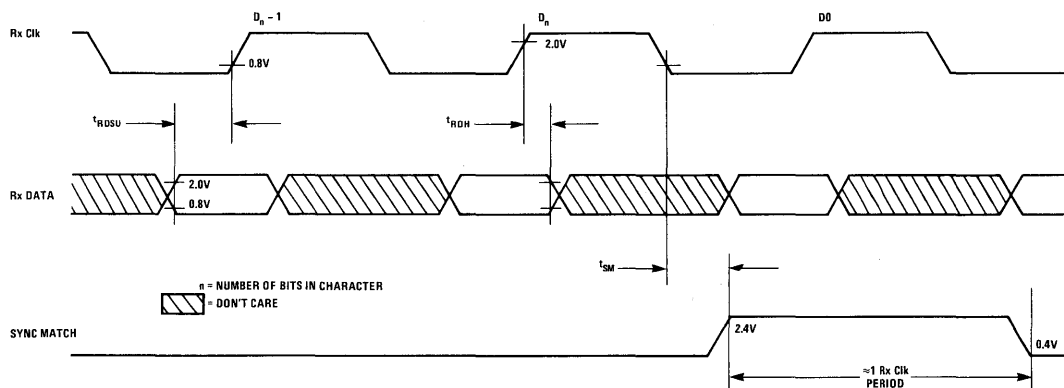
Figure 4. Transmit Data Output Delay and Transmitter Underflow Delay Time

n = NUMBER OF BITS IN CHARACTER
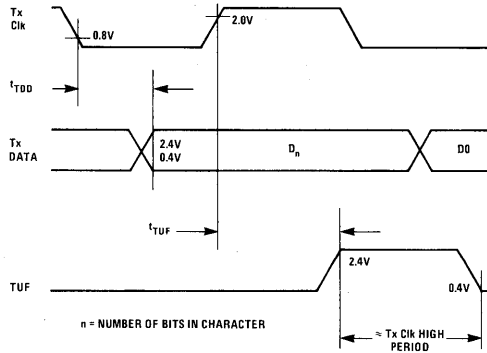
Figure 5. Data Terminal Ready and Interrupt Request Release Times
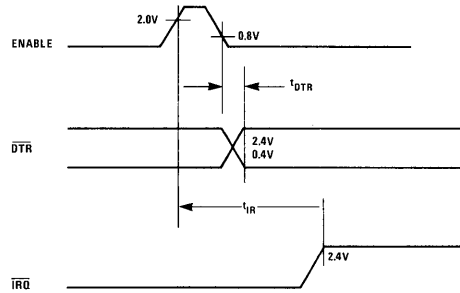
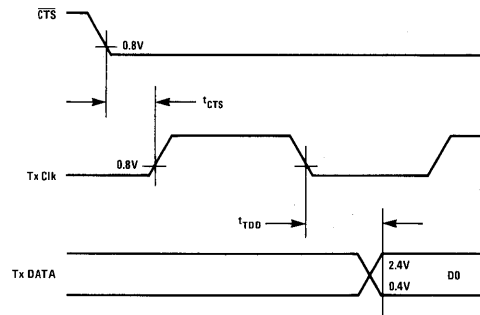Figure 6. Clear-To-Send Setup Time
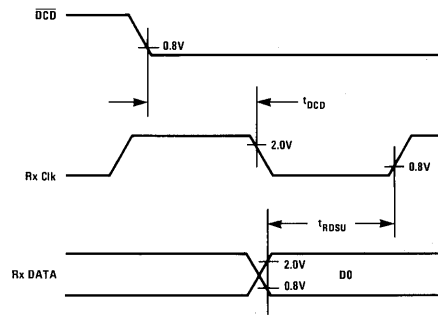

Figure 7. Data Carrier Detect Setup Time

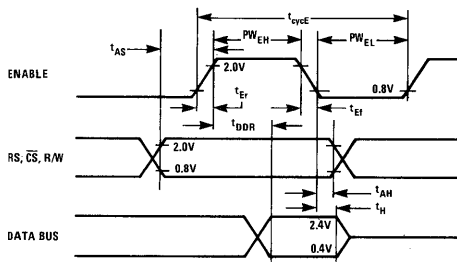Figure 8. Bus Read Timing Characteristics (Read Information from SSDA)

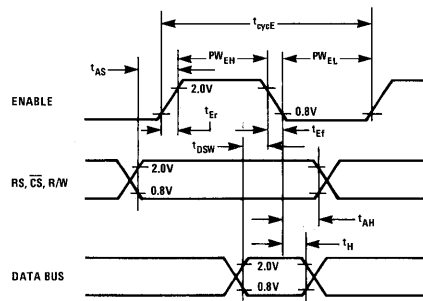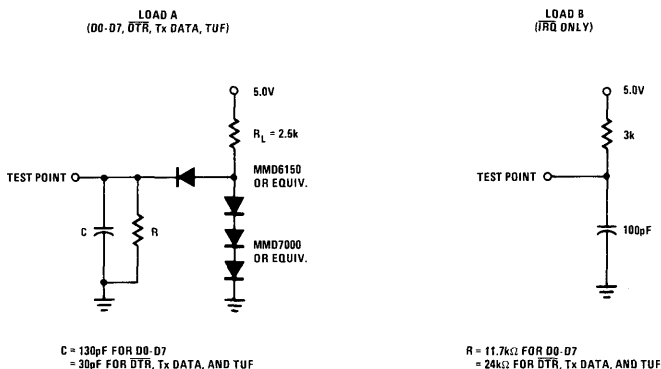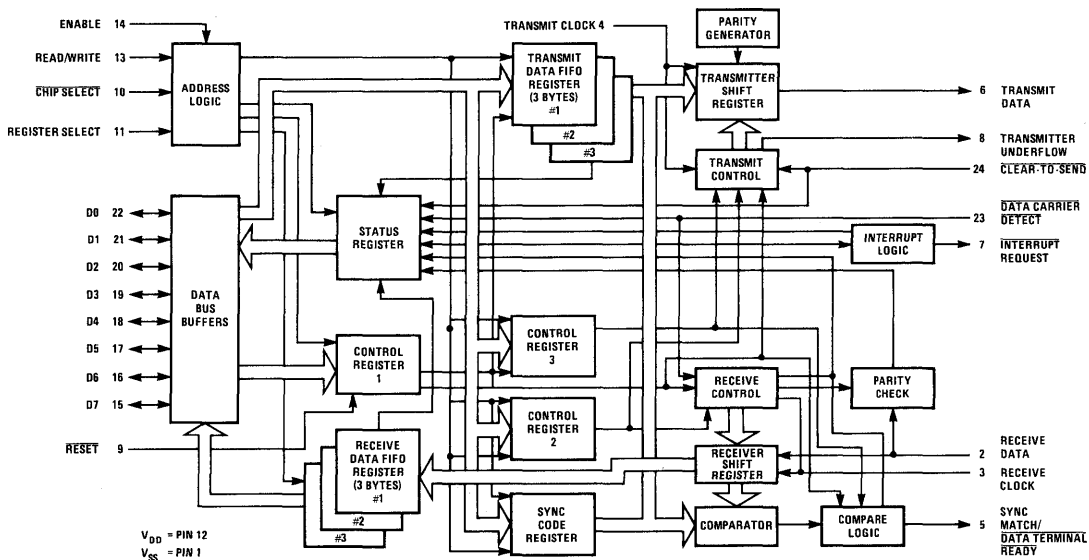Figure 9. Bus Write Timing Characteristics (Write Information into SSDA)

Figure 10. Bus Timing Test Loads

LOAD A
(D0-D7, DTR, Tx DATA, TUF)

LOAD B
(IRQ ONLY)

5.0V

R_L = 2.5k

MMD6150
OR EQUIV.

TEST POINT

MMD7000
OR EQUIV.

5.0V

3k

TEST POINT

100pF

C = 130pF FOR D0-D7
  = 30pF FOR DTR, Tx DATA, AND TUF

R = 11.7kΩ FOR D0-D7
  = 24kΩ FOR DTR, Tx DATA, AND TUF

Expanded Block Diagram

V_{DD} = PIN 12
V_{SS} = PIN 1

ADVANCED DATA LINK CONTROLLER

Features

- [ ] S6800 Compatible
- [ ] Protocol Features
  - [ ] Automatic Flag Detection and Synchronization
  - [ ] Zero Insertion and Deletion
  - [ ] Extendable Address, Control and Logical Control Fields (Optional)
  - [ ] Variable Word Length Info Field — 5, 6, 7, or 8-bits
  - [ ] Automatic Frame Check Sequence Generation and Check
  - [ ] Abort Detection and Transmission
  - [ ] Idle Detection and Transmission
- [ ] Loop Mode Operation
- [ ] Loop Back Self-Test Mode
- [ ] NRZ/NRZI Modes
- [ ] Quad Data Buffers for Each Rx and Tx
- [ ] Prioritized Status Register (Optional)
- [ ] MODEM/DMA/Loop Interface

General Description

The S6854 ADLC performs the complex MPU/data communication link function for the "Advanced Data Communication Control Procedure" (ADCCP). High Level Data Link Control (HDLC) and Synchronous Data Link Control (SDLC) standards. The ADLC provides key interface requirements with improved software efficiency. The ADLC is designed to provide the data communications interface for both primary and secondary stations in stand-alone, polling, and loop configurations.

Block Diagram

Pin Configuration

Absolute Maximum Ratings*

Supply Voltage	−0.3 to +7.0V
Input Voltage	−0.3 to +7.0V
Operating Temperature Range	0° to +70°C
Storage Temperature Range	−55° to +150°C
Thermal Resistance	70°C/W

*This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Electrical Characteristics ($V_{CC} = 5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to $+70°C$ unless otherwise noted.)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
V_{IH}	Input High Voltage	$V_{SS}+2.0$			Vdc	
V_{IL}	Input Low Voltage			$V_{SS}+0.8$	Vdc	
I_{IN}	Input Leakage Current All Inputs Except D0−D7		1.0	2.5	μAdc	$V_{IN}=0$ to 5.25 Vdc
I_{TSI}	Three State (Off State) Input Current D0−D7		2.0	10	μAdc	$V_{IN}=0.4$ to 2.4Vdc $V_{CC}=5.25$Vdc
V_{OH}	Output High Voltage D0-D7 All Others	$V_{SS}+2.4$ $V_{SS}+2.4$			Vdc Vdc	$I_{LOAD}=-205$μAdc $I_{LOAD}=-100$μAdc
V_{OL}	Output Low Voltage			$V_{SS}+0.4$	Vdc	$I_{LOAD}=1.6$mAdc
I_{LOH}	Output Leakage Current (Off State) $\overline{IRQ}$		1.0	10	μAdc	$V_{OH}=2.4$Vdc
P_D	Power Dissipation			850	mW	
C_{IN}	Capacitance D0-D7 All Other Inputs			12.5 7.5	pF pF	$V_{IN}=0$, $T_A=+25°C$, $f=1.0$MHz
C_{OUT}	$\overline{IRQ}$ All Others			5.0 10	pF pF	

Symbol	Characteristic	S6854		S68A54		S68B54		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
PW_{CL}	Minimum Clock Pulse Width, Low	700		450		280		ns
PW_{CH}	Minimum Clock Pulse Width, High	700		450		280		ns
f_C	Clock Frequency		0.66		1.0		1.5	MHz
t_{RDSU}	Receive Data Setup Time	250		200		120		ns
t_{RDH}	Receive Data Hold Time	120		100		60		ns
t_{RTS}	Request-to-Send Delay Time		680		460		340	ns
t_{TDD}	Clock-to-Data Delay for Transmitter		460		320		250	ns
t_{FD}	Flag Detect Delay Time		680		460		340	ns
t_{DTR}	DTR Delay Time		680		460		340	ns
t_{LOC}	Loop On-Line Control Delay Time		680		460		340	ns
t_{RDSR}	RDSR Delay Time		540		400		340	ns
t_{TDSR}	TDSR Delay Time		540		400		340	ns
t_{IR}	Interrupt Request Release Time		1.2		0.9		0.7	μs
t_{RES}	Reset Minimum Pulse Width	1.0		0.65		0.40		μs
t_r, t_f	Input Rise and Fall Times except Enable (0.8V to 2.0V)		1.0*		1.0*		1.0*	μs

*1.0μs or 10% of the pulse width, whichever is smaller.

S6800

Bus Timing Characteristics ($V_{CC} = +5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to $+70°C$ unless otherwise noted.)

Read

Symbol	Characteristic	S6854		S68A54		S68B54		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{CYC}	Enable Cycle Time	1.0		0.666		0.50		μs
PW_{EH}	Enable Pulse Width, High	0.45		0.28		0.22	25	μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.28		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DDR}	Data Delay Time		320		220		180	ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

Write

Symbol	Characteristic	S6850		S68A50		S68B50		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{CYCE}	Enable Cycle Time	1.0		0.666		0.50		μs
PW_{EH}	Enable Pulse Width, High	0.45		0.28		0.22		μs
PW_{EL}	Enable Pulse Width, Low	0.43		0.28		0.21		μs
t_{AS}	Setup Time, Address and R/W Valid to Enable Positive Transition	160		140		70		ns
t_{DSW}	Data Setup Time	195		80		60		ns
t_H	Data Hold Time	10		10		10		ns
t_{AH}	Address Hold Time	10		10		10		ns
t_{Er}, t_{Ef}	Rise and Fall Time for Enable Input		25		25		25	ns

Figure 1. Bus Timing Test Loads

S6800
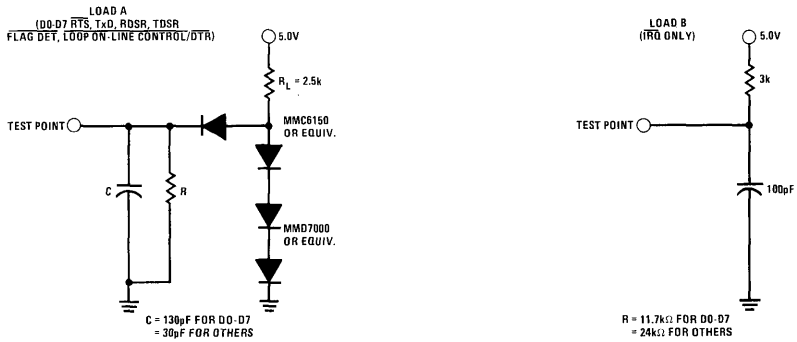
Figure 2. Receiver Data Setup/Hold, Flag Detect
          and Loop On-Line Control Delay Timing
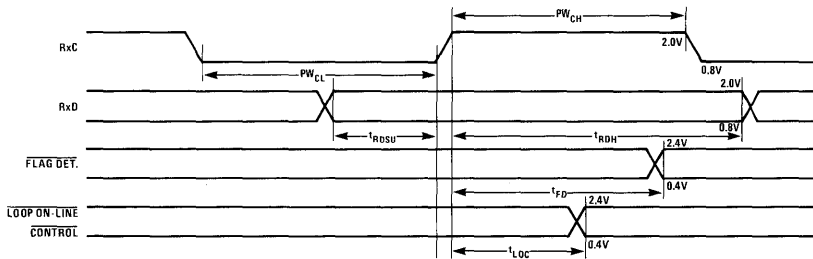
Figure 3. Transmit Data Output Delay and Request to Send Delay Timing
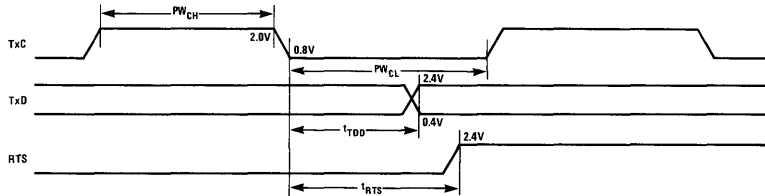
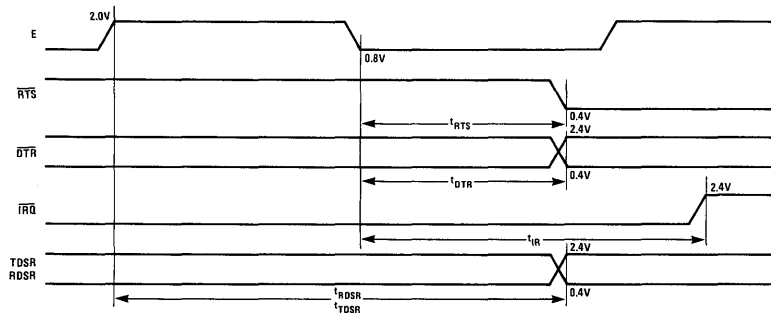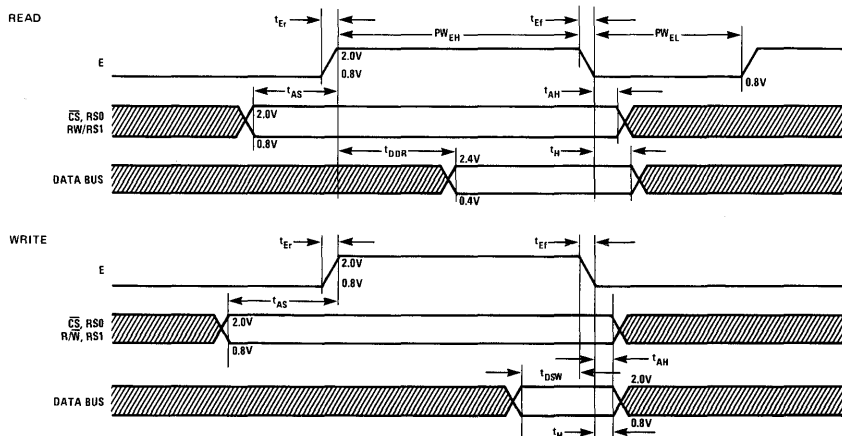**Figure 4. TDSR/RDSR Delays, IRQ Release Delay, RTS and DTR Delay Timing**

Figure 5. Bus Read/Write Timing Characteristics

![AMI logo]

AMERICAN MICROSYSTEMS, INC.

GENERAL PURPOSE
INTERFACE ADAPTER

Features

☐ Single or Dual Primary Address Recognition
☐ Secondary Address Capability
☐ Complete Source and Acceptor Handshakes
☐ Programmable Interrupts
☐ RFD Holdoff to Prevent Data Overrun
☐ Operates with DMA Controller
☐ Serial and Parallel Polling Capability
☐ Talk-Only or Listen-Only Capability
☐ Selectable Automatic Features to Minimize
   Software
☐ Synchronization Trigger Output
☐ S6800 Bus Compatible

General Description

The S68488 GPIA provides the means to interface between the IEEE488 standard instrument bus and the S6800. The 488 instrument bus provides a means for controlling and moving data from complex systems of multiple instruments.

The S68488 will automatically handle all handshake protocol needed on the instrument bus.

S6800

Block Diagram
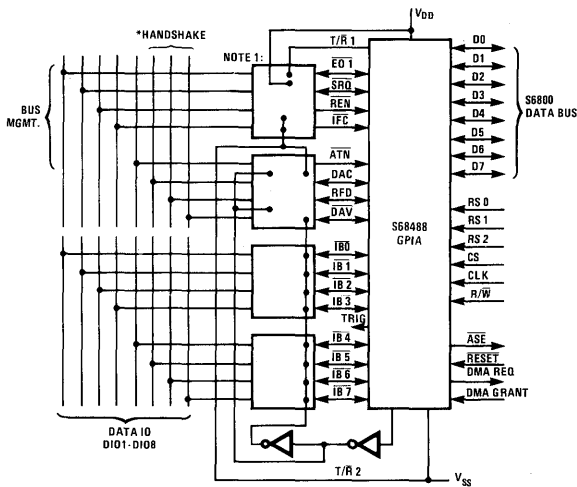
NOTE 1:
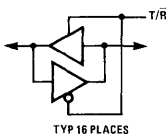
TYP 16 PLACES

*The 3-wire handshake described is the subject of patents owned by Hewlett-Packard Co.

Pin Configuration

	S68488	
V$_{SS}$ 1		40 IRQ
DMA GRANT 2		39 RS2
CS 3		38 RS1
ASE 4		37 RS0
R/W 5		36 IB0
φ2 6		35 IB1
D0 7		34 IB2
D1 8		33 IB3
D2 9		32 IB4
D3 10	S68488	31 IB5
D4 11		30 IB6
D5 12		29 IB7
D6 13		28 T/R 1
D7 14		27 T/R 2
DMA REQUEST 15		26 ATN
DAV 16		25 EOI
DAC 17		24 TRIG
RFD 18		23 SRQ
RESET 19		22 REN
V$_{DD}$ 20		21 IFC
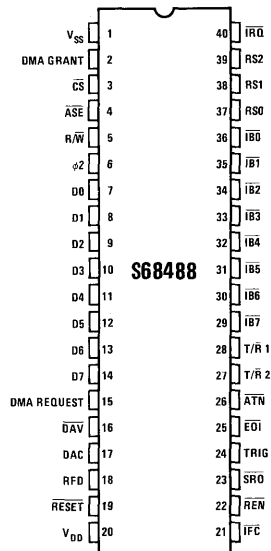
Functional Description

The IEEE 488 instrument bus standard is a bit-parallel, byte-serial bus structure designed for communiation to and from intelligent instruments. Using this standard, many instruments may be interconnected and remotely and automatically controlled or programmed. Data may be taken from, sent to, or transferred between instruments. A bus controller dictates the role of each device by making the attention line true and sending talk or listen addresses on the instrument bus data lines; those devices which have matching addresses are activated. Device addresses are set into each GPIA from switches or jumpers on a PC board by a microprocessor as a part of the initialization sequence.

When the controller makes the attention line true, instrument bus commands may also be sent to single or multiple GPIAs.

Information is transmitted on the instrument bus data lines under sequential control of the three handshake lines. No step in the sequence can be initiated until the previous step is completed. Information transfer can proceed as fast as the devices can respond, but no faster than the slowest device presently addressed as active. This permits several devices of different speeds to receive the same data concurrently.

The GPIA is designed to work with standard 488 bus driver Ics (S3448As) to meet the complete electrical specifications of the IEEE488 bus. Additionally, a powered-off instrument may be powered-on without disturbing the 488 bus. With some additional logic, the GPIA could be used with other microprocessors.

The S68488 GPIA has been designed to interface between the S6800 microprocessor and the complex protocol of the IEEE488 instrument bus. Many instrument bus protocol functions are handled automatically by the GPIA and require no additional MPU action. Other functions require minimum MPU response due to a large number of internal registers conveying information on the state of the GPIA and the instrument bus.

Figure 1.
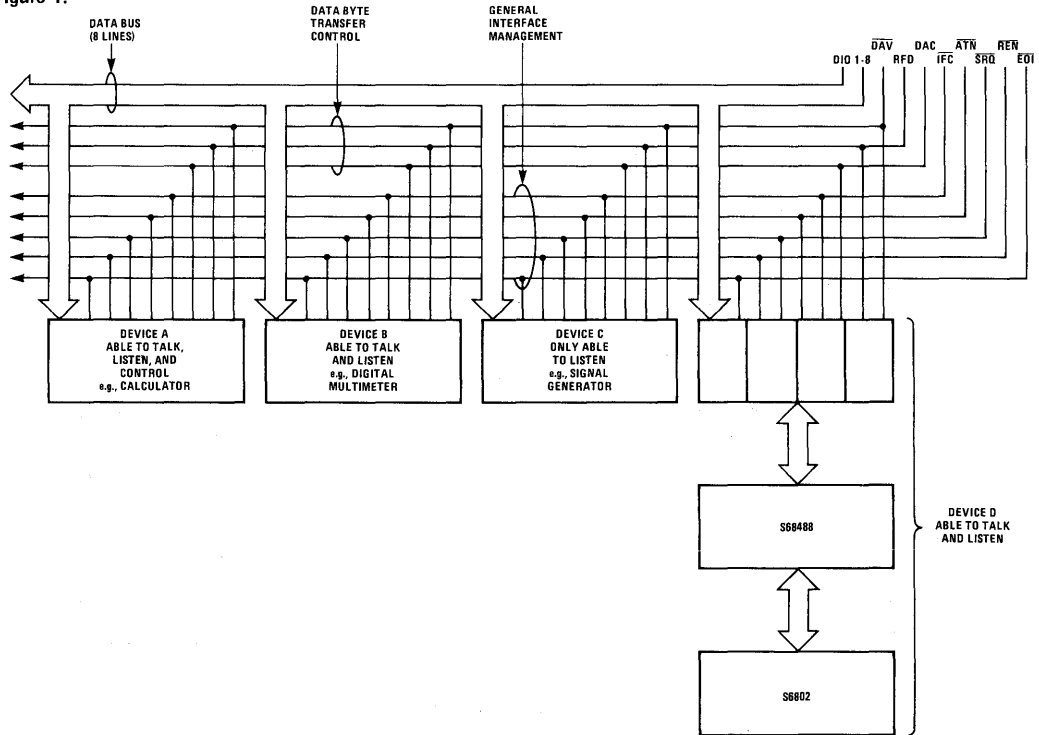
Maximum Ratings

Supply Voltage . . . . -0.3Vdc to +7.0Vdc

Input Voltage . . . . -0.3Vdc to +7.0Vdc

Operating Temperature Range . . . . 0°C to +70°C

Storage Temperature Range . . . . -55°C to +150°C

Thermal Resistance . . . . +82.5°C/W

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields, however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

Electrical Characteristics (V_{CC} = 5.0V ±5%, V_{SS} = 0, T_A = 0°C to +70°C unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
V_{IH}	Input High Voltage	V_{SS} + 2.0		V_{CC}	Vdc	
V_{IL}	Input Low Voltage	V_{SS} - 0.3		V_{SS} + 0.8		
I_{IN}	Input Leakage Current		1.0	2.5	μAdc	V_{IN} = 0 to 5.25V
I_{TSI}	Three-State (Off State) Input Current D0-D7		2.0	10	μAdc	V_{IN} = 0.4 to 2.4V
V_{OH}	Output High Voltage D0-D7	V_{SS} + 2.4			Vdc	I_{load} = -205μA
V_{OL}	Output Low Voltage D0-D7 $\overline{IRQ}$			V_{SS} + 0.4 V_{SS} + 0.4	Vdc	I_{load} = 1.6mA I_{load} = 3.2mA
I_{LOH}	Output Leakage Current (Off State) $\overline{IRQ}$		1.0	10	μAdc	V_{OH} = 2.4Vdc
P_D	Power Dissipation		600		mW	
C_{IN}	Input Capacitance D0-D7 All Others			12.5 7.5	pF	V_{IN} = 0, T_A = 25°C, f = 1.0MHz

Figure 2. Source and Acceptor Handshake
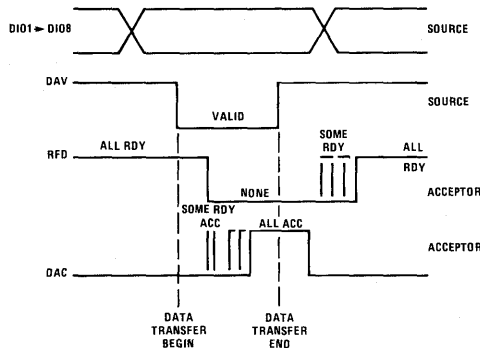
Bus Timing Characteristics
Read (See Figure 3)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
t_{cycE}	Enable Cycle Time	1.0			μs	
PW_{EH}	Enable Pulse Width, High	0.45			μs	
PW_{EL}	Enable Pulse Width, Low	0.43			μs	
t_{AS}	Setup Time, Address and $R/\overline{W}$ valid to enable positive transition	160			ns	See Figure 3
t_{DDR}	Data Delay Time			320	ns	
t_H	Data Hold Time	10			ns	
t_{AH}	Address Hold Time	10			ns	
t_{Er}, t_{Ef}	Rise and Fall Time for Enable input			25	ns	

Write (See Figure 4)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
t_{cycE}	Enable Cycle Time	1.0			μs	
PW_{EH}	Enable Pulse Width, High	0.45			μs	
PW_{EL}	Enable Pulse Width, Low	0.43			μs	
t_{AS}	Setup Time, Address and $R/\overline{W}$ valid to enable positive transition	160			ns	See Figure 4
t_{DSW}	Data Setup Time	195			ns	
t_H	Data Hold Time	10			ns	
t_{AH}	Address Hold Time	10			ns	
t_{Er}, t_{Ef}	Rise and Fall Time for Enable input			25	ns	

Output (See Figure 5)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
t_{HD}	Output Delay Time			400	ns	$\overline{DAV}$, DAC, RFD, $\overline{EOI}$, $\overline{ATN}$ valid
$t_{T/\overline{R}1, 2D}$				400	ns	$T/\overline{R}1$, $T/\overline{R}2$ valid

Figure 3. Bus Read Timing Characteristics (Read Information from GPIA)
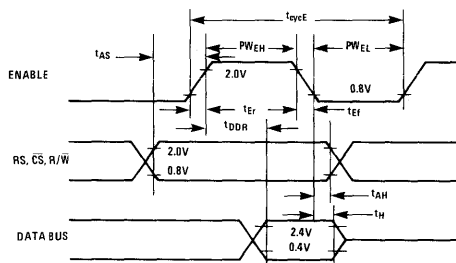
Figure 4. Bus Write Timing Characteristics (Write Information into GPIA)
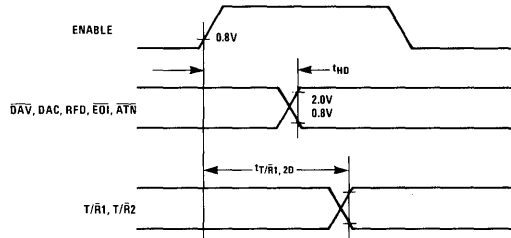
AMI.
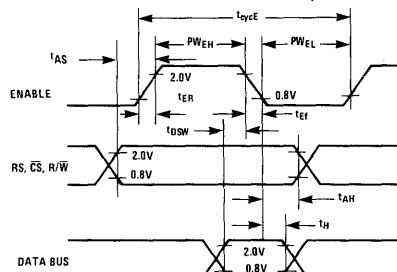
Figure 5. Output Bus Timing

S6800

A.C. Time Values

Symbol*	Parameter		Min.	Typ.	Max.	Unit	Conditions
T_1	Settling Time for Multiple Message	SH		$\geqslant 2$		μs**	
t_2	Response to $\overline{ATN}$	SH, AH, T, L		$\leqslant 200$		ns	
T_3	Interface Message Accept Time †	AH		>0		ϕ	
t_4	Response to $\overline{IFC}$ or $\overline{REN}$ False	T, TE, L, LE		<100		μs	
t_5	Response to $\overline{ATN} \cdot \overline{EOI}$	PP		$\leqslant 200$		ns	

* Time values specified by a lower case t indicate the maximum time allowed to make a state transition. Time values specified by an upper case T indicate the minimum time that a function must remain in a state before exiting.

** If three-state drivers are used on the $\overline{DIO} - \overline{DAV}$ and $\overline{EOI}$ lines, T_1 may be:
 (1) $\geqslant 1100$ns
 (2) Or $\geqslant 700$ns if it is known that within the controller $\overline{ATN}$ is driven by a three-state driver.
 (3) Or $\geqslant 500$ns for all subsequent bytes following the first sent after each false transition of $\overline{ATN}$ [the first byte must be sent in accordance with (1) or (2)].

† Time required for interface functions to accept, not necessarily respond to interface messages.

ϕ Implementation dependent.

MPU bus clock rate — The current 6800 bus clock is $\leqslant$ 1MHz but part should operate at 1.5MHz (design goal), with appropriate settling times (T1).

AMERICAN MICROSYSTEMS, INC.
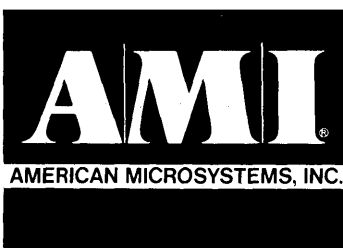
DATA ENCRYPTION UNIT

Features

- [ ] **Full Implementation of the NBS DES Algorithm**
- [ ] **A Complete Set of Operations, Including Encrypt Data, Decrypt Data, Enter New Key, Return Status, and Partial and Full Resets**
- [ ] **High-Speed Operation — Full Encryption or Decryption of a 64-Bit Data Block, Including All Command and Data Transfers, in 14.0ms.**

- [ ] **64-Bit Key Entry and Processing in 11.0ms, Including Odd Parity Checking of 8-Bit Key Data Bytes**
- [ ] **Simple Interface Through a General Purpose 8-Bit Paralled Digital I/O Port**

General Description

In addition, the AMI S6894 DEU offers an on-chip clock circuit, TTL-compatible I/O, single +5V power supply, in a two-chip set.

The 14.0ms data encryption/decryption time provided by the AMI DEU corresponds to a data rate in excess of 4600 bits-per-second in sustained operation. Allowing only 5% overhead for communications protocol control and checksum bits, this data rate is adequate to support a 4800 baud synchronous data link operated at 100% utilization. For start-stop asynchronous communications, the S6894 data rate is adequate to support lines with an aggregate transmission capacity in excess of 5700 baud. Two or more S6894 DEUs can be operated in parallel where higher data rates are required.

The encryption key is processed separately at the time it is entered. Once entered into S6894 DEU, an encryption key cannot be accessed by external means in either its original or processed form. Thus, security of the encryption key is fully protected. Each encryption key is entered only once — following a DEU reset, at DEU initialization, or when the key is to be changed. The entered key is then used for all subsequent data encryption and decryption operations.

Interface to the S6894 DEU is through a conventional general purpose 8-bit parallel I/O port. This allows the unit to be used with a wide range of host processors having different bus structures.

Other DEU Products

Although the S6894 DEU is the primary AMI NBS DES hardware product, other versions can be supplied at customer request. These include:

S6894-2 — Features and performance are identical to the S6894 DEU except that two encryption keys are accommodated. DEU encrypt and decrypt commands explicitly designate which key is to be used. Thus, the DEU-2 can serve two data paths having different encryption keys, can be used in the Master Key/Session Key mode, and so forth. Two new commands — Enter and Decrypt New Key, and Process New Key — are provided. These allow a new encrypted key to be decrypted under control of either existing key and then to replace either key, while prohitibing external access to the intermediate decrypted key value. The S6894-2 is implemented as a three-chip set that includes an S6810 RAM.

S6894-3 — Features and performances are identical to the S6894-2 DEU except that three encryption keys are accommodated. The S6894-3 consists of a four-chip set that includes two S5101 CMOS RAMs. An added feature is low power key data retention. During power-down conditions, all three encryption key values can be preserved using battery backup with only 0.1mW power drain. Preserved encryption keys are restored during power-on reset processing.

S6894-3A — Features are identical to the S6894-3 DEU in a two-chip set implementation. Data encryption and decryption times are 22.5ms, corresponding to a data rate in excess of 2800 bits-per-second in sustained operation. Low power data retention power requirements are less than 40mW.

Prices and delivery for all of the above DEUs will be quoted on request.

Customized Data Encryption Units

AMI DEU products can be customized to specific customer requirements in a number of ways. Protocols and conventions for transfer of data and command words between the controlling host processor and the DEU can be modified, and commands can be added or modified. For example, commands can be modified and added to facilitate Master/Session Key and/or Cypher Feedback (CFB) modes of operation. Further, the hardware interface can be modified or customized to meet specific application requirements. For example, the general purpose 8-bit parallel I/O port interface can be replaced — e.g., by a DMA interface or a custom LSI circuit — to precisely match the bus interface requirements of a particular host processor, to simplify DEU control and minimize host processor overhead, and/or to achieve maximum efficiency and speed in data and command word transfers.

AMI can also make available high-speed versions of any of the above DEUs. Because the object of such an implementation of the NBS DES is high performance, AMI plans at this time to offer high speed DEU products only in versions specifically customized to individual user requirements.

AMI will be pleased to work with interested customers in specifying and implementing customized versions of DEU products that meet requirements of specific applications.

S6800

AMI

AMERICAN MICROSYSTEMS, INC.

S6810/S68A10/S68B10

## 128 X 8 STATIC
READ/WRITE MEMORY

Features

- ☐ Organized as 128 Bytes of 8 Bits
- ☐ Static Operation
- ☐ Bidirectional Three-State Data Input/Output
- ☐ Six Chip Enable Inputs (Four Active Low, Two Active High
- ☐ Single 5 Volt Power Supply
- ☐ TTL Compatible
- ☐ Maximum Access Time
  450ns for S6810
  360ns for S68A10
  250ns for S68B10

General Description

The S6810/S68A10 and S68B10 are static 128x8 Read/Write Memories designed and organized to be compatible with the S6800/S68A00 and S68B00 Microprocessors. Interfacing to the S6810/S68A10 and S68B10 consists of an 8-bit bidirectional data bus, seven address lines, a single Read/Write control line, and six chip enable lines, four negative and two positive.

For ease of use, the S6810/S68A10 and S68B10 are a totally static memory requiring no clocks or cell refresh. The S6810/S68A10 and S68B10 are fabricated with N-channel silicon gate depletion load technology to be fully DTL/TTL compatible with only a single +5 volt power supply required.
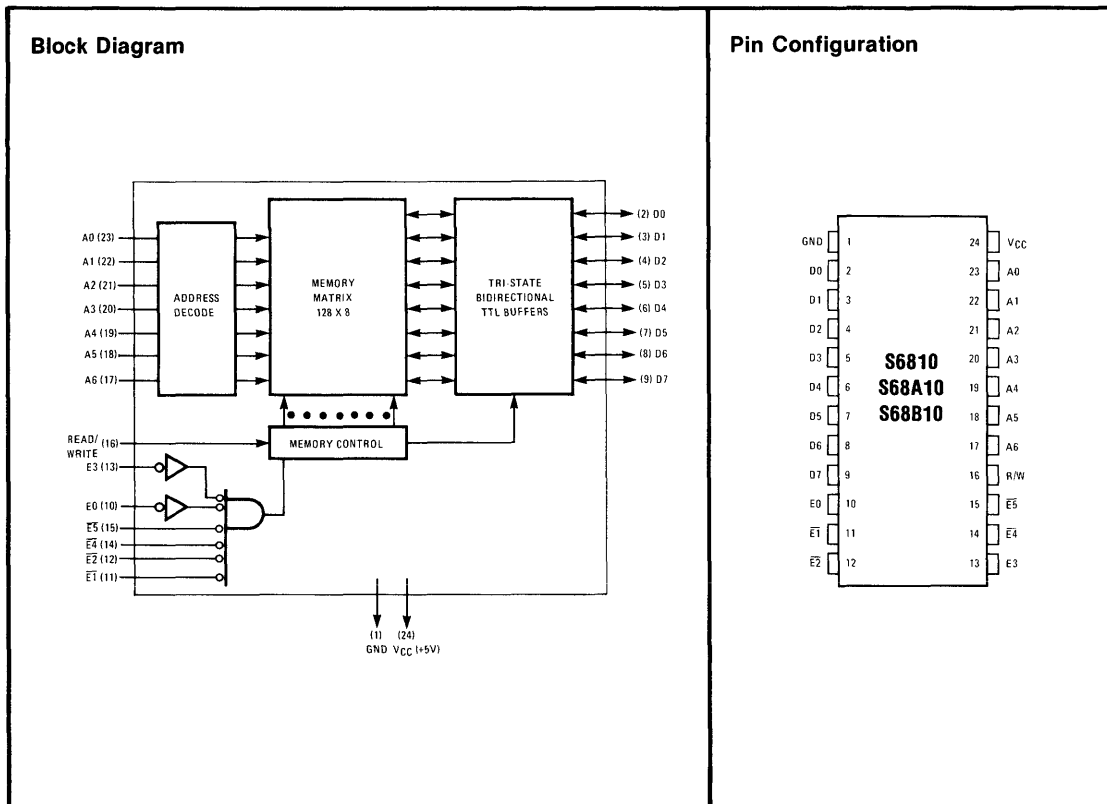
Block Diagram

Pin Configuration

Absolute Maximum Ratings

Supply Voltage . . . . −0.3V to +7.0V
Input Voltage . . . . −0.3V to +7.0V
Operating Temperature Range . . . . 0°C to +70°C
Storage Temperature Range . . . . −55°C to +150°C

D.C. Characteristics:

($V_{CC} = +5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to 70°C unless otherwise noted.)

| Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_{IN}	Input Current (A_n, R/W, CS_n, $\overline{CS_n}$)			2.5	μAdc	$V_{IN} = 0V$ to 5.25V
V_{OH}	Output High Voltage	2.4			Vdc	$I_{OH} = -205\mu A$
V_{OL}	Output Low Voltage			0.4	Vdc	$I_{OL} = 1.0mA$
I_{LO}	Output Leakage Current (Three State)			10	μAdc	$CS = 0.8V$ or $\overline{CS} = 2.0V$, $V_{OUT} = 0.4V$ to 2.4V
I_{CC}	Supply Current S6810 S68A10/S68B10			80 100	mAdc mAdc	$V_{CC} = 5.25V$, all other pins grounded, $T_A = 0°C$

A.C. Characteristics:
Read Cycle

($V_{CC} = +5.0V \pm 5\%$, $V_{SS} = 0$, $T_A = 0°C$ to 70°C unless otherwise noted.)

Symbol	Parameter	S6810		S68A10		S68B10		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{cyc(R)}$	Read Cycle Time	450		360		250		ns
t_{acc}	Access Time		450		360		250	ns
t_{AS}	Address Setup Time	20		20		20		ns
t_{AH}	Address Hold Time	0		0		0		ns
t_{DDR}	Data Delay Time (Read)		230		220		180	ns
t_{RCS}	Read to Select Delay Time	0		0		0		ns
t_{DHA}	Data Hold from Address	10		10		10		ns
t_H	Output Hold Time	10		10		10		ns
t_{DHW}	Data Hold from Write	10	60	10	60	10	60	ns
t_{RH}	Read Hold from Chip Select	0		0		0		ns

S6800

Write Cycle

(V_{CC} = +5.0V ± 5%, V_{SS} = 0, T_A=0°C to 70°C unless otherwise noted.)

Symbol	Parameter	S6810		S68A10		S68B10		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{cyc(W)}$	Write Cycle Time	450		360		250		ns
t_{AS}	Address Setup Time	20		20		20		ns
t_{AH}	Address Hold Time	0		0		0		ns
t_{CS}	Chip Select Pulse Width	300		250		210		ns
t_{WCS}	Write to Chip Select Delay Time	0		0		0		ns
t_{DSW}	Data Setup Time (Write)	100		80		60		ns
t_H	Input Hold Time	10		10		10		ns
t_{WH}	Write Hold Time from Chip Select	0		0		0		ns

Read Cycle Timing
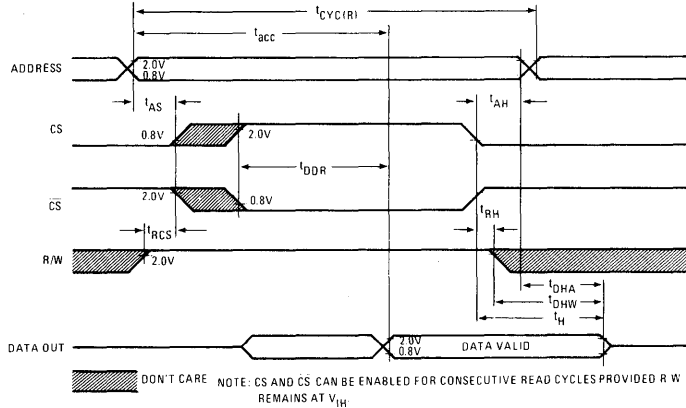
Write Cycle Timing

AC Test Load

TEST POINT○

5.0V

R_L = 2.5k

MMD6150
OR EQUIV

130 pF*   25k

MMD7000
OR EQUIV
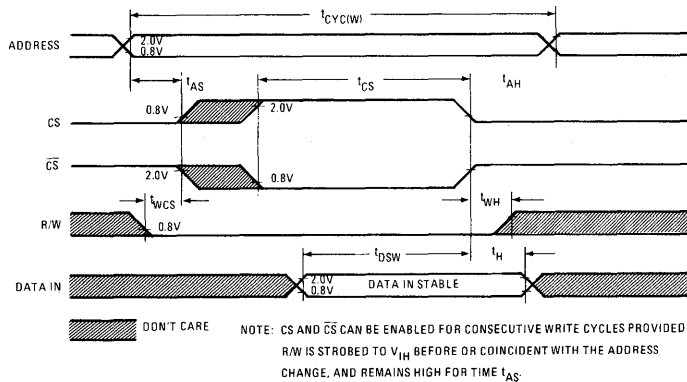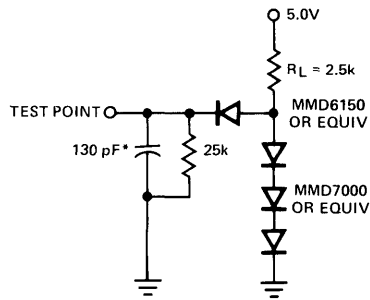
*Includes Jig Capacitance

AMI

High Performance
Microprocessor Family

Sixteen Bit

MICROPROCESSORS

S9900	16-Bit Microprocessor
S9940	Single Chip Microcomputer 2K ROM, 128×8 RAM
S9980A/S9981	16-Bit Microprocessor 8-Bit Data Bus (S9981 has Internal Clock)

PERIPHERALS

S9901	Programmable Systems Interface (PSI)
S9902	UART/Asynchronous Communications Controller (USRT/ACC)

AMI

AMERICAN MICROSYSTEMS, INC.

16-BIT
MICROPROCESSOR

Features

☐ 16-Bit Instruction Word

☐ Full Minicomputer Instruction Set Capability including Multiply and Divide

☐ Up to 65,536 Bytes of Memory

☐ 3.3MHz Speed

☐ Advanced Memory-to-Memory Architecture

☐ Separate Memory, I/O and Interrupt-Bus Structures

☐ 16 General Registers

☐ 16 Prioritized Interrupts

☐ Programmed and DMA I/O Capability

☐ N-Channel Silicon-Gate Technology

General Description

The S9900 microprocessor is a single-chip 16-bit central processing unit (CPU) produced using N-channel silicon-gate MOS technology. The instruction set of the S9900 includes the capabilities offered by full minicomputers. The unique memory-to-memory architecture features multiple register files, resident in memory, which allow faster response to interrupts and increased programming flexibility. The separate bus structure simplifies the system design effort. AMI provides a compatible set of MOS memory and support circuits to be used with an S9900 system. The system is fully supported by software and complete prototyping systems.

S9900

Block Diagram

Pin Configuration

V_BB	1	64	HOLD
V_CC	2	63	MEMEN
WAIT	3	62	READY
LOAD	4	61	WE
HOLDA	5	60	CRUCLK
RESET	6	59	V_CC
IAQ	7	58	NC
φ1	8	57	NC
φ2	9	56	D15
A14	10	55	D14
A13	11	54	D13
A12	12	53	D12
A11	13	52	D11
A10	14	51	D10
A9	15	50	D9
A8	16	49	D8
A7	17	48	D7
A6	18	47	D6
A5	19	46	D5
A4	20	45	D4
A3	21	44	D3
A2	22	43	D2
A1	23	42	D1
A0	24	41	D0
φ4	25	40	V_SS
V_SS	26	39	NC
V_DD	27	38	NC
φ3	28	37	NC
DBIN	29	36	IC0
CRUOUT	30	35	IC1
CRUIN	31	34	IC2
INTREQ	32	33	IC3
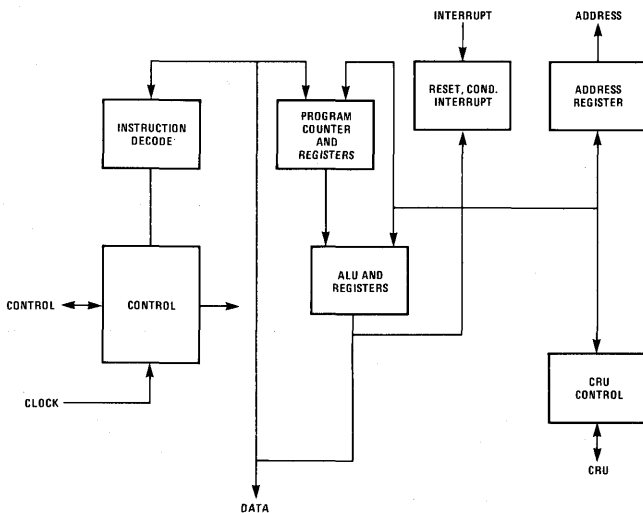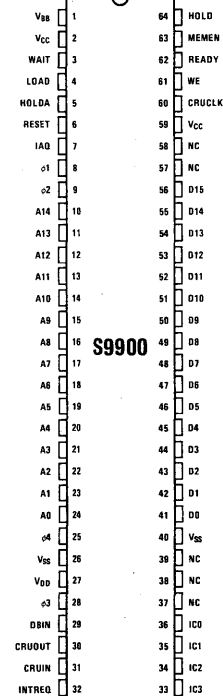
S9900

NC = NO INTERNAL CONNECTION

S9900 Electrical and Mechanical Specifications

Absolute Maximum Ratings Over Operating Free-Air Temperature Range (unless otherwise noted)*

Supply Voltage, V_{CC} (See Note 1).. $-0.3V$ to $+20V$
Supply Voltage, V_{DD} (See Note 1).. $-0.3V$ to $+20V$
Supply Voltage, V_{SS} (See Note 1).. $-0.3V$ to $+20V$
All Input Voltages (See Note 1).. $-0.3V$ to $+20V$
Output Voltage (with Respect to V_{SS}).. $-2V$ to $+7V$
Continuous Power Dissipation.. 1.2W
Operating Free-Air Temperature Range.. 0°C to $+70$°C
Storage Temperature Range.. -55°C to $+150$°C

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" section of this specification is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Under absolute maximum ratings voltage values are with respect to the most negative supply, V_{BB} (substrate), unless otherwise noted. Throughout the remainder of this section, voltage values are with respect to V_{SS}.

Recommended Operating Conditions

Symbol	Parameter	Min.	Nom.	Max.	Unit	Conditions
V_{BB}	Supply voltage	-5.25	-5	-4.75	V	
V_{CC}	Supply voltage	4.75	5	5.25	V	
V_{DD}	Supply voltage	11.4	12	12.6	V	
V_{SS}	Supply voltage		0		V	
V_{IH}	High-level input voltage (all inputs except clocks)	2.2	2.4	$V_{CC}+1$	V	
$V_{IH(\phi)}$	High-level clock input voltage	$V_{DD}-2$		V_{DD}	V	
V_{IL}	Low-level input voltage (all inputs except clocks)	-1	0.4	0.8	V	
$V_{IL(\phi)}$	Low-level clock input voltage	-0.3	0.3	0.6	V	
T_A	Operating free-air temperature	0		70	°C	

Timing Requirements Over Full Range of Recommended Operating Conditions (See Figures 1 and 2)

Symbol	Parameter	Min.	Nom.	Max.	Unit	Conditions
$t_{c(\phi)}$	Clock cycle time	0.3	0.333	0.5	μs	
$t_{r(\phi)}$	Clock rise time	10	12		ns	
$t_{f(\phi)}$	Clock fall time	10	12		ns	
$t_{w(\phi)}$	Pulse width, any clock high	40	45	100	ns	
$t_{\phi 1L, \phi 2L}$	Delay time, clock 1 low to clock 2 low (time between clock pulses)	0	5		ns	
$t_{\phi 2L, \phi 3L}$	Delay time, clock 2 low to clock 3 low (time between clock pulses)	0	5		ns	
$t_{\phi 3L, \phi 4L}$	Delay time, clock 3 low to clock 4 low (time between clock pulses)	0	5		ns	
$t_{\phi 4L, \phi 1L}$	Delay time, clock 4 low to clock 1 low (time between clock pulses)	0	5		ns	
$t_{\phi 1H, \phi 2H}$	Delay time, clock 1 high to clock 2 high (time between leading edges)	73	83		ns	
$t_{\phi 2H, \phi 3H}$	Delay time, clock 2 high to clock 3 high (time between leading edges)	73	83		ns	
$t_{\phi 3H, \phi 4H}$	Delay time, clock 3 high to clock 4 high (time between leading edges)	73	83		ns	
$t_{\phi 4H, \phi 1H}$	Delay time, clock 4 high to clock 1 high (time between leading edges)	73	8		ns	
t_{su}	Data or control setup time before clock 1	30			ns	
t_h	Data hold time after clock 1	10			ns	

Electrical Characteristics Over Full Range of Recommended Operating Conditions (unless otherwise noted)

Symbol	Parameter		Min.	Typ.†	Max.	Unit	Conditions
I_I	Input current	Data Bus during DBIN		±50	±100	μA	$V_I = V_{SS}$ to V_{CC}
		$\overline{WE}$, $\overline{MEMEN}$, DBIN, Address bus, Data bus during HOLDA		±50	±100		$V_I = V_{SS}$ to V_{CC}
		Clock*		±25	±75		$V_I = -0.3$ to 12.6V
		Any other inputs		±1	±10		$V_I = V_{SS}$ to V_{CC}
V_{OH}	High-level output voltage		2.4		V_{CC}	V	$I_O = -0.4mA$
V_{OL}	Low-level output voltage				0.65 0.50	V	$I_O = 32.mA$ $I_O = 2mA$
I_{BB}	Supply current from V_{BB}			0.1	1	mA	
I_{CC}	Supply current from V_{CC}			50	75	mA	
I_{DD}	Supply current from V_{DD}			25	45	mA	
C_i	Input capacitance (any inputs except clock and data bus)			10	15	pF	$V_{BB} = -5$, f = 1MHz, unmeasured pins at V_{SS}
$C_{i(\phi 1)}$	Clock-1 input capacitance			100	150	pF	$V_{BB} = -5$, f = 1MHz, unmeasured pins at V_{SS}
$C_{i(\phi 2)}$	Clock-2 input capacitance			150	200	pF	$V_{BB} = -5$, f = 1MHz unmeasured pins at V_{SS}
$C_{i(\phi 3)}$	Clock-3 input capacitance			100	150	pF	$V_{BB} = -5$, f = 1MHz, unmeasured pins at V_{SS}
$C_{i(\phi 4)}$	Clock-4 input capacitance			100	150	pF	$V_{BB} = -5$, f = 1MHz, unmeasured pins at V_{SS}
C_{DB}	Data bus capacitance			15	25	pF	$V_{BB} = -5$, f = 1MHz, unmeasured pins at V_{SS}
C_o	Output capacitance (any output except data bus)			10	15	pF	$V_{BB} = -5$, f = 1MHz, unmeasured pins at V_{SS}

†All typical values are at $T_A = 25°C$ and nominal voltages.
*D.C. Component of Operating Clock.

Switching Characteristics Over Full Range of Recommended Operating Conditions (See Figure 2)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
t_{PLH} or t_{PHL}	Propagation delay time, clocks to outputs CRUCLK, WE, MEMEN, WAIT, DBIN All other outputs		 20	30 40	ns ns	$C_L = 200pF$

Figure 1. Clock Timing
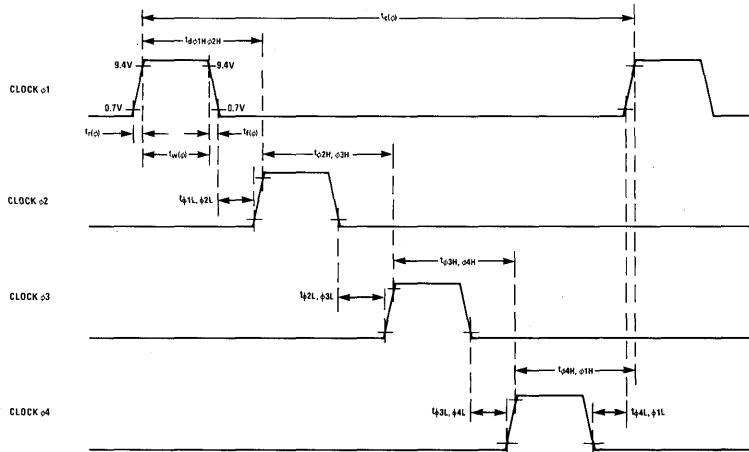
Note: All timing and voltage levels shown on φ1 apply to φ2, φ3, and φ4 in the same manner.

Figure 2. Signal Timing
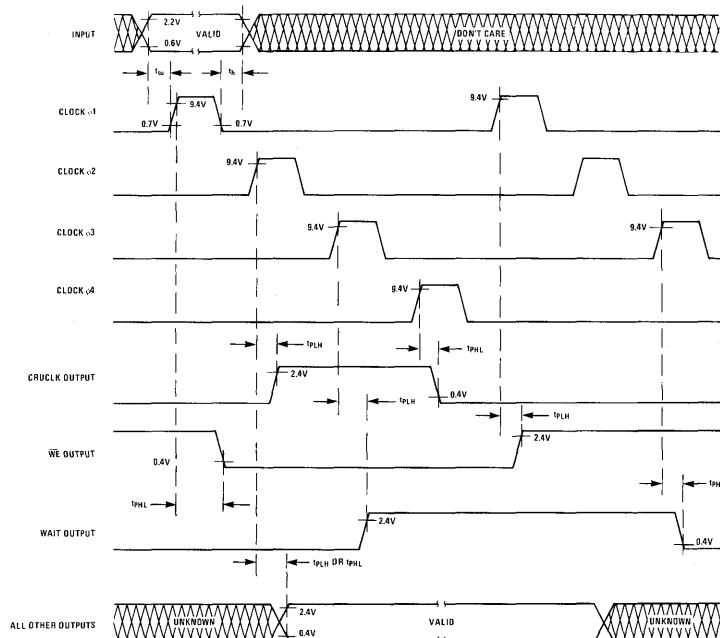
†The number of cycles over which input/output data must/will remain valid can be determined from the number of wait states required for memory access. Note that in all cases data should not change during φ1.

AMI
## AMERICAN MICROSYSTEMS, INC.

MICROPROCESSOR

Features

☐ **16-Bit Instruction Word**
☐ **Minicomputer Instruction Set Including Multiply and Divide**
☐ **2048 Bytes of ROM on Chip**
☐ **128 Bytes of RAM on Chip**
☐ **16 General Purpose Registers**
☐ **4 Prioritized Interrupts**
☐ **On Chip Timer/Event Counter**
☐ **32 Bits General Purpose I/O**
☐ **256 Bits I/O Expansion**
☐ **Multiprocessor System Interface**
☐ **Single 5 Volt Power Supply**
☐ **Power Down Capability for Low Stand-by Power**
☐ **N-Channel Silicon Gate MOS**

General Description

The S9940 is a single-chip, 16-bit microcomputer containing a CPU, memory (RAM and ROM), and extensive I/O. The instruction set of the S9940 is a subset of the S9900 instruction set and includes capabilities offered by minicomputers. The unique memory-to-memory architecture features multiple register files, resident in the RAM, which allow faster response to interrupts, and increased programming flexibility. The memory consists of 128 bytes of RAM and 2048 bytes of ROM. The S9940 implements four levels of interrupts, including an internal decrementer which can be programmed as a timer or an event counter. All members of the S9900 family of peripheral circuits are compatible with the S9940.

S9900

Block Diagram

Pin Configuration
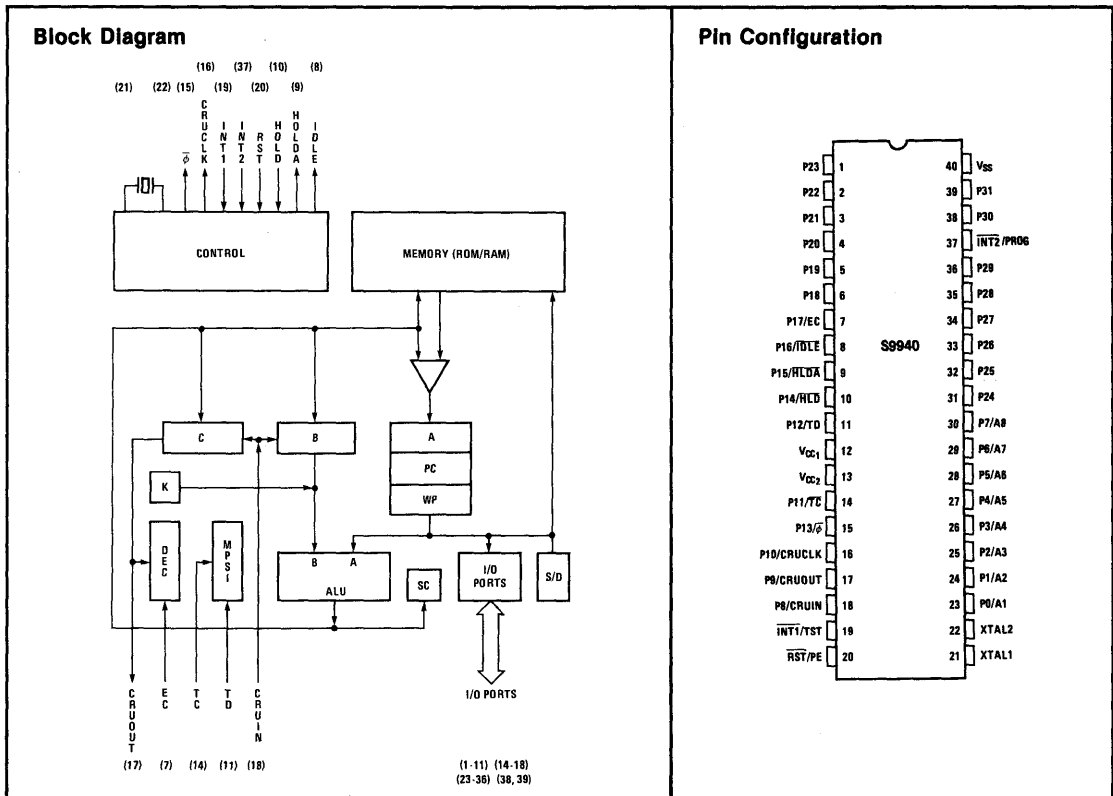
S9940 Electrical Specifications

Absolute Maximum Ratings Over Operating Free-Air Temperature Range (unless otherwise noted)*

Supply Voltage, V_{CC1}(1)	$-0.3V$ to $+20V$
Supply Voltage, V_{CC2}(1)	$-0.3V$ to $+20V$
Programming Voltage, PE (1)	$-0.3V$ to $+35V$
All Input Voltages (1)	$-0.3V$ to $+20V$
Output Voltage (1)	$-2V$ to $+7V$
Continuous Power Dissipation	1.5W
Operating Free-Air Temperature Range	0°C to 70°C
Storage Temperature Range	-55°C to $+150$°C

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" section of this specification is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

(1) All voltage values are with respect to V_{SS}

Recommended Operating Conditions

Symbol	Parameter	Min.	Nom.	Max.	Unit	Condition
V_{CC1}	Supply Voltage		5		V	
V_{CC2}	Supply Voltage		5		V	
V_{SS}	Supply Voltage		0		V	
V_{IH}	High-Level Input Voltage	2.0			V	
V_{IL}	Low-Level Input Voltage			0.8	V	
V_{IP}	Test Input Voltage		26		V	
T_A	Operating Free-Air Temperature	0		$+70$	°C	

Electrical Characteristics

Symbol	Parameter	Min.	Nom.	Max.	Unit	Condition
I_I	Input Current, All Inputs		± 10		μA	$V_I = V_{SS}$ to V_{CC}
V_{OH}	High-Level Output Voltage, All Inputs		2.4		V	$I_O = -0.4mA$
V_{OL}	Low-Level Output Voltage, All Outputs		0.4		V	$I_O = 2mA$
I_{CC1}	Supply Current from I_{CC1}		10		mA	
I_{CC2}	Supply Current from I_{CC2}		150		mA	
C_1	Input Capacitance, All Inputs		15		pF	$f = 1MHz$ unmeasured pins at V_{SS}
C_0	Output Capacitance, All Outputs		15		pF	$f = 1MHz$ unmeasured pins at V_{SS}

Clock Characteristics

The S9940 has an internal oscillator and 2-phase clock generator controlled by an external crystal. The user may also disable the oscillator and directly inject a frequency source into the XTAL2 input. The crystal frequency and the external frequency source must be 2 times the desired system frequency.

Internal Clock Option

The internal oscillator is enabled by connecting a crystal across XTAL1 and XTAL2. The system frequency is one-half the crystal frequency.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
	Crystal Frequency		5.0		MHz	$0°C \leq T \leq +70°C$

External Clock Options

An external frequency source can be used by injecting the frequency directly into XTAL2 with XTAL1 left uncon-nected. The external frequency must conform to the following specifications:

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
f_{ext}	External Source Frequency		5		MHz	
C_{OUT}	Output capacitance of External Source		15		pF	
V_H	External Source High-Level		4.5		V	
V_L	External Source Low-Level		0.4		V	
$t_{w(H)}$	External Source High-Level Pulse Width		90		ns	
$t_{w(L)}$	External Source Low-Level Pulse Width		90		ns	

Switching Characteristics Over Full Range of Recommended Operating Conditions

All external signal timings are with reference to ϕ (see Figure 1).

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
$t_{R\phi}$	Rise Time of ϕ		20		ns	
$t_{f\phi}$	Fall Time of ϕ		20		ns	
$t_{w\phi}$	Pulse Width of ϕ		350		ns	
t_{D1}	Output Delay Time		100		ns	$C_L = 100pF$
t_{D2}	Output Delay Time		400		ns	
t_{su}	Input Set Up Time		10		ns	
t_H	Input Hold Time		0		ns	

Programming Characteristics (see Figure 2).

Symbol	Parameter	Min.	Typ.	Max.	Unit	Condition
t_{RPE}	Rise Time of PE		50		ns	
t_{FPE}	Fall Time of PE		50		ns	
t_{SUDA}	Data Set Up Time		0		ns	
t_{HDA}	Data Hold Time		0		ns	
t_{RPR}	Data Time of PROG		50		ns	
t_{FPR}	Fall Time of PROG		50		ns	
t_{WPR}	PROG Pulse Width		100		ms	
t_{HPE}	PE Hold Time		30		tp*	
t_{supR}	PROG Set Up Time		30		tp*	
t_{rst}	Reset Time		800		ns	

*tp = System Clock Time Period

Figure 1. External Signal Timing Diagram

OSC
INPUT

$t_{w(H)}$ $t_{w(L)}$

$tr\phi$ $tf\phi$ $tw\phi$

t_{D1}

PO-P16

t_{D2} t_{su} t_H

P17-P31

ALL INPUTS

CRU ADDRESS

CRU IN

CRU OUT

CRU CLK
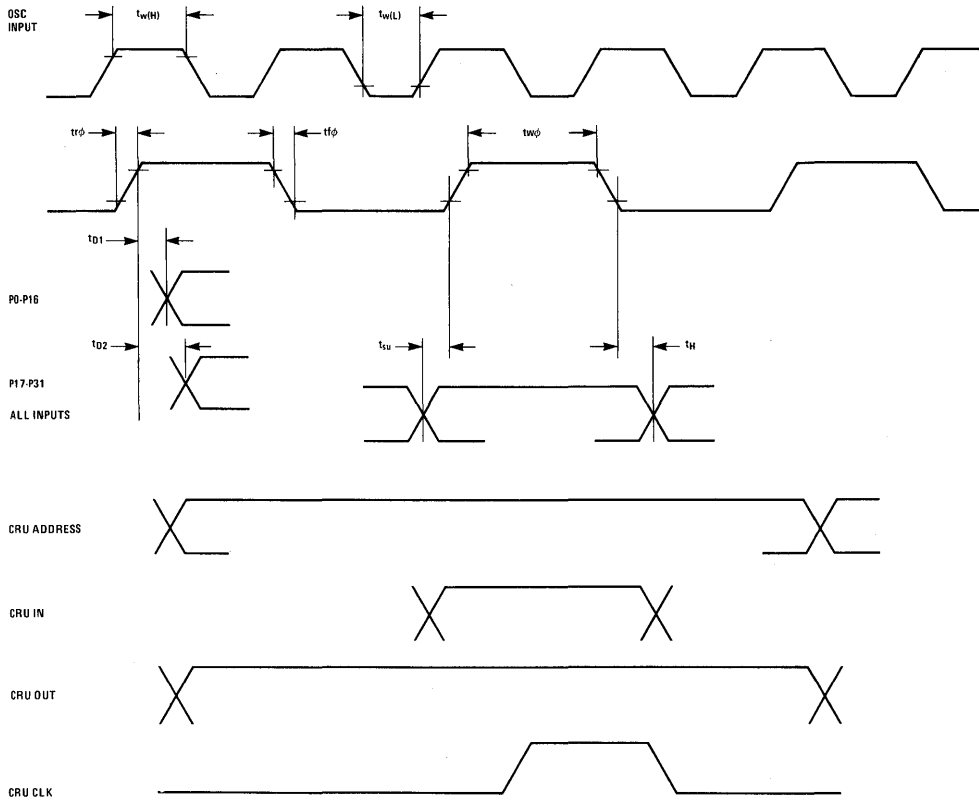
Figure 2. Programming Signal Timing Diagram
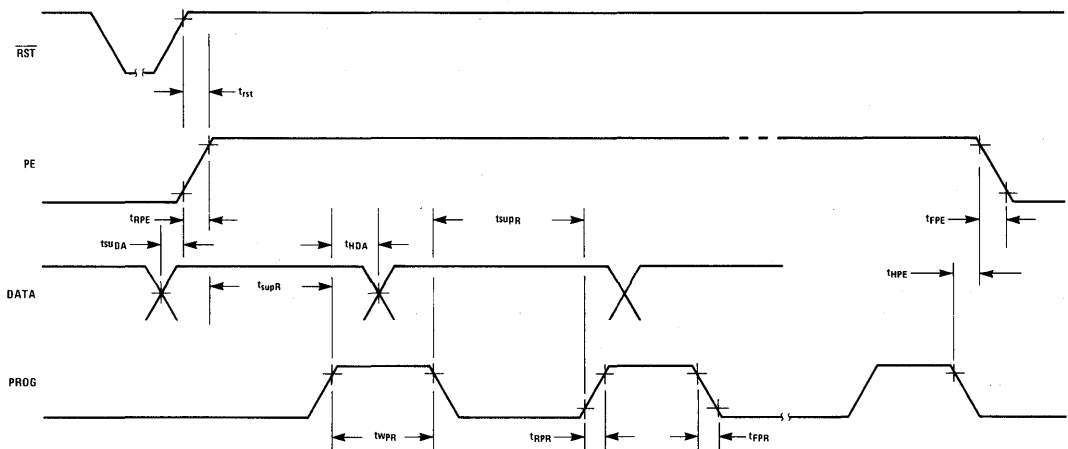
$\overline{RST}$

t_{rst}

PE

t_{RPE} t_{supR} t_{FPE}

t_{suDA} t_{HDA} t_{HPE}

DATA t_{supR}

PROG

t_{WPR} t_{RPR} t_{FPR}

AMI.

AMERICAN MICROSYSTEMS, INC.

16-BIT MICROPROCESSOR

Features

- ☐ 16-Bit Instruction Word
- ☐ Full Minicomputer Instruction Set Capability Including Multiply and Divide
- ☐ Up to 16,384 Bytes of Memory
- ☐ 8-Bit Memory Data Bus
- ☐ Advanced Memory-to-Memory Architecture
- ☐ Separate Memory, I/O, and Interrupt-Bus Structures
- ☐ 16 General Registers
- ☐ 4 Prioritized Interrupts
- ☐ Programmed and DMA I/O Capability
- ☐ On-Chip 4-Phase Clock Generator
- ☐ 40-Pin Package
- ☐ N-Channel Silicon-Gate Technology

The S9980A and the S9981 although very similar, have several differences which are:

1. The S9980A requires a V_{BB} supply (pin 21) while the S9981 has an internal charge pump to generate V_{BB} from V_{CC} and V_{DD}.

2. The S9981 has an optional on-chip crystal oscillator in addition to the external clock mode of the S9980A.

3. The pin-outs are not compatible for D0-D7, INT0-INT2, and $\bar{\phi}3$.

Description

The S9980A/S9981 is a software-compatible member of AMI's 9900 family of microprocessors. Designed to minimize the system cost for smaller systems, the S9980A/S9981 is a single-chip 16-bit central processing unit (CPU) which has an 8-bit data bus, on-chip clock, and is packaged in a 40-pin package (see Figure 1). The instruction set of the S9980A/S9981 includes the capabilities offered by full minicomputers and is exactly the same as the 9900's. The unique memory-to-memory architecture features multiple register files, resident in memory, which allow faster response to interrupts and increased programming flexibility. The separate bus structure simplifies the system design effort.

S9900

Block Diagram

Pin Configuration

			9980	9981
HOLD	1	40	MEMEN	MEMEN
HOLDA	2	39	READY	READY
IAQ	3	38	WE	WE
A13/CRUOUT	4	37	CRUCLK	CRUCLK
A12	5	36	VDD	VDD
A11	6	35	VSS	VSS
A10	7	34	CKIN	CKIN
A9	8	33	D7	OSCOUT
A8	9	32	D6	D7
A7	10	31	D5	D6
A6	11	30	D4	D5
A5	12	29	D3	D4
A4	13	28	D2	D3
A3	14	27	D1	D2
A2	15	26	D0	D1
A1	16	25	INT 0	D0
A0	17	24	INT 1	INT 0
DBIN	18	23	INT 2	INT 1
CRUIN	19	22	$\bar{\phi}3$	INT 2
VCC	20	21	VBB	$\phi3$
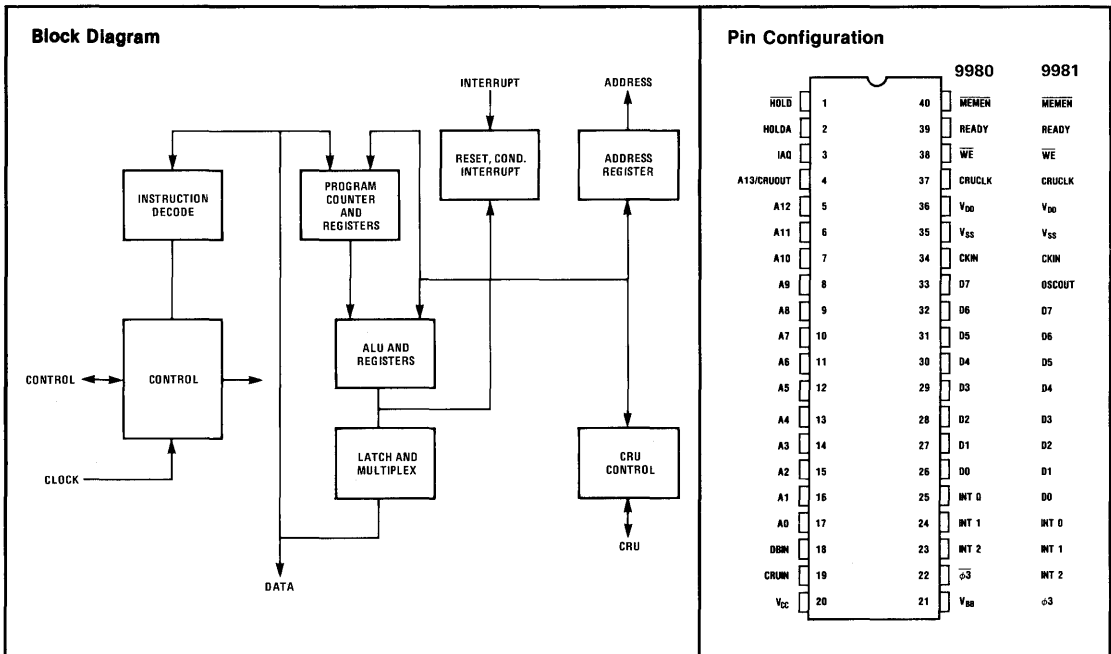
S9980A/S9981 Electrical and Mechanical Specifications
Absolute Maximum Ratings Over Operating Free-Air Temperature Range (unless otherwise noted)*

Supply voltage, V_{CC} (see Note 1) .... − 0.3V to 15V
Supply voltage, V_{DD} (see Note 1) .... − 0.3V to 15V
Supply voltage, V_{BB} (see Note 1) (9980A only) .... − 5.25V to 0V
All input voltages (see Note 1) .... − 0.3V to 15V
Output voltage (see Note 1) .... − 2V to 7V
Continuous power dissipation 1.4W
Operating free-air temperature range .... 0°C to 70°C
Storage temperature range .... − 55°C to 150°C

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" section of this specification is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTE 1: Under absolute maximum ratings voltage values are with respect to V_{SS}.

Recommended Operating Conditions

Symbol	Parameter	Min.	Nom.	Max.	Unit	Conditions
V_{BB}	Supply voltage (9980A only)	− 5.25	− 5	− 4.75	V	
V_{CC}	Supply voltage	4.75	5	5.25	V	
V_{DD}	Supply voltage	11.4	12	12.6	V	
V_{SS}	Supply voltage		0		V	
V_{IH}	High-level input voltage	2.2	2.4	V_{CC} + 1	V	
V_{IL}	Low-level input voltage	− 1	0.4	0.8	V	
T_A	Operating free-air temperature	0	20	70	°C	

Electrical Characteristics Over full Range of Recommended Operating Conditions (unless otherwise noted)

Symbol	Parameter		Min.	Typ.*	Max.	Unit	Conditions
I_I	Input current	Data bus during DBIN			± 75	μA	$V_I = V_{SS}$ to V_{CC}
		$\overline{WE}$, $\overline{MEMEN}$, DBIN during HOLDA			± 75	μA	$V_I = V_{SS}$ to V_{CC}
		Any other inputs			± 10	μA	$V_I = V_{SS}$ to V_{CC}
V_{OH}	High-level output voltage		2.4			V	$I_O = -0.4mA$
V_{OL}	Low-level output voltage				0.5		$I_O = 2mA$
					0.65	V	$I_O = 3.2mA$
I_{BB}	Supply current from V_{BB} (9980A only)				1	mA	
I_{CC}	Supply current from V_{CC}			50	60	mA	0°C
				40	50		70°C
I_{DD}	Supply current from V_{DD}			70	80	mA	0°C
				65	75		70°C
C_I	Input capacitance (any inputs except data bus)			15		pF	f = 1MHz, unmeasured pins at V_{SS}
C_{DB}	Data bus capacitance			25		pF	f = 1MHz, unmeasured pins at V_{SS}
C_O	Output capacitance (any output except data bus)			15		pF	f = 1MHz, unmeasured pins at V_{SS}

*All typical values are at T_A = 25°C and nominal voltages.

Clock Characteristics

The S9980A and S9981 have an internal 4-phase clock generator/driver. This is driven by an external TTL compatible signal to control the phase generation. In addition, the S9981 provides an output (OSCOUT) that in conjunction with CKIN forms an on-chip crystal oscillator. This oscillator requires an external crystal and two capacitors as shown in Figure 1. The external signal or crystal must be 4 times the desired system frequency.

Figure 1. Crystal Oscillator Circuit
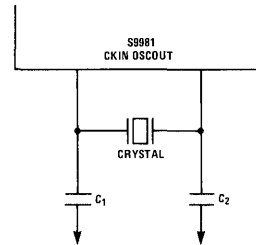
Internal Crystal Oscillator (9981 Only)

The internal crystal oscillator is used as shown in Figure 1. The crystal should be a fundamental series resonant type. C_1 and C_2 represent the total capacitance on these pins including strays and parasitics.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
	Crystal frequency	6		10	MHz	0°C-70°C
	C_1, C_2	10	15	25	pF	0°C-70°C

External Clock

The external clock on the S9980A and optional on the S9981, uses the CKIN pin. In this mode the OSCOUT pin of the S9981 must be left floating. The external clock source must conform to the following specifications.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
f_{ext}	External source frequency*	6		10	MHz	
V_H	External source high level	2.2			V	
V_L	External source low level			0.8	V	
T_r/T_f	External source rise/fall time		10		ns	
T_{WH}	External source high level pulse width	40			ns	
T_{WL}	External source low level pulse width	40			ns	

*This allows a system speed of 1.5MHz to 2.5MHz

Switching Characteristics Over Full Range of Recommended Operating Conditions

The timing of all the inputs and outputs is controlled by the internal 4 phase clock; thus all timings are based on the width of one phase of the internal clock. This is $1/f_{(CKIN)}$ (whether driven or from a crystal). This is also $\frac{1}{4} f_{system}$. In the following table this phase time is denoted t_w.

All external signals are with reference to $\phi 3$ (see Figure 2).

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
$t_r(\phi3)$	Rise time of $\phi3$	3	5	10	ns	
$t_f(\phi3)$	Fall time of $\phi3$	5	7.5	15	ns	
$t_w(\phi3)$	Pulse width of $\phi3$	$t_w - 15$	$t_w - 10$	$t_w + 10$	ns	
t_{su}	Data or control setup time*	$t_w - 30$			ns	
t_h	Data hold time*	$2t_{tw} + 10$			ns	$tw = 1/f(CKIN)$
t_{PHL} ($\overline{WE}$)	Propagation delay time WE high to low	$t_w - 10$	t_w	$t_w + 20$	ns	$= \frac{1}{4} f_{system}$
t_{PLH} ($\overline{WE}$)	Propagation delay time WE low to high	t_w	$t_w + 10$	$t_w + 30$	ns	
t_{PHL} (CRUCLK)	Propagation delay time, CRUCLK high to low	-20	-10	$+10$	ns	$C_L = 200pf$
t_{PLH} (CRUCLK)	Propagation delay time, CRUCLK low to high	$2t_w - 10$	$2t_w$	$2t_w + 20$	ns	
t_{OV}	Delay time from output valid to $\phi3$ low	$t_w - 50$	$t_w - 30$		ns	
t_{OX}	Delay time from output invalid to $\phi3$ low		$t_w - 20$	t_w	ns	

*All inputs except IC0-IC2 must be synchronized to meet these requirements. IC0-IC2 may change asynchronously.

Figure 2. External Signal Timing Diagram

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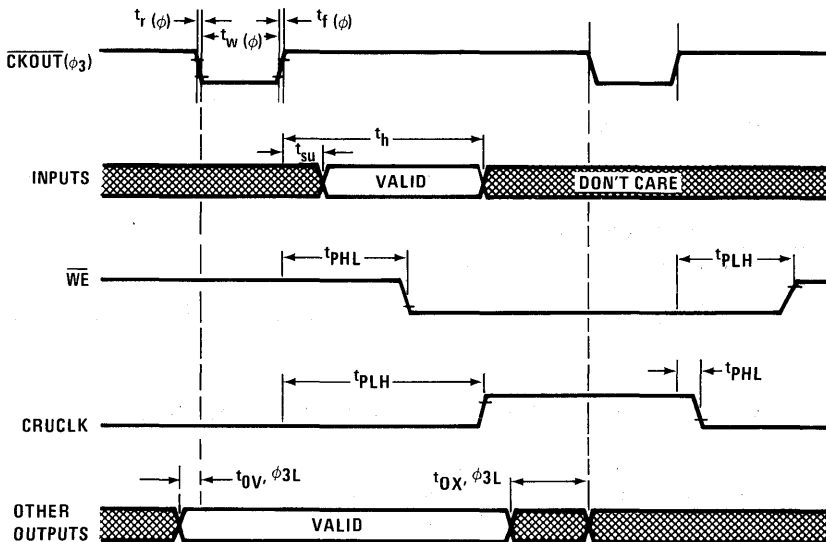
PROGRAMMABLE SYSTEMS INTERFACE CIRCUIT

Features

- **N-Channel Silicon-Gate Process**
- **9900 Series CRU Peripheral**
- **Performs Interrupt and I/O Interface Functions**
  - 6 Dedicated Interrupt Input Lines
  - 7 Dedicated I/O Ports
  - 9 Ports Programmable as Interrupts or I/O
- **Easily Stacked for Interrupt and I/O Expansion**
- **Interval and Event Timer**
- **Single 5V Supply**

General Description

The S9901 Programmable Systems Interface is a multifunctioned component designed to provide low cost interrupts and I/O ports in a 9900/9980 microprocessor system. It is fabricated with N-channel silicon-gate technology and is completely TTL compatible on all inputs including the power supply (+5V) and single-phase clock. Figure 1 is a block diagram of the S9901. The Programmable Systems Interface provides a 9900/9980 system with interrupt control, I/O ports, and a real-time clock as shown in Figure 2.

S9900

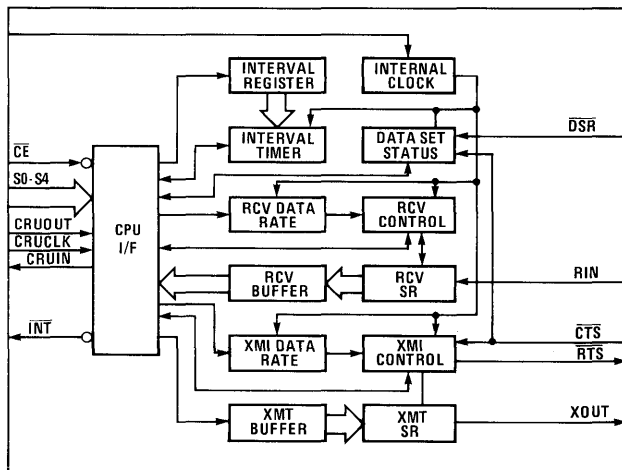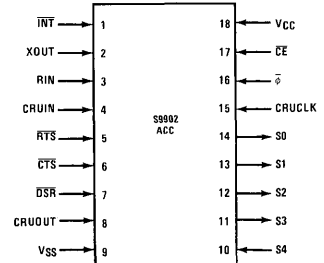Figure 1. Block Diagram

S9901 Pin Configuration

Figure 2. 9900/9980 System
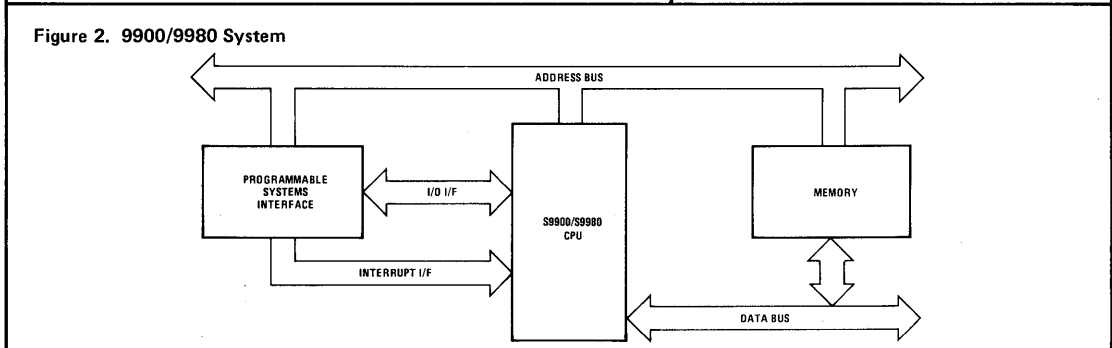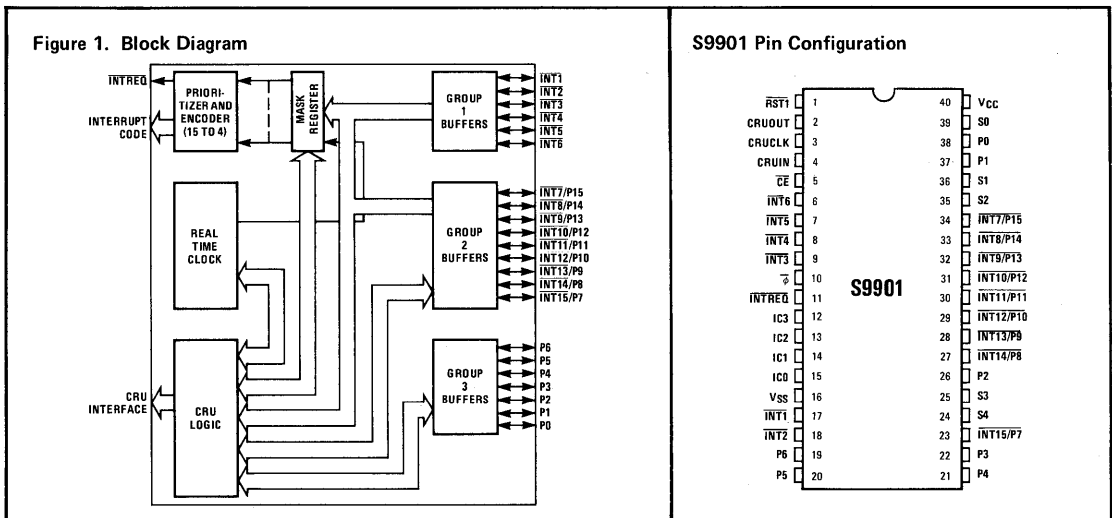
S9901 Electrical Specifications

Absolute Maximum Ratings Over Operating Free Air Temperature Range (Unless Otherwise Noted)*

Supply Voltages, V_{CC} and V_{SS} .... −0.3V to +10V
All Input and Output Voltages .... −0.3V to +10V
Continuous Power Dissipation 0.75W
Operating Free-Air Temperature Range .... 0°C to +70°C
Storage Temperature Range .... −65°C to +150°C

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" section of this specification is not implied. Exposure to absolute maximum rated conditions for extended period may affect device reliability.

Recommended Operating Conditions

Parameter	Min.	Nom.	Max.	Unit
Supply Voltage, V_{CC}	4.75	5	5.25	V
Supply Voltage, V_{SS}		0		V
High-Level Input Voltage, V_{IH}		2		V
Low-Level Input Voltage, V_{IL}		0.8		V
Operating Free-Air Temperature, T_A	0		70	°C

Electrical Characteristics Over Full Range of Recommended Operating Conditions (Unless Otherwise Noted)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
I_I	Input Current (Any Input)		±10		μA	V_I = 0V to V_{CC}
V_{OH}	High Level Output Voltage		2.4		V	I_{OH} = 100μA
			2		V	I_{OH} = −400μA
V_{OL}	Low Level Output Voltage		0.4		V	I_{OL} = 3.2mA
I_{CC}	Supply Current from V_{CC}		100		mA	
I_{SS}	Supply Current from V_{SS}		200		mA	
$I_{CC(av)}$	Average Supply Current from V_{CC}		60		mA	$t_{c(\phi)}$ = 333ns, T_A = 25°C
C_i	Capacitance, Any Input		10		pF	f = 1MHz,
C_o	Capacitance, Any Output		20		pF	All Other Pins at 0V

Timing Requirements Over Full Range of Operating Conditions

Symbol	Parameter	Min.	Nom.	Max.	Unit
$t_{c(\phi)}$	Clock Cycle Time		333		ns
$t_{r(\phi)}$	Clock Rise Time		10		ns
$t_{f(\phi)}$	Clock Fall Time		10		ns
$t_{w(\phi L)}$	Clock Pulse Low Width		55		ns
$t_{w(\phi H)}$	Clock Pulse High Width		240		ns
t_{su}	Setup Time for S0-S4, CE, or CRUOUT before CRUCLK		200		ns
t_{su}	Setup Time, Input Before Valid CRUIN		200		ns
t_{su}	Setup Time, Interrupt Before ϕ Low		40		ns
$t_{w(CRUCLK)}$	CRU Clock Pulse Width		100		ns
t_h	Address Hold Time		80		ns

Switching Characteristics Over Full Range of Recommended Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{PD}	Propagation Delay, $\overline{\phi}$ Low to Valid $\overline{\text{INTREQ}}$, I_{C0}-I_{C3}		80		ns	$C_L = 100pF$, 2 TTL Loads
t_{PD}	Propagation Delay, S0-S4 or $\overline{\text{CE}}$ to Valid CRUIN		400		ns	$C_L = 100pF$

Figure 3. Switching Characteristics
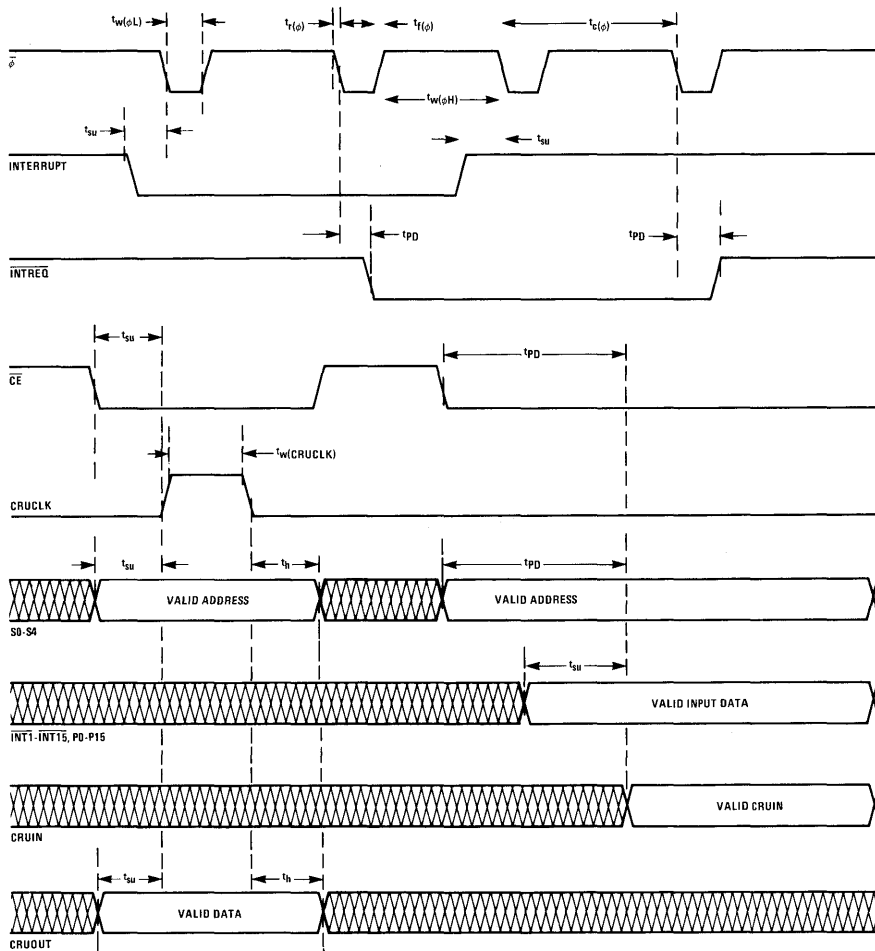
NOTE 1: ALL TIMING MEASUREMENTS ARE FROM 10% and 90% POINTS

S9900

AMERICAN MICROSYSTEMS, INC.

ASYNCHRONOUS COMMUNICATIONS CONTROLLER (ACC)

Features

- 5- to 8-Bit Character Length
- 1, 1 1/2, or 2 Stop Bits
- Even, Odd, or No Parity
- Fully Programmable Data Rate Generation
- Interval Timer with Resolution from 64 to 16,320 μs
- Fully TTL Compatible, Including Single Power Supply.

General Description

The S9902 Asynchronous Communication Controller (ACC) is a peripheral device for the S9900 family of microprocessors. The ACC provides an interface between the microprocessor and a serial asynchronous communication channel, performing the timing and data serialization and deserialization, thus facilitating the control of the asynchronous channel by the microprocessor.

Figure 1. Block Diagram

Figure 2. Pin Configuration

S9902 Electrical Specifications

Absolute Maximum Ratings Over Operating Free Air Temperature Range (Unless Otherwise Noted)*

Supply Voltage, V_{CC} .... -0.3V to +10V
All Inputs and Output Voltages .... -0.3V to +10V
Continuous Power Dissipation 0.7W
Operating Free-Air Temperature Range .... 0°C to +70°C
Storage Temperature Range .... -65°C to +150°C

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" section of this specification is not implied. Exposure to Absolute Maximum Rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Min.	Nom.	Max.	Unit
Supply Voltage, V_{CC}	4.75	5	5.25	V
Supply Voltage, V_{SS}		0		V
High-Level Input Voltage, V_{IH}	2.2	2.4	V_{CC}	V
Low-Level Input Voltage, V_{IL}		0.4	0.8	V
Operating Free-Air Temperature, T_A	0		70	°C

Electrical Characteristics Over Full Range of Recommended Operating Conditions (Unless Otherwise Noted)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Conditions
I_I	Input Current (Any Input)			±10	μA	V_I = 0V to V_{CC}
V_{OH}	High-Level Output Voltage	2.2	3.0		V	I_{OH} = -100μA
		2.0	2.5			I_{OH} = -400μA
V_{OL}	Low-Level Output Voltage		0.4	0.85	V	I_{OL} = 3.2mA
$I_{CC(AV)}$	Average Supply Current from V_{CC}		2.5	100	mA	$t_{c(\phi)}$ = 250ns, T_A = 25°C
C_i	Capacitance, Any Input		10		pF	f = 1 MHz,
C_o	Capacitance, Any Output		20			All other pins at 0V

Timing Requirements Over Full Range of Recommended Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
$t_{c(\phi)}$	Clock Cycle Time	300	333	2000	ns
$t_{r(\phi)}$	Clock Rise Time		10	12	ns
$t_{f(\phi)}$	Clock Fall Time		10	12	ns
$t_{H(\phi)}$	Clock Pulse Width (High Level)		225	240	ns
$t_{L(\phi)}$	Clock Pulse Width (Low Level)		45	55	ns
$t_{su(ad)}$	Setup Time for Address and CRUOUT Before CRUCLK		220		ns
$t_{su(CE)}$	Setup Time for CE Before CRUCLK		190		ns
t_{HD}	Hold Time for Address, CE and CRUOUT After CRUCLK		90		ns
t_{wcc}	CRUCLK Pulse Width		120		ns

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S9902 Pin Description

Table 1 defines the S9902 pin assignments and describes the function of each pin as shown in Figure 2.

Table 1

Signature	Pin	I/O	Description
$\overline{\text{INT}}$	1	O	Interrupt — when active (low), the $\overline{\text{INT}}$ output indicates that at least one of the interrupt conditions has occured.
XOUT	2	O	Transmitter serial data output line — XOUT remains inactive (high) when S9902 is not transmitting.
RIN	3	I	Receiver serial data input line — RCV — must be held in the inactive (high) state when not receiving data. A transition from high to low will activate the receiver circuitry.
CRUIN	4	O	Serial data output pin from S9902 to CRUIN input pin of the CPU.
$\overline{\text{RTS}}$	5	O	Request-to-send output from S9902 to modem. This output is enabled by the CPU and remains active (low) during transmission from the S9902.
$\overline{\text{CTS}}$	6	I	Clear-to-send input from modem to S9902. When active (low), it enables the transmitter section of S9902.
$\overline{\text{DSR}}$	7	I	Data set ready input from modem to S9902. This input generates an interrupt when going On or Off.
CRUOUT	8	I	Serial data input line to S9902 from CRUOUT line of the CPU.
V_{SS}	9	I	Ground reference voltage.
S4 (LSB)	10	I	
S3	11	I	
S2	12	I	
S1	13	I	Address bus S0-S4 are the lines that are addressed by the CPU to select a
S0	14	I	particular S9902 function.
CRUCLK	15	I	CRU Clock. When active (high), S9902 from CRUOUT line of the CPU.
$\overline{\phi}$	16	I	TTL Clock.
$\overline{\text{CE}}$	17	I	Chip enable — when CE is inactive (high), the S9902 address decoding is inhibited which prevents execution of any S9902 command function. CRUIN remains at high-impedance when $\overline{\text{CE}}$ is inactive (high).
V_{CC}	18	I	Supply voltage (+5V nominal).

Device Interface

The relationship of the ACC to other components in the system is shown in Figures 4 and 5. The ACC is connected to the asychronous channel through level shifters which translate the TTL inputs and outputs to the appropriate levels (e.g., RS-232C, TTY current loop, etc.). The microprocessor transfers data to and from the ACC via the Communication Register Unit (CRU).

CPU Interface

The ACC interfaces to the CPU through the Communication Register Unit (CRU). The CRU interface consists of five address-select lines (S0-S4), chip enable ($\overline{\text{CE}}$), and three CRU control lines (CRUIN, CRUOUT, and CRUCLK). When $\overline{\text{CE}}$ becomes active (low), the five select lines address the CRU bit being accessed. When data is being transferred to the ACC from the CPU, CRUOUT contains the valid datum which is strobed by CRUCLK. When ACC data is being read, CRUIN is the datum output by the ACC.

AMI

$\mu P/\mu C$

Microprocessor/Microcomputer
Development Systems Products

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DEVELOPMENT

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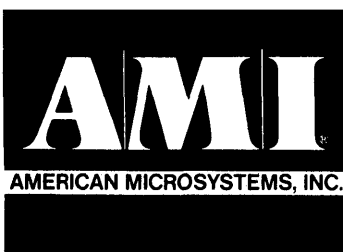
AMI CROSS SUPPORT

☐ **AMI Pascal™ Based**

☐ **Increase Programmer Productivity**

☐ **Extends Usefulness of Microprocessor Development Hardware**

☐ **Shortens Programmer Learning Time**

☐ **Shortens System Development Time**

☐ **Low Cost Means of Evaluating a Variety of MPUs Including S2200, S6800, S9900, 8080 and Z80**

☐ **Provides Common Software Base for All Support Packages**

☐ **Enhances Software Portability**

☐ **Simple Upgrade to Include AMI Pascal**

☐ **Software Warranty Included**

☐ **Software Maintenance Available**

AMI cross support is part of the Advanced Support Tools concept which permits users to learn one common software base for use throughout the various packages. The software system will operate on many of the most popular development systems and extends the usefulness of development hardware through additional development software and cross compatibility with application software packages planned by AMI.

The AMI cross support relies on a common software base. This commonality extends to the pseudo-operations of the assemblers. Included in each assembler are:

INCLUDE	directs assembler to get source from a file
EQU	allows values to be equated to a symbol
DEF	defines a label for global usage
REF	defines a label to be outside current code or data segment
PAGE	perform page eject
TITLE	print a title heading

The assemblers are each a full macro assembler supporting local and global labels. Arithmetic and logic operations include plus, minus, ones complement, exclusive-or, multiplication, truncating division, remainder division,

or, and, equal, and not equal. Many of the assemblers' features are normally found only in larger systems.

Software simulators are available for the S2200 family of microcomputers as a development tool. Basic capabilities supported are similar to those available with in circuit emulation but without the hardware interaction. Software facilities include: breakpoint, dump memos, alter memory, single step, set-up I/O and observe I/O. When coupled with the appropriate SES module a complete harware-software integration can be performed.

AMI Cross Support is part of our Advanced Support Tools package designed to increase your profitability through systems solutions.

AMI

AMERICAN MICROSYSTEMS, INC.

AMI PASCAL ™

☐ USCD Level II.0 Compatible

☐ Replaces Host Operating System and Results in One-Stop Software Service

☐ Pascal Compiler for Easy Systems Programming

☐ Wide Range of Assemblers Available Including S2200, S6800, S9900, 8080, and Z80

☐ Floppy Disk Based with Minimal Swapping

☐ CRT or TTY Oriented Editors with Menu Select

☐ Linker

☐ Optimized for Use on the Host Machine

☐ Easy to Transport to Many Different Systems based on S6800, S9900, 8080, Z80 or PDP-11

☐ Extensive Programming Examples

$\mu P/\mu C$
DEVELOPMENT

The AMI Pascal system is part of the AMI Advanced Support Tools concept in which the users learn only one common operating system and editor. The package will operate on most of the popular development systems and extends the usefulness of development hardware through development software for numerous microprocessors and cross compatibility with application software packages planned by AMI.

AMI Pascal is a complete software system intended to run on a stand alone micro or minicomputer. It is compatible with the UCSD Pascal® version 2.0 and features fault-tolerant software intended to increase programmer productivity. This is accomplished by sophisticated error recovery mechanisms built into the software package and by informative user prompts. The system is intended as an interactive programming tool and therefore relies on a CRT for user display. Hard copy (TTY) terminals may be used with the system but at a slower output rate.

AMI Pascal can be broken down into three logical groupings: general support, cross-assemblers and systems support. **General support** includes a disk based operating system, screen oriented editor and utility programs. **Cross-assemblers** are available at a low incremented cost for the AMI Pascal system. All assemblers use a common format and pseudo-operations for ease of use. **Systems support** derives from the Pascal compiler coupled with the operating system. The basic Pascal compiler produces an intermediate code suitable for interpretation or native code generation. It is suggested that the interpretive option be used to develop software tools like assemblers and compilers since this form uses the least memory.

AMI Pascal can be used as a system implementation language to investigate algorithm design and debug. Production software can be produced by recoding the Pascal version in assembly language. The overall result is less expensive software with higher reliability.

AMI Pascal is part of our Advanced Support Tools package designed to increase your profitability through systems solutions.

Software Service Subscription

AMI will provide a software service subscription ("Subscription Service") to LICENSEES of Licensed Programs, in accordance with the terms of the License Agreement. This Subscription Service entitles the LICENSEE to free updates of Class 2 and 3, as described below, for a period of six months. The Subscription Service also provides the LICENSEE with a special discount rate specified in the Agreement on prices for Class 1 software updates, as described below.

The LICENSEE may renew the software Subscription Service in accordance with the terms of the Agreement.

Software Updates

There are three clases of software updates which vary according to the nature and scope of the update.

Class 1–Software updates in which new languages (compilers) or operating systems are added to existing software packages. The scope of the update is far different from the previous existing software packages. This type of update may change the first significant digit of the software revision level. For example, the integration of a new high level language into an operating system will bring the rev. level from 1.5 to 2.0.

Class 2–Software updates which are improvements on existing software packages. These updates will correct design deficiencies or produce minor improvements in the use of the programs. If the scope of the change in the software is large enough, the software revision level may be updated to the first significant digit. If the improvement is minor, it will only change the decimal revision level.

Class 3–Software updates which are corrections of software problems (bugs) reported by users of the software packages. These updates will make minor changes in the packages and will always be related to software problems. The decimal fraction of the software revision level will be changed only by this update.
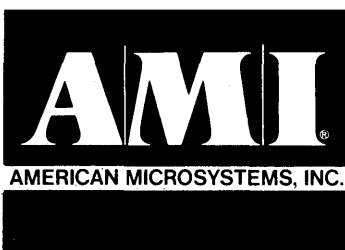
CA2000 BOSTON SYSTEMS OFFICE CROSS ASSEMBLER FOR S2000 MICROPROCESSORS BY AMI (and all compatible devices)

This cross assembler, one of a family of cross assemblers produced by The Boston Systems Office, is a powerful programming tool used to develop microprocessor software. It allows the user to take full advantage of a larger computer, whether in a time-sharing or in-house mode, thereby significantly reducing the number of man-hours spent in program development. The advantages of a larger computer include:

- Faster processing speeds
- More powerful editors
- Higher speed peripherals

These cross assemblers are written in the assembly language of the host computer. They require only 8K words of memory to assemble practically any size program. The symbol table can be expanded to fit any program or can be shrunk to fit into a smaller machine if required. The assemblers require much less CPU time to execute, even at this reduced memory requirement, when compared to manufacturer supplied cross assemblers. Benchmarks against competitive products in a time-sharing environment have shown that savings of over 85% are common. Similar efficiencies are realized when using an in-house computer.

The instruction set of each cross assembler is the same as documented in the manuals supplied by the microprocessor manufacturer. Mnemonics exist for data manipulation, binary arithmetic, jumps to subroutines, etc. In addition, all of the BSO cross assemblers have full macro and conditional assembly capabilities. The assembler outputs to disk, which may then be punched on paper tape, loaded into a PROM burner or down line loaded into memory, depending on your facilities.

Cross assemblers are now available for the following microprocessors:

AMD 9080A
AMI S2000, S6800 & S9900
Fairchild 6800 & F8
Hitachi 6800
Intel 8080, 8080A, 8085, 4040, 4004, 8008 8048, 8748, 8035 8049 & 8039
Intersil 8048
MOS Technology 6500 series
Mostek F8 & Z80
Motorola M6800

Nat'l Semiconductor IMP-8, SC/MP, 8080 & PACE
NEC uPD8080AF & uPD8080A
RCA CDP 1800 series (COSMAC)
Rockwell R6500, PPS-8 & PPS-4
Signetics 8048 & 8035
Synertek 6500 series
Thomson-CSF 6800
Texas Instruments TMS1000, 8080, & TMS9900
Zilog Z80

Please feel free to contact The Boston Systems Office for further information on any microprocessor not mentioned above, as we are constantly adding to our product line. BSO will also produce custom assemblers and other application and system software on a contract basis.

$\mu P/\mu C$ DEVELOPMENT

AMERICAN MICROSYSTEMS, INC.

S2150 Emulator Module

☐ **Full Microcomputer Emulation**

☐ **Erasable Program Memory**

☐ **Fully-tested Operational System**

☐ **System Socket Compatible**
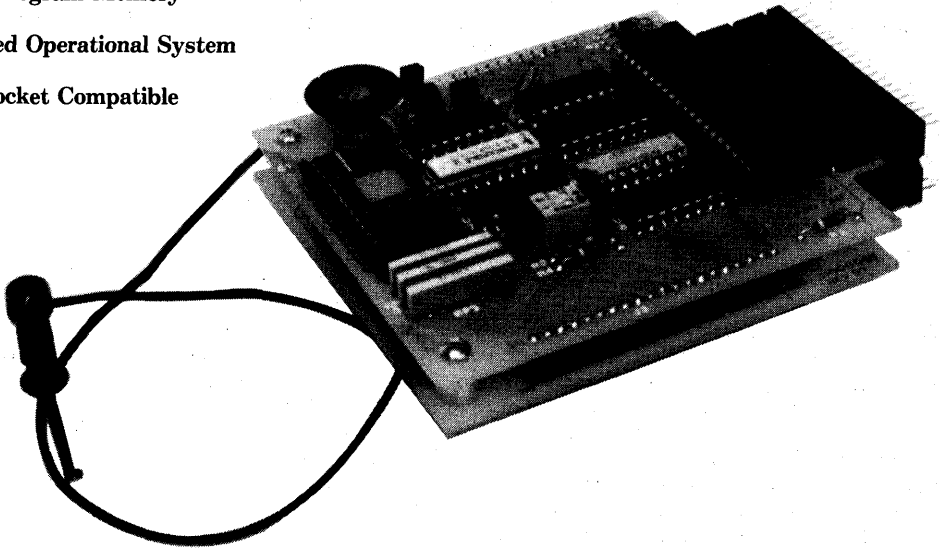
The SES Series of boards provide pin for pin emulation of single-chip microcomputers. The board offers the full operational capabilities of the single-chip microcomputer coupled with the flexibility of board level design. The Series incorporates on-board Erasable PROM to provide ease of program modification in a prototype environment.

SES2000/S2150

The SES2000/S2150 is an emulator board for the popular S2000/S2150 single-chip microcomputer. This board level unit is configured to plug directly into the system socket that would normally hold the mask programmed S2000 /S2150. Through the use of the SES2000/S2150, system hardware and program configurations can be quickly and efficiently accomplished in the prototype stages. The board is also suited for integration into pre-production systems allowing full freedom of modification through memory changes in standard EPROM's.

Incorporated onto the SES2000/S2150 Emulator Module are latches and buffers which allow the S2000/S2150

microcomputer to access user programmed EPROM also located on the module. A separate source of power for the additional circuits eliminates the possibility of altering the users system characteristics. Thus to the system circuitry the SES module appears as a single-chip microcomputer operating from its internally programmed ROM.

General Description:

The S2000/S2150 Static Emulator provides a means of trying a user's program without committing the program to ROM within the S2000/S2150.

This is accomplished by using a S2000/S2150 that is placed into the multiplex mode and providing EPROM as the memory. The EPROM (2716 − 2K×8) can be programmed with a user's program

It is intended that the emulator can be plugged into a socket that would normally be used by the S2000/S2150 in its finished form (the S2000/S2150 ROM would contain a user defined program).

Specifications

Power Requirements

External Clip (V_{CC})	$+9V \pm 5\%$ @ 350mA (max)
V_{DD}[1]	$+5$ or $+9V \pm 5\%$ @ 75mA (max)
V_{GG} (Max)	$(-)\, 0.3/18V$
V_{GG} (NOM)	$+9V \pm 5\%$ @ 50mA (max)

Interface Signals [2] ($V_{SS} = O_V$, $V_{GG}\, 9 \pm 0.5V$, $V_{DD} = V_{CC} = 5 \pm 5\%$, $T_A = 25°C$)

Inputs

$K_1 - K_8$	Low Level	$0.0 - (K_{REF} - 0.5V)$
	High Level	$(K_{REF} + 0.5) - V_{GG}V$
K_{REF}		$0.28\, V_{GG} - 0.32\, V_{GG}V$
$I_1 - I_8$, ROMs,	Low Level	$0.0 - 0.5V$[3]
Run, POR	High Level	$5.3 - V_{GG}V$[3]
$D_0 - D_7$	Low Level	$0.0 - 0.8V$
	High Level	$4.5 - V_{GG}V$

Outputs

$A_0 - A_3$	Low Level	$0.0 - 0.6V$ (I $= 30$mA)
	High Level	$3.5 - V_{DD}V$ (I $= -3$mA)
$A_4 - A_{12}$, $\overline{EXT}$	Low Level	$0.0 - 0.6V$ (I $= 4.35$mA)
SYNC + S	High Level	$3.5 - V_{DD}V$ (I $= -2$mA)
$D_0 - D_7$	Low Level	$0.0 - 1.0V$ (I $= 9$mA)
	High Level	$3.5 - V_{DD}V$ (I $= -4$mA)

Operating Temperature		$0 - 70°C$
Physical Dimensions	WxHxT	3.4 x 4.375 x 1.75 in.
Connector	40 Pin DIP socket	

Notes:

1. V_{DD} may be connected to V_{GG} if single power supply operation is desired.

2. Some minor variations exist in interface levels and currents between the SES 2000/2150 and the S2000/S2150. Consult the S2000/S2150 data sheet for a full description and values.

3. A 100μA pull up to V_{GG} internal to the S2000/S2150 is connected to these inputs.

AMERICAN MICROSYSTEMS, INC.

STATIC MOS RANDOM ACCESS MEMORIES

Part No.	Organization	Process	Max. Access Time(ns)	Max. Active Power(mW)	Max. Standby Power(mW)	Power Supplies	Package
S68B10	128×8	NMOS	250	420	N/A	+5V	24 Pin
S68A10	128×8	NMOS	360	420	N/A	+5V	24 Pin
S6810	128×8	NMOS	450	400	N/A	+5V	24 Pin
S6810-1	128×8	NMOS	575	500	N/A	+5V	24 Pin

STATIC CMOS RANDOM ACCESS MEMORIES

Part No.	Organization	Max. Access Time(ns)	Max. Active Power(mW)	Max. Standby Power(mW)	Power Supplies	Package
S5101L-1	256×4	450	115	.055	+5V	22 Pin
S5101L	256×4	650	115	.055	+5V	22 Pin
S5101L-3	256×4	650	115	.735	+5V	22 Pin
S5101-8	256×4	800	115	2.7	+5V	22 Pin
S6504[2]	4096×1	300	75	0.5	+5V	18 Pin
S6508-1	1024×1	300	13	.055	+5V	16 Pin
S6508	1024×1	460	13	.55	+5V	16 Pin
S6508A-1	1024×1	275/115[2]	12.5/50[2]	1.15	+4V to +11V	16 Pin
S6508A	1024×1	460/185[2]	12.5/50[2]	1.1	+4V to +11V	16 Pin
S6514[2]	1024×4	300	75	0.25	+5V	18 Pin

UV ERASABLE ELECTRICALLY PROGRAMMABLE READ ONLY MEMORIES

Part No.	Organization	Process	Max. Access Time(ns)	Max. Active Power(mW)	Max. Standby Power(mW)	Power Supplies	Package
S5204A[1]	512×8	PMOS	750	750	N/A	+5/−12	24 Pin
S6834[1]	512×8	PMOS	575	750	N/A	+5/−12	24 Pin
S6834-1[1]	512×8	PMOS	750	750	N/A	+5/−12	24 Pin

MOS READ ONLY MEMORIES

Part No.	Description	Organization	Process	Max. Access Time(ns)	Max. Active Power(mW)	Power Supplies	Package
S6831B	16,384 Bit Static ROM	2048×8	NMOS	450	420	+5	24 Pin
S68332	32,768 Bit Static ROM	4096×8	NMOS	450	370	+5	24 Pin
S4264	65,536 Bit Static ROM	8192×8	NMOS	450	550	+5	24 Pin
S68364	65,536 Bit Static ROM	8192×8	NMOS	450	330	+5	24 Pin

[1] Not recommended for new designs

[2] To be announced

1024 BIT (256×4) STATIC CMOS RAM

Features

☐ Ultra Low Standby Power

☐ Data Retention at 2V (L Version)

☐ Single +5 Volt Power Supply

☐ Completely Static Operation

☐ Completely TTL Compatible Inputs

☐ Three-State TTL Compatible Outputs

General Description

The AMI S5101 family of 256 x 4-bit ultra low power CMOS RAMs offers fully static operation with a single + 5 volt power supply. All inputs and outputs are directly TTL compatible. With data inputs and outputs on adjacent pins, either separate or common data I/O operations can easily be implemented for maximum design flexibility. The three-state outputs will drive one full TTL load and are disabled (high impedance state) by output disable (OD), either chip enable (CE1 or CE2), or in a write cycle (R/W = LOW). This facilitates the control of common data I/O systems.

Block Diagram
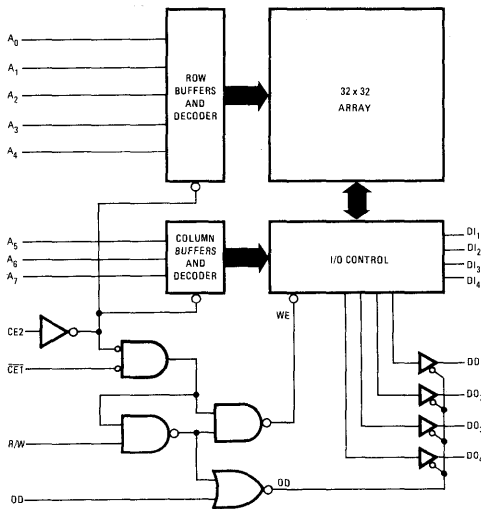
Logic Symbol
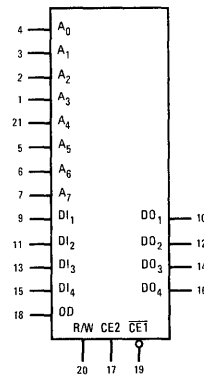
Pin Configuration
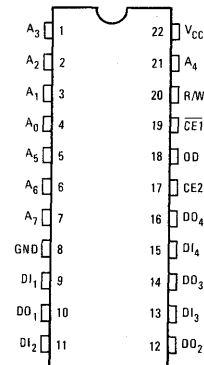
Truth Table

$\overline{CE1}$	CE2	OD	R/W	DIN	Output	Mode
H	X	X	X	X	High Z	Not selected
X	L	X	X	X	High Z	Not Selected
X	X	H	H	X	High Z	Output Disabled
L	H	H	L	X	High Z	Write
L	H	L	L	X	High Z	Write
L	H	L	H	X	Dout	Read

Pin Names

A_0 - A_7	Address Inputs	$\overline{CE1}$	Chip Enable
DI_1 - DI_4	Data Inputs	CE2	Chip Enable
DO_1 - DO_4	Data Outputs	R/W	Read/Write Input
OD	Output Disable	V_{CC}	+5 Volt Power Supply

General Description (Continued)

The stored data is read out nondestructively and is the same polarity as the original input data. The S5101 is totally static, making clocks unnecessary for a new address to be accepted. The device has two chip enable inputs ($\overline{CE1}$ and CE2) allowing easy system expansion. CE2 disables the entire device but $\overline{CE1}$ does not disable the address buffers and decoders. Thus, minimum power dissipation is achieved when CE2 is low.

The L version of the S5101 has the additional feature of guaranteed data retention with the power supply as low as 2 volts. This makes the device an ideal choice when battery augmented non-volatile RAM storage is mandatory.

The S5101 is fabricated using a silicon gate CMOS process suitable for high volume production of ultra low power, high performance memories.

Absolute Maximum Ratings*

Ambient Temperature Under Bias .... $-10°C$ to $80°C$
Storage Temperature .... $-65°C$ to $150°C$
Voltage on Any Pin with Respect to Ground .... $-0.3V$ to $V_{CC} +0.3V$
Maximum Power Supply Voltage 8V
Power Dissipation 1W

*COMMENT: Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. Characteristics: $T_A = 0°C$ to $70°C$, $V_{CC} = 5V \pm 5\%$ (Unless otherwise specified)

Symbol	Parameter		Limits Min.	Max.	Units	Conditions
I_{LI}	Input Leakage Current			1	μA	$V_{IN} = 0V$ to V_{CC}
I_{LO}	Output Leakage Current			1	μA	$\overline{CE1} = V_{IH}$ $V_{OUT} = 0V$ to V_{CC}
I_{CC}	Operating Supply Current			22	mA	Outputs = Open, $V_{IN} = V_{IL}$ to V_{CC}
I_{CCL}	Standby Supply Current	S5101L1, S5101L		10	μA	$V_{IN} = 0V$ to V_{CC} except CE2 $\leqslant 0.2V$
		S5101L3		140	μA	
		S5101L8, S5101-8		500	μA	
V_{IL}	Input Low Voltage		-0.3	0.65	V	
V_{IH}	Input High Voltage		2.2	V_{CC}	V	
V_{OL}	Output Low Voltage			0.4	V	$I_{OL} = 2$ mA
V_{OH}	Output High Voltage		2.4		V	$I_{OH} = -1$ mA

Capacitance

Symbol	Parameter	Limits Min.	Max.	Units	Conditions
C_{IN}	Input Capacitance		8	pF	$V_{IN} = 0V$, on all Input Pins
C_O	Output Capacitance		12	pF	$V_O = 0V$

A.C. Characteristics for Read Cycle: $T_A = 0°C$ to $70°C$, $V_{CC} = 5V \pm 5\%$ (Unless otherwise specified)

Symbol	Parameter	S5101L1 Limits		S5101L S5101L3 Limits		S5101L8 S5101-8 Limits		Units	Conditions
		Min.	Max.	Min.	Max.	Min.	Max.		
T_{RC}	Read Cycle Time	450		650		800		ns	
T_{ACC}	Access Time		450		650		800	ns	
T_{CO1}	$\overline{CE1}$ to Output Delay		400		600		800	ns	
T_{CO2}	CE2 to Output Delay		500		700		850	ns	See A.C.
T_{OD}	Output Disable to Enabled Output Delay		250		350		450	ns	Conditions of Test and
T_{DF}	Output Disable to Output H-Z State Delay	0	130	0	150	0	200	ns	A.C. Test Load
T_{OH1}	Output Data Valid Into Next Cycle with respect to Address	0		0		0		ns	
T_{OH2}	Output Data Valid Into Next Cycle with respect to Chip Enable	0		0		0		ns	

Read Cycle
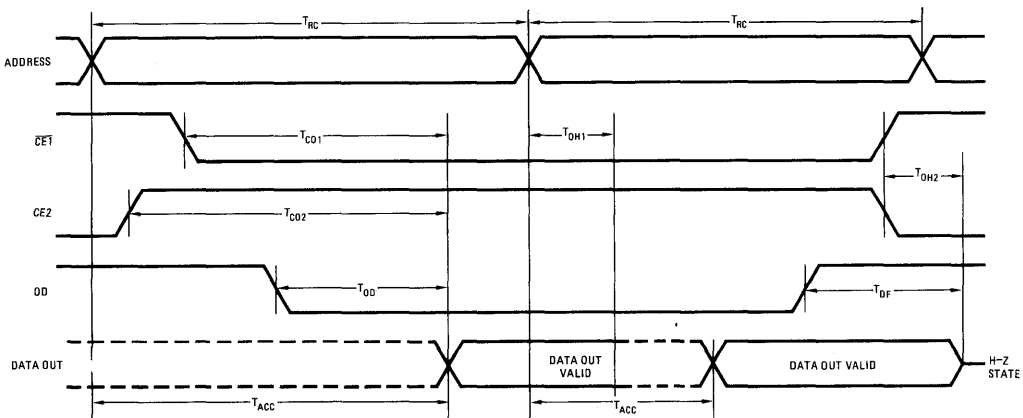
1076145

Note:
1. OD may be tied low for seaprate I/O information.
2. The output will go into a high impedance state if either CE1 is high, CE2 is low, OD is high or R/W is low.

A.C. Characteristics for Write Cycle — Separate or Common Data I/O Using Output Disable

$T_A = 0°C$ to $70°C$, $V_{CC} = 5V \pm 5\%$ (Unless otherwise specified)

Symbol	Parameter	S5101L1 Limits		S5101L S5101L3 Limits		S5101L8 S5101-8 Limits		Units	Conditions
		Min.	Max.	Min.	Max.	Min.	Max.		
T_{WC}	Write Cycle Time	450		650		800		ns	
T_{AW}	Address To Write Delay	130		150		200		ns	
T_{CW1}	CE1 to Write Delay	350		550		650		ns	See A.C.
T_{CW2}	CE2 to Write Delay	350		550		650		ns	Conditions
T_{DW}	Data Set-Up to End of Write Time	250		400		450		ns	of Test and A.C.
T_{DH}	Data Hold After End of Write Time	50		100		100		ns	Test Load
T_{WP}	Write Pulse Width	250		400		450		ns	
T_{WR}	End of Write to New Address Recovery Time	50		50		100		ns	
T_{DS}	Output Disable to Data-In Set-Up Time	130		150		200		ns	

Write Cycle — For Separate or Common Data I/O
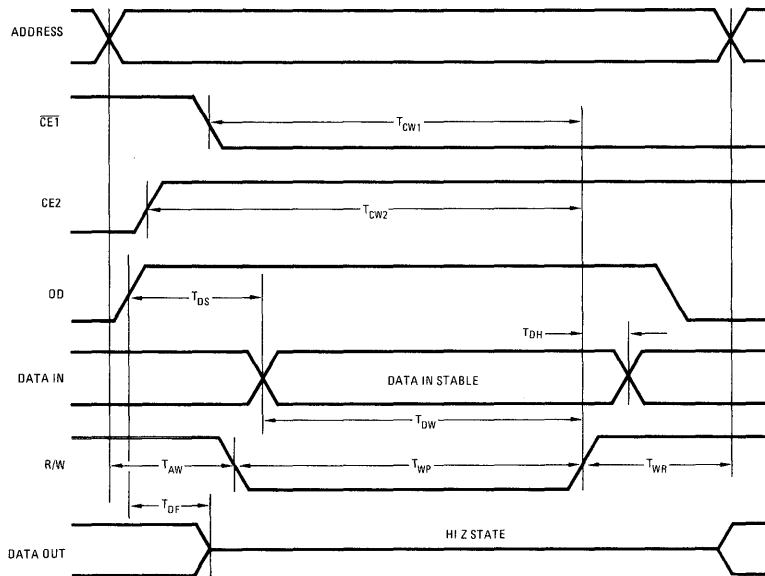
1076147

Low V$_{CC}$ Data Retention Characteristics for S5101L, S5101L1, S5101L3 and S5101L8 [1]

T$_A$ = 0°C to 70°C

Symbol	Parameter		Min.	Max.	Units	Conditions
				Limits		
			Min.	**Max.**	**Units**	**Conditions**
V$_{DR}$	V$_{CC}$ for Data Retention		2.0		V	CE2 ≤ 0.2V
I$_{CCDR}$	Data Retention Supply Current	S5101L1, S5101L		10	μA	V$_{CC}$ = V$_{DR}$
		S5101L3		140	μA	T$_R$ = T$_F$ = 20ns
		S5101L8		500	μA	CE2 ≤ 0.2V
T$_{CRD}$	Chip Deselect to Data Retention Time		0		ns	
T$_R$	Operation Recovery Time		T$_{RC}$[2]		ns	

Notes:
[1] For guaranteed low V$_{CC}$ Data Retention @ 2.0V, order must specify S5101L, S5101L1, S5101L3 or S5101L8.
[2] T$_{RC}$ = Read Cycle Time.

Low V$_{CC}$ Data Retention Wave Form

1. 4.75V
2. V$_{DR}$
3. V$_{IH}$
4. 0.2V
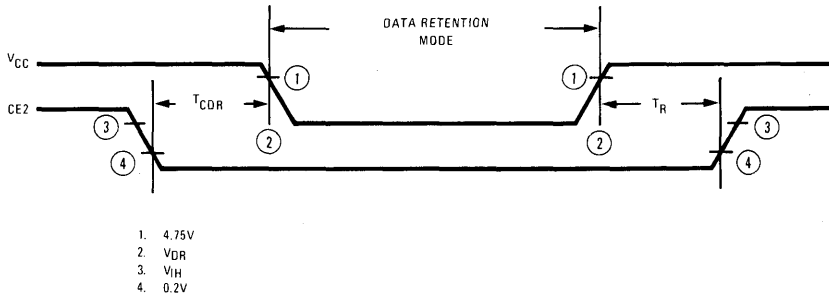
477215

A.C. Test Load
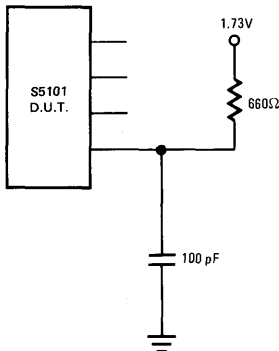
1076146

A.C. Conditions of Test

Input Levels	0.65V to 2.2V
Input Rise and Fall Time	20ns
Timing Measurement Reference Level	1.5V

AMI

AMERICAN MICROSYSTEMS, INC.

4096 BIT (4096×1) STATIC CMOS RAM

Features

- ☐ Low Standby Power—10μW Typ.
- ☐ Low Operating Power—20mW Typ.
- ☐ Low Voltage Data Retention —2.0V
- ☐ High Density Standard 18 Pin Package
- ☐ Fast Access Time 300ns
- ☐ On Chip Address Latches
- ☐ SiGate CMOS Technology

General Description

The AMI S6504 is a 4096×1 bit low power CMOS RAM offering static operation with a single +5V power supply. All inputs and outputs are fully TTL compatible. The addresses are buffered by on-chip address latches. These internal registers are latched by the HIGH to LOW transition of the $\overline{CE}$. The write enable and chip enable functions are designed such that either separate or common data 110 operat ms can be easily implemented for maximum design flexibility.

Block Diagram

Logic Symbol

Pin Configuration

Truth Table

Mode	$\overline{W}$	$\overline{CE}$	Data In	Data Out
Read	H	L	X	Data In
Write	L	L	X	Hi-Z
Not Selected	X	H	X	Hi-Z

Pin Names

A0—A11 .... Address Inputs
Q .... Output
D .... Data In
$\overline{CE}$ .... Chip Enable (Active LOW)
$\overline{W}$ .... Write Enable (Active LOW)
V_{CC} .... +5V Power Supply

1024 BIT (1024×1) STATIC CMOS RAM

Features

☐ Ultra Low Standby Power

☐ S6508 Completely TTL Compatible

☐ S6508A Completely CMOS Compatible

☐ 4V to 11V Operation (S6508A)

☐ Data Retention at 2V

☐ Three-State Output

☐ Low Operating Power: 10mW @ 1MHz (5V)

☐ Fast Access Time: 115ns @ 10V

General Description

The AMI S6508 family of 1024x1 bit static CMOS RAMs offers ultra low power dissipation with a single power supply. The device is available in two versions. The basic part (S6508) operates on 5V and is directly TTL compatible on all inputs and the three-state output. The S6508 "A" operates from 4V to 11V and is fully CMOS compatible. The data is stored in ultra low power CMOS static RAM cells (six transistor). The stored data is read out nondestructively and is the same polarity as the original input data. The address is buffered by on-chip address registers. These internal registers are latched by the HIGH to LOW transition of chip enable ($\overline{CE}$). The write enable and chip enable functions are designed such that either separate or common data I/O operations can be easily implemented for maximum design flexibility.

Block Diagram

Logic Symbol

Pin Configuration

Pin Names

A0-A9	Address Inputs	$\overline{CE}$	Chip Enable
D_{IN}	Data Input	$\overline{WE}$	Write Enable
D_{OUT}	Data Output	V_{CC}	Power Supply
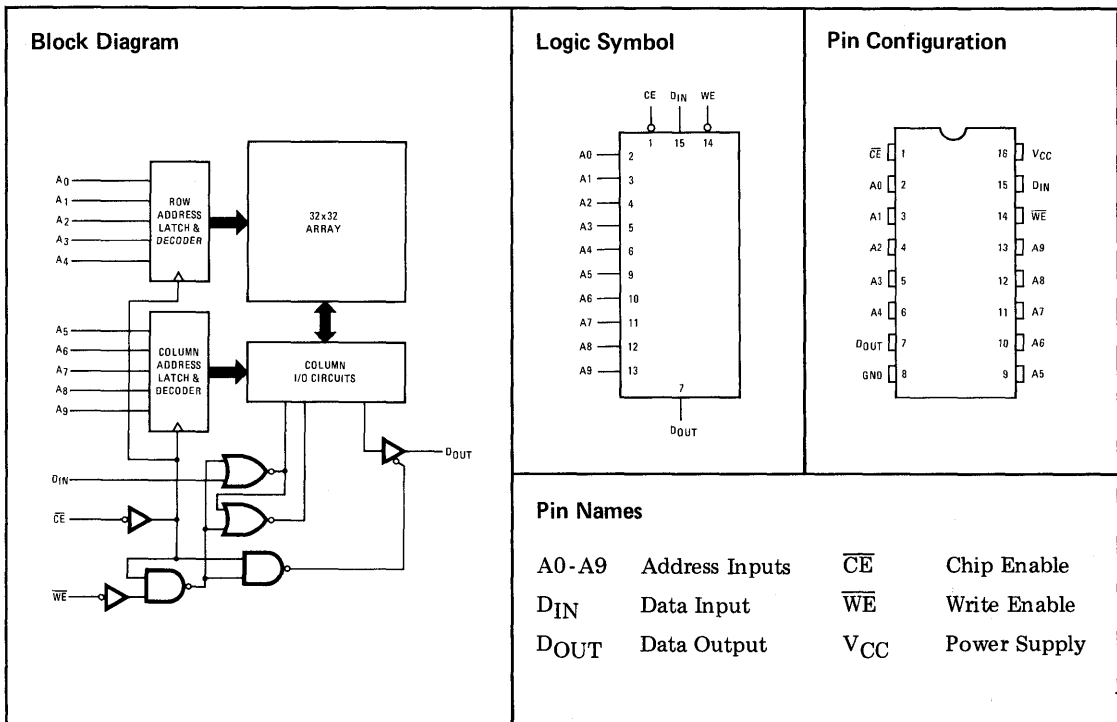
General Description (Continued)

The S6508 is fabricated using a silicon gate CMOS process suitable for high volume production of high performance, ultra low power memories. When deselected ($\overline{CE}$ = HIGH), the S6508-1 draws less than 10 microamps from the 5V supply. In addition, it offers guaranteed data retention with the power supply as low as 2 volts. This process makes the device an ideal choice where battery augmented nonvolatile RAM storage is mandatory.

CMOS to TTL — S6508/S6508-1
Absolute Maximum Ratings

Supply Voltage 8.0V
Input or Output Voltage Supplied .... GND – 0.5V to V_{CC} + 0.5V
Storage Temperature Range .... –65°C to 150°C
Operating Temperature Range, Commercial .... 0°C to 70°C

D.C. Characteristics (V_{CC} = 5.0V ± 10%, T_A = 0°C to 70°C)

Symbol	Parameter		Min.	Max.	Units	Conditions
V_{IH}	Logical "1" Input Voltage		V_{CC}– 2.0		V	
V_{IL}	Logical "0" Input Voltage			0.8	V	
I_{IL}	Input Leakage		– 1.0	1.0	μA	$0V < V_{IN} < V_{CC}$
V_{OH2}	Logical "1" Output Voltage		V_{CC}– 0.01		V	I_{OUT} = 0
V_{OH1}	Logical "1" Output Voltage		2.4		V	I_{OH} = – 0.2mA
V_{OL2}	Logical "0" Output Voltage			GND+0.01	V	I_{OUT} = 0
V_{OL1}	Logical "0" Output Voltage			0.45	V	I_{OL} = 2.0mA
I_O	Output Leakage		– 1.0	1.0	μA	$0V < V_O < V_{CC}, \overline{CE} = V_{IH}$
I_{CCL}	Standby Supply Current	S6508		100	μA	$V_{IN} = V_{CC}$
		S6508-1		10	μA	
I_{CC}	Supply Current S6508/S6508-1			2.5	mA	f = 1MHz
C_{IN}	Input Capacitance			7.0	pF	
C_O	Output Capacitance			10.0	pF	

A.C. Characteristics (V_{CC} = 5.0V ± 10%, C_L = 50pF (One TTL Load), T_A = 0°C to 70°C)

Symbol	Parameter	S6508-1		S6508		Units	Conditions
		Min.	Max.	Min.	Max.		
t_{ACC}	Access Time from $\overline{CE}$		300		460	ns	
t_{EN}	Output Enable Time		180		285	ns	
t_{DIS}	Output Disable Time		180		285	ns	
t_{CEH}	$\overline{CE}$ HIGH	200		300		ns	
t_{CEL}	$\overline{CE}$ LOW	300		460		ns	See A.C. conditions of test and A.C. test load.
t_{WP}	Write Pulse Width (LOW)	200		300		ns	
t_{AS}	Address Setup Time	7		15		ns	
t_{AH}	Address Hold Time	90		130		ns	
t_{DS}	Data Setup Time	200		300		ns	
t_{DH}	Data Hold Time	0		0		ns	
t_{MOD}	Data Modify Time	0		0		ns	

CMOS to CMOS – S6508A/S6508A-1

Absolute Maximum Ratings

Supply Voltage 12.0V
Input or Output Voltage Applied .... −0.5V to V_{CC} + 0.5V
Storage Temperature Range .... −65°C to 150°C
Operating Temperature Range, Commercial .... 0°C to 70°C

D.C. Characteristics (V_{CC} = 4V to 11V, T_A = 0°C to 70°C)

Symbol	Parameter		Min.	Max.	Units	Conditions
V_{IH}	Logical "1" Input Voltage		70% V_{CC}		V	
V_{IL}	Logical "0" Input Voltage			20% V_{CC}	V	
I_{IL}	Input Leakage		−1.0	1.0	μA	$0V < V_{IN} < V_{CC}$
V_{OH}	Logical "1" Output Voltage		V_{CC}− 0.01		V	I_{OUT} = 0
V_{OL}	Logical "0" Output Voltage			GND+0.01	V	I_{OUT} = 0
I_O	Output Leakage		−1.0	1.0	μA	$0V < V_O < V_{CC}$, $\overline{CE} = V_{IH}$
I_{CCL}	Standby Supply Current	S6508A		500	μA	$V_{IN} = V_{CC}$
		S6508A-1		100	μA	
I_{CC}	Supply Current (S6508A/S6508A-1)	V_{CC} = 5V		2.5	mA	f = 1MHz
		V_{CC}=10V		5.0	mA	
C_{IN}	Input Capacitance			7.0	pF	
C_O	Output Capacitance			10.0	pF	

A.C. Characteristics (V_{CC} = V_{CC} ± 10%, T_A = 0°C to 70°C)

Symbol	Parameter	VCC	S6508A-1 Min.	S6508A-1 Max.	S6508A Min.	S6508A Max.	Units	Conditions
t_{ACC}	Access Time from $\overline{CE}$	5V		275		460	ns	
		10V		115		185	ns	
t_{EN}	Output Enable Time	5V		165		285	ns	
		10V		75		120	ns	
t_{DIS}	Output Disable Time	5V		165		285	ns	
		10V		75		120	ns	
t_{CEH}	$\overline{CE}$ HIGH	5V	175		300		ns	
		10V	80		125		ns	
t_{CEL}	$\overline{CE}$ LOW	5V	275		460		ns	
		10V	115		185		ns	
t_{WP}	Write Pulse Width (LOW)	5V	175		300		ns	See A.C. conditions
		10V	80		125		ns	of test and A.C. test
t_{AS}	Address Setup Time	5V	7		15		ns	load.
		10V	7		15		ns	
t_{AH}	Address Hold Time	5V	80		130		ns	
		10V	40		60		ns	
t_{DS}	Data Setup Time	5V	175		300		ns	
		10V	80		125		ns	
t_{DH}	Data Hold Time	5V	0		0		ns	
		10V	0		0		ns	
t_{MOD}	Data Modify Time	5V	0		0		ns	
		10V	0		0		ns	

RAMs

Read Cycle
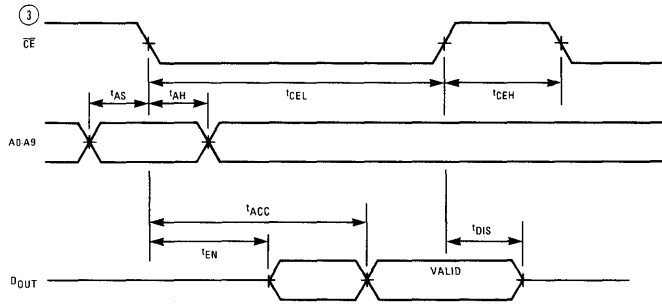
Write Cycle
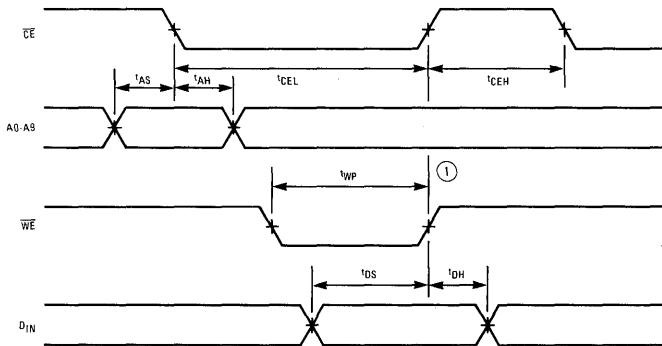
Read Modify Write Cycle
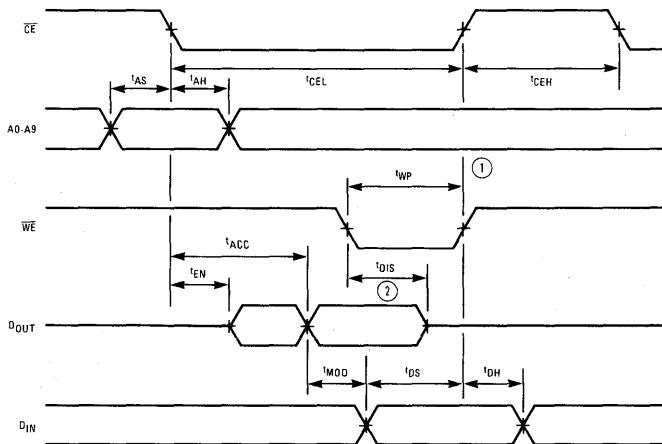
NOTES:

1. The write operation is terminated on any positive edge of Chip Enable ($\overline{\text{CE}}$) or Write Enable ($\overline{\text{WE}}$).
2. The data output will be in the high impedance state whenever $\overline{\text{WE}}$ is LOW.
3. $\overline{\text{WE}}$ is HIGH during a read operation.
4. Rise and fall times of V_{CC} equal 20ns.

Low V$_{CC}$ Data Retention Characteristics (T$_A$ = 0°C to 70°C)

Symbol	Parameter		Min.	Max.	Units	Conditions
V$_{DR}$	V$_{CC}$ for Data Retention		2.0		V	$\overline{CE}$ = 2.0V
I$_{CCDR}$	Data Retention	S6508, S6508A		10	μA	V$_{CC}$ = V$_{DR}$ Min.
	Supply Current	S6508-1, S6508A-1		1.0	μA	V$_{IN}$ = V$_{CC}$
t$_{CDR}$	Deselect Setup Time		t$_{CEH}$		ns	
t$_R$	Recovery Time		t$_{CEH}$		ns	

Low V$_{CC}$ Data Retention Waveform (note 4)

877243

A.C. Test Load

2.217V

909Ω

OUTPUT

50pF
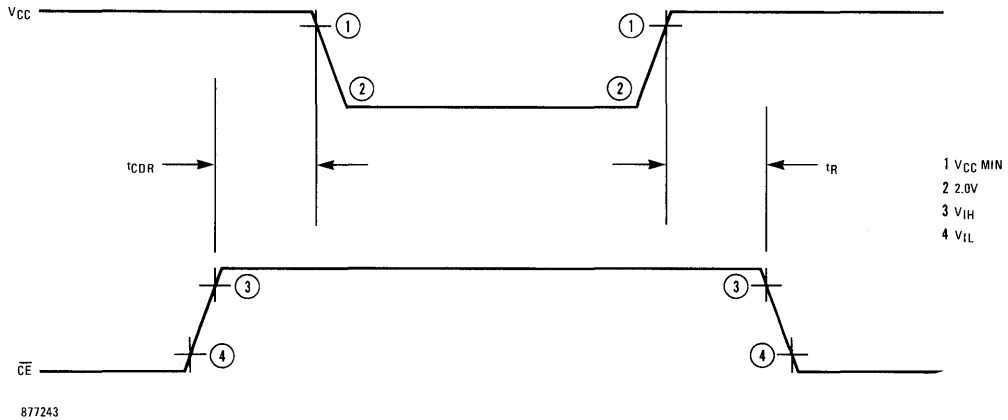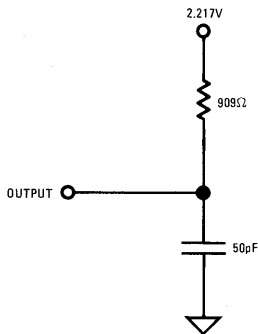
A.C. Test Conditions

Input Levels . . . . V$_{IL}$ to V$_{IH}$
Input Rise & Fall 20ns
Timing Measurement Reference Level
    S6508/S6508-1 . . . . 1.5V
    S6508A/S6508-1 . . . . 50% V$_{CC}$

877244

RAMs

AMI
AMERICAN MICROSYSTEMS, INC.

4096 BIT (1024 × 4)
STATIC CMOS RAM

Features

☐ **Low Power Standby—1mW MAX**

☐ **TTL Compatible Inputs/Outputs**

☐ **Three-State Outputs**

☐ **On-Chip Address Registers**

☐ **Data Retention @ 2V**

☐ **Standard 18 pin Package/Pinouts**

General Description

The AMI S6514 is a 1024x4 static CMOS RAM offering low power and static operation with a single +5 volt power supply. All inputs and outputs are TTL compatible. The common Data I/O pins allow direct interface with common bus systems.

Battery-backup design is simplified by use of $\overline{CE}$, which when HIGH, allows the other inputs to float.

Block Diagram

Pin Connections

A6	1	18	VCC
A5	2	17	A7
A4	3	16	A8
A3	4	15	A9
A0	5	14	D/Q1
A1	6	13	D/Q2
A2	7	12	D/Q3
$\overline{CE}$	8	11	D/Q4
GND	9	10	$\overline{WE}$

Pin Names

A0-A9	Address Inputs
D/Q_1-D/Q_4	Data Inputs/Outputs
$\overline{CE}$	Chip Enable
$\overline{WE}$	Write Enable

Truth Table

Mode	$\overline{E}$	$\overline{W}$	Data Out
Read	L	H	Data In
Write	L	L	HI-Z
Disable	H	X	HI-Z
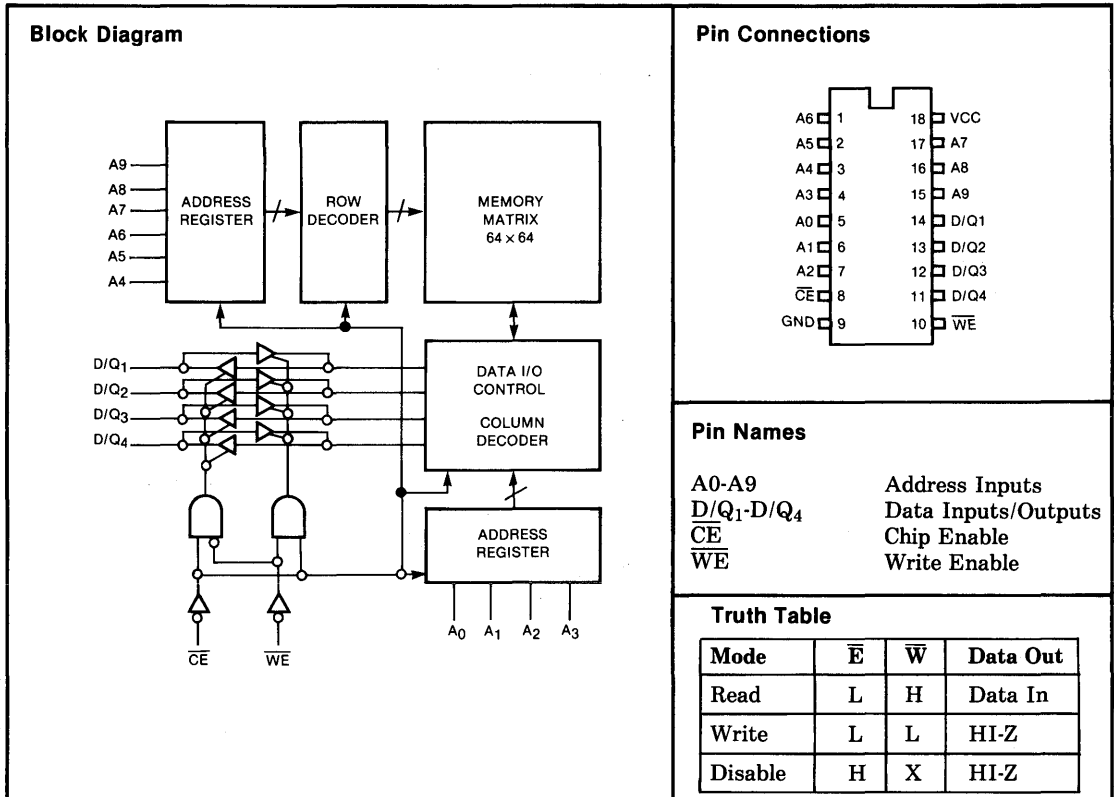
Absolute Maximum Ratings

Supply Voltage – VCC .... −0.3V to +7.0V

Input/Output Voltage Applied .... −0.3V to VCC +0.3V

Storage Temperature–Tstg .... −65 °C to +150 °C

DC Electrical Characteristics: TA= 0 °C to 70 °C, VCC = +5V±10%

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
ILI	Input Leakage Current	−1		1	μA	Vin=GND to VCC
ILO	Output Leakage Current			1	μA	Vin=GND to VCC
ISB	Standby Supply Current			50	μA	Vin=GND or VCC
ICC	Operating Supply Current			7	mA	Vin=GND or VCC,f=1MHz
VIL	Input Voltage LOW	−0.3		0.8	V	
VIH	Input Voltage HIGH	2.4		VCC+0.3	V	
VOL	Output Voltage LOW			0.4	V	IOL=1.6mA
VOH	Output Voltage HIGH	2.4			V	IOH=0.4mA

Capacitance: TA=25 °C, t=1MHz. Capacitance is sampled and guaranteed.

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
Cin	Input Capacitance			8	p^F	
Cout	Output Capacitance			10	p^F	

Low VCC Data Retention Characteristics:

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
ICCDR	ICC For Data Retention			25	μA	Vin=GND or VCC
VCCDR	VCC for Data Retention	2.0			V	
tCDR	Chip Deselect to Data Retention Time	0			ns	
tR	Operation Recovery Time	TELEL				

Low VCC Data Retention Wave Form
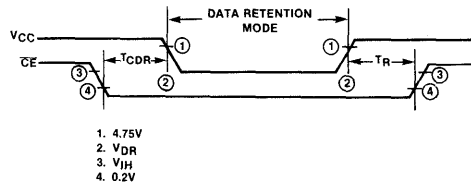
AC Test Conditions

t rise/t fall 20ns

Output Load 50pF

All Timing 1.5V

AC Electrical Characteristics: TA=0 °C to 70 °C, VCC=5V± 10%

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
TELQV	Chip Enable Access Time			300	ns	
TAVQV	Address Access Time			320	ns	
TWLQZ	Write Enable Output Disable Time			100	ns	
TEHQZ	Chip Enable Output Disable Time			100	ns	
TELEH	Chip Enable Pulse Negative Width	300			ns	
TEHEL	Chip Enable Pulse Positive Width	120			ns	
TAVEL	Address Setup Time	20			ns	
TELAX	Address Hold Time	50			ns	
TWLWH	Write Enable Pulse Width	300			ns	
TWLEH	Write Enable Pulse Setup Time	300			ns	
TELWH	Write Enable Pulse Hold Time	300			ns	
TDVWH	Data Setup Time	200			ns	
TWHDZ	Data Hold Time	0			ns	
TWHEL	Write Enable Read Setup Time	0			ns	
TQVWL	Output Data Valid to Write Time	0			ns	
TWLDV	Write Data Delay Time	100			ns	
TELWL	Early Output High-Z Time			0	ns	
TWHEH	Late Output High-Z Time			0	ns	
TELEL	Read or Write Cycle Time	420			ns	

Read Modify Write Cycle
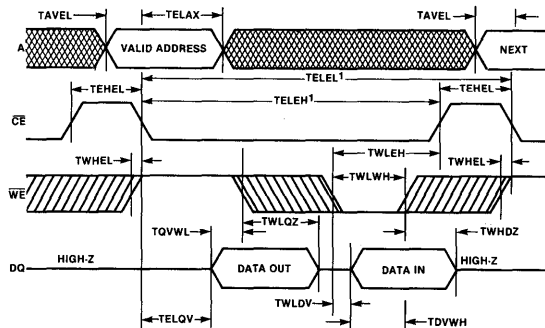
Note 1: TELEL & TELEH are longer than the minimum given for Read or Write cycle.

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Read Cycle: $\overline{WE}$ = HIGH

Write Cycle

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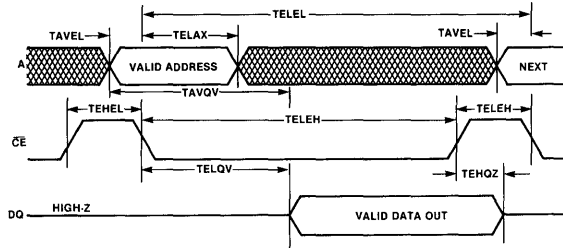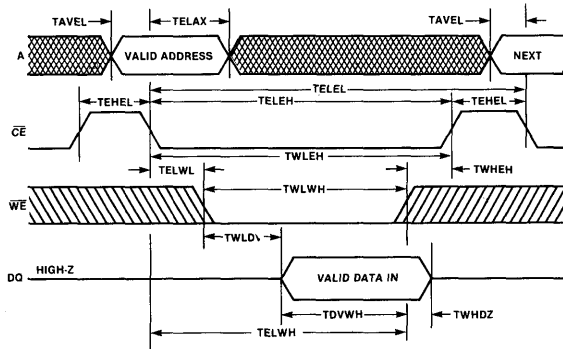
16,384 BIT (2048x8) STATIC NMOS ROM

Features

☐ Single +5V Power Supply

☐ Directly TTL Compatible Inputs

☐ Three-State TTL Compatible Outputs

☐ Three Programmable Enables

☐ Access Time: 450ns Maximum

☐ 2716 EPROM Pin Compatible

☐ Low Power: Supply Current is 80mA Maximum

General Description

The AMI S6831B is a 16,384 bit mask programmable Read-Only-Memory offering fully static operation with a single +5V power supply. The device is fully TTL compatible on all inputs and three-state outputs. The three enables are mask programmable, the active level is specified by the user.

The S6813B is pin compatible with the 2708 and 2716 EPROMs. Software developed in EPROMs can be put in low cost ROM for high volume production.

The device is organized as 2048 words by 8 bits, a configuration particularly suitable for microprocessors. The S6831B is manufactured with an N-channel silicon gate depletion load technology.

Block Diagram

*PROGRAMMABLE CHIP SELECTS

Logic Symbol

Pin Configuration

Pin Names

$A_0 - A_{10}$	Address Inputs
$Q_0 - Q_7$	Data Outputs
CS1 — CS3	Chip Select Inputs
V_{CC}	+5V Power Supply

Absolute Maximum Ratings

Ambient Temperature Under Bias .... $-0°C$ to $70°C$

Storage Temperature .... $-65°C$ to $150°C$

Output or Supply Voltages .... $-0.5V$ to $7V$

Input Voltages .... $-0.5V$ to $7V$

Power Dissipation .... $1W$

COMMENT: Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may effect device reliability.

D.C. Characteristics: $V_{CC} = +5V \pm 5\%$, $T_A = 0°C$ to $70°C$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{OL}	Output LOW Voltage			0.4	V	$I_{OL} = 3.2mA$
V_{OH}	Output HIGH Voltage	2.4			V	$I_{OH} = -220\mu A$
V_{IL}	Input LOW Voltage	-0.5		0.8	V	
V_{IH}	Input HIGH Voltage	2.0		V_{CC}	V	
I_{LI}	Input Leakage Current			10	μA	$V_{IN} = 0V$ to 5.25V
I_{LO}	Output Leakage Current			10	μA	$V_O = 0.4V$ to 5.25V Chip Deselected
I_{CC}	Power Supply Current			70	mA	$V_{CC} = 5.25V$, $T_A = 0°C$

Capacitance: $T_A = 25°C$, $f = 1.0MHz$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
C_{IN}	Input Capacitance			7	pF	$V_{IN} = 0V$
C_{OUT}	Output Capacitance			10	pF	$V_{OUT} = 0V$

A.C. Characteristics: $V_{CC} = +5V \pm 5\%$, $T_A = 0°C$ to $70°C$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
t_{CYC}	Read Cycle Time	450			ns	See Test Circuit and Waveforms
t_{AA}	Address Access Time			450	ns	
t_{AE}	Enable Access Time			200	ns	
t_{OFF}	Output Disable Time	10		150	ns	

Propagation Delay from Address Inputs
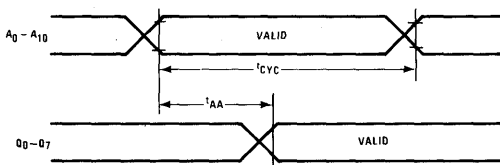
Propagation Delay From Chip Enable
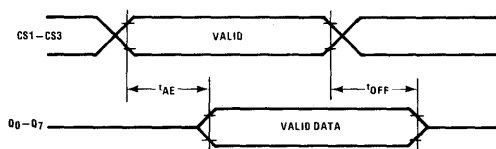
A.C. Test Conditions

Input Pulse Levels .... 0.4V to 2.4V
Input Rise and Fall Times .... ⩽20ns
Input Timing Level 1.5V
Output Timing Levels .... 0.8V and 2.0V
Output Load .... 1 TTL Gate and $C_L = 100pF$

Custom Programming

The preferred method of pattern submission is the AMI Hex format as described below, with its built-in address space mapping and error checking. This is the format produced by the AMI Assembler. The format is as follows and may be on paper tape, punched cards or other media readable by AMI.

Position	Description
1	Start of record (Letter S)
2	Type of record
	0 — Header record (comments)
	1 — Data record
	9 — End of file record
3, 4	Byte Count
	Since each data byte is represented as two hex characters, the byte count must be multiplied by two to get the number of characters to the end of the record. (This includes checksum and address data.) Records may be of any length defined in each record by the byte count.
5, 6, 7, 8	Address Value
	The memory location where the first data byte of this record is to be stored. Addresses should be in ascending order.
9, . . ., N	Data
	Each data byte is represented by two hex characters. Most significant character first.
N+1, N+2	Checksum
	The one's complement of the additive summation (without carry) of the data bytes, the address, and the byte count.

Example: S 1 1 3 0 0 0 0 4 9 E 9 F 1 0 3 2 0 F 0 4 9 3 1 3 9 F 7 2 0 0 0 F 5 E 0 F 0 0 1 2 6
S 9 0 3 0 0 0 0 F C

NOTES:
1. Only positive logic formats for E_0, E_1, E_2 are accepted. 1 = V_{HIGH}; 0 = V_{LOW}
2. A "0" indicates the chip is enabled by a logic 0.
   A "1" indicates the chip is enabled by a logic 1.
3. Paper tape format is the same as the card format above except:
   a. The record should be a maximum of 80 characters.
   b. Carriage return and line feed after each record followed by another record.
   c. There should NOT be any extra line feed between records at all.
   d. After the last record, four (4) $$$$ (dollar) signs should be punched with carriage return and line feed indicating end of file.

AMI

S68332/S68A332

32,768 BIT (4096x8)
STATIC NMOS ROM

Features

☐ **Fast Access Time:**
   S68332: 450ns Maximum
   S68A332: 350ns Maximum

☐ **Fully Static Operation**

☐ **Single +5V ±5% Power Supply**

☐ **Directly TTL Compatible Inputs**

☐ **Three-State TTL Compatible Outputs**

☐ **Two Programmable Chip Selects**

☐ **EPROM Pin Compatible**

General Description

The AMI S68332 is a 32,768 bit static mask programmable NMOS ROM organized as 4096 words by 8 bits. The device is fully TTL compatible on all inputs and outputs and has a single +5V power supply. The three state outputs facilitate memory expansion by allowing the outputs to be OR-tied to other devices.

The S68332 is pin compatible with UV EPROMs making system development much easier and more cost effective. It is fully static, requiring no clocks for operation. The two chip selects are mask programmable, the active level for each being specified by the user.

The S68332 is fabricated using AMI's N-Channel MOS technology. This permits the manufacture of very high density, high performance mask programmable ROMs.

Block Diagram

*PROGRAMMABLE CHIP SELECTS

Logic Symbol

Pin Configuration

Pin Names

$A_0 - A_{11}$	Address Inputs
$Q_0 - Q_7$	Data Outputs
$CS_1 - CS_2$	Chip Select Inputs
V_{CC}	+5V Power Supply

ROMs

Absolute Maximum Ratings*

Ambient Temperature Under Bias .... $-0°C$ to $70°C$
Storage Temperature .... $-65°C$ to $150°C$
Output or Supply Voltages .... $-0.5V$ to $7V$
Input Voltages .... $-0.5V$ to $7V$
Power Dissipation 1W

*COMMENT: Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may effect device reliability.

D.C. Characteristics: $V_{CC} = +5V \pm 5\%$, $T_A = 0°C$ to $70°C$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{OL}	Output LOW Voltage			0.4	V	$I_{OL} = 3.2mA$
V_{OH}	Output HIGH Voltage	2.4			V	$I_{OH} = -220\mu A$
V_{IL}	Input LOW Voltage	-0.5		0.8	V	
V_{IH}	Input HIGH Voltage	2.0		V_{CC}	V	
I_{LI}	Input Leakage Current			10	μA	$V_{IN} = 0V$ to 5.25V
I_{LO}	Output Leakage Current			10	μA	$V_O = 0.4V$ to 5.25V Chip Deselected
I_{CC}	Power Supply Current			70	mA	$V_{CC} = 5.25V$, $T_A = 0°C$

Capacitance: $T_A = 25°C$, $f = 1.0MHz$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
C_{IN}	Input Capacitance			7	pF	$V_{IN} = 0V$
C_{OUT}	Output Capacitance			10	pF	$V_{OUT} = 0V$

A.C. Characteristics: $V_{CC} = +5V \pm 5\%$, $T_A = 0°C$ to $70°C$

Symbol	Parameter		Min.	Typ.	Max.	Units	Conditions
t_{AA}	Address Access Time	S68332			450	ns	See. A.C. Test Conditions and Waveform
		S68A332			350	ns	
t_{ACS}	Chip Select Access Time	S68332			150	ns	
		S68A332			150	ns	
t_{OFF}	Chip Deselect Time	S68332	0		150	ns	
		S68A332	0		150	ns	

Waveforms
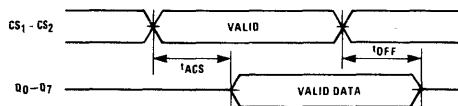
Propagation From Chip Select
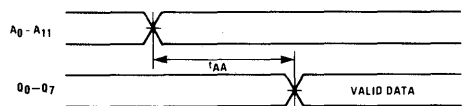
Propagation From Address

A.C. Test Conditions

Input Pulse Levels	0.4V to 2.4V
Input Rise and Fall Times	≤20ns
Input Timing Level	1.5V
Output Timing Levels	0.8V and 2.0V
Output Load	1 TTL Load and 100pF

Custom Programming

The preferred method of pattern submission is the AMI Hex format as described below, with its built-in address space mapping and error checking. This is the format produced by the AMI Assembler. The format is as follows and may be on paper tape, punched cards or other media readable by AMI.

Position	Description
1	Start of record (Letter S)
2	Type of record
	0 — Header record (comments)
	1 — Data record
	9 — End of file record
3, 4	Byte Count
	Since each data byte is represented as two hex characters, the byte count must be multiplied by two to get the number of characters to the end of the record. (This includes checksum and address data.) Records may be of any length defined in each record by the byte count.
5, 6, 7, 8	Address Value
	The memory location where the first data byte of this record is to be stored. Addresses should be in ascending order.
9, . . ., N	Data
	Each data byte is represented by two hex characters. Most significant character first.
N+1, N+2	Checksum
	The one's complement of the additive summation (without carry) of the data bytes, the address, and the byte count.

Example:
```
S 1 1 3 0 0 0 0 4 9 E 9 F 1 0 3 2 0 F 0 4 9 3 1 3 9 F 7 2 0 0 0 F 5 E 0 F 0 0 1 2 6
S 9 0 3 0 0 0 0 F C
```


NOTES:
1. Only positive logic formats for CS_1 and CS_2 are accepted. $1 = V_{HIGH}$; $0 = V_{LOW}$
2. A "0" indicates the chip is enabled by a logic 0.
   A "1" indicates the chip is enabled by a logic 1.
3. Paper tape format is the same as the card format above except:
   a. The record should be a maximum of 80 characters.
   b. Carriage return and line feed after each record followed by another record.
   c. There should NOT be any extra line feed between records at all.
   d. After the last record, four (4) $$$$ (dollar) signs should be punched with carriage return and line feed indicating end of file.

AMERICAN MICROSYSTEMS, INC.

65,536 BIT (8192x8)
STATIC NMOS ROM

Features

☐ Single +5V±10% Power Supply

☐ High Performance:
  Maximum Access Time: 450ns

☐ EPROM Compatible for Cost Effective
  System Development

☐ Completely Static Operation

☐ Directly TTL Compatible Inputs

☐ Three-State TTL Compatible Outputs

☐ Industry Standard 24 Pin Package

General Description

The AMI S4264 is a 65,536 bit fully static NMOS mask programmable ROM organized as 8192 words by 8 bits. The device is fully TTL compatible on all inputs and outputs and has a single +5V power supply. The three-state outputs facilitate memory expansion by allowing the outputs to be OR-tied to other devices.

The S4264 is fully static requiring no clocks for operation. Data access is simple as no address setup times are required. The byte organization of the S4264 makes it ideal for microprocessor applications.

The S4264 is fabricated using AMI's proprietary NMOS technology. This process permits the manufacture of very high density, high performance mask programmable ROMs.

Block Diagram

Logic Symbol

Pin Configuration

Pin Names

$A_0 - A_{12}$ .... Address Inputs
$Q_0 - Q_7$ .... Data Outputs
CS .... Chip Select Inputs
V_{CC} .... +5V Power Supply

Absolute Maximum Ratings*

Ambient Temperature Under Bias .... 0°C to 70°C
Storage Temperature .... −65°C to 150°C
Output or Supply Voltages .... −0.5V to 7V
Input Voltages .... −0.5V to 7V
Power Dissipation 1W

*COMMENT: Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. Characteristics: $T_A = 0°C$ to $70°C$, $V_{CC} = +5V \pm 10\%$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{OL}	Output LOW Voltage			0.4	V	$I_{OL} = 3.2mA$
V_{OH}	Output HIGH Voltage	2.4			V	$I_{OH} = -220\mu A$
V_{IL}	Input LOW Voltage	−0.5		0.8	V	
V_{IH}	Input HIGH Voltage	2.0		V_{CC}	V	
I_{LI}	Input Leakage Current			10	μA	$V_{IN} = 0V$ to $5.5V$
I_{LO}	Output Leakage Current			10	μA	$\overline{CS} \geqslant 2.4V$, $V_O = 0.4V$ to $5.5V$
I_{CC}	Power Supply Current			100	mA	$V_{CC} = 5.5V$, $T_A = 0°C$

Capacitance: $T_A = 25°C$, $f = 1.0MHz$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
C_{IN}	Input Capacitance			7	pF	$V_{IN} = 0V$
C_{OUT}	Output Capacitance			10	pF	$V_{OUT} = 0V$

A.C. Characteristics: $T_A = 0°C$ to $70°C$, $V_{CC} = +5V \pm 10\%$

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
t_{AA}	Address Access Time			450	ns	See Test Circuit
t_{ACS}	Chip Select Access Time			150	ns	and Waveforms
t_{OFF}	Chip Deselect Time	0		150	ns	

Wave Forms
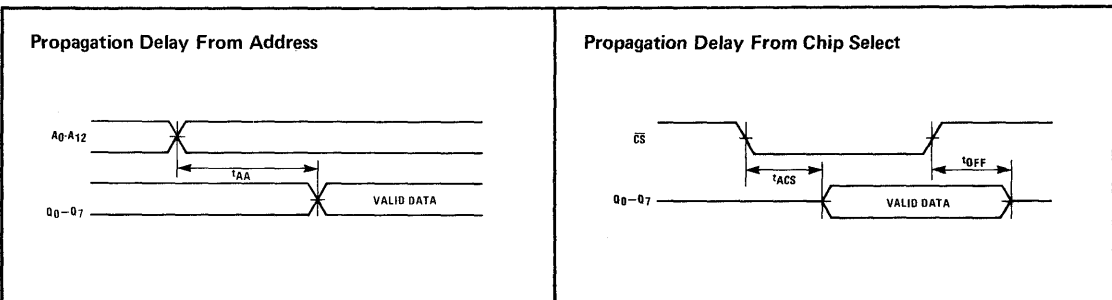
Propagation Delay From Address

Propagation Delay From Chip Select

ROMs

A.C. Test Conditions

Input Pulse Levels	0.4V to 2.4V
Input Rise and Fall Times	≤20ns
Input Timing Levels	1.5V
Output Timing Levels	0.8V to 2.0V
Output Load	1 TTL Load and 100pF

Custom Programming

The preferred method of pattern submission is the AMI Hex format as described below, with its built-in address space mapping and error checking. This is the format produced by the AMI Assembler. The format is as follows and may be on paper tape, punched cards or other media readable by AMI (see NOTES at bottom of page).

Position	Description
1	Start of record (Letter S)
2	Type of record
	0 — Header record (comments)
	1 — Data record
	9 — End of file record
3, 4	Byte Count
	Since each data byte is represented as two hex characters, the byte count must be multiplied by two to get the number of characters to the end of the record. (This includes checksum and address data.) Records may be of any length defined in each record by the byte count.
5, 6, 7, 8	Address Value
	The memory location where the first data byte of this record is to be stored. Addresses should be in ascending order.
9, . . ., N	Data
	Each data byte is represented by two hex characters. Most significant character first.
N+1, N+2	Checksum
	The one's complement of the additive summation (without carry) of the data bytes, the address, and the byte count.

Example: S 1 1 3 0 0 0 0 4 9 E 9 F 1 0 3 2 0 F 0 4 9 3 1 3 9 F 7 2 0 0 0 F 5 E 0 F 0 0 1 2 6
          S 9 0 3 0 0 0 0 F C

NOTES:
1. Paper tape format is the same as the card format above except:
   a. The record should be a maximum of 80 characters.
   b. Carriage return and line feed after each record followed by another record.
   c. There should be NOT be any extra line feed between records at all.
   d. After the last record, four (4) $$$$ (dollar) signs should be punched with carriage return and line feed indicating end of file.

AMI

AMERICAN MICROSYSTEMS, INC.

AMI

AMERICAN MICROSYSTEMS, INC.

S5204A

512 × 8 BIT ERASABLE AND ELECTRICALLY REPROGRAMMABLE READ ONLY MEMORY

Features

- On-Board Programmability
- Fast Access Time — 750ns Max.
- High Speed Programming — Less than 1 Minute for all 4096 Bits
- Programmed with R/W, CS and V_{PROG} Pins
- Completely TTL Compatible — Excluding the V_{PROG} Pin during Read or Write
- Ultraviolet Light Erasable — Less than 10 Minutes
- Static Operation — No Clocks Required
- Three-State Data I/O
- Standard Power Supplies — +5V and -12V
- Mature P-Channel Process

General Description

The S5204A is a high speed, static, 512×8 bit, erasable and electrically programmable read only memory designed for use in bus-organized systems. Both input and output are TTL compatible during both read and write modes. Packaged in a 24-pin hermetically sealed dual in-line package, the bit pattern can be erased by exposing the chip to an ultraviolet light source through the transparent lid, after which a new pattern can be written.

Block Diagram

77675

Pin Configuration

V_{CC}	1	24	GND
R/W	2	23	V_{GG}
$\overline{CS}$	3	22	D7
VPROG	4	21	D6
A0	5	20	D5
A1	6	19	D4
A2	7	18	D3
A3	8	17	D2
A4	9	16	D1
A5	10	15	D0
A6	11	14	A8
V_{CC}	12	13	A7

S5204A
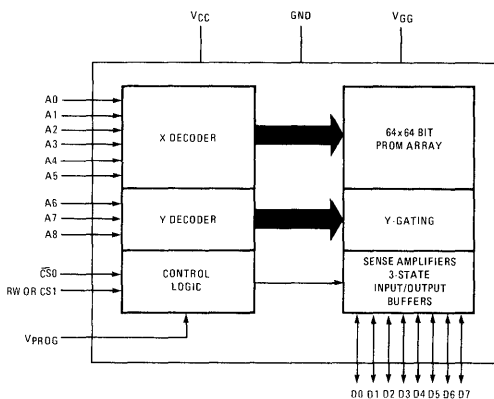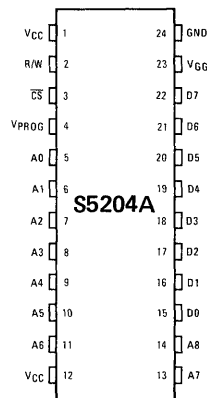
877254

Typical Applications

- ROM Program Debugging
- Code Translation
- Microprogramming
- Look-up Tables
- Random Logic Replacement
- Programmable Waveforms
- Character Generation
- Electronic Keyboards

ABSOLUTE MAXIMUM RATINGS

Voltage on any pin relative to V_{SS} except the V_{PROG} pin	+0.3 to −20V
Voltage on the V_{PROG} pin relative to V_{SS}	+0.3 to −60V
Operating Temperature	0°C to +70°C
Storage Temperature (programmed)	−55°C to +85°C
Storage Temperature (unprogrammed)	−55°C to 150°C

NOTE:

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields, however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

DC (STATIC) CHARACTERISTICS (V_{CC} = +5.0V ± 5%, V_{GG} = −12.0V ± 5% T_A = 0 − 70°C unless otherwise noted).

SYMBOL	CHARACTERISTIC	MIN	MAX	UNIT
V_{IL}	INPUT VOLTAGE LOW		0.8	V
V_{IH}	INPUT VOLTAGE HIGH	V_{CC} −2.25	V_{CC} +.3	V
V_{OL}	OUTPUT VOLTAGE LOW I_{OL} = 1.6 ma		0.4	V
V_{OH}	OUTPUT VOLTAGE HIGH I_{OH} = 200µA	2.4		V
I_{LI}	INPUT LEAKAGE CURRENT		10	µa
I_{LO}	OUTPUT LEAKAGE CURRENT CS = 5V		20	µa
I_{GG}	V_{GG} SUPPLY CURRENT		45	ma
I_{CC}	V_{CC} SUPPLY CURRENT		50	ma
P_D	POWER DISSIPATION		750	mw

NOTE: Program input V_{PROG} may be tied to V_{CC} during the Read.

AC (DYNAMIC) CHARACTERISTICS (Loading is as shown in Figure 1 unless otherwise noted).

SYMBOL	CHARACTERISTIC	MIN	MAX	UNIT
T_{ACC}	ACCESS TIME		750	ns
T_{CO}	CHIP SELECT TO OUTPUT DELAY		400	ns
T_{DD}	CHIP DESELECT TO OUTPUT DELAY			ns

EPROMs

ERASABLE AND ELECTRICALLY PROGRAMMABLE READ ONLY MEMORY

Features

☐ On-Board Programmability
☐ Fast Access Time — 575ns Typ.
☐ Pin Configuration Similar to the S6830 1K x 8 Bit ROM
☐ High Speed Programming — Less than 1 Minute for All 4096 Bits
☐ Programmed with R/W, CS and V$_{PROG}$ Pins
☐ Completely TTL Compatible — Excluding the V$_{PROG}$ Pin
☐ Ultraviolet Light Erasable — Less than 10 Minutes
☐ Static Operation — No Clocks Required
☐ Three-State Data I/O
☐ Standard Power Supplies +5V and −12V
☐ Mature P-Channel Process

General Description

The S6834 is a high speed, static, 512 x 8 bit, erasable and electrically programmable read only memory designed for use in bus-organized systems. Both input and output are TTL compatible during both read and write modes. Packaged in a 24 pin hermetically sealed dual in-line package the bit pattern can be erased by exposing the chip to an ultra-violet light source through the transparent lid, after which a new pattern can be written.

Block Diagram

Pin Configuration

GND	1	24	A$_0$
D$_0$	2	23	A$_1$
D$_1$	3	22	A$_2$
D$_2$	4	21	A$_3$
D$_3$	5	20	A$_4$
D$_4$	6	19	A$_5$
D$_5$	7	18	A$_6$
D$_6$	8	17	A$_7$
D$_7$	9	16	A$_8$
V$_{GG}$	10	15	$\overline{CS}$
V$_{PROG}$	11	14	R/W
V$_{CC}$	12	13	V$_{CC}$

Typical Applications

☐ ROM Program Debugging
☐ Code Translation
☐ Microprogramming
☐ Look-up Tables
☐ Random Logic Replacement
☐ Programmable Waveforms
☐ Character Generation
☐ Electronic Keyboards

ABSOLUTE MAXIMUM RATINGS

Voltage on any pin relative to V_{SS} except the V_{PROG} pin	+0.3 to −20V
Voltage on the V_{PROG} pin relative to V_{SS}	+0.3 to −60V
Operating Temperature	0°C to +70°C
Storage Temperature (programmed)	−55°C to +85°C
Storage Temperature (unprogrammed)	−55°C to 150°C

NOTE:
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields, however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

DC (STATIC) CHARACTERISTICS (V_{CC} = +5.0V ± 5%, V_{GG} = −12.0V ± 5% T_A = 0 − 70°C unless otherwise noted).

SYMBOL	CHARACTERISTIC	MIN	MAX	UNIT
V_{IL}	INPUT VOLTAGE LOW		0.8	V
V_{IH}	INPUT VOLTAGE HIGH	V_{CC} −2.25	V_{CC} +.3	V
V_{OL}	OUTPUT VOLTAGE LOW I_{OL} = 1.6 ma		0.4	V
V_{OH}	OUTPUT VOLTAGE HIGH I_{OH} = 200μA	2.4		V
I_{LI}	INPUT LEAKAGE CURRENT		10	μa
I_{LO}	OUTPUT LEAKAGE CURRENT CS = 5V		20	μa
I_{GG}	V_{GG} SUPPLY CURRENT		45	ma
I_{CC}	V_{CC} SUPPLY CURRENT		50	ma
P_D	POWER DISSIPATION		750	mw

NOTE: Program input V_{PROG} may be tied to V_{CC} during the Read.

AC (DYNAMIC) CHARACTERISTICS (Loading is as shown in Figure 1 unless otherwise noted).

SYMBOL	CHARACTERISTIC	MIN	MAX		UNIT
			(6834)	(6834−1)	
T_{ACC}	ACCESS TIME		575	750	ns
T_{CO}	CHIP SELECT TO OUTPUT DELAY		300	400	ns
T_{DD}	CHIP DESELECT TO OUTPUT DELAY		250	325	ns

EPROMs

ULAs

AMI

AMERICAN MICROSYSTEMS, INC.

UNCOMMITTED LOGIC ARRAYS
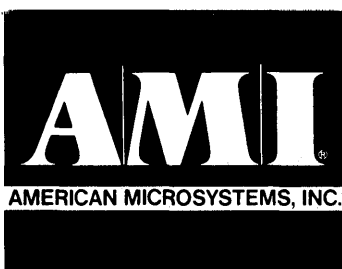
Features

☐ Arrays of uncommitted C-MOS devices "programmed" by metal layer interconnect to implement arbitrary digital logic functions.

☐ Six array configurations—from 300 to 1260 gates.

☐ Quick Turn Prototypes.

☐ Advanced oxide-isolated C-MOS technology.

☐ High Performance—5 to 10 ns typical gate delay.

☐ Broad Power Supply Range—2.5V to 12V.

☐ TTL Compatible I/O.

☐ Up to 76 I/O connections.

☐ Numerous package options.

☐ Full Military temperature range (−55°C to 125°C).

Description

AMI's Uncommitted Logic Array (ULA) products consist of arrays of C-MOS devices whose interconnections are initially unspecified. By "programming" interconnect at the metal layer mask level, virtually arbitrary configurations of digital logic can be realized in an LSI implementation.

AMI ULA designs are based on topological cells—i.e., groups of uncommitted silicon-gate N-channel and P-channel transistors—that are placed at regular intervals along the X and Y axes of the chip with intervening polysilicon underpasses. Pads, input protection circuitry, and uncommitted output drivers are placed around the periphery.

A family of C-MOS ULA products is offered in six configurations, summarized in Table I, with circuit complexities equivalent to 300, 400, 540, 770, 1000, and 1260 two-input gates, respectively. All pads (except the two pre-assigned power supply connections) can be individually configured as inputs, outputs, or I/O's. Input switching characteristics can be programmed for either C-MOS or TTL compatibility. LS Buffer output drivers will support C-MOS levels or two low power schottky TTL loads. TTL Buffer outputs will also provide C-MOS levels and are capable of driving

TABLE I

Circuit	Equivalent Two-Input Gates	Pads	LS Output Drivers	TTL Output Drivers	Low Drive I/O
UA-1	300	40	17	20	1
UA-2	400	46	23	20	1
UA-3	540	52	25	24	1
UA-4	770	62	31	28	1
UA-5	1000	70	35	32	1
UA-6	1260	78	39	36	1

two standard TTL loads. One low drive (C-MOS level) output driver is provided. All output drivers can be programmed for tri-state or open drain (open collector) operation as required.

Pinout or lead count varies with die size and array complexity as shown in Table I. The arrays are offered in standard 40-pin, 48-pin, and 64-pin DIPs (plastic, ceramic or cerdip). Lower lead count DIPs can be provided on request, as can JEDEC-Standard Leadless Chip Carrier (LCC) packages. AMI ULA products are also offered in wafer or unpackaged die form where required.

The C-MOS technology used for these products is AMI's state-of-the-art 5-micron, oxide-isolated, silicon-gate C-MOS process. This process offers all the conventional advantages of C-MOS—i.e., very low power consumption, broad power supply voltage range (2.5V to 12V), and high noise immunity—as well as dense circuits with high performance. Gate propagation delays are in the five to ten ns range for room temperature operation. AMI ULA products operate over the full military temperature range ($-55\,°C$ to $125\,°C$).

In conjunction with these arrays, AMI has developed a set of "functional overlays." These are basic logic element building blocks—e.g. two input and larger gates of various types, flip-flops, and so forth—from which complete logic designs can be developed. Each functional overlay corresponds to a metal interconnect pattern that is superimposed on a set of uncommitted transistors (and polysilicon underpasses) in the array to implement the logic element. Typical functional overlay logic elements and the number of two-input

gate equivalents they utilize are shown in Table II.

AMI will convert customer designed logic to metal interconnect patterns using functional overlays and its proprietary Symbolic Interactive Design System (SIDS). SIDS is a computer aided design tool for layout using on-line color graphics terminals. Interested customers should submit logic diagrams for evaluation and a quotation.

For programs involving multiple ULA patterns from customers with suitable MOS design and layout experience, AMI will also support arrangements in which the customer designs the ULA metal interconnect patterns and furnishes AMI with corresponding metal mask PG tapes to AMI specifications.

TABLE II

Logic Element	2-Input Gate Equivalent
2-Input NOR	1
2-Input NAND	1
3-Input NOR	1.5
3-Input NAND	1.5
INVERTER	.5
D FLIP-FLOP	4
D FLIP-FLOP W/RESET	5
D FLIP-FLOP W/SET-RESET	6
J-K FLIP-FLOP	6.5
CLOCKED LATCH	2
EXCLUSIVE OR	2.5
SCHMITT TRIGGER	5.5
4-BIT BCD CNTR W/RESET	27

DC Characteristics—TTL Interface

Specified @ $V_{DD} = +5V \pm 5\%$
Temperature = $-55\,°C$ to $+125\,°C$

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{IH}	Input High Voltage	2.0			V
V_{IL}	Input Low Voltage			0.8	V
V_{OH}	Output High Voltage (LS Buffer IOH = -700 μa) (T-Buffer IOH = -1.5 ma)	2.7 2.4			V V
I_{OL}	Output Low Voltage (T Buffer IOL = 3.2 ma) (LS Buffer IOL = 0.8 ma)			0.4 0.4	V V
I_{OZ}	3-State Output Leakage Vo = 0 or V_{DD}	-10	0.001	10	μa

ULAs

AMI.

D.C. Characteristics — CMOS Interface

Sym.	Parameter	V_{DD} (Vdc)	Condition	* T Low Min	* T Low Max	25°C Min	25°C Typ	25°C Max	* T High Min	* T High Max	Units
I_{DD}	Quiescent Device Current	5V	$V_{IN} = V_{DD}$		0.1		.005	0.1		1	$\mu A/gate$
		10V			0.2		.01	0.2		2	$\mu A/gate$
V_{OL}	Low Level Output Voltage		$I_O = 1\mu A$		0.05			0.05		0.05	V
V_{OH}	High Level Output Voltage	5V	$I_O = 1\mu A$	4.95		4.95			4.95		V
		10V		9.95		9.95			9.95		V
V_{IL}	Input Low Voltage	5V			1.5			1.5		1.5	V
		10V			3.0			3.0		3.0	V
V_{IH}	Input High Voltage	5V		3.5		3.5			3.5		V
		10V		7.0		7.0			7.0		V
I_{OL}	Output Low (Sink) Current T Buffer	5V	$V_O = 0.4V$	4		4	6.5		3.2		mA
		10V	$V_O = 0.5V$	7		7	12.5		4.0		mA
	LS Buffer	5V	$V_O = 0.4V$	1.0		1.0	1.6		0.8		mA
		10V	$V_O = 0.5V$	1.8		1.8	3.1		1.0		mA
I_{OH}	Output High (Source) Current										
	T Buffer	5V	$V_O = 4.6V$		−400			−400		−400	μA
		10V	$V_O = 9.5V$		−750			−750		−750	μA
	LS Buffer	5V	$V_O = 4.6V$		−200			−200		−200	μA
		10V	$V_O = 9.5V$		−375			−375		−375	μA
I_{IN}	Input Current		$V_{IN} = 0$ or V_{DD}		1			1		1	μA
I_{OZ}	3 State Output Leakage Current		$V_O = 0$ or V_{DD}		±1			±1		±10	μA
	Input Capacitance		Any Input				5				pF

* Military Temperature Range is −55°C to +125°C.
  Commercial Temperature Range is −40°C to +85°C.

11.4

AMI

Communications Products

S2559 Digital Tone Generator 79T01

Describes design considerations, test methods, and results obtained using the S2559 Tone Generator family in DTMF pushbutton telephones. Interface with type 500 and 2500 networks are discussed. Use in ancillary equipment is also covered.

Consumer Products

Useful Noise 79C01

The S2688 Noise Generator is useful in many applications where digital noise is required for audio effects.

Programming the S8890 Rhythm Generator 79C02

Explains the program format and how to submit data for ROM programming.

Touch MOS for Capacitive Switching 79C03

Explains the circuit operation and the design formulas needed to determine system parameters of pad areas, scan clock frequency and reference level adjustments.

18 Touchy Questions 79C04

Answers many of the common questions which may arise when using TouchControl. This note should provide assistance for the successful design of a TouchControl system.

MOS Music 79C05

MOS Music is a primer on the application of standard MOS/LSI circuits in creating electronic music. This note discusses the key elements of music production in an electronic organ.

Real Remote Control 79C06

A remote control system using the S2742 and S2743 with infrared transmission is shown. A simple but effective alignment technique is demonstrated which will ensure successful operation.

S2000 Family

Extended Memory 792K01

This note describes the necessary circuitry needed to extend the program memory (ROM) beyond an S2000/S2150's normal amount.

Musical Application for an S2000 Microcomputer 792K02

This note describes some theory and the application of a microcomputer to generate musical notes. Applications might include electronic games, alarm clock, door bells and telephones.

Repertory Dialers/Feature Phones Using S2000/S2150 .... 792K05

This note describes how an S2000/S2150 can be used in a repertory dialer circuit and how to communicate with external RAM.

AMI.

Application Note Summary

APP NOTE SUMMARY

AMERICAN MICROSYSTEMS, INC.

At AMI we are continually searching for more effective methods of providing protection for MOS devices. Present configurations of protective devices are the result of years of research and review of field problems.

In the normal course of producing integrated circuits however, there occasionally occur variations in oxide thickness which may allow a condition where gate oxide breakdown voltage is less than the protective device breakdown. Although the oxide breakdown voltage may still be far beyond normal voltage levels encountered in operation, excessive voltages may cause permanent damage. Even though AMI has evolved the best designed protective device possible, we recognize that it is not 100% effective.

A large number of failed returns have been due to misapplication of biases. In particular, forward bias conditions cause excessive current through the protective devices, which in turn will vaporize metal lines to the inputs. *Careful inspection of the device data sheets and proper pin designation should help reduce this failure mode.*

Gate ruptures caused by static discharge also account for a large percentage of device failures in customers' manufacturing areas. *Precautions should be taken to minimize the possibility of static charges occurring during handling and assembly of MOS circuits.*

To assist our customers in reducing the hazards which may be detrimental to MOS circuits, the following guidelines for handling MOS are offered. *The precautions listed here are used at AMI.*

1. All benches used for assembly or test of MOS circuits are covered with conductive sheets. *WARNING:* Never expose an operator directly to a hard electrical ground. For safety reasons, the operator must have a resistance of at least 100K Ohms between himself and hard electrical ground.

2. All entrances to work areas have grounding plates on door and/or floor, which must be contacted by people entering the area.

3. Conductive straps are worn inside and outside of employees' shoes so that body charges are grounded when entering work area.

4. Anti-static neutralized smocks are worn to eliminate the possibility of static charges being generated by friction of normal wear. Two types are available; Dupont anti-static nylon and Dupont neutralized 65% polyester/35% cotton.

5. Cotton gloves are worn while handling parts. Nylon gloves and rubber finger cots are not allowed.

6. Humidity is controlled at a minimum of 35% to help reduce generation of static voltages.

7. All parts are transported in conductive trays. Use of plastic containers is forbidden. Axial leaded parts are stored in conductive foam, such as Velofoam#7611.

8. All equipment used in the assembly area must be thoroughly grounded. Attention should be given to equipment that may be inductively coupled and generate stray voltages. Soldering irons must have grounded tips. Grounding must also be provided for solder posts, reflow soldering equipment, etc.

9. During assembly of I.C.'s to printed circuit boards, it is advisable to place a grounding clip across the fingers of the board to ground all leads and lines on the board.

10. Use of carpets should be discouraged in work areas, but in other areas may be treated with anit-static solution to reduce static generation.

11. MOS parts should be handled on conductive surfaces and the handler must touch the conductive surface *before* touching the parts.

12. In addition, no power should be applied to the socket or board while the MOS device is being inserted. This permits any static charge accumulated on the MOS device to be safely removed before power is applied.

13. MOS devices should not be handled by their leads unless absolutely necessary. If possible, MOS devices should be handled by their packages as opposed to their leads.

14. In general, materials prone to static charge accumulation should not come in contact with MOS devices.

These precautions should be observed even when an MOS device is suspected of being defective. The true cause of failure cannot be accurately determined if the device is damaged due to static charge build-up.

It should be remembered that even the most elaborate physical prevention techniques will not eliminate device failure if personnel are not fully trained in the proper handling of MOS.

This is a most important point and should not be overlooked.

More information can be obtained by contacting the Product Assurance Department.

American Microsystems, Inc.
3800 Homestead Road
Santa Clara, California 95051
Telephone (408) 246-0330
TWX 910-338-0024 or 910-338-0018

PROCESS DESCRIPTIONS

Each of the major MOS processes is described on the following pages. First, the established production proven processes are described, followed by those advanced processes, which are starting to go into volume production now. In each case, the basic processes is described first, followed by an explanation of its advantages, applications, etc.

P-CHANNEL METAL GATE PROCESS

Of all the basic MOS processes, P-Channel Metal Gate is the oldest and the most completely developed. It has served as the foundation for the MOS/LSI industry and still finds use today in some devices. Several versions of this process have evolved since its earliest days. A thin slice (8 to 10 mils) of lightly doped N-type silicon wafer serves as the substrate or body of the MOS transistor. Two closely spaced, heavily doped P-type regions, the source and drain, are formed within the substrate by selective diffusion of an impurity that provides holes as majority electrical carriers. A thin deposited layer of aluminum metal, the gate, covers the area between the source and drain regions, but is electrically insulated from the substrate by a thin layer (1000-15000Å) of silicon dioxide. The P-Channel transistor is turned on by a negative gate voltage and conducts current between

Figure B.1. Summary of MOS Process Characteristics

P-CHANNEL METAL GATE
VARIATIONS:
1. High Threshold (HiV$_T$)
2. Low Threshold (LoV$_T$)

MATERIALS: N-SILICON SUBSTRATE — [111] FOR HIGH V$_T$, [100] FOR LOW V$_T$.
ALUMINUM GATE, SOURCE, AND DRAIN CONTACTS.
PERFORMANCE: POOR SPEED—POWER PRODUCT: V$_T$/V$_{TF}$ TRADEOFF.
COMPLEXITY: TYPICALLY 15 OR LESS PROCESS STEPS.

ION IMPLANTED P-CHANNEL METAL GATE
VARIATIONS:
1. With enhancement and depletion mode devices on same chip

MATERIALS: SAME AS ABOVE, ALWAYS [111] SILICON.
PERFORMANCE: LOWER V$_T$ BY ALTERING Q$_B$ TERM; HIGH V$_{TF}$ OF [111] SILICON; ENHANCEMENT AND DEPLETION MODE TRANSISTORS POSSIBLE
COMPLEXITY: OVER 15, LESS THAN 20 PROCESS STEPS.

P-CHANNEL
MATERIALS: [111] SUBSTRATE, DOPED POLYCRYSTALLINE SILICON GATE
PERFORMANCE: LOWER V$_T$ THROUGH ϕ_{MS} TERM, BUT HIGH V$_{TF}$ OF [111] SILICON
COMPLEXITY: 15-20 PROCESS STEPS, BUT OVER 25 WITH COMBINED ENHANCEMENT AND DEPLETION MODE DEVICES

SILICON GATE
(Usually with Ion Implantation)
VARIATIONS:
1. With buried interconnect layer
2. With enhancement and depletion mode devices on same chip
3. Selective Fox (Field Oxidation)
4. Four V$_T$ Process

N-CHANNEL
MATERIALS: [100] P-SILICON SUBSTRATE, DOPING POLYSILICON GATE, ION IMPLANTED FIELD
PERFORMANCE: FAST CIRCUITS, THROUGH HIGH MOBILITY (μ) OF ELECTRONS
COMPLEXITY: SAME AS P—CHANNEL SIGATE FOR OLDER PROCESSES. 20-25 PROCESS STEPS FOR NEWER PROCESSES.

CMOS
VARIATIONS:
1. Planar, N+/P+ Poly
2. Selective Fox, N+Poly
3. Selective Fox, N+ Poly, isolated P-Well

PERFORMANCE: LOW POWER, HIGH SPEED
MATERIALS: [100] N-SILICON SUBSTRATE, ION IMPLANTED P-WELL
COMPLEXITY: OVER 25 PROCESS STEPS
SPECIAL PROCESS: LINEAR CAPACITORS FOR SWITCHED CAPCITOR LINEAR INTEGRATED CIRCUITS

the source and the drain by means of holes as the majority carriers.

The basic P-Channel metal gate process can be subdivided into two general categories: *High-threshold and low-threshold.* Various manufacturers use different techniques (particularly so with the low threshold process) to achieve similar results, but the difference between them always rests in the threshold voltage V_T required to turn a transistor on. The high threshold V_T is typically -3 to -5 volts and the low threshold V_T is typically -1.5 to -2.5 volts.

The original technique used to achieve the difference in threshold voltages was by the use of substrates with different crystalline structures. The high V_T process used [111] silicon whereas, the low V_T process used [100] silicon. The difference in the silicon structure causes the surface charge between the substrate and the silicon dioxide to change in such a manner that it lowers the threshold voltages.

One of the main advantages of lowering V_T is the ability to interface the device with TTL circuitry. However, the use of [100] silicon carries with it a distinct disadvantage also. Just as the surface layer of the [100] silicon can be inverted by a lower V_T, so it also can be inverted at other random locations—through the thick oxide layers—by large voltages that may appear in the metal interconnections between circuit components. This is undesirable because it creates parasitic transistors, which interfere with circuit operation. The maximum voltage that can be carried in the interconnections is called the parasitic field oxide threshold voltage V_{TF}, and generally limits the overall voltage at which a circuit can operate. This, then, is the main factor that limits the use of the [100] low V_T process. A drop in V_{TF} between a high V_T and low V_T process may, for example, be from $-28V$ to $-17V$.

The low V_T process, because of its lower operating voltages, usually produces circuits with a lower operating speed than the high V_T process, but is easier to interface with other circuits, consumes less power, and therefore is more suitable for clocked circuits. Both P-Channel metal gate processes yield devices slower in speed than those made by other MOS processes, and have a relatively poor speed/power product. Both processes require two power supplies in most circuit designs, but the high V_T process, because it operates at a high threshold voltage, has excellent noise immunity.

Ion Implanted P-Channel Metal Gate Process

The P-Channel Ion Implanted process uses essentially the same geometrical structure and the same materials as the high V_T P-Channel process, but includes the ion implantation step. The purpose of ion implantation is to introduce P-type impurity ions into the substrate in the limited area under the gate electrode. By changing the characteristics of the substrate in the gate area, it is possible to lower the threshold voltage V_T of the transistor, without influencing any other of its properties.

Figure B.2. shows the ion implantation step in a diagrammatic manner. It is performed after the gate oxide is grown, but before the source, gate, and drain metallization deposition. The wafer is exposed to an ion beam which penetrates through the thin gate oxide layer and implants ions into the silicon substrate. Other areas of the substrate are protected both by the thicker oxide layer and sometimes also by other masking means. Ion implantation can be used with any process and, therefore could, except for the custom of the industry, be considered a special technique, rather than a process in itself.

Figure B.2. Diagram of Ion Implantation Step
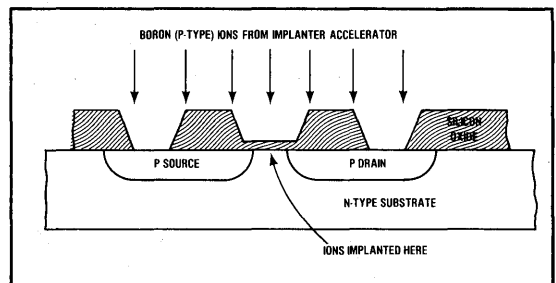
The implantation of P-type ions into the substrate, in effect, reduces the effective concentration of N-type ions in the channel area and thus lowers the V_T required to turn the transistor on. At the same time, it does not alter the N-type ion concentration elsewhere in the substrate and therefore, does not reduce the parasitic field oxide threshold voltage V_{TF} (a problem with the low V_T P-Channel Metal Gate process, described above). The [111] silicon usually is used in ion-implanted transistors.

In fact, if the channel area is exposed to the ion beam long enough, the substrate in the area can be turned into P-type silicon (while the body of the substrate still re-

mains N-type) and the transistor becomes a depletion mode device. In any circuit some transistors can be made enhancement type, while others are depletion type, and the combination is a very useful circuit design tool.

The Ion-implanted P-Channel Metal Gate process is very much in use toady. Among all the processes, it represents a good optimization between cost and performance and thus is the logical choice for many common circuits, such as memory devices, data handling (communication) circuits, and others.

Because of its low V_T, it offers the designer a choice of using low power supply voltages to conserve power or increase supply voltages to get more driving power and thus increase speed. At low power levels it is more feasible to implement clock generating and gating circuits on the chip. In most circuit designs only a single power supply voltage is required.

N-CHANNEL PROCESS

Historically, N-Channel process and its advantages were known well at the time when the first P-Channel devices were successfully manufactured; however, it was much more difficult to produce N-Channel. One of the main reasons was that the polarity of intrinsic charges in the materials combined in such a way that a transistor was on at 0V and had a V_T of only a few tenths of a volt (*positive*). Thus, the transistor operated as a marginal depletion mode device without a well-defined *on/off* biasing range. Attempts to raise V_T by varying gate oxide thickness, increasing the substrate doping, and back biasing the substrate, created other objectionable results and it was not until research into materials, along with ion implantation, silicon gates, and other improvements came about that N-Channel became practical for high density circuits.

The N-Channel process gained its strength only after the P-Channel process, ion implantation, and silicon gate all were already well developed. N-Channel went into volume productions with advent of the 4K dynamic RAM and the microprocessor, both of which required speed and high density. Because P-Channel processes were nearing their limits in both of these respects, N-Channel became the logical answer.

The N-Channel process is structurally different from any

of the processes described so far, in that the source, drain, and channel all are N-type silicon, whereas the body of the substrate is P-type. Conduction in the N-Channel is by means of electrons, rather than holes.

The main advantage of the N-Channel process is that the mobility of electrons is about three times greater than that of holes and, therefore, N-Channel transistors are faster than P-Channel . In addition, the increased mobility allows more current flow in a channel of any given size, and therefore N-Channel transistors can be made smaller. The positive gate voltage allows an N-Channel transistor to be completely compatible with TTL.

Although metal gate N-Channel processes have been used, the predominant N-Channel process is a silicon gate process. Among the advantages of silicon gate is the possibility of a buried layer of interconnect lines, in addition to the normal aluminum interconnections deposited on the surface of the chip. This gives the circuit designer more latitude in layout and often allows the reduction of the total chip size. Because the polysilicon gate electrode is deposited in a separate step, after the thick oxide layer is in place, the simultaneous deposition of additional polysilicon interconnect lines is only a matter of masking. These interconnect lines are buried by later steps, as shown in Figure B.3.

Figure B.3. Crossection of an N-Channel Silicon Gate MOS Transistor
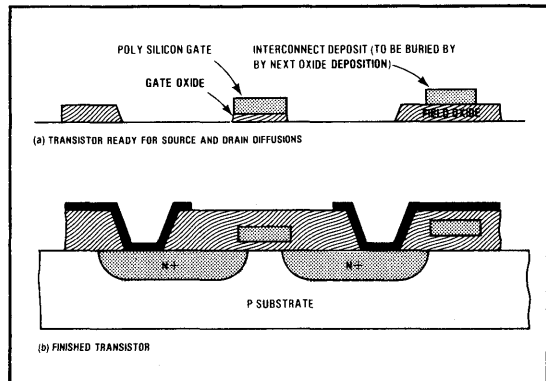
One minor limitation associated with the buried interconnect lines is their location. Because the source and drain diffusions are done after the polysilicon is deposited [see (a) of Figure B.3] the interconnect lines cannot be located over these diffusion regions.

A second advantage of a silicon gate is associated with the reduction of overlap between the gate and both the source and drain. This reduces the parasitic capacitance at each location and improves speed, as well as power consumption characteristics. Whereas in the metal gate process, the P region source and drain diffusion must be done prior to deposition of the gate electrode, in silicon gate process, the electrode is in place during diffusion, see (a) of Figure B.3. Therefore, no planned overlap for manufacturing tolerance purposes need exist and the gate is said to be *self-aligned*. The only overlap that occurs is due to the normal lateral extension of the source and drain regions during the diffusion process.

The silicon-gate process produces devices that are more compact than metal gate, and are slightly faster because of the reduced gate overlap capacitance. Because the basic silicon gate process is relatively simple, it is also economical. It is a versatile process that is used in memory devices and most any other circuit.

N-Channel development continues at a vigorous pace, resulting in all kinds of process variations, production techniques and applications. The combination of high speed, TTL compatibility, low power requirements, and compactness have already made N-Channel the most widely used process. The cost of N-Channel has been coming down also.

In addition to its use in large memory chips and microprocessors, N-Channel has become a good general purpose process for circuits in which compactness and high speed are important.

CMOS

The basic CMOS circuit is an inverter, which consists of two adjacent transistors—one an N-Channel, the other a P-Channel, as shown in Figure B.4. The two are fabricated on the same substrate, which can be either N or P type.

The CMOS inverter in Figure B.4 is fabricated on an N-type silicon substrate in which a P "tub" is diffused to form the body for the N-Channel transistor. All other steps, including the use of silicon gates and ion implantation, are much the same as for other processes.

The main advantage of CMOS is extremely low power consumption. When the common input to both gate electrodes is at a logic 1 (a positive voltage) the N-Channel transistor is biased on, the P-Channel is off, and the output is near ground potential. Conversely, when the input is at a logic 0 level, its negative voltage biases only the P-Channel transistor on and the output is near the drain voltage $+V_{DD}$. In either case, only one of the two transistors is on at a time and thus, there is virtually no current flow and no power consumption. Only during the transition from one logic level to the other are both transistors on and current flow increases momentarily.

Silicon Gate CMOS is also fast, approaching speeds of bipolar TTL circuits. On the other hand, the use of two transistors in every gate makes CMOS slightly more complex and costly, and requires more chip size. For these reasons, the original popularity of CMOS was in SSI logic elements and MSI circuits—logic gates, inverters, small shift registers, counters, etc. These CMOS devices consititute a logic family in the same way as TTL, ECL, and other bipolar circuits do; and in the areas of very low power consumption, high noise immunity, and simplicity of operation, are still widely accepted by discrete logic circuit designers.

Low power CMOS circuits made the watch circuit possible and also have been used in space exploration, battery operated consumer products, and automotive control devices. As experience was gained with CMOS, tighter design rules and reduced device sizes have been implemented and now LSI circuits, such as 1K RAM memories and microprocessors, are being manufactured in volume.

CMOS circuits can be operated on a single power supply voltage, which can be varied from $+2.5$ to about $+15$ volts, with a higher voltage giving more speed and higher noise immunity.

The first implementation of an inverting gate is a process that uses both $n+$ and $p+$ polysilicon. The basic structure is a first-generation approach to which a selective field-oxidation process has been added. (At American Microsystems, Inc., the selective field-oxidation process is used only to shrink existing designs down to 5-micrometer rules; it is not applied to new designs.)

Figure B.5 shows the plan and section views of the three-device gate portion. Because the P-Well in the top view spans both N-Channel devices, it is referred to as ubiquitous, and the process is called Ubiquitous P-Well.

In this planar process, $p+$ guard rings are used to reduce surface leakage. Polysilicon cannot cross the rings, however, so that bridges must be built. Note the use of

p+ polysilicon in the P-Channel areas. The plan view shows the construction of the bridges linking p+ to metal to n+. (Were the process to be used for a low-voltage, first-generation application like a watch circuit, the guard rings would not be necessary and polysilicon could directly connect N-Channel and P-Channel devices; however, to ensure good ohmic contact from one type of polysilicon to another, polysilicon-diode contacts must be capped with metal.)

This process provides a buried contact (n+ polysilicon to n+ diffusion) that can yield a circuit-density advantage. However, neither of the other two second-generation approaches provides buried contacts. Therefore, if a layout in this process is to be compatible with the others, the buried contact must be eliminated. Though there will be a penalty in real estate, the gain for custom applications is a great increase in the number of available CMOS vendors.

The n+-Only Polysilicon Aproach

Both of the second-generation CMOS processes that follow are variants of the n+-only, selective-field-oxide approach. One closely resembles the p+ n+ Ubiquitous-P-Well process, since it, too, has a Ubiquitous P-Well that is implanted before the field oxidation and thus runs under the field oxide. The other, called isolated P-Well, has separate wells for each N-Channel device that are implanted after field oxidation.

Figure B.6 shows the section and plan views of the n+-only Ubiquitous-P-Well approach used to build the gate of Figure B.4. This is the $5\mu m$ process recommended by AMI and others for new, high-performance CMOS designs. The layout is simpler than with the n+/p+ polysilicon Ubiquitous-Well approach (there are no buried contacts and no polysilicon-diode contacts), and it occupies less area for the same line widths. Also, since the process permits implanting in the field region, no guard rings are required. Polysilicon can thus cross directly from P- to N-Channel device areas without the need for bridges or polysilicon-dioxide contacts.

Figure B.4. Crossection and Schematic Diagram of a CMOS Inverter
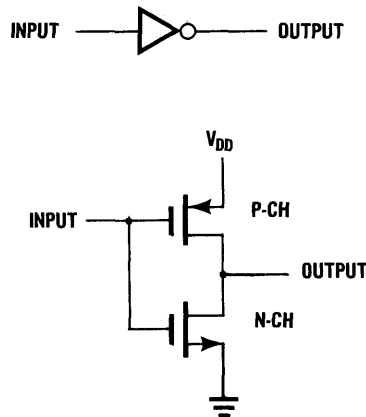
Figure B.5. n+/p+ Polysilicon Approach

P-CHANNEL   N-CHANNEL

p+-POLYSILICON-TO-
p+ DIFFUSION BURIED
CONTACT

POLYSILICON
GATE

INTERMEDIATE OXIDE

FIELD OXIDE

P-WELL
GUARD
RING

n+-POLYSILICON-TO
n+ DIFFUSION BURIED
CONTACT

p+   p+   p+   n+   n+

METAL-TO-DIFFUSION
CONTACT

n−   p−

n−

GUARD-RING
JUMPER

p+ POLYSILICON

BURIED
CONTACT

METAL

n+ POLYSILICON

n+ DIFFUSION

METAL

n+
POLY

TO V_DD

p+ DIFFUSION

P-WELL EDGE

p+ GUARD RING
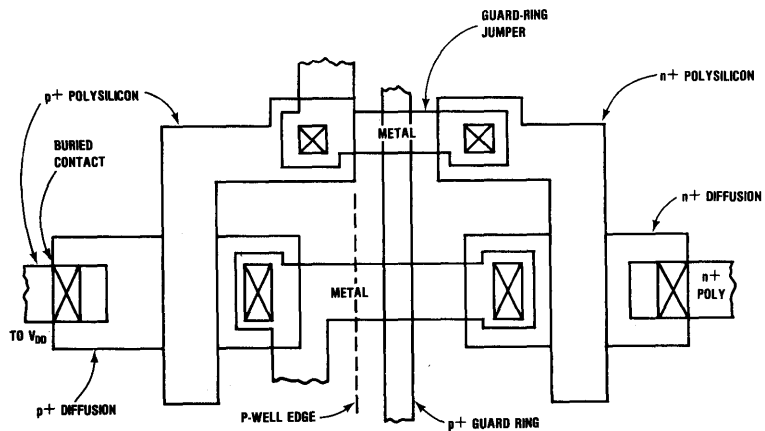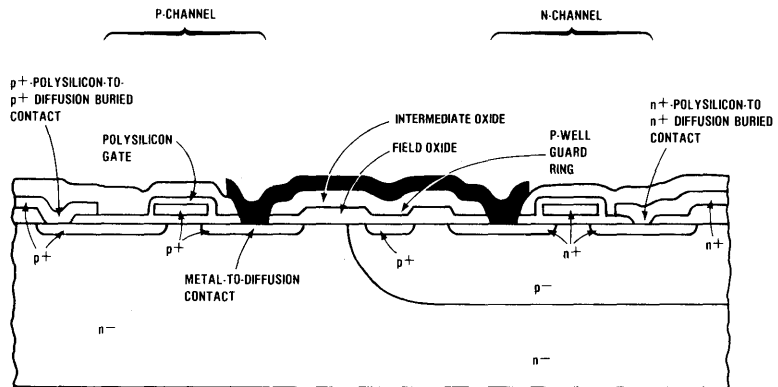
THE FIRST HIGH-PERFORMANCE COMPLEMENTARY-MOS PLANAR
PROCESS. ITS DRAWBACKS: TWO TYPES OF POLYSILICON ARE
USED, AND THE UNAVAILABILITY OF FIELD IMPLANT DOPING TIES
FIELD THRESHOLD TO DEVICE THRESHOLDS.

Figure B.6. n+-Only Polysilicon Approach

P-CHANNEL · N-CHANNEL

IMPLANTED FIELD · FIELD OXIDE · ALUMINUM

n+ · p+ · p+ · n+ · n+ · n+

p−

n−

n+ POLYSILICON · METAL · n+ POLYSILICON

METAL

METAL

p+ DIFFUSION · P-WELL EDGE · n+ DIFFUSION
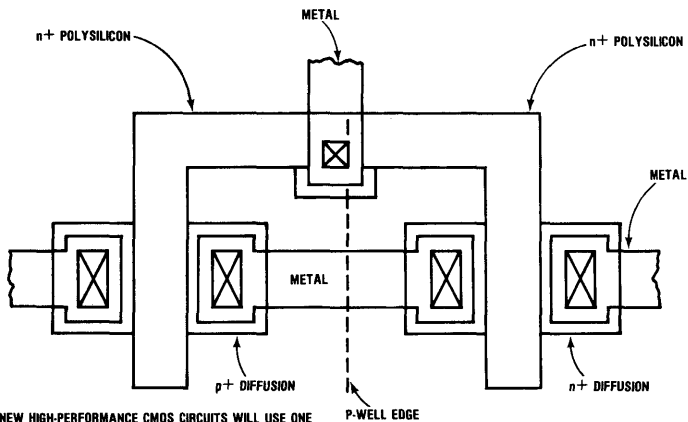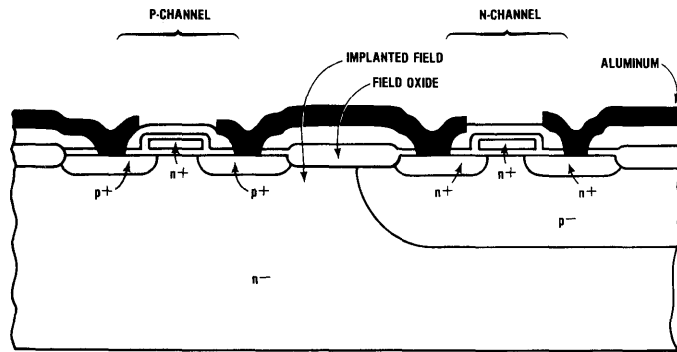
ALL NEW HIGH-PERFORMANCE CMOS CIRCUITS WILL USE ONE
TYPE OF POLYSILICON. THIS VERSION HAS A UBIQUITOUS
P-WELL: THAT IS, SERIES N-CHANNEL DEVICES SIT IN A COMMON
P-WELL, WHICH, IMPLANTED BEFORE FIELD OXIDATION, RUNS
UNDER THE FIELD OXIDE. THIS IS AMI'S PREFERRED CMOS PRO-
CESS FORMAT FOR ALL NEW DESIGNS.

Figure B.7. Isolated Wells.
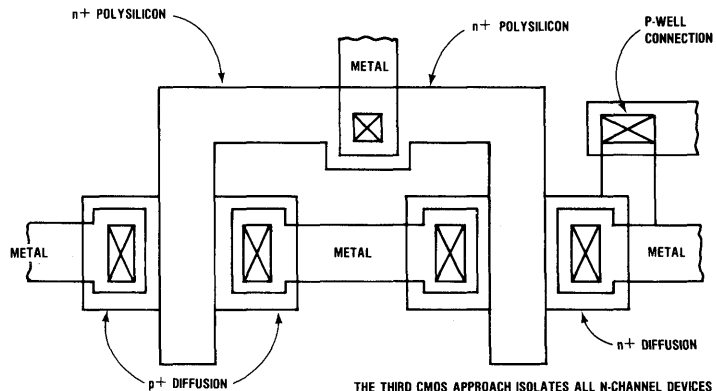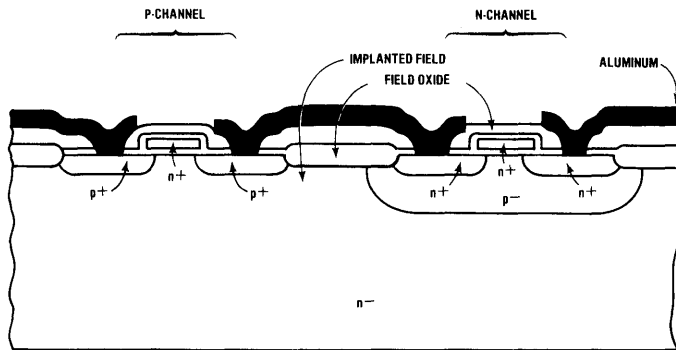
THE THIRD CMOS APPROACH ISOLATES ALL N-CHANNEL DEVICES
IN SEPARATE P-WELLS. SINCE THE ISOLATED WELLS MUST BE
DOPED MUCH MORE HEAVILY THAN THOSE OF THE UBIQUITOUS-
WELL APPROACH, n+-TO P-WELL CAPACITANCE IS GREATER
AND SWITCHING SPEEDS LOWER. THIS IS AN n+-ONLY
POLYSILICON PROCESS.

A variant of the all n+ (See Figure B.7) polysilicon process just discussed uses basically the selective field-oxide approach except that the P-Wells are not continuous under the field-oxide areas; they are instead bounded by field-oxide edges. Since the P-Wells are naturally isolated from one another, the process is called n+ poly-isolated P-Well. The isolated wells must all be connected to ground; if they are left floating, circuit malfunctions are bound to occur. The grounding is done either with p+ diffusions or with top-side metalization that covers a p+-to-P-Well contact diffusion.

In the Isolated-Well process, the P-Wells must be doped much more heavily than in the Ubiquitos-Well process. One result is a higher junction capacitance between the n+ areas and the wells that both slows switching speeds and raises the power dissipation of a device. Even though the speed loss could be compensated for by slightly shorter channel lengths, the operating power still remains high.

Although currently available from AMI and other manufacturers, the Isolated-Well process is in fact not recommended for new designs by AMI. Its layout takes up more area than does one using the Ubiquitous-Well approach, even though its P-Well to p+-area spacing is slightly less.

Table 1. Layout Compatibility Concerns for CMOS Processes

LAYOUT FEATURE	n+/p+ POLY-SILICON UBIQUITOUS P-WELL	n+-ONLY POLYSILICON UBIQUITOUS P-WELL	n+-ONLY POLY SILICON ISOLATED P-WELL
BURIED CONTACT	X	NO	NO
POLYSILICON DIODE CONTACT	YES	X	X
P-WELL ISOLATION WITH DIFFUSION MASK	NO	NO	YES
TIGHT P-WELL-TO-p+ SPACING	NO	NO	YES
LAYOUT CARE REQUIRED FOR P-WELL ELECTRICAL CONTACTS	NO	NO	YES

X = DOES NOT MATTER

Figure B.8. Comparative Data on Major MOS Processes

RELATIVE SPEED POWER PRODUCT (NS-MW)

RELATIVE POWER (AT FIXED SPEED)

RELATIVE PROPAGATION DELAY

MASKS REQUIRED

RELATIVE COST PER LOGIC FUNCTION
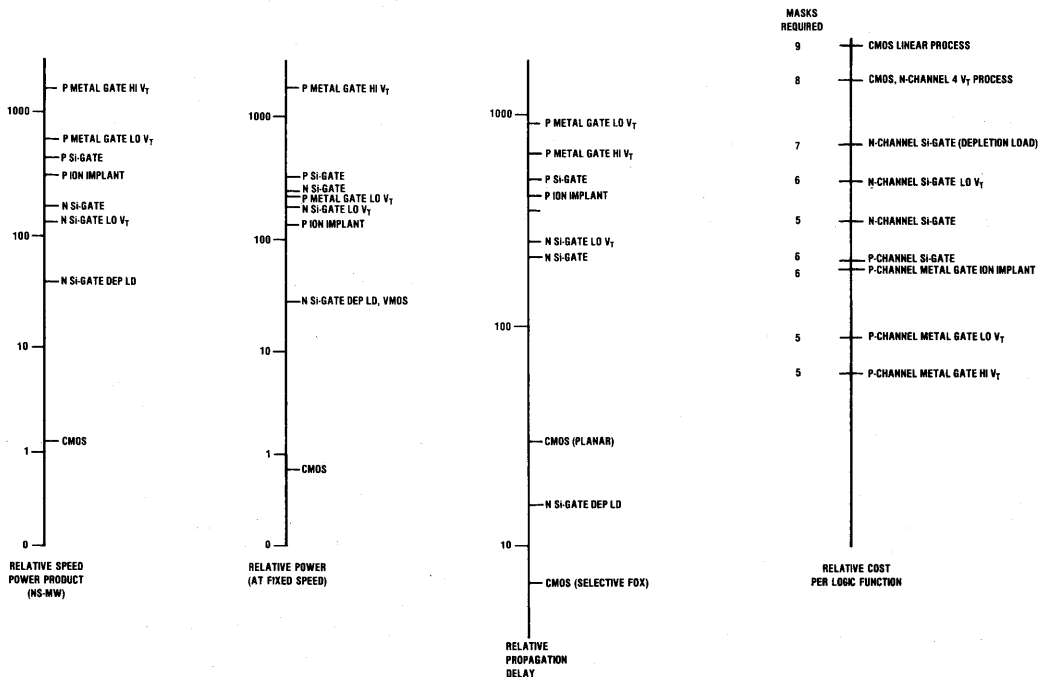
INTRODUCTION

Quality is one of the most used, least understood, and variously defined assets of the semiconductor industry. At AMI we have always known just how important effective quality assurance, quality control, and reliability monitoring are in the ability to deliver a repeatably reliable product. Particularly, through the manufacture of custom MOS/LSI, experience has proved that one of the most important tasks of quality assurance is the effective control and monitoring of manufacturing processes. Such control and monitoring has a twofold purpose: to assure a consistently good product, and to assure that the product can be manufactured at a later date with the same degree of reliability.

To effectively achieve these objectives, AMI has developed a Product Assurance Program consisting of three major functions:

☐ Quality Control
☐ Quality Assurance
☐ Reliability

Each function has a different area of concern, but all share the responsibility for a reliable product.

The AMI Product Assurance Program

The program is based on MIL-STD-883, MIL-M-38510, and MIL-Q-9858A methods. Under this program, AMI manufactures highest quality MOS devices for all segments of the commercial and industrial market and, under special adaptations of the basic program, also manufactures high reliability devices to full military specifications for specific customers.

The three aspects of the AMI Product Assurance Program—Quality Control, Quality Assurance, and Reliability— have been developed as a result of many years of experience in MOS device design and manufacture.

Quality Control establishes that every method meets or fails to meet, processing or production standards—*QC checks methods.*

Quality Assurance establishes that every method meets, or fails to meet, product parameters—*QA checks results.*

Reliability establishes that QA and QC are effective—*Reliability checks device performance.*

One indication that the AMI Product Assurance Program has been effective is that NASA has endorsed AMI products for flight quality hardware since 1967. The Lunar Landers and Mars Landers all have incorporated

AMI circuits, and AMI circuits have also been utilized in the Viking and Vinson programs, as well as many other military airborne and reconnaissance hardware programs.

QUALITY CONTROL

The Quality Control function in AMI's Product Assurance Program involves constant monitoring of all aspects of materials and production, starting with the raw materials purchased, through all processing steps, to device shipment. There are three major areas of Quality Control:

☐ Incoming Materials Control
☐ Microlithography Control
☐ Process/Assembly Control

Incoming Materials Control

All purchased materials, including raw silicon, are checked carefully to various test and sampling plans. The purpose of incoming materials inspection is to ensure that all items required for the production of AMI MOS circuits meet such standards as are required for the production of high quality, high reliability devices.

Incoming inspection is performed to specifications agreed to by suppliers of all materials. The Quality Control group continuously analyzes supplier performance, performs comparative analysis of different suppliers, and qualifies the suppliers.

Tests are performed on all direct material, including packages, wire, lids, eutectics, and lead frames. These tests are performed using a basic sampling plan in accordance with MIL-S-19500, generally to a Lot Tolerance Percent Defective (LTPD) level of 10%. The AQL must be below 1% overall.

Two incoming material inspection sequences illustrate the thoroughness of AMI Quality Control:

☐ Purchased packages are first inspected visually. Then, dimensional inspections are performed, followed by a full functional inspection, which subjects the packages to an entire production run simulation. Finally, a full electrical evaluation is made, including checks of the insulation, resistance, and lead-to-lead isolation. A package lot which passes these tests to an acceptable LTPD level is accepted.

☐ Raw silicon must also pass visual and dimensional checks. In addition, a preferential etch quality inspection is performed. For this inspection, the underlayers

of bulk silicon are examined for potential anomalies such as dislocation, slippage or etch pits. Resistivity of the silicon is also tested.

Microlithography Control

Microlithography involves the processes which result in finished working plates, used for the fabrication of wafers. These processes are pattern or artwork generation, photo-reduction, and the actual printing of the working plates.

Pattern generation now is the most common practice at AMI. The circuit layout is digitized and stored on a tape, which then is read into an automated pattern generator which prints a highly accurate 10x reticle directly.

In cases where the more traditional method of artwork generation is used whether Rubylith, Gerber Plots, AMI generated or customer generated—the artwork is throughly inspected. It is checked for level-to-level registration and dimensional tolerances. Also, a close visual inspection of the workmanship is made. AMI artwork is usually produced at 200x magnification and must conform to stringent design rules, which have been developed over a period of years as part of the process control requirements.

Acceptable artwork is photographically reduced to a 20x magnification, and then further to a 10x magnification. The resulting 10x reticles are then used for producing 1x masters. The masters undergo severe registration comparisons to a registration master and all dimensions are checked to insure that reductions have been precise. During this step, image and geometry are scrutinized for missing or faded portions and other possible photographic omissions.

For a typical N-Channel silicon gate device, master sets are checked at all six geometry levels in various combinations against each other and against a proven master set. Allowable deviations within the die are limited to 0.5 micron, deviations within a plate are limited to 1 micron, and all plate deviations are considered cumulatively.

Upon successful completion of a device master set, it is released to manufacturing where the 1x plates are printed. A sample inspection is performed by manufacturing on each 30-plate lot and the entire lot is returned to Quality Control for final acceptance. Quality Control performs audits on each manufacturing inspector daily, by sample inspection techniques.

The plates can be rejected first by manufacturing, when the 30-plate lots are inspected, or by Quality Control when the lots are submitted for final acceptance. If either group rejects the plates, they are rescreened and then undergo the same inspection sequence. In the rescreening process, the plates undergo registration checks; visual checks for pin holes, protrusions, and faded or missing images, as well as all critical dimension checks.

Process Control

Once device production has started in manufacturing, AMI Quality Control becomes involved in one of the most important aspects of the Product Assurance Program—the analysis and monitoring of virtually all production processes, equipment, and devices.

Process controls are performed in the fabrication area, by the Quality Control Fabrication Group, to assure adherence to specifications. This involves checks on operators, equipment and environment. Operators are tested for familiarity with equipment and adherence to procedure. Equipment is closely checked both through calibration and maintenance audits. Environmental control involves close monitoring of temperature, relative humidity, water resistivity and bacteria content, as well as particle content in ambient air. All parameters are accurately controlled to minimize the possiblity of contamination or adverse effects due to temperature or humidity excesses.

Experience has proven that such close control of the operators, equipment, and environment is highly effective towards improved quality and increased yields.

In addition to the specification adherence activities of the QC Fabrication Group, a QC Laboratory performs constant process monitoring of virtually every step of all processes. Specimens are taken from all production steps and critically evaluated. Sampling frequency varies, depending on the process, but generally, oxidation, diffusion, masking, and evaporization are the most closely monitored steps.

Results are supplied both to manufacturing and engineering. When evidence of a problem occurs, QC provides recommendations for corrections and follows up the corrective action taken.

Optical Inspections are performed at several steps; quality control limits are based on a 10% LTPD. The chart in Figure 1 shows process steps and process control points.

Figure 1. Flowchart of Product Assurance Program Implementation
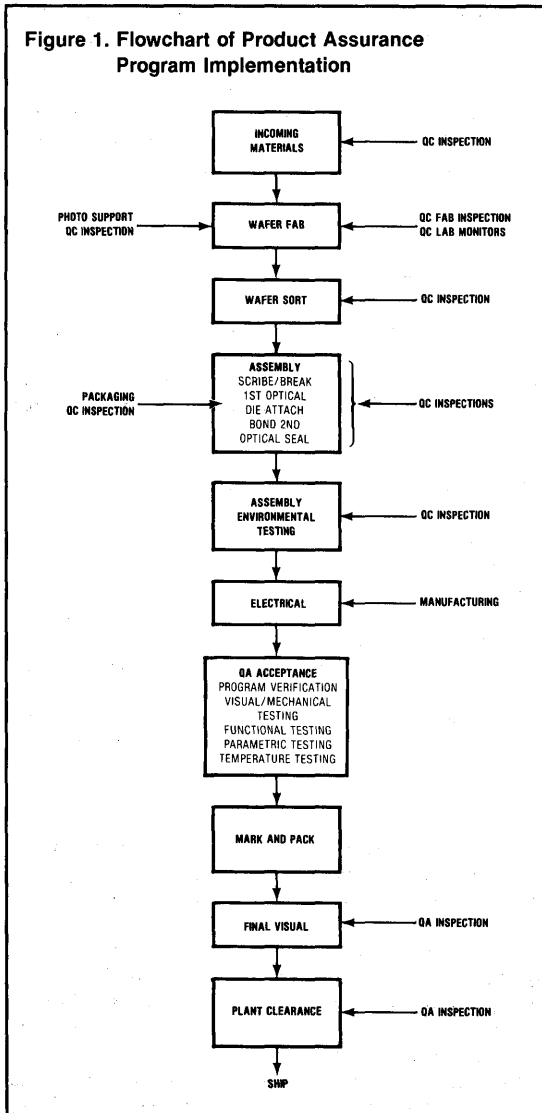
mance with customer specifications or other AMI specifications.

After devices undergo 100% testing in manufacturing, they are sent to Quality Assurance for acceptance. Lots are defined, and using the product specifications, sample sizes are determined, along with the types of tests to be performed and the test equipment to be used. Lots must pass QA testing either with an LTPD of 10%, or less, if the specification requires tighter limits. Lots with quantities greater than 2000 are checked to a 1% AQL.

Three types of tests are performed on the samples: visual/mechanical, parametric, and functional. All tests are performed both at room temperature and at elevated temperature. In addition, a number of other special temperature tests may be performed if required by the specification. Generally, high temperature tests are at 125°C.

To perform the tests, QA uses AMI *PAFT* test systems, ROM test systems, Macrodata testers, Fairchild *Sentry, Sentinel, XINCOM* systems, Teradyne test systems, and various bench test units. In special instances a part may also be tested in a real life environment in the equipment which is to finally utilize it.

If a lot is rejected during QA testing, it is returned to the production source for an electrical rescreening. It is then returned to QA for acceptance but is identified as a resubmitted lot. If it fails again, corrective action in engineering is initiated. As evidence of the problem is detected, the parts may also be traced all the way back to the wafer run to analyze the cause.

When a lot is acceptable, it is sent to packaging and then to finished goods. When parts leave finished goods, they are again checked by the QA group to a 10% LTPD with visual/mechanical tests. Also, all supporting documentation for the parts is verified, including QA acceptance, special customer specifications, certificates of compliance, etc. Only after this last check are devices considered ready for plant clearance.

If there are customer returns, they are first sample tested by QA to determine the cause of the return. (Many times an invalid customer test will incorrectly cause returns.) Selected return samples are sent to Reliability for failure analysis.

QUALITY ASSURANCE

The Quality Assurance function in the Product Assurance Program involves checking the ability of manufactured parts to meet specifications. In addition, the QA group also is responsible for calibration of all equipment, and for the maintenance of AMI internal product specifications, to assure that they are always in confor-

RELIABILITY

The Reliability function in the Product Assurance Program involves process qualification, device qualification,

package qualification, reliability program qualification and failure analysis. To perform these functions AMI Reliability group is organized into two major areas:

- ☐ Reliability Laboratory
- ☐ Failure Analysis

Reliability Laboratory

AMI Reliability Laboratory is responsible for the following functions.

- ☐ New Process Qualification
- ☐ Process Change Qualification
- ☐ Process Monitoring
- ☐ New Device Qualification
- ☐ Device Change Qualification
- ☐ New Package Qualification
- ☐ Device Monitoring
- ☐ Package Change Qualification
- ☐ Package Monitoring
- ☐ High Reliability Programs

There are various closely interrelated and interactive phases involved in the development of a new process, device, package or reliability program. A process change may affect device performance, a device change may affect process repeatability, and a package change may affect both device performance and process repeatability. To be effective. the Reliability Laboratory must monitor and analyze all aspects of new or changed processes, devices, and packages. It must be determined what the final effect is on product reliability, and then evaluate the merits of the innovation or change.

Process Qualification

For example, AMI Research and Development group recommends a new process or process alteration when it feels that the change can result in product improvement. The Reliability Laboratory then performs appropriate environmental and electrical evaluations of a new process. Typically, a special test vehicle, or "rel chip", generated by R&D during process development, is used to qualify the recommended new process or process change.

The rel chip is composed of circuit elements similar to those that may be required under worst-case circuit design conditions. The rel chip elements are standard for any given process, and thus allow precise comparisons between diffusion runs. The following is an example of what is included on a typical rel chip:

- ☐ A discrete inverter and an MOS capacitor
- ☐ A large P-N junction covered by an MOS capacitor.

- ☐ A large P-N junction area (identical to the junction area above, but without the MOS capacitor)
- ☐ A large area MOS capacitor over substrate
- ☐ Several long contact strings with different contact geometries
- ☐ Several long conductor geometries, which cross a series of eight deeply etched areas

Each circuit element of a rel chip allows a specific test to be performed. As an example, the discrete inverter and MOS load device accommodate power life tests. As a consequence, any type of parameter drift can be observed. The MOS capacitor, covering the large P-N junction, can serve to indicate the presence of contamination in the oxide, under the oxide, or in the bulk silicon. If unusual drift is evidenced, the location of contamination can be determined through analysis of the additional MOS capacitor and the large P-N junction area. The metal conductor interconnecting contacts is useful for life testing under relatively high current conditions. It facilitates the detection of metal separation when moisture or other contaminants are present.

The conductors crossing deeply etched areas allow the checking of process control. Rather than depending upon optical inspection of metal quality, burned out areas caused by high currents are readily identified and provide a quantitative measure of metal quality.

If the Reliability Laboratory determines that a recommended new process or process change is viable for manufacturing purposes, further analysis is necessary to determine that production devices can be manufactured in high volume, in a repeatable and reliable manner.

Process Monitoring

In addition to process qualification, the Reliability group also conducts ongoing process monitoring programs. Once every 90 days each major production process is evaluated using rel chips as test vehicles. The resulting test data is analyzed for parameter limits and process stability. In this manner AMI can help assure repeatability and high product quality.

Package Qualification

New packages are also qualified before they are adopted. To analyze packages, a qualification matrix is designed, according to which the new package and an established package (used for control) are tested concurrently. The test matrix consists of a full spectrum of electrical and environmental stress tests, in accordance with MIL-STD-883.

Failure Analysis

Another important function of the Reliability group is failure analysis. Scanning electron microscopes, high power optical microscopes, diagnostic probe stations, and other equipment is used in failure analysis of devices submitted from various sources. It is the function of the Reliability group to determine the cause of failure and recommend corrective action.

The Reliability group provides a failure analysis service for the previously mentioned in-house programs and for the evaluation of customer returns. All AMI customers are provided a failure analysis service for any part that fails within one year from date of purchase and the results of the analysis are returned in the form of a written report.

SUMMARY

The Product Assurance Program at AMI is oriented towards process control and monitoring, and the evaluation of devices. The Program consists of three major functions: Quality Control, Quality Assurance, and Reliability. Constant monitoring of all phases of production, with information feedback at all levels, allows fast and efficient detection of problems, evaluation and analysis, correction, and verification of the correction. The overall result is a line of products which are highly repeatable and reliabile, with a very low reject level.

Aerospace and defense equipments generally require LSI microcircuits capable of superior product reliability and performance. To meet these needs, AMI offers three standard screening options patterned after MIL-STD-883, Method 5004. Please note that two Class B flows are available:

☐ One per Method 5004.5, the current official revision. This Class B level requires temperature extreme electrical testing on both a 100% and on a Group A sampling basis.

☐ A more economical Class B flow patterned after a much earlier and officially obsolete revision . . . Method "5004.0". Temperature extreme electrical testing is performed only on a Group A sampling basis.

Operation/MIL-STD-883 Test Method	Class B Method 5004.5 MIL-STD-883	Class B Method 5004.0 MIL-STD-883	Class C Method 5004.5 MIL-STD-883
Internal Visual/2010	Cond. B	Cond. B	Cond. B
Final Seal	100%	100%	100%
Stabilization Bake/1008	Cond. C, 24 Hrs	Cond. C, 24 Hrs	Cond. C, 24 Hrs
Temperature Cycle/1010, 10 Cycles	Cond. C	Cond. C	Cond. C
Constant Acceleration/2001[1]	Y_1 Axis	Y_1 Axis	Y_1 Axis
Seal Test/1014 — Fine Leak — Gross Leak	Cond. A or B Cond. C	Cond. A or B Cond. C	Cond. A or B Cond. C
Pre-burn-in Electrical Test	@AMI Option[2]	@AMI Option[2]	—
Burn-in/1015[3]	125°C Min, 160 Hrs.	125°C Min, 160 Hrs.	—
Final Electrical Test/5004[4] — Static Tests, 25°C — Static Tests, Maximum Rated Operating Temperature — Static Tests, Minimum Rated Operating Temperature — Switching Tests, 25°C — Functional Tests, 25°C	100% 100% 100% 100% 100%	100% — — 100% 100%	100% — — — 100%
Group A Electricals/5005 — 55°C, 25°C, 125°C	Sample[5] Table I	Sample[5] Table I	Sample[5] Table I

Notes:

(1) Stress level (g) applied is dependent on package size/lead count.

(2) Per paragraph 3.5.1 of MIL-STD-883, Method 5004.

(3) Per MIL-STD-883, Method 1015 and Method 5004, paragraph 3.4.2, accelerated testing (Test Condition F of Method 1015) may be used at AMI's option.

(4) Final test electrical measurements per the applicable AMI data sheet.

(5) Group A is performed on each lot.

PLASTIC PACKAGE

The AMI plastic dual-in-line package is the equivalent of the widely accepted industry standard, refined by AMI for MOS/LSI applications. The package consists of a plastic body, transfer-molded directly onto the assembled lead frame and die. The lead frame is Kovar or Alloy 42, with external pins tin plated. Internally, there is a 50μin. gold spot on the die attach pad and on each bonding fingertip. Gold bonding wire is attached with the thermocompression gold ball bonding technique.

Materials of the lead frame, the package body, and the die attach are all closely matched in thermal expansion coefficients, to provide optimum response to various thermal conditions. During manufacture every step of the process is rigorously monitored to assure maximum quality of the AMI plastic package.

Available in: 8, 14, 16, 18, 22, 24, 28, 40 and 64 pin configurations.

GOLD BONDING WIRE
GOLD PLATING
BODY
LEAD FRAME
SEALANT
TIN PLATING
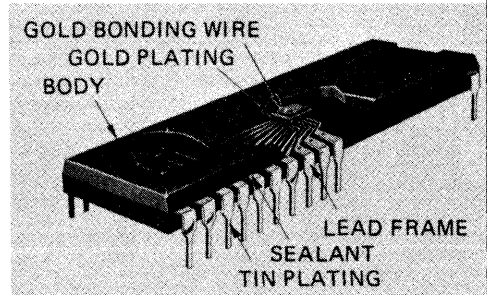
Cerdip PACKAGE

The Cerdip dual-in-line package has the same high performance characteristics as the standard three-layer ceramic package yet is a cost-effective alternative. It is a military approved type package with excellent reliability characteristics.

The package consists of an Alumina (Al_2O_3) base and the same material lid, hermetically fused onto the base with low temperature solder glass. Inert gasses are sealed inside the die cavity.

Available in 14,16,18,22,24,28 and 40 pin configurations.

96% ALUMINA BASE
ISLAND GROUND BOND TO CAVITY METALLIZATION
96% ALUMINA LID
CORNING 7583 SOLDER GLASS
ALUMINUM METALLIZATION ON BONDING FINGERS
ALUMINUM WIRE TO DIE
42 NICKEL-IRON ALLOY LEAD FRAME PLATED 200 MICROINCHES ELECTRONIC GRADE & TIN
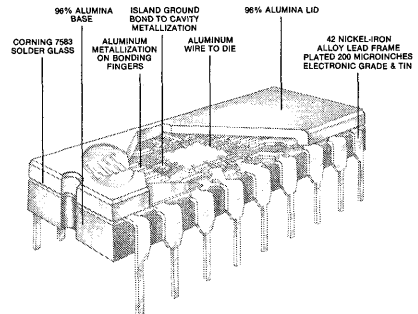
CERAMIC PACKAGE

Industry standard high performance, high reliability package, made of three layers of Al_2O_3 ceramic and nickel-plated refractory metal. Either a low temperature glass sealed ceramic lid or a gold tin *eutectic* sealer Kovar lid is used to form the hermetic cavity of this package. Package leads are available with gold over nickel or tin plating for socket insertion or soldering.
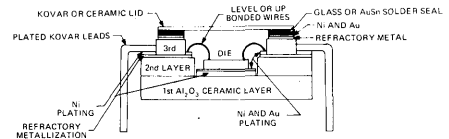
Available in 14,16,18,22,24,28,40 and 64 pin configurations.

8-Pin Plastic
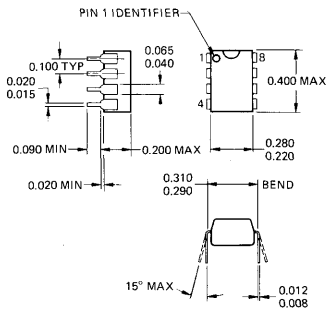
14-Pin Plastic
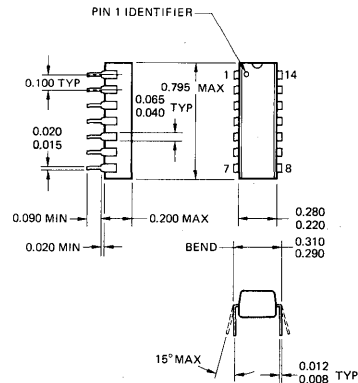
14-Pin Ceramic
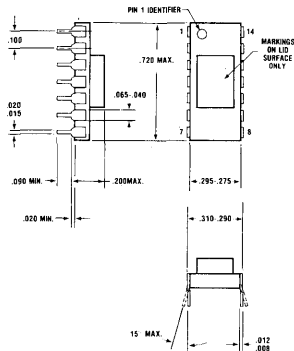
16-Pin Plastic
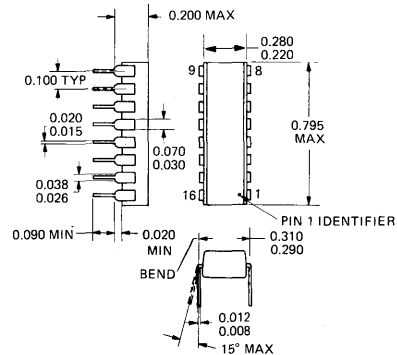
16-Pin Cerdip
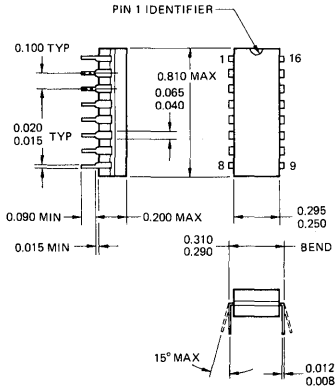
16-Pin Ceramic
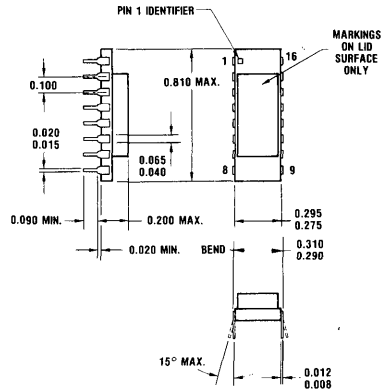
18-Pin Plastic
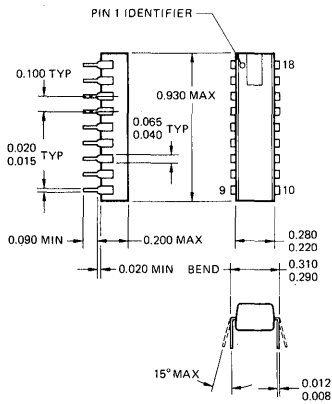
18-Pin Ceramic
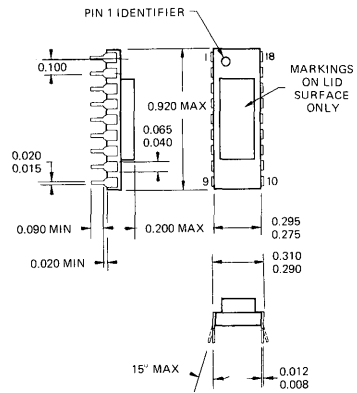
18-Pin Cerdip
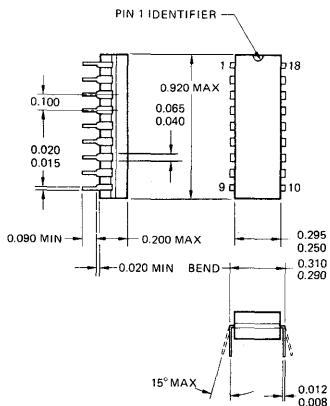
22-Pin Plastic

22-Pin Cerdip

PIN 1 IDENTIFIER

1   22
1.110 MAX
0.100
0.065
0.040
0.020
0.015
11   12
0.090 MIN   0.200 MAX   0.395 / 0.355
0.015 MIN   BEND   0.410 / 0.390
15° MAX   0.012 / 0.008

22-Pin Ceramic

PIN 1 IDENTIFIER

1   22
MARKINGS ON LID SURFACE ONLY
0.100   1.120 MAX
0.065
0.040
0.020
0.015
11   12
0.090 MIN   0.200 MAX   0.395 / 0.375
0.020 MIN   0.410 / 0.390
15° MAX   0.012 / 0.008

24-Pin Plastic

PIN 1 IDENTIFIER

1   24
1.270 MAX
0.100
0.065
0.040
0.020
0.016
12   13
0.090 MIN   0.200 MAX   0.580 / 0.515
0.020 MIN   BEND   0.610 / 0.590
15° MAX   0.012 / 0.008

24-Pin Cerdip

PIN 1 IDENTIFIER

1   24
1.310 MAX
0.100
0.065
0.040
0.020
0.015
12   13
0.090 MIN   0.200 MAX   0.590 / 0.480
0.015 MIN   BEND   0.610 / 0.590
15° MAX   0.012 / 0.008

24-Pin Ceramic

PIN 1 IDENTIFIER

1   24
MARKINGS ON LID SURFACE ONLY
0.100   1.310 MAX
0.065
0.040
0.020
0.015
12   13
0.090 MIN   0.200 MAX   0.595 / 0.575
0.020 MIN   0.610 / 0.590
15° MAX   0.012 / 0.008

28-Pin Plastic

PIN 1 IDENTIFIER

1   28
1.450 MAX
0.100
0.065
0.040
0.020
0.015
14   15
0.090 MIN   0.200 MAX   0.585 / 0.515
0.020 MIN   BEND   0.610 / 0.590
15° MAX   0.012 / 0.008

28-Pin Cerdip

PIN 1 IDENTIFIER

1   28
1.520
0.100
0.065
0.040
0.020
0.015
14   15
0.090 MIN
0.590
0.480
0.015 MIN   0.200 MAX
0.610
0.590   BEND
15° MAX
0.012
0.008

28-Pin Ceramic

PIN 1 IDENTIFIER

1   28
MARKINGS
ON LID
SURFACE
ONLY
1.450 MAX.
.100
.065
.040
.020
.015
14   15
.090 MIN.   .200 MAX.
.595
.575
.020 MIN.
.610
.590
15° MAX.
.012
.008

40-Pin Plastic

PIN 1 IDENTIFIER

1   40
2.060 MAX
0.100
0.065
0.040
0.020
0.015
20   21
0.090 MIN
0.580
0.515
0.020 MIN   0.200 MAX
0.610
0.590   BEND
15° MAX
0.012
0.008

40-Pin Ceramic

PIN 1 IDENTIFIER

1   40
MARKINGS
ON LID
SURFACE
ONLY
2.060 MAX
0.100
0.065
0.040
0.020
0.015
20   21
0.090 MIN   0.200 MAX
0.595
0.575
0.020 MIN
0.610
0.590
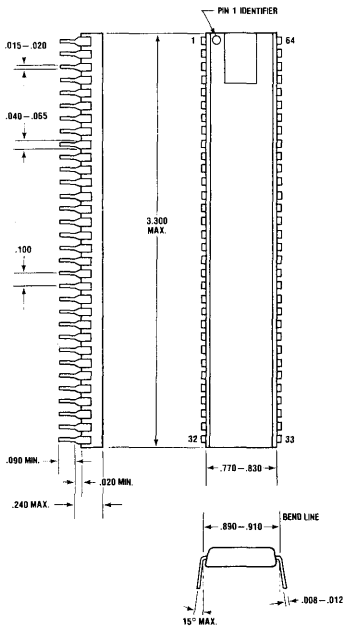15° MAX
0.012
0.008

40-Pin Cerdip

64-Pin Ceramic
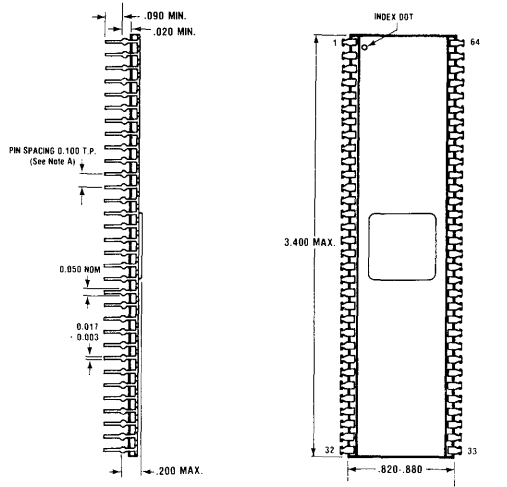
NOTE A. Each pin centerline is located within 0.010 of its true longitudinal position.
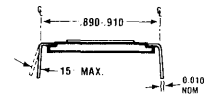
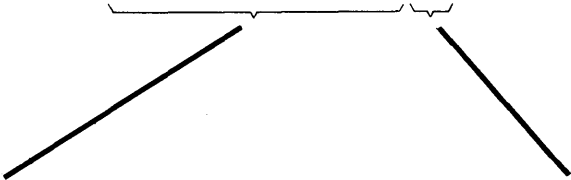## 64-Pin Plastic

Standard Products:

Any product in this MOS Products Catalog can be ordered using the simple system described below. With this system it is possible to completely specify any standard device in this catalog in a manner that is compatible with AMI's order processing methods. The example below shows how this ordering system works and will help you to order your parts in a manner that can be expedited rapidly and accurately.

All orders (except those in sample quantities) are normally shipped in plastic carriers or aluminum tube containers, which protect the devices from static electricity damage under all normal handling conditions. Either container is compatible with standard automatic IC handling equipment.

Any device described in this catalog is an AMI Standard Product. However, ROM devices that require mask preparation or programming to the requirements of a particular user, devices that must be tested to other than AMI Quality Assurance standard procedures, or other devices requiring special masks are sold on a negotiated price basis.

S2559	— P
S2559A	— P
S6800	— D
S68H00	— D
S5101-8	— C
S10110	— C

Device Number — prefix S, followed by four (or five*) numeric digits that define the basic device type. Versions to the basic device are indicated by an additional alpha or numeric digit as shown in the above examples.

*Organ Circuits

Package Type — a single letter designation which identifies the basic package type. The letters are coded as follows:

P — Plastic package

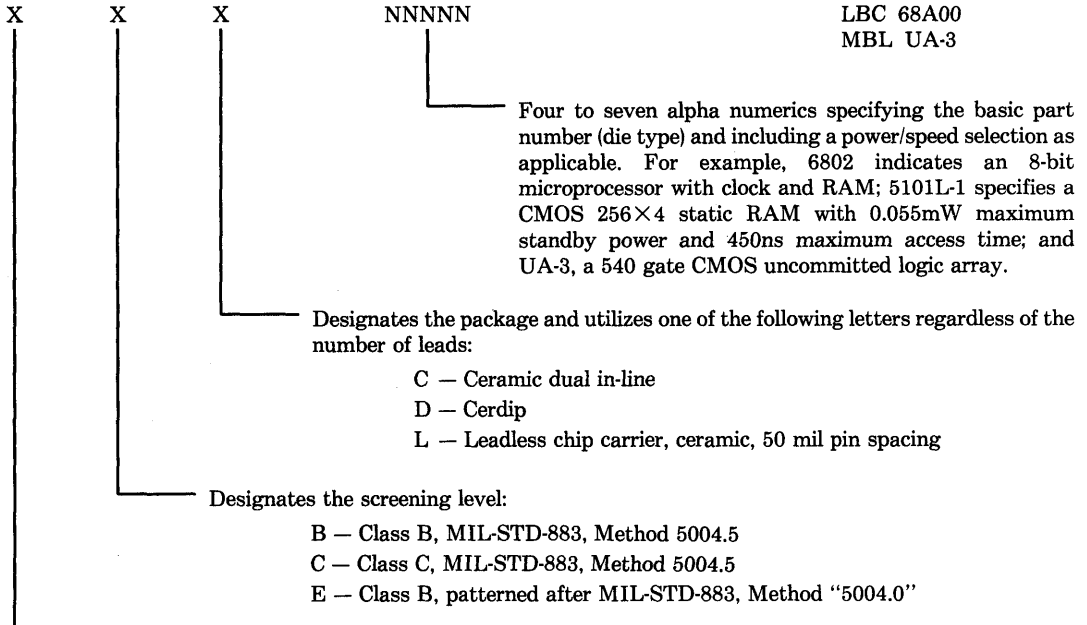D — Cerdip package

C — Ceramic (three-layer) package

Microprocessor/Microcomputer Development Support:

Consult your local sales office.

Custom Circuits:

Consult your local sales office.

Military Products:

Parts Numbering Format

X   X   X   NNNNN

Four to seven alpha numerics specifying the basic part number (die type) and including a power/speed selection as applicable. For example, 6802 indicates an 8-bit microprocessor with clock and RAM; 5101L-1 specifies a CMOS 256×4 static RAM with 0.055mW maximum standby power and 450ns maximum access time; and UA-3, a 540 gate CMOS uncommitted logic array.

Designates the package and utilizes one of the following letters regardless of the number of leads:

        C — Ceramic dual in-line
        D — Cerdip
        L — Leadless chip carrier, ceramic, 50 mil pin spacing

Designates the screening level:

        B — Class B, MIL-STD-883, Method 5004.5
        C — Class C, MIL-STD-883, Method 5004.5
        E — Class B, patterned after MIL-STD-883, Method "5004.0"

Designates the operating temperature range and utilizes one of the letters M or L. Definitions:

        M—Full military temperature range, −55°C to +125°C
        L —Limited military temperature range, −55°C to +85°C

Ordering Information

Please specify part numbers in accordance with the parts numbering format above.

1. **ACCEPTANCE:** THE TERMS OF SALE CONTAINED HEREIN APPLY TO ALL QUOTATIONS MADE AND PURCHASE ORDERS ENTERED INTO BY THE SELLER. SOME OF THE TERMS SET OUT HERE MAY DIFFER FROM THOSE IN BUYER'S PURCHASE ORDER AND SOME MAY BE NEW. THIS ACCEPTANCE IS CONDITIONAL ON BUYER'S ASSENT TO THE TERMS SET OUT HERE IN LIEU OF THOSE IN BUYER'S PURCHASE ORDER. SELLER'S FAILURE TO OBJECT TO PROVISIONS CONTAINED IN ANY COMMUNICATION FROM BUYER SHALL NOT BE DEEMED A WAIVER OF THE PROVISIONS OF THIS ACCEPTANCE. ANY CHANGES IN THE TERMS CONTAINED HEREIN MUST SPECIFICALLY BE AGREED TO IN WRITING BY AN OFFICER OF THE SELLER BEFORE BECOMING BINDING ON EITHER THE SELLER OR THE BUYER. All orders or contracts must be approved and accepted by the Seller at its home office. These terms shall be applicable whether or not they are attached to or enclosed with the products to be sold or sold hereunder. Prices for the items described above and acknowledged hereby are firm and not subject to audit, price revision, or price redetermination.

2. **PAYMENT:**
    (a) Unless otherwise agreed, all invoices are due and payable thirty (30) days from date of invoice. No discounts are authorized. Shipments, deliveries, and performance of work shall at all times be subject to the approval of the Seller's credit department and the Seller may at any time decline to make any shipments or deliveries or perform any work except upon receipt of payment or upon terms and conditions or security satisfactory to such department.
    (b) If, in the judgment of the Seller, the financial condition of the Buyer at any time does not justify continuation of production or shipment on the terms of payment originally specified, the Seller may require full or partial payment in advance and, in the event of the bankruptcy or insolvency of the Buyer or in the event any proceeding is brought by or against the Buyer under the bankruptcy or insolvency laws, the Seller shall be entitled to cancel any order then outstanding and shall receive reimbursement for its cancellation charges.
    (c) Each shipment shall be considered a separate and independent transaction, and payment therefor shall be made accordingly. If shipments are delayed by the Buyer, payments shall become due on the date when the Seller is prepared to make shipment. If the work covered by the purchase order is delayed by the Buyer, payments shall be made based on the purchase price and the percentage of completion. Products held for the Buyer shall be at the risk and expense of the Buyer.

3. **TAXES:** Unless otherwise provided herein, the amount of any present or future sales, revenue, excise or other taxes, fees, or other charges of any nature, imposed by any public authority, (national, state, local or other) applicable to the products covered by this order, or the manufacturer or sale thereof, shall be added to the purchase price and shall be paid by the Buyer, or in lieu thereof, the Buyer shall provide the Seller with a tax exemption certificate acceptable to the taxing authority.

4. **F.O.B. POINT:** All sales are made F.O.B. point of shipment. Seller's title passes to Buyer, and Seller's liability as to delivery ceases upon making delivery of material purchased hereunder to carrier at shipping point, the carrier acting as Buyer's agent. All claims for damages must be filed with the carrier. Shipments will normally be made by Parcel Post, Railway Express, Air Express, or Air Freight. Unless specific instructions from Buyer specify which of the foregoing methods of shipment is to be used, the Seller will exercise his own discretion.

5. **DELIVERY:** Shipping dates are approximate and are based upon prompt receipt from Buyer of all necessary information. In no event will Seller be liable for any re-procurement costs, nor for delay or non-delivery, due to causes beyond its reasonable control including, but not limited to, acts of God, acts of civil or military authority, priorities, fires, strikes, lock-outs, slow-downs, shortages, factory or labor conditions, errors in manufacture, and inability due to causes beyond the Seller's reasonable control to obtain necessary labor, materials, or manufacturing facilities. In the event of any such delay, the date of delivery shall, at the request of the Seller, be deferred for a period equal to the time lost by reason of the delay.

    In the event Seller's production is curtailed for any of the above reasons so that Seller cannot deliver the full amount released hereunder, Seller may allocate production deliveries among its various customers then under contract for similar goods. The allocation will be made in a commercially fair and reasonable manner. When allocation has been made, Buyer will be notified of the estimated quota made available.

6. **PATENTS:** The Buyer shall hold the Seller harmless against any expense or loss resulting from infringement of patents, trademarks, or unfair competition arising from compliance with Buyer's designs, specifications, or instructions. The sale of products by the Seller does not convey any license, by implication, estoppel or otherwise, under patent claims covering combinations of said products with other devices or elements.·

    Except as otherwise provided in the preceding paragraph, the Seller shall defend any suit or proceeding brought against the Buyer, so far as based on a claim that any product, or any part thereof, furnished under this contract constitutes an infringement of any patent of the United States, if notified promptly in writing and given authority, information, and assistance (at the Seller's expense) for defense of same, and the Seller shall pay all damages and costs awarded therein against the Buyer. In case said product, or any part thereof, is, in such suit, held to constitute infringement of patent, and the use of said product is enjoined, the Seller shall, at its own expense, either procure for the Buyer the right to continue using said product or part, replace same with non-infringing product, modify it so it becomes non-infringing, or remove said product and refund the purchase price and the transportation and installation costs thereof. In no event shall Seller's total liability to the Buyer under or as a result of compliance with the provisions of this paragraph exceed the aggregate sum paid by the Buyer for the allegedly infringing product. The foregoing states the entire liability of the Seller for patent infringement by the said products or any part thereof. THIS

PROVISION IS STATED IN LIEU OF ANY OTHER EXPRESSED, IMPLIED, OR STATUTORY WARRANTY AGAINST INFRINGEMENT AND SHALL BE THE SOLE AND EXCLUSIVE REMEDY FOR PATENT INFRINGEMENT OF ANY KIND.

7. **INSPECTION:** Unless otherwise specified and agreed upon, the material to be furnished under this order shall be subject to the Seller's standard inspection at the place of manufacture. If it has been agreed upon and specified in this order that Buyer is to inspect or provide for inspection at place of manufacture such inspection shall be so conducted as to not interfere unreasonably with Seller's operations and consequent approval or rejection shall be made before shipment of the material. Notwithstanding the foregoing, if, upon receipt of such material by Buyer, the same shall appear not to conform to the contract, the Buyer shall immediately notify the Seller of such conditions and afford the Seller a reasonable opportunity to inspect the material. No material shall be returned without Seller's consent. Seller's Return Material Authorization form must accompany such returned material.

8. **WARRANTY:** The Seller warrants that the products to be delivered under this purchase order will be free from defects in material and workmanship under normal use and service. Seller's obligations under this Warranty are limited to replacing or repairing or giving credit for, at its option, at its factory, any of said products which shall, within one (1) year after shipment, be returned to the Seller's factory of origin, transportation charges prepaid, and which are, after examination, disclosed to the Seller's satisfaction to be thus defective. THIS WARRANTY IS EXPRESSED IN LIEU OF ALL OTHER WARRANTIES, EXPRESSED, STATUTORY, OR IMPLIED, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE, AND OF ALL OTHER OBLIGATIONS OR LIABILITIES ON THE SELLER'S PART, AND IT NEITHER ASSUMES NOR AUTHORIZES ANY OTHER PERSON TO ASSUME FOR THE SELLER ANY OTHER LIABILITIES IN CONNECTION WITH THE SALE OF THE SAID ARTICLES. This Warranty shall not apply to any of such products which shall have been repaired or altered, except by the Seller, or which shall have been subjected to misuse, negligence, or accident. The aforementioned provisions do not extend the original warranty period of any product which has either been repaired or replaced by Seller.

    It is understood that if this order calls for the delivery of semiconductor devices which are not finished and fully encapsulated, that no warranty, statutory, expressed or implied, including the implied warranty of merchantability and fitness for a particular purpose, shall apply. All such devices are sold as is where is.

9. **GENERAL:**
    (a) The validity, performance and construction of these terms and all sales hereunder shall be governed by the laws of the State of California.
    (b) The Seller represents that with respect to the production of articles and/or performance of the services covered by this order it will fully comply with all requirements of the Fair Labor Standards Act of 1938, as amended, Williams-Steiger Occupational Safety and Health Act of 1970, Executive Orders 11375 and 11246, Section 202 and 204.
    (c) In no event shall Seller be liable for consequential or special damages.
    (d) The Buyer may not unilaterally make changes in the drawings, designs or specifications for the items to be furnished hereunder without Seller's prior consent.
    (e) Except to the extent provided in Paragraph 10, below, this order is not subject to cancellation or termination for convenience.
    (f) Buyer acknowledges that all or part of the products purchased hereunder may be manufactured and/or assembled at any of Seller's facilities, domestic or foreign.
    (g) In the event that the cost of the products are increased as a result of increases in materials, labor costs, or duties, Seller may raise the price of the products to cover the cost increases.
    (h) If Buyer is in breach of its obligations under this order, Buyer shall remain liable for all unpaid charges and sums due to Seller and will reimburse Seller for all damages suffered or incurred by Seller as a result of Buyer's breach. The remedies provided herein shall be in addition to all other legal means and remedies available to Seller.

10. **GOVERNMENT CONTRACT PROVISIONS:** If Buyer's original purchase order indicates by contract number, that it is placed under a government contract, only the following provisions of the current Armed Services Procurement Regulation are applicable in accordance with the terms thereof, with an appropriate substitution of parties, as the case may be — i.e., "Contracting Officer" shall mean "Buyer", "Contractor" shall mean "Seller", and the term "Contract" shall mean this order:

    > 7-103.1, Definitions; 7-103.3, Extras; 7-103.4, Variation in Quantity; 7-103.8, Assignment of Claims; 7-103.9, Additional Bond Security; 7-103.13, Renegotiation; 7-103.15, Rhodesia and Certain Communist Areas; 7-103.16, Contract Work Hours and Safety Standards Act — Overtime Compensation; 7-103.17, Walsh-Healey Public Contracts Act; 7-103.18, Equal Opportunity Clause; 7-103.19, Officials Not to Benefit; 7-103.20, Covenant Against Contingent Fees; 7-103.21, Termination for Convenience of the Government (only to the extent that Buyer's contract is terminated for the convenience of the government); 7-103.22, Authorization and Consent; 7-103.23, Notice and Assistance Regarding Patent Infringement; 7-103.24, Responsibility for Inspection; 7-103.25, Commercial Bills of Lading Covering Shipments Under FOB Origin Contracts; 7-103.27, Listing of Employment Openings; 7-104.4, Notice to the Government of Labor Disputes; 7-104.11, Excess Profit; 7-104.15, Examination of Records by Comptroller General; 7-104.20, Utilization of Labor Surplus Area Concerns.

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